# applied surface science

A journal devoted to the properties of interfaces in relation to the synthesis and behaviour of materials

**Editors**:

L.C. Feldman, Murray Hill, NJ, USA W.F. van der Weg, Utrecht, The Netherlands

**MASTER INDEX** 

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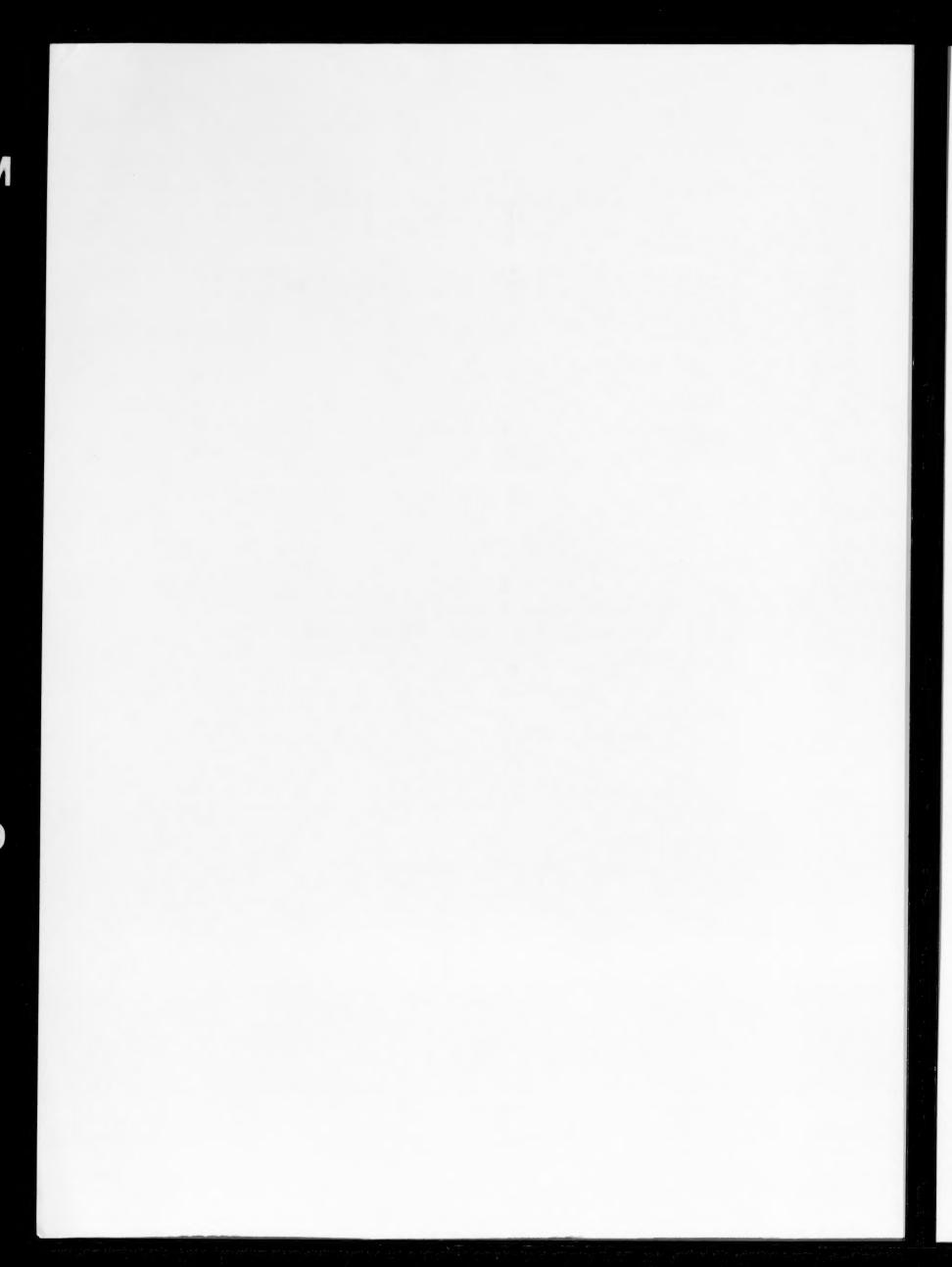
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### APPLIED SURFACE SCIENCE



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Master Index to Volumes 41-50



NORTH-HOLLAND

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## **MASTER INDEX**

Volumes 41-50

Author index	1
Subject index	36
List of terms used in the subject index	134



# Author index to volumes 41-50

Aarnink, W.A.M., A. Weishaupt and A.		angular dependent XPS and reactivity	
van Silfhout, Angle-resolved X-ray		study	44 (1990) 49
photoelectron spectroscopy (ARXPS)		Akimoto, K., J. Mizuki, I. Hirosawa and	
and a modified Levenberg-Marquardt		J. Matsui, Interfacial superstructures	
fit procedure: a new combination for		studied by grazing incidence X-ray	
modeling thin layers	45 (1990) 37	diffraction	41/42 (1989) 317
Aarnink, W.A.M., see Gao	46 (1990) 74	Akimoto, K., see Fujieda	41/42 (1989) 516
Aarnink, W.A.M., D.H.A. Blank, D.J.		Akimoto, M., see Gekka	41/42 (1989) 184
Adelerhof, J. Flokstra, H. Rogalla, A.		Akiyama, K., see Takayanagi	41/42 (1989) 337
van Silfhout and R. de Reus, Interdif-		Akiyama, M., see Horikawa	41/42 (1989) 598
fusion studies on high- $T_c$ supercon-		Allen, J.T., see Pemble	46 (1990) 32
ducting YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-8</sub> thin films on		Alnot, P., see Barrière	41/42 (1989) 383
Si(111) with a NiSi <sub>2</sub> /ZrO <sub>2</sub> buffer layer	47 (1991) 195	Amarger, V., C. Dubon-Chevallier, A.C.	
Abdesselam, M., see Chibani	50 (1991) 177	Papadopoulo, B. Descouts and Y. Gao,	
Abe, Y., see Hasegawa	41/42 (1989) 372	Correlated use of characterization	
Abel, F., C. Cohen, J.A. Davies, J. Moulin		techniques to optimize the Mg implan-	
and D. Schmaus, Thin-film growth of		tation annealing for self-aligned HBT's	50 (1991) 462
Sn on Cu(100)	44 (1990) 17	Ameen, M.S., see Krauss	46 (1990) 67
Abstreiter, G., Micro-Raman spectrosco-		Ammerlaan, C.A.J., see Heijmink Liesert	50 (1991) 245
py for characterization of semiconduc-		Ammerlaan, C.A.J., see Van Gisbergen	50 (1991) 273
tor devices	50 (1991) 73	Amouroux, A., see Ermolieff	48/49 (1991) 178
Abukawa, T., see Kono	41/42 (1989) 75	Andersen, LU.A. and J. Bøttiger, Crys-	
Adachi, G., see Arakawa	41/42 (1989) 212	tallization of Fe-Zr metallic glasses	
Adams, P.M., see Moss	50 (1991) 337	during ion irradiation	46 (1990) 427
Adelerhof, D.J., see Aarnink	47 (1991) 195	Anderson, F.G., see O'Connor	50 (1991) 312
Adriaenssens, G.J., see Usala	50 (1991) 265	Anderson, G.B., see Epler	43 (1989) 432
Afonso, C.N., J. Solis and F. Catalina,		Anderson, M.A., see Woolf	50 (1991) 445
Time-resolved optical measurements		Anderson, T., see Deneuville	50 (1991) 308
of laser melting and rapid solidifica-		Andersson, S.L.T. and J.C. Otamiri,	
tion on GeAl films	43 (1989) 171	Surface and bulk composition of	
Afonso, C.N., R. Serna, F. Catalina and		$YBa_2Cu_3O_{6+x}$ compounds studied by	
D. Bermejo, Good-quality Ge films		XPS	45 (1990) 1
grown by excimer laser deposition	46 (1990) 249	Andriamanantenasoa, I., see Sébenne	41/42 (1989) 352
Afonso, C.N., see Solis	46 (1990) 383	Antolini, A. and C. Lamberti, Computing	
Afonso, C.N., see Serna	46 (1990) 405	errors in Fourier transform photo-	
Agafonov, A.I. and T.M. Makhviladze,		luminescence	50 (1991) 212
Mechanisms of photon-stimulated de-		Aono, M., see King	48/49 (1991) 246
sorption and chemisorption of atomic		Aoyama, T., T. Sugi and T. Ito, De-	
particles on the surfaces of semicon-		termination of band line-up in $\beta$ -	
ductors and metals	46 (1990) 288	SiC/Si heterojunction for Si-HBT's	41/42 (1989) 584
Ajioka, T., see Itoh	41/42 (1989) 262	Arai, T., see Kawadzu	41/42 (1989) 296
Akaida, Y., see Gekka	41/42 (1989) 184	Arakawa, T., H. Baba and G. Adachi,	
Akashi, K., see Yumoto	48/49 (1991) 173	Deep level transient spectroscopic	
Akatsu, H. and I. Ohdomari, HRTEM		studies of the perovskite oxides as gas	
observation of the Si/SiO <sub>2</sub> interface	41/42 (1989) 357	sensor material	41/42 (1989) 212
Akhter, S., K.C. Cannon and J.M. White,		Ardelean, I., see Gao	50 (1991) 131
Distribution of compositional defects		Arienzo, M., S.S. Iyer, B.S. Meyerson,	
in solvent cast polyvinyl alcohol films:		G.L. Patton and J.M.C. Stork, Si-Ge	

alloys: growth, properties and applica- tions	48/49 (1991) 377	The interaction of NO, O <sub>2</sub> and CO with Cu(100) and Cu(110)	47 (1991) 341
Arnold, G.S., see Hills	47 (1991) 77	Baller, T.S. and J. Dieleman, Nanosecond	
As, D.J., see Wang	50 (1991) 228	excimer laser-enhanced chemical etch-	42 (1090) 400
Asakura, H., see Ohnishi	50 (1991) 233	ing	43 (1989) 409
Asano, S., see Fujitani	41/42 (1989) 164	Baller, T.S., J.C.S. Kools and J. Dieleman,	
Ashenford, D., J.H.C. Hogg, B. Lunn and		Surface temperature measurements	
C.G. Scott, The relationship between		using pyrometry during excimer laser	
electrical and structural characteristics		pulsed etching of silicon in a Cl <sub>2</sub> en- vironment	46 (1990) 292
of CdTe and CdMnTe layers grown	50 (1001) 440		46 (1990) 292
on InSb	50 (1991) 440	Ballutaud, D., P. de Mierry, M. Aucou-	
Ashida, M., see Yano	41/42 (1989) 457	turier and E. Darque-Ceretti, In-	
Ashok, S., see Kar	48/49 (1991) 264	fluence of thermal treatments on the	
Ashu, P. and C.C. Matthai, A molecular		distribution of contaminating copper	
dynamics study of the critical thick-	49 /40 /1001) 30	near the surface of silicon: a compara- tive SIMS and XPS study	47 (1991) 1
ness of Ge layers on Si substrates	48/49 (1991) 39 50 (1991) 103	Baltrus, J.P. and A. Proctor, Composition	47 (1991) 1
Astles, M.G., see Keir Atkinson, A., see Jain	48/49 (1991) 387	of overlayers on oxidized pyrite sur-	
		faces	44 (1000) 147
Ausialla O and Krausa	46 (1990) 78		44 (1990) 147
Auciello, O., see Krauss	46 (1990) 67	Baltrus, J.P., see Khan	47 (1991) 355
Augusturier, M., see Ballutaud	47 (1991) 1	Balvinskii, O.E., see Shapoval	45 (1990) 257
Aumayr, F., G. Lakits and H. Winter, On		Banerjee, P.K., J.S. Kim and S.S. Mitra,	
the measurement of statistics for par- ticle-induced electron emission from a		Electrical and optical properties of a-	
	47 (1001) 120	luminum-doped amorphous silicon carbide films	40 /40 /1001) 200
clean metal surface	47 (1991) 139		48/49 (1991) 288
Auret, F.D., see Bredell	50 (1991) 466	Banerjee, P.K., see Kim	48/49 (1991) 548
Austin, R.F., see Donegan	50 (1991) 321	Banse, B.A., see Kelber	44 (1990) 193
Auvert, G., Kinetics and mechanisms of		Baraldi, A., C. Ghezzi, A. Parisini, A.	
CW laser induced deposition of metals for microelectronics	42 (1090) 47	Bosacchi and S. Franchi, Analysis of	
	43 (1989) 47	electron mobility versus temperature	
Auvray, P., A. Poudoulec, M. Baudet, B.		after photoexcitation in Si-doped	50 (1001) 405
Guenais, A. Regreny, C. d'Anterroches and J. Massies, Interface		Al <sub>x</sub> Ga <sub>1-x</sub> As	50 (1991) 405
roughness of GaAs/AlAs super-		Baranovskii, S.D., Theoretical basis for the quantitative characterization of	
lattices MBE-grown on vicinal sur-		impurities in n-type III-V compound	
faces	50 (1991) 109	semiconductors by photoelectromag-	
Ayyub, P., see Deneuville	50 (1991) 308	netic spectroscopy	50 (1991) 218
Ayyuo, F., see Deneuvine	30 (1991) 300	Barba, M.F., see Fariñas	50 (1991) 202
		Barfknecht, A.T., see Bernhardt	46 (1990) 121
Baba, H., see Arakawa	41/42 (1989) 212	Barnard, W.O., see Bredell	
Bachmann, F.G., see Woratschek	43 (1989) 264	Barnett, S.J., see Keir	50 (1991) 466
Bachmann, F.G., Industrial laser applica-	43 (1909) 204	Barnett, S.J., see Lee	50 (1991) 103 50 (1991) 428
tions	46 (1990) 254	Baró, A.M., see Gómez-Rodríguez	44 (1990) 185
Baer, D.R., R.L. Gordon and C.W. Hub-	40 (1990) 234	Barr, T., see Krauss	46 (1990) 67
bard, Work function and UPS study		Barrière, A.S., G. Couturier, H. Guegan,	40 (1990) 07
of Au and O on Re	45 (1990) 71	T. Séguelong, A. Thabti, P. Alnot and	
Baerends, E.J., see Van den Hoek	41/42 (1989) 236	J. Chazelas, Interface GaAs – gallium	
Bahners, T., see Kesting	46 (1990) 326	fluoride thin film grown by fluorin-	
Bairamov, B.H., V.A. Voitenko, I.P.	40 (1990) 320	ation. Electrical behaviour of the ob-	
Ipatova, V.V. Toporov, G. Irmer, J.		tained MIS fluorinated GaAs struc-	
Monecke and E. Jahne, Characteriza-		tures	41/42 (1989) 383
tion of III-V compounds by quasi-		Barteau, M.A., see Peng	44 (1990) 87
elastic electronic scattering of light	50 (1991) 300	Bartlett, R., H. Jaeger, B.A. Sexton, R.P.	TT (1770) 07
Baker, S.D., see Milne	43 (1989) 277	Netterfield and P.J. Martin, A scan-	
Bała, W., see Bukaluk	45 (1990) 57	ning tunnelling and transmission elec-	
Balkanski, M., see Julien	48/49 (1991) 1	tron microscopy comparison of the	
Balkenende, A.R., H. den Daas, M. Huis-	. ()	surface structure of evaporated and	
man, O.L.J. Gijzeman and J.W. Geus,		ion-assisted gold films	47 (1991) 187
,		0000	(2772) 107

Bartsch, H., see Voelskow	43 (1989) 196	Si <sub>1-x</sub> Ge <sub>x</sub> /Si layers produced by Ge	
Bastl, Z., see Ptáček	45 (1990) 319	ion implantation	43 (1989) 158
Baudet, M., see Auvray	50 (1991) 109	Besland, M.P., see Tardy	50 (1991) 383
Bauer, A., J. Ganz, K. Hesse and E.	00 (1771) 107	Besson, M., see Strasser	50 (1991) 261
Köhler, Laser-assisted deposition for		Bevk, J., see Ourmazd	41/42 (1989) 365
electronic packaging applications	46 (1990) 113	Bharathi, S., V. Yegnaraman and G.	11/ 12 (1505) 500
Bauer, J.G., R. Treichler, T. Hillmer, J.	(2,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	Prabhakara Rao, Alloy formation in	
Müller and G. Ebbinghaus, Optimiza-		the monolayers of underpotentially	
tion of Zn dopant profiles in a pin-di-		deposited lead and thallium	47 (1991) 293
ode/FET by combination of depth		Bhardwaj, P., O.J. Gregory, K. Bragga	(====) ===
profiling techniques: a SIMS, ECV		and M.H. Richman, Sputtered TiN	
and AES study	50 (1991) 138	thin films for improved corrosion re-	
Baumgartner, M. and K. Löhnert, Char-		sistance	48/49 (1991) 555
acterization of si-GaAs wafer quality		Bianconi, M., see Nipoti	43 (1989) 321
by room-temperature photolumines-		Biermann, S., see Buerhop	46 (1990) 430
cence	50 (1991) 222	Biglari, B., see Hage-Ali	50 (1991) 377
Baurichter, A., M. Deicher, S. Deubler,		Biliński, B., W. Wójcik and A.L. Dawido-	
D. Forkel, J. Meier, H. Wolf, W. Witt-		wicz, Investigation of the surface free	
huhn and ISOLDE Collaboration, Mi-		energy components of thermally	
croscopical studies at cadmium impur-		treated controlled porosity glasses by	
ities in compound semiconductors	50 (1991) 165	inverse gas chromatography	47 (1991) 99
Bauser, E., see Strasser	50 (1991) 261	Bimberg, D., see Christen	41/42 (1989) 329
Beard, B.C., Cellulose nitrate as a binding	,	Blank, D.H.A., see Aarnink	47 (1991) 195
energy reference in N(1s) XPS studies		Blumenthal, B., see Buerhop	46 (1990) 430
of nitrogen-containing organic mole-		Blunt, R., see Pickering	50 (1991) 346
cules	45 (1990) 221	Boch, E., C. Fuchs, E. Fogarassy and P.	
Beaulieu, R., see Kim	48/49 (1991) 548	Siffert, Influence of dilution in nitro-	
Beauvillain, J., see Claverie	43 (1989) 106	gen on the photodissociation processes	
Bebelaar, D., see Elders	46 (1990) 215	of silane and disilane at 193 nm	43 (1989) 17
Beech, F., see Sajjadi	46 (1990) 84	Bode, M., E.W. Kreutz and M. Krösche,	
Bell, L.D., see Hecht	41/42 (1989) 17	Direct writing of conducting traces by	
Benchiguer, T., E. Christoffel, A. Golt-		chemical modification of solid coat-	
zené, B. Mari, B. Meyer and C.		ings with laser radiation	46 (1990) 148
Schwab, Donor-acceptor charge		Boelle, A., J.A. Roger, B. Canut, J.	7
transfers in bulk semi-insulating GaAs		Mugnier and M. Pitaval, Sol-gel low-	
as revealed by photo-EPR	50 (1991) 277	temperature preparation of silica	
Benck, E.C., Z. Rong, S.H. Chen and		films: RBS, TEM and MOS $C-V$	
H.A. Schuessler, Cavity-enhanced de-		characterization	46 (1990) 200
tection of surface ablation	48/49 (1991) 257	Bogdanski, P., see Mary	43 (1989) 102
Bender, G., see Herres	50 (1991) 97	Boiteux, G., see Davenas	46 (1990) 330
Bensalah, S., see Orlowski	41/42 (1989) 491	Bolle, M., K. Luther, J. Troe, J. Ihlemann	
Bensoussan, M., see Nissim	46 (1990) 175	and H. Gerhardt, Photochemically as-	
Benyattou, T., see Roura	50 (1991) 496	sisted laser ablation of doped poly-	
Berden, W.C.M., see Giardini-Guidoni	46 (1990) 321	methyl-methacrylate	46 (1990) 279
Berger, S., Y. Komem and B.Z. Weiss, On		Bollmann, D., see Pielmeier	46 (1990) 163
the microstructure, composition and		Bollmann, D., see Stock	46 (1990) 348
electrical properties of Al/TiW/poly-		Bollmann, D., see Hu	46 (1990) 388
Si system	48/49 (1991) 281	Bolmont, D., see Haderbache	41/42 (1989) 257
Bermejo, D., see Afonso	46 (1990) 249	Bomchil, G., A. Halimaoui and R. Herino,	
Bernhardt, A.F., A.T. Barfknecht, R.J.		Porous silicon: the material and its	
Contolini, V. Malba, S.T. Mayer, N.F.		applications in silicon-on-insulator	
Raley and D.B. Tuckerman, Multichip		technologies	41/42 (1989) 604
packaging for very-high-speed digital		Bonchik, A.Yu., see Prokhorov	43 (1989) 340
systems	46 (1990) 121	Bonnet, A., see Morsli	50 (1991) 500
Berthier, Y., see Vassilakis	47 (1991) 273	Bonnet, J.E., see Le Lay	41/42 (1989) 25
Berti, M., G. Mazzi, A.V. Drigo, A.		Bonnet-Jobez, S., see Gaffet	43 (1989) 248
Migliori, E. Jannitti and S. Nicoletti,		Booth, J.P., see Raynaud	46 (1990) 435
Laser induced epitaxial regrowth of		Borchardt, G., see Quadakkers	47 (1991) 261

Borensztein, Y., T. Lopez-Rios and G.		of polyimide with IR and UV laser	
Vuye, Roughness induced at Si(111)		radiation	43 (1989) 352
surfaces by high temperature heating	41/42 (1989) 439	Braun, W., see Zahn	41/42 (1989) 179
Borisenko, V.E., see Tokarev	44 (1990) 241	Brec, R., see Morsli	50 (1991) 500
Borondo, F., see López	41/42 (1989) 464	Bredell, L.J., F.D. Auret, G. Myburg and	4
Borsella, E., see Fantoni	43 (1989) 308	W.O. Barnard, Electrical characteriza-	
Bosacchi, A., see Ghezzi	50 (1991) 400	tion of argon-ion sputtered n-GaAs	50 (1991) 466
Bosacchi, A., see Baraldi	50 (1991) 405	Breivik, L., see Brozel	50 (1991) 475
Bostanjoglo, O. and P. Thomsen-Schmidt,		Bremond, G., see Hizem	50 (1991) 490
Laser-induced multiple phase transi-		Bremond, G., see Roura	50 (1991) 496
tions in Ge-Te films traced by time-		Breuer, J., S. Metev, G. Sepold, OD.	
resolved TEM	43 (1989) 136	Hennemann, H. Kollek and G. Krüger,	
Bostanjoglo, O. and P. Thomsen-Schmidt,		Laser-induced photochemical adher-	
Time-resolved TEM of laser-induced		ence enhancement	46 (1990) 336
structural changes in GeTe films	46 (1990) 392	Bringans, R.D., see Epler	43 (1989) 432
Bøttiger, J., see Andersen	46 (1990) 427	Brockmeyer, A., see Priggemeyer	44 (1990) 255
Bou, M., J.M. Martin, Th. Le Mogne and		Brongersma, H.H., see Roosenbrand	44 (1990) 121
L. Vovelle, Chemistry of the interface		Broussoux, D., see Davenas	46 (1990) 330
between aluminium and polyethylene-		Brown, M., M. Shiloh, R.B. Jackman and	, ,
terephthalate by XPS	47 (1991) 149	I.W. Boyd, Geometric optimisation for	
Boudart, B., B. Prévot and C. Schwab,		the deposition of high temperature su-	
Free-carrier concentration in n-doped		perconductors	43 (1989) 382
InP crystals determined by Raman		Browne, V.M., A.F. Carley, R.G. Cop-	
scattering measurements	50 (1991) 295	perthwaite, P.R. Davies, E.M. Moser	
Boulmer, J., B. Bourguignon, J.P. Budin	, , , ,	and M.W. Roberts, Activation of	
and D. Debarre, Time of flight study		carbon dioxide at bismuth, gold and	
of low pressure laser etching of silicon		copper surfaces	47 (1991) 375
by chlorine	43 (1989) 424	Brozel, M.R., see Tüzemen	50 (1991) 395
Boulmer-Leborgne, C., see Hermann	46 (1990) 315	Brozel, M.R., L. Breivik, D.J. Stirland,	
Bourdon, E.B.D. and R.H. Prince, Growth		G.M. Williams and A.G. Cullis, Dislo-	
mechanisms of diamond-like films		cation density, infrared absorption and	
formed by laser ablation of graphite	48/49 (1991) 50	cathodoluminescence mapping of mi-	
Bourguignon, B., see Boulmer	43 (1989) 424	crostructure associated with disloca-	
Bowker, M. and D. Halstead, Adsorption		tion cells in semi-insulating LEC GaAs	50 (1991) 475
studies on catalysts. II. Application to		Buchmann, P., see Marclay	43 (1989) 43
rapid adsorbers - oxygen on Euro-		Buchner, R., see Stock	46 (1990) 348
platinum 1	44 (1990) 1	Buchner, R., see Hu	46 (1990) 388
Bowman, Jr., R.C., see Moss	50 (1991) 337	Buck, M. and P. Hess, Ablation of ben-	, , ,
Boyd, I.W., see Brown	43 (1989) 382	zene from van der Waals films with	
Boyd, I.W., see Tyrrell	43 (1989) 439	excimer laser pulses at 248 nm	43 (1989) 358
Boyd, I.W., see Sajjadi	46 (1990) 84	Budin, J.P., see Boulmer	43 (1989) 424
Boyd, I.W., see Patel	46 (1990) 352	Buerhop, C., B. Blumenthal, R. Weiss-	, ,
Brádler, J., see Lejček	44 (1990) 75	mann, N. Lutz and S. Biermann, Glass	
Bradley, D.C., New metallo-organic pre-		surface treatment with excimer and	
cursors for surface processing	46 (1990) 1	CO <sub>2</sub> lasers	46 (1990) 430
Bradshaw, A.M., see Radhakrishnan	46 (1990) 36	Bugiel, E., see Richter	44 (1990) 127
Bragga, K., see Bhardwaj	48/49 (1991) 555	Buhaenko, D.S., see Pemble	46 (1990) 32
Braichotte, D., see Garrido	43 (1989) 68	Bukaluk, A. and W. Bała, AES depth	
Braichotte, D., C. Garrido and H. van		profile studies of interdiffusion in thin	
den Bergh, The photolytic laser chem-		polycrystalline Au-Ag multilayer	
ical vapor deposition rate of platinum,		films	45 (1990) 57
its dependence on wavelength, pre-		Bureau, J.M., see Davenas	46 (1990) 330
cursor vapor pressure, light intensity,		Burkhard, H., see Dinges	50 (1991) 359
and laser beam diameter	46 (1990) 9	Buschick, K., see Müller	46 (1990) 143
Brandstättner, M., see Sartorius	50 (1991) 369	Busmann, HG., see Ulmer	46 (1990) 272
Brase, B., see Heidberg	46 (1990) 44	Busquet, C.C.A., see Van Zwol	43 (1989) 363
Braun, R., R. Nowak, P. Hess, H. Oetz-			
mann and C. Schmidt, Photoablation		Cabrera, M., see Zouari	46 (1990) 411

Caillard D. saa Lavada	50 (1991) 119	Chapeaublanc, JF., see Petitjean	46 (1990) 189
Caillard, D., see Levade Calcagno, L., see Compagnini	43 (1989) 228	Charatan, R.M., see Williams	41/42 (1989) 70
Callec, R., see L'Haridon	50 (1991) 237	Chartier, J.L., A. Serrari, R. Le Bihan, M.	41/42 (1909) 70
Calvo, M., see Zouari	46 (1990) 411	Ligeon, F. Gaspard and F. Muller,	
Campbell, E.E.B., G. Ulmer, B. Hassel-	40 (1990) 411	Thermal nitridation of anodic silicon	
berger and I.V. Hertel, Investigation		dioxide	45 (1990) 351
of positive and negative ionic products		Chazelas, J., see Barrière	41/42 (1989) 383
from laser ablation of polymers	43 (1989) 346	Cheenne, A., see Roulet	47 (1991) 173
Campbell, E.E.B., see Ulmer	46 (1990) 272	Chen, B.L., M. Eckstein and HU.	47 (1771) 173
Campisano, S.U., see Priolo	41/42 (1989) 619	Habermeier, Cathodoluminescence in-	
Campisano, S.U., see Spinella	43 (1989) 187	vestigations of RIE-induced defects in	
Canale, A.J., see Kulkarni	48/49 (1991) 307	InP	50 (1991) 191
Cannon, K.C., see Akhter	44 (1990) 49	Chen Guangxi, see Zhang Rong	48/49 (1991) 356
Canteri, R., see Nipoti	43 (1989) 321	Chen, P., see Ding	41/42 (1989) 123
Canut, B., see Boelle	46 (1990) 200	Chen, S.H., see Schuessler	48/49 (1991) 254
Cao, R., see Spicer	41/42 (1989) 1	Chen, S.H., see Benck	48/49 (1991) 257
Cardinaud, Ch. and G. Turban, Mecha-	41/42 (1707)	Cheng, C.C., see Wallace	45 (1990) 201
nistic studies of the initial stages of		Cherief, N., R. Cinti, M. De Crescenzi, J.	15 (1550) 201
etching of Si and SiO <sub>2</sub> in a CHF <sub>3</sub>		Derrien, T.A. Nguyen Tan and J.Y.	
plasma	45 (1990) 109	Veuillen, Heteroepitaxy of metallic	
Carey, P.G., see Woratschek	43 (1989) 264	and semiconducting silicides on sili-	
Carey, P.G. and T.W. Sigmon, In-situ	10 (1707) 20 .	con	41/42 (1989) 241
doping of silicon using the gas immer-		Chernov, A.A., see Ukraintsev	48/49 (1991) 151
sion laser doping (GILD) process	43 (1989) 325	Chernov, A.A., see Ukraintsev	48/49 (1991) 198
Carles, R., see Raisin	50 (1991) 434	Chevarier, A., N. Chevarier, M. El	, ()
Carley, A.F., see Browne	47 (1991) 375	Bouanani, E. Gerlic, M. Stern, B. Roux	
Cartier, C., see Roulet	47 (1991) 173	and F. Thimon, Profiling of carbon,	
Castaldini, A., A. Cavallini, E. Gombia,	()	oxygen and argon contamination in	
R. Mosca and L. Tarricone, Evalua-		sputter-deposited films using nuclear	
tion of the diffusion length of minor-		backscattering and nuclear reaction	
ity carriers in bulk GaAs	50 (1991) 485	spectroscopy	48/49 (1991) 215
Catalina, F., see Afonso	43 (1989) 171	Chevarier, N., see Chevarier	48/49 (1991) 215
Catalina, F., see Afonso	46 (1990) 249	Chevy, A., see Mari	50 (1991) 415
Catalina, F., see Solis	46 (1990) 383	Chibani, H., J.P. Stoquert, M. Hage-Ali,	
Catalina, F., see Serna	46 (1990) 405	J.M. Koebel, M. Abdesselam and P.	
Catherinot, A., see Girault	46 (1990) 78	Siffert, Carbon analysis in CdTe by	
Caudano, R., see Sporken	41/42 (1989) 201	nuclear activation	50 (1991) 177
Caudano, R., see Petit	43 (1989) 285	Cho, G.C., see Kütt	50 (1991) 325
Caudano, R., see Petit	46 (1990) 357	Choyke, W.J., see Wallace	45 (1990) 201
Cavagnat, R., see Huong	43 (1989) 256	Christen, J., M. Grundmann and D. Bim-	
Cavallini, A., see Castaldini	50 (1991) 485	berg, Direct imaging and theoretical	
Ceccato, R., see Fantoni	43 (1989) 308	modelling of the atomistic morpho-	
Cerva, H., Transmission electron mi-		logical and chemical structure of semi-	
croscopy of heteroepitaxial layer		conductor heterointerfaces	41/42 (1989) 329
structures	50 (1991) 19	Christoffel, E., see Benchiguer	50 (1991) 277
Cerva, H., see Schwarz	50 (1991) 456	Christou, A., see Dimoulas	50 (1991) 353
Cetronio, A., see Nipoti	50 (1991) 410	Chumakov, A.A., see Shapoval	45 (1990) 257
Cháb, V., see Kubátová	43 (1989) 297	Chyan, O.M.R., see Frank	48/49 (1991) 166
Chamberod, A., see Eymery	47 (1991) 127	Cibert, J., see Tatarenko	41/42 (1989) 470
Chami, A.C., see Tatarenko	41/42 (1989) 470	Cimino, R., see Zahn	41/42 (1989) 179
Champeaux, C., see Girault	46 (1990) 78	Cinti, R., see Cherief	41/42 (1989) 241
Champness, C.H. and W.R. Clark, Anom-		Claassen, W.C.M., R.W.A.H. Schmitz and	
alous inductive effect in Se-metal		J. Dieleman, Influence of surface fluo-	
contacts	48/49 (1991) 337	rination on the oxidation of amor-	
Chang, H.L.M., H. You, J. Guo and D.J.		phous silicon by atomic oxygen at 300	40 (4000)
Lam, Epitaxial TiO <sub>2</sub> and VO <sub>2</sub> films		K	43 (1989) 292
prepared by MOCVD	48/49 (1991) 12	Clark, W.R., see Champness	48/49 (1991) 337

Claverie, A., C. Vieu and J. Beauvillain,		Davenas, J., Influence of the temperature	
3D simulations of ion implantation		on the ion beam induced conductivity	
processes	43 (1989) 106	of polyimide	43 (1989) 218
Clough, F.J., see Milne	43 (1989) 277	Davenas, J., G. Boiteux, J.M. Bureau and	
Cocke, D.L., see Perry	44 (1990) 321	D. Broussoux, Ion-beam-assisted for-	
Cohen, C., see Abel	44 (1990) 17	mation of interconnections into high	
Colavita, E., see Nelson	48/49 (1991) 419	temperature polymers	46 (1990) 330
Compagnini, G., R. Reitano, L. Calcagno,		Davidson, J.L., see Jubber	43 (1989) 74
G. Marletta and G. Foti, Hydro-		Davidson, M.R., see Lee	47 (1991) 91
genated amorphous carbon synthesis		Davies, J.A., see Abel	44 (1990) 17
by ion beam irradiation	43 (1989) 228	Davies, P.R., see Browne	47 (1991) 375
Conan, A., see Morsli	50 (1991) 500	Dawidowicz, A.L., see Biliński	47 (1991) 99
Conrad, H., see Radhakrishnan	46 (1990) 36	De Crescenzi, M., see Cherief	41/42 (1989) 241
Consalvo, D., see Mele	43 (1989) 398	De Figueiredo, S.K. and A.C. Ferraz, In-	
Contolini, R.J., see Bernhardt	46 (1990) 121	terface geometry of $(GaAs)_n(InAs)_n$	
Copperthwaite, R.G., see Browne	47 (1991) 375	and $(GaP)_n(InP)_n$ ultra-thin super-	
Coquille, R., see L'Haridon	50 (1991) 237	lattices	41/42 (1989) 509
Cornelio, P.A., see Heens	47 (1991) 163	De González, C.O. and E.A. García, De-	
Couderc, J.J., see Levade	50 (1991) 119	termination of the diffusion coeffi-	
Couret, A., see Levade	50 (1991) 119	cients of oxygen in zirconium by	
Couturier, G., see Barrière	41/42 (1989) 383	means of XPS	44 (1990) 211
Craciun, V., G. Leggieri, A. Luches, M.	, , , ,	De las Heras, C., I.J. Ferrer and C.	
Martino, I.N. Mihailescu and I. Ursu,		Sánchez, Comparison of pyrite thin	
Synthesis of metallic and semiconduc-		films obtained from Fe and natural	
tor nitrides by multipulse laser irradia-		pyrite powder	50 (1991) 505
tion of solid samples in ambient gases	43 (1989) 304	De Michele, G., see Curcio	46 (1990) 225
Craciun, V., see Prokhorov	43 (1989) 340	De Mierry, P., see Ballutaud	47 (1991) 1
Craig, Jr., J.H. and J. Lozano, Effect of	( , , , , , , , , , , , , , , , , , , ,	De Potter, M., see Frigeri	50 (1991) 115
oxygen on chemisorption of CO on		De Reus, R., see Aarnink	47 (1991) 195
Rh(100)	45 (1990) 151	De Rossi, S., see Moretti	45 (1990) 341
Craig, Jr., J.H., see Durrer	45 (1990) 275	De Unamuno, S., see Mathé	43 (1989) 142
Crean, G.M., P.A.F. Herbert, I. Little,	15 (1550) 215	De Unamuno, S., see Maillou	43 (1989) 150
W.M. Kelly, J.Y. Marzin, A. Izrael		De Unamuno, S., see Fogarassy	43 (1989) 316
and B. Jusserand, Investigation of re-		De Unamuno, S., see Elliq	46 (1990) 378
active ion etch-induced damage in InP		De Wit, A.R., M.D. Janssen and J.J. Kelly,	10 (1550) 570
surfaces using a noncontact photo-		Electrochemical characterization of	
thermal radiometric probe	50 (1991) 281	polycrystalline ZnO layers	45 (1990) 21
Cros, A., see Marfaing	43 (1989) 165	De Zwart, S.T., see Van Zwol	43 (1989) 363
Crow, M.L., see Pickart	48/49 (1991) 436	Deacon, G.B., see Pain	48/49 (1991) 76
Cullis, A.G., see Brozel	50 (1991) 475	Deane, S.C., see Milne	43 (1989) 277
Curcio, F., M. Musci, N. Notaro and G.	30 (1991) 4/3	Debarre, D., see Boulmer	43 (1989) 424
De Michele, Synthesis of ultrafine		Deckers, S., F.H.P.M. Habraken, W.F.	43 (1707) 424
TiO <sub>2</sub> powders by a CW CO <sub>2</sub> laser	46 (1990) 225	van der Weg, A.W. Denier van der	
Cussenot, J.R., see Easwarakhanthan	47 (1991) 299	Gon, J.F. van der Veen and J.W. Geus,	
Cussenot, J.R., see Laswarakhanthan	47 (1991) 299		
Do Cilvo M.E. coo Corne	46 (1000) 405	Oxidation-induced segregation at the	
Da Silva, M.F., see Serna	46 (1990) 405	Pt <sub>0.5</sub> Ni <sub>0.5</sub> (111) surface studied by	45 (1000) 121
Daley, R.S., see Williams	41/42 (1989) 70	medium-energy ion scattering	45 (1990) 121
Dalins, I., M. Karimi and D. Ila, Violent		Deckers, S., F.H.P.M. Habraken, W.F.	
oxidation of lithium-containing alumi-	40 (40 (1001) 500	van der Weg and J.W. Geus, Oxida-	45 (1000) 207
num alloys in liquid oxygen	48/49 (1991) 509	tion of clean and Pt-covered Ni(111)	45 (1990) 207
Damiani, D., see Girault	46 (1990) 78	Deicher, M., see Pfeiffer	50 (1991) 154
D'Anna, E., G. Leggieri, A. Luches, M.		Deicher, M., see Magerle	50 (1991) 159
Martino, A.V. Drigo, G. Majni, P.		Deicher, M., see Baurichter	50 (1991) 165
Mengucci and I.N. Mihailescu, Nitri-		Delrue, J.P., see Sporken	41/42 (1989) 201
dation of titanium by multipulse ex-	46 (4000) 244	Demchenko, A.I., see Tokarev	44 (1990) 241
cimer laser irradiation	46 (1990) 365	Den Daas, H., see Balkenende	47 (1991) 341
D'Anterroches, C., see Auvray	50 (1991) 109	Deneuville, A., D.B. Tanner, R.M. Park	
Darque-Ceretti, E., see Ballutaud	47 (1991) 1	and P.H. Holloway, Semiconductor	

electrical properties from the frequen-		S.R. Morrison, Spread films of single	
cy dependence of the dielectric con-		molecular transition-metal sulphides	48/49 (1991) 572
stant: application to n-type ZnSe		Domínguez, J.M., see Vázquez	44 (1990) 331
heterepitaxial thin films	50 (1991) 285	Donegan, J.F., J.P. Doran, R.P. Stanley,	11 (1) 0) 331
Deneuville, A., C.H. Park, P. Ayyub, T.	( , , , , , , , , , , , , , , , , , , ,	J. Hegarty, R.D. Feldman and R.F.	
Anderson, P. Lowen, K. Jones and		Austin, Resonant Rayleigh scattering	
P.H. Holloway, O implantation in		from excitons in $Cd_xZn_{1-x}Te:ZnTe$	
ZnSe: lattice distortion by Raman		quantum wells: measurement of ho-	
measurement	50 (1991) 308	mogeneous linewidths	50 (1991) 321
Denier van der Gon, A.W., see Deckers	45 (1990) 121	Dong, G.S., see Ding	41/42 (1989) 123
Derekis, A., see Dimoulas	50 (1991) 353	Doran, J.P., see Donegan	50 (1991) 321
Derrien, J., see Cherief	41/42 (1989) 241	Dötsch, H., see Priggemeyer	44 (1990) 255
Derrien, J., see Nguyen Tan	41/42 (1989) 266	Drigo, A.V., see Berti	43 (1989) 158
Descouts, B., see Amarger	50 (1991) 462	Drigo, A.V., see D'Anna	46 (1990) 365
Desimoni, E., see Giardini-Guidoni	46 (1990) 321	Drouhin, HJ., see Paget	41/42 (1989) 38
Desnica, D.I., B. Šantić and U.V. De-		Dubois, S., see Strasser	50 (1991) 261
snica, Time-evolution of low-tempera-		Dubon-Chevallier, C., see Amarger	50 (1991) 462
ture photoconductivity and Hall mo-		Dubreuil, B., see Hermann	46 (1990) 315
bility in semi-insulating GaAs	50 (1991) 269	Ducros, R. and J. Fusy, Oxygen adsorp-	
Desnica, U.V., see Magerle	50 (1991) 159	tion on Pt(110)(1 $\times$ 2). Surface char-	
Desnica, U.V., see Desnica	50 (1991) 269	acterization by photoemission of ad-	44 (4000) - 50
Desoyer, J.C., see Maillou	43 (1989) 150	sorbed xenon (PAX)	44 (1990) 59
Deubler, S., see Baurichter	50 (1991) 165	Dufour, G., see Roulet	47 (1991) 173
Deutscher, G., see Feldman	48/49 (1991) 535	Dumas, Ph., see Salvan	41/42 (1989) 88
Deveaud, B., Subpicosecond lumines-		Dupendant, H., J.P. Gavigan, D. Givord,	
cence spectroscopy of heterostructures	50 (1001) 62	A. Lienard, J.P. Rebouillat and Y.	
(Extended Abstract)	50 (1991) 63	Souche, Velocity distribution of mi-	
Dharmadasa, I.M., see Williams Di, Y., see Halpern	41/42 (1989) 189 48/49 (1991) 19	cron-size particles in thin film laser ablation deposition (LAD) of metals	
Diarra, A., S. Hotchandani, H. Kassi and	40/49 (1991) 19	and oxide superconductors	43 (1989) 369
R.M. Leblanc, Capacitance character-		Dupuis, V., M.F. Ravet, C. Tête and M.	43 (1707) 307
istics of mixed monolayers of chloro-		Piecuch, Thermal evolution of W/Si	
phyll a and carotenoid canthaxanthin	48/49 (1991) 567	and W/C multilayers under pulsed	
Dickson, R.S., see Pain	48/49 (1991) 76	laser heating and classical annealing	46 (1990) 398
Dieleman, J., see Claassen	43 (1989) 292	Durán, J.C., see Flores	41/42 (1989) 144
Dieleman, J., see Van Zwol	43 (1989) 363	Durand, J., see Gendry	44 (1990) 309
Dieleman, J., see Baller	43 (1989) 409	Durrer, W.G., J.H. Craig, Jr. and J.	()
Dieleman, J., see Baller	46 (1990) 292	Lozano, Surface carbon and its effects	
Dilhac, JM., N. Nolhier and C. Ganibal,		on hydrogen adsorption on Rh(100)	45 (1990) 275
In situ silicon solid state regrowth		Duś, R., see Nowicka	45 (1990) 13
kinetics measurement in a rapid ther-		Duś, R., see Zommer	45 (1990) 93
mal processor	46 (1990) 451	Dwir, B., see James	43 (1989) 393
Dimoulas, A., A. Derekis, G. Kyriakidis		Dyer, P.E., R.D. Greenough, A. Issa and	
and A. Christou, Alloy disorder ef-		P.H. Key, TEA CO <sub>2</sub> laser ablation	
fects in III-V ternaries studied by		studies of Y-Ba-Cu-O	43 (1989) 387
modulation spectroscopy	50 (1991) 353	Dyer, P.E., A. Issa and P.H. Key, An	
Dinan, J.H., see Zahn	41/42 (1989) 497	investigation of laser ablation and de-	
DiNardo, N.J., see Heskett	48/49 (1991) 260	position of Y-Ba-Cu-O in an oxygen	
Ding, M.Q., see Jones	45 (1990) 85	environment	46 (1990) 89
Ding, X.M., G.S. Dong, X.K. Lu, H.Y.			
Xiao, P. Chen and X. Wang, Applica-		Easwarakhanthan, T., Z. Ouennoughi, M.	
tion of HREELS to Al/GaAs and		Renard and J.R. Cussenot, Characteri-	
Al/GaP interfaces	41/42 (1989) 123	zation of double-layer transparent	
Dinges, H.W., B. Kempf, H. Burkhard		films on absorbing substrates using	47 (1001) 200
and R. Göbel, Determination of ion		multiple-angle ellipsometry	47 (1991) 299
beam etching damage on InP by spec-	50 (1001) 250	Ebbinghaus, G., see Bauer	50 (1991) 138
troscopic ellipsometry	50 (1991) 359	Eckstein, M., see Chen	50 (1991) 191
Divigalpitiya, W.M.R., R.F. Frindt and		Eickhoff, T., see Zahn	41/42 (1989) 497

Eitle, J., see Schelz	48/49 (1991) 301	Esser, N., see Zahn	41/42 (1989) 179
El Bouanani, M., see Chevarier	48/49 (1991) 215	Eymery, J., C. Senillou, J.C. Joud and A.	12/ 12 (2505) 215
Elbiache, A. and P. Marcus, Adsorption	, , , ,	Chamberod, An Auger depth profile	
and surface segregation of sulphur on		analysis of a sputtered Fe-Ti multi-	
Fe-17Cr-12.6Ni(100) and Fe-17Cr-		layer structure	47 (1991) 127
14.5Ni-2.3Mo(100) alloys	45 (1990) 49		
Elders, J., D. Bebelaar and J.D.W. van		Fabbri, R., see Nipoti	43 (1989) 321
Voorst, Photochemical vapor deposi-		Falta, J., M. Horn and M. Henzler, SPA-	
tion of titaniumdiboride	46 (1990) 215	LEED studies of defects in thin epi-	
Eleftheriadis, N., HP. Ludescher, M.		taxial NiSi <sub>2</sub> layers on Si(111)	41/42 (1989) 230
Süssbauer and D. von der Linde, Pico-		Fantoni, R., E. Borsella, S. Piccirillo, C.A.	
second time-resolved laser desorption	46 (1990) 284	Nannetti, R. Ceccato and S. Enzo,	
Elliman, R.G., see Pain	48/49 (1991) 76	Laser assisted synthesis of ultrafine	40 (4000) 400
Elliott, G.S., see Smith	48/49 (1991) 135	silicon powder	43 (1989) 308
Elliq, M., see Mathé	43 (1989) 142	Fantoni, R., see Giardini-Guidoni	46 (1990) 321
Elliq, M., E. Fogarassy, J.P. Stoquert, C.		Fariñas, J.C. and M.F. Barba, Inductively	
Fuchs, S. de Unamuno, B. Prévot and		coupled plasma-atomic emission	
H. Pattyn, Pulsed excimer and		spectrometry (ICP-AES): an analyti-	
Nd:YAG laser crystallization of a-	46 (1000) 278	cal technique for the chemical char-	
Si:H. The specific role of hydrogen	46 (1990) 378 50 (1991) 420	acterization of perovskite ceramic semiconductors	50 (1991) 202
Emanuelsson, P., see Meyer	43 (1989) 224	Favennec, P.N., see L'Haridon	50 (1991) 237
Emiliani, G., see Scaglione Endo, K., see Okumura	41/42 (1989) 548	Feldman, C., G. Deutscher and E.	30 (1991) 237
Endrédi, G., see Horányi	50 (1991) 143	Grünbaum, Single-crystal transforma-	
	48/49 (1991) 419	tion of sphalerite CdS to cubic phase	
Engelhardt, M., see Nelson Engemann, J., see Korzec	46 (1990) 299	Cu <sub>x</sub> S	48/49 (1991) 535
Engemann, J., see Hütten	46 (1990) 306	Feldman, R.D., see Donegan	50 (1991) 321
Enta, Y., see Kono	41/42 (1989) 75	Fendrych, F., see Kubátová	43 (1989) 297
Enzo, S., see Fantoni	43 (1989) 308	Feng Duan, see Zhang Rong	48/49 (1991) 356
Epler, J.E., R.D. Bringans, F.A. Ponce,	45 (1707) 500	Ferla, G., see Priolo	41/42 (1989) 619
G.B. Anderson, D.W. Treat and T.L.		Ferla, G., see Priolo	43 (1989) 178
Paoli, Laser patterned desorption		Fernandez, A., see Gonzalez-Elipe	45 (1990) 103
within an upflow metalorganic chem-		Fernández, D., see Szörényi	46 (1990) 206
ical vapor deposition reactor	43 (1989) 432	Fernandez, J.E., see King	45 (1990) 325
Erman, M., see Gendry	44 (1990) 309	Fernie, P.A., see Jubber	43 (1989) 74
Ermolieff, A., F. Martin, A. Amouroux,	44 (1770) 307	Ferraris, G., see Moretti	45 (1990) 341
S. Marthon and J.F.M. Westendorp,		Ferraz, A.C., see De Figueiredo	41/42 (1989) 509
Surface composition analysis of HF		Ferreira, I., see Zeman	46 (1990) 245
vapour cleaned silicon by X-ray pho-		Ferrer, I.J., see De las Heras	50 (1991) 505
toelectron spectroscopy	48/49 (1991) 178	Feuillet, G., see Tatarenko	41/42 (1989) 470
Espinos, J.P., see Gonzalez-Elipe	45 (1990) 103	Fewster, P.F., Multicrystal X-ray diffrac-	12/ 12 (2202) 110
Esrom, H., see Wahl	46 (1990) 96	tion of heteroepitaxial structures	50 (1991) 9
Esrom, H. and U. Kogelschatz, Investiga-	()	Fijol, J.J., A.M. Then, G.W. Tasker and	
tion of the mechanism of the UV-in-		R.J. Soave, Secondary electron yield	
duced palladium deposition process		of SiO2 and Si3N4 thin films for con-	
from thin solid palladium acetate films	46 (1990) 158	tinuous dynode electron multipliers	48/49 (1991) 464
Esser, A., W. Kütt, M. Strahnen, G.	, ,	Filiouguine, I.V., see Jadin	46 (1990) 375
Maidorn and H. Kurz, Femtosecond		Fischer, A.E.M.J., W.F.J. Slijkerman, J.F.	
transient reflectivity measurements as		van der Veen and I. Ohdomari, Ther-	
a probe for process-induced defects in		mal stability of supersaturated oxy-	
silicon	46 (1990) 446	gen-doped silicon epitaxial films	44 (1990) 115
Esser, N., M. Hünermann, U. Resch, D.	, ,	Fischer, T., see Schwarz	50 (1991) 456
Spaltmann, J. Geurts, D.R.T. Zahn,		Flokstra, J., see Aarnink	47 (1991) 195
W. Richter and R.H. Williams, Bis-		Flores, F., A. Muñoz and J.C. Durán,	,
muth on GaAs(110): characterisation		Semiconductor interface formation:	
of growth mode and Schottky barrier		the role of the induced density of in-	
formation at low and room tempera-	4	terface states	41/42 (1989) 144
ture	41/42 (1989) 169	Flori, D., see Scaglione	43 (1989) 224

Fogarassy, E., see Boch	43 (1989) 17	Fujieda, S., K. Akimoto, I. Hirosawa, Y.	
Fogarassy, E., see Mathé	43 (1989) 142	Mochizuki, J. Mizuki, Y. Matsumoto	
Fogarassy, E., see Maillou	43 (1989) 150	and J. Matsui, Electrical properties	
Fogarassy, E., C. Fuchs, S. de Unamuno		and structures of the MOCVD-AIN/	
and P. Siffert, Excimer laser induced		GaAs interface	41/42 (1989) 516
melting of heavily doped silicon: a		Fujii, A., see Kawadzu	41/42 (1989) 296
contribution to the optimization of the		Fujii, T., see Ichimiya	41/42 (1989) 82
laser doping process	43 (1989) 316	Fujiki, N., see Okuyama	41/42 (1989) 633
Fogarassy, E., A. Slaoui, C. Fuchs and		Fujimura, N. and T. Ito, TiSi <sub>2</sub> formation	, - (,
J.P. Stoquert, Deposition of SiO <sub>2</sub> by		at the Ti-rich TiN <sub>x</sub> /Si interface	41/42 (1989) 272
reactive excimer laser ablation from a		Fujimura, N., S. Tachibana and T. Ito,	, . ( ,
SiO target	46 (1990) 195	Characterization of Si-rich WSi, on Si	41/42 (1989) 286
Fogarassy, E., see Elliq	46 (1990) 378	Fujisawa, A., see Nakanishi	48/49 (1991) 55
Forkel, D., see Pfeiffer	50 (1991) 154	Fujita, H., see Ma	41/42 (1989) 572
Forkel, D., see Baurichter	50 (1991) 165	Fujita, K., see Matsuda	48/49 (1991) 231
Fornari, R., N. Tchandjou, P. Gall and		Fujita, S., see Hayashi	41/42 (1989) 534
J.M. Lussert, A study of structural		Fujita, S., see Hayashi	41/42 (1989) 534
properties of bulk double-doped InP		Fujitani, H. and S. Asano, Electronic	, , , , , , , , , , , , , , , , , , , ,
by laser scattering tomography and		structure of Si/disilicide interfaces	41/42 (1989) 164
photoetching	50 (1991) 207	Fujiwara, K., see Kanamoto	41/42 (1989) 526
Förster, A., J.M. Layet and H. Lüth,		Fujiyasu, H., see Nakamura	48/49 (1991) 478
Evaluation of dopant profiles and dif-		Fukuchi, E., see Nagashima	48/49 (1991) 44
fusion constants by means of electron		Fukuchi, K., see Oishi	48/49 (1991) 276
energy loss spectroscopy	41/42 (1989) 306	Fukuda, Y., see Nakanishi	48/49 (1991) 55
Forsyth, N., see Williams	41/42 (1989) 189	Fukuda, Y. and M. Nagoshi, Chemisorp-	, , , , , , , , , , , , , , , , , , , ,
Foti, G., see Compagnini	43 (1989) 228	tion of hydrogen on Cr(111) studied	
Foulon, F., A. Slaoui and P. Siffert, ArF		by XPS, UPS, and HREELS	48/49 (1991) 147
excimer laser doping of boron into		Fukuda, Y., see Nakanishi	48/49 (1991) 297
silicon	43 (1989) 333	Fukushima, K. and I. Yamada, Surface	, , , , ,
Foxon, C.T., Control of MBE, MOMBE	` '	smoothness and crystalline structure	
and CBE growth using RHEED	50 (1991) 28	of ICB deposited TiO <sub>2</sub> films	43 (1989) 32
Fraissard, J., see Nogier	47 (1991) 287	Fuoss, P.H., see Ourmazd	41/42 (1989) 365
Franchi, S., see Ghezzi	50 (1991) 400	Furukawa, K. and A. Nakagawa, Appli-	, , , ,
Franchi, S., see Baraldi	50 (1991) 405	cations of the silicon wafer direct-	
Francis, S.M., see Pemble	46 (1990) 32	bonding technique to electron devices	41/42 (1989) 627
Frank, D.G., T. Golden, O.M.R. Chyan		Furukawa, S., see Lee	41/42 (1989) 553
and A.T. Hubbard, Direct imaging		Fusy, J., see Ducros	44 (1990) 59
of thin film atomic structure by an-		•	
gular distribution Auger microscopy		Gaffet, E., J.M. Pelletier and S. Bonnet-	
(ADAM)	48/49 (1991) 166	Jobez, Laser surface alloying of Ni	
Freeouf, J.L., The analysis of complex		film on Al-based alloy	43 (1989) 248
samples by spectroscopic ellipsometry	41/42 (1989) 323	Gall, P., see Fornari	50 (1991) 207
Freltoft, T., see Vase	46 (1990) 61	Gall, P., see L'Haridon	50 (1991) 237
Friedland, E., see Myburg	43 (1989) 242	Ganibal, C., see Dilhac	46 (1990) 451
Frigeri, C., J.L. Weyher and M. De Potter,		Ganz, J., see Bauer	46 (1990) 113
TEM study of the origin of the surface		Gao, D., see Pain	48/49 (1991) 76
microroughness in DSL photoetched		Gao, J., W.A.M. Aarnink, G.J. Gerritsma	
Si-implanted GaAs wafers	50 (1991) 115	and H. Rogalla, High quality YBa2	
Frindt, R.F., see Divigalpitiya	48/49 (1991) 572	Cu <sub>3</sub> O <sub>x</sub> ultra-thin films and Y/Pr/Y	
Fu, S.S. and G.A. Somorjai, Zinc oxide		multilayers made by a modified RF-	
and oxygen overlayers on Cu(110): a		magnetron sputtering technique	46 (1990) 74
model for Cu-Zn-O catalysts	48/49 (1991) 93	Gao, Y., I. Ardelean, D. Renard, B. Rose	
Fuchs, C., see Boch	43 (1989) 17	and Y. Jin, High-depth-resolution	
Fuchs, C., see Fogarassy	43 (1989) 316	SIMS analysis for InGaAs/InP inter-	
Fuchs, C., see Fogarassy	46 (1990) 195	faces	50 (1991) 131
Fuchs, C., see Elliq	46 (1990) 378	Gao, Y., see Amarger	50 (1991) 462
Fuchs, G., see Massouras	43 (1989) 213	Garawal, N.S., see Pickering	50 (1991) 346
Fuentes, S., see Vázquez	44 (1990) 331	Garbassi, F., see Occhiello	47 (1991) 235

García, E.A., see De González	44 (1990) 211	Giorgi, M., see Giardini-Guidoni	46 (1990) 321
Gardella, Jr., J.A., see Hook	44 (1990) 29	Giorgi, R., see Lascovich	47 (1991) 17
Gardella, Jr., J.A., see Hook	44 (1990) 252	Girault, C., D. Damiani, C. Champeaux,	
Gardella, Jr., J.A., see Heens	47 (1991) 163	P. Marchet, C. Germain, J.P. Mercuri-	
Gardiner, R., see Hamaguchi	48/49 (1991) 441	o, J. Aubreton and A. Catherinot,	
Garrido, C., D. Braichotte, H. van den		Characterization of the KrF laser-in-	
Bergh, B. León and M. Pérez-Amor,		duced plasma plume created above an	
Interconnection lines of Pt induced by	42 (1000) (0	YBaCuO superconducting target and	
laser direct writing	43 (1989) 68	preparation of superconducting thin	4/ (1000) 70
Garrido, C., see Braichotte	46 (1990) 9	films	46 (1990) 78
Gaspard, F., see Chartier	45 (1990) 351	Givord, D., see Dupendant	43 (1989) 369
Gates, A.D. and J.L. Robins, Nucleation	40 /40 (1001) 154	Glanvill, S.R., see Pain	48/49 (1991) 76
of gold on Ca <sup>2+</sup> -doped NaCl	48/49 (1991) 154	Glynn, T.J., see O'Connor	50 (1991) 312
Gauneau, M., see L'Haridon	50 (1991) 237 43 (1989) 111	Göbel, H., see Zaus	50 (1991) 92
Gauthier, R., see M'Ghaieth Gauzzi, A., see James	43 (1989) 393	Göbel, R., see Dinges Gobil, Y., see Tatarenko	50 (1991) 359 41/42 (1989) 470
Gavand, M., see Hizem	50 (1991) 490	Goda, T., see Hishinuma	48/49 (1991) 405
Gavigan, J.P., see Dupendant	43 (1989) 369	Godlewski, M., see Heijmink Liesert	50 (1991) 245
Gebhard, S., see Nelson	48/49 (1991) 419	Godlewski, M., see Zakrzewski	50 (1991) 257
Geerts, M.J., see Zeman	46 (1990) 245	Godlewski, M., see Van Gisbergen	50 (1991) 273
Geiler, H.D., see Wagner	43 (1989) 260	Godowski, P.J., Analysis of surface segre-	30 (1991) 273
Geiler, H.D., see Wagner	50 (1991) 373	gation in Co-Ru alloy using Auger	
Gekka, Y., M. Saitoh, K. Ohga, Y. Akaida	30 (1771) 373	electron spectroscopy	47 (1991) 333
and M. Akimoto, Electrical character-		Gofuku, E., Y. Toyoda, Y. Uehara, M.	47 (1771) 333
istics of metal contacts on the surfaces		Kohara and M. Nunoshita, Highly	
of a-Si:H films annealed at low tem-		conductive TiO <sub>2</sub> thin films prepared	
perature	41/42 (1989) 184	by EB-modification	48/49 (1991) 343
Gendry, M., J. Durand, M. Erman, J.B.	11/ 12 (1707) 101	Golanski, A., Ion beam synthesis of buried	10/ 15 (1551) 0 10
Theeten, L. Nevot and B. Pardo,		compound layers: accomplishments	
Chemical and structural analysis by		and perspectives	43 (1989) 200
ellipsometry and X-ray reflectometry		Golden, T., see Frank	48/49 (1991) 166
of thin sulfide layers grown on InP	44 (1990) 309	Golding, T.D., see Zahn	41/42 (1989) 497
Gendry, M., see Tardy	50 (1991) 383	Goldoni, S., see Hoffmann	43 (1989) 54
Gentilini, P., see Huong	43 (1989) 256	Goltzené, A., see Benchiguer	50 (1991) 277
Gerhardt, H., see Bolle	46 (1990) 279	Golusda, E., R. Lange, G. Mollekopf and	, ,
Gerlic, E., see Chevarier	48/49 (1991) 215	H. Stafast, On the role of the substrate	
Germain, C., see Girault	46 (1990) 78	position in the CO <sub>2</sub> laser CVD of	
Gerritsma, G.J., see Gao	46 (1990) 74	amorphous hydrogenated silicon	46 (1990) 230
Geurts, J., see Esser	41/42 (1989) 169	Golz, J.W., see Halpern	48/49 (1991) 19
Geurts, J., see Zahn	41/42 (1989) 497	Gombia, E., see Ghezzi	50 (1991) 400
Geus, J.W., see Deckers	45 (1990) 121	Gombia, E., see Castaldini	50 (1991) 485
Geus, J.W., see Deckers	45 (1990) 207	Gómez-Rodríguez, J.M., A.M. Baró and	
Geus, J.W., see Balkenende	47 (1991) 341	V.P. Parkhutik, Morphology of porous	
Gewinner, G., see Haderbache	41/42 (1989) 257	silicon studied by STM/SEM	44 (1990) 185
Ghezzi, C., R. Mosca, A. Bosacchi, S.		González, P., see Szörényi	46 (1990) 206
Franchi and E. Gombia, The influence		Gonzalez-Elipe, A.R., J.P. Espinos, A.	
of the DX center on the capacitance		Fernandez and G. Munuera, XPS	
of Schottky barriers in n-type AlGaAs	50 (1991) 400	study of the surface carbonation/hy-	
Ghezzi, C., see Baraldi	50 (1991) 405	droxylation state of metal oxides	45 (1990) 103
Giardini-Guidoni, A., see Mele	43 (1989) 398	Gordon, R.L., see Baer	45 (1990) 71
Giardini-Guidoni, A., see Teghil	46 (1990) 220	Gore, R.B., R.K. Pandey and S.R. Kumar,	
Giardini-Guidoni, A., A. Morone, M.		Preparation and characterisation of	
Snels, E. Desimoni, A.M. Salvi, R.		nearly stoichiometric CdTe films from	
Fantoni, W.C.M. Berden and M.		a non-aqueous electrodeposition bath	48/49 (1991) 530
Giorgi, Luminescence and ESCA		Gornik, E., see Strasser	50 (1991) 261
analysis of laser-ablated materials	46 (1990) 321	Goto, S., H. Kakibayashi, M. Kawata and	
Giess, J., see Keir	50 (1991) 103	T. Usagawa, Evaluation of disordering	
Gijzeman, O.L.J., see Balkenende	47 (1991) 341	at low doping concentration in selec-	

tively Si-doped Al <sub>0.3</sub> Ga <sub>0.7</sub> As/GaAs		Samimi, B. Biglari and P. Siffert, Mi-	
heterointerfaces	41/42 (1989) 480	croscopic defect level characterization	
Goulding, P.A., see Pemble	46 (1990) 32	of semi-insulating compound semicon-	
Grabke, H.J., D. Wiemer and H. Viefhaus,	, , , , , , , , , , , , , , , , , , , ,	ductors by TSC and PICTS. Applica-	
Segregation of sulfur during growth of		tion to the effect of hydrogen in CdTe	50 (1991) 377
oxide scales	47 (1991) 243	Hagino, M., see Nomura	41/42 (1989) 512
Graettinger, T.M., see Krauss	46 (1990) 67	Hagino, M., see Takeuchi	41/42 (1989) 530
Grattepain, C. and A.M. Huber, Sec-		Haight, R. and J.A. Silberman, Surface	
ondary ion mass spectrometry of		intervalley scattering on GaAs(110)	
dopants and impurities in compound		studied with picosecond laser photo-	
semiconductors: depth profiling of		emission	41/42 (1989) 487
homo- and heterostructure	50 (1991) 42	Halimaoui, A., see Bomchil	41/42 (1989) 604
Greenough, R.D., see Dyer	43 (1989) 387	Halpern, B.L., J.J. Schmitt, J.W. Golz, Y.	
Grégoire, Ch., see Heens	47 (1991) 163	Di and D.L. Johnson, Gas jet deposi-	
Gregoire, J., see Hizem	50 (1991) 490	tion of thin films	48/49 (1991) 19
Gregorkiewicz, T., see Heijmink Liesert	50 (1991) 245	Halstead, D., see Bowker	44 (1990) 1
Gregorkiewicz, T., see Van Gisbergen	50 (1991) 273	Hamaguchi, N., R. Gardiner and P.S.	
Gregory, O.J., see Bhardwaj	48/49 (1991) 555	Kirlin, MOCVD of TlBaCaCuO su-	
Grimmeiss, H.G. and M. Kleverman,		perconducting thin films: structure-	
Electrical and optical defect spectros-		property-processing relationships	48/49 (1991) 441
copy of compound semiconductors	50 (1991) 52	Hamakawa, Y., see Inoue	41/42 (1989) 407
Grötzschel, R., see Richter	44 (1990) 127	Hamakawa, Y., see Okuyama	41/42 (1989) 633
Grovenor, C.R.M., see Mackenzie	50 (1991) 196	Han, B., see Interrante	46 (1990) 5
Gruen, D.M., see Krauss	46 (1990) 67	Han, I.K., Y.J. Lee, J.W. Jo, J.I. Lee and	
Grünbaum, E., see Feldman	48/49 (1991) 535	K.N. Kang, Growth and characteriza-	
Grundmann, M., see Christen	41/42 (1989) 329	tion of silicon-nitride films by plas-	
Guegan, H., see Barrière	41/42 (1989) 383	ma-enhanced chemical vapor deposi-	
Guenais, B., see Auvray	50 (1991) 109	tion	48/49 (1991) 104
Guerfi, N., see Nguyen Tan	41/42 (1989) 266	Hanawa, T., see Sumitomo	41/42 (1989) 112
Guillot, G., see Hizem	50 (1991) 490	Hanawa, T., see Katayama	48/49 (1991) 361
Guillot, G., see Roura	50 (1991) 496	Haneman, D. and N. McAlpine, Light	
Gumienny, Z., see Jezierski	50 (1991) 341	emission from Si cleaved and gas-	
Guo, J., see Chang	48/49 (1991) 12	covered surfaces	48/49 (1991) 111
Gupta, A., see Pickart	48/49 (1991) 436	Hanesch, P., see Schwarz	50 (1991) 456
Gusinsky, G.M., see Kudoyarova	50 (1991) 173	Hanus, F. and M. Wautelet, Time-re-	
Gustafsson, A., S. Nilsson and L. Samuel-		solved temperature measurements dur-	
son, Intensity variations in the near-		ing laser-induced synthesis of Cu-Te	
band-edge recombination of GaP epi-		compounds	43 (1989) 271
taxial layers, grown on (111) and (001)		Haranou, T., see Shigesato	48/49 (1991) 269
oriented substrates, as observed by		Hariu, T., S. Yamauchi, H. Tanaka and S.	
cathodoluminescence imaging	50 (1991) 186	Ono, Interface characterization of	40 (40 (1001) 204
	42 (1000) 41 (	ZnSe/GaAs heterojunctions	48/49 (1991) 204
Haarer, D., see Meiler	43 (1989) 416	Hartiti, B., A. Slaoui, J.C. Muller and P.	
Haberger, K., see Pielmeier	46 (1990) 163	Siffert, Annealing kinetics during	
Haberger, K., see Stock	46 (1990) 348	rapid thermal processing of excimer	46 (1000) 271
Haberger, K., see Hu	46 (1990) 388	laser-induced defects in virgin silicon	46 (1990) 371
Habermeier, HU., see Chen	50 (1991) 191	Hasegawa, H., H. Ohno, H. Ishii, T. Haga,	
Habraken, F.H.P.M., see Deckers	45 (1990) 121	Y. Abe and H. Takahashi, Origin and	
Habraken, F.H.P.M., see Deckers	45 (1990) 207	properties of interface states at insula-	
Haderbache, L., P. Wetzel, C. Pirri, J.C.		tor-semiconductor and semiconduc- tor-semiconductor interfaces of com-	
Peruchetti, D. Bolmont and G.			41 /42 (1090) 272
Gewinner, Identification of three dis-		pound semiconductors	41/42 (1989) 372 41/42 (1989) 390
tinct $CoSi_2(111)(1 \times 1)$ surface structures	41 /42 (1090) 257	Hasegawa, H., see Ishii	41/42 (1989) 402
tures	41/42 (1989) 257 41/42 (1989) 372	Hasegawa, H., see Saitoh Hasegawa, S., see Li	41/42 (1989) 402
Haga, T., see Hasegawa	46 (1990) 422	Hasegawa, S., see Li Hasegawa, S., see Maehashi	41/42 (1989) 567
Hage Ali, M., see Marfaing Hage-Ali, M., see Chibani	50 (1991) 177	Hasegawa, Y., see Hashizume	48/49 (1991) 119
Hage-Ali, M., B. Yaacoub, S. Mergui, M.	30 (1791) 177	Hashimoto, F., see Kamiura	41/42 (1989) 447
riago-rii, ivi., D. 1 dacouo, S. Iviergui, Ivi.		ambinition, and training	.1/ 12 (1707) 441

Hashimoto, S., XPS and AES studies on		sorption in the adsorbate CO-	
the interface between metal and poly-		NaCl(100)	46 (1990) 44
mer layers. The effect of Ar-plasma		Heijmink Liesert, B.J., M. Godlewski, T.	
treatment of the polymer surface pre-		Gregorkiewicz and C.A.J. Ammerlaan,	
ceding the metal deposition	47 (1991) 323	Neutron transmutation doping of	
Hashizume, T., Y. Hasegawa and T.		GaP: optical studies	50 (1991) 245
Sakurai, Alkali-metal adsorption on		Heiland, W., see Priggemeyer	44 (1990) 255
silicon surfaces studied by field ion-		Heinig, KH., see Voelskow	43 (1989) 196
scanning tunneling microscopy (FI-		Heinig, KH., see Neelmeijer	43 (1989) 232
STM)	48/49 (1991) 119	Heinig, KH., see Wagner	43 (1989) 260
Hasobe, M., see Iizuka	41/42 (1989) 587	Heinz, T.F., see Himpsel	41/42 (1989) 346
Hasselberger, B., see Campbell	43 (1989) 346	Hennemann, OD., see Breuer	46 (1990) 336
Hasselberger, B., see Ulmer	46 (1990) 272	Henry, M.O., see O'Connor	50 (1991) 312
Hatanaka, Y., K. Mitsuoka and T.	(2220) 2.2	Henzler, M., see Falta	41/42 (1989) 230
Yamaguchi, Properties of a-Si:H based		Herbert, P.A.F., see Crean	50 (1991) 281
interface transient layers measured by		Hergert, W., see Schreiber	50 (1991) 181
in-situ ellipsometry	41/42 (1989) 591	Herino, R., see Bomchil	41/42 (1989) 604
Hatanaka, Y., see Nakanishi	48/49 (1991) 55	Hermann, J., C. Boulmer-Leborgne and	11/ 12 (1707) 00 .
Hatanaka, Y., see Nakanishi	48/49 (1991) 297	B. Dubreuil, Spectroscopic study of	
Hatanaka, Y., Heterostructures with hy-	40/49 (1991) 297	the plasma created by interaction be-	
drogenated amorphous silicon for use	40 (40 (1001) 457	tween a TEA CO <sub>2</sub> laser beam and a Ti	46 (1000) 215
in imaging devices	48/49 (1991) 457	target in a cell containing helium gas	46 (1990) 315
Hatanaka, Y., see Mimura	48/49 (1991) 472	Herres, N., G. Bender and G. Neumann,	
Hatta, A., see Wadayama	44 (1990) 43	Assessment of mismatched epitaxial	
Hatta, A., Y. Suzuki, T. Wadayama and		layers by X-ray rocking curve mea-	50 (1004) OF
W. Suëtaka, Kretschmann ATR-IR		surements and simulations	50 (1991) 97
spectroscopy of investigating metal/		Hertel, I.V., see Campbell	43 (1989) 346
liquid(or solid) interfaces	48/49 (1991) 222	Herzog, HJ., see Holländer	50 (1991) 450
Hatta, A., see Wadayama	48/49 (1991) 409	Hesch, K., P. Hess, H. Oetzmann and C.	
Hattori, T., H. Yamagishi, N. Koike, K.		Schmidt, Laser CVD of a-Si:H from	
Imai and K. Yamabe, Structural stud-		SiH <sub>4</sub> and Si <sub>2</sub> H <sub>6</sub> : relations between	
ies of ultrathin silicon oxides and their		chemistry, growth rate and film prop-	
interfaces by XPS	41/42 (1989) 416	erties	46 (1990) 233
Hayashi, S., T. Sakamoto, S. Fujita and S.		Heskett, D., D. Tang, A.B. McLean, R.	
Fujita, Strained-layer superlattice buf-		Ludeke, M. Prietsch, T. Maeda Wong,	
fers for high-quality heteroepilayers of		E.W. Plummer and N.J. DiNardo,	
ZnSe on GaAs	41/42 (1989) 534	Metal-induced states on the GaAs	
Hayashi, S., see Hishinuma	48/49 (1991) 405	(110) surface probed by angle-resolved	
Hecht, M.H., L.D. Bell and W.J. Kaiser,		photoemission spectroscopy	48/49 (1991) 260
Ballistic-electron-emission microscopy		Heslinga, D.R., see Hibma	48/49 (1991) 209
of subsurface defects at the Au-		Hess, P., see Nowak	43 (1989) 11
GaAs(100) interface	41/42 (1989) 17	Hess, P., see Braun	43 (1989) 352
Hecking, N. and E.H. te Kaat, Modelling	, , , ,	Hess, P., see Buck	43 (1989) 358
of lattice damage accumulation during		Hess, P., see Konstantinov	46 (1990) 102
high energy ion implantation	43 (1989) 87	Hess, P., see Hesch	46 (1990) 233
Heddleson, J.M., see Karulkar	48/49 (1991) 237	Hesse, K., see Bauer	46 (1990) 113
Heens, B., Ch. Grégoire, J.J. Pireaux, P.A.	10/ 15 (1551) 201	Hettwer, HG., W. Lerch, B. Lentfort,	()
Cornelio and J.A. Gardella, Jr., On		N.A. Stolwijk and H. Mehrer, Com-	
the stability and homogeneity of		bined application of spreading-resis-	
Langmuir-Blodgett films as models of		tance and electron-microprobe depth	
polymers and biological materials for		profiling on GaAs:Zn and Si:P	50 (1991) 470
surface studies: an XPS study	47 (1991) 163	Hibma, T., H.H. Weitering, D.R. Heslinga	20 (2771) 470
Hegarty, J., see Donegan	50 (1991) 321	and T.M. Klapwijk, Interface struc-	
Heichler, W., see Kalki	48/49 (1991) 59	ture and Schottky barriers of epitaxial	
Heidberg, J., B. Brase, KW. Stahmer	40/47 (1771) 37	Pb on Si(111)	48/49 (1991) 209
and M. Suhren, Second harmonic gen-		Higashi, G.S., The chemistry of alkyl–alu-	10/ 12 (1221) 209
eration of CO <sub>2</sub> -laser radiation and		minum compounds during laser-as-	
FTIR spectroscopy for resonant de-		sisted chemical vapor deposition	43 (1989) 6
The specificacopy for resonant de-		sisted elicilical vapor deposition	15 (1707)

Hilder A. R. see Saure   43 (1989) 54   Hoffund, G.B., see Loe   47 (1991) 49   Hoffund, G.B., see Loe	Higashi, H., see Kishida	48/49 (1991) 446	thin solid surface layers of metalor-	
Hillner, R.J., see Bauer Hillner, R.J., see Bauer Hillner, R.J., see Bauer Hills, M.M. and G.S. Arnold, Chemical treatment of fused silica with xenon diffuoride Himpsel, F.J., T.F. Heinz, A.B. McLean and E. Palange, Bonding at silicon/insulator interfaces Hillner, and E. Palange, Bonding at silicon/insulator interfaces (1991) 414 (1991) 415 (1991) 415 (1991) 416 (1991) 416 (1991) 416 (1991) 416 (1991) 416 (1991) 416 (1991) 417 (1991) 417 (1991) 417 (1991) 417 (1991) 417 (1991) 418 (1991) 418 (1991) 418 (1991) 419 (1991) 41	Hihara, T., see Wadayama	48/49 (1991) 409	ganic compounds	43 (1989) 54
Hillmer, T., see Bauer Hoffman, D., see Mosel Hoffsiss, H., see Jahn Hogg, J.H.C., D. Shaw and D.M. Staudte, Modelling interdiffusion in epitaxial multiper structures using X-ray simulation techniques simulation techniques Holland, O.W., see Withrow Holland, O.W., see Linehinger Holland, O.W., see Withrow Holland, O.W., see Linehinger Holland, O.W., see Withrow Holland, O.W., see Withrow Holland, O.W., see Withrow Holland, O.W., see Withrow Holla	Hildebrandt, S., see Schreiber	50 (1991) 181	Hoflund, G.B., see Hoekje	47 (1991) 43
Hillis, M.M. and G.S. Arnold, Chemical treatment of fused silica with xenon diffuoride Himpsel, F.J., T.F. Heinz, A.B. McLean and E. Palange, Bonding at silicon/insulator interfaces Hino, T., see Yamashina Hinotani, S., see Matsuda Hinria, M., see Iwami Hirai, M., see Iwami Hirai, M., see Iwami Hirai, A., see Kato Hiraki, A., see Iso Hiraki, A.	Hillard, R.J., see Karulkar	48/49 (1991) 237	Hoflund, G.B., see Lee	47 (1991) 91
treatment of fused silica with xenon diffluoride Himpsel, F.J., T.F. Heinz, A.B. McLean and E. Palange, Bonding at silicon/insulator interfaces Hino, T., see Yamashina Hinotani, S., see Matsuda Hino, T., see Yamashina Hirai, M., see Iwami Hirai, M., see Iwami Hirai, A., see Wasumatsu Hirai, A., see Iwami Hirai, A., see Iwami Hirai, A., see Wasumatsu Hirai		50 (1991) 138	Hofmann, D., see Mosel	50 (1991) 364
diffuoride Himpsel, F.J., T.F. Heinz, A.B. McLean and E. Palange, Bonding at silicon/insulator interfaces and E. Palange, Bonding at silicon/insulator interfaces 41/42 (1989) 346 Hino, T., see Varnashina Hinotani, S., see Matsuda Hirai, M., see Iwami Hirai, M.,	Hills, M.M. and G.S. Arnold, Chemical		Hofsäss, H., see Jahn	50 (1991) 169
Himpsel, F.J., T.F. Heinz, A.B. McLean and E. Palange, Bonding at silicon/insulator interfaces and E. (1989) 346 41/42 (1989) 345 41/4	treatment of fused silica with xenon		Hogg, J.H.C., D. Shaw and D.M. Staudte,	
simulation techniques simulation techniques simulation techniques simulation techniques solvent states and substates such as spectrometry and adhesion of metal-polymer interfaces Hork, P. S. Chemistry and adhesion of silicon dioxide films in acidic solutions Horken, P. B. Lecchier, S. Goldini and H. van den Bergh, F. Set Nationa H. Na washara, Evangation and H. Chemistry and adhesion of metal-polymer interfaces Horken, P. B. Lecchier, S. Goldini and H. van den Bergh, F. Ste Nationa H. Skaper, S. Grigon, S. S. Chaffler, HJ. Hork, J.H. Wandass and J.A. Gardella, Jr., Secondary ion formation from functional polymer systems in static secondary ion measured modifications of this double and single acceptor state of isolated Nicg, in GaAs Horken, P. B. Lecchier, S. Goldini and H. van den Bergh, F. Stat laser write the self-raction and H. van den Bergh, F. Sta	difluoride	47 (1991) 77	Modelling interdiffusion in epitaxial	
sulator interfaces   44/42 (1989) 346   Hogg, J.H.C., see Ashenford   43 (1989) 191   Hinotani, S., see Matsuda   48/49 (1991) 231   41/42 (1989) 37   41/42	Himpsel, F.J., T.F. Heinz, A.B. McLean		multilayer structures using X-ray	
Hino, T., see Yamashina Hinotani, S., see Matsuda Hinotani, S., see Matsuda Hirai, M., see Iwami Hirai, M., see Wathon Hirai, M., see Iwami Hirai, M., see Wathon Hiraid, M., see Wathon Holloway, P.H., see Deneuville Hongo, S., T. Urano and T.  Kanaji, Wathon, M.	and E. Palange, Bonding at silicon/in-		simulation techniques	50 (1991) 87
Hinciani, M., see Iwami Hirai, M., see Wami Hirai, M., see Pala Mirai Hillolloway, P.H., see Deneuville Holloway, P.H., see Deneuville Holloway	sulator interfaces	41/42 (1989) 346	Hogg, J.H.C., see Ashenford	50 (1991) 440
Hirai, M., see Iwami Hirai, M., see Wasumots Hirai, M., see Hoo Hirai, A., see Iwami Hirai, M., see Wasumots Hirai, M., see Hoo Hirai, A., see Iwami Hirai, M., see Wasumots Hirai, A., see Iwami Hirai, M., see Wasumots Hirai, M., see Wasumots Hirai, A., see Ma Hirai, A., see Iwami Hirai, A., see Iwami Hirai, A., see Wasumots Hirai, M., see Wasumots Hirai, A., see Wasumots Hirai, M., see W	Hino, T., see Yamashina	48/49 (1991) 483	Holland, O.W., see Withrow	43 (1989) 191
Hiraki, A., see Ma Hiraki, A., see Melson and cured poly- imide films by Arf excimer laser: applications of Mapton and Cured poly- imide films by Arf excimer laser: applications of Mapton and H. Maya den Bergh, Fast laser wit-  46 (1990) 264  46 (1990) 264  46 (1990) 264  46 (1990) 324  46 (1990) 324  46 (1990) 324  46 (1990) 324  46 (1990) 324  46 (1990) 324  47 (1991) 371  47 (1991) 371  47 (2 (1989) 572  48 (1990) 371  47 (1991) 371  47 (2 (1989) 572  48 (1990) 371  47 (1991) 371  48 (1990) 29  49 (1991) 490  49 (1991) 490  49 (1991) 490  49 (1	Hinotani, S., see Matsuda	48/49 (1991) 231	Holländer, B., S. Mantl, B. Stritzker, F.	
Hiraki, A., see Ma 41/42 (1989) 572 Hiraki, A., see Kato 41/42 (1989) 572 Hiraki, A., see Kato 41/42 (1989) 572 Hiraki, A., see Kato 41/42 (1989) 572 Hiraki, A., see Yasumatsu Hiraoka, H. and S. Lazare, Surface modifications of Kapton and cured polyimide films by ArF excimer laser: applications to imagewise wetting and metallization Hiraki, A., see Kusunoki Hiraki, A., see Yasumatsu Hiraoka, H. and S. Lazare, Applications of doing and dedoping of Teflon AF films in microfabrication using KrF and ArF excimer lasers Hiroi, M., see Kusunoki Hiroskawa, K., see Sasaki Hirosawa, I., see Akimoto Hokok, J.J., see Hook Hook, K.J., T.J. Hook, J	Hirai, M., see Iwami	41/42 (1989) 57	Schäffler, HJ. Herzog and E. Kasper,	
Hiraki, A., see Ma Hiraki, A., see Kato Hiraki, A., see Kato Hiraki, A., see Yasumatsu Hiraki, A., see Poneuville Holloway, P.H., see Deneuville Holloway, P.	Hirai, M., see Iwami	41/42 (1989) 97	Strain and defect densities in Si/	
Hiraki, A., see Rato Hiraki, A., see Yasumatsu Hiraki, A., see Pan Holloway, P.H., see Deneuville Holloway, P.H., see Deneu	Hiraki, A., see Ito	41/42 (1989) 301	$Si_{1-x}Ge_x$ heterostructures investigated	
Hiraki, A., see Yasumatsu Hiraki, A., see Paimatsu Hiraki, A., see Paimatsu Holloway, P.H., see Deneuville H	Hiraki, A., see Ma	41/42 (1989) 572	by ion scattering and X-ray diffrac-	
Hiraki, A., see Yasumatsu Hongo, S., Y. Kataoka, T. Urano and T. Kanaji, Evaluation by resonant light scattering of Zaff eepitxaial layer deposited on GaAs Hongo, S., T. Urano and T. Kanaji, Evaluation by resonant light scattering of Zaff eepitxaial layer deposited on GaAs Hongo, S., T. Urano and T. Kanaji, Evaluation by resonant light scattering of Zaff eepitxaial layer deposited on GaAs Hongo, S., T. Urano and T. Kanaji, Mechanisms of He'(2'S) de-excitation on oxygen-adsorbed Si(100) surfaces Hirokawa, K., see Sasaki Hongo, S., T. Urano and T. Kanaji, Mechanisms of He'(2'S) de-excitation on oxygen-adsorbed Si(100) surfaces Hook, K.J., T.J. Hook, J.H. Wandass and J.A. Gardella, Jr., Secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static seconda	Hiraki, A., see Kato	41/42 (1989) 614	tion	50 (1991) 450
Hiraoka, H. and S. Lazare, Surface modifications of Kapton and cured polyimide films by ArF excimer laser: applications to imagewise wetting and metallization  Hiraoka, H. and S. Lazare, Applications of doping and dedoping of Teflon AF films in microfabrication using KrF and ArF excimer lasers  Hirokawa, K., see Kusunoki  Hirosawa, I., see Akimoto  Hirosawa, I., see Hujieda  Hirosawa, I., see Fujieda  Hirosawa, I., see Fujieda  Hirosawa, I., see Hujieda  Hirosawa, I., see Fujieda  Hirosawa, I., see Fujieda  Hirose, K., H. Tsuda and T. Mizutani, Control of the Al/GaAs Schottky barrier height using a rare-earth metal interlayer  Hishinuma, A., T. Goda, M. Kitaoka, S. Hayashi and H. Kawahara, Formation of silicon dioxide films in acidic solutions  Hizem, N., G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double and single acceptor state of isolated Nica in GaAs  Ho, P.S., Chemistry and adhesion of metal-polymer interfaces  Höckje, S. J. T. Hook, J.H. Wandass and J.A. Gardella, Jr., Secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion f	Hiraki, A., see Ito	44 (1990) 97	Holloway, P.H., see Deneuville	50 (1991) 285
ifications of Kapton and cured polyimide films by ArF excimer laser: applications to imagewise wetting and metallization  Hiroka, H. and S. Lazare, Applications of doping and dedoping of Teflon AF films in microfabrication using KrF and ArF excimer lasers  Af (1990) 342  Hiroi, M., see Kusunoki  Hirokawa, K., see Sasaki  Hirosawa, I., see Fujieda  Hirosawa, I., see Fujieda  Hirose, K., H. Tsuda and T. Mizutani, Control of the Al/GaAs Schottky barrier height using a rare-earth metal interlayer  Hishinuma, A., T. Goda, M. Kitaoka, S. Hayashi and H. Kawahara, Formation of silicon dioxide films in acidic solutions  Hizem, N., G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and W. Ufrici, Identification of the double and single acceptor state of isolated Nic, a in GaAs  HO, P.S., Chemistry and adhesion of metal-polymer interfaces  Höchst, H., see Nelson  Hockie, S. J. And G.B. Hoffund, Surface characterization study of InP(100) substrates using ISS, AES and ESCA: comparison of substrates from two different commercial sources  Hoffmann, P., B. Lecohier, S. Goldoni and H. van den Bergh, Fast laser writ-	Hiraki, A., see Yasumatsu	48/49 (1991) 414	Holloway, P.H., see Deneuville	50 (1991) 308
imide films by ÅrF excimer laser: applications to imagewise wetting and metallization  Hiraoka, H. and S. Lazare, Applications of doping and dedoping of Teflon AF films in microfabrication using KrF and ArF excimer lasers  46 (1990) 342  Hiroi, M., see Kusunoki  Hirosawa, I., see Akimoto  Hirosawa, I., see Jeided  Hirosawa, I., see Jeimen  Control of the Al/GaAs Schottky barrier height using a rare-earth metal interlayer  Hishinuma, A., T. Goda, M. Kitaoka, S. Hayashi and H. Kawahara, Formation of silicon dioxide films in acidic solutions  Hizem, N., G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double and single acceptor state of isolated Nica in GaAs  Hook, F.J., see Hook  Hook, T.J., see ondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer sy	Hiraoka, H. and S. Lazare, Surface mod-		Hongo, S., see Urano	41/42 (1989) 103
plications to imagewise wetting and metallization  Miraoka, H. and S. Lazare, Applications of doping and dedoping of Teflon AF films in microfabrication using KrF and ArF excimer lasers  Af (1990) 342  Hiroi, M., see Kusunoki  Hirokawa, K., see Sasaki  Hirosawa, I., see Huimoto  Af (1991) 371  Hirosawa, I., see Huimoto  Af (1998) 516  Hirosawa, I., see Fujieda  Hirosawa, I., see Fujieda  Af (1998) 516  Hirosawa, I., see Fujieda  Hirosawa, I., see Fujieda  Af (1998) 516  Hirosawa, I., see Fujieda  Af (1998) 517  Af (1991) 371  Af (1998) 516  Af (1990) 242  Af (1990) 252  Hook, K.J., T.J. Hook, J.H. Wandass and J.A. Gardella, Jr., Secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion mass spectrometry. Erratum  Af (1990) 29  Hook, K.J., T.J. Hook, J.H. Wandass and J.A. Gardella, Jr., Secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion mass spectrometry. Erratum  Af (1990) 29  Hook, K.J., T.J. Hook, J.H. Wandass and J.A. Gardella, Jr., Secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in st	ifications of Kapton and cured poly-		Hongo, S., Y. Kataoka, T. Urano and T.	
metallization 46 (1990) 264 Hiraoka, H. and S. Lazare, Applications of doping and dedoping of Teflon AF films in microfabrication using KrF and ArF excimer lasers 46 (1990) 342 Hiroi, M., see Kusunoki 45 (1990) 171 Hirosawa, I., see Akimoto 47 (1991) 371 Hirosawa, I., see Akimoto 47 (1991) 371 Hirosawa, I., see Fujieda 47 (1991) 371 Hirosawa, I., see Fujieda 47 (1991) 371 Hirosawa, I., see Fujieda 47 (1991) 371 Hook, K.J., T.J. Hook, J.H. Wandass and J.A. Gardella, Jr., Secondary ion formation from functional polymer systems in static secondary ion mass spectrometry.  Hishinuma, A., T. Goda, M. Kitaoka, S. Hayashi and H. Kawahara, Formation of silicon dioxide films in acidic solutions  Hizem, N., G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double and single acceptor state of isolated Ni <sub>Ga</sub> in GaAs  Hook, P.S., Chemistry and adhesion of metal–polymer interfaces  Hook, P.S., Chemistry and adhesion of metal–polymer interfaces  Hook, P.S., Chemistry and be seen and the substrates using ISS, AES and ESCA: comparison of substrates from two different commercial sources  Hoffmann, P., B. Lecohier, S. Goldoni and H. van den Bergh, Fast laser writ-	imide films by ArF excimer laser: ap-		Kanaji, Evaluation by resonant light	
Hiraoka, H. and S. Lazare, Applications of doping and dedoping of Teflon AF films in microfabrication using KrF and ArF excimer lasers  Hiroi, M., see Kusunoki  Hirosawa, K., see Sasaki  Control of the Al/GaAs Schottky barrier height using a rare-earth metal interlayer  Hishinuma, A., T. Goda, M. Kitaoka, S. Hayashi and H. Kawahara, Formation of silicon dioxide films in acidic solutions  Hizem, N., G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double and single acceptor state of isolated Ni Ga in GaAs  Hock, P.S., Chemistry and adhesion of metal-polymer interfaces  Höchst, H., see Nelson  Hocky, E. J. and G.B. Hoflund, Surface characterization study of InP(100) substrates using ISS, AES and ESCA: comparison of substrates from two different commercial sources  Hoffmann, P., B. Lecohier, S. Goldoni and H. van den Bergh, Fast laser writ-	plications to imagewise wetting and		scattering of ZnTe epitaxial layer de-	
of doping and dedoping of Teflon AF films in microfabrication using KrF and ArF excimer lasers  Hiroi, M., see Kusunoki  Hirokawa, K., see Sasaki  Hirosawa, I., see Akimoto  Hirosawa, I., see Fujieda  Hirose, K., H. Tsuda and T. Mizutani, Control of the Al/GaAs Schottky barrier height using a rare-earth metal interlayer  Hishinuma, A., T. Goda, M. Kitaoka, S. Hayashi and H. Kawahara, Formation of silicon dioxide films in acidic solutions  Hizem, N., G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double and single acceptor state of isolated Ni <sub>Ga</sub> in GaAs  Ho, P.S., Chemistry and adhesion of metal-polymer interfaces  Hock, E.J. and G.B. Hoflund, Surface characterization study of InP(100) substrates using ISS, AES and ESCA: comparison of substrates from two different commercial sources  Hoffmann, P., B. Lecohier, S. Goldoni and H. van den Bergh, Fast laser writ-	metallization	46 (1990) 264	posited on GaAs	41/42 (1989) 522
films in microfabrication using KrF and ArF excimer lasers  Af (1990) 342  Hiroi, M., see Kusunoki  Hirokawa, K., see Sasaki  Hirokawa, K., see Sasaki  Hirosawa, I., see Fujieda  Hirose, K., H. Tsuda and T. Mizutani,  Control of the Al/GaAs Schottky barrier height using a rare-earth metal interlayer  Hishinuma, A., T. Goda, M. Kitaoka, S. Hayashi and H. Kawahara, Formation of silicon dioxide films in acidic solutions  Hizem, N., G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double and single acceptor state of isolated Ni <sub>Ga</sub> in GaAs  Ho, P.S., Chemistry and adhesion of metal-polymer interfaces  Höchst, H., see Nelson  Hoekje, S.J. and G.B. Hoflund, Surface characterization study of InP(100) substrates using ISS, AES and ESCA: comparison of substrates using ISS, AES and ESCA: comparison of substrates from two different commercial sources  Hoffmann, P., B. Lecohier, S. Goldoni and H. van den Bergh, Fast laser writ-	Hiraoka, H. and S. Lazare, Applications		Hongo, S., T. Urano and T. Kanaji,	
and ArF excimer lasers  Hiroi, M., see Kusunoki  Hirokawa, K., see Sasaki  Hirosawa, I., see Akimoto  Hirosawa, I., see Fujieda  Hook, K.J., T.J. Hook, J.H. Wandass and J.A. Gardella, Jr., Secondary ion mass spectrometry  Hook, K.J., T.J. Hook, J.H. Wandass and J.A. Gardella, Jr., Secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from func	of doping and dedoping of Teflon AF		Mechanisms of He*(21S) de-excita-	
Hirokawa, K., see Sasaki Hirokawa, I., see Akimoto Hirokawa, I., see Akimoto Hirosawa, I., see Fujieda Hirosawa, I., see Fujieda Hirose, K., H. Tsuda and T. Mizutani, Control of the Al/GaAs Schottky barrier height using a rare-earth metal interlayer Hishinuma, A., T. Goda, M. Kitaoka, S. Hayashi and H. Kawahara, Formation of silicon dioxide films in acidic solu- tions Hizem, N., G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double and single acceptor state of isolated Ni <sub>Ga</sub> in GaAs Ho, P. S., Chemistry and adhesion of metal-polymer interfaces Höchst, H., see Nelson Hoekje, S.J. and G.B. Hoflund, Surface characterization study of InP(100) substrates using ISS, AES and ESCA: comparison of substrates from two different commercial sources Hoffmann, P., B. Lecohier, S. Goldoni and H. van den Bergh, Fast laser writ-	films in microfabrication using KrF		tion on oxygen-adsorbed Si(100) sur-	
Hirokawa, K., see Sasaki Hirosawa, I., see Akimoto Hirosawa, I., see Fujieda Hook, K.J., T.J. Hook, J.H. Wandass and J.A. Gardella, Jr., Secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from func	and ArF excimer lasers	46 (1990) 342	faces	48/49 (1991) 143
Hirosawa, I., see Akimoto Hirosawa, I., see Fujieda Hook, T.J., Hook, J.H. Wandass and J.A. Gardella, Jr., Secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion mass spectrometry.  ### Provided Hook, K.J., T.J. Hook, J.H. Wandass and J.A. Gardella, Jr., Secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation for functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion formation for functional polymer systems in static secondary ion formation for functional polymer systems in st	Hiroi, M., see Kusunoki	45 (1990) 171	Hook, K.J., T.J. Hook, J.H. Wandass and	
Hirosawa, I., see Fujieda Hirose, K., H. Tsuda and T. Mizutani, Control of the Al/GaAs Schottky barrier height using a rare-earth metal interlayer Hishinuma, A., T. Goda, M. Kitaoka, S. Hayashi and H. Kawahara, Formation of silicon dioxide films in acidic solu- tions Hizem, N., G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double and single acceptor state of isolated Ni <sub>Ga</sub> in GaAs Ho, P.S., Chemistry and adhesion of metal-polymer interfaces Höchst, H., see Nelson Hoekje, S.J. and G.B. Hoflund, Surface characterization study of InP(100) substrates using ISS, AES and ESCA: comparison of substrates from two different commercial sources Hoffmann, P., B. Lecohier, S. Goldoni and H. van den Bergh, Fast laser writ-	Hirokawa, K., see Sasaki	47 (1991) 371	J.A. Gardella, Jr., Secondary ion for-	
Hirose, K., H. Tsuda and T. Mizutani, Control of the Al/GaAs Schottky barrier height using a rare-earth metal interlayer  Hishinuma, A., T. Goda, M. Kitaoka, S. Hayashi and H. Kawahara, Formation of silicon dioxide films in acidic solutions  Hizem, N., G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double and single acceptor state of isolated Ni <sub>Ga</sub> in GaAs  Hö, P.S., Chemistry and adhesion of metal-polymer interfaces  Höck, K.J., T.J. Hook, J.H. Wandass and J.A. Gardella, Jr., Secondary ion formation from functional polymer systems in static secondary ion mass spectrometry. Erratum  44 (1990) 252  Hook, T.J., see Hook  Hook, T.J., see Hook  Hook, T.J., see Hook  Hook, T.J., see Hook  Horányi, T.S., P. Tüttö and G. Endrédi, Improved method for depth profiling of multilayer structures  Horiike, Y., T. Ichihara and H. Sakaue, Filling of Si oxide into a deep trench using digital CVD method  Horikawa, H., M. Akiyama, S. Onozawa, Y. Kawai and M. Sakuta, Interfacial layers of InP/Si heteroepitaxy  Horio, Y., see Ichimiya  Horio, Y., see Ichimiya  44 (1990) 29  Hook, T.J., Hook, J.H. Wandass and J.A. Gardella, Jr., Secondary ion mass spectrometry. Erratum  Hook, T.J., see Hook  Horányi, T.S., P. Tüttö and G. Endrédi, Improved method for depth profiling of multilayer structures  Horiike, Y., T. Ichihara and H. Sakaue, Filling of Si oxide into a deep trench using digital CVD method  Horikawa, H., M. Akiyama, S. Onozawa, Y. Kawai and M. Sakuta, Interfacial layers of InP/Si heteroepitaxy  Horio, Y., see Ichimiya  Horio, Y., see Ichimi	Hirosawa, I., see Akimoto	41/42 (1989) 317	mation from functional polymer sys-	
Control of the Al/GaAs Schottky barrier height using a rare-earth metal interlayer  Hishinuma, A., T. Goda, M. Kitaoka, S. Hayashi and H. Kawahara, Formation of silicon dioxide films in acidic solutions  Hizem, N., G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double and single acceptor state of isolated Ni Ga in GaAs  Hö, P.S., Chemistry and adhesion of metal-polymer interfaces  Höchs, H., see Nelson  Höchs, E.J. and G.B. Hoflund, Surface characterization study of InP(100) substrates using ISS, AES and ESCA: comparison of substrates from two different commercial sources  Hook, K.J., T.J. Hook, J.H. Wandass and J.A. Gardella, Jr., Secondary ion formation from functional polymer systems in static secondary ion formation from functional polymer systems in static secondary ion mass spectrometry. Erratum  44 (1990) 252  Hook, T.J., see Hook  Horianyi, T.S., P. Tüttö and G. Endrédi, Improved method for depth profiling of multilayer structures  Filling of Si oxide into a deep trench using digital CVD method  Horikawa, H., M. Akiyama, S. Onozawa, Horio, Y., see Ichimiya  Hori	Hirosawa, I., see Fujieda	41/42 (1989) 516	tems in static secondary ion mass	
barrier height using a rare-earth metal interlayer  Hishinuma, A., T. Goda, M. Kitaoka, S. Hayashi and H. Kawahara, Formation of silicon dioxide films in acidic solutions  Hizem, N., G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double and single acceptor state of isolated Ni <sub>Ga</sub> in GaAs  Ho, P.S., Chemistry and adhesion of metal-polymer interfaces  Höchst, H., see Nelson  Höckje, S.J. and G.B. Hoflund, Surface characterization study of InP(100) substrates using ISS, AES and ESCA: comparison of substrates from two different commercial sources  Horiman, P., B. Lecohier, S. Goldoni and H. van den Bergh, Fast laser writ-  J.A. Gardella, Jr., Secondary ion formation from functional polymer systems in static secondary ion mass spectrometry. Erratum  44 (1990) 252  Hook, T.J., see Hook  44 (1990) 252  Hook, T.J., see Hook  44 (1990) 252  Hook, T.J., see Hook  Horian, T.S., P. Tüttö and G. Endrédi, Improved method for depth profiling of multilayer structures  Filling of Si oxide into a deep trench using digital CVD method  46 (1990) 168  Horian, Y., see Ichimiya  Horio, Y., see Ichimiya  Horio, Y., see Ichimiya  Horio, Y., see Ichimiya  Horio, Y., see Ichimiya  Horian, Y., see Ich	Hirose, K., H. Tsuda and T. Mizutani,			44 (1990) 29
interlayer  Hishinuma, A., T. Goda, M. Kitaoka, S. Hayashi and H. Kawahara, Formation of silicon dioxide films in acidic solutions  Hizem, N., G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double and single acceptor state of isolated Ni <sub>Ga</sub> in GaAs  Höchst, H., see Nelson  Höchst, H., see Nelson  Höchst, H., see Nelson  Höchst, H., see Nelson  Hoekje, S.J. and G.B. Hoflund, Surface characterization study of InP(100) substrates using ISS, AES and ESCA: comparison of substrates from two different commercial sources  Hoffmann, P., B. Lecohier, S. Goldoni and H. van den Bergh, Fast laser writ-	Control of the Al/GaAs Schottky		Hook, K.J., T.J. Hook, J.H. Wandass and	
Hishinuma, A., T. Goda, M. Kitaoka, S. Hayashi and H. Kawahara, Formation of silicon dioxide films in acidic solutions  Hizem, N., G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double and single acceptor state of isolated Ni <sub>Ga</sub> in GaAs  Ho, P.S., Chemistry and adhesion of metal-polymer interfaces  Höchst, H., see Nelson  Hockje, S.J. and G.B. Hoflund, Surface characterization study of InP(100) substrates using ISS, AES and ESCA: comparison of substrates from two different commercial sources  Hoshinuma, A., T. Goda, M. Kitaoka, S.  Hayashi and H. Kawahara, Formation of silconted wisined acide (1990) 252  Hook, T.J., see Hook  Hook, T.J., see Hook  Horányi, T.S., P. Tüttö and G. Endrédi, Improved method for depth profiling of multilayer structures  Horike, Y., T. Ichihara and H. Sakaue, Filling of Si oxide into a deep trench using digital CVD method  Horikawa, H., M. Akiyama, S. Onozawa, Y. Kawai and M. Sakuta, Interfacial layers of InP/Si heteroepitaxy  Horio, Y., see Hook  Horike, Y., T. Ichihara and H. Sakaue, Filling of Si oxide into a deep trench using digital CVD method  Horikawa, H., M. Akiyama, S. Onozawa, Y. Kawai and M. Sakuta, Interfacial layers of InP/Si heteroepitaxy  Horio, Y., see Hook  Horianyi, T.S., P. Tüttö and G. Endrédi, Improved method for depth profiling of multilayer structures  Horike, Y., T. Ichihara and H. Sakaue, Filling of Si oxide into a deep trench using digital CVD method  Horikawa, H., M. Akiyama, S. Onozawa, Y. Kawai and M. Sakuta, Interfacial layers of InP/Si heteroepitaxy  Horio, Y., see Hook  Horianyi, T.S., P. Tüttö and G. Endrédi, Improved method for depth profiling of multilayer structures  Horike, Y., T. Ichihara and H. Sakaue, Filling of Si oxide into a deep trench using digital CVD method  Horikawa, H., M. Akiyama, S. Onozawa, Y. Kawai and M. Sakuta, Interfacial layers of InP/Si heteroepitaxy  Horio, Y., see Hook  Horianyi, T.S., P. Tüttö and G. Endrédi, Improved method for depth profiling of Si oxide into a deep trench us	barrier height using a rare-earth metal			
Hayashi and H. Kawahara, Formation of silicon dioxide films in acidic solutions  48/49 (1991) 405  Hizem, N., G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double and single acceptor state of isolated Ni Ga in GaAs  Ho, P.S., Chemistry and adhesion of metal-polymer interfaces  Höchst, H., see Nelson  Hoekje, S.J. and G.B. Hoflund, Surface characterization study of InP(100) substrates using ISS, AES and ESCA: comparison of substrates from two different commercial sources  Hoshar, P., B. Lecohier, S. Goldoni and H. van den Bergh, Fast laser writ-  Spectrometry. Erratum  44 (1990) 252  Hook, T.J., see Hook  Hook, T.J., see Hook  Hook, T.J., see Hook  Horian, T.S., P. Tüttö and G. Endrédi, Improved method for depth profiling of multilayer structures  Filling of Si oxide into a deep trench using digital CVD method  46 (1990) 168  Horia, W. J., See Hook  Horianyi, T.S., P. Tüttö and G. Endrédi, Improved method for depth profiling of multilayer structures  Horiike, Y., T. Ichihara and H. Sakaue, Filling of Si oxide into a deep trench using digital CVD method  46 (1990) 168  Horianyi, T.S., P. Tüttö and G. Endrédi, Improved method for depth profiling of multilayer structures  Horiike, Y., T. Ichihara and H. Sakaue, Filling of Si oxide into a deep trench using digital CVD method  46 (1990) 168  Horianyi, T.S., P. Tüttö and G. Endrédi, Improved method for depth profiling of multilayer structures  Horiike, Y., T. Ichihara and H. Sakaue, Filling of Si oxide into a deep trench using digital CVD method  46 (1990) 168  Horianyi, T.S., P. Tüttö and G. Endrédi, Improved method for depth profiling of multilayer structures  46 (1990) 168  Horianyi, T.S., P. Tüttö and G. Endrédi, Improved method for depth profiling of multilayer structures  47 (1991) 490  48 (1991) 490  48 (1991) 490  49 (1991) 490  40 (1991) 490  41 (1992) 598  41 (1992) 598  41 (1992) 598  41 (1993) 598  42 (1994) 491  43 (1990) 252		41/42 (1989) 174		
of silicon dioxide films in acidic solutions  48/49 (1991) 405  Hizem, N., G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double and single acceptor state of isolated Ni <sub>Ga</sub> in GaAs  Hö, P.S., Chemistry and adhesion of metal-polymer interfaces  Höchst, H., see Nelson  Hoekje, S.J. and G.B. Hoflund, Surface characterization study of InP(100) substrates using ISS, AES and ESCA: comparison of substrates from two different commercial sources  Hook, T.J., see Hook  Hook, T.J., see Hook  Horányi, T.S., P. Tüttö and G. Endrédi, Improved method for depth profiling of multilayer structures  50 (1991) 439  Horiike, Y., T. Ichihara and H. Sakaue, Filling of Si oxide into a deep trench using digital CVD method  46 (1990) 168  Horikawa, H., M. Akiyama, S. Onozawa, Y. Kawai and M. Sakuta, Interfacial layers of InP/Si heteroepitaxy  41/42 (1989) 598  Horin, M., see Falta  Horn, M., see Falta  41/42 (1989) 230  47 (1991) 43  Hosaka, T., Effects of impurities in a two-layer evaporated Au film on its tensile fracture  48/49 (1991) 502	Hishinuma, A., T. Goda, M. Kitaoka, S.		The state of the s	
tions  Hizem, N., G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double and single acceptor state of isolated Ni Ga in GaAs  Ho, P.S., Chemistry and adhesion of metal-polymer interfaces Höchst, H., see Nelson Hoekje, S.J. and G.B. Hoflund, Surface characterization study of InP(100) substrates using ISS, AES and ESCA: comparison of substrates from two different commercial sources Hoizen, N., G. Bremond, L. Mayet, M. Horányi, T.S., P. Tüttö and G. Endrédi, Improved method for depth profiling of multilayer structures Filling of Si oxide into a deep trench using digital CVD method 46 (1990) 168 Horikawa, H., M. Akiyama, S. Onozawa, Y. Kawai and M. Sakuta, Interfacial layers of InP/Si heteroepitaxy Horio, Y., see Ichimiya Horn, M., see Falta Horn, M., see Falta Horn, M., see Falta Horn, M., see Pan Hosaka, T., Effects of impurities in a two-layer evaporated Au film on its tensile fracture  48/49 (1991) 502	Hayashi and H. Kawahara, Formation			
Hizem, N., G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double and single acceptor state of isolated Ni Ga in GaAs Ho, P.S., Chemistry and adhesion of metal-polymer interfaces Höchst, H., see Nelson Hoekje, S.J. and G.B. Hoflund, Surface characterization study of InP(100) substrates using ISS, AES and ESCA: comparison of substrates from two different commercial sources Horimann, P., B. Lecohier, S. Goldoni and H. van den Bergh, Fast laser writ-  Horányi, T.S., P. Tüttö and G. Endrédi, Improved method for depth profiling of multilayer structures 50 (1991) 143 Horiike, Y., T. Ichihara and H. Sakaue, Filling of Si oxide into a deep trench using digital CVD method 46 (1990) 168 Horikawa, H., M. Akiyama, S. Onozawa, Y. Kawai and M. Sakuta, Interfacial layers of InP/Si heteroepitaxy Horio, Y., see Ichimiya Horin, M., see Falta Horanyi, T.S., P. Tüttö and G. Endrédi, Improved method for depth profiling of multilayer structures 50 (1991) 143 Horiike, Y., T. Ichihara and H. Sakaue, Filling of Si oxide into a deep trench using digital CVD method 46 (1990) 168 Horikawa, H., M. Akiyama, S. Onozawa, Y. Kawai and M. Sakuta, Interfacial layers of InP/Si heteroepitaxy Horio, Y., see Ichimiya 41/42 (1989) 598 Horn, M., see Falta Horing, Shean-Ren, see Pan Hosaka, T., Effects of impurities in a two-layer evaporated Au film on its tensile fracture 48/49 (1991) 502	of silicon dioxide films in acidic solu-			44 (1990) 29
Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double and single acceptor state of isolated Ni Ga in GaAs  Ho, P.S., Chemistry and adhesion of metal-polymer interfaces Höchst, H., see Nelson Hoekje, S.J. and G.B. Hoflund, Surface characterization study of InP(100) substrates using ISS, AES and ESCA: comparison of substrates from two different commercial sources Hoffmann, P., B. Lecohier, S. Goldoni and H. van den Bergh, Fast laser writ-  Improved method for depth profiling of multilayer structures Horiike, Y., T. Ichihara and H. Sakaue, Filling of Si oxide into a deep trench using digital CVD method 46 (1990) 168 Horikawa, H., M. Akiyama, S. Onozawa, Y. Kawai and M. Sakuta, Interfacial layers of InP/Si heteroepitaxy Horio, Y., see Ichimiya 41/42 (1989) 598 Horn, M., see Falta 41/42 (1989) 230 Horng, Shean-Ren, see Pan 47 (1991) 43 Hosaka, T., Effects of impurities in a two-layer evaporated Au film on its tensile fracture 48/49 (1991) 502	tions	48/49 (1991) 405		44 (1990) 252
W. Ulrici, Identification of the double and single acceptor state of isolated Ni <sub>Ga</sub> in GaAs  Horiike, Y., T. Ichihara and H. Sakaue, Filling of Si oxide into a deep trench using digital CVD method  Ho, P.S., Chemistry and adhesion of metal-polymer interfaces  Höchst, H., see Nelson  Höchst, S.J. and G.B. Hoflund, Surface characterization study of InP(100) substrates using ISS, AES and ESCA: comparison of substrates from two different commercial sources  Hoffmann, P., B. Lecohier, S. Goldoni and H. van den Bergh, Fast laser writ-  Of multilayer structures  Horiike, Y., T. Ichihara and H. Sakaue, Filling of Si oxide into a deep trench using digital CVD method  Horiike, Y., T. Ichihara and H. Sakaue, Filling of Si oxide into a deep trench using digital CVD method  Horikawa, H., M. Akiyama, S. Onozawa, Y. Kawai and M. Sakuta, Interfacial layers of InP/Si heteroepitaxy  Horio, Y., see Ichimiya  Horn, M., see Falta  Horn, M., see Pan  Hosaka, T., Effects of impurities in a two-layer evaporated Au film on its tensile fracture  48/49 (1991) 502	Hizem, N., G. Bremond, L. Mayet, M.			
and single acceptor state of isolated Ni <sub>Ga</sub> in GaAs  Horiike, Y., T. Ichihara and H. Sakaue, Filling of Si oxide into a deep trench using digital CVD method  Horikawa, H., M. Akiyama, S. Onozawa, Höchst, H., see Nelson  Hoekje, S.J. and G.B. Hoflund, Surface characterization study of InP(100) substrates using ISS, AES and ESCA: comparison of substrates from two different commercial sources  Horiike, Y., T. Ichihara and H. Sakaue, Filling of Si oxide into a deep trench using digital CVD method  46 (1990) 168 Horikawa, H., M. Akiyama, S. Onozawa, Y. Kawai and M. Sakuta, Interfacial layers of InP/Si heteroepitaxy Horio, Y., see Ichimiya  41/42 (1989) 598 Horn, M., see Falta 41/42 (1989) 230 Horng, Shean-Ren, see Pan  47 (1991) 43 Hosaka, T., Effects of impurities in a two-layer evaporated Au film on its tensile fracture  48/49 (1991) 502				
Ni Ga in GaAs  Ho, P.S., Chemistry and adhesion of metal-polymer interfaces  Höchst, H., see Nelson  Hoekje, S.J. and G.B. Hoflund, Surface characterization study of InP(100) substrates using ISS, AES and ESCA: comparison of substrates from two different commercial sources  Hoffmann, P., B. Lecohier, S. Goldoni and H. van den Bergh, Fast laser writ-  Sol (1991) 490  Filling of Si oxide into a deep trench using digital CVD method  46 (1990) 168  Horikawa, H., M. Akiyama, S. Onozawa, Y. Kawai and M. Sakuta, Interfacial layers of InP/Si heteroepitaxy  41/42 (1989) 598  Horio, Y., see Ichimiya  41/42 (1989) 82  Horn, M., see Falta  41/42 (1989) 230  Horng, Shean-Ren, see Pan  47 (1991) 43  Hosaka, T., Effects of impurities in a two-layer evaporated Au film on its tensile fracture  48/49 (1991) 502				50 (1991) 143
Ho, P.S., Chemistry and adhesion of metal-polymer interfaces  Höchst, H., see Nelson  Hoekje, S.J. and G.B. Hoflund, Surface characterization study of InP(100) substrates using ISS, AES and ESCA: comparison of substrates from two different commercial sources  Hoffmann, P., B. Lecohier, S. Goldoni and H. van den Bergh, Fast laser writ-  Hoky (1989) 559  Horikawa, H., M. Akiyama, S. Onozawa, Y. Kawai and M. Sakuta, Interfacial layers of InP/Si heteroepitaxy  Horikawa, H., M. Akiyama, S. Onozawa, Y. Kawai and M. Sakuta, Interfacial layers of InP/Si heteroepitaxy  Horio, Y., see Ichimiya  Horn, M., see Falta  Horn, M., see Falta  Hosaka, T., Effects of impurities in a two-layer evaporated Au film on its tensile fracture  48/49 (1991) 502				
metal-polymer interfaces  Höchst, H., see Nelson  Höchst, H., see Nelson  Hoekje, S.J. and G.B. Hoflund, Surface characterization study of InP(100) substrates using ISS, AES and ESCA: comparison of substrates from two different commercial sources  Hoffmann, P., B. Lecohier, S. Goldoni and H. van den Bergh, Fast laser writ-  Höchst, H., see Nelson  41/42 (1989) 559  48/49 (1991) 419  Y. Kawai and M. Sakuta, Interfacial layers of InP/Si heteroepitaxy  41/42 (1989) 598  Horikawa, H., M. Akiyama, S. Onozawa,  Y. Kawai and M. Sakuta, Interfacial layers of InP/Si heteroepitaxy  41/42 (1989) 598  Horikawa, H., M. Akiyama, S. Onozawa,  Y. Kawai and M. Sakuta, Interfacial layers of InP/Si heteroepitaxy  41/42 (1989) 598  Horikawa, H., M. Akiyama, S. Onozawa,  Y. Kawai and M. Sakuta, Interfacial layers of InP/Si heteroepitaxy  41/42 (1989) 598  Horikawa, H., M. Akiyama, S. Onozawa,  Y. Kawai and M. Sakuta, Interfacial layers of InP/Si heteroepitaxy  41/42 (1989) 230  Horn, M., see Falta  Horng, Shean-Ren, see Pan  47 (1991) 9  Hosaka, T., Effects of impurities in a two-layer evaporated Au film on its tensile fracture  48/49 (1991) 502		50 (1991) 490		
Höchst, H., see Nelson  Hoekje, S.J. and G.B. Hoflund, Surface characterization study of InP(100) substrates using ISS, AES and ESCA: comparison of substrates from two different commercial sources  Hoffmann, P., B. Lecohier, S. Goldoni and H. van den Bergh, Fast laser writ-  48/49 (1991) 419  Y. Kawai and M. Sakuta, Interfacial layers of InP/Si heteroepitaxy 41/42 (1989) 598 Horio, Y., see Ichimiya 41/42 (1989) 82 Horn, M., see Falta 41/42 (1989) 230 Horng, Shean-Ren, see Pan 47 (1991) 9 Hosaka, T., Effects of impurities in a two-layer evaporated Au film on its tensile fracture 48/49 (1991) 502				46 (1990) 168
Hoekje, S.J. and G.B. Hoflund, Surface characterization study of InP(100) Horio, Y., see Ichimiya 41/42 (1989) 598 substrates using ISS, AES and ESCA: Horn, M., see Falta 41/42 (1989) 230 comparison of substrates from two different commercial sources 47 (1991) 43 Hosaka, T., Effects of impurities in a two-layer evaporated Au film on its and H. van den Bergh, Fast laser writ-				
characterization study of InP(100) substrates using ISS, AES and ESCA: comparison of substrates from two different commercial sources Hoffmann, P., B. Lecohier, S. Goldoni and H. van den Bergh, Fast laser writ- Horio, Y., see Ichimiya Horio, Y., see Ichimiya 41/42 (1989) 82 41/42 (1989) 230 Horng, Shean-Ren, see Pan 47 (1991) 9 Hosaka, T., Effects of impurities in a two-layer evaporated Au film on its tensile fracture 48/49 (1991) 502		48/49 (1991) 419		
substrates using ISS, AES and ESCA: comparison of substrates from two different commercial sources Hoffmann, P., B. Lecohier, S. Goldoni and H. van den Bergh, Fast laser writ- Horn, M., see Falta Horn, M., see Falta Horng, Shean-Ren, see Pan 47 (1991) 9 Hosaka, T., Effects of impurities in a two-layer evaporated Au film on its tensile fracture 48/49 (1991) 502				
comparison of substrates from two different commercial sources 47 (1991) 43 Hosaka, T., Effects of impurities in a two-layer evaporated Au film on its and H. van den Bergh, Fast laser writ- 48/49 (1991) 502				
different commercial sources 47 (1991) 43 Hosaka, T., Effects of impurities in a two-layer evaporated Au film on its tensile fracture 48/49 (1991) 502				
Hoffmann, P., B. Lecohier, S. Goldoni two-layer evaporated Au film on its and H. van den Bergh, Fast laser writtensile fracture 48/49 (1991) 502	•			47 (1991) 9
and H. van den Bergh, Fast laser writ- tensile fracture 48/49 (1991) 502		47 (1991) 43	· · · · · · · · · · · · · · · · · · ·	
				40 440 42224
ing of copper and iridium lines from Hotchandani, S., see Diarra 48/49 (1991) 567				
	ing of copper and iridium lines from		Hotchandani, S., see Diarra	48/49 (1991) 567

Hardton M.D. and Lon	50 (1991) 428	Inada, T., see Itoh	41/42 (1989) 262
Houlton, M.R., see Lee	46 (1990) 175	Indlekofer, G., see Mansour	48/49 (1991) 312
Houzay, F., see Nissim Hrbek, J., see Shek	48/49 (1991) 332	Ingram, J.C., K.W. Nebesny and J.E.	40/49 (1991) 312
Hricovini, K., see Le Lay	41/42 (1989) 25	Pemberton, Optical properties of metal	
Hu, B., A. Seidl, R. Buchner, D. Boll-	41/42 (1969) 23	surfaces from electron energy loss	
mann, W. van der Wel and K. Ha-		spectroscopy in the reflection mode	44 (1990) 279
berger, Investigation of laser recrys-		Ingram, J.C., K.W. Nebesny and J.E.	44 (1770) 217
tallization of thin Si films using		Pemberton, Optical constants of the	
numerical simulation	46 (1990) 388	noble metals determined by reflection	
Hu Liqun, see Zhang Rong	48/49 (1991) 356	electron energy loss spectroscopy	44 (1990) 293
Hua, Z.Y., see Qiu	48/49 (1991) 430	Ingram, J.C., K.W. Nebesny and J.E.	(2550) 250
Huang, J.H., see Williams	41/42 (1989) 70	Pemberton, Optical properties of	
Hubbard, A.T., see Frank	48/49 (1991) 166	selected first-row transition metals de-	
Hubbard, C.W., see Baer	45 (1990) 71	termined by reflection electron energy	
Huber, A.M., see Grattepain	50 (1991) 42	loss spectroscopy	45 (1990) 247
Huber, R., see Schmaderer	46 (1990) 53	Ingram, J.C., K.W. Nebesny and J.E.	, , , , , , , , , , , , , , , , , , , ,
Hudson, J.B., see Interrante	46 (1990) 5	Pemberton, Optical properties of metal	
Hughes, G.J., see O'Connor	50 (1991) 312	surfaces from electron energy loss	
Hughes, G.J., see Roberts	50 (1991) 424	spectroscopy in the reflection mode.	
Huisman, M., see Balkenende	47 (1991) 341	Erratum	45 (1990) 278
Humphrey, P., see Occhiello	47 (1991) 235	Inoue, K., M. Okuyama and Y. Hamaka-	
Hünermann, M., see Esser	41/42 (1989) 169	wa, Optical and interfacial properties	
Huong, P.V., O. Segond, P. Gentilini and		of SiO <sub>2</sub> films deposited on Si by	
R. Cavagnat, Silicon aggregates pro-		photo-CVD	41/42 (1989) 407
duced by laser beam in a silicon		Inoue, K., see Okuyama	41/42 (1989) 633
carbide surface	43 (1989) 256	Inoue, M., see Yano	41/42 (1989) 457
Hütten, H.M., KD. Raddatz, M.K.		Interrante, L.V., B. Han, J.B. Hudson and	
Sharma and J. Engemann, On the two-		C. Whitmarsh, Design and synthesis	
and three-dimensional simulation of		of CVD precursors to thin film ceramic	
ion-milled structures	46 (1990) 306	materials	46 (1990) 5
Hwang, H.L., see Jiang	48/49 (1991) 392	Ipatova, I.P., see Bairamov	50 (1991) 300
		Irmer, G., see Bairamov	50 (1991) 300
		Ishida, H., see Yoshida	44 (1990) 301
		Ishihara, N., see Nakanishi	41/42 (1989) 44
	46 (4000) 460	Ishihara, N., see Nishimori	41/42 (1989) 49
Ichihara, T., see Horiike	46 (1990) 168	Ishihara, N., see Nishimori	47 (1991) 365
Ichimiya, A., S. Kohmoto, T. Fujii and Y.		Ishihara, N., see Kishida	48/49 (1991) 446
Horio, RHEED intensity analysis of	41 (42 (1000) 02	Ishihara, N., see Nishimori	48/49 (1991) 450
$Si(111)\sqrt{3} \times \sqrt{3}$ -Ag structure	41/42 (1989) 82	Ishihara, S., see Yokota	41/42 (1989) 411
Ichimiya, A., see Kohmoto	41/42 (1989) 107	Ishii, A., see Ishii	41/42 (1989) 390
Ichimura, M., see Wada	41/42 (1989) 580	Ishii, H., see Hasegawa	41/42 (1989) 372
Igarashi, Y., T. Yamaji, S. Nishikawa and		Ishii, H., H. Hasegawa, A. Ishii and H. Ohno, X-ray photo-electron spectros-	
S. Ohno, Influence of annealing ambients on ZrSi, formation	41 /42 (1080) 282	copy analysis of InP insulator-semi-	
bients on ZrSi <sub>2</sub> formation	41/42 (1989) 282 45 (1990) 171	conductor structures prepared by	
Igari, Y., see Kusunoki Igata, N., see Yumoto	48/49 (1991) 173	anodic oxidation	41/42 (1989) 390
Ihlemann, J., see Bolle	46 (1990) 279	Ishii, M., see Kanamoto	41/42 (1989) 526
Iioka, M., see Kawadzu	41/42 (1989) 296	Ishikawa, H., see Sasaki	41/42 (1989) 342
Iizuka, K., T. Yoshida, M. Hasobe, I.	41/42 (1909) 290	Ishikawa, K., see Takeuchi	41/42 (1989) 530
Matsuda and T. Suzuki, Raman study		Ishitsuka, T., see Takayanagi	41/42 (1989) 337
of the stress in MBE-grown Al <sub>x</sub>		Ishiwara, H., see Lee	41/42 (1989) 553
$Ga_{1-x}$ As on Si	41/42 (1989) 587	ISOLDE Collaboration, see Baurichter	50 (1991) 165
Ila, D., see Dalins	48/49 (1991) 509	ISOLDE Collaboration, see Jahn	50 (1991) 169
Imai, K., see Hattori	41/42 (1989) 416	Issa, A., see Dyer	43 (1989) 387
Imai, K., see Nadahara	41/42 (1989) 425	Issa, A., see Dyer	46 (1990) 89
Imamura, S., see Kanemitsu	41/42 (1989) 544	Ito, T., see Fujimura	41/42 (1989) 272
Imbihl, R., see Madden	48/49 (1991) 130	Ito, T., see Fujimura	41/42 (1989) 286
	,		,

Ito, T., A. Yamama, A. Hiraki and M.		Jannitti, E., see Berti	43 (1989) 158
Satou, Silicidation of porous silicon		Janssen, M.D., see De Wit	45 (1990) 21
and its application for the fabrication		Jantz, W., see Wang	50 (1991) 228
of a buried metal layer	41/42 (1989) 301	Jantz, W., R. Stibal, J. Windscheif and J.	()
Ito, T., see Aoyama	41/42 (1989) 584	Wagner, Variation of material param-	
Ito, T., see Kato	41/42 (1989) 614	eters along the growth direction of	
Ito, T., T. Yasumatsu and A. Hiraki, Ho-		liquid encapsulated Czochralski grown	
moepitaxial growth of silicon on		GaAs ingots	50 (1991) 480
anodized porous silicon	44 (1990) 97	Jedlinski, J., see Quadakkers	47 (1991) 261
Ito, T., see Yasumatsu	48/49 (1991) 414	Jen, J.S., see Yoshida	44 (1990) 301
Itoh, M., M. Kinoshita, T. Ajioka, M.		Jezequel, G., see Ludeke	41/42 (1989) 151
Itoh and T. Inada, Crystalline quality		Jezierski, K., Z. Gumienny and J. Mis-	, (2,0), 202
of heteroepitaxial silicon on epitaxial		iewicz, Reflectometry-aided surface	
NiSi <sub>2</sub> /Si(100)	41/42 (1989) 262	layer investigation	50 (1991) 341
Itoh, M., see Itoh	41/42 (1989) 262	Jiang Ruolian, see Zhang Rong	48/49 (1991) 356
Itoh, T., see Suguro	41/42 (1989) 277	Jiang, Y.L. and H.L. Hwang, Electron	, ()
Ivanov, A.I., see Tokarev	44 (1990) 241	transport in hydrogenated amorphous	
Iwai, Y., see Yano	41/42 (1989) 457	silicon quantum wells	48/49 (1991) 392
Iwami, M., M. Kusaka, M. Hirai and H.	, ( , , , , , , , , , , , , , , , , , ,	Jin, Y., see Gao	50 (1991) 131
Nakamura, A new non-destructive		Jiříček, P., see Kubátová	43 (1989) 297
analysis of semiconductor heterojunc-		Jo, J.W., see Han	48/49 (1991) 104
tions with very thin surface layers: an		Jobic, S., see Morsli	50 (1991) 500
application of soft X-ray spectroscopy		John, P., see Jubber	43 (1989) 74
to Si-compound (film)/Si (substrate)	41/42 (1989) 57	Johnson, D., see Occhiello	47 (1991) 235
Iwami, M., M. Kusaka, M. Hirai, M.	/ (/	Johnson, D.L., see Halpern	48/49 (1991) 19
Kubota, H. Tochihara and Y. Murata,		Jones, K., see Deneuville	50 (1991) 308
Mechanism of alloy formation due to		Jones, R.G., see Mowbray	48/49 (1991) 27
noble metal deposition on silicon sur-		Jones, T.S., M.Q. Ding, N.V. Richardson	, (,
faces at room temperature: chemical		and C.F. McConville, The effects of	
bonding model	41/42 (1989) 97	surface damage on surface plasmon	
Iwami, M., see Kamiura	41/42 (1989) 447	excitations in doped InSb(100)	45 (1990) 85
Iyer, S.S., see Arienzo	48/49 (1991) 377	Joud, J.C., see Eymery	47 (1991) 127
Izawa, Y., see Sumitomo	41/42 (1989) 112	Jubber, M., J.I.B. Wilson, J.L. Davidson,	()
Izrael, A., see Crean	50 (1991) 281	P.A. Fernie and P. John, Laser writing	
	()	of high purity gold tracks	43 (1989) 74
		Julien, C. and M. Balkanski, Thin-film	(2.27)
Jackman, R.B., see Brown	43 (1989) 382	growth and structure for solid-state	
Jackman, R.B., see Tyrrell	43 (1989) 439	batteries	48/49 (1991) 1
Jadin, A., I.V. Filiouguine, M. Wautelet		Jusserand, B., see Crean	50 (1991) 281
and L.D. Laude, Influence of the sub-		Jusserand, B. and F. Mollot, Confined	()
strate on the temperature induced by		optical vibrations: a new probe for	
pulsed laser irradiation of thin films	46 (1990) 375	alloy disorder	50 (1991) 317
Jaeger, H., see Bartlett	47 (1991) 187	•	**
Jahn, S.G., H. Hofsäss, U. Wahl, S.			
Winter, E. Recknagel and ISOLDE		Kaburagi, M., see Urano	41/42 (1989) 103
Collaboration, Structural defect re-		Kahn, A., see Mao	48/49 (1991) 324
covery in GaP after heavy ion implan-		Kaida, T., see Yasuda	41/42 (1989) 429
tation	50 (1991) 169	Kaiser, W.J., see Hecht	41/42 (1989) 17
Jahne, E., see Bairamov	50 (1991) 300	Kakibayashi, H., see Goto	41/42 (1989) 480
Jain, S.C., A. Atkinson and W.S. Khokle,		Kaliński, Z., see Tatarkiewicz	50 (1991) 249
Relationship between mechanical,		Kalish, R., see Pfeiffer	50 (1991) 154
electronic and vibrational properties		Kalki, K., B. Pennemann, U. Schröder,	
of $Ge_xSi_{1-x}$ strained layers	48/49 (1991) 387	W. Heichler and K. Wandelt, Proper-	
James, J.H., B.J. Kellett, A. Gauzzi, B.		ties of noble metal and binary alloy	40 440 44-5-5
Dwir and D. Pavuna, In-situ super-		monolayer films on Ru(001)	48/49 (1991) 59
conducting YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7</sub> thin films	40 14 0001 000	Kamimura, K., Y. Takase, Y. Onuma and	
grown by ion beam co-deposition	43 (1989) 393	A. Kunioka, Surface nitridation of InP	41 /40 /1000 440
Jammul, N., see Nogier	47 (1991) 287	with a N <sub>2</sub> plasma	41/42 (1989) 443

		V	40 (40 (1001) 410
Kamiura, Y., F. Hashimoto and M.		Kazmerski, L.L., see Nelson	48/49 (1991) 419
Iwami, Iron accumulation at the Si-		Keir, A.M., S.J. Barnett, J. Giess, T.D.	
SiO <sub>2</sub> interface and possible reduction	41 /42 /1000) 447	Walsh and M.G. Astles, A combina-	
of SiO <sub>2</sub>	41/42 (1989) 447	tion of high-resolution X-ray dif-	
Kanaji, T., see Urano	41/42 (1989) 103	fractometry and diffraction imaging	
Kanaji, T., see Hongo	41/42 (1989) 522	techniques applied to the study of	
Kanaji, T., see Hongo	48/49 (1991) 143	MOVPE-grown $Cd_xHg_{1-x}Te/CdTe$ on GaAs	50 (1991) 103
Kanamoto, K., K. Fujiwara, Y. Tokuda,		Kelber, J.A., J.W. Rogers, Jr., B.A. Banse	30 (1991) 103
N. Tsukada, M. Ishii and T. Nakaya- ma, Photoluminescence line shape due		and B.E. Koel, Interaction of dimeth-	
		ylamine with clean and partially	
to arrayed steps at the interfaces of		oxidized copper surfaces	44 (1990) 193
GaAs/AlGaAs single quantum wells grown on vicinal surfaces by molecu-		Keller, R., see Pfeiffer	50 (1991) 154
	41/42 (1989) 526	Keller, R., see Magerle	50 (1991) 159
lar beam epitaxy	41/42 (1909) 320	Kellett, B.J., see James	43 (1989) 393
Kanemitsu, Y. and S. Imamura, Charge		Kelly, J.J., see De Wit	45 (1990) 21
transport and trapping at the interface	41/42 (1989) 544	Kelly, W.M., see Crean	50 (1991) 281
in two-layer organic photoconductors	48/49 (1991) 104	Kempf, B., see Dinges	50 (1991) 359
Kang, K.N., see Han Kanski, J., see Morar	41/42 (1989) 312	Kendelewicz, T., see Spicer	41/42 (1989) 1
Kar, S., A. Raychaudhuri, A.K. Sinha and	41/42 (1909) 312	Kendelewicz, T., see Soukiassian	41/42 (1989) 395
S. Ashok, Ion beam modification of		Kessler, T., see Korzec	46 (1990) 299
the dielectric properties of thin silicon		Kesting, W., T. Bahners and E. Scholl-	40 (1990) 299
dioxide films	48/49 (1991) 264	meyer, Controlled structuring of poly-	
Karimi, M., see Li	48/49 (1991) 160	mer surfaces by UV-laser irradiation	46 (1990) 326
Karimi, M., see Dalins	48/49 (1991) 509	Kevan, S.D., see Smith	48/49 (1991) 135
Karlsson, U.O., see Morar	41/42 (1989) 312	Key, P.H., see Dyer	43 (1989) 387
Karulkar, P.C., R.J. Hillard, J.M. Heddle-	41/42 (1909) 312	Key, P.H., see Dyer	46 (1990) 89
son and P. Rai-Choudhury, A pres-		Kezuka, H. and T. Masaki, Characteriza-	40 (1990) 69
sure contact current-voltage tech-		tion of the surface of high- $T_c$ Y-Ba-	
nique for rapid characterization of thin		Cu-O	48/49 (1991) 454
dielectric films	48/49 (1991) 237	Khan, S.U.M., J.P. Baltrus, R.W. Lai and	40/47 (1771) 434
Kasemo, B., see Lausmaa	44 (1990) 133	A.G. Richardson, X-ray photoelectron	
Kasemo, B., see Lausmaa	45 (1990) 189	spectroscopic study of the interaction	
Kasper, E., see Holländer	50 (1991) 450	of xanthate with coal pyrite and	
Kassi, H., see Diarra	48/49 (1991) 567	mineral pyrite surfaces	47 (1991) 355
Kataoka, Y., see Hongo	41/42 (1989) 522	Khial, M., see Sébenne	41/42 (1989) 352
Katayama, I., see Sumitomo	41/42 (1989) 112	Khokle, W.S., see Jain	48/49 (1991) 387
Katayama, I., T. Hanawa, F. Shoji and K.	11/ 12 (1707) 111	Kibardin, A.V., see Tokarev	44 (1990) 235
Oura, ISS-AES study of the initial		Kim, H.J., see Murakami	41/42 (1989) 195
growth stage of Cu thin films on		Kim, J.S., see Banerjee	48/49 (1991) 288
Si(111)-7 × 7	48/49 (1991) 361	Kim, J.S., P.K. Banerjee, S.S. Mitra, H.	10, 11 (2172) 200
Katayama, M., see King	48/49 (1991) 246	Shastry, J.J. Loferski and R. Beaulieu,	
Kato, Y., T. Ito and A. Hiraki, Low tem-	()	Optical, electrical and mechanical	
perature oxidation of crystalline por-		properties of RF-sputtered TiN-W-	
ous silicon	41/42 (1989) 614	Au films	48/49 (1991) 548
Katsui, A., see Sasaki	41/42 (1989) 504	Kimura, I., see Yokota	41/42 (1989) 411
Kaufel, G., see Zappe	50 (1991) 290	Kimura, M., A. Tanaka and T. Sukegawa,	()
Kawadzu, Y., M. Iioka, A. Fujii, H.		Dissolution process of silicon in an	
Oyanagi and T. Arai, Interfacial reac-		indium solution	48/49 (1991) 185
tion of nickel/hydrogenated amor-		King, B.V., D.J. O'Connor, Y. Shen, R.J.	, , , , , , , , , , , , , , , , , , , ,
phous silicon system at low tempera-		MacDonald, M. Katayama and M.	
ture studied by fluorescence EXAFS	41/42 (1989) 296	Aono, LEIS for structure determina-	
Kawahara, H., see Hishinuma	48/49 (1991) 405	tion of surfaces and thin films	48/49 (1991) 246
Kawai, Y., see Horikawa	41/42 (1989) 598	King, D.E., J.E. Fernandez and W.E.	
Kawakyu, Y., see Sasaki	41/42 (1989) 342	Swartz, An XPS study of the doping	
Kawamura, T., see Yamada Maruo	41/42 (1989) 647	of trans, trans-p-distyrylbenzene with	
Kawarada, H., see Ma	41/42 (1989) 572	AsF <sub>5</sub> : a model conducting polymer	
Kawata, M., see Goto	41/42 (1989) 480	system	45 (1990) 325

Kingon, A.I., see Krauss	46 (1990) 67	Konstantinov, L., R. Nowak and P. Hess,	
Kinoshita, M., see Itoh	41/42 (1989) 262	Gas-phase transport and kinetics in	
Kinoshita, T., see Kono	41/42 (1989) 75	pulsed-laser CVD	46 (1990) 102
Kirlin, P.S., see Hamaguchi	48/49 (1991) 441	Kools, J.C.S., see Baller	46 (1990) 292
Kishida, S., see Nakanishi	41/42 (1989) 44	Korzec, D., T. Kessler and J. Engemann,	
Kishida, S., see Nishimori	41/42 (1989) 49	Reactive ion beam etching of Si/SiO <sub>2</sub>	
Kishida, S., see Morishige	46 (1990) 108	systems using SF <sub>6</sub> /O <sub>2</sub> chemistry	46 (1990) 299
Kishida, S., see Tokutaka	48/49 (1991) 425	Koschmieder, H., see Priggemeyer	44 (1990) 255
Kishida, S., H. Tokutaka, H. Higashi, K.	, , , , ,	Kothari, D.C. and A. Miotello, Effects on	, ,
Nishimori and N. Ishihara, Prepara-		the implanted profiles of point defect	
tion conditions of flat 80 K phase		flux during nitrogen implantation in	
Bi-Sr-Ca-Cu-O thin films by RF		copper	43 (1989) 237
magnetron sputtering	48/49 (1991) 446	Kötz, R., Ultraviolet photoelectron spec-	
Kishida, S., see Nishimori	48/49 (1991) 450	troscopy (UPS) of anodic oxide films	
Kitamura, K., see Mimura	48/49 (1991) 521	on Au, Pt, Ru and Ru <sub>0.5</sub> Ir <sub>0.5</sub> alloy	47 (1991) 109
Kitamura, S., see Morishige	46 (1990) 108	Koutník, M., see Lejček	44 (1990) 75
Kitaoka, M., see Hishinuma	48/49 (1991) 405	Kouzaki, T., see Ogawa	41/42 (1989) 290
Kiyak, S.G., see Prokhorov	43 (1989) 340	Koyama, H., see Miyatake	41/42 (1989) 643
Klapwijk, T.M., see Hibma	48/49 (1991) 209	Kozanecki, A., see Tatarkiewicz	50 (1991) 249
Klemberg-Sapieha, J.E., see Sapieha	44 (1990) 165	Krans, R.L., see Van Maaren	46 (1990) 138
Kleverman, M., see Grimmeiss	50 (1991) 52	Krašovec, M., see Quadakkers	47 (1991) 261
Klumpp, A. and H. Sigmund, Photoin-		Krauss, A.R., O. Auciello, A.I. Kingon,	
duced transformation of polysiloxane		M.S. Ameen, Y.L. Liu, T. Barr, T.M.	
layers to SiO <sub>2</sub>	43 (1989) 301	Graettinger, S.H. Rou, C.S. Soble and	
Klumpp, A., see León	46 (1990) 210	D.M. Gruen, Computer-controlled ion	
Knothe, P., see Voelskow	43 (1989) 196	beam deposition systems for high $T_c$	
Knothe, P., see Neelmeijer	43 (1989) 232	superconductor and other multi-com-	
Knudsen, J.F., see Moss	50 (1991) 337	ponent oxide thin films and layered	
Koebel, J.M., see Chibani	50 (1991) 177	structures	46 (1990) 67
Koel, B.E., see Kelber	44 (1990) 193	Kreutz, E.W., see Bode	46 (1990) 148
Kogelschatz, U., see Esrom	46 (1990) 158	Krösche, M., see Bode	46 (1990) 148
Kohara, M., see Gofuku	48/49 (1991) 343	Krüger, G., see Breuer	46 (1990) 336
Köhler, E., see Bauer	46 (1990) 113	Kubátová, J., V. Cháb, I. Lukeš, P. Jiříček	
Kohmoto, S., see Ichimiya	41/42 (1989) 82	and F. Fendrych, ArF excimer laser	
Kohmoto, S., S. Mizuno and A. Ichimiya,		induced changes in the Si(100)/SiO <sub>2</sub>	
RHEED intensity analysis of Li/		interface studied in situ by ESCA and	
Si(111) structures	41/42 (1989) 107	LEED	43 (1989) 297
Koide, Y., see Yasuda	41/42 (1989) 429	Kubota, M., see Iwami	41/42 (1989) 97
Koide, Y., see Ohshima	48/49 (1991) 69	Kudo, K., see Kuniyoshi	43 (1989) 447
Koike, N., see Hattori	41/42 (1989) 416	Kudoyarova, V.Kh., G.M. Gusinsky, L.A.	
Kolev, K., M. Wautelet and L.D. Laude,		Rassadin and I.V. Kudryavtsev, Hy-	
CW laser-induced transformation of	46 (1000) 410	drogen depth profile measurement in	
thin Sb, Se and Sb <sub>2</sub> Se <sub>3</sub> films in air	46 (1990) 418	$a-Si_{1-x}C_x$ : H films by elastic recoil de-	50 (1001) 172
Kollek, H., see Breuer	46 (1990) 336	tection IV	50 (1991) 173
Kolodzey, J., see Schwarz	50 (1991) 456	Kudryavtsev, I.V., see Kudoyarova	50 (1991) 173
Koma, A., K. Saiki and Y. Sato, Hetero-		Kuen-Lau, K., see Sajjadi	46 (1990) 84
epitaxy of a two-dimensional material on a three-dimensional material	41 /42 (1090) 451	Kulkarni, A.K. and A.J. Canale, Electri- cal and structural characterization of	
	41/42 (1989) 451	Co and Ni silicide contacts to silicon	48/49 (1991) 307
Koma, A., see Lee	41/42 (1989) 553 48/49 (1991) 281	Kumar, S.R., see Gore	48/49 (1991) 530
Komem, Y., see Berger Konishi, S., see Saitoh	41/42 (1989) 402		40/49 (1991) 330
	41/42 (1909) 402	Kumomi, H., T. Yonehara, Y. Nishigaki	
Kono, S., Y. Enta, T. Abukawa, T. Kinoshita and T. Sakamoto, Photo-		and N. Sato, Selective nucleation based epitaxy (Sentaxy). Investigation	
electron spectroscopy and photoelec-		of initial nucleation stages	41/42 (1989) 638
tron diffraction studies of Si(001)		Kunioka, A., see Kamimura	41/42 (1989) 443
$2 \times 1$ -K and -Cs surfaces	41/42 (1989) 75	Kuniyoshi, S., K. Kudo and K. Tanaka,	71/72 (1707) 773
Z / I II und -C5 surfaces	11/ 12 (1707) 13	rainjoon, S., R. Rudo and R. Tanaka,	

Surface modification of low density		and surface spectroscopy studies of	
polyethylene by N <sup>+</sup> , Ar <sup>+</sup> ion implan-	40 (4000) 447	prototypical systems: lead-semicon-	44 449 (4000) 25
tation for space charge devices	43 (1989) 447	ductor interfaces	41/42 (1989) 25
Kurz, H., see Esser	46 (1990) 446	Le Mogne, Th., see Bou	47 (1991) 149
Kurz, H., see Kütt	50 (1991) 325	Lebland, R.M., see Diarra	48/49 (1991) 567
Kusaka, M., see Iwami	41/42 (1989) 57	Lebland, F., see Nissim	46 (1990) 175
Kusaka, M., see Iwami	41/42 (1989) 97	Lecohier, B., see Hoffmann	43 (1989) 54
Kusunoki, I., M. Hiroi, T. Sato, Y. Igari and S. Tomoda, SiC film formation on		Lecohier, B. and H. van den Bergh, Selective copper film growth on platinum	
Si(001) by reaction with $C_2H_2$ beams	45 (1990) 171	clusters	43 (1989) 61
Kütt, W., see Esser	46 (1990) 446	Lee, D., S.J. Barnett, A.D. Pitt, M.R.	43 (1909) 01
Kütt, W., G.C. Cho, M. Strahnen and H.	40 (1770) 440	Houlton and G.W. Smith, Characteri-	
Kurz, Electro-optic sampling of		zation of alloy composition in $Ga_{1-x}$	
surface space-charge fields on III-V		Al <sub>x</sub> As/GaAs structures: comparison	
compounds	50 (1991) 325	of photovoltage, X-ray, SIMS and	
Kwietniak, M.S., see Pain	48/49 (1991) 76	RHEED techniques	50 (1991) 428
Kyriakidis, G., see Dimoulas	50 (1991) 353	Lee, H.C., H. Ishiwara, S. Furukawa, K.	
	,	Saiki and A. Koma, Distribution of	
La Ferla, A., see Priolo	41/42 (1989) 619	interfacial As atoms in the electron-	
La Ferla, A., see Priolo	43 (1989) 178	beam exposure and epitaxy (EBE-epi-	
Lacharme, J.P., see Sébenne	41/42 (1989) 352	taxy) technique for growing GaAs	
Lacharme, J.P., see Orlowski	41/42 (1989) 491	films on CaF <sub>2</sub> /Si(111) structures	41/42 (1989) 553
Lacquet, B.M., see Swart	50 (1991) 330	Lee, J., see Pemble	46 (1990) 32
Lai, R.W., see Khan	47 (1991) 355	Lee, J.I., see Han	48/49 (1991) 104
Lakits, G., see Aumayr	47 (1991) 139	Lee, W.S., R.A. Outlaw, G.B. Hoflund	
Lam, D.J., see Chang	48/49 (1991) 12	and M.R. Davidson, Auger electron	
Lamberti, C., see Antolini	50 (1991) 212	intensity variations in oxygen-charged	
Lancefield, D., see Pickering	50 (1991) 346	silver	47 (1991) 91
Landa, G., see Raisin	50 (1991) 434	Lee, Y.C., see Oral	44 (1990) 65
Landers, R., see Morais	44 (1990) 161	Lee, Y.J., see Han	48/49 (1991) 104
Lange, R., see Golusda	46 (1990) 230	Leggieri, G., see Craciun	43 (1989) 304
Lanzieri, C., see Nipoti	50 (1991) 410	Leggieri, G., see D'Anna	46 (1990) 365
Lapicque, F., see Zouari	46 (1990) 411	Leitch, A.W.R., Th. Prescha and M.	
Larciprete, R., Photoprocesses in	14 (1000) 10	Stutzmann, Hydrogen passivation and	
organometallics	46 (1990) 19	reactivation of shallow Zn acceptors	
Lascovich, J.C., R. Giorgi and S. Scagl-		in GaAs	50 (1991) 390
ione, Evaluation of the sp <sup>2</sup> /sp <sup>3</sup> ratio		Lejček, P., M. Koutník, J. Brádler, V.	
in amorphous carbon structure by XPS	47 (1001) 17	Paidar and A. Potměšilová, Ani-	
and XAES	47 (1991) 17	sotropy of grain boundary segregation	
Lassabatere, L., see Raisin	50 (1991) 434	in as-grown Fe-6at%Si alloy bi-	44 (1000) 75
Laude, L.D., see Jadin	46 (1990) 375	crystals	44 (1990) 75
Laude, L.D., see Kolev	46 (1990) 418	Lenkkeri, J., see Milne	43 (1989) 81
Lausmaa, J., B. Kasemo and H. Mattsson,		Lentfort, B., see Hettwer	50 (1991) 470
Surface spectroscopic characterization of titanium implant materials	44 (1990) 133	León, B., see Garrido León, B., see Szörényi	43 (1989) 68 46 (1990) 206
Lausmaa, J., B. Kasemo, H. Mattsson and	44 (1990) 133	León, B., A. Klumpp, M. Pérez-Amor and	40 (1990) 200
H. Odelius, Multi-technique surface		H. Sigmund, Excimer laser deposition	
characterization of oxide films on		of silica films: a comparison between	
electropolished and anodically oxi-		two methods	46 (1990) 210
dized titanium	45 (1990) 189	Lepage, J., see Zaïdi	44 (1990) 221
Layet, J.M., see Förster	41/42 (1989) 306	Lerch, W., see Hettwer	50 (1991) 470
Lazare, S., see Hiraoka	46 (1990) 264	Levade, C., J.J. Couderc, G.	30 (1991) 470
Lazare, S., see Hiraoka	46 (1990) 342	Vanderschaeve, D. Caillard and A.	
Le Bihan, R., see Chartier	45 (1990) 351	Couret, TEM in-situ observation of	
Le Guillou, Y., see L'Haridon	50 (1991) 237	recombination-enhanced mobility of	
Le Lay, G., K. Hricovini and J.E. Bonnet,	( , , , , , , , , , , , , , , , , , , ,	dislocations in II–VI compounds	50 (1991) 119
Synchrotron radiation investigation		Levenson, L.L., see Yahashi	43 (1989) 37
			()

L'Haridon, H., P.N. Favennec, R. Co-		facial structures and selective growth	
quille, M. Salvi, M. Gauneau, Y. Le		of diamond particles formed by	
Guillou, R. Callec and P. Gall, Spatial		plasma-assisted CVD	41/42 (1989) 572
investigation of an iron-doped indium	50 (1001) 207	MacDonald, R.J., see King	48/49 (1991) 246
phosphide ingot	50 (1991) 237	Machado, A.M., see Morais	44 (1990) 161
Li Qi, see Zhang Rong	48/49 (1991) 356	Mackenzie, R.A.D., J.A. Liddle and	
Li, ST., S. Hasegawa, N. Yamashita and		C.R.M. Grovenor, Ultrahigh resolu-	
H. Nakashima, Initial stages of alumi-		tion characterisation of compound	
num epitaxy on the Si(111) $\sqrt{3} \times \sqrt{3}$ -Al		semiconductors using pulsed laser	50 (1001) 10(
surface studied by electron-energy-loss	41 /42 (1090) 119	atom probe techniques	50 (1991) 196
spectroscopy	41/42 (1989) 118	Mackey, K.J., see Zahn Mackey, K.J., D.C. Rodway, P.C. Smith	41/42 (1989) 497
Li, W., JS. Lin, M. Karimi, C. Moses and G. Vidali, Structural characteriza-		and A.W. Vere, Photo-assisted	
tion of ultra-thin metal overlayers on		MOVPE growth of calcium fluoride	43 (1989) 1
Cu(001) by atom beam scattering	48/49 (1991) 160	Madden, H.H. and R. Imbihl, Interaction	43 (1909)
Licoppe, C., see Nissim	46 (1990) 175	of NO and H <sub>2</sub> with Pt(100)	48/49 (1991) 130
Liddle, J.A., see Mackenzie	50 (1991) 196	Maeda Wong, T., see Heskett	48/49 (1991) 260
Lienard, A., see Dupendant	43 (1989) 369	Maehashi, K., S. Hasegawa and H.	40/ 47 (1771) 200
Lieske, H., see Unger	45 (1990) 29	Nakashima, Atomic rearrangement	
Lietz, G., see Unger	45 (1990) 29	during the initial stages of GaAs	
Ligeon, E., see Tatarenko	41/42 (1989) 470	growth on Si(111)( $\sqrt{3} \times \sqrt{3}$ )-Ga sur-	
Ligeon, M., see Chartier	45 (1990) 351	face	41/42 (1989) 567
Liliental-Weber, Z., see Spicer	41/42 (1989) 1	Maeyama, S., see Yamada Maruo	41/42 (1989) 647
Lin, JS., see Li	48/49 (1991) 160	Maezawa, C., see Takeuchi	41/42 (1989) 530
Lin, Yuh-Lin, see Pan	47 (1991) 9	Magerle, R., see Pfeiffer	50 (1991) 154
Lindau, I., see Spicer	41/42 (1989) 1	Magerle, R., M. Deicher, U. Desnica, R.	` '
Linker, G., see Seidel	43 (1989) 97	Keller, W. Pfeiffer, F. Pleiter, H.	
Little, I., see Crean	50 (1991) 281	Skudlik and Th. Wichert, Defects in	
Liu, Y.L., see Krauss	46 (1990) 67	CdS:In detected by perturbed angular	
Loferski, J.J., see Kim	48/49 (1991) 548	correlation spectroscopy (PAC)	50 (1991) 159
Löhnert, K., see Baumgartner	50 (1991) 222	Maidorn, G., see Esser	46 (1990) 446
Lombardo, S., see Spinella	43 (1989) 187	Maillou, J.G., see Mathé	43 (1989) 142
López, C., J. Sánchez-Dehesa, F. Mese-		Maillou, J.G., E.L. Mathé, J.C. Desoyer,	
guer, F. Borondo and K. Ploog, Elec-		S. de Unamuno and E. Fogarassy,	
tronic structure of modulation n-		Comparison between microscopical	
doped multiple quantum well	41/42 (1989) 464	aspects of a-Si films crystallized by	
Lopez-Rios, T., see Borensztein	41/42 (1989) 439	pulsed UV excimer laser and calcu-	
Louis, P., see Tardy	50 (1991) 383	lated temperature profiles	43 (1989) 150
Lowen, P., see Deneuville	50 (1991) 308	Majni, G., see D'Anna	46 (1990) 365
Lozano, J., see Craig, Jr.	45 (1990) 151	Makhviladze, T.M., see Agafonov	46 (1990) 288
Lozano, J., see Durrer	45 (1990) 275	Makita, Y., see Ohnishi	50 (1991) 233
Lu, X.K., see Ding	41/42 (1989) 123	Malba, V., see Bernhardt	46 (1990) 121
Luches, A., see Craciun	43 (1989) 304	Malherbe, J.B., see Myburg	43 (1989) 242
Luches, A., see D'Anna	46 (1990) 365	Malherbe, J.B., see Tjong	44 (1990) 179
Ludeke, R., A. Taleb-Ibrahimi and G.		Malikov, I.V., see Shapoval	45 (1990) 257
Jezequel, Delocalization of defects: a	41 /42 /1000\ 151	Manenkov, A.A., see Prokhorov	43 (1989) 340
new model for the Schottky barrier	41/42 (1989) 151	Mansour, A., G. Indlekofer and P.	
Ludeke, R., see Heskett	48/49 (1991) 260	Oelhafen, Investigation of the elec- tronic structure of thin diamond films	
Ludescher, HP., see Eleftheriadis	46 (1990) 284 43 (1989) 297		48/49 (1991) 312
Lukeš, I., see Kubátová	50 (1991) 440	by photoelectron spectroscopy Mantl, S., see Holländer	50 (1991) 450
Lunn, B., see Ashenford Lussert, J.M., see Fornari	50 (1991) 207	Mao, D., A. Kahn, M. Marsi and G.	30 (1331) 430
Lüth, H., see Förster	41/42 (1989) 306	Margaritondo, Synchrotron radiation	
Luther, K., see Bolle	46 (1990) 279	induced surface photovoltage at	
Lutz, N., see Buerhop	46 (1990) 430	metal/GaAs interfaces	48/49 (1991) 324
Eutz, 11., see Buelliop	10 (1770) 130	Marchet, P., see Girault	46 (1990) 78
Ma, JS., H. Kawarada, T. Yonehara,		Marclay, E., D.J. Webb, P. Buchmann	(-22)
JI. Suzuki, J. Wei, Y. Yokota, H.		and P. Vettiger, Broadband low-reflec-	
Mori, H. Fujita and A. Hiraki, Inter-		tivity coating for semiconductor power	
•		-	

Marciago	lasers by ion-beam and PECVD de-	42 (1000) 42	amuno, Excimer laser recrystallization	
Marfaing, J., W. Marine, R. Pierrisand and A. Cros, Structural changes in Au, Si, alloy films under laser irradiation   Marfaing, J., w. Marine, B. Vidal, M. Toulemonde, M. Hage Ali and J.P. Stoquert, Instability and structural transformation of amorphous ultrathin W-Si multilayer structures during heavy ion irradiation   Margaritondo, G., see Mao	position	43 (1989) 43	of amorphous Si films characterized	
and $A$ . Cros. Structural changes in Au, $Si_{1}$ alloy films under laser irradiation Marfaing, $J$ ., w. Marine, $A$ (1989) 165 Marfaing, $J$ ., w. Marine, $A$ (1990) 239 Marfaing, $J$ ., w. Marine, $A$ (1990) 239 Marfaing, $J$ ., w. Marine, $A$ (1990) 239 Margaritondo, $A$ (1990) 239 Margaritondo, $A$ (1990) 240 Marine, $A$ (1990) 240 Marine, $A$ (1990) 250 Marine, $A$ (1990) 251 Marine, $A$ (1990) 252 Marine, $A$ (1990) 253 Marine, $A$ (1990) 264 Marine, $A$ (1990) 274 Marine, $A$ (1990) 275 Marine, $A$ (1990) 276 Marine, $A$ (1990) 277 Marine, $A$ (1990) 278 Marine, $A$ (1990) 279 Marine, $A$ (1990) 270 Marin		45 (1990) 49		40 (4000) 440
Au, Si alloy films under laser irradiation   A3 (1989) 165			The state of the s	3 /
Marfaing J., see Marine   46 (1990) 239   Matsuda, Y., K. Fujita and S. Hinotani, Raman studies on GaAs epitaxial films on St   Matsudi, J., see Akimoto   4/42 (1989) 317   Matsui, J., see Akimoto   4/42 (1989) 317   Matsui, J., see Akimoto   4/42 (1989) 317   Matsui, J., see Akimoto   Matsui, J., see Jujieda   Matsui, J., see Jujieda   Matsui, J., see Jujieda   Matsui, J., Study of strain variation in LEC-grown GaAs bulk crystals by synchrotron radiation X-ray topography   Margaritondo, G., see Mao   Matsui, J., see May of strain variation in LEC-grown GaAs bulk crystals by synchrotron radiation X-ray topography   Matsumori, T., see Ohnishi				, ,
Marfaing, J., see Marine Marfaing, J., W. Marine, B. Vidal, M. Toulemonde, M. Hage Ali and J.P. Stoquert, Instability and structural transformation of amorphous ultrathin W-Si multilayer structures during heavy ion irradiation Margaritondo, G., see Niles Margaritondo, G., see Niles Margaritondo, G., see Niles Marine, B., See Benchiguer Marine, B., See Benchiguer Marine, W., w. Peray, Y. Mathey and D. Pailharey, Deposition of Y-Ba-Cu oxide superconducting thin films by Nd: YAG laser evaporation Marine, W., J.M. Scotto D'Aniello and J. Marfaing, Ficosecond YAG laser photoablation of amorphous silicon Marine, W., see Marfaing Marnero, E.E., Material transformations in semiconductor and magnetic thin films Markewitz, G., see Werner Martelta, G., see Compagnini Martin, J.M., see Bano Martin, J.M., see Bou Martin, J.M., see Bou Martin, J.M., see Broulieff Martin, J.M., see Broulieff Martin, J.M., see Danna Martin, J.M., see Danna Martin, J.M., see Danna Martin, J.M., see Danna Maryuyama, T., see Zaima Maryyama, T., see Zaima Maryyama, T., see Kezuka Mashiko, Y., see Maripi, Classer oxportation Massouras, G., J.A. Roger, G. Fuchs, A. Perez and L. Romana, Fluence dependence of ion beam induced atomic  Marsinda, Y., K. Fujita and S. Hinotani, 44/42 (1989) 131 Matsuid, J., see Akimoto Matsuid, J., see Akimoto Matsuid, J., see Akimoto Matsuid, J., see Hipieda Matsuid, J., see Opiedash bulk crystals by synchrotron radiation X-ray topogra-phy Matsumoto, Y., see Fujieda Matsuo, J., see Ohnishi Matsumot, Y., see Fujieda Matsumot, T., see Ohnishi Matsumot, Y., see Fujieda Matsuid, J., see Ohnishi Matsumot, Y., see Fujieda Matsuid, J., see Ohnishi Matsumot, Y., see Fujieda Matsuid, J., see Ohnishi Matsumot, Y., see Sujieda Matsuok, T., see Saaki Matsuok, T., see Saaki Matsuok, T., see Saaki Matsuok, V., see Saaki Matsuok, V., see Pujieda Matsuok, T., see Ohnishi Matsuok, V., see Pujieda Matsuok, T., see Saaki Matsuok, V., see Pujieda Matsuok, T., see Ohnishi Matsuok, V., see Pujieda Matsuok, T., see Ohnishi Matsuok, V., see Olo				
Marfaing, J., W. Marine, B. Vidal, M. Toulemonde, M. Hage Ali and J.P. Stoquert, Instability and structural transformation of amorphous ultrathin W. Si multilayer structures during heavy ion irradiation and transformation of amorphous ultrathin W. Si multilayer structures during heavy ion irradiation and transformation of a specific structures during heavy ion irradiation and transformation of a specific solution of specific solution of a specific specific solution of specific sp				41/42 (1989) 587
Toulemonde, M. Hage Ali and J.P. Stoquert, Instability and structural transformation of amorphous ultrathin W-Si multilayer structures during heavy ion irradiation Margaritondo, G., see Mao Margaritondo, G., see Mao Margaritondo, G., see Mao Mari, B., A. Segura and A. Chevy, Electrical properties of neutron-transmutation-doped InSe Marine, W., see Marfaing Marine, W., M. Peray, Y. Mathey and D. Pailharey, Deposition of Y-Ba-Cu oxide superconducting thin films by Nch'y AG laser evaporation Marine, W., J.M. Scotto D'Aniello and J. Marfaing, Picosecond YAG laser photoablation of amorphous silicon Marine, W., see Marfaing Marine, W., See Marfaing Marine, W., See Marfaing Marine, W., see Marfaing Markewitz, G., see Werner Marletta, G., see Werner Marletta, G., see Compagnini Alarshon, S., see Ermolieff Martin, J.M., see Bou Marthon, S., see Ermolieff Martin, J.M., see Doub Marthon Martin, M., see Doub Marthon Matthough Marthon Martin, M., see Doub Mart		46 (1990) 239		
Matsui, J., see Akimoto   41/42 (1989) 317			•	40 /40 /4004
Marsui, J., see Fujieda   41/42 (1989) 516				
Marsunication				
Margaritondo, G., see Mao				41/42 (1989) 516
Margaritondo, G., see Mao	The state of the s	4.5 (4.000) 400		
Margaritondo, G., see Mao         48/49 (1991) 324 box         phy         50 (1991) 27         50 (1991) 275         50 (1991) 275         Matsumori, T., see Ohnishi         50 (1991) 233         41/42 (1989) 516         50 (1991) 233         Matsumori, T., see Ohnishi         50 (1991) 233         41/42 (1989) 516         50 (1991) 233         41/42 (1989) 516         42 (1989) 516         42 (1989) 516         Matsumoto, Y., see Fujieda         41/42 (1989) 516         41/42 (1989) 516         Matsunok, N. and K. Nakano, Characterization of semiconductor oxides by IR diffuse reflectance spectroscopy         41/42 (1989) 516		*		
Mari, B., see Benchiguer				50 (1001)
Mari, B., A. Segura and A. Chevy, Electrical properties of neutron-transmutation-doped InSe         50 (1991) 415         Matsumoto, Y., see Fujieda         41/42 (1989) 516           Marine, W., see Marfaing         43 (1989) 165         diffuse reflectance spectroscopy         41/42 (1989) 53           Marine, W., M. Peray, Y. Mathey and D. Pailbarey, Deposition of Y-Ba-Cu oxide superconducting thin films by Nd: YaG laser evaporation         43 (1989) 377         Matsuoka, T., see Sasaki         41/42 (1989) 504           Marine, W., J.M. Scotto D'Aniello and J. Marfaing, Picosecond YAG laser photoablation of amorphous silicon of marine, W., see Marfaing         46 (1990) 239         Mattsson, H., see Lausmaa         44 (1990) 139           Marinero, E., Material transformations in semiconductor and magnetic thin films         46 (1990) 422         Matz, R., see Meiler         43 (1989) 117           Markewitz, G., see Werner         41/42 (1989) 594         Mazzi, G., see Bernhardt         46 (1990) 123           Marrion, S., see Ermolieff         48/49 (1991) 178         McCarry, J.G., see Vajo         47 (1991) 23           Martin, F., see Ermolieff         48/49 (1991) 178         McConville, C.F., see Jones         45 (1990) 89           Martin, M., see Bou         47 (1991) 189         McGovern, I.T., see Zahn         46 (1990) 365           Martin, J.M., see Bou         47 (1991) 189         McGovern, I.T., see Fickart         48/49 (1991) 39           Martino				, ,
Matsuo, K. and K. Nakano, Characterization-doped InSe   Marine, W., see Marfaing   43 (1989) 165   Marine, W., M. Peray, Y. Mathey and D. Pailharey, Deposition of Y-Ba-Cu oxide superconducting thin films by Nd: YAG laser evaporation   43 (1989) 377   Marine, W., J.M. Scotto D'Aniello and J. Marfaing, Picosecond YAG laser photoablation of amorphous silicon   46 (1990) 239   Mattsuoka, T., see Asshu   48 (49 (1991) 39   Mattsook, M., see Lausmaa   44 (1990) 139   Mattsson, H., see Lausmaa   45 (1990) 189   Mattswitz, G., see Werner   41 (1989) 159   Martin, F., see Ermolieff   48 (1990) 189   Mattswitz, G., see Werner   41 (1989) 159   Martin, F., see Ermolieff   48 (1991) 178   Martin, F.J., see Bartlett   47 (1991) 187   McGovern, I.T., set X-ray photoelectron   Spectroscopy of compound semiconductor surfaces and interfaces   McGuire, T.R., see Pickart   48 (49 (1991) 260   McLean, A.B., see Himpsel   41 (42 (1989) 179   McLean, A.B		50 (1991) 277		, ,
tion-doped InSe  Marine, W., see Marfaing  Marine, W., see Marfaing  Marine, W., M. Peray, Y. Mathey and D. Pailharey, Deposition of Y-Ba-Cu oxide superconducting thin films by Nd:YAG laser evaporation  Marine, W., J. M. Scotto D'Aniello and J. Marfaing, Picosecond YAG laser photoablation of amorphous silicon  Marine, W., see Marfaing  Marine, W., J. M. Scotto D'Aniello and J.  Martino, M., see Werner  Martino, M., see Compagnini  Martino, M., see Bou  Martino, M., see Craciun  Martino, M., see Soasaki  Martino, M., see Soasaki  Martino, M., see Mare  Martino, M., see Mare  Martino, M., see Mare  Martino, M., see Bou  Martino, M., see Mare  Martino, M., see Craciun  Martino, M., see Craciun  Martino, M., see Mare  Martino, M., see Mare  Martino, M., see Mare  Martin				41/42 (1989) 516
Marine, W., see Marfaing         43 (1989) 165         diffuse reflectance spectroscopy         41/42 (1989) 53           Marine, W., M. Peray, Y. Mathey and D. Pailharey, Deposition of Y-Ba-Cu oxide superconducting thin films by Nd:YAG laser evaporation         43 (1989) 377         Mattsuoka, T., see Sasaki         43 (1989) 196           Marine, W., J.M. Scotto D'Aniello and J. Marfaing, Picosecond YAG laser photoablation of amorphous silicon Marine, W., see Marfaing         46 (1990) 239         Mattson, L.M., Surface effects in reactive ion plating         48/49 (1991) 39           Marine, W., see Marfaing Marine, W., see Marfaing Marine, W., see Marfaing Ifilms         46 (1990) 239         Mattsson, H., see Lausmaa         44 (1990) 133           Markewitz, G., see Werner Martin, S., see Emoliciff Martin, F., see Compagnini Attin, F., see Emoliciff Martin, J.M., see Mao         48 (49 (1991) 178         MacCanville, C.F., see Jones         45 (1990) 85           Martin, P.J., see Bardlett Martin, P.J., see Barlett Martin, P.J., see Barlett Attino, M., see Craciun Martino, M., see Craciun Martino, M., see Craciun Martino, M., see Craciun Martino, M., see D'Anna Maruyama, T., see Zaima Maruyama, T., see Keuka Mashita, M., see Riyatake Mashita, M., see Riyatake Mashita, M., see Sasaki Mashita, M., see Auvaray Massies, J., see Auvray Massies, J., see Auvray Shassies, J., see Auvray Shas	• •		•	
Marine, W., M. Peray, Y. Mathey and D. Pailharey, Deposition of Y-Ba-Cu oxide superconducting thin films by Nd: YAG laser evaporation         Matthaei, J., see Voelskow Matthaei, J., see Ke Ashu 48 (49 (1991) 39 (48 (49 (1991) 39 (1989) 177 (1991) 189 (1990) 189 (1			The state of the s	
Pailharey, Deposition of Y-Ba-Cu oxide superconducting thin films by Nd: YAG laser exporation		43 (1989) 165		
oxide superconducting thin films by Nd:YAG laser evaporation         43 (1989) 377         Matthai, C.C., see Ashu         48/49 (1991) 39           Marine, W., J.M. Scotto D'Aniello and J. Marfaing, Picosecond YAG laser photoablation of amorphous silicon         46 (1990) 239         Mattsson, H., see Lausmaa         44 (1990) 189           Marine, W., see Marfaing         46 (1990) 422         Mattsson, H., see Lausmaa         45 (1990) 189           Marinero, E.E., Material transformations in semiconductor and magnetic thin films         43 (1989) 117         Marteson, H., see Lausmaa         45 (1990) 189           Markwitz, G., see Werner         41/42 (1989) 159         Mattsson, H., see Elausmaa         45 (1990) 189           Markwitz, G., see Werner         41/42 (1989) 159         Mazzi, G., see Bernhardt         46 (1990) 21           Marinero, E.E., Material transformations in semiconductor and magnetic thin films         43 (1989) 117         Mazzi, G., see Berniardt         46 (1990) 121           Markwitz, G., see Werner         41/42 (1889) 159         McAlpine, N., see Hizem         50 (1991) 490           Marthon, S., see Ermolieff         48/49 (1991) 178         McCarty, J.G., see Vajo         47 (1991) 23           Marthon, S., see Ermolieff         48/49 (1991) 178         McGovern, I.T., see Zahn         41/42 (1989) 191           Martin, P.J., see Bartlett         47 (1991) 149         McGovern, I.T., soft X-ray photoelectron s				
Nd:YAG laser evaporation         43 (1989) 377         Mattox, D.M., Surface effects in reactive ion plating         48/49 (1991) 540           Marine, W., J.M. Scotto D'Aniello and J. Marriang, Picosecond YAG laser photoablation of amorphous silicon         46 (1990) 239         Mattsson, H., see Lausmaa         44 (1990) 133           Marine, W., see Marriang         46 (1990) 422         Mattsson, H., see Lausmaa         45 (1990) 189           Marinero, E.E., Material transformations in semiconductor and magnetic thin films         43 (1989) 117         Maze, E., see Meiler         43 (1989) 169           Markewitz, G., see Werner         41/42 (1989) 159         Mazzi, G., see Bertinem         50 (1991) 490           Maris, M., see Mao         48/49 (1991) 324         McCarty, J.G., see Vajo         47 (1991) 12           Martin, F., see Ermolieff         48/49 (1991) 178         McConville, C.F., see Jones         45 (1990) 85           Martin, F., see Ermolieff         48/49 (1991) 178         McGovern, I.T., see Zahn         41/42 (1989) 179           Martin, P.J., see Bartlett         47 (1991) 187         McGovern, I.T., see Zahn         41/42 (1989) 179           Martino, M., see D'Anna         46 (1990) 365         McGovern, I.T., see Pickart         48/49 (1991) 34           Martino, M., see D'Anna         46 (1990) 365         McGovern, I.T., see Pickart         48/49 (1991) 34           Mary, P., P. Bo				
Marine, W., J.M. Scotto D'Aniello and J.   Marfaing, Picosecond YAG laser photoablation of amorphous silicon   46 (1990) 239   Mattsson, H., see Lausmaa   45 (1990) 133   Mattson, H., see Lausmaa   45 (1990) 183   Mattson, H., see Lausmaa   45 (1990) 184   Mattson, H., see Lausmaa   45 (1990) 184   Mayer, E., see Bernhardt   46 (1990) 416   Mayer, S.T., see Bernhardt   46 (1990) 121   Mayer, L., see Hizem   50 (1991) 490   Mattson, H., see Lausmaa   45 (1990) 185   Mayer, C.F., see Bernhardt   46 (1990) 422   Mayer, E., see Bernhardt   46 (1990) 121   Mayer, L., see Hizem   50 (1991) 490   Mayer, E., see Berni   43 (1989) 185   McAlpine, N., see Berti   43 (1989) 185   McConville, C.F., see Jones   45 (1990) 85   McConville, C.F., see Jones   45 (1990) 85   McGovern, I.T., see Zahn   47 (1991) 187   McGovern, I.T., see Zahn   47 (1991) 187   McGovern, I.T., see Zahn   48 (1990) 340   Martino, M., see D'Anna   46 (1990) 365   McGovern, I.T., see Fickart   48 (49 (1991) 320   Mattson, H., see Heitwer   43 (1989) 121   McGovern, I.T., see Pickart   48 (49 (1991) 320   McGo				48/49 (1991) 39
Marfaing, Picosecond YAG laser photoablation of amorphous silicon         46 (1990) 239         Mattsson, H., see Lausmaa         44 (1990) 133           Marine, W., see Marfaing         46 (1990) 422         Matz, R., see Meiler         43 (1989) 416           Marine, W., see Marfaing         46 (1990) 422         Matz, R., see Meiler         43 (1989) 416           Marine, W., see Marfaing         46 (1990) 422         Matz, R., see Meiler         43 (1989) 416           Marine, W., see Marfaing         46 (1990) 422         Matz, R., see Meiler         43 (1989) 416           Marine, W., see Marfaing         46 (1990) 422         Matz, R., see Meiler         43 (1989) 416           Marine, W., see Marfaing         43 (1989) 117         Mayer, S.T., see Bernhardt         46 (1990) 121           Martin, G., see Werner         41 /42 (1989) 159         McArin, N., see Haneman         48 /49 (1991) 490           Martin, M., see Mao         48 /49 (1991) 324         McConville, C.F., see Jones         45 (1990) 85           Martin, J.M., see Bou         47 (1991) 149         McGovern, I.T., see Zone         50 (1991) 312           Martino, M., see Craciun         43 (1989) 304         McGovern, I.T., see Zone         41/42 (1989) 179           Martino, M., see D'Anna         46 (1990) 365         McGuire, T.R., see Pickart         48/49 (1991) 436           Mary, P.,		43 (1989) 377		
toablation of amorphous silicon         46 (1990) 239         Mattsson, H., see Lausmaa         45 (1990) 189           Marine, W., see Marfaing         46 (1990) 422         Matz, R., see Meiler         43 (1989) 416           Marinero, E.E., Material transformations in semiconductor and magnetic thin films         Mayer, S.T., see Bernhardt         46 (1990) 121           Markewitz, G., see Werner         41 /42 (1989) 159         Mazzi, G., see Berti         43 (1989) 158           Marletta, G., see Compagnini         43 (1989) 228         McCarty, J.G., see Vajo         47 (1991) 21           Marthon, S., see Ermolieff         48 /49 (1991) 178         McCoven, I.T., see Jones         45 (1990) 85           Martin, P.J., see Bernblieff         48 /49 (1991) 178         McGovern, I.T., see Zahn         41 /42 (1989) 179           Martin, P.J., see Bartlett         47 (1991) 189         McGovern, I.T., soft X-ray photoelectron spectroscopy of compound semiconductor surfaces and interfaces         50 (1991) 34           Martino, M., see D'Anna         46 (1990) 365         McGuire, T.R., see Pickart         48 /49 (1991) 43           Mary, P., P. Bogdanski, G. Nouet and M. Toulemonde, Defects created by 3.5         McKinley, J., see Niles         41 /42 (1989) 139           Masaki, T., see Kezuka         48 /49 (1991) 454         McLean, A.B., see Himpsel         41 /42 (1989) 346           Mashiko, Y., see Miyatake				
Marine, W., see Marfaing         46 (1990) 422         Matz, R., see Meiler         43 (1989) 416           Marinero, E.E., Material transformations in semiconductor and magnetic thin films         43 (1989) 117         Mayer, S.T., see Bernhardt         46 (1990) 121           Markewitz, G., see Werner         41/42 (1989) 159         Mazzi, G., see Berti         43 (1989) 158           Marletta, G., see Compagnini         43 (1989) 228         McCarty, J.G., see Vajo         47 (1991) 123           Marsi, M., see Mao         48/49 (1991) 324         McConville, C.F., see Jones         45 (1990) 85           Martin, S., see Ermolieff         48/49 (1991) 178         McDonagh, C.J., see O'Connor         50 (1991) 312           Martin, P., see Barlett         47 (1991) 187         McGovern, I.T., Soft X-ray photoelectron spectroscopy of compound semiconductor surfaces and interfaces         41/42 (1989) 179           Martino, M., see Craciun         43 (1989) 304         McKinley, J., see Niles         48/49 (1991) 436           Mary, P., P. Bogdanski, G. Nouet and M. Toulemonde, Defects created by 3.5 GeV xenon ions in silicon         43 (1989) 42         McKinley, J., see Himpsel         41/42 (1989) 34           Masaki, T., see Kezuka         48/49 (1991) 454         McLean, A.B., see Himpsel         41/42 (1989) 34           Mashiko, Y., see Miyatake         41/42 (1989) 342         Mcier, J., see Beaurichter         50 (1991) 105				, ,
Marinero, E.E., Material transformations in semiconductor and magnetic thin films         Mayer, S.T., see Bernhardt Mayet, L., see Hizem         46 (1990) 121 Mayet, L., see Hizem         50 (1991) 490 Mayet, L., see Hizem         43 (1989) 158 Mazet, L., see Hizem         48 (1991) 151 Mazet, McApine, N., see Haneman         48 (49 (1991) 111 Mazet, McApine, N., see Haneman         48 (49 (1991) 111 Mazet, McApine, N., see Macet, L., see Picher         47 (1991) 23 MacCovern, I.T., see Dones         45 (1990) 85 McCovern, I.T., see Dones         45 (1990) 85 McGovern, I.T., see Tahn         41 (42 (1989) 179 McGovern, I.T., see Tahn	toablation of amorphous silicon	, ,		
in semiconductor and magnetic thin films		46 (1990) 422		
films         43 (1989) 117         Mazzi, G., see Berti         43 (1989) 158           Markewitz, G., see Werner         41/42 (1989) 159         McAlpine, N., see Haneman         48/49 (1991) 111           Marletta, G., see Compagnini         43 (1989) 228         McCarty, J.G., see Vajo         47 (1991) 23           Marsi, M., see Mao         48/49 (1991) 324         McConville, C.F., see Jones         45 (1990) 85           Marthon, S., see Ermolieff         48/49 (1991) 178         McDonagh, C.J., see O'Connor         50 (1991) 312           Martin, F., see Ermolieff         48/49 (1991) 178         McGovern, I.T., see Zahn         41/42 (1989) 179           Martin, J.M., see Bou         47 (1991) 187         McGovern, I.T., Soft X-ray photoelectron spectroscopy of compound semiconductor surfaces and interfaces         50 (1991) 34           Martino, M., see D'Anna         46 (1990) 365         McGuire, T.R., see Pickart         48/49 (1991) 436           Maruyama, T., see Zaima         41/42 (1989) 433         McKinley, J., see Niles         41/42 (1989) 139           Mary, P., P. Bogdanski, G. Nouet and M.         McLean, A.B., see Himpsel         41/42 (1989) 139           McLean, A.B., see Himpsel         41/42 (1989) 346           Merzin, J.Y., see Kezuka         48/49 (1991) 454         Meier, J., see Baurichter         50 (1991) 470           Masskit, T., see Auvray				
Markewitz, G., see Werner         41/42 (1989) 159         McAlpine, N., see Haneman         48/49 (1991) 111           Marletta, G., see Compagnini         43 (1989) 228         McCarty, J.G., see Vajo         47 (1991) 23           Marsi, M., see Mao         48/49 (1991) 324         McConville, C.F., see Jones         45 (1990) 85           Marthon, S., see Ermolieff         48/49 (1991) 178         McDonagh, C.J., see O'Connor         50 (1991) 312           Martin, J.M., see Bou         47 (1991) 149         McGovern, I.T., see Zahn         41/42 (1989) 179           Martino, M., see Craciun         43 (1989) 304         McGovern, I.T., see Tode         48/49 (1991) 34           Martino, M., see D'Anna         46 (1990) 365         McGuire, T.R., see Pickart         48/49 (1991) 436           Maruyama, T., see Zaima         41/42 (1989) 433         McKinley, J., see Niles         41/42 (1989) 179           Marzin, J.Y., see Crean         43 (1989) 102         McLean, A.B., see Himpsel         41/42 (1989) 346           Marzin, J.Y., see Kezuka         48/49 (1991) 251         McLean, A.B., see Heitwer         50 (1991) 470           Massies, J., see Auvray         50 (1991) 109         Meier, J., see Baurichter         50 (1991) 105           Massouras, G., J.A. Roger, G. Fuchs, A.         50 (1991) 109         Mele, A., D. Consalvo, D. Stranges, A.         43 (1989) 416	in semiconductor and magnetic thin		· ·	
Marletta, G., see Compagnini         43 (1989) 228         McCarty, J.G., see Vajo         47 (1991) 23           Marsi, M., see Mao         48/49 (1991) 324         McConville, C.F., see Jones         45 (1990) 85           Marthon, S., see Ermolieff         48/49 (1991) 178         McDonagh, C.J., see O'Connor         50 (1991) 312           Martin, F., see Ermolieff         48/49 (1991) 178         McGovern, I.T., see Zahn         41/42 (1989) 179           Martin, J.M., see Bou         47 (1991) 149         McGovern, I.T., Soft X-ray photoelectron spectroscopy of compound semiconductor surfaces and interfaces         50 (1991) 34           Martino, M., see Craciun         43 (1989) 304         McGuire, T.R., see Pickart         48/49 (1991) 436           Maruyama, T., see Zaima         41/42 (1989) 433         McKinley, J., see Niles         41/42 (1989) 139           Mary, P., P. Bogdanski, G. Nouet and M.         McLean, A.B., see Himpsel         41/42 (1989) 139           McLean, A.B., see Himpsel         41/42 (1989) 346           McLean, A.B., see Himpsel         41/42 (1989) 346           McLean, A.B., see Hetwer         50 (1991) 470           Masski, T., see Kezuka         48/49 (1991) 454         Meier, J., see Baurichter         50 (1991) 470           Massies, J., see Auvray         50 (1991) 109         Meiler, J., R. Matz and D. Haarer, Laserinduced photochemical etching of InP by HBr and HCl		1		
Marsi, M., see Mao         48/49 (1991) 324         McConville, C.F., see Jones         45 (1990) 85           Marthon, S., see Ermolieff         48/49 (1991) 178         McDonagh, C.J., see O'Connor         50 (1991) 312           Martin, F., see Ermolieff         48/49 (1991) 178         McGovern, I.T., see Zahn         41/42 (1989) 179           Martin, J.M., see Bou         47 (1991) 187         McGovern, I.T., soft X-ray photoelectron spectroscopy of compound semiconductor surfaces and interfaces         50 (1991) 34           Martino, M., see Craciun         43 (1989) 304         McGovern, I.T., see Pickart         48/49 (1991) 436           Martino, M., see D'Anna         46 (1990) 365         McGovern, I.T., see Pickart         48/49 (1991) 436           Mary, P., P. Bogdanski, G. Nouet and M.         McLean, A.B., see Pickart         48/49 (1991) 436           McLean, A.B., see Lahn         41/42 (1989) 139           McLean, A.B., see Himpsel         41/42 (1989) 346           McLean, A.B., see Heikwer         48/49 (1991) 260           Marzin, J.Y., see Crean         50 (1991) 281         Mehrer, H., see Hettwer         50 (1991) 470           Masski, T., see Kezuka         48/49 (1991) 454         Meiler, J., R. Matz and D. Haarer, Laser-induced photochemical etching of InP         50 (1991) 109           Massouras, G., J.A. Roger, G. Fuchs, A.         Giardini-Guidoni and R. Teghil, Cluster ion formation b				
Marthon, S., see Ermolieff Martin, F., see Ermolieff Martin, F., see Ermolieff Martin, J.M., see Bou Martin, P.J., see Bartlett Martin, P.J., see Bartlett Martino, M., see Craciun Martino, M., see Craciun Martino, M., see D'Anna Maruyama, T., see Zaima Maruyama, T., see Zaima Mary, P., P. Bogdanski, G. Nouet and M. Toulemonde, Defects created by 3.5 GeV xenon ions in silicon Marzin, J.Y., see Crean Masaki, T., see Kezuka Mashiko, Y., see Miyatake Massies, J., see Auvray Massouras, G., J.A. Roger, G. Fuchs, A. Perez and L. Romana, Fluence dependence of ion beam induced atomic  Martino, M., see Ermolieff 48/49 (1991) 178 McCovern, I.T., see C'Connor McGovern, I.T., see C'Connor McGovern, I.T., see C'Connor McGovern, I.T., see Tahn McGovern, I.T., see Fickart McGovern, I.T., see Fickart McGovern, I.T., see Pickart McGovern, I.T., see		* *		
Martin, F., see Ermolieff Martin, J.M., see Bou Martin, P.J., see Bartlett Martino, M., see Craciun Martino, M., see Craciun Martino, M., see D'Anna Maruyama, T., see Zaima Mary, P., P. Bogdanski, G. Nouet and M. Toulemonde, Defects created by 3.5 GeV xenon ions in silicon Marzin, J.Y., see Kezuka Masaki, T., see Kezuka Mashiko, Y., see Miyatake Mashita, M., see Sasaki Massouras, G., J.A. Roger, G. Fuchs, A. Perez and L. Romana, Fluence dependence of ion beam induced atomic  Martin, J.M., see Bou 47 (1991) 149 McGovern, I.T., see Zahn McGovern, I.T., see T., see Pickart  41/42 (1989) 179 McGovern, I.T., see Zahn McGovern, I.T., see T., see Pickart  48/49 (1991) 436 McKinley, J., see Niles McKinley, J., see Niles McKinley, J., see Niles McLean, A.B., see Himpsel McLean, A.B., see Himpsel McLean, A.B., see Himpsel McLean, A.B., see Heskett Mehrer, H., see Hettwer Meier, J., see Baurichter Meier, J., see Baurichter Mele, A., D. Consalvo, D. Stranges, A. Giardini-Guidoni and R. Teghil, Cluster ion formation by laser evaporation	Marsi, M., see Mao			
Martin, J.M., see Bou 47 (1991) 149 McGovern, I.T., Soft X-ray photoelectron spectroscopy of compound semiconductor surfaces and interfaces 50 (1991) 34 Martino, M., see Craciun 43 (1989) 304 Martino, M., see D'Anna 46 (1990) 365 Maruyama, T., see Zaima 41/42 (1989) 433 Mary, P., P. Bogdanski, G. Nouet and M. Toulemonde, Defects created by 3.5 GeV xenon ions in silicon 43 (1989) 102 Marzin, J.Y., see Crean 50 (1991) 281 Masaki, T., see Kezuka 48/49 (1991) 454 Mashiko, Y., see Miyatake 41/42 (1989) 342 Massouras, G., J.A. Roger, G. Fuchs, A. Perez and L. Romana, Fluence dependence of ion beam induced atomic  47 (1991) 149 McGovern, I.T., Soft X-ray photoelectron spectroscopy of compound semiconductor surfaces and interfaces 50 (1991) 34 McKinley, J., see Pickart 48/49 (1991) 436 McKinley, J., see Niles 41/42 (1989) 179 McLean, A.B., see Himpsel 41/42 (1989) 346 McLean, A.B., see Himpsel 41/42 (1989) 346 McLean, A.B., see Heskett 48/49 (1991) 260 Meler, J., see Hettwer 50 (1991) 470 Meier, J., see Baurichter 50 (1991) 165 Meier, J., R. Matz and D. Haarer, Laser-induced photochemical etching of InP by HBr and HCl 43 (1989) 416 Mele, A., D. Consalvo, D. Stranges, A. Giardini-Guidoni and R. Teghil, Cluster ion formation by laser evaporation	Marthon, S., see Ermolieff			
Martin, P.J., see Bartlett  47 (1991) 187  Martino, M., see Craciun  43 (1989) 304  Martino, M., see D'Anna  46 (1990) 365  Maruyama, T., see Zaima  41/42 (1989) 433  Mary, P., P. Bogdanski, G. Nouet and M.  Toulemonde, Defects created by 3.5  GeV xenon ions in silicon  43 (1989) 102  Marzin, J.Y., see Crean  Masaki, T., see Kezuka  48/49 (1991) 436  McKinley, J., see Niles  McLean, A.B., see Zahn  McLean, A.B., see Himpsel  41/42 (1989) 346  McLean, A.B., see Himpsel  48/49 (1991) 260  McLean, A.B., see Heskett  48/49 (1991) 260  McLean, A.B., see Himpsel  41/42 (1989) 346  McLean, A.B., see Heskett  48/49 (1991) 260  McLean, A.B., see Himpsel  48/49 (1991) 260  McLean, A.B., see Himpsel  48/49 (1991) 260  McLean, A.B., see Heskett  48/49 (1991) 260  McLean, A.B., see Himpsel  41/42 (1989) 346  McLean, A.B., see Himpsel  41/42 (1989) 346  McLean, A.B., see Himpsel  48/49 (1991) 260  McLean, A.B., see Heskett  48/49 (1991) 260  McLean, A.B., see Hesket				41/42 (1989) 179
Martino, M., see Craciun  Martino, M., see D'Anna  Martino, M., see D'Anna  Maruyama, T., see Zaima  Mary, P., P. Bogdanski, G. Nouet and M.  Toulemonde, Defects created by 3.5  GeV xenon ions in silicon  Marzin, J.Y., see Crean  Masaki, T., see Kezuka  Mashiko, Y., see Miyatake  Mashita, M., see Sasaki  Massies, J., see Auvray  Massouras, G., J.A. Roger, G. Fuchs, A.  Perez and L. Romana, Fluence dependence of ion beam induced atomic  43 (1989) 304  McGuire, T.R., see Pickart  McKinley, J., see Niles  McKinley, J., see Niles  McLean, A.B., see Zahn  McLean, A.B., see Himpsel  41/42 (1989) 179  McLean, A.B., see Heskett  48/49 (1991) 260  McLean, A.B., see Heskett  48/49 (1991) 260  McLean, A.B., see Hettwer  50 (1991) 270  Meier, J., see Baurichter  Meier, J., R. Matz and D. Haarer, Laser-  induced photochemical etching of InP  by HBr and HCl  Mele, A., D. Consalvo, D. Stranges, A.  Giardini-Guidoni and R. Teghil, Cluster ion formation by laser evaporation	Martin, J.M., see Bou	, ,		
Martino, M., see D'Anna  Maruyama, T., see Zaima  Maruyama, T., see Zaima  Mary, P., P. Bogdanski, G. Nouet and M.  Toulemonde, Defects created by 3.5  GeV xenon ions in silicon  Marzin, J.Y., see Crean  Masaki, T., see Kezuka  Mashiko, Y., see Miyatake  Mashita, M., see Sasaki  Massouras, G., J.A. Roger, G. Fuchs, A.  Perez and L. Romana, Fluence dependence of ion beam induced atomic  Maruyama, T., see Pickart  48/49 (1991) 436  McKinley, J., see Niles  McLean, A.B., see Pickart  48/49 (1991) 436  McKinley, J., see Niles  McLean, A.B., see Himpsel  41/42 (1989) 346  McLean, A.B., see Heskett  48/49 (1991) 260  Mehrer, H., see Hettwer  50 (1991) 470  Meier, J., see Baurichter  Meiler, J., R. Matz and D. Haarer, Laser-  induced photochemical etching of InP  by HBr and HCl  Mele, A., D. Consalvo, D. Stranges, A.  Giardini-Guidoni and R. Teghil, Cluster ion formation by laser evaporation	Martin, P.J., see Bartlett	,		
Maruyama, T., see Zaima  Mary, P., P. Bogdanski, G. Nouet and M.  Toulemonde, Defects created by 3.5  GeV xenon ions in silicon  Marzin, J.Y., see Crean  Masaki, T., see Kezuka  Mashiko, Y., see Miyatake  Mashita, M., see Sasaki  Massouras, G., J.A. Roger, G. Fuchs, A.  Perez and L. Romana, Fluence dependence of ion beam induced atomic  Mary, P., P. Bogdanski, G. Nouet and M.  McLean, A.B., see Niles  McLean, A.B., see Himpsel  41/42 (1989) 346  McLean, A.B., see Heskett  48/49 (1991) 260  Mehrer, H., see Hettwer  50 (1991) 470  Meiler, J., see Baurichter  Meiler, J., R. Matz and D. Haarer, Laser-  induced photochemical etching of InP  by HBr and HCl  Mele, A., D. Consalvo, D. Stranges, A.  Giardini-Guidoni and R. Teghil, Cluster ion formation by laser evaporation	Martino, M., see Craciun	43 (1989) 304		
Mary, P., P. Bogdanski, G. Nouet and M. Toulemonde, Defects created by 3.5 GeV xenon ions in silicon Marzin, J.Y., see Crean Masaki, T., see Kezuka Mashiko, Y., see Miyatake Massies, J., see Auvray Massouras, G., J.A. Roger, G. Fuchs, A. Perez and L. Romana, Fluence dependence of ion beam induced atomic  McLean, A.B., see Zahn McLean, A.B., see Himpsel McLean, A.B., see Heskett McLean, A.B., see Heskett  41/42 (1989) 346 McLean, A.B., see Himpsel McLean, A.B., see Heskett McLean, A.B., see Himpsel McLean, A.B., see Heskett McLean, A	Martino, M., see D'Anna	46 (1990) 365		48/49 (1991) 436
Toulemonde, Defects created by 3.5 GeV xenon ions in silicon 43 (1989) 102 Marzin, J.Y., see Crean 50 (1991) 281 Masaki, T., see Kezuka 48/49 (1991) 454 Mashiko, Y., see Miyatake 41/42 (1989) 643 Massies, J., see Auvray Massouras, G., J.A. Roger, G. Fuchs, A. Perez and L. Romana, Fluence dependence of ion beam induced atomic  McLean, A.B., see Himpsel 41/42 (1989) 346 McLean, A.B., see Himpsel 44/42 (1989) 346 McLean, A.B., see Himpsel 48/49 (1991) 260 McLean, A.B., see Himpsel 48/49 (1991) 260 McLean, A.B., see Himpsel 48/49 (1991) 260 McLean, A.B., see Himpsel 41/42 (1989) 346 McLean, A.B., see Himpsel 48/49 (1991) 260 McLean, A.B., see Heskett 48/49 (1991) 260 McLean, A.B., see Heskett 48/49 (1991) 260 McLean, A.B., see Himpsel 41/42 (1989) 346 McLean, A.B., see Himpsel 41/42 (1989) 346 McLean, A.B., see Himpsel 48/49 (1991) 260 McLean, A.B., see Heskett 48/49 (1991) 26	Maruyama, T., see Zaima	41/42 (1989) 433		
GeV xenon ions in silicon  43 (1989) 102  McLean, A.B., see Heskett  48/49 (1991) 260  Marzin, J.Y., see Crean  50 (1991) 281  Mehrer, H., see Hettwer  50 (1991) 470  Meier, J., see Baurichter  Meier, J., R. Matz and D. Haarer, Laser- induced photochemical etching of InP  Massies, J., see Auvray  Massouras, G., J.A. Roger, G. Fuchs, A.  Perez and L. Romana, Fluence dependence of ion beam induced atomic  McLean, A.B., see Heskett  48/49 (1991) 260  Mehrer, H., see Hettwer  50 (1991) 470  Meier, J., R. Matz and D. Haarer, Laser- induced photochemical etching of InP  by HBr and HCl  Mele, A., D. Consalvo, D. Stranges, A.  Giardini-Guidoni and R. Teghil, Cluster ion formation by laser evaporation	Mary, P., P. Bogdanski, G. Nouet and M.		McLean, A.B., see Zahn	41/42 (1989) 179
Marzin, J.Y., see Crean  Masaki, T., see Kezuka  Masaki, T., see Kezuka  Mashiko, Y., see Miyatake  Mashita, M., see Sasaki  Massouras, G., J.A. Roger, G. Fuchs, A.  Perez and L. Romana, Fluence dependence of ion beam induced atomic  Maskita, J., see Hettwer  Meier, J., see Hettwer  Meier, J., see Baurichter  Meier, J., see Baurichter  Meier, J., R. Matz and D. Haarer, Laser-  induced photochemical etching of InP  by HBr and HCl  Mele, A., D. Consalvo, D. Stranges, A.  Giardini-Guidoni and R. Teghil, Cluster ion formation by laser evaporation	Toulemonde, Defects created by 3.5		McLean, A.B., see Himpsel	41/42 (1989) 346
Masaki, T., see Kezuka  Masaki, T., see Kezuka  Mashiko, Y., see Miyatake  Mashiko, Y., see Miyatake  Mashiko, Y., see Miyatake  Mashiko, Y., see Miyatake  Meier, J., see Baurichter  Meiler, J., R. Matz and D. Haarer, Laser- induced photochemical etching of InP by HBr and HCl  Massouras, G., J.A. Roger, G. Fuchs, A.  Perez and L. Romana, Fluence dependence of ion beam induced atomic  Meier, J., see Baurichter  Meiler, J., R. Matz and D. Haarer, Laser- induced photochemical etching of InP by HBr and HCl  Mele, A., D. Consalvo, D. Stranges, A.  Giardini-Guidoni and R. Teghil, Cluster ion formation by laser evaporation	GeV xenon ions in silicon	43 (1989) 102	McLean, A.B., see Heskett	48/49 (1991) 260
Mashiko, Y., see Miyatake  41/42 (1989) 643  Meiler, J., R. Matz and D. Haarer, Laser-induced photochemical etching of InP  by HBr and HCl  Massouras, G., J.A. Roger, G. Fuchs, A.  Perez and L. Romana, Fluence dependence of ion beam induced atomic  Meiler, J., R. Matz and D. Haarer, Laser-induced photochemical etching of InP  by HBr and HCl  Mele, A., D. Consalvo, D. Stranges, A.  Giardini-Guidoni and R. Teghil, Cluster ion formation by laser evaporation	Marzin, J.Y., see Crean	50 (1991) 281	Mehrer, H., see Hettwer	
Mashita, M., see Sasaki  Massies, J., see Auvray  Massouras, G., J.A. Roger, G. Fuchs, A.  Perez and L. Romana, Fluence dependence of ion beam induced atomic  41/42 (1989) 342  50 (1991) 109  by HBr and HCl  Mele, A., D. Consalvo, D. Stranges, A.  Giardini-Guidoni and R. Teghil, Cluster ion formation by laser evaporation	Masaki, T., see Kezuka	48/49 (1991) 454	Meier, J., see Baurichter	50 (1991) 165
Massies, J., see Auvray  Massouras, G., J.A. Roger, G. Fuchs, A.  Perez and L. Romana, Fluence dependence of ion beam induced atomic  50 (1991) 109  by HBr and HCl  Mele, A., D. Consalvo, D. Stranges, A.  Giardini-Guidoni and R. Teghil, Cluster ion formation by laser evaporation	Mashiko, Y., see Miyatake	41/42 (1989) 643	Meiler, J., R. Matz and D. Haarer, Laser-	
Massouras, G., J.A. Roger, G. Fuchs, A.  Perez and L. Romana, Fluence dependence of ion beam induced atomic  Mele, A., D. Consalvo, D. Stranges, A.  Giardini-Guidoni and R. Teghil, Cluster ion formation by laser evaporation	Mashita, M., see Sasaki	41/42 (1989) 342	induced photochemical etching of InP	
Perez and L. Romana, Fluence depen- dence of ion beam induced atomic  Giardini-Guidoni and R. Teghil, Clus- ter ion formation by laser evaporation	Massies, J., see Auvray	50 (1991) 109	by HBr and HCl	43 (1989) 416
dence of ion beam induced atomic ter ion formation by laser evaporation	Massouras, G., J.A. Roger, G. Fuchs, A.		Mele, A., D. Consalvo, D. Stranges, A.	
	Perez and L. Romana, Fluence depen-		Giardini-Guidoni and R. Teghil, Clus-	
mixing in the immiscible tin-silicon of solid complex oxides 43 (1989) 398	dence of ion beam induced atomic		ter ion formation by laser evaporation	
	mixing in the immiscible tin-silicon		of solid complex oxides	43 (1989) 398
system 43 (1989) 213 Mele, A., see Teghil 46 (1990) 220	system	43 (1989) 213	Mele, A., see Teghil	46 (1990) 220
Masui, M., see Takeuchi 48/49 (1991) 517 Mendik, M., M. Ospelt, H. von Känel	Masui, M., see Takeuchi	48/49 (1991) 517	Mendik, M., M. Ospelt, H. von Känel	
Mathé, E.L., J.G. Maillou, A. Naudon, E. and P. Wachter, Determination of	Mathé, E.L., J.G. Maillou, A. Naudon, E.		and P. Wachter, Determination of	
Fogarassy, M. Elliq and S. de Un-	Fogarassy, M. Elliq and S. de Un-		elastic properties of Si/Ge super-	

surface acoustic modes by Brillouin scattering Mengaci, P., see D'Arna Merzurio, J.P., see Girant Merzurio, J.P., see Girant Merzurio, S., see Hage-Ail Merguri, S., see Hage-Ail Mesguer, F., see Loper Merxe, S. and K. Meteva, Nucleation and growth of laser-plasma deposited thin films Merzurio, S., see Breuer Merxe, S. and K. Meteva, Nucleation and growth of laser-plasma deposited thin films Merzurio, J.P., see Breuer Merxe, S., see Breuer Merxe, S., see Breuer Merxe, S., see Breuer Merxe, S., see Breuer Merxelar, J.W., see Zeman Meryer, B., see Benchiguer Meyer, B., see Benchiguer Meyer, B., see Benchiguer Meyer, B., see Rondingare Merxe, S., see Metev Meyer, B., see Rondingare Meyer, B., see Rondingare Merxe, S., see Metev Meyer, B., see Rondingare Meyer, B., see Rondingare Merxe, S., see Metev Meyer, B., see Benchiguer Meyer, B., see Benchiger Meyer, B., see Benchiger Meyer, B., see Benchiger Meyer, B., see Bench	lattices and Si <sub>1-x</sub> Ge <sub>x</sub> films from		Mitra, S.S., see Kim	48/49 (1991) 548
Scattering   So (1991) 303   Miyahara, T., see Yamada Maruo   41/42 (1989) 647   Miyano, M., see Nomura   41/42 (1989) 530   Miyano, M., see Nomura   41				, , ,
Mercurio, J.P., see Girault Mercurio, J.P., see Girault Merguri, S., see Hage-Ali Meseguer, F., see López Mertey, S. and K. Meteva, Nucleation and growth of laser-plasma deposited thin films Mertey, S., see Bruer Meteva, K., see Merev Meyer, B., see Benchiguer Meyer, B., p. Omling and P. Emanuels- son, Landau oscillations in single quantum wells observed by microwave detection Meyerston, B.S., see Arienzo Meyerston, B.R., Gauthire and P. Pinard, Structure and defects induced by elec- tron beam irradiation in silicon sub- strates and EPR ribbons Milailescu, I.N., see Cracium Milailescu, I.N., see Porkhorov Mihailescu, I.N., see Prokhorov M	-	50 (1991) 303		
Mergui, S., see Hage-Ali Mergui, S., see Hage-Ali Mesey, S. and K. Meteva, Nucleation and growth of laser-plasma deposited thin films Metev, S. and K. Meteva, Mucleation and growth of laser-plasma deposited thin films Meteva, K. s., see Breuer Meteva, K. s., see Metev Meteva, K. s., see Metev Meteva, K. s., see Metev Meteva, M. see Name Meyer, B., see Benchiguer Meyer, B., ee Benchiguer Meyer, B., P. Omling and P. Emanuelsson, Landau oscillations in single quantum wells observed by microwave detection Meyerheim, H.L., see Schwarz Meyerson, B. S., see Arienzo Meyerheim, H.L., see Schwarz Meyerson, B. S., see Arienzo Meyerheim, H.L., see Schwarz Meyerson, B. S., see Arienzo Meyerheim, H.L., see Schwarz Meyerson, B. S., see Arienzo Meyerheim, H.L., see Schwarz Meyerson, B. S., see Arienzo Meyerheim, H.L., see Schwarz Meyerson, B. S., see Arienzo Meyerheim, H.L., see Schwarz Meyerson, B. S., see Arienzo Methalieseu, I.N., see Prokhorov Mihaileseu, I.N., see Prokhorov Miki, K., see Okumura Mihailesu, I.N., see Prokhorov Miki, K., see Okumura Mihailesu, I.N., see Prokhorov Miki, K., see Okumura Mihine, M.L., I.B. Wilson, T.T. Rantala and J. Lenkkeri, Morphological and structural changes in laser CVD of silicon: comparison of theoretical temperature calulations with experimental results Milne, M.J., I.B. Wilson, T.T. Rantala and J. Lenkkeri, Morphological and structural changes in laser CVD of silicon: comparison of theoretical temperature calulations with experimental results Milne, M.J., I.B. Wilson, T.T. Rantala and J. Lenkkeri, Morphological and structural changes in laser CVD of silicon: comparison of theoretical temperature calulations with experimental results Milne, M.J., I.P., Clough, S.C. Deane, S.D. Baker and P.A. Robertson, Photoenhanced CVD of hydrogenated amorphous silicon using an internal hydrogen discharge lamp Morphous silicon using an internal hydrogen and school and their application to an imaging device  Minnura, H. and Y. Hatanaka, The current transport mechanism of p-tyse a-Si-H/P-type -ES heter				
Mergue, S., see Hage-Ali Mesequer, F., see López Metev, S. and K. Meteva, Nucleation and growth of laser-plasma deposited thin films Mereix, K., see Bereir Meteva, K., see Metev Meyer, B., See Benchiguer Meyer, B., P. Omling and P. Emanuels- son, Landau oscillations in single quantum wells observed by microwave detection Meyerson, B.S., see Arienzo Meyerson, B.R., Gauthire and P. Finard, Structure and defects induced by electron beam irradiation in silicon sub- strates and EPR ribbons Miglion: A., see Berti Miglion: A., see Berti Minailescu, I.N., see Prokhorov Miki, K., see Okumura Miller, M.K., see Prokhorov Miller, M.S., Else Miller, M.S., see Prokhorov Miller, M.S., Else Miller, M.S., see Prokhorov Miller, M.S., Else Miller, M.S., see Prokhorov Miller, M.S., S		, ,		
Meseys, R. K. Metevs, Nucleation and growth of laser-plasma deposited thin from the properties and structure of high temperature annealed SIMOX wafer (1,42 (1989) 402 (1989) 402 (1989) 403 (1989) 403 (1989) 404 (1990) 325 (1991) 425 (1991) 425 (1991) 425 (1991) 425 (1991) 425 (1991) 425 (1991) 426 (1991) 42		,		
Metev, S. and K. Meteva, Nucleation and growth of laser-plasma deposited thin films  Meteva, K., See Breuer  Meteva, K., see Metev  Meteva, K., see Metev  Meteva, K., see Metev  Meteva, R., see Metev  Meteva, R., see Benchiguer  Meyer, B., P. Omling and P. Emanuels- son, Landau oscillations in single quantum wells observed by microwave detection  Meyers, B., See Schwarz  Meyers, B., See Arienzo  Meyers, B., See Schwarz  Meyers, B., See Arienzo  Meyerson, B.S., see Takeuchi  Monose, Y., see Takeuchi  Monose, Y., see Takeuchi  Monose, Y., see Takeuchi  Morai, J., A.M. Machado, M.A. Sacilotti  and J. Lankkeri, Morphological and structural c		, ,		41/42 (1909) 330
structure of high temperature and structured structured temperature calculations in single quantum wells observed by microwave detection  Meyer, B., See Benchiguer  Meyer, B., P. Omiting and P. Emanuelsson, Landau oscillations in single quantum wells observed by microwave detection  Meyerhem, H.L., see Schwarz  Meyerson, B.S., see Arienzo  Meyerhem, H.L., see Schwarz  Minglori, A., see Berti  Mihailescu, I.N., see Prokhorov  Mikailowa, G.N., see		41/ 42 (1707) 404		
films         43 (1989) 402         mealed SIMOX wafer         41/42 (1989) 378           Metev, R., see Metev         45 (1990) 356         Mizuki, J., see Akimoto         41/42 (1989) 374           Meteva, K., see Metev         45 (1990) 245         Mizuki, J., see Fujieda         41/42 (1989) 179           Meyer, B., See Benchiguer         50 (1991) 277         Mizuki, J., see Hirose         41/42 (1989) 179           Meyer, B., P. Omling and P. Emanuelsson, Landau oscillations in single quantum wells observed by microwave detection.         50 (1991) 420         Mizuki, J., see Hirose         41/42 (1989) 179           Meyerson, B. S., see Asinar         50 (1991) 420         Mochcizuki, Y., see Fujieda         41/42 (1989) 179         41/42 (1989) 179           Meyerson, B. S., see Asinaro         48 (49 (1991) 377         Mochizuki, Y., see Fujieda         41/42 (1989) 179         41/42 (1989) 179           Meyerson, B. S., see Asinaro         48 (49 (1991) 377         Mochizuki, Y., see Fujieda         41/42 (1989) 179         41/42 (1989) 179           Mcyerson, B. S., see Asinaro         48 (49 (1991) 377         Mochtales, L., see Roura         Momose, Y., see Takeuchi         46 (1990) 175         48 (49 (1991) 377         48 (49 (1991) 377         48 (49 (1991) 379         48 (49 (1991) 379         43 (1989) 340         43 (1989) 340         43 (1989) 340         44 (1980) 341         44 (1980) 341         44 (				
Metev, S., see Breuer         46 (1990) 336         Mizuki, J., see Akimoto         41/42 (1989) 316           Metva, K., see Metev         43 (1989) 402         Mizuki, J., see Fujieda         41/42 (1989) 167           Meyer, B., P. Omling and P. Emanuelsson, Landau oscillations in single quantum wells observed by microwave detection         46 (1990) 245         Mizuki, J., see Fujieda         41/42 (1989) 167           Meyer, B., P. Omling and P. Emanuelsson, Landau oscillations in single quantum wells observed by microwave detection         50 (1991) 420         Mizuki, J., see Fujieda         41/42 (1989) 167           Meyer, B., P. Omling and P. Emanuelsson, Landau oscillations in single quantum wells observed by microwave detection         50 (1991) 420         Mizuki, J., see Fujieda         41/42 (1989) 167           Morbidelia, R., Gauthier and P. Structure and defects induced by electron beam irradiation in silicon substates and EPR ribbons         43 (1989) 137         Mollot, F., see Jusserand         46 (1990) 125         46 (1990) 125         48/49 (1991) 517           Migliori, A., see Brribhons         43 (1989) 118         43 (1989) 118         43 (1989) 118         43 (1989) 118         43 (1989) 118         43 (1989) 118         43 (1989) 118         43 (1989) 118         43 (1989) 118         43 (1989) 118         44 (1990) 125         44 (1990) 129         44 (1990) 129         44 (1990) 129         44 (1990) 129         44 (1990) 129         44 (1990) 129         44 (1990) 129		43 (1989) 402		41 /42 (1080) 643
Meteva, K., see Metev Metselaar, J.W., see Zeman         43 (1989) 402         Mizuki, J., see Fujieda         41/42 (1989) 107           Meyer, B., See Benchiguer         50 (1991) 277         Mizutani, T., see Hirose         41/42 (1989) 107           Meyer, B., P. Omling and P. Emanuelsson, Landau oscillations in single quantum wells observed by microwave detection         Mochizuki, Y., see Fujieda         41/42 (1989) 174           Meyerson, B.S., see Arienzo         48 (49) (1991) 377         Mochizuki, Y., see Fujieda         41/42 (1989) 174           Meyerson, B.S., see Arienzo         48 (49) (1991) 456         Mochizuki, Y., see Fujieda         41/42 (1989) 174           Meyerson, B.S., see Arienzo         48 (49) (1991) 377         Mollekopf, G., see Golusda         46 (1990) 175           Meyerson, B.S., see Arienzo         48 (49) (1991) 377         Momose, Y., see Takeuchi         46 (1990) 159           Mchailer, R., R. Gauthier and P. Pinard, Structure and defects induced by elector beam irradiation in silicon substrates and EPR ribbons         43 (1989) 111         Monck, W., Mechanisms of barrier formation in Mendoped GaPs samples         41/42 (1989) 158           Mijalier, M., see Cracium         43 (1989) 158         Morais, J., A.M. Machado, M.A. Sacilotti and R. Landers, AES sputter depth Mikalieva, G.N., see Prokhorov         41/42 (1989) 340           Miller, M.K., see Okumara         41/42 (1989) 340         Morais, J., See Roulamand All Lenkeri, Morphological and structural changes in				
Metselaur, J.W., see Zeman Meyer, B., P. Omling and P. Emanuels- son, Landau oscillations in single quantum wells observed by microwave detection Meyerhein, H.L., see Schwarz Meyerson, B.S. see Arienzo Meyerhein, H.L., see Schwarz Meyerson, B.S., see Arienzo Meyerhein, H.L., see Schwarz Meyerhoin, H.L., see Schwarz Moreith, Mornhoin, Morch, W., Mechanisms of barrier formation in Mendoped GaP samples Moretic, T. and E. Pereira, Complex formation in Mn-doped GaP samples Moretic, J., see Brairamo Miki, K., see O'Anna Miki, H.S., see Prokhorov Miki, K., see O'Anna Miki, H.S., the Merchizuki, Y., see Fuijeda Moretic, Golubalo, J., see Reira Moretic, Gallen, J.				,
Meyer, B., see Benchiguer Meyer, B., P. Omling and P. Emanuelsson, Landau oscillations in single quantum wells observed by microwave detection Meyersheim, H.L., see Schwarz Meyerson, B.S., see Arienzo Meyerson, B.G. dollotop, G., see Golusda Moloson, J.M., see Disserand Momose, Y., see Takeuchi Momose, Y., see Takeuchi Momose, Y., see Baixramo Monteiro, T. and E. Pereira, Complex formation in Schottky contacts: metal-induced surface and interface states Morais, J., A.M. Machado, M.A. Sacilotti Morante, J.R., see Roura Mikhailora, C.N., see Prokhorov Miki, K., see Okumura Miller, M.K., see Prokhorov Miki, K., see Prokhorov Miki, K., see Okumura Miller, M.K., see Prokhorov Miki, M., see Okumura Morart, J.F., see Ourmazd Morart, J.F., see Ourmazd Morart,		• •		
Meyer, B., P. Omling and P. Emanuels- son, Landau oscillations in single quantum wells observed by microwae detection Meyerheim, H.L., see Schwarz Meyerson, B.S., see Arienzo Meyerheim, H.L., see Schwarz Meyerson, B.S., see Arienzo Mezhuyev, A.N., see Ukraintsev M'Ghaieth, R., R. Gauthier and P. Pinard, Structure and defects induced by electron beam irradiation in silicon sub- strates and EPR ribbons Migliori, A., see Prokhorov Migliori, A., see Prokhorov Mihailescu, I.N., see Pronkhorov Mihailescu, I.N., see Prokhorov Mihailescu, I.N.,				
son, Landau oscillations in single quantum wells observed by microwave detection  Meyerson, B.S., see Afenarz  Momose, Y., see Takeuchi  Monose, Y., see Takeuchi  Monose, Y., see Takeuchi  Monose, Y., see Takeuchi  Momose, Y., see Takeuchi  Monose, Y., see Takeuchi  Monose, Y., see Takeuchi  Monose, Y., see Takeuchi  Momose, Y., see Takeuchi  Momose, Y., see Takeuchi  Momose, Y., see Takeuchi  Momose, Y., see Panary  Morati, J., A.M. Machado, M.A. Sacilotti  Morati, J.R., see Roura  Morati, J.R., see Roura  Morati, J.R., see Roura  Mora		30 (1991) 277		
quantum wells observed by microwave detection detection  50 (1991) 420  50 (1991) 456  Meyerson, B.S., see Arienzo Meyerson, B.S., see Arienzo Mezhuyev, A.N., see Uraintsev M'Ghaieth, R., R. Gauthier and P. Pinard, Structure and defects induced by electron beam irradiation in silicon substrates and EPR ribbons Migliori, A., see Berti Mihailescu, I.N., see Prokhorov Mihailescu, I.N., see Prokhorov Mihailescu, I.N., see Prokhorov Miki, K., see Perty Milne, D., J.I.B. Wilson, T.T. Rantala and J. Lenkkeri, Morphological and structural changes in laser CVD of silicon: comparison of theoretical temperature calculations with experimental results Milne, W.I., F.J. Clough, S.C. Deane, S.D. Baker and P.A. Robertson, Photoenhaneed CVD of hydrogenated amorphous silicon using an internal hydrogen disknarge lamp Mimura, H. and Y. Hatanaka, The current transport mechanism of p-type a-Si: Hry-type c-Si heterojunctions and their application to an imaging device Mimura, H., K. Sai, Y. Ohta, K. Yamamoto and K. Kitamura, A two-dimensional image sensor with a-Si:H pin diodes Miscous, M., see Kothari Miscous, M., see Rickards Mollote, F., see Jusserand Mollot, F., see Takeuchi Mollot, W., Mechanisms of barrier formation in Schottly contacts: metal-induced surface and interface states Moreate, J., see Bairamov Morait, N., see Breira, Complex formation in Mn-doped GaP samples Morait, J., See Bairamov Morait, N., see Bairamov Morait, N., see Bairamov Morait, N., see Dreira canalysis of Galnas/InP grown by atmospheric pressure MOCVD Morait, M., see Outmard Morait, J., see Mam Morait, J., see Outmard Morait, J., see Mam Morait, J., see Mam Morait, J., see Mam Morait, J., se			The state of the s	, , ,
detection				
Meyerheim, H.L., see Schwarz Meyerson, B.S., see Arienzo Mezhuyev, A.N., see Utraintsev M'Ghaieth, R., R. Gauthier and P. Pinard, Structure and defects induced by electron beam irradiation in silicon substrates and EPR ribbons Migliori, A., see Berti Mihailescu, I.N., see Craciun Mihailescu, I.N., see Prokhorov Miki, K., see Okumura Miki, K., see Okumura Miki, K., see Okumura Miller, M.K., see Perus Miller, M.K., see Pothonov Miller, M.S., see Prokhorov Miller, M.S., see Prokhorov Miller, M.S., see Prokhorov Miki, M.S., see Okumura Miller, M.S., see Prokhorov Miki, M.S., see Prokhorov Miki, M.S., see Prokhorov Miki, M.S., see Prokhorov Miki, M.S., see Rokumura Miller, M.S., see Prokhorov Morart, J.F., U.O. Karlsson, R.I.G. Uhrberg, J. Kanski, P.O. Nilsson and H. Qu. Angle-resolved photocemission study of the As/Ge(100) interface and photocemission study of the As/Ge(100) interface and photocemission in terunal h	-	50 (1001) 420		
Mezhuyev, A.N., see Ukraintsev  Monetich, R., R. Gauthier and P. Pinard, Structure and defects induced by electron beam irradiation in silicon submit and R. Landers, AES sputter depth profiles applied to interface analysis of GalnAs/InP grown by atmospheric pressure MOCVD  Morante, J.R., see Roura  Morant, J.R., see Roura  Morant, J.R., see Roura  Morar, J.F., see Ourmazd  Morar, J.F., see Ourmazd  Moretti, G., S. De Rossi and G. Ferraris, Characterization of well dispersed copper species on the surface of ZnO by X-ray photoelectron spectroscopy and their application to an imaging device  Mimura, H., K. Sai, Y. Ohta, K. Yamamoto and K. Kitamura, A two-dimensional image sensor with a-Si:H pin diodes  Miscous, M., see Kothari  Miscous, M., see Rimmer  48/49 (1991) 521  Mönck, W., Mechanisms of barrier formation in Schottuky contacts states Monecke, J., see Bairamov  Monetico, T., and E. Pereira, Complex formation in Mn-doped GaP samples  Morais, J., A.M. Machado, M.A. Sacilotti and R. Landers, AES sputter depth profiles applied to interface analysis of GalnAs/InP grown by atmospheric pressure MOCVD  Morar, J.F., 2.O. Narlsson, R.I.G. Uhrberg, J. Kanski, P.O. Nilsson and H. Qu., Angle-resolved phot				,
Mezhuyev, A.N., see Ukraintsev M'Ghaieth, R., R. Gauthier and P. Pinard, Structure and defects induced by electron beam irradiation in silicon substrates and EPR ribbons Mijaliescu, I.N., see Prokhorov Mihailescu, I.N., see Prokhorov Mihailescu, I.N., see Prokhorov Mihailescu, I.N., see Prokhorov Mihailescu, I.N., see Prokhorov Miki, K., see Okumura Miller, M.K., see Perry Morat, J.F., U				48/49 (1991) 317
M'Ghaieth, R., R. Gauthier and P. Pinard, Structure and defects induced by electron beam irradiation in silicon substrates and EPR ribbons  Migliori, A., see Berti Mihailescu, I.N., see Prokhorov Mihailescu, I.N., see Craciun Mihailescu, I.N., see Prokhorov Mihailescu, I.N., see Prokhorov Mihailescu, I.N., see Prokhorov Mikikailova, G.N., see Prokhorov Miline, D., J.I.B. Wilson, T.T. Rantala and J. Lenkkeri, Morphological and structural changes in laser CVD of silicon: comparison of theoretical temperature calculations with experimental results Milne, W.I., F.J. Clough, S.C. Deane, S.D. Baker and P.A. Robertson, Photoenhanced CVD of hydrogenated amorphous silicon using an internal hydrogen device Mimura, H., and Y. Hatanaka, The current transport mechanism of p-type a-Si:H/n-type c-Si heterojunctions and their application to an imaging device Mimura, H., K. Sai, Y. Ohta, K. Yamamoto and K. Kitamura, A two-dimensional image sensor with a-Si:H pin diodes Misouk, M., see Rimmer Moranda, J., see Rickards Misouk, M., see Rimmer Moranda, J., see Rickards Morant, J.F., under substitute and R. Landers, AES sputter depth profiles applied to interface analysis of GalnAs/InP grown by atmospheric pressure MOCVD Morant, J.F., under substitute and R. Landers, AES sputter depth profiles applied to interface analysis of GalnAs/InP grown by atmospheric pressure MOCVD Morant, J.F., under substitute and R. Landers, AES sputter depth profiles applied to interface analysis of GalnAs/InP grown by atmospheric pressure MOCVD Morant, J.F., under substitute and R. Landers, AES sputter depth profiles applied to interface analysis of GalnAs/InP grown by atmospheric pressure MOCVD Morant, J.F., under substitute and R. Landers, AES sputter depth profiles applied to interface analysis of GalnAs/InP grown by atmospheric pressure MOCVD Morant, J.F., under substitute and R. Landers, AES sputter depth profiles applied to interface analysis of GalnAs/InP grown by atmospheric pressure MOCVD Morant, J.F., under substitute and R. Landers, AES sputte		,		
Structure and defects induced by electron beam irradiation in silicon substrates and EPR ribbons Migliori, A., see Berti Mihailescu, I.N., see Prokhorov Mihailescu, I.N., see Prokhorov Mihailescu, I.N., see Prokhorov Miki, K., see Okumura Miller, M.K., see Perry Miller, D., J.I.B. Wilson, T.T. Rantala and J. Lenkkeri, Morphological and structural changes in laser CVD of silicon: comparison of theoretical temperature calculations with experimental results Milne, W.I., F.J. Clough, S.C. Deane, S.D. Baker and P.A. Robertson, Photoenhanced CVD of hydrogenated amorphous silicon using an internal hydrogen device Mimura, H., and Y. Hatanaka, The current transport mechanism of p-type a-Si:H/n-type c-Si heterojunctions and their application to an imaging device Mimura, H., S. Sai, Y. Ohta, K. Yamamoto and K. Kitamura, A two-dimensional image sensor with a-Si:H pin diodes Missous, M., see Rimmer Monocke, J., see Bairamov Monotico, T. and E. Pereira, Complex formation in Mn-doped GaP samples Morais, J., A.M. Machado, M.A. Sacilotti and R. Landers, AES sputter depth profiles applied to interface analysis of GalnAs/InP grown by atmospheric pressure MOCVD Morant, J.R., see Roura Morar, J.F., U.O. Karlsson, R.I.G. Uhrberg, J. Kanski, P.O. Nilsson and H. Qu., Angle-resolved photoemission study of the As/Ge(100) interface Morar, J.F., see Ourmazd Moretti, G., S. De Rossi and G. Ferraris, Characterization of well dispersed copper species on the surface of ZnO by X-ray photoelectron spectroscopy Morgan, G.P., see O'Connor Mori, H., see Ma Morision, R.I.G. Uhrberger species on the surface of ZnO by X-ray photoelectron spectroscopy Morgan, G.P., see O'Connor Mori, H., see Ma Morision, R.I.G. Uhrberger species on the surface of ZnO by X-ray photoelectron spectroscopy Morgan, G.P., see O'Connor Mori, H., see Ma Morision, R.I.G. Uhrberger species on the surface of ZnO by X-ray photoelectron spectroscopy Morgan, G.P., see O'Connor Mori, H., see Ma Morision, R.I.G. Uhrberger species on the surface of ZnO by X-ray photoelectron spectrosc		48/49 (1991) 198	· ·	41 /42 (1000) 120
tron beam irradiation in silicon substrates and EPR ribbons  Migliori, A., see Berti Migliori, A., see Craciun Mihailescu, I.N., see Craciun Mihailescu, I.N., see Prokhorov Mihailescu, I.N., see Prokhorov Mihailescu, I.N., see Prokhorov Miki, K., see Proy Miller, M.K., see Perry Miller, M.K., see Perry Milne, D., J.I.B. Wilson, T.T. Rantala and J. Lenkkeri, Morphological and structural changes in laser CVD of silicon: comparison of theoretical temperature calculations with experimental results Milne, W.I., F.J. Clough, S.C. Deane, S.D. Baker and P.A. Robertson, Photoenhanced CVD of hydrogenated amorphous silicon using an internal hydrogen device Mimura, H. and Y. Hatanaka, The current transport mechanism of p-type a-Si:H/n-type c-Si heterojunctions and their application to an imaging device Mimura, H., K. Sai, Y. Ohta, K. Yamamoto and K. Kitamura, A two-dimensional image sensor with a-Si:H pin diodes Moratic, J., A.M. Machado, M.A. Sacilotti and R. Landers, AES sputter depth profiles applied to interface analysis of GalnAs/InP grown by atmospheric pressure MOCVD Morant, J.F., see Roura Morat, J.F., see Roura Morat, J.F., see Roura Morat, J.F., see Roura Morat, J.F., see Ourmazd Morat, J.F., see Ournor Mora, H., see Ma Moriya, N., see Pfeiffer Morone, A., see Giardini-Guidoni Mora, M., see Occhiello Moratic, M., see Divigalpitiva Morone, A., see Giardini-Guidoni Moratic, M., see Divigalpitiva Morsil, M., A. Bonnet, Y. Tregouet, A. Conan, S. Jobic and R. Brec, Electronic properties and band structure of IrSe <sub>2</sub> 50 (1991) 500				
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Migliori, A., see Berti Mihailescu, I.N., see Craciun Mihailescu, I.N., see Prokhorov Mihailescu, I.N., see Prokhorov Mihailescu, I.N., see Prokhorov Miki, K., see Okumura Miller, M.K., see Perry Miller, M.K., see Perry Miller, D., J.I.B. Wilson, T.T. Rantala and J. Lenkkeri, Morphological and structural changes in laser CVD of silicon: comparison of theoretical temperature calculations with experimental results Miller, W.I., F.J. Clough, S.C. Deane, S.D. Baker and P.A. Robertson, Photoen- hanced CVD of hydrogenated amorphous silicon using an internal hydrogen discharge lamp Mimura, H. and Y. Hatanaka, The current transport mechanism of p-type a-Si:H/n-type c-Si heterojunctions and their application to an imaging device Mimura, H., K. Sai, Y. Ohta, K. Yamamoto and K. Kitamura, A two-dimensional image sensor with a-Si:H pin diodes Misous, M., see Rickards Missous, M., see Rickards Missous, M., see Rimmer  43 (1989) 340 46 (1990) 365 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 45 (1989) 372 45 (1991) 472 46 (1990) 184 48 (1991) 521 48 (1991) 521 48 (1991) 521 48 (1990) 155 48 (1990) 155 49 (1991) 496 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 45 (1990) 321 46 (1990) 321 46 (1990) 321 46 (1990) 321 47 (1991) 323 48 (1991) 521 48 (1991		42 (1000) 111		50 (1001) 252
Mihailescu, I.N., see Craciun Mihailescu, I.N., see Prokhorov Mihailescu, I.N., see Prokhorov Mihailescu, I.N., see Prokhorov Mihailescu, I.N., see Prokhorov Mikhailova, G.N., see Prokhorov Mikhailova, G.N., see Prokhorov Mikhailova, G.N., see Prokhorov Milke, M.K., see Okumura Miller, M.K., see Perry Milne, D., J.I.B. Wilson, T.T. Rantala and J. Lenkkeri, Morphological and structural changes in laser CVD of silicon: comparison of theoretical temperature calculations with experimental results Milne, W.I., F.J. Clough, S.C. Deane, S.D. Baker and P.A. Robertson, Photoenhanced CVD of hydrogenated amorphous silicon using an internal hydrogen discharge lamp Mimura, H. and Y. Hatanaka, The current transport mechanism of p-type a-Si:H/n-type c-Si heterojunctions and their application to an imaging device Mimura, H., K. Sai, Y. Ohta, K. Yamamoto and K. Kitamura, A two-dimensional image sensor with a-Si:H pin diodes Minailescu, I.N., see Prokhorov 43 (1989) 340 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 44 (1990) 321 41/42 (1989) 365 Moratt, J.R., see Roura Morar, J.F., see Roura Morar, J.F., see Ourmazd Moretti, G., S. De Rossi and G. Ferraris, Characterization of well dispersed copper species on the surface of ZnO by X-ray photoelectron spectroscopy Morgan, G.P., see Wa Morishi, R., see Renda Moriya, N., see Renda Moriya, N., see Renda Moriya, N., see Renda Moriya, N., see Giardini-Guidoni Morra, M., see Occhiello Morrison, S.R., see Divigalpitiya Morision, S.R., see Divigalpitiya Morsli, M., A. Bonnet, Y. Tregouet, A. Conan, S. Jobic and R. Brec, Electronic properties and band structure of IrSe <sub>2</sub> 50 (1991) 50		,	•	30 (1991) 253
Mihailescu, I.N., see Prokhorov Mihailescu, I.N., see D'Anna Mikhailova, G.N., see Prokhorov Mikhailova, G.N., see Prokhorov Miki, K., see Okumura Miller, M.K., see Dokumura Miller, M.K., see Porty Milne, D., J.I.B. Wilson, T.T. Rantala and J. Lenkkeri, Morphological and structural changes in laser CVD of silicon: comparison of theoretical temperature calculations with experimental results Milne, W.I., F.J. Clough, S.C. Deane, S.D. Baker and P.A. Robertson, Photoenhanced CVD of hydrogenated amorphous silicon using an internal hydrogen discharge lamp Mimura, H. and Y. Hatanaka, The current transport mechanism of p-type a-Si:H/n-type c-Si heterojunctions and their application to an imaging device  Mimura, H., K. Sai, Y. Ohta, K. Yamamoto and K. Kitamura, A two-dimensional image sensor with a-Si:H pin diodes  Mihailova, G.N., see Prokhorov 44 (1990) 365  Moran, J.F., see Roura Morar, J.F., U.O. Karlsson, R.I.G. Uhberg, J. Kanski, P.O. Nilsson and H. Qu. Angle-resolved photoemission study of the As/Ge(100) interface Morar, J.F., see Ourmazd Moretti, G., S. De Rossi and G. Ferrarias, Characterization of well dispersed copper species on the surface of ZnO by X-ray photoelectron spectroscopy Moran, G.P., see O'Connor Mora, H., see Ma Morishi, E., see Renda Morita, K., see Ma Morishi, E., see Renda Morita, K., see Renda Moriya, N., see Renda Moriya, N., see Pfeiffer Morone, A., see Giardini-Guidoni Morra, M., see Occhiello Morra,		, ,		
Mihailescu, I.N., see D'Anna Mikhi, K., see Prokhorov Miki, K., see Okumura Miller, M.K., see Perry Miller, M.K., see Perry Miller, D., J.I.B. Wilson, T.T. Rantala and J. Lenkkeri, Morphological and structural changes in laser CVD of silicon: comparison of theoretical temperature calculations with experimental results Milne, W.I., F.J. Clough, S.C. Deane, S.D. Baker and P.A. Robertson, Photoenhanced CVD of hydrogenated amorphous silicon using an internal hydrogen discharge lamp Mimura, H. and Y. Hatanaka, The current transport mechanism of p-type a-Si:H/n-type c-Si heterojunctions and their application to an imaging device Mimura, H., K. Sai, Y. Ohta, K. Yamamoto and K. Kitamura, A two-dimensional image sensor with a-Si:H pin diodes Misewicz, J., see Rickards Misous, M., see Rimmer  44 (1990) 321  44 (1990) 321  44 (1990) 321  44 (1990) 321  44 (1990) 321  44 (1990) 321  44 (1990) 321  44 (1990) 321  44 (1990) 321  44 (1990) 321  45 (1990) 321  46 (1990) 321  47 (2 (1989) 322  48 (1989) 377  Morant, J.R., see Roura  Morant, J.R., see Roura  Morant, J.R., see Roura  Morar, J.F., U.O. Karlsson, R.I.G. Uhrberg, J. Kanski, P.O. Nilsson and H. Qu., Angle-resolved photoemission study of the As/Ge(100) interface  Morart, J.F., see Ourmazd  Moretti, G., S. De Rossi and G. Ferraris, Characterization of well dispersed copper species on the surface of ZnO by X-ray photoelectron spectroscopy  Morgan, G.P., see O'Connor  Morgan, G.P., see Ma  Morishi, E., see Ma  Morishi, E., see Ma  Morishi, E., see Ma  Morishi, E., see Na  Morishi, E., see Na  Morishi, E., see Na  Moretti, G., S. De Rossi and G. Ferraris, Characterization of well dispersed copper species on the surface of ZnO by X-ray photoelectron spectroscopy  Morgan, G.P., see O'Connor  Morgan, G.P., see O'Connor  Morgan, G.P., see Ma  Moretti, G., S. De Rossi and G. Ferraris, Characterization of well dispersed copper species on the surface of ZnO by X-ray photoelectron spectroscopy  Morgan, G.P., see O'Connor  Morgan, G.P., see O'Connor  Morgan, J.F., see Ourmazd  Mor				
Mikhailova, G.N., see Prokhorov Miki, K., see Okumura Miller, M.K., see Okumura Miller, M.K., see Perry Milne, D., J.I.B. Wilson, T.T. Rantala and J. Lenkkeri, Morphological and structural changes in laser CVD of silicon: comparison of theoretical temperature calculations with experimental results Milne, W.I., F.J. Clough, S.C. Deane, S.D. Baker and P.A. Robertson, Photoen- hanced CVD of hydrogenated amor- phous silicon using an internal hydro- gen discharge lamp Mimura, H. and Y. Hatanaka, The current transport mechanism of p-type a-Si: H/n-type c-Si heterojunctions and their application to an imaging device Mimura, H., K. Sai, Y. Ohta, K. Yama- moto and K. Kitamura, A two-dimensional image sensor with a-Si:H pin diodes Misewicz, J., see Jezierski Missous, M., see Rimmer Missous, M., see Rimmer Milne, M.I., F.J. Clough, S.C. Deane, S.D. 43 (1989) 277 Moran, J.F., see Ourmazd Moran, J.F., see Ourmazd Morat, J.F., see Ourmazd Morat, J.F., see Ourmazd Morat, J.F., see Ourmazd Moretti, G., S. De Rossi and G. Ferraris, Characterization of well dispersed copper species on the surface of ZnO by X-ray photoelectron spectroscopy Morgan, G.P., see O'Connor Mori, H., see Ma Morish, K., see Renda Morish, K., see Renda Morish, K., see Renda Morish, K., see Renda Moriya, N., see Pfeiffer Morone, A., see Giardini-Guidoni Moran, M., see Occhiello Morsin, M., a. Bonnet, Y. Tregouet, A. Conan, S. Jobic and R. Brec, Elec- tronic properties and band structure of IrSe 50 (1991) 500		,		
Miki, K., see Okumura Miller, M.K., see Perry Milne, D., J.I.B. Wilson, T.T. Rantala and J. Lenkkeri, Morphological and structural changes in laser CVD of silicon: comparison of theoretical tem- perature calculations with experimental results Milne, W.I., F.J. Clough, S.C. Deane, S.D. Baker and P.A. Robertson, Photoen- hanced CVD of hydrogenated amor- phous silicon using an internal hydro- gen discharge lamp Mimura, H. and Y. Hatanaka, The cur- rent transport mechanism of p-type a-Si:H/n-type c-Si heterojunctions and their application to an imaging device Mimura, H., K. Sai, Y. Ohta, K. Yama- moto and K. Kitamura, A two-dimen- sional image sensor with a-Si:H pin diodes Morant, J.R., see Roura Morart, J.F., Loo, Nilsson, and H. Qu. Angle-resolved photoemission study of the As/Ge(100) interface Morart, J.F., see Ourmazd Moretti, G., S. De Rossi and G. Ferraris, Characterization of well dispersed copper species on the surface of ZnO by X-ray photoelectron spectroscopy Morgan, G.P., see O'Connor Morishige, Y., S. Kitamura and S. Kis- hida, High performance contact for- mation in LSI circuit restructuring using visible pulse laser induced abla- tion and CVD Morita, K., see Renda Moriya, N., see Pfeiffer Morone, A., see Giardini-Guidoni Morra, J.F., see Ourmazd 41/42 (1989) 352 41/42 (1989) 572 43 (1989) 277 Morita, K., see Renda Morita, K., see Renda Moriya, N., see Pfeiffer Morone, A., see Giardini-Guidoni Morra, J.F., see Ourmazd 41/42 (1989) 365 48/49 (1991) 472 Morita, K., see Renda Morita, M.,				44 (1000) 161
Miller, M.K., see Perry Miller, D., J.I.B. Wilson, T.T. Rantala and J. Lenkkeri, Morphological and structural changes in laser CVD of silicon: comparison of theoretical temperature calculations with experimental results Milne, W.I., F.J. Clough, S.C. Deane, S.D. Baker and P.A. Robertson, Photoenhanced CVD of hydrogenated amorphous silicon using an internal hydrogen discharge lamp Mimura, H. and Y. Hatanaka, The current transport mechanism of p-type a-Si:H/n-type c-Si heterojunctions and their application to an imaging device Mimura, H., K. Sai, Y. Ohta, K. Yamamoto and K. Kitamura, A two-dimensional image sensor with a-Si:H pin diodes Miranda, J., see Richards Miranda, J., see Richards Missous, M., see Rimmer Missous, M., see Rimmer  44 (1990) 321 Morar, J.F., U.O. Karlsson, R.I.G. Uhrberg, J. Kanski, P.O. Nilisson and H. Qu, Angle-resolved photoemission study of the As/Ge(100) interface Morar, J.F., see Ourmazd Moretti, G., S. De Rossi and G. Ferraris, Characterization of well dispersed copper species on the surface of ZnO by X-ray photoelectron spectroscopy Morgan, G.P., see O'Connor Mori, H., see Se O'Connor Mori, H., see Se O'Connor Mori, H., see Peidfer Moria, K., see Renda Morision, S.R., see Renda Morision, S.R., see Renda Morison, S.R., see Giardini-Guidoni Morra, J.F., U.O. Karlsson, R.I.G. Uhrbetherg, J. Kanski, P.O. Nilison and H. Qu, Angle-resolved photoemission study of the As/Ge(100) interface Moretti, G., S. De Rossi and G. Ferraris, Characterization of well dispersed copper species on the surface of ZnO by X-ray photoelectron spectroscopy Morgan, G.P., see O'Connor Mori, H., see Peo 'Connor Mori, H., see Renda Morishige, Y., S. Kitamura and S. Kishida, High performance contact formation in LSI circuit restructuring using visible pulse laser induced ablation and CVD Morison, S.R., see Piciffer Morone, A., see Giardini-Guidoni Moria, H., see Peidfer Morison, S.R., see D			•	, ,
Milne, D., J.I.B. Wilson, T.T. Rantala and J. Lenkkeri, Morphological and structural changes in laser CVD of silicon: comparison of theoretical temperature calculations with experimental results  Milne, W.I., F.J. Clough, S.C. Deane, S.D. Baker and P.A. Robertson, Photoenhanced CVD of hydrogenated amorphous silicon using an internal hydrogen discharge lamp  Mimura, H. and Y. Hatanaka, The current transport mechanism of p-type a-Si:H/n-type c-Si heterojunctions and their application to an imaging device  Mimura, H., K. Sai, Y. Ohta, K. Yamamoto and K. Kitamura, A two-dimensional image sensor with a-Si:H pin diodes  Michological and D. Lenkkeri, Morphological and S. Kis-Mida, High performance contact formation in LSI circuit restructuring using visible pulse laser induced ablation and CVD  Moriya, N., see Pfeiffer  Moron, A., see Giardini-Guidoni Morra, M., see Pfeiffer Moron, A., see Giardini-Guidoni Morra, M., see Pfeiffer Moron, A., see Giardini-Guidoni Morra, M., see Pfeiffer Moron, A., see Giardini-Guidoni Morra, M., see Pfeiffer Moron, A., see Divigalpitiya  Morsion, S.R., see Divigalpitiya  Morsion, S. R., see Divigalpitiya  Morsion, S. Jobic and R. Brec, Electronic properties and band structure of IrSe <sub>2</sub> 50 (1991) 500				50 (1991) 496
and J. Lenkkeri, Morphological and structural changes in laser CVD of silicon: comparison of theoretical temperature calculations with experimental results  Milne, W.I., F.J. Clough, S.C. Deane, S.D. Baker and P.A. Robertson, Photoenhanced CVD of hydrogenated amorphous silicon using an internal hydrogen discharge lamp  Mimura, H. and Y. Hatanaka, The current transport mechanism of p-type a-Si:H/n-type c-Si heterojunctions and their application to an imaging device  Mimura, H., K. Sai, Y. Ohta, K. Yamamoto and K. Kitamura, A two-dimensional image sensor with a-Si:H pin diodes  Microsing, G.P., see O'Connor Moria, H., see Ma  Morishige, Y., S. Kitamura and S. Kishida, High performance contact formation in LSI circuit restructuring using visible pulse laser induced ablation and CVD  Morita, K., see Renda  Morita, K., see Renda  Morita, K., see Renda  Morita, K., see Renda  Morita, K., see Giardini-Guidoni Morra, M., see Occhiello  Morra, M., see O'Connor  Morita, K., see Piffer  Morone, A., see Giardini-Guidoni Morra, M., see Occhiello  Morra, M., see Occhiello  Morra, M., see O'Connor  Morita, K., see Piffer  Morone, A., see Giardini-Guidoni Morra, M., see Occhiello  Morra, M., see Occhiello  Morra, M., see Occhiello  Morra, M., see Occhiello  Morra, M., see O'Connor  Morita, K., see Divigalpitiya  Morra, M., see Occhiello  Morra, M., see Occhiello  Morra, M., see Occhiello  Morra, M., see Divigalpitiya  Morra, M., see Occhiello  Morra, M., see Divigalpitiya  Morra, M., see Nona  Morra, M., see Nona  Morra, M., see Nona  Morra, M., see Nona  Morra, M., see Diviga		44 (1990) 321		
structural changes in laser CVD of silicon: comparison of theoretical temperature calculations with experimental results  Milne, W.I., F.J. Clough, S.C. Deane, S.D.  Baker and P.A. Robertson, Photoenhanced CVD of hydrogenated amorphous silicon using an internal hydrogen discharge lamp  As (1989) 277  Mimura, H. and Y. Hatanaka, The current transport mechanism of p-type a-Si:H/n-type c-Si heterojunctions and their application to an imaging device  Mimura, H., K. Sai, Y. Ohta, K. Yamamoto and K. Kitamura, A two-dimensional image sensor with a-Si:H pin diodes  Morar, J.F., see Ourmazd  Moretti, G., S. De Rossi and G. Ferraris, Characterization of well dispersed copper species on the surface of ZnO by X-ray photoelectron spectroscopy  Morgan, G.P., see O'Connor  Morih, H., see Ma  Morishing, Y., S. Kitamura and S. Kishida, High performance contact formation in LSI circuit restructuring using visible pulse laser induced ablation and CVD  Moriya, N., see Pieiffer  Morone, A., see Giardini-Guidoni  Morra, M., see Occhiello  Morrison, S.R., see Divigalpitiya  Morsion, S.R., see Rickards  Morsion, S.R., see Divigalpitiya  Morsion, S.R., see Rickards  Morsion, S.R., see Divigalpitiya  Morsion, S.R., see Divigalpitiya  Morsion, S.R., see Rickards  Morsion, S.R., see Divigalpitiya  Morsion, S.R., see Divigalpitiya  Morsion, S.R., see Rickards  Morsion, S.R., see Divigalpitiya  Morsion, S.R., see Rickards  Morsion, S.R., see Divigalpitiya  Morsion, S.R., see Divigalpitiya  Morsion, S.R., see Rickards  Morsion, S.R., see Divigalpitiya  Morsion, S.R., see Divigalpitiya  Morsion, S.R., see Divigalpitiya  Morsion, S.R., see Ma  Morsion, S.R., see Divigalpitya  Morsion, S.R., see Divigalpitya  Morsion, S.R., see Ma  Morsion, S.R., see Divigalpitya  Morsion, S.R.				
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perature calculations with experimental results  Milne, W.I., F.J. Clough, S.C. Deane, S.D.  Baker and P.A. Robertson, Photoenhanced CVD of hydrogenated amorphous silicon using an internal hydrogen discharge lamp  a-Si:H/n-type c-Si heterojunctions and their application to an imaging device  Mimura, H., K. Sai, Y. Ohta, K. Yamamoto and K. Kitamura, A two-dimensional image sensor with a-Si:H pin diodes  Moretti, G., S. De Rossi and G. Ferraris, Characterization of well dispersed copper species on the surface of ZnO by X-ray photoelectron spectroscopy  Morgan, G.P., see O'Connor  Morishige, Y., S. Kitamura and S. Kishida, High performance contact formation in LSI circuit restructuring using visible pulse laser induced ablation and CVD  Morita, K., see Renda  Moriya, N., see Pfeiffer  Morone, A., see Giardini-Guidoni  Morra, M., see Occhiello  Morra, M., see Occhiello  Morra, M., see Occhiello  Morra, M., see Divigalpitiya  48/49 (1991) 521  Morsli, M., A. Bonnet, Y. Tregouet, A. Conan, S. Jobic and R. Brec, Electronic properties and band structure  Missous, M., see Rimmer  Moretti, G., S. De Rossi and G. Ferraris, Characterization of well dispersed copper species on the surface of ZnO by X-ray photoelectron spectroscopy  Morgan, G.P., see O'Connor  Morishige, Y., S. Kitamura and S. Kishida, High performance contact formation in LSI circuit restructuring using visible pulse laser induced ablation and CVD  Morita, K., see Renda  Moriya, N., see Pfeiffer  Morone, A., see Giardini-Guidoni  Morra, M., see Occhiello  Morra, M., see Occhiello  Morra, M., see Divigalpitiya  Morsli, M., A. Bonnet, Y. Tregouet, A. Conan, S. Jobic and R. Brec, Electronic properties and band structure  Missous, M., see Rimmer  Morsli, M., a. Bonnet, Y. Tregouet, A. Conan, S. Jobic and R. Brec, Electronic properties and band structure  Missous, M., see Rimmer  Morsli, M., a. Bonnet, Y. Tregouet, A. Conan, S. Jobic and R. Brec, Electronic properties and band structure  Missous, M., see Rimmer				, , ,
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Milne, W.I., F.J. Clough, S.C. Deane, S.D.  Baker and P.A. Robertson, Photoen- hanced CVD of hydrogenated amor- phous silicon using an internal hydro- gen discharge lamp  Mimura, H. and Y. Hatanaka, The cur- rent transport mechanism of p-type a-Si:H/n-type c-Si heterojunctions and their application to an imaging device  Mimura, H., K. Sai, Y. Ohta, K. Yama- moto and K. Kitamura, A two-dimen- sional image sensor with a-Si:H pin diodes  Miotello, A., see Kothari Missous, M., see Rimmer  Millone, W.I., F.J. Clough, S.C. Deane, S.D.  by X-ray photoelectron spectroscopy Morgan, G.P., see O'Connor Mori, H., see Ma  43 (1989) 277  Morishige, Y., S. Kitamura and S. Kis- hida, High performance contact for- mation in LSI circuit restructuring using visible pulse laser induced abla- tion and CVD  48/49 (1991) 472  Morita, K., see Renda Moriya, N., see Pfeiffer Morrone, A., see Giardini-Guidoni Morrison, S.R., see Divigalpitiya Morsion, S.R., see Divigalpitiya Morsion, S.R., see Divigalpitiya Morsion, S. Jobic and R. Brec, Elec- tronic properties and band structure Missous, M., see Rimmer  Copper species on the surface of ZnO by X-ray photoelectron spectroscopy Morgan, G.P., see O'Connor Mori, H., see Ma  41/42 (1989) 572  Morishige, Y., S. Kitamura and S. Kis- hida, High performance contact for- mation in LSI circuit restructuring using visible pulse laser induced abla- tion and CVD  46 (1990) 108  46 (1990) 108  47 (1991) 235  Morrison, S.R., see Divigalpitiya Morsion, S.R., see Divigalpitiya Morsion, S. Jobic and R. Brec, Elec- tronic properties and band structure for photoscients and photoscients and band structure for photoscients and photoscien	•			
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hanced CVD of hydrogenated amorphous silicon using an internal hydrogen discharge lamp  43 (1989) 277  Mori, H., see Ma  Morishige, Y., S. Kitamura and S. Kishida, High performance contact formation in LSI circuit restructuring using visible pulse laser induced ablation and CVD  Mimura, H., K. Sai, Y. Ohta, K. Yamamoto and K. Kitamura, A two-dimensional image sensor with a-Si:H pin diodes  Miotello, A., see Kothari  Missous, M., see Rimmer  Morgan, G.P., see O'Connor  Mori, H., see Ma  Morishige, Y., S. Kitamura and S. Kishida, High performance contact formation in LSI circuit restructuring using visible pulse laser induced ablation and CVD  48/49 (1991) 472  Morita, K., see Renda  Moriya, N., see Pfeiffer  Morone, A., see Giardini-Guidoni  Morra, M., see Occhiello  48/49 (1991) 521  Morrison, S.R., see Divigalpitiya  48/49 (1991) 572  Morsli, M., A. Bonnet, Y. Tregouet, A.  Conan, S. Jobic and R. Brec, Electronic properties and band structure  Missous, M., see Rimmer  50 (1991) 312  41/42 (1989) 572  46 (1990) 108  46 (1990) 108  46 (1990) 108  47 (1991) 154  Morrison, S.R., see Divigalpitiya  Morsli, M., A. Bonnet, Y. Tregouet, A.  Conan, S. Jobic and R. Brec, Electronic properties and band structure  for IrSe <sub>2</sub> 50 (1991) 500				
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rent transport mechanism of p-type a-Si:H/n-type c-Si heterojunctions and their application to an imaging device  48/49 (1991) 472  Mimura, H., K. Sai, Y. Ohta, K. Yama- moto and K. Kitamura, A two-dimen- sional image sensor with a-Si:H pin diodes  Miotello, A., see Kothari  Miotello, A., see Rickards  Miranda, J., see Rickards  Missous, M., see Rimmer  Mation in LSI circuit restructuring using visible pulse laser induced abla- tion and CVD  Morita, K., see Renda  41/42 (1989) 216  Moriya, N., see Pfeiffer  Morone, A., see Giardini-Guidoni 46 (1990) 321  Morra, M., see Occhiello  48/49 (1991) 521  Morrison, S.R., see Divigalpitiya  48/49 (1991) 572  Morsli, M., A. Bonnet, Y. Tregouet, A. Conan, S. Jobic and R. Brec, Elec- tronic properties and band structure of IrSe <sub>2</sub> 50 (1991) 500		43 (1989) 277		
a-Si:H/n-type c-Si heterojunctions and their application to an imaging device  48/49 (1991) 472  Mimura, H., K. Sai, Y. Ohta, K. Yamamoto and K. Kitamura, A two-dimensional image sensor with a-Si:H pin diodes  Miotello, A., see Kothari  Miranda, J., see Rickards  Missous, M., see Rimmer  48/49 (1991) 472  Morita, K., see Renda  41/42 (1989) 216  Moriya, N., see Pfeiffer  Morone, A., see Giardini-Guidoni  46 (1990) 321  Morra, M., see Occhiello  47 (1991) 235  Morrison, S.R., see Divigalpitiya  48/49 (1991) 572  Morsli, M., A. Bonnet, Y. Tregouet, A.  Conan, S. Jobic and R. Brec, Electronic properties and band structure  Missous, M., see Rimmer  50 (1991) 149  of IrSe <sub>2</sub> 50 (1991) 500			•	
and their application to an imaging device  48/49 (1991) 472  Mimura, H., K. Sai, Y. Ohta, K. Yamamoto and K. Kitamura, A two-dimensional image sensor with a-Si:H pin diodes  Miotello, A., see Kothari  Miranda, J., see Rickards  Missous, M., see Rimmer  tion and CVD  Morita, K., see Renda  41/42 (1989) 216  Moriya, N., see Pfeiffer  Morone, A., see Giardini-Guidoni  46 (1990) 321  Morrison, S.R., see Divigalpitiya  48/49 (1991) 521  Morsli, M., A. Bonnet, Y. Tregouet, A.  Conan, S. Jobic and R. Brec, Electronic properties and band structure  of IrSe <sub>2</sub> 50 (1991) 500				
device       48/49 (1991) 472       Morita, K., see Renda       41/42 (1989) 216         Mimura, H., K. Sai, Y. Ohta, K. Yamamoto and K. Kitamura, A two-dimensional image sensor with a-Si:H pin diodes       Moriya, N., see Pfeiffer       50 (1991) 154         Morone, A., see Giardini-Guidoni       46 (1990) 321         Morra, M., see Occhiello       47 (1991) 235         Morison, S.R., see Divigalpitiya       48/49 (1991) 572         Miotello, A., see Kothari       43 (1989) 237       Morsli, M., A. Bonnet, Y. Tregouet, A.         Miranda, J., see Rickards       45 (1990) 155       Conan, S. Jobic and R. Brec, Electronic properties and band structure of IrSe2       50 (1991) 500				
Mimura, H., K. Sai, Y. Ohta, K. Yamamoto and K. Kitamura, A two-dimensional image sensor with a-Si:H pin diodes  Moriya, N., see Pfeiffer  Morone, A., see Giardini-Guidoni  Morra, M., see Occhiello  Morra, M., see Occhiello  Morrison, S.R., see Divigalpitiya  Morsli, M., A. Bonnet, Y. Tregouet, A.  Miranda, J., see Rickards  Moriya, N., see Pfeiffer  Morone, A., see Giardini-Guidoni  46 (1990) 321  Morrison, S.R., see Divigalpitiya  Morsli, M., A. Bonnet, Y. Tregouet, A.  Conan, S. Jobic and R. Brec, Electronic properties and band structure  Missous, M., see Rimmer  Moriya, N., see Pfeiffer  50 (1991) 154  Morone, A., see Giardini-Guidoni  47 (1991) 235  Morrison, S.R., see Divigalpitiya  48/49 (1991) 572  Morsli, M., A. Bonnet, Y. Tregouet, A.  Conan, S. Jobic and R. Brec, Electronic properties and band structure  of IrSe <sub>2</sub> 50 (1991) 500	and their application to an imaging			, ,
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Misiewicz, J., see Jezierski 50 (1991) 341 tronic properties and band structure Missous, M., see Rimmer 50 (1991) 149 of IrSe <sub>2</sub> 50 (1991) 500	Miotello, A., see Kothari	43 (1989) 237	Morsli, M., A. Bonnet, Y. Tregouet, A.	
Missous, M., see Rimmer 50 (1991) 149 of IrSe <sub>2</sub> 50 (1991) 500	Miranda, J., see Rickards	45 (1990) 155	Conan, S. Jobic and R. Brec, Elec-	
	Misiewicz, J., see Jezierski	50 (1991) 341	tronic properties and band structure	
Mitra, S.S., see Banerjee 48/49 (1991) 288 Mosca, R., see Ghezzi 50 (1991) 400	Missous, M., see Rimmer	50 (1991) 149	of IrSe <sub>2</sub>	50 (1991) 500
	Mitra, S.S., see Banerjee	48/49 (1991) 288	Mosca, R., see Ghezzi	50 (1991) 400

Mosca, R., see Castaldini	50 (1991) 485	Nakagawa, A., see Furukawa	41/42 (1989) 627
Mosel, F., A. Seidl, D. Hofmann and G.		Nakamura, H., see Iwami	41/42 (1989) 57
Müller, Infrared absorption of n- and		Nakamura, T., see Nakanishi	48/49 (1991) 55
p-type Fe-doped InP and mapping of		Nakamura, T., Y. Takeuchi, H. Mura-	
the Fe distribution	50 (1991) 364	matsu, H. Fujiyasu and Y. Nakanishi,	
Moser, E.M., see Browne	47 (1991) 375	ESR studies on luminescent ZnS:Mn	
Moses, C., see Li	48/49 (1991) 160	films and CdS-ZnS:Mn superlattices	
Moss, S.C., J.F. Knudsen, R.C. Bowman,		deposited on a GaAs(100) substrate	
Jr., P.M. Adams and D.D. Smith, Pi-		by hot-wall epitaxy	48/49 (1991) 478
cosecond transient photoreflectance		Nakanishi, S., H. Tokutaka, K. Nishimori,	
measurements of ion-implanted GaAs	50 (1991) 337	S. Kishida and N. Ishihara, The dif-	
Moulin, J., see Abel	44 (1990) 17	ference between 6H-SiC (0001) and	
Mowbray, A. and R.G. Jones, Homo- and		(0001) faces observed by AES, LEED	
hetero-iodide thin film growth on		and ESCA	41/42 (1989) 44
InSb(001): low-temperature iodide		Nakanishi, Y., Y. Suzuki, T. Nakamura,	
formation and epitaxial growth of		Y. Hatanaka, Y. Fukuda, A. Fujisawa	
CdI <sub>2</sub>	48/49 (1991) 27	and G. Shimaoka, Coloration of Sn-	
Mugnier, J., see Boelle	46 (1990) 200	Sb-O thin films	48/49 (1991) 55
Muhler, M., Z. Paál and R. Schlögl, XPS	()	Nakanishi, Y., Y. Fukuda, Y. Hatanaka	, (-,, -,
of platinum in Pt/SiO <sub>2</sub> (Europt-1):		and G. Shimaoka, The dependence of	
possibilities and limitations of the		the polycrystalline structure and elec-	
method	47 (1991) 281	troluminescent properties of ZnS:Mn	
Muller, F., see Chartier	45 (1990) 351	deposited on Y <sub>2</sub> O <sub>3</sub> films on thickness	48/49 (1991) 297
Müller, G., see Mosel	50 (1991) 364	Nakanishi, Y., see Nakamura	48/49 (1991) 478
Müller, H.G., K. Buschick, S. Schuler and	30 (1771) 304	Nakano, K., see Matsuo	41/42 (1989) 53
A. Paredes, Laser direct writing of		Nakasaki, Y., see Suguro	, , , , , , , , , , , , , , , , , , , ,
copper on various thin-film substrate			41/42 (1989) 277
materials	46 (1000) 142	Nakashima, H., see Li	41/42 (1989) 118
	46 (1990) 143	Nakashima, H., see Maehashi	41/42 (1989) 567
Müller, J., see Bauer	50 (1991) 138	Nakatani, Y., see Okuyama	41/42 (1989) 633
Muller, J.C., see Hartiti	46 (1990) 371	Nakayama, N., see Tatsuyama	41/42 (1989) 539
Muñoz, A., see Flores	41/42 (1989) 144	Nakayama, T., see Kanamoto	41/42 (1989) 526
Munuera, G., see Gonzalez-Elipe	45 (1990) 103	Nannetti, C.A., see Fantoni	43 (1989) 308
Murakami, M., H.J. Kim, YC. Shih,		Naudon, A., see Mathé	43 (1989) 142
W.H. Price and C.C. Parks, Effects of		Nebesny, K.W., see Ingram	44 (1990) 279
interfacial microstructure on ohmic	41 /40 (1000) 105	Nebesny, K.W., see Ingram	44 (1990) 293
contacts to GaAs	41/42 (1989) 195	Nebesny, K.W., see Ingram	45 (1990) 247
Muramatsu, H., see Nakamura	48/49 (1991) 478	Nebesny, K.W., see Ingram	45 (1990) 278
Murata, Y., see Iwami	41/42 (1989) 97	Neelmeijer, C., P. Knothe, M. Posselt, E.	
Muschik, T., see Schwarz	50 (1991) 456	Richter and KH. Heinig, Wear re-	
Musci, M., see Curcio	46 (1990) 225	sistant coatings produced by C+ im-	
Myburg, G., J.B. Malherbe and E. Fried-		plantation	43 (1989) 232
land, Electrical characteristics of ion		Nelson, A.J., S. Gebhard, L.L. Kazmer-	
bombarded Ni/n-Si Schottky contacts	43 (1989) 242	ski, A. Rockett, E. Colavita, M. En-	
Myburg, G., see Bredell	50 (1991) 466	gelhardt and H. Höchst, Soft X-ray	
		photoemission investigation of the	
		CdS/CuInSe <sub>2</sub> heterojunction inter-	
		face	48/49 (1991) 419
		Nesladek, M., see Usala	50 (1991) 265
Nadahara, S., J. Shiozawa, K. Imai, K.		Netterfield, R.P., see Bartlett	47 (1991) 187
Suguro and K. Yamabe, Protuberance		Neumann, G., see Herres	50 (1991) 97
growth at polysilicon surfaces during		Neumayer, G., see Stock	46 (1990) 348
oxidation	41/42 (1989) 425	Nevot, L., see Gendry	44 (1990) 309
Nagano, J., see Sugahara	41/42 (1989) 207	Newman, N., see Spicer	41/42 (1989) 1
Nagashima, S., E. Fukuchi and I. Ogura,	, (,	Nguyen Tan, T.A., see Cherief	41/42 (1989) 241
Growth modes of overlayers of Se de-		Nguyen Tan, T.A., N. Guerfi, J.Y. Veuil-	-/ ()
posited on Cu(111) surfaces	48/49 (1991) 44	len and J. Derrien, Oxidation of TaSi <sub>2</sub>	
Nagoshi, M., see Fukuda	48/49 (1991) 147	thin films on polycrystalline Si	41/42 (1989) 266
,,	(222)	min on porjor journile of	.1/ 12 (1707) 200

Nickel, H., see Quadakkers	47 (1991) 261	chromium films deposited from	
Nicoletti, S., see Berti	43 (1989) 158	Cr(CO) <sub>6</sub> at 248 nm	43 (1989) 11
Nicoletti, S., see Nipoti	43 (1989) 321	Nowak, R., see Braun	43 (1989) 352
Niles, D.W., M. Tang, J. McKinley, R.		Nowak, R., see Konstantinov	46 (1990) 102
Zanoni and G. Margaritondo, From		Nowicka, E., Z. Wolfram and R. Duś,	
heterojunction interfaces to metal-		Deuterium adsorption on thin nickel	
semiconductor interfaces	41/42 (1989) 139	films	45 (1990) 13
Nilsson, P.O., see Morar	41/42 (1989) 312	Nunes, A.C., see Pickart	48/49 (1991) 436
Nilsson, S., see Gustafsson	50 (1991) 186	Nunoshita, M., see Gofuku	48/49 (1991) 343
Nipoti, R., M. Bianconi, R. Fabbri, M.			
Servidori, S. Nicoletti and R. Canteri,		Occhiello, E., M. Morra, F. Garbassi, D.	
Electrical and structural characteriza-		Johnson and P. Humphrey, SSIMS	
tion of silicon layers directly doped		studies of hydrophobic recovery:	
with boron by excimer laser irradia-		oxygen plasma treated PS	47 (1991) 235
tion	43 (1989) 321	Ochi, M., see Yokota	41/42 (1989) 411
Nipoti, R., D. Pocci, A. Cetronio and C.		O'Connor, D.J., see Priggemeyer	44 (1990) 255
Lanzieri, Carrier and mobility profile		O'Connor, D.J., see King	48/49 (1991) 246
measurements in n-type ion-implanted		O'Connor, G.M., C.J. McDonagh, F.G.	
GaAs by the differential sheet resistiv-		Anderson, T.J. Glynn, G.P. Morgan,	
ity and Hall effect technique	50 (1991) 410	G.J. Hughes, L. Roberts and M.O.	
Niselson, L.A., see Shapoval	45 (1990) 257	Henry, Raman characterization of	
Nishigaki, Y., see Kumomi	41/42 (1989) 638	passivated GaAs surfaces	50 (1991) 312
Nishikawa, S., see Igarashi	41/42 (1989) 282	Odelius, H., see Lausmaa	45 (1990) 189
Nishimori, K., see Nakanishi	41/42 (1989) 44	Oelhafen, P., see Schelz	48/49 (1991) 301
Nishimori, K., H. Tokutaka, Z. Okinaga,		Oelhafen, P., see Mansour	48/49 (1991) 312
S. Kishida and N. Ishihara, Observa-		Oetzmann, H., see Nowak	43 (1989) 11
tion of Si and SiC surface structures	41 /42 (1000) 40	Oetzmann, H., see Braun	43 (1989) 352
using the magnetic LEED method	41/42 (1989) 49	Oetzmann, H., see Schmaderer	46 (1990) 53
Nishimori, K., H. Tokutaka, H. Sumi and		Oetzmann, H., see Hesch	46 (1990) 233
N. Ishihara, Interface reaction of Si	47 (1001) 265	Ogawa, A., see Shoji	48/49 (1991) 373
thin film on Au substrate	47 (1991) 365 48/49 (1991) 446	Ogawa, S., T. Yoshida, T. Kouzaki, S. Okuda and K. Tsukamoto, Thermal	
Nishimori, K., see Kishida Nishimori, K., H. Tokutaka, T. Tamon, S.	40/49 (1991) 440	instability of the TiSi <sub>2</sub> /Si structure:	
Kishida and N. Ishihara, Surface study		impurity effects	41/42 (1989) 290
of single-crystal 80 K Bi-Sr-Ca-Cu-		Ogura, I., see Nagashima	48/49 (1991) 44
O superconductor with Si and Nb by		Ohdomari, I., see Akatsu	41/42 (1989) 357
RHEED and XPS depth profile	48/49 (1991) 450	Ohdomari, I., see Fischer	44 (1990) 115
Nishimura, T., see Miyatake	41/42 (1989) 643	Ohga, K., see Gekka	41/42 (1989) 184
Nishizawa, H., see Yasumatsu	48/49 (1991) 414	Ohnishi, N., Y. Makita, A. Yamada, H.	41/42 (1707) 104
Nissim, Y.I., J.M. Moison, F. Houzay, F.	40/42 (1221) 414	Asakura and T. Matsumori, Effect of	
Lebland, C. Licoppe and M. Bensous-		substrate orientation on the defect-in-	
san, Photo-assisted deposition of thin		duced bound exciton emissions in	
films on III-V semiconductors with		GaAs grown by molecular beam epi-	
UV and IR lamps	46 (1990) 175	taxy	50 (1991) 233
Nogier, J.Ph., J. Thoret, N. Jammul and J.	()	Ohno, H., see Hasegawa	41/42 (1989) 372
Fraissard, Phase distribution in Ti-		Ohno, H., see Ishii	41/42 (1989) 390
V-O catalysts	47 (1991) 287	Ohno, H., see Saitoh	41/42 (1989) 402
Nolhier, N., see Dilhac	46 (1990) 451	Ohno, S., see Igarashi	41/42 (1989) 282
Nomura, T., K. Wakatuki, M. Miyao and		Ohshima, N., Y. Koide, S. Zaima and Y.	, , , , , ,
M. Hagino, Characterization of the		Yasuda, Formation of a superstruc-	
GaAs buffer layer grown on GaP by		ture in the initial stage of Ge epitaxial	
MBE for the two-step growth method	41/42 (1989) 512	growth on Si(100) substrates	48/49 (1991) 69
Nomura, T., see Takeuchi	41/42 (1989) 530	Ohta, Y., see Mimura	48/49 (1991) 521
Notaro, N., see Curcio	46 (1990) 225	Ohtsuki, K., see Yokota	41/42 (1989) 411
Nouet, G., see Mary	43 (1989) 102	Oishi, K., K. Fukuchi, T. Suzuki and J.	
Nowak, R., P. Hess, H. Oetzmann and C.		Sunada, Mechanism of photoconduc-	
Schmidt, XPS characterization of		tion on surface-oxidized Ge films	48/49 (1991) 276

Okinaga, Z., see Nishimori	41/42 (1989) 49	Rossouw, A.W. Stevenson, S.P. Russo,	
Öktü, Ö., see Usala	50 (1991) 265	R.G. Elliman, L.S. Wielunski, R.S.	
Oku, M., see Suzuki	44 (1990) 151	Rowe, G.B. Deacon, R.S. Dickson and	
Okuda, S., see Ogawa	41/42 (1989) 290	B.O. West, Characterization of low- temperature MOCVD Cd <sub>1-x</sub> Mn <sub>x</sub> Te	
Okumura, H., K. Miki, K. Sakamoto, T.		thin films $MOCVD Cd_{1-x}Mn_x$ Te	48/49 (1991) 76
Sakamoto, K. Endo and S. Yoshida, Raman scattering and photolumines-		Palange, E., see Himpsel	41/42 (1989) 346
cence characterization of Ge/Si		Pan, Fu-Ming, Yuh-Lin Lin and Shean-	41/42 (1909) 340
strained-layer superlattices grown by		Ren Horng, Decomposition of perflu-	
phase-locked epitaxy	41/42 (1989) 548	oropolyethers during XPS measure-	
Okuyama, M., see Inoue	41/42 (1989) 407	ments	47 (1991) 9
Okuyama, M., N. Fujiki, Y. Nakatani, K.	12/ 12 (1505) 101	Pandey, R.K., see Gore	48/49 (1991) 530
Inoue and Y. Hamakawa, Growth be-		Paoli, T.L., see Epler	43 (1989) 432
havior of highly oriented Si films on		Papadopoulo, A.C., see Amarger	50 (1991) 462
fused quartz by photo-CVD	41/42 (1989) 633	Paprocki, K., see Tatarkiewicz	50 (1991) 249
Oliver, A., see Rickards	45 (1990) 155	Pardo, B., see Gendry	44 (1990) 309
Omling, P., see Meyer	50 (1991) 420	Paredes, A., see Müller	46 (1990) 143
Ono, S., see Hariu	48/49 (1991) 204	Parisini, A., see Baraldi	50 (1991) 405
Onozawa, S., see Horikawa	41/42 (1989) 598	Park, C.H., see Deneuville	50 (1991) 308
Onuma, Y., see Kamimura	41/42 (1989) 443	Park, R.M., see Deneuville	50 (1991) 285
Oral, B., Y.C. Lee and R.W. Vook, Ther-		Parkhutik, V.P., see Gómez-Rodríguez	44 (1990) 185
mal desorption spectroscopy investi-		Parks, C.C., see Murakami	41/42 (1989) 195
gation of CO adsorption on Cu/	V. 11222	Parrott, M.J., see Pemble	46 (1990) 32
Pd(111) surfaces	44 (1990) 65	Pashunin, Yu.M., see Pertsin	44 (1990) 171
Oral, B., see Vook	48/49 (1991) 125	Pashunin, Yu.M., see Pertsin	47 (1991) 115
Orlowski, B.A., J.P. Lacharme, C.A.		Patel, P. and I.W. Boyd, Low temperature	
Sébenne and S. Bensalah, Interface		VUV enhanced growth of thin silicon	46 (1000) 252
formation on n- and p-CdTe(110) sur- faces with Cu and Au	41 /42 /1090) 401	dioxide films	46 (1990) 352
	41/42 (1989) 491 41/42 (1989) 647	Patton, G.L., see Arienzo	48/49 (1991) 377 46 (1990) 378
Oshima, M., see Yamada Maruo Ospelt, M., see Mendik	50 (1991) 303	Pattyn, H., see Elliq Paulmier, D., see Zaïdi	44 (1990) 221
Ossart, P. and E.V.K. Rao, Investigation	30 (1991) 303	Pavuna, D., see James	43 (1989) 393
of surface and sub-surface defects on		Peaker, A.R., see Rimmer	50 (1991) 149
polished InP substrates using Auger		Pelletier, J.M., see Gaffet	43 (1989) 248
electron spectroscopy coupled to argon		Pemberton, J.E., see Ingram	44 (1990) 279
ion sputtering	50 (1991) 125	Pemberton, J.E., see Ingram	44 (1990) 293
Otamiri, J.C., see Andersson	45 (1990) 1	Pemberton, J.E., see Ingram	45 (1990) 247
Oudar, J., see Vassilakis	47 (1991) 273	Pemberton, J.E., see Ingram	45 (1990) 278
Ouennoughi, Z., see Easwarakhanthan	47 (1991) 299	Pemble, M.E., J.T. Allen, D.S. Buhaenko,	,
Oura, K., see Sumitomo	41/42 (1989) 112	S.M. Francis, P.A. Goulding, J. Lee	
Oura, K., see Katayama	48/49 (1991) 361	and M.J. Parrott, The adsorption of	
Oura, K., see Shoji	48/49 (1991) 373	triethylgallium on GaAs(100) at 300	
Ourmazd, A., P.H. Fuoss, J. Bevk and		K: adsorption kinetics from optical	
J.F. Morar, The Si(001)/SiO <sub>2</sub> inter-		second harmonic generation transients	46 (1990) 32
face	41/42 (1989) 365	Peng, X.D. and M.A. Barteau, Characteri-	
Outlaw, R.A., see Lee	47 (1991) 91	zation of the crystallographic structure	
Oyanagi, H., see Kawadzu	41/42 (1989) 296	of MgO thin films by ISS on the basis	
Ozawa, S., see Sasajima	48/49 (1991) 498	of trajectory-dependent neutralization	44 (1990) 87
Ozawa, S., see Takeuchi	48/49 (1991) 526	Pennemann, B., see Kalki	48/49 (1991) 59
		Pennycook, S.J., see Withrow	43 (1989) 191
Paál, Z., see Muhler	47 (1991) 281	Peray, M., see Marine	43 (1989) 377
Paget, D., HJ. Drouhin and J. Peretti,		Pereira, E., see Monteiro	50 (1991) 253
Infrared field assisted photoemission	41 (42 (1000) 20	Peretti, J., see Paget	41/42 (1989) 38
of metal-semiconductor structures	41/42 (1989) 38	Perez, A., see Massouras	43 (1989) 213
Paidar, V., see Lejček	44 (1990) 75 43 (1989) 377	Pérez-Amor, M., see Garrido	43 (1989) 68
Pailharey, D., see Marine Pain, G.N., T. Warminski, S. Sulcs, M.S.	43 (1989) 377	Pérez-Amor, M., see Szörényi Pérez-Amor, M., see León	46 (1990) 206 46 (1990) 210
Kwietniak, D. Gao, S.R. Glanvill, C.J.		Perrin, J., see Petitjean	46 (1990) 189
- C.J. Oldivill, C.J.		zorini, s., see retigean	40 (1770) 109

Perrossier, J.L., see Tardy Perry, E.M., D.L. Cocke and M.K. Miller,	50 (1991) 383	Pitt, A.D., see Lee Pleiter, F., see Magerle	50 (1991) 428 50 (1991) 159
The oxidation of Ni <sub>3</sub> Zr investigated		Ploog, K., see López	41/42 (1989) 464
by atom-probe field-ion microscopy		Plummer, E.W., see Heskett	48/49 (1991) 260
and X-ray photoelectron spectroscopy	44 (1990) 321	Pocci, D., see Nipoti	50 (1991) 410
Persch, G., see Strecker	46 (1990) 441	Podolsky, B.S., see Ukraintsev	48/49 (1991) 151
Pertsin, A.J. and Yu.M. Pashunin, Dif-	(	Podolsky, B.S., see Ukraintsev	48/49 (1991) 198
ferential charging in XPS studies of		Pokhmurskaja, A.V., see Prokhorov	43 (1989) 340
polymer/metal interfaces	44 (1990) 171	Polla-Mattiot, F., see Teghil	46 (1990) 220
Pertsin, A.J. and Yu.M. Pashunin, An		Polman, A., see Sinke	43 (1989) 128
XPS study of the in-situ formation of		Pomot, C., see Raynaud	46 (1990) 435
the polyimide/copper interface	47 (1991) 115	Ponce, F.A., see Epler	43 (1989) 432
Peruchetti, J.C., see Haderbache	41/42 (1989) 257	Posselt, M., see Neelmeijer	43 (1989) 232
Petit, E.J., J. Riga, R. Caudano and J.	, , , , ,	Post, G., see Tardy	50 (1991) 383
Verbist, Ultraviolet laser-induced oxi-		Poston, J.A., see Siriwardane	45 (1990) 131
dation of antimony: chemical com-		Potměšilová, A., see Lejček	44 (1990) 75
position and growth kinetics of the		Pou, J., see Szörényi	46 (1990) 206
oxide layer	43 (1989) 285	Poudoulec, A., see Auvray	50 (1991) 109
Petit, E.J. and R. Caudano, Chemical re-		Prabhakara Rao, G., see Bharathi	47 (1991) 293
actions at solid-solid interfaces in-		Prabhakaran, K. and C.N.R. Rao, Ad-	
duced by pulsed laser annealing	46 (1990) 357	sorption of carbonyl compounds on	
Petitjean, M., N. Proust, JF. Chapeaub-	, ,	clean and modified Cu(110) surfaces:	
lanc and J. Perrin, SiO <sub>2</sub> deposition by		a combined EELS-UPS study	44 (1990) 205
direct photolysis at 185 nm of N <sub>2</sub> O		Pradier, CM., see Vassilakis	47 (1991) 273
and SiH <sub>4</sub>	46 (1990) 189	Prescha, Th., see Leitch	50 (1991) 390
Petzold, HC., see Putzar	46 (1990) 131	Prévot, B., see Elliq	46 (1990) 378
Pfeiffer, W., M. Deicher, R. Keller, R.		Prévot, B., see Boudart	50 (1991) 295
Magerle, P. Pross, H. Skudlik, Th.		Price, W.H., see Murakami	41/42 (1989) 195
Wichert, H. Wolf, D. Forkel, N.		Prietsch, M., see Heskett	48/49 (1991) 260
Moriya and R. Kalish, Characteriza-		Priggemeyer, S., A. Brockmeyer, H.	
tion of Cd implanted and annealed		Dötsch, H. Koschmieder, D.J. O'Con-	
GaAs and InP by perturbed angular		nor and W. Heiland, The segregation	
correlation (PAC) spectroscopy	50 (1991) 154	of Pb on yttrium-iron-garnet (YIG)	
Pfeiffer, W., see Magerle	50 (1991) 159	surfaces studied by ion scattering	
Piccirillo, S., see Fantoni	43 (1989) 308	spectrometry (ISS)	44 (1990) 255
Piccirillo, S., see Teghil	46 (1990) 220	Prince, R.H., see Bourdon	48/49 (1991) 50
Pickart, S.J., M.L. Crow, A.C. Nunes, T.R.		Priolo, F., A. La Ferla, C. Spinella, E.	
McGuire and A. Gupta, Neutron de-		Rimini, S.U. Campisano and G. Ferla,	
polarization study of a high-T <sub>c</sub> epi-		Crystal-amorphous-silicon interface	
taxial thin film	48/49 (1991) 436	kinetics under ion beam irradiation	41/42 (1989) 619
Pickering, C., N.S. Garawal, D. Lance-		Priolo, F., C. Spinella, A. La Ferla, E.	
field, J.P. Piel and R. Blunt, Non-de-		Rimini and G. Ferla, Ion-assisted re-	
structive characterisation of (Ga,In,		crystallization of amorphous silicon	43 (1989) 178
Al,As,P)-based ternary multilayer		Proctor, A., see Baltrus	44 (1990) 147
structures using spectroscopic el-		Prokhorov, A.M., A.Yu. Bonchik, S.G.	
lipsometry	50 (1991) 346	Kiyak, A.A. Manenkov, G.N. Mik-	
Piecuch, M., see Dupuis	46 (1990) 398	hailova, A.V. Pokhmurskaja, A.S.	
Piel, J.P., see Pickering	50 (1991) 346	Seferov, I. Ursu, V. Craciun and I.N.	
Pielmeier, R., D. Bollmann and K. Ha-		Mihailescu, Laser solid-phase doping	40 (1000) 040
berger, Laser evaporation of metal		of semiconductors	43 (1989) 340
sandwich layers for improved IC	46 (1000) 163	Pross, P., see Pfeiffer	50 (1991) 154
metallization	46 (1990) 163	Proust, N., see Petitjean	46 (1990) 189
Pierrisnard, R., see Marfaing	43 (1989) 165	Ptáček, P. and Z. Bastl, XPS characteriza-	
Pinard, P., see M'Ghaieth	43 (1989) 111	tion of supported bimetallic pal-	AE (1000) 210
Pireaux, J.J., see Heens	47 (1991) 163	ladium-silver clusters	45 (1990) 319
Pirri, C., see Haderbache	41/42 (1989) 257	Puik, E.J., M.J. van der Wiel, H. Zeijle-	
Pitaval, M., see Boelle	46 (1990) 200	maker and J. Verhoeven, Ion etching	

		form and the later to the constant	
of thin W layers: enhanced reflectivity	47 (1991) 63	surfaces studied by in-situ spectro- scopic ellipsometry	46 (1990) 435
of W-C multilayer coatings Puik, E.J., M.J. van der Wiel, H. Zeijle-	47 (1991) 03	Razykov, T.M., Chemical molecular beam	40 (1990) 43.
maker and J. Verhoeven, Ion bom-		deposition of II–VI binary and ternary	
bardment of X-ray multilayer coat-		compound films in a gas flow	48/49 (1991) 89
ings: comparison of ion etching and		Rebouillat, J.P., see Dupendant	43 (1989) 369
ion assisted deposition	47 (1991) 251	Recknagel, E., see Jahn	50 (1991) 169
Putzar, R., HC. Petzold and H. Staiger,	(2272) 222	Regreny, A., see Auvray	50 (1991) 109
Optimization of the laser-induced de-		Reichardt, H., see Richter	44 (1990) 127
position technique for its application		Reitano, R., see Compagnini	43 (1989) 228
in X-ray mask repair	46 (1990) 131	Reithmaier, JP., see Zaus	50 (1991) 92
Pyatkova, T.M., see Tokarev	44 (1990) 235	Ren, D.G., Study of interface structure of	
		the oxide grown on nickel alloys by	
		AP-FIM	48/49 (1991) 227
Qian, Y.J., see Qiu	48/49 (1991) 430	Renard, D., see Gao	50 (1991) 131
Qiu, J.W., L.W. Zhou, X.F. Zhang, Z.M.		Renard, M., see Easwarakhanthan	47 (1991) 299
Tang, Y.J. Qian and Z.Y. Hua, A		Renda, M. and K. Morita, Epitaxial	
high- $T_c$ SQUID for measuring sus-		growth of a mono-crystalline metasta-	
ceptibility of high- $T_c$ superconductive		ble AuIn layer at the Au/InP(001)	
thin films	48/49 (1991) 430	interface	41/42 (1989) 216
Qu, H., see Morar	41/42 (1989) 312	Resch, U., see Esser	41/42 (1989) 169
Quadakkers, W.J., J. Jedlinski, K.		Rhead, G.E., On the work function varia-	
Schmidt, M. Krašovec, G. Borchardt		tions produced by the oxidation of	47 (1001) 25
and H. Nickel, The effect of im-		adsorbed alkali metal layers	47 (1991) 35
planted yttrium on the growth and		Richardson, A.G., see Khan	47 (1991) 355
adherence of alumina scales on Fe-	47 (1001) 261	Richardson, N.V., see Jones	45 (1990) 85 48/49 (1991) 555
20Cr–5Al	47 (1991) 261 48/49 (1991) 319	Richman, M.H., see Bhardwaj	43 (1989) 232
Quinn, J.J., see Vecris	40/49 (1991) 319	Richter, E., see Neelmeijer Richter, F., E. Bugiel, R. Grötzschel, H.	43 (1909) 232
		Reichardt, A. Schöpke, E. Wieser and	
Raas, M.C., see Sondag	47 (1991) 205	F. Wolf, Formation of titanium dis-	
Raddatz, KD., see Hütten	46 (1990) 306	ilicide using different annealing meth-	
Radhakrishnan, G., W. Stenzel, H. Con-	10 (1570) 500	ods	44 (1990) 127
rad and A.M. Bradshaw, Photoreac-		Richter, W., see Esser	41/42 (1989) 169
tions of adsorbed CH <sub>3</sub> Br on Pt(111)	46 (1990) 36	Richter, W., see Zahn	41/42 (1989) 179
Rai-Choudhury, P., see Karulkar	48/49 (1991) 237	Richter, W., see Zahn	41/42 (1989) 497
Raisin, C., A. Rocher, G. Landa, R. Carles		Rickards, J., A. Oliver, J. Miranda and	
and L. Lassabatere, GaSb/GaAs het-		E.P. Zironi, Uses of PIXE at low pro-	
eroepitaxy characterized as a stress-		ton energies	45 (1990) 155
free system	50 (1991) 434	Riechert, H., see Strasser	50 (1991) 261
Raley, N.F., see Bernhardt	46 (1990) 121	Riga, J., see Petit	43 (1989) 285
Ramaker, D.E., Evidence for vertical C <sub>2</sub>		Rimini, E., see Priolo	41/42 (1989) 619
on Ni as a precursor for graphite		Rimini, E., see Priolo	43 (1989) 178
nucleation	48/49 (1991) 351	Rimmer, J.S., M. Missous and A.R.	
Randzio, S.L., see Zommer	45 (1990) 93	Peaker, A new, fast method for the	
Ranga Rao, G. and C.N.R. Rao, Adsorp-		computer simulation of CV profiles in	50 (1004) 1 10
tion of nitrogen on clean and modified	45 (4000) 55	multilayer structures	50 (1991) 149
single-crystal Ni surfaces	45 (1990) 65	Roberts, L., see O'Connor	50 (1991) 312
Rantala, T.T., see Milne	43 (1989) 81	Roberts, L. and G. Hughes, An investiga-	
Rao, C.N.R., see Prabhakaran	44 (1990) 205	tion of metal/GaAs(100) interfaces by	50 (1001) 424
Rao, C.N.R., see Ranga Rao	45 (1990) 65 50 (1991) 125	deep level transient spectroscopy	50 (1991) 424
Rao, E.V.K., see Ossart Rassadin, L.A., see Kudoyarova	50 (1991) 125	Robertson, P.A. see Browne	47 (1991) 375 43 (1989) 277
Ravet, M.F., see Dupuis	50 (1991) 173 46 (1990) 398	Robertson, P.A., see Milne Robins, J.L., see Gates	48/49 (1991) 154
Raychaudhuri, A., see Kar	48/49 (1991) 264	Rocher, A., see Raisin	50 (1991) 434
Raynaud, P., J.P. Booth and C. Pomot,	10/ 47 (1771) 204	Rochet, F., see Roulet	47 (1991) 173
Hydrogen plasma treatment of silicon		Rockett, A., see Nelson	48/49 (1991) 419
Jacoban planting troublett of sincon		rockett, 11., 500 Heison	.0/ 1/ (1//1) 41/

Rodway, D.C., see Mackey	43 (1989) 1	Salvan, F., F. Thibaudau and Ph. Dumas,	
Rogalla, H., see Gao	46 (1990) 74	STM studies of metal-semiconductor	
Rogalla, H., see Aarnink	47 (1991) 195	interface formation	41/42 (1989) 88
Roger, J.A., see Massouras	43 (1989) 213	Salvi, A.M., see Giardini-Guidoni	46 (1990) 321
Roger, J.A., see Boelle	46 (1990) 200	Salvi, M., see L'Haridon	50 (1991) 237
Rogers, Jr., J.W., see Kelber	44 (1990) 193	Samimi, M., see Hage-Ali	50 (1991) 377
Romana, L., see Massouras	43 (1989) 213	Saminadayar, K., see Tatarenko	41/42 (1989) 470
Rong, Z., see Schuessler	48/49 (1991) 254	Samria, N.K., see Sil	45 (1990) 229
Rong, Z., see Benck	48/49 (1991) 257	Samuelson, L., see Gustafsson	50 (1991) 186
Roorda, S., see Sinke	43 (1989) 128	Sánchez, C., see De las Heras	50 (1991) 505
Roosenbrand, A.G., M.W.C. van Beck-	(/	Sánchez-Dehesa, J., see López	41/42 (1989) 464
hoven and H.H. Brongersma, Surface		Šantić, B., see Desnica	50 (1991) 269
topography of pyrolytic graphite	44 (1990) 121	Santinelli, C., see Tardy	50 (1991) 383
Rose, B., see Gao	50 (1991) 131	Sapieha, S., M. Verreault, J.E. Klemberg-	
Rosenfeld, A., see Treverton	45 (1990) 263	Sapieha, E. Sacher and M.R. Wert-	
Rossouw, C.J., see Pain	48/49 (1991) 76	heimer, X-ray photoelectron study of	
Rou, S.H., see Krauss	46 (1990) 67	the plasma fluorination of lignocellu-	
Roulet, H., G. Dufour, A. Cheenne, F.	(2770)	lose	44 (1990) 165
Rochet and C. Cartier, Physicoche-		Sartorius, B., M. Brandstättner and H.	(=,, =,
mistry of laser-deposited BiSrCaCuO		Venghaus, Two-wavelength transmis-	
thin films studied by XPS and XAS	47 (1991) 173	sion: a rapid and precise method for	
Roura, P., J.R. Morante, G. Bremond, T.	17 (1771) 173	measuring the light absorption in	
Benyattou, G. Guillot and W. Ulrici,		semiconductors	50 (1991) 369
Complete identification of the Ti-re-		Sasajima, Y., Y. Suzuki, M. Takeuchi and	20 (1)/1) 20/
lated levels in GaP	50 (1991) 496	S. Ozawa, New approach for a com-	
Roux, B., see Chevarier	48/49 (1991) 215	puter simulation of the vacuum de-	
Roux, J.P., see Van Staden	44 (1990) 259	position process	48/49 (1991) 498
Roux, J.P., see Van Staden	44 (1990) 263	Sasaki, M., Y. Kawakyu, H. Ishikawa and	10/ 17 (1771) 170
Roux, J.P., see Van Staden	44 (1990) 271	M. Mashita, UV absorption spectra of	
Rowe, R.S., see Pain	48/49 (1991) 76	adlayers of MOCVD source gases	41/42 (1989) 342
Russo, S.P., see Pain	48/49 (1991) 76	Sasaki, T., T. Matsuoka and A. Katsui,	41/ 42 (1707) 542
Russo, S.I., see I am	40/47 (1991) 70	MOVPE-grown GaN on polar planes	
		of 6H-SiC	41/42 (1989) 504
Saba, F., see Sajjadi	46 (1990) 84	Sasaki, Y.C. and K. Hirokawa, New tech-	41/ 42 (1909) 304
Sacher, E., see Sapieha	44 (1990) 165	nique for evaluation of surfaces and	
Sacilotti, M.A., see Morais	44 (1990) 161	interfaces at atmospheric pressure by	
Sai, K., see Mimura	48/49 (1991) 521	using refracted X-ray fluorescence	
Saiki, K., see Koma	41/42 (1989) 451	(RXF)	47 (1991) 371
Saiki, K., see Lee	41/42 (1989) 553	Sato, N., see Kumomi	41/42 (1989) 638
Saitch, M., see Gekka	41/42 (1989) 184	Sato, T., see Kusunoki	45 (1990) 171
Saitoh, T., H. Hasegawa, S. Konishi and	41/42 (1909) 104	Sato, Y., see Koma	41/42 (1989) 451
H. Ohno, A computer simulation of		Satou, M., see Ito	41/42 (1989) 301
the recombination process at com-		Scaglione, S., D. Flori and G. Emiliani,	11/ 12 (1707) 301
pound semiconductor surfaces and		Modification of mechanical properties	
hetero-interfaces	41/42 (1989) 402	of e-gun evaporated MgF <sub>2</sub> and CaF <sub>2</sub>	
Sajjadi, A., K. Kuen-Lau, F. Saba, F.	41/42 (1707) 402	thin films under ion beam bombard-	
Beech and I.W. Boyd, Laser-ablation		ment	43 (1989) 224
deposition of uniform thin films of		Scaglione, S., see Lascovich	47 (1991) 17
Bi <sub>2</sub> Sr <sub>2</sub> CaCu <sub>2</sub> O <sub>x</sub>	46 (1990) 84	Schäffler, F., see Holländer	50 (1991) 450
Sakamoto, K., see Okumura	41/42 (1989) 548	Schelz, S., J. Eitle, R. Steiner and P.	30 (1))1) 130
Sakamoto, T., see Kono	41/42 (1989) 75	Oelhafen, In situ electron spectrosco-	
Sakamoto, T., see Hayashi	41/42 (1989) 534	py on polymeric films prepared by RF	
Sakamoto, T., see Okumura	41/42 (1989) 548	plasma polymerization: styrene and	
Sakashita, M., see Yasuda	41/42 (1989) 420	hydrogen/styrene gas mixtures as pro-	
Sakaue, H., see Horiike	46 (1990) 168	cess gases	48/49 (1991) 301
Sakurai, T., see Hashizume	48/49 (1991) 119	Scherzer, B.M.U., see Schwarz	50 (1991) 456
Sakuta, M., see Hasinzume Sakuta, M., see Horikawa	41/42 (1989) 598	Schlögl, R., see Muhler	47 (1991) 281
Sakuta, W., See Hollkawa	71/72 (1909) 370	bomogi, ic., see Munici	17 (1771) 201

Schmaderer, F., R. Huber, H. Oetzmann		induced by excimer laser irradiation in	
and G. Wahl, High-T <sub>c</sub> YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-8</sub>		Ge-Sb thin film bilayers	46 (1990) 405
prepared by chemical vapour deposi-		Serrari, A., see Chartier	45 (1990) 351
tion	46 (1990) 53	Servidori, M., see Nipoti	43 (1989) 321
Schmaus, D., see Abel	44 (1990) 17	Sexton, B.A., see Bartlett	47 (1991) 187
Schmidt, C., see Nowak	43 (1989) 11	Sham, T.K., see Shek	48/49 (1991) 332
Schmidt, C., see Braun	43 (1989) 352	Shapoval, S.Yu., O.E. Balvinskii, I.V.	10/ 12 (1221) 002
Schmidt, C., see Hesch	46 (1990) 233	Malikov, A.A. Chumakov and L.A.	
Schmidt, K., see Quadakkers	47 (1991) 261	Niselson, Chemical vapour deposition	
Schmitt, J.J., see Halpern	48/49 (1991) 19	of tungsten layers at low substrate	
Schmitz, R.W.A.H., see Claassen	43 (1989) 292	temperatures	45 (1990) 257
Schollmeyer, E., see Kesting	46 (1990) 326	Sharma, M.K., see Hütten	46 (1990) 306
Schöpke, A., see Richter	44 (1990) 127	Shastry, H., see Kim	48/49 (1991) 548
Schreiber, J., W. Hergert and S. Hilde-	(1>>0) 12/	Shaw, D., see Hogg	50 (1991) 87
brandt, Combined application of		Shek, M.L., T.K. Sham, J. Hrbek and	30 (1771) 67
SEM-CL and SEM-EBIC for the in-		GQ. Xu, A soft X-ray study of a	
vestigation of compound semiconduc-		Li-S surface compound	48/49 (1991) 332
tors	50 (1991) 181	Shen, Y., see King	48/49 (1991) 246
Schrey, F., see Tung	41/42 (1989) 223	Shen Yueqiang, see Vase	46 (1990) 61
Schröder, U., see Kalki	48/49 (1991) 59	Shigesato, Y., S. Takaki and T. Haranou,	40 (1990) 01
Schuessler, H.A., S.H. Chen, Z.C. Tang	40/49 (1991) 39	Crystallinity and electrical properties	
and Z. Rong, Cavity-enhanced photo-		of tin-doped indium oxide films de-	
thermal spectroscopy and detection	48/49 (1991) 254	posited by DC magnetron sputtering	49 /40 (1001) 260
	48/49 (1991) 257	Shih, YC., see Murakami	48/49 (1991) 269
Schuler S. and Müller	,	Shiloh, M., see Brown	41/42 (1989) 195
Schuler, S., see Müller	46 (1990) 143		43 (1989) 382
Schuster, M., see Zaus	50 (1991) 92	Shimaoka, G., see Nakanishi	48/49 (1991) 55
Schwab, C., see Benchiguer	50 (1991) 277	Shimaoka, G., MEED studies of thin	
Schwarz R. T. Fischer R. Hancock T.	50 (1991) 295	metal film covered semiconductor sur-	40 (40 (1001) 100
Schwarz, R., T. Fischer, P. Hanesch, T.		faces	48/49 (1991) 190
Muschik, J. Kolodzey, H. Cerva, H.L.		Shimaoka, G., see Nakanishi	48/49 (1991) 297
Meyerheim and B.M.U. Scherzer,		Shiozawa, J., see Nadahara	41/42 (1989) 425
Limitations of interface sharpness in	EO (1001) 4E(	Shiraishi, W., see Wadayama	44 (1990) 43
a-Si:H/a-SiC:H multilayers	50 (1991) 456	Shoji, F., see Sumitomo	41/42 (1989) 112
Scott, C.G., see Ashenford	50 (1991) 440	Shoji, F., see Katayama	48/49 (1991) 361
Scotto D'Aniello, J.M., see Marine	46 (1990) 239	Shoji, F., A. Ogawa and K. Oura,	
Sébenne, C.A., J.P. Lacharme, I. Andria-		Sputter-deposition by a new Penning-	
manantenasoa and M. Khial, Local		discharge source with an axially in-	40 /40 /4004> 450
roughness and surface states on		tegrated hot-cathode	48/49 (1991) 373
Si(001): analysis of vacuum anneal-		Siffert, P., see Boch	43 (1989) 17
ings and oxygen adsorption-desorp-	41 (40 (1000) 050	Siffert, P., see Fogarassy	43 (1989) 316
tion processes	41/42 (1989) 352	Siffert, P., see Foulon	43 (1989) 333
Sébenne, C.A., see Orlowski	41/42 (1989) 491	Siffert, P., see Hartiti	46 (1990) 371
Seferov, A.S., see Prokhorov	43 (1989) 340	Siffert, P., see Chibani	50 (1991) 177
Segond, O., see Huong	43 (1989) 256	Siffert, P., see Hage-Ali	50 (1991) 377
Séguelong, T., see Barrière	41/42 (1989) 383	Sigmon, T.W., see Carey	43 (1989) 325
Segura, A., see Mari	50 (1991) 415	Sigmund, H., see Klumpp	43 (1989) 301
Seidel, A. and G. Linker, Amorphization		Sigmund, H., see León	46 (1990) 210
mechanisms in Mn <sup>+</sup> -implanted thin Al		Sil, A., N.K. Samria and D.S. Venkates-	
films and single crystals	43 (1989) 97	warlu, Thermal analysis of a cathode:	
Seidl, A., see Hu	46 (1990) 388	temperature distribution and warm-up	
Seidl, A., see Mosel	50 (1991) 364	time	45 (1990) 229
Senillou, C., see Eymery	47 (1991) 127	Silberman, J.A., see Haight	41/42 (1989) 487
Sepold, G., see Breuer	46 (1990) 336	Simpson, J. and J.O. Williams, Prefer-	
Serna, R., see Afonso	46 (1990) 249	ential (111) orientation of ZnSe on	
Serna, R., C.N. Afonso, F. Catalina, N.		(100) GaAs deposited by laser-in-	
Teixeira, M.F. da Silva and J.C.		duced MOCVD	46 (1990) 27
Soares, Diffusion and microstructures		Sinha, A.K., see Kar	48/49 (1991) 264

Sinke, W.C., A. Polman, S. Roorda and		Snorken D. D.A. Thirty D. Vhonnoux D.	
P.A. Stolk, Explosive crystallization of		Sporken, R., P.A. Thiry, P. Xhonneux, R. Caudano and J.P. Delrue, Spectro-	
amorphous silicon: triggering and		scopic study of metal/semimetal and	
propagation	43 (1989) 128	metal/semiconductor interfaces	41/42 (1989) 201
Sinke, W.C., see Van Maaren	46 (1990) 138	Stafast, H., see Golusda	46 (1990) 230
Siriwardane, R.V. and J.A. Poston, Inter-	40 (1770) 130	Stahmer, KW., see Heidberg	46 (1990) 44
action of H <sub>2</sub> S with zinc titanate in the		Staiger, H., see Putzar	46 (1990) 131
presence of H <sub>2</sub> and CO	45 (1990) 131	Stanley, R.P., see Donegan	50 (1991) 321
Skorupa, W., see Voelskow	43 (1989) 196	Starnberg, H.I., see Soukiassian	41/42 (1989) 395
Skudlik, H., see Pfeiffer	50 (1991) 154	Staudte, D.M., see Hogg	50 (1991) 87
Skudlik, H., see Magerle	50 (1991) 159	Steiner, R., see Schelz	48/49 (1991) 301
Slaoui, A., see Foulon	43 (1989) 333	Steinfeld, J.I., see Xu	45 (1990) 281
Slaoui, A., see Fogarassy	46 (1990) 195	Stenzel, W., see Radhakrishnan	46 (1990) 36
Slaoui, A., see Hartiti	46 (1990) 371	Stephens, C., see Zahn	41/42 (1989) 179
Slijkerman, W.F.J., see Fischer	44 (1990) 115	Stern, M., see Chevarier	48/49 (1991) 215
Smith, D.D., see Moss	50 (1991) 337	Stevenson, A.W., see Pain	48/49 (1991) 76
Smith, G.W., see Lee	50 (1991) 428	Stibal, R., see Jantz	50 (1991) 480
Smith, K.E., G.S. Elliott and S.D. Kevan,	30 (1991) 428	Stirland, D.J., see Brozel	50 (1991) 475
The role of non-adiabaticity and two-		Stock, G., D. Bollmann, R. Buchner, G.	30 (1991) 473
dimensional Fermi surfaces in the re-		Neumayer and K. Haberger, Ultra-flat	
construction of Mo(001) and W(001)	48/49 (1991) 135	p-n junctions formed by solid source	
Smith, P.C., see Mackey	43 (1989) 1	laser doping	46 (1990) 348
Snels, M., see Giardini-Guidoni	46 (1990) 321	Stolk, P.A., see Sinke	43 (1989) 128
Soares, J.C., see Serna	46 (1990) 405	Stolwijk, N.A., see Hettwer	50 (1991) 470
Soave, R.J., see Fijol	48/49 (1991) 464	Stolz, M., see Woratschek	43 (1989) 264
Sobiesierski, Z., see Williams	41/42 (1989) 189	Stoquert, J.P., see Fogarassy	46 (1990) 195
Soble, C.S., see Krauss	46 (1990) 67	Stoquert, J.P., see Flagarassy Stoquert, J.P., see Elliq	46 (1990) 378
Solis, J., see Afonso	43 (1989) 171	Stoquert, J.P., see Eniq Stoquert, J.P., see Marfaing	46 (1990) 422
Solis, J., See Alonso and F. Catalina,	43 (1909) 171	Stoquert, J.P., see Marraing Stoquert, J.P., see Chibani	50 (1991) 177
The influence of the substrate on the		Stork, J.M.C., see Arienzo	48/49 (1991) 377
transformations induced in Si by		Stradling, R.A., Far-infrared spectroscopy	40/49 (1991) 377
nanosecond laser irradiation: a time-		of impurities in semiconductors	50 (1991) 65
resolved study	46 (1990) 383		46 (1990) 446
Somorjai, G.A., see Fu	48/49 (1991) 93	Strahnen, M., see Esser Strahnen, M., see Kütt	50 (1991) 325
Sondag, A.H.M., M.C. Raas and F.J.	40/49 (1991) 93		43 (1989) 398
Touwslager, A comparison between		Stranges, D., see Mele	43 (1909) 390
inelastic electron tunnelling and in-		Strasser, G., S. Dubois, M. Besson, E. Gornik, G. Weimann, E. Bauser and	
frared reflection-absorption spectros-		H. Riechert, Analysis of impurity dis-	
copy for vibrational surface analysis	47 (1991) 205	tribution in n-GaAs layers by photo-	
Souche, Y., see Dupendant	43 (1989) 369		
Soukiassian, P., H.I. Starnberg and T.	43 (1969) 309	conductivity and cyclotron resonance	50 (1991) 261
Kendelewicz, Insulator–semiconduc-		Stratmann M. see Wolpers	45 (1990) 167
		Stratmann, M., see Wolpers	47 (1991) 49
tor interface formation by electronic promotion using alkali metal and re-		Stratmann, M., see Wolpers Strecker, H. and G. Persch, Scanning tun-	47 (1991) 49
moval of the catalyst	41/42 (1989) 395	neling microscopy and technical appli-	
•	41/42 (1989) 169	cations	46 (1990) 441
Spaltmann, D., see Esser	41/42 (1909) 109		50 (1991) 450
Spicer, W.E., R. Cao, K. Miyano, T.		Stritzker, B., see Holländer	30 (1991) 430
Kendelewicz, I. Lindau, E. Weber, Z. Liliental-Weber and N. Newman,		Strohmeier, B.R., Evaluation of polymeric standard reference materials for moni-	
From synchrotron radiation to $I-V$		toring the performance of X-ray pho-	47 (1001) 225
measurements of GaAs Schottky bar-	41 /42 (1090) 1	toelectron spectrometers	47 (1991) 225 46 (1990) 153
rier formation	41/42 (1989) 1	Stuke, M., see Zhang	46 (1990) 153
Spinella, C., see Priolo	41/42 (1989) 619	Stutzmann, M., see Leitch	50 (1991) 390
Spinella, C., see Priolo	43 (1989) 178	Suëtaka, W., see Wadayama	44 (1990) 43 48/49 (1991) 222
Spinella, C., S. Lombardo and S.U.		Suëtaka, W., see Hatta	, , ,
Campisano, Amorphous to polycrystal		Suëtaka, W., see Wadayama	48/49 (1991) 409
transition in ion irradiated chemical	42 (1000) 107	Sugahara, H. and J. Nagano, Thermal	
vapor deposited amorphous silicon	43 (1989) 187		

stability of WSiN-GaAs and Au-		toelectrochemical cells	48/49 (1991) 517
WSiN interfaces	41/42 (1989) 207	Takeuchi, M., Y. Watanabe and S. Ozawa,	, (,
Sugi, T., see Aoyama	41/42 (1989) 584	Gas-sensitive properties of ultrafine	
Suguro, K., Y. Nakasaki, T. Yoshii and T.		In 2O3 particle layers prepared by gas	
Itoh, Barrier metal between tungsten		evaporation technique	48/49 (1991) 526
and silicon for high temperature		Takeuchi, T., C. Maezawa, T. Nomura, K.	
processing	41/42 (1989) 277	Ishikawa, M. Miyao and M. Hagino,	
Suguro, K., see Nadahara	41/42 (1989) 425	Raman study of strain distribution in	
Suhren, M., see Heidberg	46 (1990) 44	interface region of GaAs/GaP hetero-	
Sukegawa, T., see Kimura	48/49 (1991) 185	epitaxial layers grown by MBE	41/42 (1989) 530
Sulcs, S., see Pain	48/49 (1991) 76	Takeuchi, Y., see Nakamura	48/49 (1991) 478
Sumi, H., see Nishimori	47 (1991) 365	Taleb-Ibrahimi, A., see Ludeke	41/42 (1989) 151
Sumitomo, K., K. Tanaka, Y. Izawa, I.		Tamon, T., see Nishimori	48/49 (1991) 450
Katayama, F. Shoji, K. Oura and T.		Tanaka, A., see Kimura	48/49 (1991) 185
Hanawa, Structural study of Ag over-		Tanaka, H., see Hariu	48/49 (1991) 204
layers deposited on a Si(111) substrate		Tanaka, K., see Sumitomo	41/42 (1989) 112
by impact-collision ion-scattering-		Tanaka, K., see Kuniyoshi Tanbo, T., see Tatsuyama	43 (1989) 447 41/42 (1989) 539
spectroscopy with time-of-flight detec- tion	41 /42 (1080) 112	Tang, D., see Heskett	48/49 (1991) 260
Sunada, J., see Oishi	41/42 (1989) 112 48/49 (1991) 276	Tang, M., see Niles	41/42 (1989) 139
Süssbauer, M., see Eleftheriadis	46 (1990) 284	Tang, Z.C., see Schuessler	48/49 (1991) 254
Suzuki, JI., see Ma	41/42 (1989) 572	Tang, Z.M., see Qiu	48/49 (1991) 430
Suzuki, S. and M. Oku, Surface orienta-	41/42 (1707) 372	Tanishiro, Y., see Takayanagi	41/42 (1989) 337
tion dependence of the surface com-		Tanner, D.B., see Deneuville	50 (1991) 285
position in an Fe-20%Cr alloy and an		Tardy, J., I. Thomas, P. Viktorovitch, M.	(2,, 2)
Fe-3%Si alloy treated by mechanical		Gendry, J.L. Perrossier, C. Santinelli,	
polishing and chemical etching	44 (1990) 151	M.P. Besland, P. Louis and G. Post,	
Suzuki, T., see Iizuka	41/42 (1989) 587	Long-term stability of InP MIS de-	
Suzuki, T., see Oishi	48/49 (1991) 276	vices	50 (1991) 383
Suzuki, Y., see Nakanishi	48/49 (1991) 55	Tarricone, L., see Castaldini	50 (1991) 485
Suzuki, Y., see Hatta	48/49 (1991) 222	Tasker, G.W., see Fijol	48/49 (1991) 464
Suzuki, Y., see Sasajima	48/49 (1991) 498	Tatarenko, S., J. Cibert, Y. Gobil, G.	
Swart, H.C., see Tjong	47 (1991) 311	Feuillet, K. Saminadayar, A.C. Chami	
Swart, P.L., B.M. Lacquet and R. Thavar,		and E. Ligeon, RHEED, XPS,	
Physical characterization of OMVPE-		HRTEM and channeling studies of	
grown $Al_xGa_{1-x}As$ multi-layer films		molecular beam epitaxy growth of	44 444 (2000) 450
by means of non-destructive optical	50 (1001) 000	CdTe on (001) GaAs	41/42 (1989) 470
reflectometry	50 (1991) 330	Tatarkiewicz, J., A. Kozanecki, Z. Kaliń-	
Swartz, W.E., see King	45 (1990) 325	ski and K. Paprocki, Photolumines-	
Szörényi, T., P. González, D. Fernández, J. Pou, B. León and M. Pérez-Amor,		cence study of proton-implanted	50 (1991) 249
Gas mixture dependence of the LCVD		$InP_{1-x}As_x$ : Yb Tatsuyama, C., T. Tanbo and N.	30 (1991) 249
of SiO <sub>2</sub> films using an ArF laser	46 (1990) 206	Nakayama, Heteroepitaxy between	
of 5102 mins using an Arr laser	40 (1770) 200	layered semiconductors GaSe and InSe	41/42 (1989) 539
Tachibana, S., see Fujimura	41/42 (1989) 286	Taylor, P.A., see Wallace	45 (1990) 201
Takahashi, H., see Hasegawa	41/42 (1989) 372	Tchandjou, N., see Fornari	50 (1991) 207
Takaki, S., see Shigesato	48/49 (1991) 269	Te Kaat, E.H., see Hecking	43 (1989) 87
Takase, Y., see Kamimura	41/42 (1989) 443	Teghil, R., see Mele	43 (1989) 398
Takayanagi, K., Y. Tanishiro, T. Ishitsuka	, ,	Teghil, R., A. Giardini-Guidoni, S. Pic-	
and K. Akiyama, In-situ UHV elec-		cirillo, A. Mele and F. Polla-Mattiot,	
tron microscope study of metal-sili-		In situ formation of ionic carbide clus-	
con surfaces	41/42 (1989) 337	ters by laser ablation	46 (1990) 220
Takeda, M., see Wada	41/42 (1989) 580	Teixeira, N., see Serna	46 (1990) 405
Takeuchi, M., see Sasajima	48/49 (1991) 498	Tête, C., see Dupuis	46 (1990) 398
Takeuchi, M., M. Masui and Y. Momose,		Thabti, A., see Barrière	41/42 (1989) 383
Copper-phthalocyanine thin film pho-		Thavar, R., see Swart	50 (1991) 330

Theeten, J.B., see Gendry	44 (1990) 309	Treverton, J.A. and A. Rosenfeld, De-	
Then, A.M., see Fijol	48/49 (1991) 464	termination of etching characteristics	
Thibaudau, F., see Salvan	41/42 (1989) 88	of a Vacuum Generators AG21 argon-	
Thimon, F., see Chevarier	48/49 (1991) 215	ion gun by interference colour and	
Thiry, P.A., see Sporken	41/42 (1989) 201	ellipsometric assessment of craters	
Thomas, I., see Tardy	50 (1991) 383	etched in tantalum oxide films	45 (1990) 263
Thomsen-Schmidt, P., see Bostanjoglo	43 (1989) 136	Troe, J., see Bolle	46 (1990) 279
Thomsen-Schmidt, P., see Bostanjoglo	46 (1990) 392	Tsuda, H., see Hirose	41/42 (1989) 174
Thoret, J., see Nogier	47 (1991) 287	Tsukada, N., see Kanamoto	41/42 (1989) 526
Tjong, S.C., Electrochemical and surface	47 (1771) 207	Tsukamoto, K., see Ogawa	41/42 (1989) 290
analysis of the Fe-Cr-Ru system in		Tuckerman, D.B., see Bernhardt	46 (1990) 121
non-oxidizing acid solutions	44 (1990) 7	Tung, R.T., see Werner	41/42 (1989) 159
Tjong, S.C. and J.B. Malherbe, Auger	(1550)	Tung, R.T. and F. Schrey, Epitaxial	11/ 42 (1707) 137
studies of the effect of Mo, V and Pd		CoSi <sub>2</sub> /Si(111) interfaces	41/42 (1989) 223
additions on the oxidation characteris-		Turban, G., see Cardinaud	45 (1990) 109
tics of Fe-24Cr alloy	44 (1990) 179	Tüttö, P., see Horányi	50 (1991) 143
Tjong, S.C., A surface study of the passi-	()	Tüzemen, S. and M.R. Brozel, An investi-	00 (1771) 110
vation of Fe-Cr-Co magnet alloys in		gation of photo-quenching properties	
sulphuric acid solution	45 (1990) 141	of LEC GaAs by using optical and	
Tjong, S.C., Self-passivation of Fe-Cr-	()	electrical techniques	50 (1991) 395
PGM alloys in reducing acids studied		Tyrrell, G.C., I.W. Boyd and R.B. Jack-	()
by electrochemical and electron spec-		man, Ion beam assisted etching of	
troscopic techniques	45 (1990) 301	silicon with bromine. The role of the	
Tjong, S.C. and H.C. Swart, Auger char-	(,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	adsorbed state	43 (1989) 439
acterization of the surface oxidation			
of austenitic Fe-26Mn-7Al-0.9C al-			
loy	47 (1991) 311		
Tochihara, H., see Iwami	41/42 (1989) 97	Uehara, Y., see Gofuku	48/49 (1991) 343
Tofterup, A.L., Estimates of errors and		Uhrberg, R.I.G., see Morar	41/42 (1989) 312
validity of Shirley-type backgrounds	44 (1990) 157	Ukraintsev, V.A., B.S. Podolsky and A.A.	
Tokarev, V.V., A.V. Kibardin, T.M.		Chernov, Water adsorption kinetics on	
Pyatkova and D.I. Zarovsky, Nickel,		Si(111)-7 $\times$ 7: defect generation mech-	
cobalt and iron silicide formation		anism	48/49 (1991) 151
stimulated by argon implantation	44 (1990) 235	Ukraintsev, V.A., A.A. Chernov, A.N.	
Tokarev, V.V., A.I. Demchenko, A.I.		Mezhuyev and B.S. Podolsky, Effec-	
Ivanov and V.E. Borisenko, Influence		tive temperature of products in laser	
of boron implantation on phase trans-		evaporation and desorption	48/49 (1991) 198
formations in nickel silicides	44 (1990) 241	Ulmer, G., see Campbell	43 (1989) 346
Tokuda, Y., see Kanamoto	41/42 (1989) 526	Ulmer, G., B. Hasselberger, HG. Bus-	
Tokutaka, H., see Nakanishi	41/42 (1989) 44	mann and E.E.B. Campbell, Excimer	
Tokutaka, H., see Nishimori	41/42 (1989) 49	laser ablation of polyimide	46 (1990) 272
Tokutaka, H., see Nishimori	47 (1991) 365	Ulrici, W., see Hizem	50 (1991) 490
Tokutaka, H. and S. Kishida, Surface		Ulrici, W., see Roura	50 (1991) 496
characterization of Bi-based high- $T_{\rm c}$		Unger, W., G. Lietz, H. Lieske and J.	
superconducting thin films and bulk		Völter, SIMS and FAB-MS surface	
single crystals	48/49 (1991) 425	studies of Pt-Sn/Al <sub>2</sub> O <sub>3</sub> and Pt <sub>3</sub> Pb	
Tokutaka, H., see Kishida	48/49 (1991) 446	model catalysts	45 (1990) 29
Tokutaka, H., see Nishimori	48/49 (1991) 450	Urano, T., M. Kaburagi, S. Hongo and T.	
Tomoda, S., see Kusunoki	45 (1990) 171	Kanaji, LEED $I-V$ curve analysis for	
Toporov, V.V., see Bairamov	50 (1991) 300	the structure of iron films on Si(111)	44 /44 /4 000
Toulemonde, M., see Mary	43 (1989) 102	surfaces	41/42 (1989) 103
Toulemonde, M., see Marfaing	46 (1990) 422	Urano, T., see Hongo	41/42 (1989) 522
Touwslager, F.J., see Sondag	47 (1991) 205	Urano, T., see Hongo	48/49 (1991) 143
Toyoda, Y., see Gofuku	48/49 (1991) 343	Ursu, I., see Craciun	43 (1989) 304
Treat, D.W., see Epler	43 (1989) 432	Ursu, I., see Prokhorov	43 (1989) 340
Tregouet, Y., see Morsli	50 (1991) 500	Usagawa, T., see Goto	41/42 (1989) 480
Treichler, R., see Bauer	50 (1991) 138	Usala, S., G.J. Adriaenssens, Ö. Öktü and	

M. Nesladek, Post-transit-time analy-		and J. Oudar, Hydrogen, hydrogen	
sis of time-of-flight photocurrents	50 (1991) 265	sulfide and hydrocarbon coadsorption	
Usui, H., see Yahashi	43 (1989) 37	on Pt(111) and Pt(110): selective for-	
		mation of alkylthiols	47 (1991) 273
Vajo, J.J. and J.G. McCarty, Thermody-		Vázquez, A., J.M. Domínguez and S.	
namics of carbon coadsorbed with		Fuentes, Thermally induced modifica-	
sulfur on Ni(100)	47 (1991) 23	tions on the crystal surface of molyb-	
Van Beckhoven, M.W.C., see Roosen-		date-type catalysts	44 (1990) 331
brand	44 (1990) 121	Vecris, G. and J.J. Quinn, Novel diagram-	
Van den Bergh, H., see Hoffmann	43 (1989) 54	matic method for analyzing the surface	
Van den Bergh, H., see Lecohier	43 (1989) 61	electronic modes of finite multilayer	40 440 44004 240
Van den Bergh, H., see Garrido	43 (1989) 68	structures	48/49 (1991) 319
Van den Bergh, H., see Braichotte	46 (1990) 9	Venghaus, H., see Sartorius	50 (1991) 369
Van den Hoek, P.J. and E.J. Baerends,		Venkateswarlu, D.S., see Sil	45 (1990) 229
Chemical bonding at metal-semicon-		Verbist, J., see Petit	43 (1989) 285
ductor interfaces	41/42 (1989) 236	Vere, A.W., see Mackey	43 (1989) 1
Van der Veen, J.F., see Vlieg	41/42 (1989) 62	Verhoeven, J., see Zeijlemaker	44 (1990) 249
Van der Veen, J.F., see Fischer	44 (1990) 115	Verhoeven, J., see Puik	47 (1991) 63
Van der Veen, J.F., see Deckers	45 (1990) 121	Verhoeven, J., see Puik	47 (1991) 251
Van der Weg, W.F., see Deckers	45 (1990) 121	Verreault, M., see Sapieha	44 (1990) 165
Van der Weg, W.F., see Deckers	45 (1990) 207	Vettiger, P., see Marclay	43 (1989) 43
Van der Wel, W., see Hu	46 (1990) 388	Veuillen, J.Y., see Cherief	41/42 (1989) 241
Van der Wiel, M.J., see Puik	47 (1991) 63	Veuillen, J.Y., see Nguyen Tan	41/42 (1989) 266
Van der Wiel, M.J., see Puik	47 (1991) 251	Vidal, B., see Marfaing	46 (1990) 422
Van Gisbergen, S.J.C.H.M., M. Godlew-		Vidali, G., see Li	48/49 (1991) 160
ski, T. Gregorkiewicz and C.A.J. Am-		Viefhaus, H., see Wolpers	45 (1990) 167
merlaan, Interstitial Mn as a new		Viefhaus, H., see Wolpers	47 (1991) 49
donor in GaP and GaAs: an EPR	50 (1001) 050	Viefhaus, H., see Grabke	47 (1991) 243
study	50 (1991) 273	Vieu, C., see Claverie	43 (1989) 106
Van Maaren, A.J.P., R.L. Krans and W.C.		Viktorovitch, P., see Tardy	50 (1991) 383
Sinke, HF formation in laser-induced	46 (1000) 120	Vlieg, E. and J.F. van der Veen, X-ray	
CVD of tungsten	46 (1990) 138	scattering studies of semiconductor in-	
Van Silfhout, A., see Aarnink	45 (1990) 37	terfaces: atomic structure and mor-	41 /42 (1090) 62
Van Silfhout, A., see Aarnink	47 (1991) 195	phology	41/42 (1989) 62
Van Staden, M.J. and J.P. Roux, The		Voelskow, M., W. Skorupa, K. Woll-	
superposition of carbon and rutheni-	44 (1990) 259	schlaeger, J. Matthaei, P. Knothe, K H. Heinig and H. Bartsch, Epitaxial	
um Auger spectra	44 (1990) 239	lateral overgrowth of amorphous CVD	
Van Staden, M.J. and J.P. Roux, The		silicon films induced by ion irradia-	
controlled oxidation of the high chro-		tion	43 (1989) 196
mium steel alloys Fe40Cr and	44 (1990) 263	Voitenko, V.A., see Bairamov	50 (1991) 300
Fe40Cr3Ru Van Staden, M.J. and J.P. Roux, Surface	44 (1990) 203	Völter, J., see Unger	45 (1990) 29
segregation in the alloys Fe40Cr3Ru,		Von der Linde, D., see Eleftheriadis	46 (1990) 284
Fe40Cr3Pt and Fe40Cr with a 1000 Å		Von Känel, H., see Werner	41/42 (1989) 159
Pt overlayer	44 (1990) 271	Von Känel, H., see Mendik	50 (1991) 303
Van Voorst, J.D.W., see Elders	46 (1990) 215	Vook, R.W., see Oral	44 (1990) 65
Van Zwol, J., S.T. de Zwart, C.C.A.	40 (1990) 213	Vook, R.W. and B. Oral, Carbon mono-	44 (1990) 03
Busquet and J. Dieleman, Resputter-		xide oxidation on epitaxial Cu(111)/	
ing of low-energy implanted inert		Pd(111) bilayers at atmospheric pres-	
gases: an angle-resolved time-of-flight		sures	48/49 (1991) 125
study	43 (1989) 363	Vovelle, L., see Bou	47 (1991) 149
Vanderschaeve, G., see Levade	50 (1991) 119	Vuye, G., see Borensztein	41/42 (1989) 439
Vase, P., Shen Yueqiang and T. Freltoft,	30 (1331) 113	. ajo, o., see borensztem	11/ 12 (1707) 437
Deposition, characterization, and laser		Wachter, P., see Mendik	50 (1991) 303
ablation patterning of YBCO thin		Wada, T., M. Takeda, T. Yamada and M.	30 (1771) 303
films	46 (1990) 61	Ichimura, Formation of a $Ge_xSi_{1-x}$	
Vassilakis, D., CM. Pradier, Y. Berthier	.0 (1770) 01	alloy layer by high-energy electron-	
		man onvig closuon	

beam irradiation	41/42 (1989) 580	Werner, J.H., H. von Känel, G. Marke-	
Wadayama, T., W. Shiraishi, A. Hatta	41/42 (1909) 300	witz and R.T. Tung, Pressure depen-	
and W. Suëtaka, A double-modulation		dences of silicide/silicon Schottky	
method of observing infrared emission		barrier heights	41/42 (1989) 159
spectra of thin films on metal surfaces	44 (1990) 43	Wertheimer, M.R., see Sapieha	44 (1990) 165
Wadayama, T., see Hatta	48/49 (1991) 222	West, B.O., see Pain	48/49 (1991) 76
Wadayama, T., T. Hihara, A. Hatta and	40/47 (1771) 222	Westendorp, J.F.M., see Ermolieff	48/49 (1991) 178
W. Suëtaka, In situ IR observation of		Westwood, D.I., see Woolf	50 (1991) 445
photo-chemically deposited silicon		Wetzel, P., see Haderbache	41/42 (1989) 257
nitride thin films	48/49 (1991) 409	Weyher, J.L., see Frigeri	50 (1991) 115
Wagner, J., Raman spectroscopy for im-	40/ 47 (1771) 407	White, J.M., see Akhter	44 (1990) 49
purity characterization in III-V semi-		White, J.M., see Zhou	44 (1990) 103
conductors	50 (1991) 79	Whitmarsh, C., see Interrante	46 (1990) 5
Wagner, J., see Jantz	50 (1991) 480	Wichert, Th., see Pfeiffer	50 (1991) 154
Wagner, M., A. Witzmann, H.D. Geiler	30 (1331) 400	Wichert, Th., see Magerle	50 (1991) 159
and KH. Heinig, Formation of p-n		Wielunski, L.S., see Pain	48/49 (1991) 76
junctions and silicides in silicon using		Wiemer, D., see Grabke	47 (1991) 243
a high performance laser beam homo-		Wieser, E., see Richter	44 (1990) 127
genization system	43 (1989) 260	Williams, G.M., see Brozel	50 (1991) 475
Wagner, M., N. Winkler and H.D. Geiler,	43 (1707) 200	Williams, J.O., see Simpson	46 (1990) 27
Single-beam thermowave analysis of		Williams, R.H., see Esser	41/42 (1989) 169
semiconductors	50 (1991) 373	Williams, R.H., see Zahn	41/42 (1989) 179
Wahl, G., see Schmaderer	46 (1990) 53	Williams, R.H., N. Forsyth, I.M. Dhar-	41/42 (1909) 179
Wahl, G. and H. Esrom, Simulation of	40 (1770) 33	madasa and Z. Sobiesierski, Metal	
laser CVD	46 (1990) 96	contacts to II-VI semiconductors:	
Wahl, U., see Jahn	50 (1991) 169	CdS and CdTe	41/42 (1989) 189
Waho, T., see Yamada Maruo	41/42 (1989) 647	Williams, R.H., see Zahn	41/42 (1989) 497
Wakatuki, K., see Nomura	41/42 (1989) 512	Williams, R.H., see Woolf	50 (1991) 445
Wallace, R.M., C.C. Cheng, P.A. Taylor,	41/42 (1707) 312	Williams, R.S., R.S. Daley, J.H. Huang	30 (1>>1) 113
W.J. Choyke and J.T. Yates, Jr., Ni		and R.M. Charatan, Initial stages of	
impurity effects on hydrogen surface		metal/semiconductor interface forma-	
chemistry and etching of Si(111)	45 (1990) 201	tion: Au and Ag on Si(111)	41/42 (1989) 70
Walsh, T.D., see Keir	50 (1991) 103	Wilson, J.I.B., see Jubber	43 (1989) 74
Wandass, J.H., see Hook	44 (1990) 29	Wilson, J.I.B., see Milne	43 (1989) 81
Wandass, J.H., see Hook	44 (1990) 252	Windscheif, J., see Wang	50 (1991) 228
Wandelt, K., see Kalki	48/49 (1991) 59	Windscheif, J., see Jantz	50 (1991) 480
Wang, X., see Ding	41/42 (1989) 123	Winkler, N., see Wagner	50 (1991) 373
Wang, Z.M., J. Windscheif, D.J. As and	41/42 (1909) 123	Winter, H., see Aumayr	47 (1991) 139
W. Jantz, Ambient and low tempera-		Winter, S., see Jahn	50 (1991) 169
ture photoluminescence topography of		Withrow, S.P., O.W. Holland and S.J.	30 (1))10)
GaAs substrates, epitaxial and im-		Pennycook, Ion beam annealing of	
planted layers	50 (1991) 228	Ga-implanted Si	43 (1989) 191
Warminski, T., see Pain	48/49 (1991) 76	Witthuhn, W., see Baurichter	50 (1991) 165
Watanabe, K., see Yumoto	48/49 (1991) 173	Witzmann, A., see Wagner	43 (1989) 260
Watanabe, Y., see Takeuchi	48/49 (1991) 526	Wójcik, W., see Biliński	47 (1991) 99
Wautelet, M., see Hanus	43 (1989) 271	Wolf, F., see Richter	44 (1990) 127
Wautelet, M., see Jadin	46 (1990) 375	Wolf, H., see Pfeiffer	50 (1991) 154
Wautelet, M., see Kolev	46 (1990) 418	Wolf, H., see Baurichter	50 (1991) 165
	43 (1989) 43	Wolfram, Z., see Nowicka	45 (1990) 13
Webb, D.J., see Marclay	41/42 (1989) 1	Wollschlaeger, K., see Voelskow	43 (1989) 196
Weber, E., see Spicer Wei, J., see Ma	41/42 (1989) 572	Wolpers, M., H. Viefhaus and M. Strat-	45 (1707) 170
Wei, S.Y., see Zhang	48/49 (1991) 139	mann, SEM and SAM imaging of	
Weimann, G., see Strasser	50 (1991) 261	silane LB films on metallic substrates	45 (1990) 167
		Wolpers, M., H. Viefhaus and M. Strat-	45 (1770) 107
Weishaupt, A., see Aarnink Weiss, B.Z., see Berger	45 (1990) 37 48/49 (1991) 281	mann, Surface analytical investiga-	
Weissmann, R., see Buerhop	46 (1990) 430	tions of metal surfaces modified by	
Weitering, H.H., see Hibma	48/49 (1991) 209	Langmuir-Blodgett films of silanes	47 (1991) 49
Wendelken, J.F., see Zuo	48/49 (1991) 366	Woolf, D.A., D.I. Westwood, M.A. An-	(2772) 17
Weildelkell, J.I., See Zuo	70/ 77 (1771) 300	John, Dan Hourious, Mills All-	

derson and R.H. Williams, The molec-		face state generation in MOS capaci-	
ular beam epitaxial growth of		tors at low temperatures	41/42 (1989) 420
GaAs $(\overline{111})$ /Si(111): a variable growth		Yasuda, Y., S. Zaima, T. Kaida and Y.	
temperature study	50 (1991) 445	Koide, Formation of Si-SiO <sub>2</sub> inter-	
Woratschek, B., P.G. Carey, M. Stolz and	00 (2272) 1.10	faces at low temperatures using micro-	
F. Bachmann, Excimer laser planari-		wave-excited plasma	41/42 (1989) 429
zation of AlSi, AlSiTi and AlSiCu al-		Yasuda, Y., see Zaima	41/42 (1989) 433
loys	43 (1989) 264	Yasuda, Y., see Ohshima	48/49 (1991) 69
loys	15 (1707) 201	Yasumatsu, T., see Ito	44 (1990) 97
		Yasumatsu, T., T. Ito, H. Nishizawa and	` ,
Xhonneux, P., see Sporken	41/42 (1989) 201	A. Hiraki, Ultrathin Si films grown	
Xiao, H.Y., see Ding	41/42 (1989) 123	epitaxially on porous silicon	48/49 (1991) 414
Xu, GQ., see Shek	48/49 (1991) 332	Yates, Jr., J.T., see Wallace	45 (1990) 201
Xu, Xin and J.I. Steinfeld, UV-laser pho-		Yegnaraman, V., see Bharathi	47 (1991) 293
todeposition of iron films from		Yokota, K., K. Ohtsuki, M. Ochi, S.	( ( ) - )
Fe(CO) <sub>5</sub> : role of gas-phase and surface		Ishihara and I. Kimura, Accumulation	
dissociation processes	45 (1990) 281	of implanted arsenic at the interface	
		during annealing on thermally oxidi-	
Yaacoub, B., see Hage-Ali	50 (1991) 377	zed Si and SiO <sub>2</sub> covered Si	41/42 (1989) 411
Yahashi, A., L.L. Levenson, H. Usui and	00 (1771) 011	Yokota, Y., see Ma	41/42 (1989) 572
I. Yamada, The structure zone model		Yonehara, T., see Ma	41/42 (1989) 572
applied to ionized cluster beam films:		Yonehara, T., see Kumomi	41/42 (1989) 638
**	43 (1989) 37	Yoon, C., see Zhou	44 (1990) 103
Al on SiO <sub>2</sub>	41/42 (1989) 416	Yoshida, S., see Okumura	, ,
Yamabe, K., see Hattori	, , ,		41/42 (1989) 548
Yamabe, K., see Nadahara	41/42 (1989) 425	Yoshida, S., H. Ishida and J.S. Jen, X-ray	
Yamada, A., see Ohnishi	50 (1991) 233	photoelectron spectroscopic and X-ray	
Yamada, I., Interfacial structure of ICB		diffractometric characterization of al-	
epitaxially deposited Al(110) bicrystal	41 (42 (1000) 252	kylimidazole films on copper oxide	
films on Si(100) substrates	41/42 (1989) 253	and alkylimidazolato copper(II) com-	
Yamada, I., Growth processes of epitaxial		plexes	44 (1990) 301
metal films on semiconductor and in-		Yoshida, T., see Ogawa	41/42 (1989) 290
sulator substrates by ionized cluster		Yoshida, T., see Iizuka	41/42 (1989) 587
beam	43 (1989) 23	Yoshii, T., see Suguro	41/42 (1989) 277
Yamada, I., see Fukushima	43 (1989) 32	You, H., see Chang	48/49 (1991) 12
Yamada, I., see Yahashi	43 (1989) 37	Yu Shidong, see Zhang Rong	48/49 (1991) 356
Yamada, T., see Wada	41/42 (1989) 580	Yumoto, H., K. Watanabe, K. Akashi and	
Yamada Maruo, Y., M. Oshima, T. Waho,		N. Igata, The effect of electronic exci-	
T. Kawamura, S. Maeyama and T.		tation produced by an electron shower	
Miyahara, Photoemission studies of		on the adhesion of copper films de-	
bonding properties at the MBE-grown		posited on stainless steel	48/49 (1991) 173
CaF <sub>2</sub> /GaAs interface	41/42 (1989) 647		
Yamagishi, H., see Hattori	41/42 (1989) 416	Zahn, D.R.T., see Esser	41/42 (1989) 169
Yamaguchi, T., see Hatanaka	41/42 (1989) 591	Zahn, D.R.T., W. Richter, A.B. McLean,	
Yamaguchi, Y., see Miyatake	41/42 (1989) 643	R.H. Williams, C. Stephens, I.T. Mc-	
Yamaji, T., see Igarashi	41/42 (1989) 282	Govern, R. Cimino, W. Braun and N.	
Yamama, A., see Ito	41/42 (1989) 301	Esser, Temperature effects on the for-	
Yamamoto, K., see Mimura	48/49 (1991) 521	mation of the Sb/InP(110) interface	41/42 (1989) 179
Yamashina, T. and T. Hino, Plasma-		Zahn, D.R.T., W. Richter, T. Eickhoff, J.	
surface interactions of graphite as		Geurts, T.D. Golding, J.H. Dinan, K.J.	
nuclear fusion material	48/49 (1991) 483	Mackey and R.H. Williams, The in-	
Yamashita, N., see Li	41/42 (1989) 118	fluence of Cd overpressure in the	
Yamauchi, S., see Hariu	48/49 (1991) 204	molecular beam epitaxy of InSb/CdTe	
Yano, M., M. Ashida, Y. Iwai and M.		heterostructures: a combined Raman	
Inoue, Characteristic properties of		and infrared spectroscopy study	41/42 (1989) 497
III-V <sub>A</sub> /III-V <sub>B</sub> heterointerfaces grown		Zaïdi, H., D. Paulmier and J. Lepage, The	, ()
by molecular beam epitaxy	41/42 (1989) 457	influence of the environment on the	
Yasuda, Y., S. Zaima and M. Sakashita,		friction and wear of graphitic carbons.	
Studies on charge trapping and inter-		II. Gas coverage of wear debris	44 (1990) 221
			(220) 221

Zaima, S., see Yasuda	41/42 (1989) 420	Ruolian, Hu Liqun, Zhong Peixin, Yu	
Zaima, S., see Yasuda	41/42 (1989) 429	Shidong, Li Qi, Feng Duan and Chen	
Zaima, S., T. Maruyama and Y. Yasuda,		Guangxi, The structure of Gex	
Piezoresistance in n-channel inversion		Si <sub>1-x</sub> /Si strained layer superlattices	
layers of Si MOSFET's	41/42 (1989) 433	and heterostructures	48/49 (1991) 356
Zaima, S., see Ohshima	48/49 (1991) 69	Zhang, T. and S.Y. Wei, Hydrogen chem-	
Zakrzewski, A. and M. Godlewski, Three-		isorption on contaminated composite	
center Auger effect and the quantum		catalysts	48/49 (1991) 139
yield of the luminescence of ZnS-based		Zhang, X.F., see Qiu	48/49 (1991) 430
phosphors	50 (1991) 257	Zhang, Y. and M. Stuke, VUV synchro-	, , , , , , , , , , , , , , , , , , , ,
Zanoni, R., see Niles	41/42 (1989) 139	tron radiation processing of thin pal-	
Zappe, H.P. and G. Kaufel, Reactive-		ladium acetate spin-on films for	
ion-etch damage in GaAs processing		metallic surface patterning	46 (1990) 153
evaluated by a microwave absorption		Zheng Youdou, see Zhang Rong	48/49 (1991) 356
technique	50 (1991) 290	Zhong Peixin, see Zhang Rong	48/49 (1991) 356
Zarovsky, D.I., see Tokarev	44 (1990) 235	Zhou, L.W., see Qiu	48/49 (1991) 430
Zaus, R., M. Schuster, H. Göbel and JP.	, , ,	Zhou, XL., C. Yoon and J.M. White,	, , , , , , , , , , , , , , , , , , , ,
Reithmaier, Characterization of (In,		Interactions of PF3 and PD3 with clean,	
Ga)As/GaAs strained-layer multiple		P-covered and H(D)-covered (100)-	
quantum wells with high-resolution		oriented W foil	44 (1990) 103
X-ray diffraction and computer simu-		Zironi, E.P., see Rickards	45 (1990) 155
lations	50 (1991) 92	Zommer, L., R. Duś and S.L. Randzio, A	(
Zeijlemaker, H. and J. Verhoeven, The		modified adsorption microcalorimeter	
application of digital techniques for		with computerized collection and re-	
electron energy spectroscopy using a		duction of the data	45 (1990) 93
retarding field analyser	44 (1990) 249	Zouari, I., M. Calvo, F. Lapicque and M.	()
Zeijlemaker, H., see Puik	47 (1991) 63	Cabrera, Morphological improvement	
Zeijlemaker, H., see Puik	47 (1991) 251	of zinc electrodeposits by laser assis-	
Zeman, M., I. Ferreira, M.J. Geerts and		tance	46 (1990) 411
J.W. Metselaar, The influence of de-		Zuo, JK. and J.F. Wendelken, Substrate	, ,
position parameters on the growth of		temperature effects on $(\sqrt{3} \times \sqrt{3})$ R30°	
a-SiGe:H alloys in a plasma CVD sys-		domain growth of Ag on Si(111)	
tem	46 (1990) 245	surface	48/49 (1991) 366
Zhang Rong, Zheng Youdou, Jiang			

## Subject index to volumes 41-50

Adhesion		V.A. Ukraintsev, B.S. Podolsky and A.A. Chernov, Water adsorption kinetics on Si(111)-7 × 7: defect generation mech-	
<ul><li>P.S. Ho, Chemistry and adhesion of metal-polymer interfaces</li><li>K. Furukawa and A. Nakagawa, Applica-</li></ul>	41/42 (1989) 559	anism	48/49 (1991) 151
tions of the silicon wafer direct-bond- ing technique to electron devices	41/42 (1989) 627	Alkali halides	
J. Breuer, S. Metev, G. Sepold, OD. Hennemann, H. Kollek and G. Krüger, Laser-induced photochemical adherence enhancement	46 (1990) 336	J. Heidberg, B. Brase, KW. Stahmer and M. Suhren, Second harmonic genera- tion of CO <sub>2</sub> -laser radiation and FTIR spectroscopy for resonant desorption	
H. Yumoto, K. Watanabe, K. Akashi and N. Igata, The effect of electronic exci- tation produced by an electron shower		in the adsorbate CO-NaCl(100)  A.D. Gates and J.L. Robins, Nucleation	46 (1990) 44
on the adhesion of copper films de- posited on stainless steel	48/49 (1991) 173	of gold on Ca <sup>2+</sup> -doped NaCl	48/49 (1991) 154
J.S. Kim, P.K. Banerjee, S.S. Mitra, H. Shastry, J.J. Loferski and R. Beaulieu,		Alkali metals	
Optical, electrical and mechanical properties of RF-sputtered TiN-W-Au films	48/49 (1991) 548	S. Kono, Y. Enta, T. Abukawa, T. Kinoshita and T. Sakamoto, Photo- electron spectroscopy and photoelec- tron diffraction studies of Si(001)	
Adsorption isotherms		2 × 1-K and -Cs surfaces  S. Kohmoto, S. Mizuno and A. Ichimiya, RHEED intensity analysis of Li/	41/42 (1989) 75
E. Nowicka, Z. Wolfram and R. Duś, Deuterium adsorption on thin nickel films	45 (1990) 13	Si(111) structures  P. Soukiassian, H.I. Starnberg and T.  Kendelewicz, Insulator-semiconduc-	41/42 (1989) 107
L. Zommer, R. Duś and S.L. Randzio, A modified adsorption microcalorimeter with computerized collection and re-		tor interface formation by electronic promotion using alkali metal and re- moval of the catalyst	41/42 (1989) 395
duction of the data M.E. Pemble, J.T. Allen, D.S. Buhaenko,	45 (1990) 93	G.E. Rhead, On the work function variations produced by the oxidation of	41/42 (1707) 373
S.M. Francis, P.A. Goulding, J. Lee and M.J. Parrott, The adsorption of triethylgallium on GaAs(100) at 300 K: adsorption kinetics from optical		adsorbed alkali metal layers  T. Hashizume, Y. Hasegawa and T.  Sakurai, Alkali-metal adsorption on silicon surfaces studied by field ion-	47 (1991) 35
second harmonic generation transients J. Heidberg, B. Brase, KW. Stahmer and M. Suhren, Second harmonic genera-	46 (1990) 32	scanning tunneling microscopy (FI-STM) S. Hongo, T. Urano and T. Kanaji, Mech-	48/49 (1991) 119
tion of CO <sub>2</sub> -laser radiation and FTIR spectroscopy for resonant desorption in the adsorbate CO-NaCl(100)	46 (1990) 44	anisms of He*(2 <sup>1</sup> S) de-excitation on oxygen-adsorbed Si(100) surfaces D. Heskett, D. Tang, A.B. McLean, R.	48/49 (1991) 143
B. Biliński, W. Wójcik and A.L. Dawidowicz, Investigation of the surface free energy components of thermally treated controlled porosity glasses by	40 (1770) 44	Ludeke, M. Prietsch, T. Maeda Wong, E.W. Plummer and N.J. DiNardo, Metal-induced states on the GaAs- (110) surface probed by angle-resolved	
inverse gas chromatography	47 (1991) 99	photoemission spectroscopy	48/49 (1991) 260

M.L. Shek, T.K. Sham, J. Hrbek and GQ. Xu, A soft X-ray study of a Li-S		Pt <sub>0.5</sub> Ni <sub>0.5</sub> (111) surface studied by medium-energy ion scattering	45 (1990) 121
surface compound  I. Dalins, M. Karimi and D. Ila, Violent	48/49 (1991) 332	S.C. Tjong, A surface study of the passivation of Fe-Cr-Co magnet alloys in	43 (1990) 121
oxidation of lithium-containing alumi- num alloys in liquid oxygen	48/49 (1991) 509	sulphuric acid solution S.C. Tjong, Self-passivation of Fe-Cr-	45 (1990) 141
Alloys		PGM alloys in reducing acids studied by electrochemical and electron spec- troscopic techniques	45 (1990) 301
J. Marfaing, W. Marine, R. Pierrisnard		R. Pielmeier, D. Bollmann and K. Ha- berger, Laser evaporation of metal	43 (1990) 301
and A. Cros, Structural changes in $Au_xSi_{1-x}$ alloy films under laser irradiation	43 (1989) 165	sandwich layers for improved IC metallization	46 (1990) 163
E. Gaffet, J.M. Pelletier and S. Bonnet- Jobez, Laser surface alloying of Ni	43 (1989) 103	R. Kötz, Ultraviolet photoelectron spec- troscopy (UPS) of anodic oxide films	
film on Al-based alloy  B. Woratschek, P.G. Carey, M. Stolz and	43 (1989) 248	on Au, Pt, Ru and Ru <sub>0.5</sub> Ir <sub>0.5</sub> alloy H.J. Grabke, D. Wiemer and H. Viefhaus, Segregation of sulfur during growth of	47 (1991) 109
F.G. Bachmann, Excimer laser plan- arization of AlSi, AlSiTi and AlSiCu		oxide scales W.J. Quadakkers, J. Jedlinski, K. Schmidt,	47 (1991) 243
alloys S.C. Tjong, Electrochemical and surface	43 (1989) 264	M. Krašovec, G. Borchardt and H. Nickel, The effect of implanted yt-	
<ul><li>analysis of the Fe-Cr-Ru system in non-oxidizing acid solutions</li><li>P. Lejček, M. Koutník, J. Brádler, V.</li></ul>	44 (1990) 7	trium on the growth and adherence of alumina scales on Fe-20Cr-5Al	47 (1991) 261
Paidar and A. Potměšilová, Ani- sotropy of grain boundary segregation		S. Bharathi, V. Yegnaraman and G. Prabhakara Rao, Alloy formation in the monolayers of underpotentially	
in as-grown Fe-6at%Si alloy bi- crystals	44 (1990) 75	deposited lead and thallium S.C. Tjong and H.C. Swart, Auger char-	47 (1991) 293
S. Suzuki and M. Oku, Surface orienta- tion dependence of the surface com- position in an Fe-20%Cr alloy and an		acterization of the surface oxidation of austenitic Fe-26Mn-7Al-0.9C al-	47 (1001) 211
Fe-3%Si alloy treated by mechanical polishing and chemical etching	44 (1990) 151	loy P.J. Godowski, Analysis of surface segre- gation in Co-Ru alloy using Auger	47 (1991) 311
S.C. Tjong and J.B. Malherbe, Auger studies of the effect of Mo, V and Pd		electron spectroscopy  D.G. Ren, Study of interface structure of	47 (1991) 333
additions on the oxidation characteris- tics of Fe-24Cr alloy M.J. van Staden and J.P. Roux, The con-	44 (1990) 179	AP-FIM	48/49 (1991) 227
trolled oxidation of the high chro- mium steel alloys Fe40Cr and		I. Dalins, M. Karimi and D. Ila, Violent oxidation of lithium-containing alumi- num alloys in liquid oxygen	48/49 (1991) 509
Fe40Cr3Ru M.J. van Staden and J.P. Roux, Surface	44 (1990) 263	Aluminium	., (,
segregation in the alloys Fe40Cr3Ru, Fe40Cr3Pt and Fe40Cr with a 1000 Å	44 (1000) 271		
Pt overlayer W. Unger, G. Lietz, H. Lieske and J. Völter, SIMS and FAB-MS surface studies of Pt-Sn/Al <sub>2</sub> O <sub>3</sub> and Pt <sub>3</sub> Pb	44 (1990) 271	<ul> <li>G.S. Higashi, The chemistry of alkyl-aluminum compounds during laser-assisted chemical vapor deposition</li> <li>A. Yahashi, L.L. Levenson, H. Usui and</li> </ul>	43 (1989) 6
model catalysts  A. Elbiache and P. Marcus, Adsorption and surface segregation of sulphur on	45 (1990) 29	I. Yamada, The structure zone model applied to ionized cluster beam films: Al on SiO <sub>2</sub>	43 (1989) 37
Fe-17Cr-12.6Ni(100) and Fe-17Cr- 14.5Ni-2.3Mo(100) alloys	45 (1990) 49	A. Seidel and G. Linker, Amorphization mechanisms in Mn <sup>+</sup> -implanted thin Al	
S. Deckers, F.H.P.M. Habraken, W.F. van der Weg, A.W. Denier van der Gon,		films and single crystals  E. Gaffet, J.M. Pelletier and S. Bonnet-	43 (1989) 97
J.F. van der Veen and J.W. Geus, Oxidation-induced segregation at the		Jobez, Laser surface alloying of Ni film on Al-based alloy	43 (1989) 248

J.C. Ingram, K.W. Nebesny and J.E. Pemberton, Optical properties of metal surfaces from electron energy loss		Y. Kawadzu, M. Iioka, A. Fujii, H. Oyanagi and T. Arai, Interfacial reaction of nickel/hydrogenated amor-	
spectroscopy in the reflection mode E.J. Petit and R. Caudano, Chemical re- actions at solid-solid interfaces in- duced by pulsed laser annealing	44 (1990) 279 46 (1990) 357	phous silicon system at low tempera- ture studied by fluorescence EXAFS Y. Hatanaka, K. Mitsuoka and T. Yama- guchi, Properties of a-Si:H based in-	41/42 (1989) 296
M. Bou, J.M. Martin, Th. Le Mogne and L. Vovelle, Chemistry of the interface	40 (1990) 337	terface transient layers measured by in-situ ellipsometry	41/42 (1989) 591
between aluminium and polyethylene- terephthalate by XPS S.C. Tjong and H.C. Swart, Auger char-	47 (1991) 149	F. Priolo, A. La Ferla, C. Spinella, E. Rimini, S.U. Campisano and G. Ferla, Crystal-amorphous-silicon interface	
acterization of the surface oxidation of austenitic Fe-26Mn-7Al-0.9C al-	47 (1991) 311	kinetics under ion beam irradiation  A. Seidel and G. Linker, Amorphization mechanisms in Mn <sup>+</sup> -implanted thin Al	41/42 (1989) 619
loy S. Berger, Y. Komem and B.Z. Weiss, On the microstructure, composition and electrical properties of Al/TiW/poly-	47 (1991) 311	films and single crystals  E.E. Marinero, Material transformations in semiconductor and magnetic thin	43 (1989) 97
Si system	48/49 (1991) 281	films	43 (1989) 117
P.K. Banerjee, J.S. Kim and S.S. Mitra, Electrical and optical properties of a- luminum-doped amorphous silicon		W.C. Sinke, A. Polman, S. Roorda and P.A. Stolk, Explosive crystallization of amorphous silicon: triggering and	
carbide films  I. Dalins, M. Karimi and D. Ila, Violent oxidation of lithium-containing alumi-	48/49 (1991) 288	propagation E.L. Mathé, J.G. Maillou, A. Naudon, E. Fogarassy, M. Elliq and S. de Un-	43 (1989) 128
num alloys in liquid oxygen P.L. Swart, B.M. Lacquet and R. Thavar, Physical characterization of OMVPE-	48/49 (1991) 509	amuno, Excimer laser recrystallization of amorphous Si films characterized by grazing X-ray diffraction and opti-	
grown $Al_xGa_{1-x}As$ multi-layer films by means of non-destructive optical reflectometry	50 (1991) 330	cal reflectivity  J.G. Maillou, E.L. Mathé, J.C. Desoyer, S. de Unamuno and E. Fogarassy,	43 (1989) 142
K. Jezierski, Z. Gumienny and J. Misiewicz, Reflectometry-aided surface layer investigation	50 (1991) 341	Comparison between microscopical aspects of a-Si films crystallized by pulsed UV excimer laser and calcu-	
layer investigation	30 (1991) 341	lated temperature profiles	43 (1989) 150
Aluminium oxide		F. Priolo, C. Spinella, A. La Ferla, E. Rimini and G. Ferla, Ion-assisted re-	
T. Wadayama, W. Shiraishi, A. Hatta and W. Suëtaka, A double-modulation method of observing infrared emission		crystallization of amorphous silicon C. Spinella, S. Lombardo and S.U. Campisano, Amorphous to polycrystal transition in ion irradiated chemical	43 (1989) 178
spectra of thin films on metal surfaces W. Unger, G. Lietz, H. Lieske and J.	44 (1990) 43	vapor deposited amorphous silicon S.P. Withrow, O.W. Holland and S.J.	43 (1989) 187
Völter, SIMS and FAB-MS surface studies of Pt-Sn/Al <sub>2</sub> O <sub>3</sub> and Pt <sub>3</sub> Pb model catalysts	45 (1990) 29	Pennycook, Ion beam annealing of Ga-implanted Si M. Voelskow, W. Skorupa, K. Woll-	43 (1989) 191
Amorphous materials		schlaeger, J. Matthaei, P. Knothe, K H. Heinig and H. Bartsch, Epitaxial lateral overgrowth of amorphous CVD	
Y. Gekka, M. Saitoh, K. Ohga, Y. Akaida and M. Akimoto, Electrical character- istics of metal contacts on the surfaces of a-Si:H films annealed at low tem-		silicon films induced by ion irradiation  G. Compagnini, R. Reitano, L. Calcagno, G. Marletta and G. Foti, Hydro-	43 (1989) 196
perature H. Sugahara and J. Nagano, Thermal stability of WSiN-GaAs and Au-WSiN	41/42 (1989) 184	genated amorphous carbon synthesis by ion beam irradiation W.I. Milne, F.J. Clough, S.C. Deane, S.D.	43 (1989) 228
interfaces	41/42 (1989) 207	Baker and P.A. Robertson, Photoen-	

hanced CVD of hydrogenated amor- phous silicon using an internal hydro-		S. Usala, G.J. Adriaenssens, Ö. Öktü and M. Nesladek, Post-transit-time analy-	
gen discharge lamp	43 (1989) 277	sis of time-of-flight photocurrents	50 (1991) 265
W.C.M. Claassen, R.W.A.H. Schmitz and	43 (1909) 277	R. Schwarz, T. Fischer, P. Hanesch, T.	30 (1991) 203
J. Dieleman, Influence of surface fluo-		Muschik, J. Kolodzey, H. Cerva, H.L.	
rination on the oxidation of amor-		Meyerheim and B.M.U. Scherzer,	
phous silicon by atomic oxygen at 300		Limitations of interface sharpness in	
K	43 (1989) 292	a-Si:H/a-SiC:H multilayers	50 (1991) 456
E. Golusda, R. Lange, G. Mollekopf and	43 (1707) 272	a-51.11/ a-51C.11 multilayers	30 (1371) 430
H. Stafast, On the role of the substrate		Annealing	
position in the CO <sub>2</sub> laser CVD of		Annealing	
amorphous hydrogenated silicon	46 (1990) 230	Y. Gekka, M. Saitoh, K. Ohga, Y. Akaida	
K. Hesch, P. Hess, H. Oetzmann and C.	40 (1770) 230	and M. Akimoto, Electrical character-	
Schmidt, Laser CVD of a-Si:H from		istics of metal contacts on the surfaces	
SiH <sub>4</sub> and Si <sub>2</sub> H <sub>6</sub> : relations between		of a-Si:H films annealed at low tem-	
chemistry, growth rate and film prop-		perature	41/42 (1989) 184
erties	46 (1990) 233	Y. Igarashi, T. Yamaji, S. Nishikawa and	41/42 (1707) 104
W. Marine, J.M. Scotto D'Aniello and J.	40 (1770) 233	S. Ohno, Influence of annealing am-	
Marfaing, Picosecond YAG laser pho-		bients on ZrSi <sub>2</sub> formation	41/42 (1989) 282
toablation of amorphous silicon	46 (1990) 239	N. Fujimura, S. Tachibana and T. Ito,	41/42 (1909) 202
M. Zeman, I. Ferreira, M.J. Geerts and	40 (1990) 239	Characterization of Si-rich WSi <sub>x</sub> on Si	41/42 (1989) 286
J.W. Metselaar, The influence of de-		K. Yokota, K. Ohtsuki, M. Ochi, S.	41/42 (1707) 200
position parameters on the growth of		Ishihara and I. Kimura, Accumulation	
a-SiGe:H alloys in a plasma CVD sys-		of implanted arsenic at the interface	
tem	46 (1990) 245	during annealing on thermally	
H. Hiraoka and S. Lazare, Applications	40 (1770) 243	oxidized Si and SiO <sub>2</sub> covered Si	41/42 (1989) 411
of doping and dedoping of Teflon AF		Y. Borensztein, T. Lopez-Rios and G.	41/42 (1707) 411
films in microfabrication using KrF		Vuye, Roughness induced at Si(111)	
and ArF excimer lasers	46 (1990) 342	surfaces by high temperature heating	41/42 (1989) 439
M. Elliq, E. Fogarassy, J.P. Stoquert, C.	40 (1770) 542	H. Miyatake, Y. Yamaguchi, Y. Mashiko,	41/42 (1707) 437
Fuchs, S. de Unamuno, B. Prévot and		T. Nishimura and H. Koyama, Micro-	
H. Pattyn, Pulsed excimer and		structure of high temperature an-	
Nd:YAG laser crystallization of a-		nealed SIMOX wafer	41/42 (1989) 643
Si:H. The specific role of hydrogen	46 (1990) 378	A.E.M.J. Fischer, W.F.J. Slijkerman, J.F.	41/42 (1707) 043
O. Bostanjoglo and P. Thomsen-Schmidt,	40 (1770) 370	van der Veen and I. Ohdomari, Ther-	
Time-resolved TEM of laser-induced		mal stability of supersaturated oxy-	
structural changes in GeTe films	46 (1990) 392	gen-doped silicon epitaxial films	44 (1990) 115
K. Kolev, M. Wautelet and L.D. Laude,	10 (1),0) 3,2	F. Richter, E. Bugiel, R. Grötzschel, H.	44 (1770) 113
CW laser-induced transformation of		Reichardt, A. Schöpke, E. Wieser and	
thin Sb, Se and Sb <sub>2</sub> Se <sub>3</sub> films in air	46 (1990) 418	F. Wolf, Formation of titanium di-	
J. Marfaing, W. Marine, B. Vidal, M.	40 (1770) 410	silicide using different annealing	
Toulemonde, M. Hage Ali and J.P.		methods	44 (1990) 127
Stoquert, Instability and structural		V.V. Tokarev, A.V. Kibardin, T.M. Pyat-	11 (1770) 127
transformation of amorphous ultra-		kova and D.I. Zarovsky, Nickel, cobalt	
thin W-Si multilayer structures dur-		and iron silicide formation stimulated	
ing heavy ion irradiation	46 (1990) 422	by argon implantation	44 (1990) 235
LU.A. Andersen and J. Bøttiger, Crys-	40 (1770) 422	V.V. Tokarev, A.I. Demchenko, A.I.	44 (1770) 255
tallization of Fe-Zr metallic glasses		Ivanov and V.E. Borisenko, Influence	
during ion irradiation	46 (1990) 427	of boron implantation on phase trans-	
J.C. Lascovich, R. Giorgi and S. Scagl-	10 (1770) 127	formations in nickel silicides	44 (1990) 241
ione, Evaluation of the sp <sup>2</sup> /sp <sup>3</sup> ratio		A. Vázquez, J.M. Domínguez and S.	44 (1))0) 241
in amorphous carbon structure by XPS		Fuentes, Thermally induced modifica-	
and XAES	47 (1991) 17	tions on the crystal surface of molyb-	
V.Kh. Kudoyarova, G.M. Gusinsky, L.A.	(1771) 11	date-type catalysts	44 (1990) 331
Rassadin and I.V. Kudryavtsev, Hy-		B. Hartiti, A. Slaoui, J.C. Muller and P.	(2)/0)/031
drogen depth profile measurement in		Siffert, Annealing kinetics during	
a-Si <sub>1-x</sub> $C_x$ :H films by elastic recoil de-		rapid thermal processing of excimer	
tection	50 (1991) 173	laser-induced defects in virgin silicon	46 (1990) 371
	()		(====)

V. Dupuis, M.F. Ravet, C. Tête and M. Piecuch, Thermal evolution of W/Si and W/C multilayers under pulsed laser heating and classical annealing	46 (1990) 398	Correlated use of characterization techniques to optimize the Mg implan- tation annealing for self-aligned HBT's L.J. Bredell, F.D. Auret, G. Myburg and	50 (1991) 462
JM. Dilhac, N. Nolhier and C. Ganibal, In situ silicon solid state regrowth kinetics measurement in a rapid ther-		W.O. Barnard, Electrical characteriza- tion of argon-ion sputtered n-GaAs	50 (1991) 466
mal processor  D. Ballutaud, P. de Mierry, M. Aucoutu-	46 (1990) 451	Antimony	
rier and E. Darque-Ceretti, Influence of thermal treatments on the distribu- tion of contaminating copper near the surface of silicon: a comparative SIMS and XPS study	47 (1991) 1	D.R.T. Zahn, W. Richter, A.B. McLean, R.H. Williams, C. Stephens, I.T. McGovern, R. Cimino, W. Braun and N. Esser, Temperature effects on the for-	
S. Kishida, H. Tokutaka, H. Higashi, K. Nishimori and N. Ishihara, Preparation conditions of flat 80 K phase Bi-Sr-Ca-Cu-O thin films by RF magnetron sputtering	48/49 (1991) 446	mation of the Sb/InP(110) interface E.J. Petit, J. Riga, R. Caudano and J. Verbist, Ultraviolet laser-induced oxi- dation of antimony: chemical com- position and growth kinetics of the	41/42 (1989) 179
W. Pfeiffer, M. Deicher, R. Keller, R. Magerle, P. Pross, H. Skudlik, Th. Wichert, H. Wolf, D. Forkel, N.		oxide layer  E.J. Petit and R. Caudano, Chemical reactions at solid-solid interfaces in-	43 (1989) 285
Moriya and R. Kalish, Characteriza- tion of Cd implanted and annealed GaAs and InP by perturbed angular correlation (PAC) spectroscopy	50 (1991) 154	duced by pulsed laser annealing R. Serna, C.N. Afonso, F. Catalina, N. Teixeira, M.F. da Silva and J.C. Soares, Diffusion and microstructures	46 (1990) 357
S.G. Jahn, H. Hofsäss, U. Wahl, S. Winter, E. Recknagel and ISOLDE Collabora- tion, Structural defect recovery in GaP after heavy ion implantation	50 (1991) 169	induced by excimer laser irradiation in Ge-Sb thin film bilayers K. Kolev, M. Wautelet and L.D. Laude, CW laser-induced transformation of	46 (1990) 405
M. Baumgartner and K. Löhnert, Characterization of si-GaAs wafer quality by room-temperature photoluminescence	50 (1991) 222	thin Sb, Se and Sb <sub>2</sub> Se <sub>3</sub> films in air Y. Nakanishi, Y. Suzuki, T. Nakamura, Y. Hatanaka, Y. Fukuda, A. Fujisawa and G. Shimaoka, Coloration of Sn-	46 (1990) 418
Z.M. Wang, J. Windscheif, D.J. As and W. Jantz, Ambient and low tempera- ture photoluminescence topography of GaAs substrates, epitaxial and im-		Sb-O thin films  Argon	48/49 (1991) 55
planted layers  H. L'Haridon, P.N. Favennec, R. Coquille, M. Salvi, M. Gauneau, Y. Le	50 (1991) 228	V.V. Tokarev, A.V. Kibardin, T.M. Pyatkova and D.I. Zarovsky, Nickel,	
Guillou, R. Callec and P. Gall, Spatial investigation of an iron-doped indium phosphide ingot  J. Tatarkiewicz, A. Kozanecki, Z. Kaliń-	50 (1991) 237	cobalt and iron silicide formation stimulated by argon implantation  A. Chevarier, N. Chevarier, M. El Bou- anani, E. Gerlic, M. Stern, B. Roux	44 (1990) 235
ski and K. Paprocki, Photoluminescence study of proton-implanted $InP_{1-x}As_x$ : Yb	50 (1991) 249	and F. Thimon, Profiling of carbon, oxygen and argon contamination in sputter-deposited films using nuclear	
A. Deneuville, C.H. Park, P. Ayyub, T. Anderson, P. Lowen, K. Jones and P.H. Holloway, O implantation in ZnSe: lattice distortion by Raman		backscattering and nuclear reaction spectroscopy	48/49 (1991) 215
measurement M. Wagner, N. Winkler and H.D. Geiler,	50 (1991) 308	Arsenic	
Single-beam thermowave analysis of semiconductors  V. Amarger, C. Dubon-Chevallier, A.C. Papadopoulo, B. Descouts and Y. Gao,	50 (1991) 373	J.F. Morar, U.O. Karlsson, R.I.G. Uhrberg, J. Kanski, P.O. Nilsson and H. Qu, Angle-resolved photoemission study of the As/Ge(100) interface	41/42 (1989) 312

Atomic and molecular beam studies		F. Abel, C. Cohen, J.A. Davies, J. Moulin and D. Schmaus, Thin-film growth of	
<ul> <li>I. Kusunoki, M. Hiroi, T. Sato, Y. Igari and S. Tomoda, SiC film formation on Si(001) by reaction with C<sub>2</sub>H<sub>2</sub> beams</li> <li>L.V. Interrante, B. Han, J.B. Hudson and C. Whitmarsh, Design and synthesis</li> </ul>	45 (1990) 171	Sn on Cu(100)  P. Lejček, M. Koutník, J. Brádler, V. Paidar and A. Potměšilová, Anisotropy of grain boundary segregation in as-grown Fe-6at%Si alloy bi-	44 (1990) 17
of CVD precursors to thin film ceramic materials	46 (1990) 5	crystals  J. Lausmaa, B. Kasemo and H. Mattsson, Surface spectroscopic characterization	44 (1990) 75
B.L. Halpern, J.J. Schmitt, J.W. Golz, Y. Di and D.L. Johnson, Gas jet deposition of thin films	49 /40 /1001 \ 10	of titanium implant materials  A.L. Tofterup, Estimates of errors and	44 (1990) 133
W. Li, JS. Lin, M. Karimi, C. Moses and G. Vidali, Structural characterization of ultra-thin metal overlayers on Cu(001) by atom beam scattering	48/49 (1991) 19 48/49 (1991) 160	validity of Shirley-type backgrounds J. Morais, A.M. Machado, M.A. Sacilotti and R. Landers, AES sputter depth profiles applied to interface analysis	44 (1990) 157
Auger electron spectroscopy		of GaInAs/InP grown by atmospheric pressure MOCVD S.C. Tjong and J.B. Malherbe, Auger	44 (1990) 161
S. Nakanishi, H. Tokutaka, K. Nishimori, S. Kishida and N. Ishihara, The dif-		studies of the effect of Mo, V and Pd additions on the oxidation characteristics of Fe-24Cr alloy	44 (1990) 179
ference between 6H-SiC (0001) and (0001) faces observed by AES, LEED and ESCA	41/42 (1989) 44	H. Zeijlemaker and J. Verhoeven, The application of digital techniques for electron energy spectroscopy using a	
R. Sporken, P.A. Thiry, P. Xhonneux, R. Caudano and J.P. Delrue, Spectroscopic study of metal/semimetal and		retarding field analyser  M.J. van Staden and J.P. Roux, The su- perposition of carbon and ruthenium	44 (1990) 249
metal/semiconductor interfaces H. Sugahara and J. Nagano, Thermal stability of WSiN-GaAs and Au-WSiN	41/42 (1989) 201	Auger spectra  M.J. van Staden and J.P. Roux, The controlled oxidation of the high chro-	44 (1990) 259
interfaces  M. Renda and K. Morita, Epitaxial growth of a mono-crystalline metastable AuIn layer at the Au/InP(001) interface	41/42 (1989) 207 41/42 (1989) 216	mium steel alloys Fe40Cr and Fe40Cr3Ru  M.J. van Staden and J.P. Roux, Surface segregation in the alloys Fe40Cr3Ru, Fe40Cr3Pt and Fe40Cr with a 1000 Å	44 (1990) 263
N. Cherief, R. Cinti, M. De Crescenzi, J. Derrien, T.A. Nguyen Tan and J.Y. Veuillen, Heteroepitaxy of metallic and semiconducting silicides on sili-	12/ 12 (1202) 110	Pt overlayer  A. Elbiache and P. Marcus, Adsorption and surface segregation of sulphur on Fe-17Cr-12.6Ni(100) and Fe-17Cr-	44 (1990) 271
N. Fujimura and T. Ito, TiSi <sub>2</sub> formation at the Ti-rich TiN <sub>x</sub> /Si interface	41/42 (1989) 241 41/42 (1989) 272	14.5Ni-2.3Mo(100) alloys  A. Bukaluk and W. Bała, AES depth profile studies of interdiffusion in thin	45 (1990) 49
M. Yano, M. Ashida, Y. Iwai and M. Inoue, Characteristic properties of III-V <sub>A</sub> /III-V <sub>B</sub> heterointerfaces grown by molecular beam epitaxy	41/42 (1989) 457	polycrystalline Au-Ag multilayer films S.C. Tjong, A surface study of the passi- vation of Fe-Cr-Co magnet alloys in	45 (1990) 57
B.A. Orlowski, J.P. Lacharme, C.A. Sébenne and S. Bensalah, Interface formation on n- and p-CdTe(110)	12/12 (1707) 431	sulphuric acid solution  M. Wolpers, H. Viefhaus and M. Stratmann, SEM and SAM imaging of	45 (1990) 141
surfaces with Cu and Au C. Tatsuyama, T. Tanbo and N. Nakayama, Heteroepitaxy between layered	41/42 (1989) 491	silane LB films on metallic substrates  I. Kusunoki, M. Hiroi, T. Sato, Y. Igari and S. Tomoda, SiC film formation on	45 (1990) 167
semiconductors GaSe and InSe H. Horikawa, M. Akiyama, S. Onozawa, Y. Kawai and M. Sakuta, Interfacial	41/42 (1989) 539	Si(001) by reaction with C <sub>2</sub> H <sub>2</sub> beams J. Lausmaa, B. Kasemo, H. Mattsson and H. Odelius, Multi-technique surface	45 (1990) 171
layers of InP/Si heteroepitaxy	41/42 (1989) 598	characterization of oxide films on	

electropolished and anodically oxid-		D. Vassilakis, CM. Pradier, Y. Berthier	
ized titanium	45 (1990) 189	and J. Oudar, Hydrogen, hydrogen	
R.M. Wallace, C.C. Cheng, P.A. Taylor,		sulfide and hydrocarbon coadsorption on Pt(111) and Pt(110): selective for-	
W.J. Choyke and J.T. Yates, Jr., Ni impurity effects on hydrogen surface		mation of alkylthiols	47 (1991) 273
chemistry and etching of Si(111)	45 (1990) 201	S.C. Tjong and H.C. Swart, Auger char-	47 (1991) 273
S. Deckers, F.H.P.M. Habraken, W.F. van	(2272) 222	acterization of the surface oxidation	
der Weg and J.W. Geus, Oxidation of		of austenitic Fe-26Mn-7Al-0.9C al-	
clean and Pt-covered Ni(111)	45 (1990) 207	loy	47 (1991) 311
W.G. Durrer, J.H. Craig, Jr. and J.		S. Hashimoto, XPS and AES studies on	
Lozano, Surface carbon and its effects	45 (4000) 455	the interface between metal and poly-	
on hydrogen adsorption on Rh(100)	45 (1990) 275	mer layers. The effect of Ar-plasma	
Xin Xu and J.I. Steinfeld, UV-laser pho- todeposition of iron films from		treatment of the polymer surface pre- ceding the metal deposition	47 (1991) 323
Fe(CO) <sub>5</sub> : role of gas-phase and surface		P.J. Godowski, Analysis of surface segre-	47 (1991) 323
dissociation processes	45 (1990) 281	gation in Co-Ru alloy using Auger	
S.C. Tjong, Self-passivation of Fe-Cr-	(1770) 201	electron spectroscopy	47 (1991) 333
PGM alloys in reducing acids studied		A.R. Balkenende, H. den Daas, M. Huis-	, , , , , , , , , , , , , , , , , , , ,
by electrochemical and electron spec-		man, O.L.J. Gijzeman and J.W. Geus,	
troscopic techniques	45 (1990) 301	The interaction of NO, O2 and CO	
E.J. Petit and R. Caudano, Chemical re-		with Cu(100) and Cu(110)	47 (1991) 341
actions at solid-solid interfaces in-		K. Nishimori, H. Tokutaka, H. Sumi and	
duced by pulsed laser annealing	46 (1990) 357	N. Ishihara, Interface reaction of Si	47 (1001) 0(5
J.C. Lascovich, R. Giorgi and S. Scagl-		thin film on Au substrate	47 (1991) 365
ione, Evaluation of the sp <sup>2</sup> /sp <sup>3</sup> ratio in amorphous carbon structure by XPS		A. Mowbray and R.G. Jones, Homo- and hetero-iodide thin film growth on	
and XAES	47 (1991) 17	InSb(001): low-temperature iodide	
S.J. Hoekje and G.B. Hoflund, Surface	47 (1221) 17	formation and epitaxial growth of	
characterization study of InP(100)		CdI <sub>2</sub>	48/49 (1991) 27
substrates using ISS, AES and ESCA:		S. Nagashima, E. Fukuchi and I. Ogura,	
comparison of substrates from two		Growth modes of overlayers of Se de-	
different commercial sources	47 (1991) 43	posited on Cu(111) surfaces	48/49 (1991) 44
M. Wolpers, H. Viefhaus and M. Strat-		S.S. Fu and G.A. Somorjai, Zinc oxide	
mann, Surface analytical investiga-		and oxygen overlayers on Cu(110): a	40 440 (4004) 00
tions of metal surfaces modified by	47 (1001) 40	model for Cu-Zn-O catalysts	48/49 (1991) 93
Langmuir-Blodgett films of silanes	47 (1991) 49	D.G. Frank, T. Golden, O.M.R. Chyan	
W.S. Lee, R.A. Outlaw, G.B. Hoflund and M.R. Davidson, Auger electron		and A.T. Hubbard, Direct imaging of thin film atomic structure by an-	
intensity variations in oxygen-charged		gular distribution Auger microscopy	
silver	47 (1991) 91	(ADAM)	48/49 (1991) 166
A.J. Pertsin and Yu.M. Pashunin, An XPS		H. Yumoto, K. Watanabe, K. Akashi and	, , , , , , , , , , , , , , , , , , , ,
study of the in-situ formation of the		N. Igata, The effect of electronic exci-	
polyimide/copper interface	47 (1991) 115	tation produced by an electron shower	
J. Eymery, C. Senillou, J.C. Joud and A.		on the adhesion of copper films de-	
Chamberod, An Auger depth profile		posited on stainless steel	48/49 (1991) 173
analysis of a sputtered Fe-Ti multi-	47 (1001) 127	S. Berger, Y. Komem and B.Z. Weiss, On	
layer structure W.A.M. Aarnink, D.H.A. Blank, D.J.	47 (1991) 127	the microstructure, composition and electrical properties of Al/TiW/poly-	
Adelerhof, J. Flokstra, H. Rogalla, A.		Si system	48/49 (1991) 281
van Silfhout and R. de Reus, Interdif-		P.K. Banerjee, J.S. Kim and S.S. Mitra,	10/ 17 (1771) 201
fusion studies on high- $T_c$ supercon-		Electrical and optical properties of a-	
ducting YBa2Cu3O7-8 thin films on		luminum-doped amorphous silicon	
Si(111) with a NiSi <sub>2</sub> /ZrO <sub>2</sub> buffer layer	47 (1991) 195	carbide films	48/49 (1991) 288
H.J. Grabke, D. Wiemer and H. Viefhaus,		A.K. Kulkarni and A.J. Canale, Electrical	
Segregation of sulfur during growth of	47 (1001) 2 12	and structural characterization of Co	40 /40 /1001 205
oxide scales	47 (1991) 243	and Ni silicide contacts to silicon	48/49 (1991) 307

M.L. Shek, T.K. Sham, J. Hrbek and G		Bismuth	
Q. Xu, A soft X-ray study of a Li-S surface compound  Zhang Rong, Zheng Youdou, Jiang Ruolian, Hu Liqun, Zhong Peixin, Yu Shidong, Li Qi, Feng Duan and Chen Guangxi, The structure of Ge <sub>x</sub> Si <sub>1-x</sub> /	48/49 (1991) 332	V.M. Browne, A.F. Carley, R.G. Copperthwaite, P.R. Davies, E.M. Moser and M.W. Roberts, Activation of carbon dioxide at bismuth, gold and	
Si strained layer superlattices and het- erostructures  I. Katayama, T. Hanawa, F. Shoji and K. Oura, ISS-AES study of the initial	48/49 (1991) 356	copper surfaces  D. Heskett, D. Tang, A.B. McLean, R. Ludeke, M. Prietsch, T. Maeda Wong, E.W. Plummer and N.J. DiNardo, Metal-induced states on the GaAs-	47 (1991) 375
growth stage of Cu thin films on $Si(111)-7 \times 7$ H. Tokutaka and S. Kishida, Surface characterization of Bi-based high- $T_c$ superconducting thin films and bulk	48/49 (1991) 361	<ul> <li>(110) surface probed by angle-resolved photoemission spectroscopy</li> <li>H. Tokutaka and S. Kishida, Surface characterization of Bi-based high-T<sub>c</sub> superconducting thin films and bulk</li> </ul>	48/49 (1991) 260
single crystals  P. Ossart and E.V.K. Rao, Investigation of surface and sub-surface defects on	48/49 (1991) 425	single crystals	48/49 (1991) 425
polished InP substrates using Auger electron spectroscopy coupled to argon		Borides	
ion sputtering  J.G. Bauer, R. Treichler, T. Hillmer, J.  Müller and G. Ebbinghaus, Optimization of Zn dopant profiles in a pin-di-	50 (1991) 125	J. Elders, D. Bebelaar and J.D.W. van Voorst, Photochemical vapor deposi- tion of titaniumdiboride	46 (1990) 215
ode/FET by combination of depth profiling techniques: a SIMS, ECV and AES study	50 (1991) 138	Boron	
Band structure	22 (2772) 200	F. Foulon, A. Slaoui and P. Siffert, ArF excimer laser doping of boron into silicon	43 (1989) 333
Bana structure		V.V. Tokarev, A.I. Demchenko, A.I.  Ivanov and V.E. Borisenko, Influence	
<ul> <li>H. Fujitani and S. Asano, Electronic structure of Si/disilicide interfaces</li> <li>P.J. van den Hoek and E.J. Baerends, Chemical bonding at metal-semicon-</li> </ul>	41/42 (1989) 164	of boron implantation on phase transformations in nickel silicides G. Stock, D. Bollmann, R. Buchner, G. Neumayer and K. Haberger, Ultra-flat	44 (1990) 241
ductor interfaces G. Vecris and J.J. Quinn, Novel diagrammatic method for analyzing the surface	41/42 (1989) 236	p-n junctions formed by solid source laser doping	46 (1990) 348
electronic modes of finite multilayer structures	48/49 (1991) 319	Cadmium	
M. Morsli, A. Bonnet, Y. Tregouet, A. Conan, S. Jobic and R. Brec, Electronic properties and band structure	50 (1001) 500	A. Mowbray and R.G. Jones, Homo- and hetero-iodide thin film growth on InSb(001): low-temperature iodide	
of IrSe <sub>2</sub>	50 (1991) 500	formation and epitaxial growth of CdI <sub>2</sub> G.N. Pain, T. Warminski, S. Sulcs, M.S.	48/49 (1991) 27
Benzene		Kwietniak, D. Gao, S.R. Glanvill, C.J. Rossouw, A.W. Stevenson, S.P. Russo, R.G. Elliman, L.S. Wielunski, R.S.	
<ul> <li>M. Buck and P. Hess, Ablation of benzene from van der Waals films with excimer laser pulses at 248 nm</li> <li>D.E. Ramaker, Evidence for vertical C<sub>2</sub></li> </ul>	43 (1989) 358	Rowe, G.B. Deacon, R.S. Dickson and B.O. West, Characterization of low-temperature MOCVD $Cd_{1-x}Mn_xTe$ thin films	48/49 (1991) 76
on Ni as a precursor for graphite nucleation	48/49 (1991) 351	W. Pfeiffer, M. Deicher, R. Keller, R. Magerle, P. Pross, H. Skudlik, Th.	

Wichert, H. Wolf, D. Forkel, N.		Cadmium telluride	
Moriya and R. Kalish, Characteriza- tion of Cd implanted and annealed GaAs and InP by perturbed angular correlation (PAC) spectroscopy	50 (1991) 154	B.A. Orlowski, J.P. Lacharme, C.A. Sébenne and S. Bensalah, Interface formation on n- and p-CdTe(110)	
A. Baurichter, M. Deicher, S. Deubler, D. Forkel, J. Meier, H. Wolf, W. Witthuhn and ISOLDE Collaboration, Mi-		surfaces with Cu and Au T.M. Razykov, Chemical molecular beam deposition of II-VI binary and ternary	41/42 (1989) 491
croscopical studies at cadmium impur- ities in compound semiconductors S.G. Jahn, H. Hofsäss, U. Wahl, S. Winter,	50 (1991) 165	Y. Hatanaka, Heterostructures with hydrogenated amorphous silicon for use	48/49 (1991) 89
E. Recknagel and ISOLDE Collabora- tion, Structural defect recovery in GaP	50 (1001) 1(0	in imaging devices R.B. Gore, R.K. Pandey and S.R. Kumar,	48/49 (1991) 457
after heavy ion implantation	50 (1991) 169	Preparation and characterisation of nearly stoichiometric CdTe films from a non-aqueous electrodeposition bath	48/49 (1991) 530
Cadmium selenide		J.H.C. Hogg, D. Shaw and D.M. Staudte, Modelling interdiffusion in epitaxial	
T.M. Razykov, Chemical molecular beam deposition of II-VI binary and ternary compound films in a gas flow	48/49 (1991) 89	multilayer structures using X-ray simulation techniques A.M. Keir, S.J. Barnett, J. Giess, T.D.	50 (1991) 87
Cadmium sulphide		Walsh and M.G. Astles, A combina- tion of high-resolution X-ray dif- fractometry and diffraction imaging	
D.W. Niles, M. Tang, J. McKinley, R.		techniques applied to the study of MOVPE-grown $Cd_xHg_{1-x}Te/CdTe$	
Zanoni and G. Margaritondo, From heterojunction interfaces to metal-	41 (42 (1000) 120	on GaAs  C. Levade, J.J. Couderc, G. Vander-schaeve, D. Caillard and A. Couret,	50 (1991) 103
semiconductor interfaces  A.J. Nelson, S. Gebhard, L.L. Kazmerski,  A. Rockett, E. Colavita, M. En-	41/42 (1989) 139	TEM in-situ observation of recombi- nation-enhanced mobility of disloca-	50 (1991) 119
gelhardt and H. Höchst, Soft X-ray photoemission investigation of the CdS/CuInSe <sub>2</sub> heterojunction inter-		tions in II-VI compounds  H. Chibani, J.P. Stoquert, M. Hage-Ali, J.M. Koebel, M. Abdesselam and P.	30 (1991) 119
face T. Nakamura, Y. Takeuchi, H. Mura-	48/49 (1991) 419	Siffert, Carbon analysis in CdTe by nuclear activation M. Hage-Ali, B. Yaacoub, S. Mergui, M.	50 (1991) 177
matsu, H. Fujiyasu and Y. Nakanishi, ESR studies on luminescent ZnS:Mn films and CdS-ZnS:Mn superlattices deposited on a GaAs(100) substrate		Samimi, B. Biglari and P. Siffert, Mi- croscopic defect level characterization of semi-insulating compound semicon-	
by hot-wall epitaxy C. Feldman, G. Deutscher and E. Grünbaum, Single-crystal transformation of	48/49 (1991) 478	ductors by TSC and PICTS. Applica- tion to the effect of hydrogen in CdTe D. Ashenford, J.H.C. Hogg, B. Lunn and	50 (1991) 377
sphalerite CdS to cubic phase Cu <sub>x</sub> S I.T. McGovern, Soft X-ray photoelectron	48/49 (1991) 535	C.G. Scott, The relationship between electrical and structural characteristics of CdTe and CdMnTe layers grown	
spectroscopy of compound semicon- ductor surfaces and interfaces R. Magerle, M. Deicher, U.V. Desnica, R.	50 (1991) 34	on InSb	50 (1991) 440
Keller, W. Pfeiffer, F. Pleiter, H. Skudlik and Th. Wichert, Defects in		Calcium	
CdS:In detected by perturbed angular correlation spectroscopy (PAC)  R. Fornari, N. Tchandjou, P. Gall and	50 (1991) 159	A.D. Gates and J.L. Robins, Nucleation of gold on Ca <sup>2+</sup> -doped NaCl	48/49 (1991) 154
J.M. Lussert, A study of structural properties of bulk double-doped InP		Carbides	
by laser scattering tomography and photoetching	50 (1991) 207	R. Teghil, A. Giardini-Guidoni, S. Pic- cirillo, A. Mele and F. Polla-Mattiot,	

In situ formation of ionic carbide clusters by laser ablation  P.K. Banerjee, J.S. Kim and S.S. Mitra,  Electrical and optical properties of a- luminum-doped amorphous silicon	46 (1990) 220	and M.W. Roberts, Activation of carbon dioxide at bismuth, gold and copper surfaces  R.W. Vook and B. Oral, Carbon monoxide oxidation on epitaxial Cu(111)/	47 (1991) 375
carbide films	48/49 (1991) 288	Pd(111) bilayers at atmospheric pressures	48/49 (1991) 125
Carbon, see also Graphite		Carbon monoxide	
<ul> <li>G. Compagnini, R. Reitano, L. Calcagno,</li> <li>G. Marletta and G. Foti, Hydrogenated amorphous carbon synthesis by ion beam irradiation</li> <li>M.J. van Staden and J.P. Roux, The superposition of carbon and ruthenium</li> </ul>	43 (1989) 228	B. Oral, Y.C. Lee and R.W. Vook, Thermal desorption spectroscopy investigation of CO adsorption on Cu/Pd(111) surfaces	44 (1990) 65
Auger spectra G. Ranga Rao and C.N.R. Rao, Adsorp-	44 (1990) 259	J.H. Craig, Jr. and J. Lozano, Effect of oxygen on chemisorption of CO on Rh(100)	45 (1990) 151
tion of nitrogen on clean and modified single-crystal Ni surfaces W.G. Durrer, J.H. Craig, Jr. and J. Lozano, Surface carbon and its effects	45 (1990) 65	J. Heidberg, B. Brase, KW. Stahmer and M. Suhren, Second harmonic genera- tion of CO <sub>2</sub> -laser radiation and FTIR	
on hydrogen adsorption on Rh(100)  V. Dupuis, M.F. Ravet, C. Tête and M. Piecuch, Thermal evolution of W/Si	45 (1990) 275	spectroscopy for resonant desorption in the adsorbate CO-NaCl(100) A.R. Balkenende, H. den Daas, M. Huis- man, O.L.J. Gijzeman and J.W. Geus,	46 (1990) 44
and W/C multilayers under pulsed laser heating and classical annealing J.J. Vajo and J.G. McCarty, Thermody- namics of carbon coadsorbed with	46 (1990) 398	The interaction of NO, O <sub>2</sub> and CO with Cu(100) and Cu(110)  R.W. Vook and B. Oral, Carbon monoxide oxidation on epitaxial Cu(111)/	47 (1991) 341
sulfur on Ni(100) E.J. Puik, M.J. van der Wiel, H. Zeijle- maker and J. Verhoeven, Ion etching of thin W layers: enhanced reflectivity	47 (1991) 23	Pd(111) bilayers at atmospheric pressures  D.E. Ramaker, Evidence for vertical C <sub>2</sub>	48/49 (1991) 125
of W-C multilayer coatings  E.J. Puik, M.J. van der Wiel, H. Zeijlemaker and J. Verhoeven, Ion bom-	47 (1991) 63	on Ni as a precursor for graphite nucleation	48/49 (1991) 351
bardment of X-ray multilayer coat- ings: comparison of ion etching and		Catalysis	
ion assisted deposition  A. Chevarier, N. Chevarier, M. El Bouanani, E. Gerlic, M. Stern, B. Roux and F. Thimon, Profiling of carbon, oxygen and argon contamination in sputter-deposited films using nuclear	47 (1991) 251	<ul> <li>P. Soukiassian, H.I. Starnberg and T. Kendelewicz, Insulator-semiconductor interface formation by electronic promotion using alkali metal and removal of the catalyst</li> <li>M. Bowker and D. Halstead, Adsorption</li> </ul>	41/42 (1989) 395
backscattering and nuclear reaction spectroscopy  D.E. Ramaker, Evidence for vertical C <sub>2</sub> on Ni as a precursor for graphite	48/49 (1991) 215	studies on catalysts. II. Application to rapid adsorbers – oxygen on Euro- platinum 1 W. Unger, G. Lietz, H. Lieske and J.	44 (1990) 1
nucleation H. Chibani, J.P. Stoquert, M. Hage-Ali, J.M. Koebel, M. Abdesselam and P.	48/49 (1991) 351	Völter, SIMS and FAB-MS surface studies of Pt-Sn/Al <sub>2</sub> O <sub>3</sub> and Pt <sub>3</sub> Pb model catalysts	45 (1990) 29
Siffert, Carbon analysis in CdTe by nuclear activation	50 (1991) 177	G. Moretti, S. De Rossi and G. Ferraris, Characterization of well dispersed copper species on the surface of ZnO	
Carbon dioxide		by X-ray photoelectron spectroscopy  D. Vassilakis, CM. Pradier, Y. Berthier	45 (1990) 341
V.M. Browne, A.F. Carley, R.G. Copperthwaite, P.R. Davies, E.M. Moser		and J. Oudar, Hydrogen, hydrogen sulfide and hydrocarbon coadsorption	

on Pt(111) and Pt(110): selective formation of alkylthiols	47 (1991) 273	stant: application to n-type ZnSe het- eroepitaxial thin films	50 (1991) 285
M. Muhler, Z. Paál and R. Schlögl, XPS of platinum in Pt/SiO <sub>2</sub> (Europt-1): possibilities and limitations of the	47 (1991) 281	A. Deneuville, C.H. Park, P. Ayyub, T. Anderson, P. Lowen, K. Jones and P.H. Holloway, O implantation in ZnSe: lattice distortion by Raman	
method  J.Ph. Nogier, J. Thoret, N. Jammul and J.  Fraissard, Phase distribution in Ti-	47 (1991) 287	measurement  J.F. Donegan, J.P. Doran, R.P. Stanley, J.  Hegarty, R.D. Feldman and R.F.	50 (1991) 308
V-O catalysts  A.R. Balkenende, H. den Daas, M. Huisman, O.L.J. Gijzeman and J.W. Geus, The interaction of NO, O <sub>2</sub> and CO	47 (1991) 287	Austin, Resonant Rayleigh scattering from excitons in $Cd_xZn_{1-x}Te:ZnTe$ quantum wells: measurement of ho-	
with Cu(100) and Cu(110)  S.S. Fu and G.A. Somorjai, Zinc oxide and oxygen overlayers on Cu(110): a	47 (1991) 341	mogeneous linewidths  B. Mari, A. Segura and A. Chevy, Electrical properties of neutron-transmuta-	50 (1991) 321
model for Cu-Zn-O catalysts  R.W. Vook and B. Oral, Carbon mono- xide oxidation on epitaxial Cu(111)/	48/49 (1991) 93	tion-doped InSe M. Morsli, A. Bonnet, Y. Tregouet, A. Conan, S. Jobic and R. Brec, Elec-	50 (1991) 415
Pd(111) bilayers at atmospheric pressures H.H. Madden and R. Imbihl, Interaction	48/49 (1991) 125	tronic properties and band structure of IrSe <sub>2</sub>	50 (1991) 500
of NO and H <sub>2</sub> with Pt(100) T. Zhang and S.Y. Wei, Hydrogen chem-	48/49 (1991) 130	Chemical vapour deposition	
isorption on contaminated composite catalysts	48/49 (1991) 139		
Cathodes		K. Inoue, M. Okuyama and Y. Hamaka- wa, Optical and interfacial properties of SiO <sub>2</sub> films deposited on Si by	
A. Sil, N.K. Samria and D.S. Venkates- warlu, Thermal analysis of a cathode: temperature distribution and warm-up time	45 (1990) 229	photo-CVD  S. Fujieda, K. Akimoto, I. Hirosawa, Y. Mochizuki, J. Mizuki, Y. Matsumoto and J. Matsui, Electrical properties and structures of the MOCVD-	41/42 (1989) 407
Ceramics		AlN/GaAs interface JS. Ma, H. Kawarada, T. Yonehara, JI. Suzuki, J. Wei, Y. Yokota, H. Mori, H. Fujita and A. Hiraki, Interfacial	41/42 (1989) 516
L.V. Interrante, B. Han, J.B. Hudson and C. Whitmarsh, Design and synthesis of CVD precursors to thin film ceramic materials	46 (1990) 5	structures and selective growth of dia- mond particles formed by plasma-as- sisted CVD	41/42 (1989) 572
J.C. Fariñas and M.F. Barba, Inductively coupled plasma-atomic emission spectrometry (ICP-AES): an analyti-		M. Okuyama, N. Fujiki, Y. Nakatani, K. Inoue and Y. Hamakawa, Growth be- havior of highly oriented Si films on	
cal technique for the chemical char- acterization of perovskite ceramic semiconductors	50 (1991) 202	fused quartz by photo-CVD  H. Kumomi, T. Yonehara, Y. Nishigaki and N. Sato, Selective nucleation based epitaxy (Sentaxy). Investigation	41/42 (1989) 633
Chalcogenides		of initial nucleation stages G.S. Higashi, The chemistry of alkyl-aluminum compounds during laser-as-	41/42 (1989) 638
E.E. Marinero, Material transformations in semiconductor and magnetic thin films	43 (1989) 117	sisted chemical vapor deposition  R. Nowak, P. Hess, H. Oetzmann and C. Schmidt, XPS characterization of	43 (1989) 6
A. Deneuville, D.B. Tanner, R.M. Park and P.H. Holloway, Semiconductor electrical properties from the frequen- cy dependence of the dielectric con-	43 (1989) 117	chromium films deposited from Cr(CO) <sub>6</sub> at 248 nm  E. Boch, C. Fuchs, E. Fogarassy and P. Siffert, Influence of dilution in nitro-	43 (1989) 11

tion G. Wahl and H. Esrom, Simulation of laser CVD	46 (1990) 53 46 (1990) 96	deposition of II-VI binary and ternary compound films in a gas flow I.K. Han, Y.J. Lee, J.W. Jo, J.I. Lee and	48/49 (1991) 89
and G. Wahl, High- $T_c$ YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-<math>\delta</math></sub> prepared by chemical vapour deposi-		tem T.M. Razykov, Chemical molecular beam	46 (1990) 245
<ul> <li>J. Simpson and J.O. Williams, Preferential (111) orientation of ZnSe on (100) GaAs deposited by laser-induced MOCVD</li> <li>F. Schmaderer, R. Huber, H. Oetzmann</li> </ul>	46 (1990) 27	erties  M. Zeman, I. Ferreira, M.J. Geerts and J.W. Metselaar, The influence of de- position parameters on the growth of a-SiGe:H alloys in a plasma CVD sys-	46 (1990) 233
laser beam diameter  R. Larciprete, Photoprocesses in organometallics	46 (1990) 9 46 (1990) 19	Schmidt, Laser CVD of a-Si:H from SiH <sub>4</sub> and Si <sub>2</sub> H <sub>6</sub> : relations between chemistry, growth rate and film prop-	46 (2005) 200
Bergh, The photolytic laser chemical vapor deposition rate of platinum, its dependence on wavelength, precursor vapor pressure, light intensity, and		<ul> <li>H. Stafast, On the role of the substrate position in the CO<sub>2</sub> laser CVD of amorphous hydrogenated silicon</li> <li>K. Hesch, P. Hess, H. Oetzmann and C.</li> </ul>	46 (1990) 230
<ul><li>C. Whitmarsh, Design and synthesis of CVD precursors to thin film ceramic materials</li><li>D. Braichotte, C. Garrido and H. van den</li></ul>	46 (1990) 5	<ul> <li>J. Elders, D. Bebelaar and J.D.W. van Voorst, Photochemical vapor deposi- tion of titaniumdiboride</li> <li>E. Golusda, R. Lange, G. Mollekopf and</li> </ul>	46 (1990) 215
<ul><li>D.C. Bradley, New metallo-organic precursors for surface processing</li><li>L.V. Interrante, B. Han, J.B. Hudson and</li></ul>	46 (1990) 1	H. Sigmund, Excimer laser deposition of silica films: a comparison between two methods	46 (1990) 210
Xin Xu and J.I. Steinfeld, UV-laser pho- todeposition of iron films from Fe(CO) <sub>5</sub> : role of gas-phase and surface dissociation processes	45 (1990) 281	<ul> <li>J. Pou, B. León and M. Pérez-Amor,</li> <li>Gas mixture dependence of the LCVD of SiO<sub>2</sub> films using an ArF laser</li> <li>B. León, A. Klumpp, M. Pérez-Amor and</li> </ul>	46 (1990) 206
Malikov, A.A. Chumakov and L.A. Niselson, Chemical vapour deposition of tungsten layers at low substrate temperatures	45 (1990) 257	<ul> <li>blanc and J. Perrin, SiO<sub>2</sub> deposition</li> <li>by direct photolysis at 185 nm of N<sub>2</sub>O</li> <li>and SiH<sub>4</sub></li> <li>T. Szörényi, P. González, D. Fernández,</li> </ul>	46 (1990) 189
Baker and P.A. Robertson, Photoen- hanced CVD of hydrogenated amor- phous silicon using an internal hydro- gen discharge lamp S.Yu. Shapoval, O.E. Balvinskii, I.V.	43 (1989) 277	Lebland, C. Licoppe and M. Bensoussan, Photo-assisted deposition of thin films on III-V semiconductors with UV and IR lamps M. Petitjean, N. Proust, JF. Chapeau-	46 (1990) 175
ural changes in laser CVD of silicon: comparison of theoretical temperature calculations with experimental results W.I. Milne, F.J. Clough, S.C. Deane, S.D.	43 (1989) 81	Y. Horiike, T. Ichihara and H. Sakaue, Filling of Si oxide into a deep trench using digital CVD method Y.I. Nissim, J.M. Moison, F. Houzay, F.	46 (1990) 168
<ul> <li>C. Garrido, D. Braichotte, H. van den Bergh, B. León and M. Pérez-Amor, Interconnection lines of Pt induced by laser direct writing</li> <li>D. Milne, J.I.B. Wilson, T.T. Rantala and J. Lenkkeri, Morphological and struct-</li> </ul>	43 (1989) 68	Optimization of the laser-induced de- position technique for its application in X-ray mask repair  A.J.P. van Maaren, R.L. Krans and W.C. Sinke, HF formation in laser-induced CVD of tungsten	46 (1990) 131 46 (1990) 138
G. Auvert, Kinetics and mechanisms of CW laser induced deposition of metals for microelectronics	43 (1989) 47	ble pulse laser induced ablation and CVD  R. Putzar, HC. Petzold and H. Staiger,	46 (1990) 108
of silane and disilane at 193 nm  E. Marclay, D.J. Webb, P. Buchmann and P. Vettiger, Broadband low-reflectivity coating for semiconductor power lasers by ion-beam and PECVD deposition	43 (1989) 17 43 (1989) 43	Gas-phase transport and kinetics in pulsed-laser CVD  Y. Morishige, S. Kitamura and S. Kishida, High performance contact formation in LSI circuit restructuring using visi-	46 (1990) 102
gen on the photodissociation processes	40 (4000) 40	L. Konstantinov, R. Nowak and P. Hess,	

K.N. Kang, Growth and characterization of silicon-nitride films by plasmaenhanced chemical vapor deposition  Zhang Rong, Zheng Youdou, Jiang Ruolian, Hu Liqun, Zhong Peixin, Yu Shidong, Li Qi, Feng Duan and Chen Guangxi, The structure of Ge <sub>x</sub> Si <sub>1-x</sub> /Si etasized layer suppolations and hot	48/49 (1991) 104	<ul> <li>L. Konstantinov, R. Nowak and P. Hess, Gas-phase transport and kinetics in pulsed-laser CVD</li> <li>Y. Fukuda and M. Nagoshi, Chemisorption of hydrogen on Cr(111) studied by XPS, UPS, and HREELS</li> </ul>	46 (1990) 102 48/49 (1991) 147
Si strained layer superlattices and het- erostructures	48/49 (1991) 356	Clusters	
M. Arienzo, S.S. Iyer, B.S. Meyerson, G.L. Patton and J.M.C. Stork, Si-Ge alloys: growth, properties and applications	48/49 (1991) 377	I. Yamada, Growth processes of epitaxial metal films on semiconductor and in- sulator substrates by ionized cluster	
T. Wadayama, T. Hihara, A. Hatta and	, , , , , , , , , , , , , , , , , , , ,	•	42 (1090) 22
W. Suëtaka, In situ IR observation of photo-chemically deposited silicon		k. Fukushima and I. Yamada, Surface smoothness and crystalline structure	43 (1989) 23
nitride thin films C.T. Foxon, Control of MBE, MOMBE	48/49 (1991) 409	of ICB deposited TiO <sub>2</sub> films  A. Yahashi, L.L. Levenson, H. Usui and	43 (1989) 32
and CBE growth using RHEED  Chemisorption theory	50 (1991) 28	I. Yamada, The structure zone model applied to ionized cluster beam films: Al on SiO <sub>2</sub>	43 (1989) 37
Chemisorpiion ineory		B. Lecohier and H. van den Bergh, Selec- tive copper film growth on platinum	
T. Zhang and S.Y. Wei, Hydrogen chem- isorption on contaminated composite catalysts	48/49 (1991) 139	clusters  A. Mele, D. Consalvo, D. Stranges, A. Giardini-Guidoni and R. Teghil, Cluster ion formation by laser evaporation	43 (1989) 61
		of solid complex oxides	43 (1989) 398
Chromium		P. Ptáček and Z. Bastl, XPS characteriza-	, , , , ,
		tion of supported bimetallic pal-	
R. Nowak, P. Hess, H. Oetzmann and C. Schmidt, XPS characterization of		ladium-silver clusters  R. Teghil, A. Giardini-Guidoni, S. Pic-	45 (1990) 319
chromium films deposited from		cirillo, A. Mele and F. Polla-Mattiot,	
Cr(CO) <sub>6</sub> at 248 nm	43 (1989) 11	In situ formation of ionic carbide clus-	46 (1000) 220
S.C. Tjong, Electrochemical and surface analysis of the Fe-Cr-Ru system in		ters by laser ablation	46 (1990) 220
non-oxidizing acid solutions S.C. Tjong and J.B. Malherbe, Auger	44 (1990) 7	Coatings	
studies of the effect of Mo, V and Pd additions on the oxidation characteris-		E. Marclay, D.J. Webb, P. Buchmann and	
tics of Fe-24Cr alloy	44 (1990) 179	P. Vettiger, Broadband low-reflectivity	
M.J. van Staden and J.P. Roux, The con- trolled oxidation of the high chro-		coating for semiconductor power lasers by ion-beam and PECVD deposition	43 (1989) 43
mium steel alloys Fe40Cr and		C. Neelmeijer, P. Knothe, M. Posselt, E.	(2,2,7)
Fe40Cr3Ru S.C. Tjong, A surface study of the passi-	44 (1990) 263	Richter and KH. Heinig, Wear re-	
vation of Fe-Cr-Co magnet alloys in		sistant coatings produced by C <sup>+</sup> implantation	43 (1989) 232
sulphuric acid solution	45 (1990) 141	M. Wolpers, H. Viefhaus and M. Strat-	(
J.C. Ingram, K.W. Nebesny and J.E. Pemberton, Optical properties of		mann, Surface analytical investiga- tions of metal surfaces modified by	
selected first-row transition metals de-		Langmuir-Blodgett films of silanes	47 (1991) 49
termined by reflection electron energy		B. Heens, Ch. Grégoire, J.J. Pireaux, P.A.	``
loss spectroscopy S.C. Tjong, Self-passivation of Fe-Cr-	45 (1990) 247	Cornelio and J.A. Gardella, Jr., On the stability and homogeneity of	
PGM alloys in reducing acids studied		Langmuir-Blodgett films as models of	
by electrochemical and electron spec-		polymers and biological materials for	
troscopic techniques	45 (1990) 301	surface studies: an XPS study	47 (1991) 163

43 (1989) 218

## Cobalt

Cobalt		T. Wada, M. Takeda, T. Yamada and M. Ichimura, Formation of a Ge <sub>x</sub> Si <sub>1-x</sub>	
V.V. Tokarev, A.V. Kibardin, T.M. Pyatkova and D.I. Zarovsky, Nickel,		alloy layer by high-energy electron- beam irradiation	41/42 (1989) 580
cobalt and iron silicide formation stimulated by argon implantation	44 (1990) 235	A. Golanski, Ion beam synthesis of buried compound layers: accomplishments	42 (1000) 200
S.C. Tjong, A surface study of the passi- vation of Fe-Cr-Co magnet alloys in		and perspectives F. Hanus and M. Wautelet, Time-re-	43 (1989) 200
sulphuric acid solution P.J. Godowski, Analysis of surface segre-	45 (1990) 141	solved temperature measurements dur- ing laser-induced synthesis of Cu-Te	
gation in Co-Ru alloy using Auger	47 (1991) 333	compounds V. Craciun, G. Leggieri, A. Luches, M.	43 (1989) 271
electron spectroscopy A.K. Kulkarni and A.J. Canale, Electrical	47 (1991) 333	Martino, I.N. Mihailescu and I. Ursu, Synthesis of metallic and semiconduc-	
and structural characterization of Co and Ni silicide contacts to silicon	48/49 (1991) 307	tor nitrides by multipulse laser irradia- tion of solid samples in ambient gases	43 (1989) 304
Compound formation		F. Abel, C. Cohen, J.A. Davies, J. Moulin and D. Schmaus, Thin-film growth of	43 (1707) 304
M. Iwami, M. Kusaka, M. Hirai, M.		Sn on Cu(100)	44 (1990) 17
Kubota, H. Tochihara and Y. Murata,		F. Richter, E. Bugiel, R. Grötzschel, H. Reichardt, A. Schöpke, E. Wieser and	
Mechanism of alloy formation due to noble metal deposition on silicon		F. Wolf, Formation of titanium di-	
surfaces at room temperature: chem-	41 /42 /1090) 07	silicide using different annealing methods	44 (1990) 127
ical bonding model M. Murakami, H.J. Kim, YC. Shih, W.H.	41/42 (1989) 97	V.V. Tokarev, A.I. Demchenko, A.I. Ivanov and V.E. Borisenko, Influence	
Price and C.C. Parks, Effects of inter- facial microstructure on ohmic con-		of boron implantation on phase trans-	44 (4000) 244
tacts to GaAs	41/42 (1989) 195	formations in nickel silicides E.J. Petit and R. Caudano, Chemical re-	44 (1990) 241
R. Sporken, P.A. Thiry, P. Xhonneux, R. Caudano and J.P. Delrue, Spectro-		actions at solid-solid interfaces in- duced by pulsed laser annealing	46 (1990) 357
scopic study of metal/semimetal and metal/semiconductor interfaces	41/42 (1989) 201	D. Vassilakis, CM. Pradier, Y. Berthier	(1//0) 00 /
M. Renda and K. Morita, Epitaxial growth of a mono-crystalline metasta-	12/ 12 (2/02) 202	and J. Oudar, Hydrogen, hydrogen sulfide and hydrocarbon coadsorption	
ble AuIn layer at the Au/InP(001)		on Pt(111) and Pt(110): selective formation of alkylthiols	47 (1991) 273
interface J. Falta, M. Horn and M. Henzler, SPA-	41/42 (1989) 216	K. Nishimori, H. Tokutaka, H. Sumi and	., (,
LEED studies of defects in thin epi-	41 (42 (1090) 220	N. Ishihara, Interface reaction of Si thin film on Au substrate	47 (1991) 365
taxial NiSi <sub>2</sub> layers on Si(111) N. Fujimura and T. Ito, TiSi <sub>2</sub> formation	41/42 (1989) 230	A. Mowbray and R.G. Jones, Homo- and hetero-iodide thin film growth on	
at the Ti-rich TiN <sub>x</sub> /Si interface K. Suguro, Y. Nakasaki, T. Yoshii and T.	41/42 (1989) 272	InSb(001): low-temperature iodide	
Itoh, Barrier metal between tungsten		formation and epitaxial growth of CdI <sub>2</sub>	48/49 (1991) 27
and silicon for high temperature processing	41/42 (1989) 277	S. Nagashima, E. Fukuchi and I. Ogura, Growth modes of overlayers of Se de-	
Y. Igarashi, T. Yamaji, S. Nishikawa and S. Ohno, Influence of annealing am-		posited on Cu(111) surfaces	48/49 (1991) 44
bients on ZrSi <sub>2</sub> formation	41/42 (1989) 282	C.H. Champness and W.R. Clark, Anomalous inductive effect in Se-metal	
Y. Kawadzu, M. Iioka, A. Fujii, H. Oyanagi and T. Arai, Interfacial reac-		contacts	48/49 (1991) 337
tion of nickel/hydrogenated amor- phous silicon system at low tempera-		Conductivity	
ture studied by fluorescence EXAFS  T. Ito, A. Yamama, A. Hiraki and M.	41/42 (1989) 296		
Satou, Silicidation of porous silicon		J. Davenas, Influence of the temperature	
and its application for the fabrication	41 /42 (1989) 301	on the ion beam induced conductivity	43 (1989) 218

41/42 (1989) 301

of polyimide

of a buried metal layer

S. Kuniyoshi, K. Kudo and K. Tanaka, Surface modification of low density		gation of CO adsorption on Cu/Pd(111) surfaces	44 (1990) 65
polyethylene by N <sup>+</sup> , Ar <sup>+</sup> ion implan- tation for space charge devices	43 (1989) 447	J.A. Kelber, J.W. Rogers, Jr., B.A. Banse and B.E. Koel, Interaction of dimeth- ylamine with clean and partially	44 (4000) 400
Contacts		oxidized copper surfaces  K. Prabhakaran and C.N.R. Rao, Adsorption of carbonyl compounds on	44 (1990) 193
M. Murakami, H.J. Kim, YC. Shih, W.H. Price and C.C. Parks, Effects of inter- facial microstructure on ohmic con- tacts to GaAs	41/42 (1989) 195	clean and modified Cu(110) surfaces: a combined EELS-UPS study <sup>a</sup> J.C. Ingram, K.W. Nebesny and J.E. Pemberton, Optical constants of the	44 (1990) 205
Y. Morishige, S. Kitamura and S. Kishida, High performance contact formation in LSI circuit restructuring using visi- ble pulse laser induced ablation and	41/ 42 (1909) 193	noble metals determined by reflection electron energy loss spectroscopy S. Yoshida, H. Ishida and J.S. Jen, X-ray photoelectron spectroscopic and X-ray	44 (1990) 293
CVD A.F. Bernhardt, A.T. Barfknecht, R.J.	46 (1990) 108	diffractometric characterization of al- kylimidazole films on copper oxide and alkylimidazolato copper(II) com-	
Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems	46 (1990) 121	plexes G. Moretti, S. De Rossi and G. Ferraris, Characterization of well dispersed copper species on the surface of ZnO	44 (1990) 301
P.C. Karulkar, R.J. Hillard, J.M. Heddle- son and P. Rai-Choudhury, A pres-		by X-ray photoelectron spectroscopy G. Wahl and H. Esrom, Simulation of	45 (1990) 341
sure contact current-voltage tech- nique for rapid characterization of thin dielectric films	48/49 (1991) 237	laser CVD H.G. Müller, K. Buschick, S. Schuler and A. Paredes, Laser direct writing of copper on various thin-film substrate	46 (1990) 96
C		materials	46 (1990) 143
Copper		M. Bode, E.W. Kreutz and M. Krösche, Direct writing of conducting traces by	10 (1220) 113
P. Hoffmann, B. Lecohier, S. Goldoni and H. van den Bergh, Fast laser writ- ing of copper and iridium lines from		<ul><li>chemical modification of solid coatings with laser radiation</li><li>D. Ballutaud, P. de Mierry, M. Aucoutu-</li></ul>	46 (1990) 148
thin solid surface layers of metalor- ganic compounds  B. Lecohier and H. van den Bergh, Selec- tive copper film growth on platinum	43 (1989) 54	rier and E. Darque-Ceretti, Influence of thermal treatments on the distribu- tion of contaminating copper near the surface of silicon: a comparative SIMS	
clusters  D.C. Kothari and A. Miotello, Effects on the implanted profiles of point defect	43 (1989) 61	and XPS study  A.J. Pertsin and Yu.M. Pashunin, An XPS study of the in-situ formation of the	47 (1991) 1
flux during nitrogen implantation in copper  J. van Zwol, S.T. de Zwart, C.C.A. Busquet and J. Dieleman, Resputter-	43 (1989) 237	polyimide/copper interface  A.R. Balkenende, H. den Daas, M. Huisman, O.L.J. Gijzeman and J.W. Geus,  The interaction of NO, O <sub>2</sub> and CO	47 (1991) 115
ing of low-energy implanted inert gases: an angle-resolved time-of-flight study	43 (1989) 363	with Cu(100) and Cu(110)  V.M. Browne, A.F. Carley, R.G. Copperthwaite, P.R. Davies, E.M. Moser	47 (1991) 341
T.S. Baller and J. Dieleman, Nanosecond excimer laser-enhanced chemical etch-		and M.W. Roberts, Activation of carbon dioxide at bismuth, gold and	
ing F. Abel, C. Cohen, J.A. Davies, J. Moulin and D. Schmaus, Thin-film growth of	43 (1989) 409	copper surfaces  S. Nagashima, E. Fukuchi and I. Ogura, Growth modes of overlayers of Se de-	47 (1991) 375
Sn on Cu(100)  B. Oral, Y.C. Lee and R.W. Vook, Thermal desorption spectroscopy investi-	44 (1990) 17	posited on Cu(111) surfaces K. Kalki, B. Pennemann, U. Schröder, W. Heichler and K. Wandelt, Properties	48/49 (1991) 44

	,		
of noble metal and binary alloy mono- layer films on Ru(001) S.S. Fu and G.A. Somorjai, Zinc oxide and oxygen overlayers on Cu(110): a	48/49 (1991) 59	<ul> <li>amorphous silicon: triggering and propagation</li> <li>O. Bostanjoglo and P. Thomsen-Schmidt, Laser-induced multiple phase transi-</li> </ul>	43 (1989) 128
model for Cu-Zn-O catalysts  R.W. Vook and B. Oral, Carbon mono- xide oxidation on epitaxial Cu(111)/ Pd(111) bilayers at atmospheric pres-	48/49 (1991) 93	tions in Ge-Te films traced by time- resolved TEM  E.L. Mathé, J.G. Maillou, A. Naudon, E. Fogarassy, M. Elliq and S. de Un-	43 (1989) 136
w. Li, JS. Lin, M. Karimi, C. Moses and G. Vidali, Structural characterization of ultra-thin metal overlayers on	48/49 (1991) 125	amuno, Excimer laser recrystallization of amorphous Si films characterized by grazing X-ray diffraction and opti- cal reflectivity	43 (1989) 142
Cu(001) by atom beam scattering H. Yumoto, K. Watanabe, K. Akashi and N. Igata, The effect of electronic exci- tation produced by an electron shower on the adhesion of copper films de-	48/49 (1991) 160	J.G. Maillou, E.L. Mathé, J.C. Desoyer, S. de Unamuno and E. Fogarassy, Comparison between microscopical aspects of a-Si films crystallized by pulsed UV excimer laser and calcu-	
posited on stainless steel  A. Chevarier, N. Chevarier, M. El Bouanani, E. Gerlic, M. Stern, B. Roux and F. Thimon, Profiling of carbon,	48/49 (1991) 173	lated temperature profiles  J. Marfaing, W. Marine, R. Pierrisnard and A. Cros, Structural changes in Au <sub>x</sub> Si <sub>1-x</sub> alloy films under laser	43 (1989) 150
oxygen and argon contamination in sputter-deposited films using nuclear backscattering and nuclear reaction		irradiation  F. Priolo, C. Spinella, A. La Ferla, E. Rimini and G. Ferla, Ion-assisted re-	43 (1989) 165
spectroscopy  I. Katayama, T. Hanawa, F. Shoji and K.  Oura, ISS-AES study of the initial growth stage of Cu thin films on	48/49 (1991) 215	crystallization of amorphous silicon  C. Spinella, S. Lombardo and S.U.  Campisano, Amorphous to polycrystal  transition in ion irradiated chemical	43 (1989) 178
Si(111)-7 $\times$ 7	48/49 (1991) 361	vapor deposited amorphous silicon S.P. Withrow, O.W. Holland and S.J.	43 (1989) 187
Corrosion		Pennycook, Ion beam annealing of Ga-implanted Si M. Voelskow, W. Skorupa, K. Woll-	43 (1989) 191
S.C. Tjong, Electrochemical and surface analysis of the Fe-Cr-Ru system in non-oxidizing acid solutions	44 (1990) 7	schlaeger, J. Matthaei, P. Knothe, K H. Heinig and H. Bartsch, Epitaxial lateral overgrowth of amorphous CVD	
S.C. Tjong, A surface study of the passi- vation of Fe-Cr-Co magnet alloys in sulphuric acid solution	45 (1990) 141	silicon films induced by ion irradia- tion  M. Wagner, A. Witzmann, H.D. Geiler	43 (1989) 196
P. Bhardwaj, O.J. Gregory, K. Bragga and M.H. Richman, Sputtered TiN thin films for improved corrosion resis-		and KH. Heinig, Formation of p-n junctions and silicides in silicon using a high performance laser beam homo-	
tance	48/49 (1991) 555	genization system M. Elliq, E. Fogarassy, J.P. Stoquert, C.	43 (1989) 260
Crystallization		Fuchs, S. de Unamuno, B. Prévot and H. Pattyn, Pulsed excimer and Nd:YAG laser crystallization of a-	
F. Priolo, A. La Ferla, C. Spinella, E. Rimini, S.U. Campisano and G. Ferla, Crystal-amorphous-silicon interface kinetics under ion beam irradiation	41/42 (1989) 619	<ul> <li>Si:H. The specific role of hydrogen</li> <li>B. Hu, A. Seidl, R. Buchner, D. Bollmann, W. van der Wel and K. Haberger, Investigation of laser recrys-</li> </ul>	46 (1990) 378
E.E. Marinero, Material transformations in semiconductor and magnetic thin films	43 (1989) 117	tallization of thin Si films using numerical simulation  K. Kolev, M. Wautelet and L.D. Laude,	46 (1990) 388
W.C. Sinke, A. Polman, S. Roorda and P.A. Stolk, Explosive crystallization of	(2,02) ***	CW laser-induced transformation of thin Sb, Se and Sb <sub>2</sub> Se <sub>3</sub> films in air	46 (1990) 418

J. Marfaing, W. Marine, B. Vidal, M. Toulemonde, M. Hage Ali and J.P. Stoquert, Instability and structural		fusion constants by means of electron energy loss spectroscopy Y. Kamiura, F. Hashimoto and M. Iwami,	41/42 (1989) 306
transformation of amorphous ultra- thin W-Si multilayer structures dur- ing heavy ion irradiation	46 (1990) 422	Iron accumulation at the Si-SiO <sub>2</sub> interface and possible reduction of SiO <sub>2</sub> C.O. de González and E.A. García, De-	41/42 (1989) 447
LU.A. Andersen and J. Bøttiger, Crystallization of Fe-Zr metallic glasses during ion irradiation	46 (1990) 427	termination of the diffusion coeffi- cients of oxygen in zirconium by means of XPS  A. Bukaluk and W. Bała, AES depth pro-	44 (1990) 211
Cyclotron resonance studies		file studies of interdiffusion in thin polycrystalline Au-Ag multilayer films	45 (1990) 57
G. Strasser, S. Dubois, M. Besson, E.		L. Konstantinov, R. Nowak and P. Hess,	()
Gornik, G. Weimann, E. Bauser and H. Riechert, Analysis of impurity dis- tribution in n-GaAs layers by photo-		Gas-phase transport and kinetics in pulsed-laser CVD G. Stock, D. Bollmann, R. Buchner, G.	46 (1990) 102
conductivity and cyclotron resonance measurements	50 (1991) 261	Neumayer and K. Haberger, Ultra-flat p-n junctions formed by solid source laser doping	46 (1990) 348
Deuterium		R. Serna, C.N. Afonso, F. Catalina, N. Teixeira, M.F. da Silva and J.C. Soares, Diffusion and microstructures	40 (1770) 340
XL. Zhou, C. Yoon and J.M. White, Interactions of PF <sub>3</sub> and PD <sub>3</sub> with clean, P-covered and H(D)-covered (100)-	44 (1990) 103	induced by excimer laser irradiation in Ge-Sb thin film bilayers W.A.M. Aarnink, D.H.A. Blank, D.J. Adelerhof, J. Flokstra, H. Rogalla, A.	46 (1990) 405
oriented W foil  E. Nowicka, Z. Wolfram and R. Duś, Deuterium adsorption on thin nickel films	45 (1990) 13	van Silfhout and R. de Reus, Interdif- fusion studies on high- $T_c$ supercon- ducting YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-<math>\delta</math></sub> thin films on	
Diamond		Si(111) with a NiSi <sub>2</sub> /ZrO <sub>2</sub> buffer layer S. Berger, Y. Komem and B.Z. Weiss, On the microstructure, composition and	47 (1991) 195
JS. Ma, H. Kawarada, T. Yonehara, JI. Suzuki, J. Wei, Y. Yokota, H. Mori,		electrical properties of Al/TiW/poly- Si system  J.H.C. Hogg, D. Shaw and D.M. Staudte,	48/49 (1991) 281
H. Fujita and A. Hiraki, Interfacial structures and selective growth of dia- mond particles formed by plasma-as- sisted CVD	41/42 (1989) 572	Modelling interdiffusion in epitaxial multilayer structures using X-ray simulation techniques  J.G. Bauer, R. Treichler, T. Hillmer, J.	50 (1991) 87
E.B.D. Bourdon and R.H. Prince, Growth mechanisms of diamond-like films formed by laser ablation of graphite	48/49 (1991) 50	Müller and G. Ebbinghaus, Optimiza- tion of Zn dopant profiles in a pin-di- ode/FET by combination of depth	
A. Mansour, G. Indlekofer and P. Oelha- fen, Investigation of the electronic structure of thin diamond films by		profiling techniques: a SIMS, ECV and AES study R. Magerle, M. Deicher, U.V. Desnica, R.	50 (1991) 138
photoelectron spectroscopy  Diffusion	48/49 (1991) 312	Keller, W. Pfeiffer, F. Pleiter, H. Skudlik and Th. Wichert, Defects in CdS:In detected by perturbed angular	50 (1001) 150
K. Suguro, Y. Nakasaki, T. Yoshii and T.		correlation spectroscopy (PAC) S.J.C.H.M. van Gisbergen, M. Godlewski, T. Gregorkiewicz and C.A.J. Am-	50 (1991) 159
Itoh, Barrier metal between tungsten and silicon for high temperature processing	41/42 (1989) 277	merlaan, Interstitial Mn as a new donor in GaP and GaAs: an EPR study	50 (1991) 273
A. Förster, J.M. Layet and H. Lüth, Evaluation of dopant profiles and dif-		HG. Hettwer, W. Lerch, B. Lentfort, N.A. Stolwijk and H. Mehrer, Com-	

bined application of spreading-resistance and electron-microprobe depth profiling on GaAs:Zn and Si:P	50 (1991) 470	Neumayer and K. Haberger, Ultra-flat p-n junctions formed by solid source laser doping A.D. Gates and J.L. Robins, Nucleation	46 (1990) 348
Doping effects		of gold on Ca <sup>2+</sup> -doped NaCl  J. Matsui, Study of strain variation in  LEC-grown GaAs bulk crystals by	48/49 (1991) 154
<ul> <li>A. Förster, J.M. Layet and H. Lüth, Evaluation of dopant profiles and dif- fusion constants by means of electron energy loss spectroscopy</li> <li>S. Goto, H. Kakibayashi, M. Kawata and</li> </ul>	41/42 (1989) 306	synchrotron radiation X-ray topogra- phy C. Grattepain and A.M. Huber, Sec- ondary ion mass spectrometry of dopants and impurities in compound	50 (1991) 1
T. Usagawa, Evaluation of disordering at low doping concentration in selectively Si-doped Al <sub>0.3</sub> Ga <sub>0.7</sub> As/GaAs heterointerfaces  R. M'Ghaieth, R. Gauthier and P. Pinard,	41/42 (1989) 480	semiconductors: depth profiling of homo- and heterostructure H. L'Haridon, P.N. Favennec, R. Coquille, M. Salvi, M. Gauneau, Y. Le Guillou, R. Callec and P. Gall, Spatial	50 (1991) 42
Structure and defects induced by elec- tron beam irradiation in silicon sub- strates and EPR ribbons	43 (1989) 111	investigation of an iron-doped indium phosphide ingot T. Monteiro and E. Pereira, Complex for-	50 (1991) 237
E. Fogarassy, C. Fuchs, S. de Unamuno and P. Siffert, Excimer laser induced melting of heavily doped silicon: a	43 (1767) 111	mation in Mn-doped GaP samples  A. Deneuville, D.B. Tanner, R.M. Park and P.H. Holloway, Semiconductor	50 (1991) 253
contribution to the optimization of the laser doping process  R. Nipoti, M. Bianconi, R. Fabbri, M. Servidori, S. Nicoletti and R. Canteri, Electrical and structural characterization of silicon layers directly doped	43 (1989) 316	electrical properties from the frequency dependence of the dielectric constant: application to n-type ZnSe heteroepitaxial thin films  B. Boudart, B. Prévot and C. Schwab, Free-carrier concentration in n-doped	50 (1991) 285
with boron by excimer laser irradiation P.G. Carey and T.W. Sigmon, In-situ doping of silicon using the gas immer-	43 (1989) 321	InP crystals determined by Raman scattering measurements  F. Mosel, A. Seidl, D. Hofmann and G. Müller, Infrared absorption of n- and	50 (1991) 295
sion laser doping (GILD) process  F. Foulon, A. Slaoui and P. Siffert, ArF excimer laser doping of boron into	43 (1989) 325	p-type Fe-doped InP and mapping of the Fe distribution  B. Sartorius, M. Brandstättner and H.	50 (1991) 364
silicon  A.M. Prokhorov, A.Yu. Bonchik, S.G.  Kiyak, A.A. Manenkov, G.N. Mik-	43 (1989) 333	Venghaus, Two-wavelength transmission: a rapid and precise method for measuring the light absorption in	
hailova, A.V. Pokhmurskaja, A.S. Seferov, I. Ursu, V. Craciun and I.N. Mihailescu, Laser solid-phase doping of semiconductors	43 (1989) 340	semiconductors  R. Nipoti, D. Pocci, A. Cetronio and C. Lanzieri, Carrier and mobility profile measurements in n-type ion-implanted	50 (1991) 369
A.E.M.J. Fischer, W.F.J. Slijkerman, J.F. van der Veen and I. Ohdomari, Thermal stability of supersaturated oxy-		GaAs by the differential sheet resistivity and Hall effect technique  B. Mari, A. Segura and A. Chevy, Electri-	50 (1991) 410
gen-doped silicon epitaxial films  D.E. King, J.E. Fernandez and W.E.  Swartz, An XPS study of the doping of trans, trans-p-distyrylbenzene with  AsF <sub>5</sub> : a model conducting polymer	44 (1990) 115	cal properties of neutron-transmuta- tion-doped InSe  D. Ashenford, J.H.C. Hogg, B. Lunn and C.G. Scott, The relationship between electrical and structural characteristics	50 (1991) 415
system  H. Hiraoka and S. Lazare, Applications of doping and dedoping of Teflon AF films in microfabrication using KrF	45 (1990) 325	of CdTe and CdMnTe layers grown on InSb A. Castaldini, A. Cavallini, E. Gombia, R. Mosca and L. Tarricone, Evaluation	50 (1991) 440
and ArF excimer lasers G. Stock, D. Bollmann, R. Buchner, G.	46 (1990) 342	of the diffusion length of minority carriers in bulk GaAs	50 (1991) 485

and single acceptor state of isolated Ni <sub>Ga</sub> in GaAs  P. Roura, J.R. Morante, G. Bremond, T. Benyattou, G. Guillot and W. Ulrici, Complete identification of the Ti-related levels in GaP  T. Hariu, S. Yamauchi, H. Tanaka and S. Ono, Interface characterization of ZnSe/GaAs heterojunctions  48/49 (1991) 204  Electrical properties  W. Mönch, Mechanisms of barrier formation in Schottky contacts: metal-induced surface and interface states  41/42 (1989) 42  T. Saitoh, H. Hasegawa, S. Konishi and H. Ohno, A computer simulation of the recombination process at compound semiconductor surfaces and hetero-interfaces  41/42 (1989) 42  41/42 (1989) 43  T. Saitoh, H. Hasegawa, S. Konishi and H. Ohno, A computer simulation of the recombination process at compound semiconductor surfaces and hetero-interfaces  41/42 (1989) 42  50 (1991) 496  Y. Yasuda, S. Zaima and M. Sakashita, Studies on charge trapping and interface state generation in MOS capacitors at low temperatures  S. Zaima, T. Maruyama and Y. Yasuda, Piezoresistance in n-channel inversion layers of Si MOSFET's  K. Kamimura, Y. Takase, Y. Onuma and A. Kunioka, Surface nitridation of InP with a N <sub>2</sub> plasma  S. Fujieda, K. Akimoto, I. Hirosawa, Y. Mochizuki, J. Mizuki, Y. Matsumoto and J. Matsui, Electrical properties and structures of the MOCVD-	(1989) 383	ation. Electrical behaviour of the ob- tained MIS fluorinated GaAs struc- tures		N. Hizem, G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double
lated levels in GaP  50 (1991) 496  Y. Yasuda, S. Zaima and M. Sakashita, Studies on charge trapping and interface state generation in MOS capacitors at low temperatures  T. Hariu, S. Yamauchi, H. Tanaka and S. Ono, Interface characterization of ZnSe/GaAs heterojunctions  48/49 (1991) 204  Electrical properties  Electrical properties  W. Mönch, Mechanisms of barrier formation in Schottky contacts: metal-induced surface and interface states  41/42 (1989) 42  Y. Yasuda, S. Zaima and M. Sakashita, Studies on charge trapping and interface state generation in MOS capacitors at low temperatures  S. Zaima, T. Maruyama and Y. Yasuda, Piezoresistance in n-channel inversion layers of Si MOSFET's  K. Kamimura, Y. Takase, Y. Onuma and A. Kunioka, Surface nitridation of InP with a N2 plasma  S. Fujieda, K. Akimoto, I. Hirosawa, Y. Mochizuki, J. Mizuki, Y. Matsumoto and J. Matsui, Electrical properties and structures of the MOCVD-		H. Ohno, A computer simulation of the recombination process at com- pound semiconductor surfaces and	50 (1991) 490	and single acceptor state of isolated Ni <sub>Ga</sub> in GaAs  P. Roura, J.R. Morante, G. Bremond, T.
tors at low temperatures  T. Hariu, S. Yamauchi, H. Tanaka and S. Ono, Interface characterization of ZnSe/GaAs heterojunctions  48/49 (1991) 204  Electrical properties  W. Mönch, Mechanisms of barrier formation in Schottky contacts: metal-induced surface and interface states  41/42 (1989) 42  S. Zaima, T. Maruyama and Y. Yasuda, Piezoresistance in n-channel inversion layers of Si MOSFET's  K. Kamimura, Y. Takase, Y. Onuma and A. Kunioka, Surface nitridation of InP with a N2 plasma  S. Fujieda, K. Akimoto, I. Hirosawa, Y. Mochizuki, J. Mizuki, Y. Matsumoto and J. Matsui, Electrical properties and structures of the MOCVD-	(1989) 402	Y. Yasuda, S. Zaima and M. Sakashita, Studies on charge trapping and inter-	50 (1991) 496	
T. Hariu, S. Yamauchi, H. Tanaka and S. Ono, Interface characterization of ZnSe/GaAs heterojunctions  48/49 (1991) 204  Electrical properties  W. Mönch, Mechanisms of barrier formation in Schottky contacts: metal-induced surface and interface states  41/42 (1989) 42  Fiezoresistance in n-channel inversion layers of Si MOSFET's  K. Kamimura, Y. Takase, Y. Onuma and A. Kunioka, Surface nitridation of InP with a N <sub>2</sub> plasma  5. Fujieda, K. Akimoto, I. Hirosawa, Y. Mochizuki, J. Mizuki, Y. Matsumoto and J. Matsui, Electrical properties and structures of the MOCVD-	(1989) 420	tors at low temperatures		Electrical measurements
ZnSe/GaAs heterojunctions  48/49 (1991) 204  K. Kamimura, Y. Takase, Y. Onuma and A. Kunioka, Surface nitridation of InP with a N <sub>2</sub> plasma  41/42 (1989) 44  S. Fujieda, K. Akimoto, I. Hirosawa, Y. Mochizuki, J. Mizuki, Y. Matsumoto and J. Matsui, Electrical properties and J. Matsui, Electrical properties and structures of the MOCVD-	(1090) 422	Piezoresistance in n-channel inversion		
W. Mönch, Mechanisms of barrier formation in Schottky contacts: metal-induced surface and interface states  with a N <sub>2</sub> plasma  S. Fujieda, K. Akimoto, I. Hirosawa, Y.  Mochizuki, J. Mizuki, Y. Matsumoto and J. Matsui, Electrical properties and structures of the MOCVD-	(1989) 433	K. Kamimura, Y. Takase, Y. Onuma and	48/49 (1991) 204	ZnSe/GaAs heterojunctions
W. Mönch, Mechanisms of barrier formation in Schottky contacts: metal-induced surface and interface states  Mochizuki, J. Mizuki, Y. Matsumoto and J. Matsui, Electrical properties and structures of the MOCVD-	(1989) 443	with a N <sub>2</sub> plasma		Electrical properties
		Mochizuki, J. Mizuki, Y. Matsumoto and J. Matsui, Electrical properties	41 /42 (1080) 128	tion in Schottky contacts: metal-in-
and R.T. Tung, Pressure dependences T. Aoyama, T. Sugi and T. Ito, De-	(1989) 516	AlN/GaAs interface T. Aoyama, T. Sugi and T. Ito, De-	41/42 (1909) 120	J.H. Werner, H. von Känel, G. Markewitz and R.T. Tung, Pressure dependences
of silicide/silicon Schottky barrier termination of band line-up in β-heights  N. Esser, M. Hünermann, U. Resch, D.  termination of band line-up in β-SiC/Si heterojunction for Si-HBT's 41/42 (1989) 58  H. Miyatake, Y. Yamaguchi, Y. Mashiko,	(1989) 584	SiC/Si heterojunction for Si-HBT's	41/42 (1989) 159	heights
Spaltmann, J. Geurts, D.R.T. Zahn, W. Richter and R.H. Williams, Bis-  T. Nishimura and H. Koyama, Microstructure of high temperature an-	4000 440	T. Nishimura and H. Koyama, Micro- structure of high temperature an-		Spaltmann, J. Geurts, D.R.T. Zahn, W. Richter and R.H. Williams, Bis-
muth on GaAs(110): characterisation nealed SIMOX wafer 41/42 (1989) 64 of growth mode and Schottky barrier formation at low and room tempera- Toulemonde, Defects created by 3.5	(1989) 643	P. Mary, P. Bogdanski, G. Nouet and M.		of growth mode and Schottky barrier
ture 41/42 (1989) 169 GeV xenon ions in silicon 43 (1989) 100 K. Hirose, H. Tsuda and T. Mizutani, Control of the Al/GaAs Schottky G. Myburg, J.B. Malherbe and E. Friedland, Electrical characteristics of ion	(1989) 102	G. Myburg, J.B. Malherbe and E. Fried-	41/42 (1989) 169	K. Hirose, H. Tsuda and T. Mizutani,
barrier height using a rare-earth metal bombarded Ni/n-Si Schottky contacts 43 (1989) 24 interlayer 41/42 (1989) 174 F. Foulon, A. Slaoui and P. Siffert, ArF	(1989) 242	F. Foulon, A. Slaoui and P. Siffert, ArF	41/42 (1989) 174	interlayer
T. Arakawa, H. Baba and G. Adachi, excimer laser doping of boron into Deep level transient spectroscopic silicon  43 (1989) 33  Studies of the perovskite oxides as gas  J.H. James, B.J. Kellett, A. Gauzzi, B.	(1989) 333	silicon		Deep level transient spectroscopic
sensor material 41/42 (1989) 212 Dwir and D. Pavuna, In-situ super- N. Fujimura and T. Ito, TiSi <sub>2</sub> formation Conducting YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7</sub> thin films		Dwir and D. Pavuna, In-situ super-	41/42 (1989) 212	sensor material
at the Ti-rich TiN <sub>x</sub> /Si interface 41/42 (1989) 272 grown by ion beam co-deposition 43 (1989) 39  S. Ogawa, T. Yoshida, T. Kouzaki, S.  Okuda and K. Tsukamoto, Thermal instability of the TiSi <sub>2</sub> /Si structure:  Pyatkova and D.I. Zarovsky, Nickel, cobalt and iron silicide formation	1989) 393	V.V. Tokarev, A.V. Kibardin, T.M. Pyatkova and D.I. Zarovsky, Nickel,	41/42 (1989) 272	S. Ogawa, T. Yoshida, T. Kouzaki, S. Okuda and K. Tsukamoto, Thermal
impurity effects 41/42 (1989) 290 stimulated by argon implantation 44 (1990) 23 H. Hasegawa, H. Ohno, H. Ishii, T. Haga, Y. Abe and H. Takahashi, Origin and V.V. Tokarev, A.I. Demchenko, A.I.  Ivanov and V.E. Borisenko, Influence	1990) 235	stimulated by argon implantation V.V. Tokarev, A.I. Demchenko, A.I. Ivanov and V.E. Borisenko, Influence	41/42 (1989) 290	impurity effects H. Hasegawa, H. Ohno, H. Ishii, T. Haga, Y. Abe and H. Takahashi, Origin and
properties of interface states at insula- tor-semiconductor and semiconduc- tor-semiconductor interfaces of com- formations in nickel silicides 44 (1990) 24 E. Nowicka, Z. Wolfram and R. Duś,	1990) 241	formations in nickel silicides		tor-semiconductor and semiconduc-
pound semiconductors 41/42 (1989) 372 Deuterium adsorption on thin nickel A.S. Barrière, G. Couturier, H. Guegan, T. Séguelong, A. Thabti, P. Alnot and A.R. de Wit, M.D. Janssen and J.J. Kelly,	1990) 13	Deuterium adsorption on thin nickel films	41/42 (1989) 372	pound semiconductors  A.S. Barrière, G. Couturier, H. Guegan,
J. Chazelas, Interface GaAs – gallium  Fluoride thin film grown by fluorin-  Electrochemical characterization of polycrystalline ZnO layers  45 (1990) 2	1990) 21	Electrochemical characterization of		J. Chazelas, Interface GaAs - gallium

	and C Chimaska Calcustian of Ca	
	and G. Shimaoka, Coloration of Sn-Sb-O thin films	48/49 (1991) 55
	deposition of II-VI binary and ternary	
45 (1990) 325	P.C. Karulkar, R.J. Hillard, J.M. Heddle- son and P. Rai-Choudhury, A pres-	48/49 (1991) 89
46 (1990) 53	nique for rapid characterization of thin	
44,4000	S. Kar, A. Raychaudhuri, A.K. Sinha and S. Ashok, Ion beam modification of	48/49 (1991) 237
46 (1990) 61	dioxide films  Y. Shigesato, S. Takaki and T. Haranou,	48/49 (1991) 264
46 (1990) 74	Crystallinity and electrical properties of tin-doped indium oxide films de- posited by DC magnetron sputtering	48/49 (1991) 269
(,	S. Berger, Y. Komem and B.Z. Weiss, On the microstructure, composition and	, (2272) 207
46 (1990) 108	Si system  P.K. Banerjee, J.S. Kim and S.S. Mitra,	48/49 (1991) 281
	Electrical and optical properties of a- luminum-doped amorphous silicon carbide films	48/49 (1991) 288
46 (1990) 121	and G. Shimaoka, The dependence of	
46 (1000) 100	troluminescent properties of ZnS:Mn deposited on Y <sub>2</sub> O <sub>3</sub> films on thickness	48/49 (1991) 297
46 (1990) 189	and structural characterization of Co	
	and Ni silicide contacts to silicon C.H. Champness and W.R. Clark, Anom- alous inductive effect in Se-metal	48/49 (1991) 307
46 (1990) 200	contacts  E. Gofuku, Y. Toyoda, Y. Uehara, M.  Kohara and M. Nunoshita, Highly	48/49 (1991) 337
46 (1990) 233	conductive TiO <sub>2</sub> thin films prepared by EB-modification M. Arienzo, S.S. Iyer, B.S. Meyerson, G.L.	48/49 (1991) 343
	loys: growth, properties and applica- tions	48/49 (1991) 377
46 (1990) 245	Relationship between mechanical,	
	electronic and vibrational properties of $Ge_xSi_{1-x}$ strained layers Y.L. Jiang and H.L. Hwang, Electron	48/49 (1991) 387
46 (1990) 330	transport in hydrogenated amorphous silicon quantum wells Y. Hatanaka, Heterostructures with hy-	48/49 (1991) 392
48/49 (1991) 1	drogenated amorphous silicon for use in imaging devices	48/49 (1991) 457
	46 (1990) 61 46 (1990) 74 46 (1990) 108 46 (1990) 121 46 (1990) 200 46 (1990) 233 46 (1990) 245 46 (1990) 330	45 (1990) 325  T.M. Razykov, Chemical molecular beam deposition of II-VI binary and ternary compound films in a gas flow P.C. Karulkar, R.J. Hillard, J.M. Heddleson and P. Rai-Choudhury, A pressure contact current-voltage technique for rapid characterization of thin dielectric films  S. Kar, A. Raychaudhuri, A.K. Sinha and S. Ashok, Ion beam modification of the dielectric properties of thin silicon dioxide films  Y. Shigesato, S. Takaki and T. Haranou, Crystallinity and electrical properties of tin-doped indium oxide films deposited by DC magnetron sputtering  S. Berger, Y. Komem and B.Z. Weiss, On the microstructure, composition and electrical properties of Al/TiW/polysis system  46 (1990) 108  P.K. Banerjee, J.S. Kim and S.S. Mitra, Electrical and optical properties of aluminum-doped amorphous silicon carbide films  Y. Nakanishi, Y. Fukuda, Y. Hatanaka and G. Shimaoka, The dependence of the polycrystalline structure and electroluminescent properties of ZnS:Mn deposited on Y <sub>2</sub> O <sub>3</sub> films on thickness  46 (1990) 189  A.K. Kulkarni and A.J. Canale, Electrical and structural characterization of Co and Ni silicide contacts to silicon  C.H. Champness and W.R. Clark, Anomalous inductive effect in Se-metal contacts  E. Gofuku, Y. Toyoda, Y. Uehara, M. Kohara and M. Nunoshita, Highly conductive TiO <sub>2</sub> thin films prepared by EB-modification  46 (1990) 233  M. Arienzo, S.S. Iyer, B.S. Meyerson, G.L. Patton and J.M.C. Stork, Si-Ge alloys: growth, properties and applications  S.C. Jain, A. Atkinson and W.S. Khokle, Relationship between mechanical, electronic and vibrational properties of Ge, Si <sub>1-x</sub> strained layers  Y.L. Jiang and H.L. Hwang, Electron transport in hydrogenated amorphous silicon for use

transport mechanism of p-type a- Si:H/n-type c-Si heterojunctions and their application to an imaging device	48/49 (1991) 472	etch damage in GaAs processing evaluated by a microwave absorption technique	50 (1991) 290
M. Takeuchi, M. Masui and Y. Momose, Copper-phthalocyanine thin film pho-		W. Kütt, G.C. Cho, M. Strahnen and H. Kurz, Electro-optic sampling of	30 (1771) 270
toelectrochemical cells  H. Mimura, K. Sai, Y. Ohta, K. Yama- moto and K. Kitamura, A two-dimen-	48/49 (1991) 517	surface space-charge fields on III-V compounds  M. Hage-Ali, B. Yaacoub, S. Mergui, M.	50 (1991) 325
sional image sensor with a-Si:H pin diodes  M. Takeuchi, Y. Watanabe and S. Ozawa, Gas-sensitive properties of ultrafine In <sub>2</sub> O <sub>3</sub> particle layers prepared by gas	48/49 (1991) 521	Samimi, B. Biglari and P. Siffert, Mi- croscopic defect level characterization of semi-insulating compound semicon- ductors by TSC and PICTS. Applica- tion to the effect of hydrogen in CdTe	50 (1991) 377
evaporation technique  J.S. Kim, P.K. Banerjee, S.S. Mitra, H.  Shastry, J.J. Loferski and R. Beaulieu,  Optical, electrical and mechanical	48/49 (1991) 526	J. Tardy, I. Thomas, P. Viktorovitch, M. Gendry, J.L. Perrossier, C. Santinelli, M.P. Besland, P. Louis and G. Post, Long-term stability of InP MIS de-	30 (1991) 377
properties of RF-sputtered TiN-W-	10 110 (1001) 510	vices	50 (1991) 383
Au films  A. Diarra, S. Hotchandani, H. Kassi and R.M. Leblanc, Capacitance character-	48/49 (1991) 548	A.W.R. Leitch, Th. Prescha and M. Stutz- mann, Hydrogen passivation and re- activation of shallow Zn acceptors in	
istics of mixed monolayers of chloro-	10 110 11001 75	GaAs	50 (1991) 390
phyll a and carotenoid canthaxanthin H.G. Grimmeiss and M. Kleverman, Electrical and optical defect spec-	48/49 (1991) 567	S. Tüzemen and M.R. Brozel, An investi- gation of photo-quenching properties of LEC GaAs by using optical and	
troscopy of compound semiconduc- tors	50 (1991) 52	electrical techniques C. Ghezzi, R. Mosca, A. Bosacchi, S.	50 (1991) 395
T.S. Horányi, P. Tüttö and G. Endrédi, Improved method for depth profiling	30 (1991) 32	Franchi and E. Gombia, The influence of the DX center on the capacitance	
of multilayer structures	50 (1991) 143	of Schottky barriers in n-type AlGaAs	50 (1991) 400
J.S. Rimmer, M. Missous and A.R. Peaker,		R. Nipoti, D. Pocci, A. Cetronio and C.	
A new, fast method for the computer		Lanzieri, Carrier and mobility profile	
simulation of CV profiles in multi-	50 (1001) 140	measurements in n-type ion-implanted	
layer structures  J. Schreiber, W. Hergert and S. Hilde-	50 (1991) 149	GaAs by the differential sheet resistiv- ity and Hall effect technique	50 (1991) 410
brandt, Combined application of SEM-CL and SEM-EBIC for the in-		B. Mari, A. Segura and A. Chevy, Electrical properties of neutron-transmuta-	30 (1991) 410
vestigation of compound semiconduc-		tion-doped InSe	50 (1991) 415
tors	50 (1991) 181	L. Roberts and G.J. Hughes, An investi-	
Z.M. Wang, J. Windscheif, D.J. As and		gation of metal/GaAs(100) interfaces	50 (1991) 424
W. Jantz, Ambient and low tempera- ture photoluminescence topography of		by deep level transient spectroscopy D. Ashenford, J.H.C. Hogg, B. Lunn and	30 (1991) 424
GaAs substrates, epitaxial and im-		C.G. Scott, The relationship between	
planted layers	50 (1991) 228	electrical and structural characteristics	
H. L'Haridon, P.N. Favennec, R. Co-		of CdTe and CdMnTe layers grown	
quille, M. Salvi, M. Gauneau, Y. Le		on InSb	50 (1991) 440
Guillou, R. Callec and P. Gall, Spatial		L.J. Bredell, F.D. Auret, G. Myburg and	
investigation of an iron-doped indium phosphide ingot	50 (1991) 237	W.O. Barnard, Electrical characteriza- tion of argon-ion sputtered n-GaAs	50 (1991) 466
A. Deneuville, D.B. Tanner, R.M. Park	30 (1991) 237	HG. Hettwer, W. Lerch, B. Lentfort,	30 (1991) 400
and P.H. Holloway, Semiconductor		N.A. Stolwijk and H. Mehrer, Com-	
electrical properties from the frequen-		bined application of spreading-resis-	
cy dependence of the dielectric con-		tance and electron-microprobe depth	
stant: application to n-type ZnSe het-		profiling on GaAs:Zn and Si:P	50 (1991) 470
eroepitaxial thin films	50 (1991) 285	W. Jantz, R. Stibal, J. Windscheif and J.	
H.P. Zappe and G. Kaufel, Reactive-ion-		Wagner, Variation of material param-	

eters along the growth direction of liquid encapsulated Czochralski grown GaAs ingots  A. Castaldini, A. Cavallini, E. Gombia, R. Mosca and L. Tarricone, Evaluation	50 (1991) 480	electron spectroscopy and photoelectron diffraction studies of Si(001) 2 × 1-K and -Cs surfaces  A. Ichimiya, S. Kohmoto, T. Fujii and Y. Horio, RHEED intensity analysis of	41/42 (1989) 75
of the diffusion length of minority carriers in bulk GaAs  N. Hizem, G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double	50 (1991) 485	Si(111) $\sqrt{3} \times \sqrt{3}$ -Ag structure T. Urano, M. Kaburagi, S. Hongo and T. Kanaji, LEED $I-V$ curve analysis for the structure of iron films on Si(111) surfaces	41/42 (1989) 82 41/42 (1989) 103
and single acceptor state of isolated Ni <sub>Ga</sub> in GaAs  M. Morsli, A. Bonnet, Y. Tregouet, A.	50 (1991) 490	S. Kohmoto, S. Mizuno and A. Ichimiya, RHEED intensity analysis of Li/ Si(111) structures	41/42 (1989) 107
Conan, S. Jobic and R. Brec, Electronic properties and band structure of IrSe <sub>2</sub>	50 (1991) 500	ST. Li, S. Hasegawa, N. Yamashita and H. Nakashima, Initial stages of alumi- num epitaxy on the Si(111) $\sqrt{3} \times \sqrt{3}$ -Al surface studied by electron-energy-loss	
Electron bombardment		spectroscopy N. Esser, M. Hünermann, U. Resch, D. Spaltmann, J. Geurts, D.R.T. Zahn,	41/42 (1989) 118
R. M'Ghaieth, R. Gauthier and P. Pinard, Structure and defects induced by elec- tron beam irradiation in silicon sub- strates and EPR ribbons	43 (1989) 111	W. Richter and R.H. Williams, Bismuth on GaAs(110): characterisation of growth mode and Schottky barrier formation at low and room tempera-	
H. Yumoto, K. Watanabe, K. Akashi and N. Igata, The effect of electronic exci- tation produced by an electron shower	43 (1767) 111	ture  M. Renda and K. Morita, Epitaxial growth of a mono-crystalline metasta-	41/42 (1989) 169
on the adhesion of copper films de- posited on stainless steel E. Gofuku, Y. Toyoda, Y. Uehara, M.	48/49 (1991) 173	ble AuIn layer at the Au/InP(001) interface  J. Falta, M. Horn and M. Henzler, SPA-	41/42 (1989) 216
<ul> <li>Kohara and M. Nunoshita, Highly conductive TiO<sub>2</sub> thin films prepared by EB-modification</li> <li>C. Levade, J.J. Couderc, G. Vanderschaeve, D. Caillard and A. Couret, TEM in-situ observation of recombi-</li> </ul>	48/49 (1991) 343	LEED studies of defects in thin epitaxial NiSi <sub>2</sub> layers on Si(111)  N. Cherief, R. Cinti, M. De Crescenzi, J. Derrien, T.A. Nguyen Tan and J.Y. Veuillen, Heteroepitaxy of metallic and semiconducting silicides on sili-	41/42 (1989) 230
nation-enhanced mobility of disloca- tions in II-VI compounds	50 (1991) 119	con I. Yamada, Interfacial structure of ICB	41/42 (1989) 241
Y. Gao, I. Ardelean, D. Renard, B. Rose and Y. Jin, High-depth-resolution SIMS analysis for InGaAs/InP inter- faces	50 (1991) 131	epitaxially deposited Al(110) bicrystal films on Si(100) substrates M. Itoh, M. Kinoshita, T. Ajioka, M. Itoh and T. Inada, Crystalline quality of	41/42 (1989) 253
Electron diffraction	30 (1771) 131	heteroepitaxial silicon on epitaxial NiSi <sub>2</sub> /Si(100)	41/42 (1989) 262
•		N. Fujimura and T. Ito, $TiSi_2$ formation at the Ti-rich $TiN_x/Si$ interface	41/42 (1989) 272
S. Nakanishi, H. Tokutaka, K. Nishimori, S. Kishida and N. Ishihara, The difference between 6H-SiC (0001) and (0001) faces observed by AES, LEED		<ul> <li>N. Fujimura, S. Tachibana and T. Ito, Characterization of Si-rich WSi<sub>x</sub> on Si</li> <li>K. Takayanagi, Y. Tanishiro, T. Ishitsuka and K. Akiyama, In-situ UHV elec-</li> </ul>	41/42 (1989) 286
and ESCA  K. Nishimori, H. Tokutaka, Z. Okinaga, S. Kishida and N. Ishihara, Observa- tion of Si and SiC surface structures	41/42 (1989) 44	tron microscope study of metal-sili- con surfaces  A. Koma, K. Saiki and Y. Sato, Heteroep- itaxy of a two-dimensional material	41/42 (1989) 337
using the magnetic LEED method  S. Kono, Y. Enta, T. Abukawa, T. Kinoshita and T. Sakamoto, Photo-	41/42 (1989) 49	on a three-dimensional material M. Yano, M. Ashida, Y. Iwai and M. Inoue, Characteristic properties of	41/42 (1989) 451

III-V <sub>A</sub> /III-V <sub>B</sub> heterointerfaces grown by molecular beam epitaxy	41/42 (1989) 457	Toulemonde, M. Hage Ali and J.P. Stoquert, Instability and structural	
S. Tatarenko, J. Cibert, Y. Gobil, G. Feuillet, K. Saminadayar, A.C. Chami	41/ 12 (1707) 107	transformation of amorphous ultra- thin W-Si multilayer structures dur-	
and E. Ligeon, RHEED, XPS, HRTEM and channeling studies of molecular beam epitaxy growth of CdTe on (001) GaAs	41/42 (1989) 470	ing heavy ion irradiation  A. Mowbray and R.G. Jones, Homo- and hetero-iodide thin film growth on InSb(001): low-temperature iodide	46 (1990) 422
T. Nomura, K. Wakatuki, M. Miyao and M. Hagino, Characterization of the	41/42 (1707) 470	formation and epitaxial growth of CdI <sub>2</sub>	48/49 (1991) 27
GaAs buffer layer grown on GaP by MBE for the two-step growth method	41/42 (1989) 512	S. Nagashima, E. Fukuchi and I. Ogura, Growth modes of overlayers of Se de-	10) 17 (1771) 21
K. Maehashi, S. Hasegawa and H. Nakashima, Atomic rearrangement during the initial stages of GaAs		posited on Cu(111) surfaces K. Kalki, B. Pennemann, U. Schröder, W. Heichler and K. Wandelt, Properties	48/49 (1991) 44
growth on Si(111)( $\sqrt{3} \times \sqrt{3}$ )-Ga surface F. Abel, C. Cohen, J.A. Davies, J. Moulin	41/42 (1989) 567	of noble metal and binary alloy mono- layer films on Ru(001) N. Ohshima, Y. Koide, S. Zaima and Y.	48/49 (1991) 59
and D. Schmaus, Thin-film growth of Sn on Cu(100)	44 (1990) 17	Yasuda, Formation of a superstruc- ture in the initial stage of Ge epitaxial	
T. Ito, T. Yasumatsu and A. Hiraki, Ho- moepitaxial growth of silicon on anodized porous silicon	44 (1990) 97	growth on Si(100) substrates  R.W. Vook and B. Oral, Carbon mono- xide oxidation on epitaxial Cu(111)/	48/49 (1991) 69
A.G. Roosenbrand, M.W.C. van Beck- hoven and H.H. Brongersma, Surface topography of pyrolytic graphite	44 (1990) 121	Pd(111) bilayers at atmospheric pres- sures H.H. Madden and R. Imbihl, Interaction	48/49 (1991) 125
H. Zeijlemaker and J. Verhoeven, The application of digital techniques for	., (1770) 121	of NO and H <sub>2</sub> with Pt(100) G. Shimaoka, MEED studies of thin metal	48/49 (1991) 130
electron energy spectroscopy using a retarding field analyser  A. Vázquez, J.M. Domínguez and S. Fuentes, Thermally induced modifica-	44 (1990) 249	film covered semiconductor surfaces Y. Nakanishi, Y. Fukuda, Y. Hatanaka and G. Shimaoka, The dependence of the polycrystalline structure and elec-	48/49 (1991) 190
tions on the crystal surface of molyb- date-type catalysts	44 (1990) 331	troluminescent properties of ZnS:Mn deposited on Y <sub>2</sub> O <sub>3</sub> films on thickness	48/49 (1991) 297
A. Elbiache and P. Marcus, Adsorption and surface segregation of sulphur on Fe-17Cr-12.6Ni(100) and Fe-17Cr-	, , , , , , , , , , , , , , , , , , , ,	JK. Zuo and J.F. Wendelken, Substrate temperature effects on $(\sqrt{3} \times \sqrt{3})$ R30° domain growth of Ag on Si(111)	., . (,
14.5Ni-2.3Mo(100) alloys F. Curcio, M. Musci, N. Notaro and G.	45 (1990) 49	surface T. Yasumatsu, T. Ito, H. Nishizawa and	48/49 (1991) 366
De Michele, Synthesis of ultrafine TiO <sub>2</sub> powders by a CW CO <sub>2</sub> laser	46 (1990) 225	A. Hiraki, Ultrathin Si films grown epitaxially on porous silicon	48/49 (1991) 414
E. D'Anna, G. Leggieri, A. Luches, M. Martino, A.V. Drigo, G. Majni, P. Mengucci and I.N. Mihailescu, Nitri-	40 (1990) 223	H. Tokutaka and S. Kishida, Surface characterization of Bi-based high- $T_c$ superconducting thin films and bulk	40/49 (1991) 414
dation of titanium by multipulse ex- cimer laser irradiation	46 (1990) 365	single crystals K. Nishimori, H. Tokutaka, T. Tamon, S.	48/49 (1991) 425
J. Solis, C.N. Afonso and F. Catalina, The influence of the substrate on the transformations induced in Si by nanosecond laser irradiation: a time-		Kishida and N. Ishihara, Surface study of single-crystal 80 K Bi-Sr-Ca-Cu- O superconductor with Si and Nb by RHEED and XPS depth profile	48/49 (1991) 450
resolved study V. Dupuis, M.F. Ravet, C. Tête and M.	46 (1990) 383	T. Hosaka, Effects of impurities in a two- layer evaporated Au film on its tensile	40/ 45 (1551) 450
Piecuch, Thermal evolution of W/Si and W/C multilayers under pulsed		fracture C. Feldman, G. Deutscher and E. Grün-	48/49 (1991) 502
laser heating and classical annealing J. Marfaing, W. Marine, B. Vidal, M.	46 (1990) 398	baum, Single-crystal transformation of sphalerite CdS to cubic phase Cu <sub>x</sub> S	48/49 (1991) 535

<ul> <li>H. Cerva, Transmission electron microscopy of heteroepitaxial layer structures</li> <li>C.T. Foxon, Control of MBE, MOMBE and CBE growth using RHEED</li> <li>J. Tardy, I. Thomas, P. Viktorovitch, M.</li> </ul>	50 (1991) 19 50 (1991) 28	<ul> <li>C. Tatsuyama, T. Tanbo and N. Nakayama, Heteroepitaxy between layered semiconductors GaSe and InSe</li> <li>H.C. Lee, H. Ishiwara, S. Furukawa, K. Saiki and A. Koma, Distribution of interfacial As atoms in the electron-</li> </ul>	41/42 (1989) 539
<ul> <li>Gendry, J.L. Perrossier, C. Santinelli,</li> <li>M.P. Besland, P. Louis and G. Post,</li> <li>Long-term stability of InP MIS devices</li> <li>D. Lee, S.J. Barnett, A.D. Pitt, M.R.</li> <li>Houlton and G.W. Smith, Characteri-</li> </ul>	50 (1991) 383	beam exposure and epitaxy (EBE-epitaxy) technique for growing GaAs films on CaF <sub>2</sub> /Si(111) structures  J.A. Kelber, J.W. Rogers, Jr., B.A. Banse and B.E. Koel, Interaction of dimethylamine with clean and partially	41/42 (1989) 553
zation of alloy composition in $Ga_{1-x}Al_xAs/GaAs$ structures: comparison of photovoltage, X-ray, SIMS and RHEED techniques	50 (1991) 428	oxidized copper surfaces  K. Prabhakaran and C.N.R. Rao, Adsorption of carbonyl compounds on clean and modified Cu(110) surfaces:	44 (1990) 193
D.A. Woolf, D.I. Westwood, M.A. Anderson and R.H. Williams, The molecular beam epitaxial growth of GaAs(111)/Si(111): a variable growth temperature		a combined EELS-UPS study J.C. Ingram, K.W. Nebesny and J.E. Pemberton, Optical properties of metal surfaces from electron energy loss	44 (1990) 205
study  Electron emission	50 (1991) 445	spectroscopy in the reflection mode J.C. Ingram, K.W. Nebesny and J.E. Pemberton, Optical constants of the noble metals determined by reflection	44 (1990) 279
M.H. Hecht, L.D. Bell and W.J. Kaiser, Ballistic-electron-emission microscopy of subsurface defects at the Au-		electron energy loss spectroscopy T.S. Jones, M.Q. Ding, N.V. Richardson and C.F. McConville, The effects of	44 (1990) 293
GaAs(100) interface  F. Aumayr, G. Lakits and H. Winter, On the measurement of statistics for particle-induced electron emission from a	41/42 (1989) 17	surface damage on surface plasmon excitations in doped InSb(100)  J.C. Ingram, K.W. Nebesny and J.E. Pemberton, Optical properties of selected first-row transition metals de-	45 (1990) 85
clean metal surface  J.J. Fijol, A.M. Then, G.W. Tasker and  R.J. Soave, Secondary electron yield	47 (1991) 139	termined by reflection electron energy loss spectroscopy G. Radhakrishnan, W. Stenzel, H. Con-	45 (1990) 247
of SiO <sub>2</sub> and Si <sub>3</sub> N <sub>4</sub> thin films for continuous dynode electron multipliers	48/49 (1991) 464	rad and A.M. Bradshaw, Photoreactions of adsorbed CH <sub>3</sub> Br on Pt(111) V.M. Browne, A.F. Carley, R.G. Copperthwaite, P.R. Davies, E.M. Moser	46 (1990) 36
Electron energy loss spectroscopy  ST. Li, S. Hasegawa, N. Yamashita and		and M.W. Roberts, Activation of carbon dioxide at bismuth, gold and copper surfaces	47 (1991) 375
H. Nakashima, Initial stages of aluminum epitaxy on the Si(111) $\sqrt{3} \times \sqrt{3}$ -Al surface studied by electron-energy-loss		Y. Fukuda and M. Nagoshi, Chemisorption of hydrogen on Cr(111) studied by XPS, UPS, and HREELS	48/49 (1991) 147
spectroscopy X.M. Ding, G.S. Dong, X.K. Lu, H.Y. Xiao, P. Chen and X. Wang, Applica-	41/42 (1989) 118	D.E. Ramaker, Evidence for vertical C <sub>2</sub> on Ni as a precursor for graphite nucleation	48/49 (1991) 351
tion of HREELS to Al/GaAs and Al/GaP interfaces  R. Sporken, P.A. Thiry, P. Xhonneux, R. Caudana and J.P. Dalwa Spectro	41/42 (1989) 123	Electron microscopy	
Caudano and J.P. Delrue, Spectroscopic study of metal/semimetal and metal/semiconductor interfaces  A. Förster, J.M. Layet and H. Lüth, Evaluation of dopant profiles and dif-	41/42 (1989) 201	M. Murakami, H.J. Kim, YC. Shih, W.H. Price and C.C. Parks, Effects of interfacial microstructure on ohmic contacts to GaAs	41/42 (1989) 195
fusion constants by means of electron energy loss spectroscopy	41/42 (1989) 306	R.T. Tung and F. Schrey, Epitaxial CoSi <sub>2</sub> /Si(111) interfaces	41/42 (1989) 223

		I C M. II V T V I I	
N. Cherief, R. Cinti, M. De Crescenzi, J.		JS. Ma, H. Kawarada, T. Yonehara, JI.	
Derrien, T.A. Nguyen Tan and J.Y.		Suzuki, J. Wei, Y. Yokota, H. Mori, H. Fujita and A. Hiraki, Interfacial	
Veuillen, Heteroepitaxy of metallic		structures and selective growth of dia-	
and semiconducting silicides on sili-			
con	41/42 (1989) 241	mond particles formed by plasma-as-	41 /42 (1090) 572
I. Yamada, Interfacial structure of ICB		sisted CVD	41/42 (1989) 572
epitaxially deposited Al(110) bicrystal	44 (40 (4000) 252	H. Horikawa, M. Akiyama, S. Onozawa,	
films on Si(100) substrates	41/42 (1989) 253	Y. Kawai and M. Sakuta, Interfacial	41 /42 /1000\ 500
M. Itoh, M. Kinoshita, T. Ajioka, M. Itoh		layers of InP/Si heteroepitaxy	41/42 (1989) 598
and T. Inada, Crystalline quality of		G. Bomchil, A. Halimaoui and R. Herino,	
heteroepitaxial silicon on epitaxial		Porous silicon: the material and its	
NiSi <sub>2</sub> /Si(100)	41/42 (1989) 262	applications in silicon-on-insulator	
N. Fujimura, S. Tachibana and T. Ito,		technologies	41/42 (1989) 604
Characterization of Si-rich WSi <sub>x</sub> on Si	41/42 (1989) 286	K. Furukawa and A. Nakagawa, Applica-	
S. Ogawa, T. Yoshida, T. Kouzaki, S.		tions of the silicon wafer direct-bond-	
Okuda and K. Tsukamoto, Thermal		ing technique to electron devices	41/42 (1989) 627
instability of the TiSi <sub>2</sub> /Si structure:		H. Kumomi, T. Yonehara, Y. Nishigaki	
impurity effects	41/42 (1989) 290	and N. Sato, Selective nucleation	
T. Ito, A. Yamama, A. Hiraki and M.		based epitaxy (Sentaxy). Investigation	
Satou, Silicidation of porous silicon		of initial nucleation stages	41/42 (1989) 638
and its application for the fabrication		H. Miyatake, Y. Yamaguchi, Y. Mashiko,	
of a buried metal layer	41/42 (1989) 301	T. Nishimura and H. Koyama, Micro-	
K. Takayanagi, Y. Tanishiro, T. Ishitsuka	, , , , , , , , , , , , , , , , , , , ,	structure of high temperature an-	
and K. Akiyama, In-situ UHV elec-		nealed SIMOX wafer	41/42 (1989) 643
tron microscope study of metal-sili-		A. Yahashi, L.L. Levenson, H. Usui and	, , , , ,
con surfaces	41/42 (1989) 337	I. Yamada, The structure zone model	
H. Akatsu and I. Ohdomari, HRTEM	12/ 12 (220)	applied to ionized cluster beam films:	
observation of the Si/SiO <sub>2</sub> interface	41/42 (1989) 357	Al on SiO <sub>2</sub>	43 (1989) 37
A. Ourmazd, P.H. Fuoss, J. Bevk and J.F.	11/ 12 (1/0/) 00	M. Jubber, J.I.B. Wilson, J.L. Davidson,	()
Morar, The Si(001)/SiO <sub>2</sub> interface	41/42 (1989) 365	P.A. Fernie and P. John, Laser writing	
H. Hasegawa, H. Ohno, H. Ishii, T. Haga,	11/ 12 (1707) 500	of high purity gold tracks	43 (1989) 74
Y. Abe and H. Takahashi, Origin and		O. Bostanjoglo and P. Thomsen-Schmidt,	(2,0,)
properties of interface states at insula-		Laser-induced multiple phase transi-	
tor-semiconductor and semiconduc-		tions in Ge-Te films traced by time-	
tor-semiconductor interfaces of com-		resolved TEM	43 (1989) 136
	41/42 (1989) 372	J. Marfaing, W. Marine, R. Pierrisnard	15 (1707) 150
pound semiconductors	41/42 (1909) 372	and A. Cros, Structural changes in	
A.S. Barrière, G. Couturier, H. Guegan,		$Au_xSi_{1-x}$ alloy films under laser	
T. Séguelong, A. Thabti, P. Alnot and		$Au_x Si_{1-x}$ and ministrated irradiation	42 (1000) 165
J. Chazelas, Interface GaAs – gallium			43 (1989) 165
fluoride thin film grown by fluorin-		R. Braun, R. Nowak, P. Hess, H. Oetz-	
ation. Electrical behaviour of the ob-		mann and C. Schmidt, Photoablation	
tained MIS fluorinated GaAs struc-	44 (42 (1000) 202	of polyimide with IR and UV laser	42 (1000) 252
tures	41/42 (1989) 383	radiation	43 (1989) 352
S. Nadahara, J. Shiozawa, K. Imai, K.		H. Dupendant, J.P. Gavigan, D. Givord,	
Suguro and K. Yamabe, Protuberance		A. Lienard, J.P. Rebouillat and Y.	
growth at polysilicon surfaces during		Souche, Velocity distribution of mi-	
oxidation	41/42 (1989) 425	cron-size particles in thin film laser	
S. Tatarenko, J. Cibert, Y. Gobil, G.		ablation deposition (LAD) of metals	
Feuillet, K. Saminadayar, A.C. Chami		and oxide superconductors	43 (1989) 369
and E. Ligeon, RHEED, XPS,		T. Ito, T. Yasumatsu and A. Hiraki, Ho-	
HRTEM and channeling studies of		moepitaxial growth of silicon on	
molecular beam epitaxy growth of		anodized porous silicon	44 (1990) 97
CdTe on (001) GaAs	41/42 (1989) 470	J.M. Gómez-Rodríguez, A.M. Baró and	
T. Sasaki, T. Matsuoka and A. Katsui,		V.P. Parkhutik, Morphology of porous	
MOVPE-grown GaN on polar planes		silicon studied by STM/SEM	44 (1990) 185
of 6H-SiC	41/42 (1989) 504	V.V. Tokarev, A.I. Demchenko, A.I.	
	,		

Ivanov and V.E. Borisenko, Influence of boron implantation on phase trans-		berger, Laser evaporation of metal sandwich layers for improved IC	
formations in nickel silicides  A.R. de Wit, M.D. Janssen and J.J. Kelly,  Electrochemical characterization of	44 (1990) 241	metallization  Y. Horiike, T. Ichihara and H. Sakaue, Filling of Si oxide into a deep trench	46 (1990) 163
polycrystalline ZnO layers  M. Wolpers, H. Viefhaus and M. Stratmann, SEM and SAM imaging of	45 (1990) 21	using digital CVD method  E. Fogarassy, A. Slaoui, C. Fuchs and J.P.  Stoquert, Deposition of SiO <sub>2</sub> by reac-	46 (1990) 168
silane LB films on metallic substrates I. Kusunoki, M. Hiroi, T. Sato, Y. Igari	45 (1990) 167	tive excimer laser ablation from a SiO target	46 (1990) 195
and S. Tomoda, SiC film formation on Si(001) by reaction with C <sub>2</sub> H <sub>2</sub> beams Xin Xu and J.I. Steinfeld, UV-laser photodeposition of iron films from	45 (1990) 171	A. Boelle, J.A. Roger, B. Canut, J. Mugnier and M. Pitaval, Sol-gel low-temperature preparation of silica films: RBS, TEM and MOS C-V	
Fe(CO) <sub>5</sub> : role of gas-phase and surface dissociation processes  F. Schmaderer, R. Huber, H. Oetzmann	45 (1990) 281	characterization  J. Elders, D. Bebelaar and J.D.W. van Voorst, Photochemical vapor deposi-	46 (1990) 200
and G. Wahl, High- $T_c$ YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-<math>\delta</math></sub> prepared by chemical vapour deposi-	46 (1990) 53	tion of titaniumdiboride F. Curcio, M. Musci, N. Notaro and G.	46 (1990) 215
tion A.R. Krauss, O. Auciello, A.I. Kingon, M.S. Ameen, Y.L. Liu, T. Barr, T.M. Graettinger, S.H. Rou, C.S. Soble and	40 (1990) 33	De Michele, Synthesis of ultrafine TiO <sub>2</sub> powders by a CW CO <sub>2</sub> laser K. Hesch, P. Hess, H. Oetzmann and C. Schmidt, Laser CVD of a-Si:H from	46 (1990) 225
D.M. Gruen, Computer-controlled ion beam deposition systems for high $T_c$ superconductor and other multi-com-		SiH <sub>4</sub> and Si <sub>2</sub> H <sub>6</sub> : relations between chemistry, growth rate and film properties	46 (1990) 233
ponent oxide thin films and layered structures	46 (1990) 67	M. Zeman, I. Ferreira, M.J. Geerts and J.W. Metselaar, The influence of de-	40 (1770) 233
P.E. Dyer, A. Issa and P.H. Key, An investigation of laser ablation and deposition of Y-Ba-Cu-O in an oxygen	44 44000	position parameters on the growth of a-SiGe:H alloys in a plasma CVD sys- tem	46 (1990) 245
environment Y. Morishige, S. Kitamura and S. Kishida, High performance contact formation	46 (1990) 89	<ul> <li>C.N. Afonso, R. Serna, F. Catalina and</li> <li>D. Bermejo, Good-quality Ge films</li> <li>grown by excimer laser deposition</li> </ul>	46 (1990) 249
in LSI circuit restructuring using visi- ble pulse laser induced ablation and CVD	46 (1990) 108	H. Hiraoka and S. Lazare, Surface modifications of Kapton and cured polyimide films by ArF excimer laser: applications to improving watting and	
A. Bauer, J. Ganz, K. Hesse and E. Köhler, Laser-assisted deposition for electronic packaging applications	46 (1990) 113	plications to imagewise wetting and metallization  M. Bolle, K. Luther, J. Troe, J. Ihlemann	46 (1990) 264
A.F. Bernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip packaging for very-high-speed digital		and H. Gerhardt, Photochemically as- sisted laser ablation of doped poly- methyl-methacrylate D. Korzec, T. Kessler and J. Engemann,	46 (1990) 279
systems  R. Putzar, HC. Petzold and H. Staiger, Optimization of the laser-induced de-	46 (1990) 121	Reactive ion beam etching of Si/SiO <sub>2</sub> systems using SF <sub>6</sub> /O <sub>2</sub> chemistry H.M. Hütten, KD. Raddatz, M.K.	46 (1990) 299
position technique for its application in X-ray mask repair H.G. Müller, K. Buschick, S. Schuler and	46 (1990) 131	Sharma and J. Engemann, On the two- and three-dimensional simulation of ion-milled structures	46 (1990) 306
A. Paredes, Laser direct writing of copper on various thin-film substrate materials	46 (1990) 143	W. Kesting, T. Bahners and E. Scholl- meyer, Controlled structuring of poly- mer surfaces by UV-laser irradiation	46 (1990) 326
M. Bode, E.W. Kreutz and M. Krösche, Direct writing of conducting traces by chemical modification of solid coat-	(1770) 143	J. Davenas, G. Boiteux, J.M. Bureau and D. Broussoux, Ion-beam-assisted for- mation of interconnections into high	(1770) 520
ings with laser radiation  R. Pielmeier, D. Bollmann and K. Ha-	46 (1990) 148	temperature polymers  J. Breuer, S. Metev, G. Sepold, OD.	46 (1990) 330

Hennemann, H. Kollek and G. Krüger, Laser-induced photochemical ad- herence enhancement H. Hiraoka and S. Lazare, Applications	46 (1990) 336	between aluminium and polyethylene- terephthalate by XPS  B. Heens, Ch. Grégoire, J.J. Pireaux, P.A. Cornelio and J.A. Gardella, Jr., On	47 (1991) 149
of doping and dedoping of Teflon AF films in microfabrication using KrF and ArF excimer lasers  E.J. Petit and R. Caudano, Chemical re- actions at solid-solid interfaces in-	46 (1990) 342	the stability and homogeneity of Langmuir-Blodgett films as models of polymers and biological materials for surface studies: an XPS study R. Bartlett, H. Jaeger, B.A. Sexton, R.P.	47 (1991) 163
duced by pulsed laser annealing  E. D'Anna, G. Leggieri, A. Luches, M. Martino, A.V. Drigo, G. Majni, P. Mengucci and I.N. Mihailescu, Nitri-	46 (1990) 357	Netterfield and P.J. Martin, A scan- ning tunnelling and transmission elec- tron microscopy comparison of the surface structure of evaporated and	47 (1001) 197
dation of titanium by multipulse excimer laser irradiation  J. Solis, C.N. Afonso and F. Catalina,	46 (1990) 365	ion-assisted gold films H.J. Grabke, D. Wiemer and H. Viefhaus, Segregation of sulfur during growth of	47 (1991) 187
The influence of the substrate on the transformations induced in Si by nanosecond laser irradiation: a time-	47 (1000) 383	oxide scales  W.J. Quadakkers, J. Jedlinski, K. Schmidt,  M. Krašovec, G. Borchardt and H.	47 (1991) 243
resolved study O. Bostanjoglo and P. Thomsen-Schmidt,	46 (1990) 383	Nickel, The effect of implanted yt- trium on the growth and adherence of	
Time-resolved TEM of laser-induced structural changes in GeTe films V. Dupuis, M.F. Ravet, C. Tête and M.	46 (1990) 392	alumina scales on Fe-20Cr-5Al  K. Nishimori, H. Tokutaka, H. Sumi and N. Ishihara, Interface reaction of Si	47 (1991) 261
Piecuch, Thermal evolution of W/Si and W/C multilayers under pulsed laser heating and classical annealing	46 (1990) 398	thin film on Au substrate  S. Nagashima, E. Fukuchi and I. Ogura, Growth modes of overlayers of Se de-	47 (1991) 365
R. Serna, C.N. Afonso, F. Catalina, N. Teixeira, M.F. da Silva and J.C. Soares, Diffusion and microstructures induced by excimer laser irradiation in	40 (1990) 390	posited on Cu(111) surfaces G.N. Pain, T. Warminski, S. Sulcs, M.S. Kwietniak, D. Gao, S.R. Glanvill, C.J. Rossouw, A.W. Stevenson, S.P. Russo,	48/49 (1991) 44
Ge-Sb thin film bilayers  I. Zouari, M. Calvo, F. Lapicque and M. Cabrera, Morphological improvement	46 (1990) 405	R.G. Elliman, L.S. Wielunski, R.S. Rowe, G.B. Deacon, R.S. Dickson and B.O. West, Characterization of low-	
of zinc electrodeposits by laser assistance  J. Marfaing, W. Marine, B. Vidal, M.	46 (1990) 411	temperature MOCVD $Cd_{1-x}Mn_xTe$ thin films  Y. Matsuda, K. Fujita and S. Hinotani,	48/49 (1991) 76
Toulemonde, M. Hage Ali and J.P. Stoquert, Instability and structural transformation of amorphous ultra-		Raman studies on GaAs epitaxial films on Si Y. Shigesato, S. Takaki and T. Haranou,	48/49 (1991) 231
thin W-Si multilayer structures dur- ing heavy ion irradiation	46 (1990) 422	Crystallinity and electrical properties of tin-doped indium oxide films de-	
C. Buerhop, B. Blumenthal, R. Weissmann, N. Lutz and S. Biermann, Glass surface treatment with excimer and		posited by DC magnetron sputtering S. Berger, Y. Komem and B.Z. Weiss, On the microstructure, composition and	48/49 (1991) 269
CO <sub>2</sub> lasers M. Wolpers, H. Viefhaus and M. Stratmann, Surface analytical investiga-	46 (1990) 430	electrical properties of Al/TiW/poly- Si system  A. Mansour, G. Indlekofer and P. Oelha-	48/49 (1991) 281
tions of metal surfaces modified by Langmuir-Blodgett films of silanes J. Eymery, C. Senillou, J.C. Joud and A.	47 (1991) 49	fen, Investigation of the electronic structure of thin diamond films by photoelectron spectroscopy	48/49 (1991) 312
Chamberod, An Auger depth profile analysis of a sputtered Fe-Ti multi-		C.H. Champness and W.R. Clark, Anomalous inductive effect in Se-metal	
layer structure  M. Bou, J.M. Martin, Th. Le Mogne and L. Vovelle, Chemistry of the interface	47 (1991) 127	contacts  E. Gofuku, Y. Toyoda, Y. Uehara, M. Kohara and M. Nunoshita, Highly	48/49 (1991) 337

conductive TiO2 thin films prepared		Couret, TEM in-situ observation of	
by EB-modification	48/49 (1991) 343	recombination-enhanced mobility of	50 (4004) 440
M. Arienzo, S.S. Iyer, B.S. Meyerson, G.L.		dislocations in II-VI compounds	50 (1991) 119
Patton and J.M.C. Stork, Si-Ge al-		P. Ossart and E.V.K. Rao, Investigation	
loys: growth, properties and applica-	49 (40 (1001) 277	of surface and sub-surface defects on	
tions	48/49 (1991) 377	polished InP substrates using Auger	
A. Hishinuma, T. Goda, M. Kitaoka, S. Hayashi and H. Kawahara, Formation		electron spectroscopy coupled to argon ion sputtering	50 (1991) 125
of silicon dioxide films in acidic solu-		Y. Gao, I. Ardelean, D. Renard, B. Rose	30 (1991) 123
tions	48/49 (1991) 405	and Y. Jin, High-depth-resolution	
T. Yasumatsu, T. Ito, H. Nishizawa and	40/49 (1991) 403	SIMS analysis for InGaAs/InP inter-	
A. Hiraki, Ultrathin Si films grown		faces	50 (1991) 131
epitaxially on porous silicon	48/49 (1991) 414	J. Schreiber, W. Hergert and S. Hilde-	30 (1),11
H. Tokutaka and S. Kishida, Surface	10/ 12 (1221) 111	brandt, Combined application of	
characterization of Bi-based high- $T_c$		SEM-CL and SEM-EBIC for the in-	
superconducting thin films and bulk		vestigation of compound semiconduc-	
single crystals	48/49 (1991) 425	tors	50 (1991) 181
N. Hamaguchi, R. Gardiner and P.S.	(	A. Dimoulas, A. Derekis, G. Kyriakidis	
Kirlin, MOCVD of TlBaCaCuO su-		and A. Christou, Alloy disorder ef-	
perconducting thin films: structure-		fects in III-V ternaries studied by	
property-processing relationships	48/49 (1991) 441	modulation spectroscopy	50 (1991) 353
S. Kishida, H. Tokutaka, H. Higashi, K.		C. Raisin, A. Rocher, G. Landa, R. Carles	
Nishimori and N. Ishihara, Prepara-		and L. Lassabatere, GaSb/GaAs het-	
tion conditions of flat 80 K phase		eroepitaxy characterized as a stress-	
Bi-Sr-Ca-Cu-O thin films by RF		free system	50 (1991) 434
magnetron sputtering	48/49 (1991) 446	R. Schwarz, T. Fischer, P. Hanesch, T.	
T. Hosaka, Effects of impurities in a two-		Muschik, J. Kolodzey, H. Cerva, H.L.	
layer evaporated Au film on its tensile		Meyerheim and B.M.U. Scherzer,	
fracture	48/49 (1991) 502	Limitations of interface sharpness in	
I. Dalins, M. Karimi and D. Ila, Violent		a-Si:H/a-SiC:H multilayers	50 (1991) 456
oxidation of lithium-containing alumi-		A. Castaldini, A. Cavallini, E. Gombia, R.	
num alloys in liquid oxygen	48/49 (1991) 509	Mosca and L. Tarricone, Evaluation	
R.B. Gore, R.K. Pandey and S.R. Kumar,		of the diffusion length of minority car-	
Preparation and characterisation of		riers in bulk GaAs	50 (1991) 485
nearly stoichiometric CdTe films from	10 110 11001 200	C. De las Heras, I.J. Ferrer and C.	
a non-aqueous electrodeposition bath	48/49 (1991) 530	Sánchez, Comparison of pyrite thin	
C. Feldman, G. Deutscher and E.		films obtained from Fe and natural	50 (1001) 505
Grünbaum, Single-crystal transforma-		pyrite powder	50 (1991) 505
tion of sphalerite CdS to cubic phase	40 (40 (1001) 525		
Cu <sub>x</sub> S	48/49 (1991) 535	Electron scattering	
H. Cerva, Transmission electron mi-			
croscopy of heteroepitaxial layer	50 (1991) 19	A.L. Tofterup, Estimates of errors and	
structures I.T. McGovern, Soft X-ray photoelectron	30 (1991) 19	validity of Shirley-type backgrounds	44 (1990) 157
spectroscopy of compound semicon-			
ductor surfaces and interfaces	50 (1991) 34	Electron spin resonance	
P. Auvray, A. Poudoulec, M. Baudet, B.	30 (1771) 34	and the second s	
Guenais, A. Regreny, C. d'Anter-		T. Nakamura, Y. Takeuchi, H. Mura-	
roches and J. Massies, Interface		matsu, H. Fujiyasu and Y. Nakanishi,	
roughness of GaAs/AlAs super-		ESR studies on luminescent ZnS:Mn	
lattices MBE-grown on vicinal surfaces	50 (1991) 109	films and CdS-ZnS:Mn superlattices	
C. Frigeri, J.L. Weyher and M. De Potter,	30 (1371) 107	deposited on a GaAs(100) substrate	
TEM study of the origin of the surface		by hot-wall epitaxy	48/49 (1991) 478
microroughness in DSL photoetched		H. Mimura, K. Sai, Y. Ohta, K. Yamamo-	, , , , , , , , , , , , , , , , , , , ,
Si-implanted GaAs wafers	50 (1991) 115	to and K. Kitamura, A two-dimen-	
C. Levade, J.J. Couderc, G.	,	sional image sensor with a-Si:H pin	
Vanderschaeve, D. Caillard and A.		diodes	48/49 (1991) 521

S.J.C.H.M. van Gisbergen, M. Godlewski, T. Gregorkiewicz and C.A.J. Ammerlaan, Interstitial Mn as a new donor in GaP and GaAs: an EPR study T. Benchiguer, E. Christoffel, A. Goltzené,	50 (1991) 273	Hydrogen plasma treatment of silicon surfaces studied by in-situ spectro- scopic ellipsometry  T. Easwarakhanthan, Z. Ouennoughi, M. Renard and J.R. Cussenot, Characteri- zation of double-layer transparent	46 (1990) 435
<ul> <li>B. Mari, B. Meyer and C. Schwab,</li> <li>Donor-acceptor charge transfers in bulk semi-insulating GaAs as revealed by photo-EPR</li> <li>B. Meyer, P. Omling and P. Emanuelsson,</li> </ul>	50 (1991) 277	films on absorbing substrates using multiple-angle ellipsometry  A.R. Balkenende, H. den Daas, M. Huisman, O.L.J. Gijzeman and J.W. Geus,  The interaction of NO, O <sub>2</sub> and CO	47 (1991) 299
Landau oscillations in single quantum wells observed by microwave detection	50 (1991) 420	with Cu(100) and Cu(110)  K. Jezierski, Z. Gumienny and J. Misiewicz, Reflectometry-aided surface	47 (1991) 341
Electron stimulated desorption		layer investigation C. Pickering, N.S. Garawal, D. Lance- field, J.P. Piel and R. Blunt, Non-de-	50 (1991) 341
J.A. Kelber, J.W. Rogers, Jr., B.A. Banse and B.E. Koel, Interaction of dimeth- ylamine with clean and partially		structive characterisation of (Ga,In, Al,As,P)-based ternary multilayer structures using spectroscopic el-	50 (1991) 346
oxidized copper surfaces  J.H. Craig, Jr. and J. Lozano, Effect of oxygen on chemisorption of CO on	44 (1990) 193	lipsometry H.W. Dinges, B. Kempf, H. Burkhard and R. Göbel, Determination of ion beam etching damage on InP by spec-	30 (1991) 340
Rh(100)	45 (1990) 151	troscopic ellipsometry	50 (1991) 359
Ellipsometry		Epitaxy	
<ul> <li>J.L. Freeouf, The analysis of complex samples by spectroscopic ellipsometry</li> <li>Y. Hatanaka, K. Mitsuoka and T. Yamaguchi, Properties of a-Si:H based in-</li> </ul>	41/42 (1989) 323	ST. Li, S. Hasegawa, N. Yamashita and H. Nakashima, Initial stages of aluminum epitaxy on the Si(111) $\sqrt{3} \times \sqrt{3}$ -Al surface studied by electron-energy-loss	
terface transient layers measured by in-situ ellipsometry  M. Gendry, J. Durand, M. Erman, J.B.	41/42 (1989) 591	spectroscopy R.T. Tung and F. Schrey, Epitaxial CoSi <sub>2</sub> /Si(111) interfaces	41/42 (1989) 118 41/42 (1989) 223
Theeten, L. Nevot and B. Pardo, Chemical and structural analysis by ellipsometry and X-ray reflectometry		I. Yamada, Interfacial structure of ICB epitaxially deposited Al(110) bicrystal films on Si(100) substrates	41/42 (1989) 253
of thin sulfide layers grown on InP S. Deckers, F.H.P.M. Habraken, W.F. van der Weg and J.W. Geus, Oxidation of	44 (1990) 309	M. Itoh, M. Kinoshita, T. Ajioka, M. Itoh and T. Inada, Crystalline quality of heteroepitaxial silicon on epitaxial	41/42 (1707) 233
clean and Pt-covered Ni(111)  J.A. Treverton and A. Rosenfeld, Determination of etching characteristics of a Vacuum Generators AG21 argon-	45 (1990) 207	NiSi <sub>2</sub> /Si(100)  S. Hongo, Y. Kataoka, T. Urano and T. Kanaji, Evaluation by resonant light scattering of ZnTe epitaxial layer de-	41/42 (1989) 262
ion gun by interference colour and ellipsometric assessment of craters etched in tantalum oxide films	45 (1990) 263	posited on GaAs  C. Tatsuyama, T. Tanbo and N. Nakayama, Heteroepitaxy between layered	41/42 (1989) 522
<ul> <li>T. Szörényi, P. González, D. Fernández,</li> <li>J. Pou, B. León and M. Pérez-Amor,</li> <li>Gas mixture dependence of the LCVD</li> </ul>		semiconductors GaSe and InSe H. Kumomi, T. Yonehara, Y. Nishigaki and N. Sato, Selective nucleation	41/42 (1989) 539
of SiO <sub>2</sub> films using an ArF laser  B. León, A. Klumpp, M. Pérez-Amor and  H. Sigmund, Excimer laser deposition of silica films: a comparison between	46 (1990) 206	based epitaxy (Sentaxy). Investigation of initial nucleation stages  I. Yamada, Growth processes of epitaxial metal films on semiconductor and in-	41/42 (1989) 638
two methods P. Raynaud, J.P. Booth and C. Pomot,	46 (1990) 210	sulator substrates by ionized cluster beam	43 (1989) 23

## Etching

Etching		Surface temperature measurements using pyrometry during excimer laser	
T. Hattori, H. Yamagishi, N. Koike, K.		pulsed etching of silicon in a Cl <sub>2</sub> en-	
Imai and K. Yamabe, Structural stud-		vironment	46 (1990) 292
ies of ultrathin silicon oxides and their		D. Korzec, T. Kessler and J. Engemann,	
interfaces by XPS	41/42 (1989) 416	Reactive ion beam etching of $Si/SiO_2$ systems using $SF_6/O_2$ chemistry	46 (1990) 299
T.S. Baller and J. Dieleman, Nanosecond		A. Ermolieff, F. Martin, A. Amouroux, S.	40 (1770) 277
excimer laser-enhanced chemical etch-	43 (1989) 409	Marthon and J.F.M. Westendorp,	
ing J. Meiler, R. Matz and D. Haarer, Laser-	43 (1989) 409	Surface composition analysis of HF	
induced photochemical etching of InP		vapour cleaned silicon by X-ray pho-	40 /40 /4004 470
by HBr and HCl	43 (1989) 416	toelectron spectroscopy H. Mimura, K. Sai, Y. Ohta, K. Yamamo-	48/49 (1991) 178
J. Boulmer, B. Bourguignon, J.P. Budin		to and K. Kitamura, A two-dimen-	
and D. Debarre, Time of flight study		sional image sensor with a-Si:H pin	
of low pressure laser etching of silicon by chlorine	43 (1989) 424	diodes	48/49 (1991) 521
G.C. Tyrrell, I.W. Boyd and R.B. Jack-	43 (1909) 424	R. Fornari, N. Tchandjou, P. Gall and	
man, Ion beam assisted etching of		J.M. Lussert, A study of structural	
silicon with bromine. The role of the		properties of bulk double-doped InP by laser scattering tomography and	
adsorbed state	43 (1989) 439	photoetching	50 (1991) 207
S. Suzuki and M. Oku, Surface orienta-		M. Baumgartner and K. Löhnert, Char-	( , , , , , , , , , , , , , , , , , , ,
tion dependence of the surface com- position in an Fe-20%Cr alloy and an		acterization of si-GaAs wafer quality	
Fe-3%Si alloy treated by mechanical		by room-temperature photolumines-	#0 (#00#) ###
polishing and chemical etching	44 (1990) 151	Cence	50 (1991) 222
Ch. Cardinaud and G. Turban, Mechanis-		H.P. Zappe and G. Kaufel, Reactive-ion- etch damage in GaAs processing	
tic studies of the initial stages of etch-		evaluated by a microwave absorption	
ing of Si and SiO <sub>2</sub> in a CHF <sub>3</sub> plasma	45 (1990) 109	technique	50 (1991) 290
R.M. Wallace, C.C. Cheng, P.A. Taylor, W.J. Choyke and J.T. Yates, Jr., Ni		H.W. Dinges, B. Kempf, H. Burkhard	
impurity effects on hydrogen surface		and R. Göbel, Determination of ion	
chemistry and etching of Si(111)	45 (1990) 201	beam etching damage on InP by spec-	50 (1991) 359
J.A. Treverton and A. Rosenfeld, De-		troscopic ellipsometry	30 (1991) 339
termination of etching characteristics		Eductors	
of a Vacuum Generators AG21 argon- ion gun by interference colour and		Ethylene	
ellipsometric assessment of craters		DE Bamahan Fridayan for continul C	
etched in tantalum oxide films	45 (1990) 263	D.E. Ramaker, Evidence for vertical C <sub>2</sub> on Ni as a precursor for graphite	
Y. Morishige, S. Kitamura and S. Kishida,		nucleation	48/49 (1991) 351
High performance contact formation			
in LSI circuit restructuring using visi-		Evaporation	
ble pulse laser induced ablation and CVD	46 (1990) 108		
Y. Horiike, T. Ichihara and H. Sakaue,	40 (1990) 100	W. Marine, M. Peray, Y. Mathey and D.	
Filling of Si oxide into a deep trench		Pailharey, Deposition of Y-Ba-Cu	
using digital CVD method	46 (1990) 168	oxide superconducting thin films by	
W. Marine, J.M. Scotto D'Aniello and J.		Nd:YAG laser evaporation	43 (1989) 377
Marfaing, Picosecond YAG laser pho-	46 (1000) 220	A. Mele, D. Consalvo, D. Stranges, A.	
toablation of amorphous silicon G. Ulmer, B. Hasselberger, HG. Bus-	46 (1990) 239	Giardini-Guidoni and R. Teghil, Cluster ion formation by laser evaporation	
mann and E.E.B. Campbell, Excimer		of solid complex oxides	43 (1989) 398
laser ablation of polyimide	46 (1990) 272	R. Bartlett, H. Jaeger, B.A. Sexton, R.P.	,
M. Bolle, K. Luther, J. Troe, J. Ihlemann		Netterfield and P.J. Martin, A scan-	
and H. Gerhardt, Photochemically as-		ning tunnelling and transmission elec-	
sisted laser ablation of doped poly- methyl-methacrylate	46 (1990) 279	tron microscopy comparison of the surface structure of evaporated and	
T.S. Baller, J.C.S. Kools and J. Dieleman,	40 (1770) 217	ion-assisted gold films	47 (1991) 187
,			()

<ul> <li>M. Takeuchi, M. Masui and Y. Momose, Copper-phthalocyanine thin film pho- toelectrochemical cells</li> <li>M. Takeuchi, Y. Watanabe and S. Ozawa, Gas-sensitive properties of ultrafine</li> </ul>	48/49 (1991) 517	<ul> <li>R. Ludeke, A. Taleb-Ibrahimi and G. Jezequel, Delocalization of defects: a new model for the Schottky barrier</li> <li>N. Esser, M. Hünermann, U. Resch, D. Spaltmann, J. Geurts, D.R.T. Zahn,</li> </ul>	41/42 (1989) 151
In <sub>2</sub> O <sub>3</sub> particle layers prepared by gas evaporation technique		W. Richter and R.H. Williams, Bismuth on GaAs(110): characterisation of growth mode and Schottky barrier	
Field ion microscopy		formation at low and room tempera- ture  J. Christen, M. Grundmann and D. Bim-	41/42 (1989) 169
E.M. Perry, D.L. Cocke and M.K. Miller, The oxidation of Ni <sub>3</sub> Zr investigated by atom-probe field-ion microscopy and X-ray photoelectron spectroscopy	44 (1990) 321	berg, Direct imaging and theoretical modelling of the atomistic morpho- logical and chemical structure of semi-	
T. Hashizume, Y. Hasegawa and T. Sakurai, Alkali-metal adsorption on silicon surfaces studied by field ion-	44 (1990) 321	R. Haight and J.A. Silberman, Surface intervalley scattering on GaAs(110) studied with picosecond laser photo-	41/42 (1989) 329
scanning tunneling microscopy (FI-	49 (40 (1001) 110	emission	41/42 (1989) 487
STM) D.G. Ren, Study of interface structure of the oxide grown on nickel alloys by AP-FIM	48/49 (1991) 119 48/49 (1991) 227	T. Takeuchi, C. Maezawa, T. Nomura, K. Ishikawa, M. Miyao and M. Hagino, Raman study of strain distribution in interface region of GaAs/GaP hetero-	
R.A.D. Mackenzie, J.A. Liddle and C.R.M. Grovenor, Ultrahigh resolu- tion characterisation of compound	13, 11 (1111) 221	epitaxial layers grown by MBE  H.C. Lee, H. Ishiwara, S. Furukawa, K. Saiki and A. Koma, Distribution of	41/42 (1989) 530
semiconductors using pulsed laser atom probe techniques	50 (1991) 196	interfacial As atoms in the electron- beam exposure and epitaxy (EBE-epi- taxy) technique for growing GaAs films on CaF <sub>2</sub> /Si(111) structures	41/42 (1989) 553
Fluorides		K. Maehashi, S. Hasegawa and H.	41/42 (1989) 333
B.V. King, D.J. O'Connor, Y. Shen, R.J. MacDonald, M. Katayama and M. Aono, LEIS for structure determination of surfaces and thin films	48/49 (1991) 246	Nakashima, Atomic rearrangement during the initial stages of GaAs growth on $Si(111)(\sqrt{3} \times \sqrt{3})$ -Ga surface  N. Eleftheriadis, HP. Ludescher, M.	41/42 (1989) 567
Calliana antimonida		Süssbauer and D. von der Linde, Pico-	46 (1000) 204
Gallium antimonide		second time-resolved laser desorption G. Shimaoka, MEED studies of thin metal	46 (1990) 284
C. Raisin, A. Rocher, G. Landa, R. Carles and L. Lassabatere, GaSb/GaAs het- eroepitaxy characterized as a stress-		film covered semiconductor surfaces Y. Matsuda, K. Fujita and S. Hinotani, Raman studies on GaAs epitaxial films	48/49 (1991) 190
free system	50 (1991) 434	on Si D. Heskett, D. Tang, A.B. McLean, R.	48/49 (1991) 231
Gallium arsenide		Ludeke, M. Prietsch, T. Maeda Wong, E.W. Plummer and N.J. DiNardo, Metal-induced states on the GaAs-	
W.E. Spicer, R. Cao, K. Miyano, T. Kendelewicz, I. Lindau, E. Weber, Z. Liliental-Weber and N. Newman, From synchrotron radiation to <i>I-V</i> measurements of GaAs Schottky bar-		<ul> <li>(110) surface probed by angle-resolved photoemission spectroscopy</li> <li>D. Mao, A. Kahn, M. Marsi and G. Margaritondo, Synchrotron radiation induced surface photovoltage at</li> </ul>	48/49 (1991) 260
rier formation	41/42 (1989) 1	metal/GaAs interfaces	48/49 (1991) 324
X.M. Ding, G.S. Dong, X.K. Lu, H.Y. Xiao, P. Chen and X. Wang, Application of HREELS to Al/GaAs and		Y. Hatanaka, Heterostructures with hy- drogenated amorphous silicon for use in imaging devices	48/49 (1991) 457
Al/GaP interfaces	41/42 (1989) 123	J. Matsui, Study of strain variation in	

LEC-grown GaAs bulk crystals by synchrotron radiation X-ray topogra- phy	50 (1991) 1	T.S. Horányi, P. Tüttö and G. Endrédi, Improved method for depth profiling of multilayer structures	50 (1991) 143
P.F. Fewster, Multicrystal X-ray diffrac-	50 (1991) 9	J.S. Rimmer, M. Missous and A.R. Peaker,	30 (1371) 143
tion of heteroepitaxial structures H. Cerva, Transmission electron mi-	30 (1991) 9	A new, fast method for the computer simulation of CV profiles in multi-	
croscopy of heteroepitaxial layer		layer structures	50 (1991) 149
structures	50 (1991) 19	W. Pfeiffer, M. Deicher, R. Keller, R.	30 (1991) 149
C.T. Foxon, Control of MBE, MOMBE	(2,7,2)	Magerle, P. Pross, H. Skudlik, Th.	
and CBE growth using RHEED	50 (1991) 28	Wichert, H. Wolf, D. Forkel, N.	
I.T. McGovern, Soft X-ray photoelectron	,	Moriya and R. Kalish, Characteriza-	
spectroscopy of compound semicon-		tion of Cd implanted and annealed	
ductor surfaces and interfaces	50 (1991) 34	GaAs and InP by perturbed angular	
C. Grattepain and A.M. Huber, Sec-		correlation (PAC) spectroscopy	50 (1991) 154
ondary ion mass spectrometry of		A. Baurichter, M. Deicher, S. Deubler, D.	
dopants and impurities in compound		Forkel, J. Meier, H. Wolf, W. Witt-	
semiconductors: depth profiling of		huhn and ISOLDE Collaboration, Mi-	
homo- and heterostructure	50 (1991) 42	croscopical studies at cadmium impur-	
H.G. Grimmeiss and M. Kleverman,		ities in compound semiconductors	50 (1991) 165
Electrical and optical defect spec-		J. Schreiber, W. Hergert and S. Hilde-	
troscopy of compound semiconduc-		brandt, Combined application of	
tors	50 (1991) 52	SEM-CL and SEM-EBIC for the in-	
R.A. Stradling, Far-infrared spectroscopy		vestigation of compound semiconduc-	
of impurities in semiconductors	50 (1991) 65	tors	50 (1991) 181
G. Abstreiter, Micro-Raman spectroscopy		M. Baumgartner and K. Löhnert, Char-	
for characterization of semiconductor	50 (1001) 73	acterization of si-GaAs wafer quality	
devices	50 (1991) 73	by room-temperature photolumines-	50 (1001) 222
J. Wagner, Raman spectroscopy for im-		cence	50 (1991) 222
purity characterization in III-V semi- conductors	50 (1991) 79	Z.M. Wang, J. Windscheif, D.J. As and W. Jantz, Ambient and low tempera-	
R. Zaus, M. Schuster, H. Göbel and JP.	30 (1991) 79	ture photoluminescence topography of	
Reithmaier, Characterization of (In,		GaAs substrates, epitaxial and im-	
Ga)As/GaAs strained-layer multiple		planted layers	50 (1991) 228
quantum wells with high-resolution		N. Ohnishi, Y. Makita, A. Yamada, H.	30 (1771) 220
X-ray diffraction and computer simu-		Asakura and T. Matsumori, Effect of	
lations	50 (1991) 92	substrate orientation on the defect-in-	
N. Herres, G. Bender and G. Neumann,	()	duced bound exciton emissions in	
Assessment of mismatched epitaxial		GaAs grown by molecular beam epi-	
layers by X-ray rocking curve mea-		taxy	50 (1991) 233
surements and simulations	50 (1991) 97	G. Strasser, S. Dubois, M. Besson, E.	
A.M. Keir, S.J. Barnett, J. Giess, T.D.		Gornik, G. Weimann, E. Bauser and	
Walsh and M.G. Astles, A combina-		H. Riechert, Analysis of impurity dis-	
tion of high-resolution X-ray dif-		tribution in n-GaAs layers by photo-	
fractometry and diffraction imaging		conductivity and cyclotron resonance	
techniques applied to the study of		measurements	50 (1991) 261
MOVPE-grown $Cd_xHg_{1-x}Te/CdTe$		D.I. Desnica, B. Šantić and U.V. Desnica,	
on GaAs	50 (1991) 103	Time-evolution of low-temperature	
P. Auvray, A. Poudoulec, M. Baudet, B.		photoconductivity and Hall mobility	
Guenais, A. Regreny, C. d'Anter-		in semi-insulating GaAs	50 (1991) 269
roches and J. Massies, Interface		S.J.C.H.M. van Gisbergen, M. Godlewski,	
roughness of GaAs/AlAs super-	50 (1001) 100	T. Gregorkiewicz and C.A.J. Am-	
lattices MBE-grown on vicinal surfaces	50 (1991) 109	merlaan, Interstitial Mn as a new	
C. Frigeri, J.L. Weyher and M. De Potter,		donor in GaP and GaAs: an EPR	50 (1001) 272
TEM study of the origin of the surface microroughness in DSL photoetched		study T. Benchiguer, E. Christoffel, A. Goltzené,	50 (1991) 273
Si-implanted GaAs wafers	50 (1991) 115	B. Mari, B. Meyer and C. Schwab,	
Si-implanted Gans waters	50 (1991) 115	b. Mail, b. Meyer and C. Schwab,	

Donor-acceptor charge transfers in		activation of shallow Zn acceptors in	
bulk semi-insulating GaAs as revealed		GaAs	50 (1991) 390
by photo-EPR	50 (1991) 277	S. Tüzemen and M.R. Brozel, An investi-	
H.P. Zappe and G. Kaufel, Reactive-ion-		gation of photo-quenching properties	
etch damage in GaAs processing		of LEC GaAs by using optical and	
evaluated by a microwave absorption		electrical techniques	50 (1991) 395
technique	50 (1991) 290	C. Ghezzi, R. Mosca, A. Bosacchi, S.	
B.H. Bairamov, V.A. Voitenko, I.P.		Franchi and E. Gombia, The influence	
Ipatova, V.V. Toporov, G. Irmer, J.		of the DX center on the capacitance	
Monecke and E. Jahne, Characteriza-		of Schottky barriers in n-type AlGaAs	50 (1991) 400
tion of III-V compounds by quasi-		A. Baraldi, C. Ghezzi, A. Parisini, A.	
elastic electronic scattering of light	50 (1991) 300	Bosacchi and S. Franchi, Analysis of	
G.M. O'Connor, C.J. McDonagh, F.G.		electron mobility versus temperature	
Anderson, T.J. Glynn, G.P. Morgan,		after photoexcitation in Si-doped	
G.J. Hughes, L. Roberts and M.O.		$Al_xGa_{1-x}As$	50 (1991) 405
Henry, Raman characterization of		R. Nipoti, D. Pocci, A. Cetronio and C.	
passivated GaAs surfaces	50 (1991) 312	Lanzieri, Carrier and mobility profile	
B. Jusserand and F. Mollot, Confined		measurements in n-type ion-implanted	
optical vibrations: a new probe for		GaAs by the differential sheet resistiv-	
alloy disorder	50 (1991) 317	ity and Hall effect technique	50 (1991) 410
W. Kütt, G.C. Cho, M. Strahnen and H.	()	B. Meyer, P. Omling and P. Emanuelsson,	
Kurz, Electro-optic sampling of		Landau oscillations in single quantum	
surface space-charge fields on III-V		wells observed by microwave detec-	
compounds	50 (1991) 325	tion	50 (1991) 420
P.L. Swart, B.M. Lacquet and R. Thavar,	00 (1771) 020	L. Roberts and G.J. Hughes, An investi-	00 (0272) 120
Physical characterization of OMVPE-		gation of metal/GaAs(100) interfaces	
grown $Al_xGa_{1-x}As$ multi-layer films		by deep level transient spectroscopy	50 (1991) 424
by means of non-destructive optical		D. Lee, S.J. Barnett, A.D. Pitt, M.R.	(
reflectometry	50 (1991) 330	Houlton and G.W. Smith, Characteri-	
S.C. Moss, J.F. Knudsen, R.C. Bowman,	20 (1), 1)	zation of alloy composition in	
Jr., P.M. Adams and D.D. Smith, Pi-		$Ga_{1-x}Al_xAs/GaAs$ structures: com-	
cosecond transient photoreflectance		parison of photovoltage, X-ray, SIMS	
measurements of ion-implanted GaAs	50 (1991) 337	and RHEED techniques	50 (1991) 428
K. Jezierski, Z. Gumienny and J. Mis-	30 (1))1) 331	C. Raisin, A. Rocher, G. Landa, R. Carles	20 (1771) 120
iewicz, Reflectometry-aided surface		and L. Lassabatere, GaSb/GaAs het-	
layer investigation	50 (1991) 341	eroepitaxy characterized as a stress-	
C. Pickering, N.S. Garawal, D. Lance-	30 (1))1) 311	free system	50 (1991) 434
field, J.P. Piel and R. Blunt, Non-de-		D.A. Woolf, D.I. Westwood, M.A. Ander-	30 (1))1) 434
structive characterisation of (Ga,In,		son and R.H. Williams, The molecular	
Al,As,P)-based ternary multilayer		beam epitaxial growth of GaAs(111)/	
structures using spectroscopic el-		Si(111): a variable growth temperature	
lipsometry	50 (1991) 346	study	50 (1991) 445
A. Dimoulas, A. Derekis, G. Kyriakidis	30 (1771) 340	V. Amarger, C. Dubon-Chevallier, A.C.	30 (1771) 443
and A. Christou, Alloy disorder ef-		Papadopoulo, B. Descouts and Y. Gao,	
fects in III-V ternaries studied by		Correlated use of characterization	
modulation spectroscopy	50 (1991) 353	techniques to optimize the Mg implan-	
B. Sartorius, M. Brandstättner and H.	30 (1991) 333	tation annealing for self-aligned HBT's	50 (1991) 462
Venghaus, Two-wavelength transmis-		L.J. Bredell, F.D. Auret, G. Myburg and	30 (1991) 402
sion: a rapid and precise method for		W.O. Barnard, Electrical characteriza-	
measuring the light absorption in		tion of argon-ion sputtered n-GaAs	50 (1991) 466
semiconductors	50 (1991) 369	HG. Hettwer, W. Lerch, B. Lentfort,	30 (1791) 400
M. Wagner, N. Winkler and H.D. Geiler,	30 (1771) 307	N.A. Stolwijk and H. Mehrer, Com-	
Single-beam thermowave analysis of		bined application of spreading-resis-	
semiconductors	50 (1991) 373	tance and electron-microprobe depth	
A.W.R. Leitch, Th. Prescha and M. Stutz-	30 (1991) 373	profiling on GaAs:Zn and Si:P	50 (1991) 470
mann, Hydrogen passivation and re-		M.R. Brozel, L. Breivik, D.J. Stirland,	30 (1771) 470
mann, rryurogen passivation and re-		wi.k. Diozei, L. Dicivik, D.J. Silliand,	

G.M. Williams and A.G. Cullis, Dislo- cation density, infrared absorption and cathodoluminescence mapping of mi-		S.J.C.H.M. van Gisbergen, M. Godlewski, T. Gregorkiewicz and C.A.J. Ammerlaan, Interstitial Mn as a new	
crostructure associated with disloca-		donor in GaP and GaAs: an EPR	
tion cells in semi-insulating LEC GaAs	50 (1991) 475	study	50 (1991) 273
W. Jantz, R. Stibal, J. Windscheif and J.		P. Roura, J.R. Morante, G. Bremond, T.	
Wagner, Variation of material param-		Benyattou, G. Guillot and W. Ulrici,	
eters along the growth direction of		Complete identification of the Ti-re-	
liquid encapsulated Czochralski grown		lated levels in GaP	50 (1991) 496
GaAs ingots	50 (1991) 480		
A. Castaldini, A. Cavallini, E. Gombia, R.		Germanium	
Mosca and L. Tarricone, Evaluation			
of the diffusion length of minority car- riers in bulk GaAs	50 (1991) 485	E. Vlieg and J.F. van der Veen, X-ray	
N. Hizem, G. Bremond, L. Mayet, M.	30 (1991) 463	scattering studies of semiconductor in-	
Gavand, J. Gregoire, G. Guillot and		terfaces: atomic structure and mor-	
W. Ulrici, Identification of the double		phology	41/42 (1989) 62
and single acceptor state of isolated		J.F. Morar, U.O. Karlsson, R.I.G. Uhr-	
Ni <sub>Ga</sub> in GaAs	50 (1991) 490	berg, J. Kanski, P.O. Nilsson and H.	
Ga .	. ,	Qu, Angle-resolved photoemission	
Gallium phosphide		study of the As/Ge(100) interface	41/42 (1989) 312
Guitum phosphiae		M. Berti, G. Mazzi, A.V. Drigo, A.	
VM Ding GS Dong VV In HV		Migliori, E. Jannitti and S. Nicoletti, Laser induced epitaxial regrowth of	
X.M. Ding, G.S. Dong, X.K. Lu, H.Y. Xiao, P. Chen and X. Wang, Applica-		Si <sub>1-x</sub> Ge <sub>x</sub> /Si layers produced by Ge	
tion of HREELS to Al/GaAs and		ion implantation	43 (1989) 158
Al/GaP interfaces	41/42 (1989) 123	M. Zeman, I. Ferreira, M.J. Geerts and	45 (1707) 150
T. Takeuchi, C. Maezawa, T. Nomura, K.	, (,	J.W. Metselaar, The influence of de-	
Ishikawa, M. Miyao and M. Hagino,		position parameters on the growth of	
Raman study of strain distribution in		a-SiGe:H alloys in a plasma CVD sys-	
interface region of GaAs/GaP hetero-		tem	46 (1990) 245
epitaxial layers grown by MBE	41/42 (1989) 530	C.N. Afonso, R. Serna, F. Catalina and	
G. Shimaoka, MEED studies of thin metal		D. Bermejo, Good-quality Ge films	
film covered semiconductor surfaces	48/49 (1991) 190	grown by excimer laser deposition	46 (1990) 249
I.T. McGovern, Soft X-ray photoelectron		O. Bostanjoglo and P. Thomsen-Schmidt,	
spectroscopy of compound semicon-	50 (1001) 24	Time-resolved TEM of laser-induced	46 (1000) 202
ductor surfaces and interfaces	50 (1991) 34	structural changes in GeTe films	46 (1990) 392
A. Baurichter, M. Deicher, S. Deubler, D. Forkel, J. Meier, H. Wolf, W. Witt-		R. Serna, C.N. Afonso, F. Catalina, N. Teixeira, M.F. da Silva and J.C.	
huhn and ISOLDE Collaboration, Mi-		Soares, Diffusion and microstructures	
croscopical studies at cadmium impur-		induced by excimer laser irradiation in	
ities in compound semiconductors	50 (1991) 165	Ge-Sb thin film bilayers	46 (1990) 405
S.G. Jahn, H. Hofsäss, U. Wahl, S. Winter,		P. Ashu and C.C. Matthai, A molecular	
E. Recknagel and ISOLDE Collabora-		dynamics study of the critical thick-	
tion, Structural defect recovery in GaP		ness of Ge layers on Si substrates	48/49 (1991) 39
after heavy ion implantation	50 (1991) 169	N. Ohshima, Y. Koide, S. Zaima and Y.	
A. Gustafsson, S. Nilsson and L. Samuel-		Yasuda, Formation of a superstruc-	
son, Intensity variations in the near-		ture in the initial stage of Ge epitaxial	
band-edge recombination of GaP epi-		growth on Si(100) substrates	48/49 (1991) 69
taxial layers, grown on (111) and (001)		K. Oishi, K. Fukuchi, T. Suzuki and J.	
oriented substrates, as observed by	50 (1001) 106	Sunada, Mechanism of photoconduc-	49 (40 (1001) 276
cathodoluminescence imaging	50 (1991) 186	tion on surface-oxidized Ge films	48/49 (1991) 276
B.J. Heijmink Liesert, M. Godlewski, T. Gregorkiewicz and C.A.J. Ammerlaan,		Zhang Rong, Zheng Youdou, Jiang Ruolian, Hu Liqun, Zhong Peixin, Yu	
Neutron transmutation doping of		Shidong, Li Qi, Feng Duan and Chen	
GaP: optical studies	50 (1991) 245	Guangxi, The structure of $Ge_xSi_{1-x}$	
T. Monteiro and E. Pereira, Complex for-	(-//-/ - 10	Si strained layer superlattices and het-	
mation in Mn-doped GaP samples	50 (1991) 253	erostructures	48/49 (1991) 356

, ,	,,		
M. Arienzo, S.S. Iyer, B.S. Meyerson, G.L. Patton and J.M.C. Stork, Si-Ge alloys: growth, properties and applications	48/49 (1991) 377	noble metals determined by reflection electron energy loss spectroscopy A. Bukaluk and W. Bała, AES depth pro- file studies of interdiffusion in thin	44 (1990) 293
S.C. Jain, A. Atkinson and W.S. Khokle, Relationship between mechanical, electronic and vibrational properties		polycrystalline Au-Ag multilayer films D.R. Baer, R.L. Gordon and C.W. Hub-	45 (1990) 57
of $Ge_xSi_{1-x}$ strained layers	48/49 (1991) 387	bard, Work function and UPS study	
Y. Hatanaka, Heterostructures with hy- drogenated amorphous silicon for use		of Au and O on Re R. Kötz, Ultraviolet photoelectron spec-	45 (1990) 71
in imaging devices	48/49 (1991) 457	troscopy (UPS) of anodic oxide films	
P.F. Fewster, Multicrystal X-ray diffrac-		on Au, Pt, Ru and Ru <sub>0.5</sub> Ir <sub>0.5</sub> alloy	47 (1991) 109
tion of heteroepitaxial structures H.G. Grimmeiss and M. Kleverman,	50 (1991) 9	F. Aumayr, G. Lakits and H. Winter, On the measurement of statistics for par-	
Electrical and optical defect spec-		ticle-induced electron emission from a	
troscopy of compound semiconduc-		clean metal surface	47 (1991) 139
tors	50 (1991) 52	R. Bartlett, H. Jaeger, B.A. Sexton, R.P.	
B.J. Heijmink Liesert, M. Godlewski, T. Gregorkiewicz and C.A.J. Ammerlaan,		Netterfield and P.J. Martin, A scan- ning tunnelling and transmission elec-	
Neutron transmutation doping of		tron microscopy comparison of the	
GaP: optical studies	50 (1991) 245	surface structure of evaporated and	
M. Mendik, M. Ospelt, H. von Känel and P. Wachter, Determination of elastic		ion-assisted gold films  K. Nishimori, H. Tokutaka, H. Sumi and	47 (1991) 187
properties of Si/Ge superlattices and		N. Ishihara, Interface reaction of Si	
Si <sub>1-x</sub> Ge <sub>x</sub> films from surface acoustic		thin film on Au substrate	47 (1991) 365
modes by Brillouin scattering	50 (1991) 303	V.M. Browne, A.F. Carley, R.G. Cop-	
B. Holländer, S. Mantl, B. Stritzker, F. Schäffler, HJ. Herzog and E. Kasper,		perthwaite, P.R. Davies, E.M. Moser and M.W. Roberts, Activation of	
Strain and defect densities in Si/		carbon dioxide at bismuth, gold and	
$Si_{1-x}Ge_x$ heterostructures investigated		copper surfaces	47 (1991) 375
by ion scattering and X-ray diffrac- tion	50 (1991) 450	K. Kalki, B. Pennemann, U. Schröder, W. Heichler and K. Wandelt, Properties	
		of noble metal and binary alloy mono-	
Glass		layer films on Ru(001) A.D. Gates and J.L. Robins, Nucleation	48/49 (1991) 59
		of gold on Ca <sup>2+</sup> -doped NaCl	48/49 (1991) 154
C. Buerhop, B. Blumenthal, R. Weiss-		T. Hosaka, Effects of impurities in a two-	
mann, N. Lutz and S. Biermann, Glass surface treatment with excimer and		layer evaporated Au film on its tensile	49 (40 (1001) 502
CO <sub>2</sub> lasers	46 (1990) 430	fracture  J.S. Kim, P.K. Banerjee, S.S. Mitra, H.	48/49 (1991) 502
B. Biliński, W. Wójcik and A.L. Dawido-		Shastry, J.J. Loferski and R. Beaulieu,	
wicz, Investigation of the surface free energy components of thermally		Optical, electrical and mechanical	
treated controlled porosity glasses by		properties of RF-sputtered TiN-W-Au films	48/49 (1991) 548
inverse gas chromatography	47 (1991) 99	C. Ghezzi, R. Mosca, A. Bosacchi, S.	40/ 47 (1771) 340
		Franchi and E. Gombia, The influence	
Gold		of the DX center on the capacitance of Schottky barriers in n-type AlGaAs	50 (1991) 400
D.G. WWW. D.G. D.L. Company		L. Roberts and G.J. Hughes, An investi-	30 (1331) 400
R.S. Williams, R.S. Daley, J.H. Huang and R.M. Charatan, Initial stages of metal/semiconductor interface forma-		gation of metal/GaAs(100) interfaces by deep level transient spectroscopy	50 (1991) 424
	41/42 (1989) 70		
tion: Au and Ag on Si(111)		Grain boundaries	
M. Jubber, J.I.B. Wilson, J.L. Davidson,			
M. Jubber, J.I.B. Wilson, J.L. Davidson, P.A. Fernie and P. John, Laser writing	43 (1989) 74		
M. Jubber, J.I.B. Wilson, J.L. Davidson,	43 (1989) 74	P. Lejček, M. Koutník, J. Brádler, V. Paidar and A. Potměšilová, Ani-	

in as-grown Fe-6at%Si alloy bi- crystals	44 (1990) 75	Hall effect	
Graphite		G. Strasser, S. Dubois, M. Besson, E. Gornik, G. Weimann, E. Bauser and H. Riechert, Analysis of impurity dis-	
<ul> <li>A.G. Roosenbrand, M.W.C. van Beckhoven and H.H. Brongersma, Surface topography of pyrolytic graphite</li> <li>H. Zaidi, D. Paulmier and J. Lepage, The influence of the environment on the</li> </ul>	44 (1990) 121	tribution in n-GaAs layers by photo- conductivity and cyclotron resonance measurements  D.I. Desnica, B. Šantić and U.V. Desnica, Time-evolution of low-temperature photoconductivity and Hall mobility	50 (1991) 261
friction and wear of graphitic carbons.  II. Gas coverage of wear debris  M.J. van Staden and J.P. Roux, The superposition of carbon and ruthenium	44 (1990) 221	in semi-insulating GaAs  B. Boudart, B. Prévot and C. Schwab, Free-carrier concentration in n-doped	50 (1991) 269
Auger spectra  J.C. Lascovich, R. Giorgi and S. Scaglione, Evaluation of the sp <sup>2</sup> /sp <sup>3</sup> ratio in amorphous carbon structure by XPS	44 (1990) 259	InP crystals determined by Raman scattering measurements  A. Baraldi, C. Ghezzi, A. Parisini, A. Bosacchi and S. Franchi, Analysis of electron mobility versus temperature	50 (1991) 295
and XAES  E.B.D. Bourdon and R.H. Prince, Growth mechanisms of diamond-like films formed by laser ablation of graphite  E.C. Benck, Z. Rong, S.H. Chen and H.A.	47 (1991) 17 48/49 (1991) 50	<ul> <li>after photoexcitation in Si-doped Al<sub>x</sub>Ga<sub>1-x</sub>As</li> <li>R. Nipoti, D. Pocci, A. Cetronio and C. Lanzieri, Carrier and mobility profile</li> </ul>	50 (1991) 405
Schuessler, Cavity-enhanced detection of surface ablation  D.E. Ramaker, Evidence for vertical C <sub>2</sub> on Ni as a precursor for graphite	48/49 (1991) 257	measurements in n-type ion-implanted GaAs by the differential sheet resistiv- ity and Hall effect technique B. Mari, A. Segura and A. Chevy, Electri-	50 (1991) 410
nucleation T. Yamashina and T. Hino, Plasma- surface interactions of graphite as nuclear fusion material	48/49 (1991) 351 48/49 (1991) 483	cal properties of neutron-transmuta- tion-doped InSe  D.A. Woolf, D.I. Westwood, M.A. Ander- son and R.H. Williams, The molecular beam epitaxial growth of GaAs-	50 (1991) 415
Halides		(111)/Si(111): a variable growth temperature study	50 (1991) 445
H.C. Lee, H. Ishiwara, S. Furukawa, K. Saiki and A. Koma, Distribution of interfacial As atoms in the electron-		Halogens	
beam exposure and epitaxy (EBE-epitaxy) technique for growing GaAs films on CaF <sub>2</sub> /Si(111) structures  D.E. King, J.E. Fernandez and W.E. Swartz, An XPS study of the doping	41/42 (1989) 553	W.C.M. Claassen, R.W.A.H. Schmitz and J. Dieleman, Influence of surface fluo- rination on the oxidation of amor- phous silicon by atomic oxygen at 300	
of trans, trans-p-distyrylbenzene with AsF <sub>5</sub> : a model conducting polymer system  M.M. Hills and G.S. Arnold, Chemical	45 (1990) 325	K S. Sapieha, M. Verreault, J.E. Klemberg- Sapieha, E. Sacher and M.R. Wert- heimer, X-ray photoelectron study of	43 (1989) 292
treatment of fused silica with xenon difluoride  A. Mowbray and R.G. Jones, Homo- and hetero-iodide thin film growth on InSb(001): low-temperature iodide	47 (1991) 77	the plasma fluorination of lignocellu- lose T.S. Baller, J.C.S. Kools and J. Dieleman, Surface temperature measurements using pyrometry during excimer laser	44 (1990) 165
formation and epitaxial growth of CdI <sub>2</sub>	48/49 (1991) 27	pulsed etching of silicon in a Cl <sub>2</sub> environment	46 (1990) 292

43 (1989) 224

44 (1990) 103

41/42 (1989) 57

41/42 (1989) 139

41/42 (1989) 144

41/42 (1989) 241

41/42 (1989) 323

41/42 (1989) 451

41/42 (1989) 457

41/42 (1989) 464

41/42 (1989) 526

## Halogenides

- S. Scaglione, D. Flori and G. Emiliani, Modification of mechanical properties of e-gun evaporated MgF<sub>2</sub> and CaF<sub>2</sub> thin films under ion beam bombardment
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   Interactions of PF<sub>3</sub> and PD<sub>3</sub> with clean,
   P-covered and H(D)-covered (100) oriented W foil

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interface region of GaAs/GaP heteroepitaxial layers grown by MBE

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N. Herres, G. Bender and G. Neumann, Assessment of mismatched epitaxial layers by X-ray rocking curve measurements and simulations

Y. Gao, I. Ardelean, D. Renard, B. Rose and Y. Jin, High-depth-resolution SIMS analysis for InGaAs/InP interfaces

T.S. Horányi, P. Tüttö and G. Endrédi, Improved method for depth profiling of multilayer structures

J.S. Rimmer, M. Missous and A.R. Peaker, A new, fast method for the computer simulation of CV profiles in multilayer structures

R.A.D. Mackenzie, J.A. Liddle and C.R.M. Grovenor, Ultrahigh resolu-

41/42 (1989) 530

41/42 (1989) 534

41/42 (1989) 539

41/42 (1989) 544

41/42 (1989) 553

41/42 (1989) 567

41/42 (1989) 580

41/42 (1989) 587

50 (1991) 19

50 (1991) 34

50 (1991) 63

50 (1991) 97

50 (1991) 131

50 (1991) 143

50 (1991) 149

tion characterisation of compound semiconductors using pulsed laser		tions on the crystal surface of molyb- date-type catalysts	44 (1990) 331
atom probe techniques  Z.M. Wang, J. Windscheif, D.J. As and	50 (1991) 196	E. Nowicka, Z. Wolfram and R. Duś, Deuterium adsorption on thin nickel	(1770) 001
W. Jantz, Ambient and low tempera- ture photoluminescence topography of GaAs substrates, epitaxial and im-		films W.G. Durrer, J.H. Craig, Jr. and J. Lozano, Surface carbon and its effects	45 (1990) 13
planted layers  H.P. Zappe and G. Kaufel, Reactive-ion- etch damage in GaAs processing evaluated by a microwave absorption	50 (1991) 228	on hydrogen adsorption on Rh(100)  P. Raynaud, J.P. Booth and C. Pomot, Hydrogen plasma treatment of silicon surfaces studied by in-situ spectro-	45 (1990) 275
technique  J.F. Donegan, J.P. Doran, R.P. Stanley, J.  Hegarty, R.D. Feldman and R.F.  Austin, Resonant Rayleigh scattering from excitons in Cd <sub>x</sub> Zn <sub>1-x</sub> Te:ZnTe	50 (1991) 290	scopic ellipsometry  D. Vassilakis, CM. Pradier, Y. Berthier and J. Oudar, Hydrogen, hydrogen sulfide and hydrocarbon coadsorption on Pt(111) and Pt(110): selective for-	46 (1990) 435
quantum wells: measurement of ho- mogeneous linewidths	50 (1991) 321	mation of alkylthiols  H.H. Madden and R. Imbihl, Interaction	47 (1991) 273
P.L. Swart, B.M. Lacquet and R. Thavar, Physical characterization of OMVPE-	30 (1771) 321	of NO and H <sub>2</sub> with Pt(100) T. Zhang and S.Y. Wei, Hydrogen chem-	48/49 (1991) 130
grown Al <sub>x</sub> Ga <sub>1-x</sub> As multi-layer films by means of non-destructive optical reflectometry	50 (1991) 330	isorption on contaminated composite catalysts  Y. Fukuda and M. Nagoshi, Chemisorption of hydrogen on Cr(111) studied	48/49 (1991) 139
C. Pickering, N.S. Garawal, D. Lance- field, J.P. Piel and R. Blunt, Non-de- structive characterisation of (Ga,In, Al,As,P)-based ternary multilayer		tion of hydrogen on Cr(111) studied by XPS, UPS, and HREELS Y.L. Jiang and H.L. Hwang, Electron transport in hydrogenated amorphous	48/49 (1991) 147
structures using spectroscopic ellipsometry D. Lee, S.J. Barnett, A.D. Pitt, M.R.	50 (1991) 346	silicon quantum wells  Y. Hatanaka, Heterostructures with hydrogenated amorphous silicon for use	48/49 (1991) 392
Houlton and G.W. Smith, Characterization of alloy composition in $Ga_{1-x}Al_xAs/GaAs$ structures: comparison of photovoltage, X-ray, SIMS		in imaging devices  H. Mimura and Y. Hatanaka, The current transport mechanism of p-type a-Si:H/n-type c-Si heterojunctions and	48/49 (1991) 457
and RHEED techniques  B. Holländer, S. Mantl, B. Stritzker, F. Schäffler, HJ. Herzog and E. Kasper, Strain and defect densities in	50 (1991) 428	their application to an imaging device H. Mimura, K. Sai, Y. Ohta, K. Yamamo- to and K. Kitamura, A two-dimen- sional image sensor with a-Si:H pin	48/49 (1991) 472
$Si/Si_{1-x}Ge_x$ heterostructures investigated by ion scattering and X-ray diffraction	50 (1991) 450	diodes  V.Kh. Kudoyarova, G.M. Gusinsky, L.A.  Rassadin and I.V. Kudryavtsev, Hy-	48/49 (1991) 521
R. Schwarz, T. Fischer, P. Hanesch, T. Muschik, J. Kolodzey, H. Cerva, H.L. Meyerheim and B.M.U. Scherzer,	,	drogen depth profile measurement in $a-Si_{1-x}C_x$ : H films by elastic recoil detection	50 (1991) 173
Limitations of interface sharpness in a-Si:H/a-SiC:H multilayers	50 (1991) 456	J. Tatarkiewicz, A. Kozanecki, Z. Kaliń- ski and K. Paprocki, Photolumines- cence study of proton-implanted	
Hydrogen		InP <sub>1-x</sub> As <sub>x</sub> :Yb M. Hage-Ali, B. Yaacoub, S. Mergui, M. Samimi, B. Biglari and P. Siffert, Mi-	50 (1991) 249
H. Zaïdi, D. Paulmier and J. Lepage, The influence of the environment on the friction and wear of graphitic carbons.		croscopic defect level characterization of semi-insulating compound semicon- ductors by TSC and PICTS. Applica-	
<ul><li>II. Gas coverage of wear debris</li><li>A. Vázquez, J.M. Domínguez and S. Fuentes, Thermally induced modifica-</li></ul>	44 (1990) 221	tion to the effect of hydrogen in CdTe A.W.R. Leitch, Th. Prescha and M. Stutz- mann, Hydrogen passivation and re-	50 (1991) 377

activation of shallow Zn acceptors in GaAs	50 (1991) 390	D. Ashenford, J.H.C. Hogg, B. Lunn and C.G. Scott, The relationship between electrical and structural characteristics of CdTe and CdMnTe layers grown	
Hydrogen sulphide		on InSb	50 (1991) 440
R.V. Siriwardane and J.A. Poston, Inter- action of H <sub>2</sub> S with zinc titanate in the presence of H <sub>2</sub> and CO	45 (1990) 131	Indium arsenide	
<ul> <li>D. Vassilakis, CM. Pradier, Y. Berthier and J. Oudar, Hydrogen, hydrogen sulfide and hydrocarbon coadsorption on Pt(111) and Pt(110): selective formation of alkylthiols</li> <li>G.M. O'Connor, C.J. McDonagh, F.G. Anderson, T.J. Glynn, G.P. Morgan,</li> </ul>	47 (1991) 273	<ul> <li>J. Christen, M. Grundmann and D. Bimberg, Direct imaging and theoretical modelling of the atomistic morphological and chemical structure of semiconductor heterointerfaces</li> <li>R.A. Stradling, Far-infrared spectroscopy of impurities in semiconductors</li> </ul>	41/42 (1989) 329 50 (1991) 65
G.J. Hughes, L. Roberts and M.O. Henry, Raman characterization of passivated GaAs surfaces	50 (1991) 312	R. Zaus, M. Schuster, H. Göbel and JP. Reithmaier, Characterization of (In, Ga)As/GaAs strained-layer multiple quantum wells with high-resolution	30 (1771) 03
Indium  C. Julien and M. Balkanski, Thin-film		<ul><li>X-ray diffraction and computer simulations</li><li>A. Baurichter, M. Deicher, S. Deubler, D.</li></ul>	50 (1991) 92
growth and structure for solid-state batteries  M. Kimura, A. Tanaka and T. Sukegawa,	48/49 (1991) 1	Forkel, J. Meier, H. Wolf, W. Witt- huhn and ISOLDE Collaboration, Mi- croscopical studies at cadmium impur-	
Dissolution process of silicon in an indium solution	48/49 (1991) 185	ities in compound semiconductors  B. Meyer, P. Omling and P. Emanuelsson, Landau oscillations in single quantum	50 (1991) 165
R. Magerle, M. Deicher, U.V. Desnica, R. Keller, W. Pfeiffer, F. Pleiter, H. Skudlik and Th. Wichert, Defects in CdS:In detected by perturbed angular		wells observed by microwave detec- tion	50 (1991) 420
correlation spectroscopy (PAC) S.G. Jahn, H. Hofsäss, U. Wahl, S. Winter, E. Recknagel and ISOLDE Collabora-	50 (1991) 159	Indium oxide	
tion, Structural defect recovery in GaP after heavy ion implantation	50 (1991) 169	Y. Shigesato, S. Takaki and T. Haranou, Crystallinity and electrical properties of tin-doped indium oxide films de- posited by DC magnetron sputtering	48/49 (1991) 269
Indium antimonide		M. Takeuchi, Y. Watanabe and S. Ozawa, Gas-sensitive properties of ultrafine	10) 12 (2522) 205
T.S. Jones, M.Q. Ding, N.V. Richardson and C.F. McConville, The effects of surface damage on surface plasmon		In <sub>2</sub> O <sub>3</sub> particle layers prepared by gas evaporation technique	48/49 (1991) 526
excitations in doped InSb(100)  A. Mowbray and R.G. Jones, Homo- and hetero-iodide thin film growth on	45 (1990) 85	Indium phosphide	
InSb(001): low-temperature iodide formation and epitaxial growth of CdI <sub>2</sub>	48/49 (1991) 27	D.R.T. Zahn, W. Richter, A.B. McLean, R.H. Williams, C. Stephens, I.T. Mc- Govern, R. Cimino, W. Braun and N.	
<ul> <li>R.A. Stradling, Far-infrared spectroscopy of impurities in semiconductors</li> <li>A. Baurichter, M. Deicher, S. Deubler, D. Forkel, J. Meier, H. Wolf, W. Witthuba and ISOLDE Collaboration. Michael Solution (Inc.)</li> </ul>	50 (1991) 65	Esser, Temperature effects on the formation of the Sb/InP(110) interface H. Ishii, H. Hasegawa, A. Ishii and H. Ohno, X-ray photo-electron spectroscopic of LaB involved.	41/42 (1989) 179
huhn and ISOLDE Collaboration, Mi- croscopical studies at cadmium impur- ities in compound semiconductors	50 (1991) 165	troscopy analysis of InP insulator- semiconductor structures prepared by anodic oxidation	41/42 (1989) 390

<ul> <li>K. Kamimura, Y. Takase, Y. Onuma and</li> <li>A. Kunioka, Surface nitridation of InP</li> <li>with a N<sub>2</sub> plasma</li> <li>J. Meiler, R. Matz and D. Haarer, Laser-</li> </ul>	41/42 (1989) 443	A. Baurichter, M. Deicher, S. Deubler, D. Forkel, J. Meier, H. Wolf, W. Witthuhn and ISOLDE Collaboration, Microscopical studies at cadmium impur-	
induced photochemical etching of InP by HBr and HCl J. Morais, A.M. Machado, M.A. Sacilotti and R. Landers, AES sputter depth	43 (1989) 416	ities in compound semiconductors  B.L. Chen, M. Eckstein and HU.  Habermeier, Cathodoluminescence investigations of RIE-induced defects in	50 (1991) 165
profiles applied to interface analysis of GaInAs/InP grown by atmospheric pressure MOCVD M. Gendry, J. Durand, M. Erman, J.B.	44 (1990) 161	InP  R. Fornari, N. Tchandjou, P. Gall and J.M. Lussert, A study of structural properties of bulk double-doped InP	50 (1991) 191
Theeten, L. Nevot and B. Pardo, Chemical and structural analysis by ellipsometry and X-ray reflectometry of thin sulfide layers grown on InP	44 (1990) 309	by laser scattering tomography and photoetching  H. L'Haridon, P.N. Favennec, R. Coquille, M. Salvi, M. Gauneau, Y. Le	50 (1991) 207
S.J. Hoekje and G.B. Hoflund, Surface characterization study of InP(100) substrates using ISS, AES and ESCA:	44 (1770) 307	Guillou, R. Callec and P. Gall, Spatial investigation of an iron-doped indium phosphide ingot	50 (1991) 237
comparison of substrates from two different commercial sources I.T. McGovern, Soft X-ray photoelectron	47 (1991) 43	J. Tatarkiewicz, A. Kozanecki, Z. Kaliń- ski and K. Paprocki, Photolumines- cence study of proton-implanted	
spectroscopy of compound semicon- ductor surfaces and interfaces  C. Grattepain and A.M. Huber, Sec- ondary ion mass spectrometry of	50 (1991) 34	InP <sub>1-x</sub> As <sub>x</sub> :Yb G.M. Crean, P.A.F. Herbert, I. Little, W.M. Kelly, J.Y. Marzin, A. Izrael and B. Jusserand, Investigation of re-	50 (1991) 249
dopants and impurities in compound semiconductors: depth profiling of homo- and heterostructure	50 (1991) 42	active ion etch-induced damage in InP surfaces using a noncontact photo-thermal radiometric probe	50 (1991) 281
<ul> <li>R.A. Stradling, Far-infrared spectroscopy of impurities in semiconductors</li> <li>N. Herres, G. Bender and G. Neumann, Assessment of mismatched epitaxial</li> </ul>	50 (1991) 65	B. Boudart, B. Prévot and C. Schwab, Free-carrier concentration in n-doped InP crystals determined by Raman scattering measurements	50 (1991) 295
layers by X-ray rocking curve mea- surements and simulations P. Ossart and E.V.K. Rao, Investigation of surface and sub-surface defects on	50 (1991) 97	B.H. Bairamov, V.A. Voitenko, I.P. Ipatova, V.V. Toporov, G. Irmer, J. Monecke and E. Jahne, Characterization of III-V compounds by quasi-	
polished InP substrates using Auger electron spectroscopy coupled to argon ion sputtering	50 (1991) 125	elastic electronic scattering of light C. Pickering, N.S. Garawal, D. Lance- field, J.P. Piel and R. Blunt, Non-de-	50 (1991) 300
Y. Gao, I. Ardelean, D. Renard, B. Rose and Y. Jin, High-depth-resolution SIMS analysis for InGaAs/InP inter- faces	50 (1991) 131	structive characterisation of (Ga,In, Al,As,P)-based ternary multilayer structures using spectroscopic el- lipsometry	50 (1991) 346
J.G. Bauer, R. Treichler, T. Hillmer, J. Müller and G. Ebbinghaus, Optimization of Zn dopant profiles in a pin-diode/FET by combination of depth		<ul> <li>A. Dimoulas, A. Derekis, G. Kyriakidis and A. Christou, Alloy disorder ef- fects in III-V ternaries studied by modulation spectroscopy</li> </ul>	50 (1991) 353
profiling techniques: a SIMS, ECV and AES study W. Pfeiffer, M. Deicher, R. Keller, R.	50 (1991) 138	H.W. Dinges, B. Kempf, H. Burkhard and R. Göbel, Determination of ion beam etching damage on InP by spec-	
Magerle, P. Pross, H. Skudlik, Th. Wichert, H. Wolf, D. Forkel, N. Moriya and R. Kalish, Characterization of Cd implanted and appealed		troscopic ellipsometry  F. Mosel, A. Seidl, D. Hofmann and G.  Müller, Infrared absorption of n- and p-type Fe-doped InP and mapping of	50 (1991) 359
tion of Cd implanted and annealed GaAs and InP by perturbed angular correlation (PAC) spectroscopy	50 (1991) 154	the Fe distribution  B. Sartorius, M. Brandstättner and H.	50 (1991) 364

Venghaus, Two-wavelength transmis- sion: a rapid and precise method for		E. Fogarassy, A. Slaoui, C. Fuchs and J.P. Stoquert, Deposition of SiO <sub>2</sub> by reac-	
measuring the light absorption in semiconductors  J. Tardy, I. Thomas, P. Viktorovitch, M.	50 (1991) 369	tive excimer laser ablation from a SiO target  T. Szörényi, P. González, D. Fernández,	46 (1990) 195
Gendry, J.L. Perrossier, C. Santinelli, M.P. Besland, P. Louis and G. Post, Long-term stability of InP MIS de-	50 (1991) 383	J. Pou, B. León and M. Pérez-Amor, Gas mixture dependence of the LCVD of SiO <sub>2</sub> films using an ArF laser B. León, A. Klumpp, M. Pérez-Amor and	46 (1990) 206
vices B. Meyer, P. Omling and P. Emanuelsson, Landau oscillations in single quantum wells observed by microwave detec-	50 (1991) 383	H. Sigmund, Excimer laser deposition of silica films: a comparison between two methods	46 (1990) 210
tion	50 (1991) 420	J. Breuer, S. Metev, G. Sepold, OD. Hennemann, H. Kollek and G. Krüger,	(2773) 222
Infrared spectroscopy		Laser-induced photochemical ad- herence enhancement	46 (1990) 336
K. Matsuo and K. Nakano, Characteriza- tion of semiconductor oxides by IR diffuse reflectance spectroscopy	41/42 (1989) 53	H. Hiraoka and S. Lazare, Applications of doping and dedoping of Teflon AF films in microfabrication using KrF	(2,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,
D.R.T. Zahn, W. Richter, T. Eickhoff, J. Geurts, T.D. Golding, J.H. Dinan, K.J.	, (2,0), 00	and ArF excimer lasers M. Wolpers, H. Viefhaus and M. Strat-	46 (1990) 342
Mackey and R.H. Williams, The in- fluence of Cd overpressure in the molecular beam epitaxy of InSb/CdTe heterostructures: a combined Raman		mann, Surface analytical investiga- tions of metal surfaces modified by Langmuir-Blodgett films of silanes M.M. Hills and G.S. Arnold, Chemical	47 (1991) 49
and infrared spectroscopy study Y. Kato, T. Ito and A. Hiraki, Low tem-	41/42 (1989) 497	treatment of fused silica with xenon difluoride	47 (1991) 77
perature oxidation of crystalline por- ous silicon W.C.M. Claassen, R.W.A.H. Schmitz and	41/42 (1989) 614	A.H.M. Sondag, M.C. Raas and F.J. Touwslager, A comparison between inelastic electron tunnelling and in-	
J. Dieleman, Influence of surface fluo- rination on the oxidation of amor-		frared reflection-absorption spec- troscopy for vibrational surface analy-	47 (1001) 207
phous silicon by atomic oxygen at 300 K  A. Klumpp and H. Sigmund, Photoin-	43 (1989) 292	sis C. Julien and M. Balkanski, Thin-film growth and structure for solid-state	47 (1991) 205
duced transformation of polysiloxane layers to SiO <sub>2</sub>	43 (1989) 301	batteries E.B.D. Bourdon and R.H. Prince, Growth	48/49 (1991) 1
T. Wadayama, W. Shiraishi, A. Hatta and W. Suëtaka, A double-modulation method of observing infrared emission		mechanisms of diamond-like films formed by laser ablation of graphite G.N. Pain, T. Warminski, S. Sulcs, M.S.	48/49 (1991) 50
spectra of thin films on metal surfaces J. Heidberg, B. Brase, KW. Stahmer and	44 (1990) 43	Kwietniak, D. Gao, S.R. Glanvill, C.J. Rossouw, A.W. Stevenson, S.P. Russo,	
M. Suhren, Second harmonic genera- tion of CO <sub>2</sub> -laser radiation and FTIR spectroscopy for resonant desorption		R.G. Elliman, L.S. Wielunski, R.S. Rowe, G.B. Deacon, R.S. Dickson and B.O. West, Characterization of low-	
in the adsorbate CO-NaCl(100) Y. Zhang and M. Stuke, VUV synchro-	46 (1990) 44	temperature MOCVD Cd <sub>1-x</sub> Mn <sub>x</sub> Te thin films	48/49 (1991) 76
tron radiation processing of thin pal- ladium acetate spin-on films for metallic surface patterning	46 (1990) 153	I.K. Han, Y.J. Lee, J.W. Jo, J.I. Lee and K.N. Kang, Growth and characteriza- tion of silicon-nitride films by	
Y. Horiike, T. Ichihara and H. Sakaue, Filling of Si oxide into a deep trench		plasma-enhanced chemical vapor de- position	48/49 (1991) 104
using digital CVD method Y.I. Nissim, J.M. Moison, F. Houzay, F.	46 (1990) 168	A. Hatta, Y. Suzuki, T. Wadayama and W. Suëtaka, Kretschmann ATR-IR spectroscopy of investigating metal/	
Lebland, C. Licoppe and M. Bensous- san, Photo-assisted deposition of thin films on III-V semiconductors with		liquid(or solid) interfaces  S. Schelz, J. Eitle, R. Steiner and P.	48/49 (1991) 222
UV and IR lamps	46 (1990) 175	Oelhafen, In situ electron spec-	

troscopy on polymeric films prepared		fluoride thin film grown by fluorin-	
by RF plasma polymerization: styrene		ation. Electrical behaviour of the ob-	
and hydrogen/styrene gas mixtures as		tained MIS fluorinated GaAs struc-	
process gases	48/49 (1991) 301	tures	41/42 (1989) 383
A. Hishinuma, T. Goda, M. Kitaoka, S.		H. Ishii, H. Hasegawa, A. Ishii and H.	
Hayashi and H. Kawahara, Formation of silicon dioxide films in acidic solu-		Ohno, X-ray photo-electron spec- troscopy analysis of InP insulator-	
tions	48/49 (1991) 405	semiconductor structures prepared by	
T. Wadayama, T. Hihara, A. Hatta and	, , , , , , , , , , , , , , , , , , , ,	anodic oxidation	41/42 (1989) 390
W. Suëtaka, In situ IR observation of		P. Soukiassian, H.I. Starnberg and T.	
photo-chemically deposited silicon	40 /40 /4004	Kendelewicz, Insulator-semiconduc-	
nitride thin films R.A. Stradling, Far-infrared spectroscopy	48/49 (1991) 409	tor interface formation by electronic	
of impurities in semiconductors	50 (1991) 65	promotion using alkali metal and re- moval of the catalyst	41/42 (1989) 395
V.Kh. Kudoyarova, G.M. Gusinsky, L.A.	30 (1771) 03	H. Miyatake, Y. Yamaguchi, Y. Mashiko,	41/ 42 (1707) 575
Rassadin and I.V. Kudryavtsev, Hy-		T. Nishimura and H. Koyama, Micro-	
drogen depth profile measurement in		structure of high temperature an-	
$a-Si_{1-x}C_x$ :H films by elastic recoil de-	50 (1001) 470	nealed SIMOX wafer	41/42 (1989) 643
tection  A. Deneuville, D.B. Tanner, R.M. Park	50 (1991) 173	Y. Yamada Maruo, M. Oshima, T. Waho, T. Kawamura, S. Maeyama and T.	
and P.H. Holloway, Semiconductor		Miyahara, Photoemission studies of	
electrical properties from the frequen-		bonding properties at the MBE-grown	
cy dependence of the dielectric con-		CaF <sub>2</sub> /GaAs interface	41/42 (1989) 647
stant: application to n-type ZnSe het-			
eroepitaxial thin films	50 (1991) 285	Interferen	
F. Mosel, A. Seidl, D. Hofmann and G. Müller, Infrared absorption of n- and		Interfaces	
p-type Fe-doped InP and mapping of			
the Fe distribution	50 (1991) 364	M.H. Hecht, L.D. Bell and W.J. Kaiser,	
R. Schwarz, T. Fischer, P. Hanesch, T.		Ballistic-electron-emission microscopy	
Muschik, J. Kolodzey, H. Cerva, H.L.		of subsurface defects at the Au- GaAs(100) interface	41/42 (1989) 17
Meyerheim and B.M.U. Scherzer,		G. Le Lay, K. Hricovini and J.E. Bonnet,	41/42 (1909) 17
Limitations of interface sharpness in a-Si:H/a-SiC:H multilayers	50 (1991) 456	Synchrotron radiation investigation	
M.R. Brozel, L. Breivik, D.J. Stirland,	30 (1771) 430	and surface spectroscopy studies of	
G.M. Williams and A.G. Cullis, Dislo-		prototypical systems: lead-semicon-	41 (42 (1000) 25
cation density, infrared absorption and		ductor interfaces  X.M. Ding, G.S. Dong, X.K. Lu, H.Y.	41/42 (1989) 25
cathodoluminescence mapping of mi-		Xiao, P. Chen and X. Wang, Applica-	
crostructure associated with disloca-	50 (1991) 475	tion of HREELS to Al/GaAs and	
tion cells in semi-insulating LEC GaAs	30 (1991) 473	Al/GaP interfaces	41/42 (1989) 123
Insulator semiconductor interfaces		H. Fujitani and S. Asano, Electronic	44 44 44 44 44 44 44 44 44 44 44 44 44
Insulator - semiconductor interfaces		structure of Si/disilicide interfaces	41/42 (1989) 164
F.J. Himpsel, T.F. Heinz, A.B. McLean		D.R.T. Zahn, W. Richter, A.B. McLean, R.H. Williams, C. Stephens, I.T. Mc-	
and E. Palange, Bonding at silicon/in-		Govern, R. Cimino, W. Braun and N.	
sulator interfaces	41/42 (1989) 346	Esser, Temperature effects on the for-	
A. Ourmazd, P.H. Fuoss, J. Bevk and J.F.		mation of the Sb/InP(110) interface	41/42 (1989) 179
Morar, The Si(001)/SiO <sub>2</sub> interface	41/42 (1989) 365	R. Sporken, P.A. Thiry, P. Xhonneux, R.	
H. Hasegawa, H. Ohno, H. Ishii, T. Haga,		Caudano and J.P. Delrue, Spectro-	
Y. Abe and H. Takahashi, Origin and properties of interface states at insula-		scopic study of metal/semimetal and metal/semiconductor interfaces	41/42 (1989) 201
tor-semiconductor and semiconduc-		R.T. Tung and F. Schrey, Epitaxial	.1/ .2 (1707) 201
tor-semiconductor interfaces of com-		CoSi <sub>2</sub> /Si(111) interfaces	41/42 (1989) 223
pound semiconductors	41/42 (1989) 372	K. Akimoto, J. Mizuki, I. Hirosawa and J.	
A.S. Barrière, G. Couturier, H. Guegan,		Matsui, Interfacial superstructures	
<ul><li>T. Séguelong, A. Thabti, P. Alnot and</li><li>J. Chazelas, Interface GaAs – gallium</li></ul>		studied by grazing incidence X-ray diffraction	41/42 (1989) 317
J. Chazelas, Interface GaAs - gainum		diffaction	11/ 12 (1707) 311

a harmonia and a superior			
H. Akatsu and I. Ohdomari, HRTEM	41 /42 (1000) 257	P. Mary, P. Bogdanski, G. Nouet and M.	
observation of the Si/SiO <sub>2</sub> interface	41/42 (1989) 357	Toulemonde, Defects created by 3.5 GeV xenon ions in silicon	42 (1090) 102
K. Yokota, K. Ohtsuki, M. Ochi, S. Ishihara and I. Kimura, Accumulation		F. Priolo, C. Spinella, A. La Ferla, E.	43 (1989) 102
of implanted arsenic at the interface		Rimini and G. Ferla, Ion-assisted re-	
		crystallization of amorphous silicon	43 (1989) 178
during annealing on thermally oxidized Si and SiO <sub>2</sub> covered Si	41/42 (1989) 411	C. Spinella, S. Lombardo and S.U.	43 (1909) 170
T. Hattori, H. Yamagishi, N. Koike, K.	41/42 (1909) 411	Campisano, Amorphous to polycrystal	
Imai and K. Yamabe, Structural stud-		transition in ion irradiated chemical	
ies of ultrathin silicon oxides and their		vapor deposited amorphous silicon	43 (1989) 187
interfaces by XPS	41/42 (1989) 416	S.P. Withrow, O.W. Holland and S.J.	15 (1707) 107
P.S. Ho, Chemistry and adhesion of	41/ 42 (1707) 410	Pennycook, Ion beam annealing of	
metal-polymer interfaces	41/42 (1989) 559	Ga-implanted Si	43 (1989) 191
Y. Hatanaka, K. Mitsuoka and T. Yama-	11/ 12 (1707) 507	M. Voelskow, W. Skorupa, K. Woll-	(1707) 171
guchi, Properties of a-Si:H based in-		schlaeger, J. Matthaei, P. Knothe, K	
terface transient layers measured by		H. Heinig and H. Bartsch, Epitaxial	
in-situ ellipsometry	41/42 (1989) 591	lateral overgrowth of amorphous CVD	
A.J. Pertsin and Yu.M. Pashunin, Dif-	, ( ,	silicon films induced by ion irradia-	
ferential charging in XPS studies of		tion	43 (1989) 196
polymer/metal interfaces	44 (1990) 171	G. Massouras, J.A. Roger, G. Fuchs, A.	
Y.I. Nissim, J.M. Moison, F. Houzay, F.	, , , , , , , , , , , , , , , , , , , ,	Perez and L. Romana, Fluence depen-	
Lebland, C. Licoppe and M. Bensous-		dence of ion beam induced atomic	
san, Photo-assisted deposition of thin		mixing in the immiscible tin-silicon	
films on III-V semiconductors with		system	43 (1989) 213
UV and IR lamps	46 (1990) 175	J. Davenas, Influence of the temperature	
E.J. Petit and R. Caudano, Chemical re-		on the ion beam induced conductivity	
actions at solid-solid interfaces in-		of polyimide	43 (1989) 218
duced by pulsed laser annealing	46 (1990) 357	S. Scaglione, D. Flori and G. Emiliani,	
A.J. Pertsin and Yu.M. Pashunin, An XPS		Modification of mechanical properties	
study of the in-situ formation of the		of e-gun evaporated MgF <sub>2</sub> and CaF <sub>2</sub>	
polyimide/copper interface	47 (1991) 115	thin films under ion beam bombard-	
M. Bou, J.M. Martin, Th. Le Mogne and		ment	43 (1989) 224
L. Vovelle, Chemistry of the interface		G. Compagnini, R. Reitano, L. Calcagno,	
between aluminium and polyethylene-		G. Marletta and G. Foti, Hydro-	
terephthalate by XPS	47 (1991) 149	genated amorphous carbon synthesis	
T. Hariu, S. Yamauchi, H. Tanaka and S.		by ion beam irradiation	43 (1989) 228
Ono, Interface characterization of		G. Myburg, J.B. Malherbe and E. Fried-	
ZnSe/GaAs heterojunctions	48/49 (1991) 204	land, Electrical characteristics of ion	
*		bombarded Ni/n-Si Schottky contacts	43 (1989) 242
Ion bombardment		G.C. Tyrrell, I.W. Boyd and R.B. Jack-	
		man, Ion beam assisted etching of	
		silicon with bromine. The role of the	42 (1000) 420
F. Priolo, A. La Ferla, C. Spinella, E.		adsorbed state	43 (1989) 439
Rimini, S.U. Campisano and G. Ferla,		T.S. Jones, M.Q. Ding, N.V. Richardson	
Crystal-amorphous-silicon interface	41 /42 (1000) 610	and C.F. McConville, The effects of	
kinetics under ion beam irradiation	41/42 (1989) 619	surface damage on surface plasmon	45 (1000) 95
<ol> <li>Yamada, Growth processes of epitaxial metal films on semiconductor and in-</li> </ol>		excitations in doped InSb(100)  J.A. Treverton and A. Rosenfeld, De-	45 (1990) 85
sulator substrates by ionized cluster		termination of etching characteristics	
beam	43 (1989) 23	of a Vacuum Generators AG21 argon-	
K. Fukushima and I. Yamada, Surface	43 (1909) 23	ion gun by interference colour and	
smoothness and crystalline structure		ellipsometric assessment of craters	
of ICB deposited TiO <sub>2</sub> films	43 (1989) 32	etched in tantalum oxide films	45 (1990) 263
A. Yahashi, L.L. Levenson, H. Usui and	15 (1707) 32	A.R. Krauss, O. Auciello, A.I. Kingon,	75 (1770) 203
I. Yamada, The structure zone model		M.S. Ameen, Y.L. Liu, T. Barr, T.M.	
applied to ionized cluster beam films:		Graettinger, S.H. Rou, C.S. Soble and	
Al on SiO <sub>2</sub>	43 (1989) 37	D.M. Gruen, Computer-controlled ion	
2	(1,0,)	C, Comparer controlled foll	

have denocition systems for high T		of lattice demage accumulation during	
beam deposition systems for high T <sub>c</sub> superconductor and other multi-com-		of lattice damage accumulation during high energy ion implantation	43 (1989) 87
ponent oxide thin films and layered		A. Seidel and G. Linker, Amorphization	45 (1707) 01
structures	46 (1990) 67	mechanisms in Mn <sup>+</sup> -implanted thin Al	
H.M. Hütten, KD. Raddatz, M.K.	()	films and single crystals	43 (1989) 97
Sharma and J. Engemann, On the two-		A. Claverie, C. Vieu and J. Beauvillain,	,
and three-dimensional simulation of		3D simulations of ion implantation	
ion-milled structures	46 (1990) 306	processes	43 (1989) 106
J. Davenas, G. Boiteux, J.M. Bureau and		M. Berti, G. Mazzi, A.V. Drigo, A.	
D. Broussoux, Ion-beam-assisted for-		Migliori, E. Jannitti and S. Nicoletti,	
mation of interconnections into high		Laser induced epitaxial regrowth of	
temperature polymers	46 (1990) 330	$Si_{1-x}Ge_x/Si$ layers produced by Ge	
J. Marfaing, W. Marine, B. Vidal, M.		ion implantation	43 (1989) 158
Toulemonde, M. Hage Ali and J.P.		A. Golanski, Ion beam synthesis of buried	
Stoquert, Instability and structural		compound layers: accomplishments	
transformation of amorphous ultra-		and perspectives	43 (1989) 200
thin W-Si multilayer structures dur-		C. Neelmeijer, P. Knothe, M. Posselt, E.	
ing heavy ion irradiation	46 (1990) 422	Richter and KH. Heinig, Wear re-	
LU.A. Andersen and J. Bøttiger, Crys-		sistant coatings produced by C+ im-	
tallization of Fe-Zr metallic glasses		plantation	43 (1989) 232
during ion irradiation	46 (1990) 427	D.C. Kothari and A. Miotello, Effects on	
E.J. Puik, M.J. van der Wiel, H. Zeijle-		the implanted profiles of point defect	
maker and J. Verhoeven, Ion etching		flux during nitrogen implantation in	42 (1000) 227
of thin W layers: enhanced reflectivity	47 (1001) (2	copper	43 (1989) 237
of W-C multilayer coatings	47 (1991) 63	J. van Zwol, S.T. de Zwart, C.C.A.	
F. Aumayr, G. Lakits and H. Winter, On		Busquet and J. Dieleman, Resputter-	
the measurement of statistics for par-		ing of low-energy implanted inert	
ticle-induced electron emission from a	47 (1001) 120	gases: an angle-resolved time-of-flight	43 (1989) 363
clean metal surface	47 (1991) 139	study	43 (1989) 303
R. Bartlett, H. Jaeger, B.A. Sexton, R.P.		S. Kuniyoshi, K. Kudo and K. Tanaka,	
Netterfield and P.J. Martin, A scan-		Surface modification of low density polyethylene by N <sup>+</sup> , Ar <sup>+</sup> ion implan-	
ning tunnelling and transmission elec- tron microscopy comparison of the		tation for space charge devices	43 (1989) 447
surface structure of evaporated and		V.V. Tokarev, A.V. Kibardin, T.M. Pyat-	43 (1707) 447
ion-assisted gold films	47 (1991) 187	kova and D.I. Zarovsky, Nickel, cobalt	
E.J. Puik, M.J. van der Wiel, H. Zeijle-	47 (1221) 107	and iron silicide formation stimulated	
maker and J. Verhoeven, Ion bom-		by argon implantation	44 (1990) 235
bardment of X-ray multilayer coat-		V.V. Tokarev, A.I. Demchenko, A.I.	(1770) 200
ings: comparison of ion etching and		Ivanov and V.E. Borisenko, Influence	
ion assisted deposition	47 (1991) 251	of boron implantation on phase trans-	
D.M. Mattox, Surface effects in reactive	, ,	formations in nickel silicides	44 (1990) 241
ion plating	48/49 (1991) 540	A. Esser, W. Kütt, M. Strahnen, G.	
H.W. Dinges, B. Kempf, H. Burkhard		Maidorn and H. Kurz, Femtosecond	
and R. Göbel, Determination of ion		transient reflectivity measurements as	
beam etching damage on InP by spec-		a probe for process-induced defects in	
troscopic ellipsometry	50 (1991) 359	silicon	46 (1990) 446
		W.J. Quadakkers, J. Jedlinski, K. Schmidt,	
Ion implantation		M. Krašovec, G. Borchardt and H.	
Ion implantation		Nickel, The effect of implanted yt-	
		trium on the growth and adherence of	
K. Yokota, K. Ohtsuki, M. Ochi, S.		alumina scales on Fe-20Cr-5Al	47 (1991) 261
Ishihara and I. Kimura, Accumulation		S. Kar, A. Raychaudhuri, A.K. Sinha and	
of implanted arsenic at the interface		S. Ashok, Ion beam modification of	
during annealing on thermally oxi-	44 444 44 44 44	the dielectric properties of thin silicon	40 /40 /1001 274
dized Si and SiO <sub>2</sub> covered Si	41/42 (1989) 411	dioxide films	48/49 (1991) 264
N. Hecking and E.H. te Kaat, Modelling		J. Wagner, Raman spectroscopy for im-	

80

purity characterization in III-V semi- conductors	50 (1991) 79	techniques to optimize the Mg implan- tation annealing for self-aligned HBT's	50 (1991) 462
C. Frigeri, J.L. Weyher and M. De Potter, TEM study of the origin of the surface microroughness in DSL photoetched		Ion scattering	
Si-implanted GaAs wafers W. Pfeiffer, M. Deicher, R. Keller, R.	50 (1991) 115	Ion scattering	
Magerle, P. Pross, H. Skudlik, Th. Wichert, H. Wolf, D. Forkel, N. Moriya and R. Kalish, Characterization of Cd implanted and annealed		R.S. Williams, R.S. Daley, J.H. Huang and R.M. Charatan, Initial stages of metal/semiconductor interface forma- tion: Au and Ag on Si(111)	41/42 (1989) 70
GaAs and InP by perturbed angular correlation (PAC) spectroscopy S.G. Jahn, H. Hofsäss, U. Wahl, S. Winter, E. Recknagel and ISOLDE Collabora-	50 (1991) 154	K. Sumitomo, K. Tanaka, Y. Izawa, I. Katayama, F. Shoji, K. Oura and T. Hanawa, Structural study of Ag over- layers deposited on a Si(111) substrate	
tion, Structural defect recovery in GaP after heavy ion implantation Z.M. Wang, J. Windscheif, D.J. As and	50 (1991) 169	by impact-collision ion-scattering- spectroscopy with time-of-flight detec- tion	41/42 (1989) 112
W. Jantz, Ambient and low tempera- ture photoluminescence topography of GaAs substrates, epitaxial and im-		M. Renda and K. Morita, Epitaxial growth of a mono-crystalline metastable AuIn layer at the Au/InP(001)	41/42 (1909) 112
planted layers  H. L'Haridon, P.N. Favennec, R. Coquille, M. Salvi, M. Gauneau, Y. Le	50 (1991) 228	interface M. Itoh, M. Kinoshita, T. Ajioka, M. Itoh and T. Inada, Crystalline quality of	41/42 (1989) 216
Guillou, R. Callec and P. Gall, Spatial investigation of an iron-doped indium phosphide ingot  J. Tatarkiewicz, A. Kozanecki, Z. Kaliń-	50 (1991) 237	heteroepitaxial silicon on epitaxial NiSi <sub>2</sub> /Si(100)  K. Suguro, Y. Nakasaki, T. Yoshii and T. Itoh, Barrier metal between tungsten	41/42 (1989) 262
ski and K. Paprocki, Photolumines- cence study of proton-implanted	50 (1001) 040	and silicon for high temperature processing	41/42 (1989) 277
InP <sub>1-x</sub> As <sub>x</sub> :Yb  A. Deneuville, C.H. Park, P. Ayyub, T. Anderson, P. Lowen, K. Jones and P.H. Holloway, O implantation in	50 (1991) 249	T. Ito, A. Yamama, A. Hiraki and M. Satou, Silicidation of porous silicon and its application for the fabrication of a buried metal layer	41/42 (1989) 301
ZnSe: lattice distortion by Raman measurement S.C. Moss, J.F. Knudsen, R.C. Bowman,	50 (1991) 308	H. Hasegawa, H. Ohno, H. Ishii, T. Haga, Y. Abe and H. Takahashi, Origin and properties of interface states at insula-	
Jr., P.M. Adams and D.D. Smith, Pi- cosecond transient photoreflectance measurements of ion-implanted GaAs	50 (1991) 337	tor-semiconductor and semiconduc- tor-semiconductor interfaces of com- pound semiconductors	41/42 (1989) 372
M. Wagner, N. Winkler and H.D. Geiler, Single-beam thermowave analysis of semiconductors	50 (1991) 373	<ul> <li>A.S. Barrière, G. Couturier, H. Guegan,</li> <li>T. Séguelong, A. Thabti, P. Alnot and</li> <li>J. Chazelas, Interface GaAs – gallium</li> </ul>	
M. Hage-Ali, B. Yaacoub, S. Mergui, M. Samimi, B. Biglari and P. Siffert, Microscopic defect level characterization		fluoride thin film grown by fluorin- ation. Electrical behaviour of the ob- tained MIS fluorinated GaAs struc-	
of semi-insulating compound semicon- ductors by TSC and PICTS. Applica- tion to the effect of hydrogen in CdTe R. Nipoti, D. Pocci, A. Cetronio and C.	50 (1991) 377	S. Tatarenko, J. Cibert, Y. Gobil, G. Feuillet, K. Saminadayar, A.C. Chami	41/42 (1989) 383
Lanzieri, Carrier and mobility profile measurements in n-type ion-implanted GaAs by the differential sheet resistiv-		and E. Ligeon, RHEED, XPS, HRTEM and channeling studies of molecular beam epitaxy growth of CdTe on (001) GaAs	41/42 (1989) 470
<ul><li>ity and Hall effect technique</li><li>V. Amarger, C. Dubon-Chevallier, A.C. Papadopoulo, B. Descouts and Y. Gao,</li></ul>	50 (1991) 410	H.C. Lee, H. Ishiwara, S. Furukawa, K. Saiki and A. Koma, Distribution of interfacial As atoms in the electron-	
Papadopoulo, B. Descouts and Y. Gao, Correlated use of characterization		interfacial As atoms in the electron- beam exposure and epitaxy (EBE-epi-	

taxy) technique for growing GaAs films on CaF <sub>2</sub> /Si(111) structures  T. Wada, M. Takeda, T. Yamada and M. Ichimura, Formation of a Ge <sub>x</sub> Si <sub>1-x</sub>	41/42 (1989) 553	Pt <sub>0.5</sub> Ni <sub>0.5</sub> (111) surface studied by medium-energy ion scattering J. Rickards, A. Oliver, J. Miranda and E.P. Zironi, Uses of PIXE at low pro-	45 (1990) 121
<ul><li>alloy layer by high-energy electron-beam irradiation</li><li>H. Horikawa, M. Akiyama, S. Onozawa,</li><li>Y. Kawai and M. Sakuta, Interfacial</li></ul>	41/42 (1989) 580	ton energies  J. Lausmaa, B. Kasemo, H. Mattsson and H. Odelius, Multi-technique surface characterization of oxide films on	45 (1990) 155
layers of InP/Si heteroepitaxy F. Priolo, A. La Ferla, C. Spinella, E. Rimini, S.U. Campisano and G. Ferla, Crystal-amorphous-silicon interface	41/42 (1989) 598	electropolished and anodically oxi- dized titanium  S. Deckers, F.H.P.M. Habraken, W.F. van der Weg and J.W. Geus, Oxidation of	45 (1990) 189
kinetics under ion beam irradiation  A. Seidel and G. Linker, Amorphization mechanisms in Mn <sup>+</sup> -implanted thin Al films and single crystals	41/42 (1989) 619 43 (1989) 97	clean and Pt-covered Ni(111)  J. Gao, W.A.M. Aarnink, G.J. Gerritsma and H. Rogalla, High quality YBa <sub>2</sub> Cu <sub>3</sub> O <sub>x</sub> ultra-thin films and Y/Pr/Y	45 (1990) 207
M. Berti, G. Mazzi, A.V. Drigo, A. Migliori, E. Jannitti and S. Nicoletti, Laser induced epitaxial regrowth of	43 (1909) 97	multilayers made by a modified RF- magnetron sputtering technique A. Boelle, J.A. Roger, B. Canut, J.	46 (1990) 74
Si <sub>1-x</sub> Ge <sub>x</sub> /Si layers produced by Ge ion implantation S.P. Withrow, O.W. Holland and S.J. Pennycook, Ion beam annealing of	43 (1989) 158	Mugnier and M. Pitaval, Sol-gel low- temperature preparation of silica films: RBS, TEM and MOS C-V characterization	46 (1990) 200
Ga-implanted Si C. Neelmeijer, P. Knothe, M. Posselt, E. Richter and KH. Heinig, Wear resistant coatings produced by C <sup>+</sup> im-	43 (1989) 191	E. D'Anna, G. Leggieri, A. Luches, M. Martino, A.V. Drigo, G. Majni, P. Mengucci and I.N. Mihailescu, Nitridation of titanium by multipulse ex-	
plantation F. Abel, C. Cohen, J.A. Davies, J. Moulin and D. Schmaus, Thin-film growth of	43 (1989) 232 44 (1990) 17	cimer laser irradiation  M. Elliq, E. Fogarassy, J.P. Stoquert, C. Fuchs, S. de Unamuno, B. Prévot and H. Pattyn, Pulsed excimer and	46 (1990) 365
Sn on Cu(100)  X.D. Peng and M.A. Barteau, Characterization of the crystallographic structure of MgO thin films by ISS on the basis		Nd:YAG laser crystallization of a- Si:H. The specific role of hydrogen R. Serna, C.N. Afonso, F. Catalina, N.	46 (1990) 378
of trajectory-dependent neutralization T. Ito, T. Yasumatsu and A. Hiraki, Ho- moepitaxial growth of silicon on anodized porous silicon	44 (1990) 87 44 (1990) 97	Teixeira, M.F. da Silva and J.C. Soares, Diffusion and microstructures induced by excimer laser irradiation in Ge-Sb thin film bilayers	46 (1990) 405
A.E.M.J. Fischer, W.F.J. Slijkerman, J.F. van der Veen and I. Ohdomari, Thermal stability of supersaturated oxygen-doped silicon epitaxial films	44 (1990) 115	S.J. Hoekje and G.B. Hoflund, Surface characterization study of InP(100) substrates using ISS, AES and ESCA: comparison of substrates from two	
V.V. Tokarev, A.V. Kibardin, T.M. Pyatkova and D.I. Zarovsky, Nickel, cobalt and iron silicide formation		different commercial sources W.A.M. Aarnink, D.H.A. Blank, D.J. Adelerhof, J. Flokstra, H. Rogalla, A.	47 (1991) 43
stimulated by argon implantation  S. Priggemeyer, A. Brockmeyer, H. Dötsch, H. Koschmieder, D.J. O'Connor and W. Heiland, The segregation of Pb on yttrium-iron-garnet (YIG)	44 (1990) 235	van Silfhout and R. de Reus, Interdif- fusion studies on high-T <sub>c</sub> supercon- ducting YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-δ</sub> thin films on Si(111) with a NiSi <sub>2</sub> /ZrO <sub>2</sub> buffer layer W.J. Quadakkers, J. Jedlinski, K. Schmidt,	47 (1991) 195
surfaces studied by ion scattering spectrometry (ISS)  S. Deckers, F.H.P.M. Habraken, W.F. van der Weg, A.W. Denier van der Gon, J.F. van der Veen and J.W. Geus, Oxidation-induced segregation at the	44 (1990) 255	<ul> <li>M. Krašovec, G. Borchardt and H. Nickel, The effect of implanted yttrium on the growth and adherence of alumina scales on Fe-20Cr-5Al</li> <li>G.N. Pain, T. Warminski, S. Sulcs, M.S. Kwietniak, D. Gao, S.R. Glanvill, C.J.</li> </ul>	47 (1991) 261

Rossouw, A.W. Stevenson, S.P. Russo, R.G. Elliman, L.S. Wielunski, R.S. Rowe, G.B. Deacon, R.S. Dickson and B.O. West, Characterization of low-		<ul> <li>S.C. Tjong, Electrochemical and surface analysis of the Fe-Cr-Ru system in non-oxidizing acid solutions</li> <li>P. Lejček, M. Koutník, J. Brádler, V.</li> </ul>	44 (1990) 7
temperature MOCVD $Cd_{1-x}Mn_xTe$ thin films  A. Chevarier, N. Chevarier, M. El Bouanani, E. Gerlic, M. Stern, B. Roux	48/49 (1991) 76	Paidar and A. Potměšilová, Anisotropy of grain boundary segregation in as-grown Fe-6at%Si alloy bicrystals	44 (1990) 75
and F. Thimon, Profiling of carbon, oxygen and argon contamination in sputter-deposited films using nuclear backscattering and nuclear reaction		J.P. Baltrus and A. Proctor, Composition of overlayers on oxidized pyrite surfaces S.C. Tjong and J.B. Malherbe, Auger	44 (1990) 147
spectroscopy  B.V. King, D.J. O'Connor, Y. Shen, R.J.  MacDonald, M. Katayama and M.	48/49 (1991) 215	studies of the effect of Mo, V and Pd additions on the oxidation characteristics of Fe-24Cr alloy	44 (1990) 179
Aono, LEIS for structure determina- tion of surfaces and thin films	48/49 (1991) 246	V.V. Tokarev, A.V. Kibardin, T.M. Pyatkova and D.I. Zarovsky, Nickel, cobalt and iron silicide formation	44 (1990) 179
I. Katayama, T. Hanawa, F. Shoji and K. Oura, ISS-AES study of the initial growth stage of Cu thin films on Si(111)-7 × 7	48/49 (1991) 361	stimulated by argon implantation  S. Priggemeyer, A. Brockmeyer, H.  Dötsch, H. Koschmieder, D.J. O'Con-	44 (1990) 235
T. Yasumatsu, T. Ito, H. Nishizawa and A. Hiraki, Ultrathin Si films grown epitaxially on porous silicon	48/49 (1991) 414	nor and W. Heiland, The segregation of Pb on yttrium-iron-garnet (YIG) surfaces studied by ion scattering	
V.Kh. Kudoyarova, G.M. Gusinsky, L.A. Rassadin and I.V. Kudryavtsev, Hy- drogen depth profile measurement in		spectrometry (ISS) S.C. Tjong, A surface study of the passivation of Fe-Cr-Co magnet alloys in	44 (1990) 255
<ul> <li>a-Si<sub>1-x</sub>C<sub>x</sub>:H films by elastic recoil detection</li> <li>B. Holländer, S. Mantl, B. Stritzker, F. Schäffler, HJ. Herzog and E. Kasper,</li> </ul>	50 (1991) 173	sulphuric acid solution  J.C. Ingram, K.W. Nebesny and J.E.  Pemberton, Optical properties of selected first-row transition metals de-	45 (1990) 141
Strain and defect densities in Si/Si <sub>1-x</sub> Ge <sub>x</sub> heterostructures investigated by ion scattering and X-ray diffraction	50 (1991) 450	loss spectroscopy Xin Xu and J.I. Steinfeld, UV-laser photodeposition of iron films from	45 (1990) 247
R. Schwarz, T. Fischer, P. Hanesch, T. Muschik, J. Kolodzey, H. Cerva, H.L. Meyerheim and B.M.U. Scherzer, Limitations of interface sharpness in		Fe(CO) <sub>5</sub> : role of gas-phase and surface dissociation processes S.C. Tjong, Self-passivation of Fe-Cr- PGM alloys in reducing acids studied	45 (1990) 281
a-Si:H/a-SiC:H multilayers	50 (1991) 456	by electrochemical and electron spec- troscopic techniques LU.A. Andersen and J. Bøttiger, Crys-	45 (1990) 301
Iridium		tallization of Fe-Zr metallic glasses during ion irradiation J. Eymery, C. Senillou, J.C. Joud and A.	46 (1990) 427
P. Hoffmann, B. Lecohier, S. Goldoni and H. van den Bergh, Fast laser writ- ing of copper and iridium lines from		Chamberod, An Auger depth profile analysis of a sputtered Fe-Ti multi- layer structure	47 (1991) 127
thin solid surface layers of metalor- ganic compounds	43 (1989) 54	S.C. Tjong and H.C. Swart, Auger characterization of the surface oxidation of austenitic Fe-26Mn-7Al-0.9C al-	
Iron		loy H. L'Haridon, P.N. Favennec, R. Co- quille, M. Salvi, M. Gauneau, Y. Le	47 (1991) 311
Y. Kamiura, F. Hashimoto and M. Iwami, Iron accumulation at the Si-SiO <sub>2</sub> in-	41 (42 (1000) 447	Guillou, R. Callec and P. Gall, Spatial investigation of an iron-doped indium	
terface and possible reduction of SiO <sub>2</sub>	41/42 (1989) 447	phosphide ingot	50 (1991) 237

E W 1 A GUI D WA			
F. Mosel, A. Seidl, D. Hofmann and G.		M. Jubber, J.I.B. Wilson, J.L. Davidson,	
Müller, Infrared absorption of n- and		P.A. Fernie and P. John, Laser writing	43 (1989) 74
p-type Fe-doped InP and mapping of the Fe distribution	50 (1991) 364	of high purity gold tracks D. Milne, J.I.B. Wilson, T.T. Rantala and	43 (1909) 74
B. Sartorius, M. Brandstättner and H.	30 (1991) 304	J. Lenkkeri, Morphological and struct-	
Venghaus, Two-wavelength transmis-		ural changes in laser CVD of silicon:	
sion: a rapid and precise method for		comparison of theoretical temperature	
measuring the light absorption in		calculations with experimental results	43 (1989) 81
semiconductors	50 (1991) 369	E.E. Marinero, Material transformations	43 (1707) 01
L. Roberts and G.J. Hughes, An investi-	30 (1991) 309	in semiconductor and magnetic thin	
gation of metal/GaAs(100) interfaces		films	43 (1989) 117
by deep level transient spectroscopy	50 (1991) 424	W.C. Sinke, A. Polman, S. Roorda and	(2,0,)
C. De las Heras, I.J. Ferrer and C.	30 (1)/1) 121	P.A. Stolk, Explosive crystallization of	
Sánchez, Comparison of pyrite thin		amorphous silicon: triggering and	
films obtained from Fe and natural		propagation	43 (1989) 128
pyrite powder	50 (1991) 505	O. Bostanjoglo and P. Thomsen-Schmidt,	12 (1707) 120
pyrite periods	30 (1)/1) 303	Laser-induced multiple phase transi-	
T .1 .1		tions in Ge-Te films traced by time-	
Lanthanides		resolved TEM	43 (1989) 136
		E.L. Mathé, J.G. Maillou, A. Naudon, E.	10 (1707) 100
J. Tatarkiewicz, A. Kozanecki, Z. Kaliń-		Fogarassy, M. Elliq and S. de Un-	
ski and K. Paprocki, Photolumines-		amuno, Excimer laser recrystallization	
cence study of proton-implanted		of amorphous Si films characterized	
$InP_{1-x}As_x:Yb$	50 (1991) 249	by grazing X-ray diffraction and opti-	
		cal reflectivity	43 (1989) 142
Laser processing		J.G. Maillou, E.L. Mathé, J.C. Desoyer,	15 (1707) 112
I		S. de Unamuno and E. Fogarassy,	
K.J. Mackey, D.C. Rodway, P.C. Smith		Comparison between microscopical	
and A.W. Vere, Photo-assisted		aspects of a-Si films crystallized by	
MOVPE growth of calcium fluoride	43 (1989) 1	pulsed UV excimer laser and calcu-	
G.S. Higashi, The chemistry of alkyl-alu-	43 (1909)	lated temperature profiles	43 (1989) 150
minum compounds during laser-as-		M. Berti, G. Mazzi, A.V. Drigo, A.	45 (1707) 150
sisted chemical vapor deposition	43 (1989) 6	Migliori, E. Jannitti and S. Nicoletti,	
R. Nowak, P. Hess, H. Oetzmann and C.	43 (1909)	Laser induced epitaxial regrowth of	
Schmidt, XPS characterization of		$Si_{1-x}Ge_x/Si$ layers produced by Ge	
chromium films deposited from		ion implantation	43 (1989) 158
Cr(CO) <sub>6</sub> at 248 nm	43 (1989) 11	J. Marfaing, W. Marine, R. Pierrisnard	15 (1707) 100
E. Boch, C. Fuchs, E. Fogarassy and P.	43 (1909) 11	and A. Cros, Structural changes in	
Siffert, Influence of dilution in nitro-		$Au_xSi_{1-x}$ alloy films under laser	
gen on the photodissociation processes		irradiation	43 (1989) 165
of silane and disilane at 193 nm	43 (1989) 17	C.N. Afonso, J. Solis and F. Catalina,	10 (2505) 200
G. Auvert, Kinetics and mechanisms of	43 (1707) 17	Time-resolved optical measurements	
CW laser induced deposition of metals		of laser melting and rapid solidifica-	
for microelectronics	43 (1989) 47	tion on GeAl films	43 (1989) 171
P. Hoffmann, B. Lecohier, S. Goldoni	43 (1707) 47	E. Gaffet, J.M. Pelletier and S. Bonnet-	()
and H. van den Bergh, Fast laser writ-		Jobez, Laser surface alloying of Ni	
ing of copper and iridium lines from		film on Al-based alloy	43 (1989) 248
thin solid surface layers of metalor-		P.V. Huong, O. Segond, P. Gentilini and	
ganic compounds	43 (1989) 54	R. Cavagnat, Silicon aggregates pro-	
B. Lecohier and H. van den Bergh, Selec-	13 (1707) 34	duced by laser beam in a silicon	
tive copper film growth on platinum		carbide surface	43 (1989) 256
clusters	43 (1989) 61	M. Wagner, A. Witzmann, H.D. Geiler	( )
C. Garrido, D. Braichotte, H. van den	15 (1707) 01	and KH. Heinig, Formation of p-n	
Bergh, B. León and M. Pérez-Amor,		junctions and silicides in silicon using	
Interconnection lines of Pt induced by		a high performance laser beam homo-	
laser direct writing	43 (1989) 68	genization system	43 (1989) 260
	(2,07)	<b>9</b>	

B. Woratschek, P.G. Carey, M. Stolz and F.G. Bachmann, Excimer laser plan- arization of AlSi, AlSiTi and AlSiCu		M. Buck and P. Hess, Ablation of ben- zene from van der Waals films with excimer laser pulses at 248 nm	43 (1989) 358
alloys  F. Hanus and M. Wautelet, Time-re- solved temperature measurements dur- ing laser-induced synthesis of Cu-Te	43 (1989) 264	<ul> <li>H. Dupendant, J.P. Gavigan, D. Givord,</li> <li>A. Lienard, J.P. Rebouillat and Y.</li> <li>Souche, Velocity distribution of micron-size particles in thin film laser</li> </ul>	
compounds  E.J. Petit, J. Riga, R. Caudano and J.  Verbist, Ultraviolet laser-induced oxidation of antimony: chemical com-	43 (1989) 271	ablation deposition (LAD) of metals and oxide superconductors W. Marine, M. Peray, Y. Mathey and D. Pailharey, Deposition of Y-Ba-Cu	43 (1989) 369
position and growth kinetics of the oxide layer  J. Kubátová, V. Cháb, I. Lukeš, P. Jiříček and F. Fendrych, ArF excimer laser	43 (1989) 285	oxide superconducting thin films by Nd:YAG laser evaporation M. Brown, M. Shiloh, R.B. Jackman and I.W. Boyd, Geometric optimisation for	43 (1989) 377
induced changes in the Si(100)/SiO <sub>2</sub> interface studied in situ by ESCA and LEED	43 (1989) 297	the deposition of high temperature su- perconductors  P.E. Dyer, R.D. Greenough, A. Issa and	43 (1989) 382
V. Craciun, G. Leggieri, A. Luches, M. Martino, I.N. Mihailescu and I. Ursu, Synthesis of metallic and semiconduc- tor nitrides by multipulse laser irradia-		<ul> <li>P.H. Key, TEA CO<sub>2</sub> laser ablation studies of Y-Ba-Cu-O</li> <li>A. Mele, D. Consalvo, D. Stranges, A. Giardini-Guidoni and R. Teghil, Clus-</li> </ul>	43 (1989) 387
tion of solid samples in ambient gases R. Fantoni, E. Borsella, S. Piccirillo, C.A. Nannetti, R. Ceccato and S. Enzo,	43 (1989) 304	ter ion formation by laser evaporation of solid complex oxides  S. Metev and K. Meteva, Nucleation and	43 (1989) 398
Laser assisted synthesis of ultrafine silicon powder	43 (1989) 308	growth of laser-plasma deposited thin films	43 (1989) 402
E. Fogarassy, C. Fuchs, S. de Unamuno and P. Siffert, Excimer laser induced melting of heavily doped silicon: a		T.S. Baller and J. Dieleman, Nanosecond excimer laser-enhanced chemical etch- ing	43 (1989) 409
contribution to the optimization of the laser doping process	43 (1989) 316	J. Meiler, R. Matz and D. Haarer, Laser- induced photochemical etching of InP	
R. Nipoti, M. Bianconi, R. Fabbri, M. Servidori, S. Nicoletti and R. Canteri, Electrical and structural characterization of silicon layers directly doped		by HBr and HCl  J. Boulmer, B. Bourguignon, J.P. Budin and D. Debarre, Time of flight study of low pressure laser etching of silicon	43 (1989) 416
with boron by excimer laser irradia- tion	43 (1989) 321	by chlorine  J.E. Epler, R.D. Bringans, F.A. Ponce,	43 (1989) 424
P.G. Carey and T.W. Sigmon, In-situ doping of silicon using the gas immer- sion laser doping (GILD) process	43 (1989) 325	G.B. Anderson, D.W. Treat and T.L. Paoli, Laser patterned desorption within an upflow metalorganic chem-	
F. Foulon, A. Slaoui and P. Siffert, ArF excimer laser doping of boron into silicon		ical vapor deposition reactor Xin Xu and J.I. Steinfeld, UV-laser pho-	43 (1989) 432
A.M. Prokhorov, A.Yu. Bonchik, S.G. Kiyak, A.A. Manenkov, G.N. Mik-	43 (1989) 333	todeposition of iron films from Fe(CO) <sub>5</sub> : role of gas-phase and surface dissociation processes	45 (1990) 281
hailova, A.V. Pokhmurskaja, A.S. Seferov, I. Ursu, V. Craciun and I.N. Mihailescu, Laser solid-phase doping		D. Braichotte, C. Garrido and H. van den Bergh, The photolytic laser chemical vapor deposition rate of platinum, its	
of semiconductors  E.E.B. Campbell, G. Ulmer, B. Hasselberger and I.V. Hertel, Investigation	43 (1989) 340	dependence on wavelength, precursor vapor pressure, light intensity, and laser beam diameter	46 (1990) 9
of positive and negative ionic products from laser ablation of polymers	43 (1989) 346	R. Larciprete, Photoprocesses in organo- metallics	46 (1990) 19
R. Braun, R. Nowak, P. Hess, H. Oetz- mann and C. Schmidt, Photoablation of polyimide with IR and UV laser		J. Simpson and J.O. Williams, Preferential (111) orientation of ZnSe on (100) GaAs deposited by laser-in-	
radiation	43 (1989) 352	duced MOCVD	46 (1990) 27

C. Girault, D. Damiani, C. Champeaux, P. Marchet, C. German, J. P. Mercurio, J. Aubreton and A. Catherinot, Characterization of the KF Isaer-induced plasma plume created above an YBaCuO superconducting target and preparation of superconducting thin films  A. Saijadi, K. Kuen-Lau, F. Saba, F. Beech and I.W. Boyd, Laser-ablation adeposition of unform thin films of B <sub>3</sub> -Sr,CaCu <sub>2</sub> O, PE. Dyer, A. Isas and P.H. Key, An investigation of laser ablation and deposition of VBa-Cu-O in an oxygen environment  C. Konstantinov, R. Nowak and P. Hess, Gas-phase transport and kinetics in pulsed-laser CVD  Y. Morishige, S. Kitamura and S. Kishida, High performance contact formation in LSI circuit restructuring using visible pulse laser induced ablation and CVD  A. Bauer, J. Ganz, K. Hesse and E. Köhler, Laser-assisted deposition for electronic packaging applications  A.F. Bernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems  A.P. Bernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems  A.P. Bernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems  A.P. Bernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems  A.P. Pernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Relay and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems  A.P. Pernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Relay and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems  A.P. Pernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Relay and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems  A.P. Pernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer,	P. Vase, Shen Yueqiang and T. Freltoft, Deposition, characterization, and laser ablation patterning of YBCO thin films	46 (1990) 61	H. Esrom and U. Kogelschatz, Investiga- tion of the mechanism of the UV-in- duced palladium deposition process from thin solid palladium acetate films	46 (1990) 158
duced plasma plume created above an YBaCuO superconducting target and preparation of superconducting thin films  A. Sajiadi, K. Kuen-Lau, F. Saba, F. Beech and I.W. Boyd, Laser-ablation deposition of uniform thin films of Bi, Sr, CaCu, O, PE. Dyer, A. Issa and P.H. Key, An investigation of laser ablation and deposition of Y-Ba-Cu-O in an oxygen environment  G. Wahl and H. Esrom, Simulation of laser CVD 46 (1990) 89  L. Konstantinov, R. Nowak and P. Hess, Gas-phase transport and kinetics in pulsed-laser CVD 46 (1990) 102  L. Konstantinov, R. Nowak and P. Hess, Gas-phase transport and kinetics in pulsed-laser CVD 46 (1990) 102  K. Morishige, S. Kitamura and S. Kishida, High performance contact formation in LSI circuit restructuring using visible pulse laser induced ablation and CVD Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems  A.F. Bernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems  A.F. Pernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems  A.F. Pernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems  A.F. Pernhardt, A.T. Barfknecht end CVD of tungsten  A.P. Putzar, HC. Petzold and H. Staiger, Optimization of the laser-induced deposition technique for its application in X-ray make repair  A.J. P. van Maaren, R.L. Krans and W.C. Sinke, HF formation in laser-induced deposition to the laser-induced deposition for electronic packaging of very-high-speed digital systems  A.F. Bernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems  A.F. Bernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip packaging fo	P. Marchet, C. Germain, J.P. Mercu-		R. Pielmeier, D. Bollmann and K. Ha- berger, Laser evaporation of metal	
A Sajjadi, K. Kuen-Lau, F. Saba, F. Beech and I.W. Boyd, Laser-ablation deposition of uniform thin films of Bi <sub>2</sub> Sr <sub>2</sub> Ca(2u <sub>2</sub> ), Q. P.E. Dyer, A. Issa and P.H. Key, An investigation of laser CVD	duced plasma plume created above an YBaCuO superconducting target and		E. Fogarassy, A. Slaoui, C. Fuchs and J.P. Stoquert, Deposition of SiO <sub>2</sub> by reac-	46 (1990) 163
A. Saljadi, K. Kuen-Lau, F. Saba, F. Beech and L.W. Boyd, Laser-ablation deposition of uniform thin films of Bi, Sr, CaCu, 20, P. E. Dyer, A. Issa and P.H. Key, An investigation of laser ablation and deposition of V-Ba-Cu-O in an oxygen environment (aser CVD) (aser CVD) (aser CVD) (b. Konstantinov, R. Nowak and P. Hess, Gas-phase transport and kinetics in pulsed-laser CVD) (b. Konstantinov, R. Nowak and P. Hess, Gas-phase transport and kinetics in pulsed-laser CVD) (b. Konstantinov, R. Nowak and P. Hess, Gas-phase transport and kinetics in pulsed-laser CVD) (b. Konstantinov, R. Nowak and P. Hess, Gas-phase transport and kinetics in pulsed-laser CVD) (b. Konstantinov, R. Nowak and P. Hess, Gas-phase transport and kinetics in pulsed-laser CVD) (b. Konstantinov, R. Nowak and P. Hess, Gas-phase transport and kinetics in pulsed-laser CVD) (b. Konstantinov, R. Nowak and P. Hess, Gas-phase transport and kinetics in pulsed-laser CVD) (b. Konstantinov, R. Nowak and P. Hess, Gas-phase transport and kinetics in pulsed-laser CVD) (b. Konstantinov, R. Nowak and P. Hess, Gas-phase transport and kinetics in pulsed-laser CVD) (b. Konstantinov, R. Nowak and P. Hess, Gas-phase transport and kinetics in pulsed-laser induced ablation and CVD (c. R. Tephi), A. Giardini-Guidoni, S. Piccirillo, A. Mele and F. Polla-Mattiot, In stu formation of ionic carbide clusters by laser ablation and H. Stagiar, On the role of the substrate of the CVD of the substrate of the CVD of the substrate of the CVD (c. R. Tephi), A. Giardini-Guidoni, S. Piccirillo, A. Mele and F. Polla-Mattio, In stu formation of ionic carbide clusters by laser ablation of the laser-induced deposition technique for its applications (c. P. Curcio, M. Muski, N. Notaro and G. De Michele, Synthesis of ultrafine TiO <sub>2</sub> powders by a CW CO <sub>2</sub> laser (d. 1990) 121 (d. 1990) 122 (d. 1990) 123 (d. 1990) 123 (d. 1990) 124 (d. 1990) 125 (d. 1990) 125 (d. 1990) 125 (d. 1990) 126 (d. 1990) 127 (d. 1990) 128 (d. 1990) 128 (d. 1990) 128 (d. 1990) 128 (d. 1990) 129 (d. 1990) 129 (d. 1990)		46 (1990) 78		46 (1990) 195
P.E. Dyer, A. Issa and P.H. Key, An investigation of laser ablation and deposition of Y-Ba-Cu-O in an oxygen environment  G. Wahl and H. Esrom, Simulation of laser CVD  L. Konstantinov, R. Nowak and P. Hess, Gas-phase transport and kinetics in pulsed-laser CVD  Y. Morishige, S. Kitamura and S. Kishida, High performance contact formation in LSI circuit restructuring using visible pulse laser induced ablation and CVD  A. Bauer, J. Ganz, K. Hesse and E. Köhler, Laser-assisted deposition for electronic packaging applications  A.F. Bernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems  R. Putzar, HC. Petzold and H. Staiger, Optimization of the laser-induced deposition in LSE circuit mestructuring of conducting traces by chemical modification of solid coatings with laser radiation  H. Sigmund, Excimer laser deposition of silica films: a comparison between two methods  J. Elders, D. Bebelaar and J.D.W. van Voorst, Photochemical wapor deposition of titaniumdiboride  R. Teghil, A. Giardini-Guidoni, S. Piccirillo, A. Mele and F. Pollat-Mattiot, In situ formation of inic transition of inication of the substrate position in the CO <sub>2</sub> laser CVD of Egobusda, R. Lange, G. Molkopf and H. Staiger, Optimization of the laser-induced deposition in the CO <sub>2</sub> laser CVD of tungsten  H. Gilwan, A. Giardini-Guidoni, S. Piccirillo, A. Mele and F. Pollat-Mattiot, In situ formation of inic transition of inic transition of inic transition of the substrate position in the CO <sub>2</sub> laser CVD of amorphous hydrogenated silicon  K. Hessh, P. Hess, H. Oetzmann and C. Schmidt, Laser CVD of a Schmidt, Laser CVD of a Schmidt, Laser CVD of a Callina and D. Bermejo, Good-quality Ge films grown by excimer laser deposition of imagewise wetting and metallization  H. Gilvan, R. Lezare, Surface modifications of Kapton and cured polyimide films by ArF excimer laser: applications to imagewise wetting and metallization  J. F. Certino, A. Musci, N. Notaro and G.	A. Sajjadi, K. Kuen-Lau, F. Saba, F. Beech and I.W. Boyd, Laser-ablation deposition of uniform thin films of		<ul> <li>T. Szörényi, P. González, D. Fernández,</li> <li>J. Pou, B. León and M. Pérez-Amor,</li> <li>Gas mixture dependence of the LCVD</li> </ul>	
G. Wahl and H. Esrom, Simulation of laser CVD L. Konstantinov, R. Nowak and P. Hess, Gas-phase transport and kinetics in pulsed-laser CVD Y. Morishige, S. Kitamura and S. Kishida, High performance contact formation in LSI circuit restructuring using visible pulse laser induced ablation and CVD A. Bauer, J. Ganz, K. Hesse and E. Köhler, Laser-assisted deposition for electronic packaging applications A.F. Bernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems R. Putzar, HC. Petzold and H. Staiger, Optimization of the laser-induced deposition technique for its application in X-ray mask repair A.J.P. van Maaren, R.L. Krans and W.C. Sinke, HF formation in laser-induced CVD of Ungsten H.G. Müller, K. Buschick, S. Schuler and A. Paredes, Laser direct writing of cooper on various thin-film substrate materials W. Bode, E.W. Kreutz and M. Krösche, Direct writing of conducting traces by chemical modification of solid coatings with laser radiation Y. Zhang and M. Stuke, VUV synchrotron radiation processing of thin palladium acetate spin-on films for	P.E. Dyer, A. Issa and P.H. Key, An investigation of laser ablation and de-	46 (1990) 84	B. León, A. Klumpp, M. Pérez-Amor and H. Sigmund, Excimer laser deposition	46 (1990) 206
L. Konstantinov, R. Nowak and P. Hess, Gas-phase transport and kinetics in pulsed-laser CVD  Y. Morishige, S. Kitamura and S. Kishida, High performance contact formation in LSI circuit restructuring using visible pulse laser induced ablation and CVD  A. Bauer, J. Ganz, K. Hesse and E. Köhler, Laser-assisted deposition for electronic packaging applications  A.F. Bernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems  R. Putzar, HC. Petzold and H. Staiger, Optimization of the laser-induced deposition technique for its application in X-ray mask repair  A.J.P. van Maaren, R.L. Krans and W.C. Sinke, HF formation in laser-induced CVD of tungsten  H.G. Müller, K. Buschick, S. Schuler and A. Paredes, Laser direct writing of cooper on various thin-film substrate materials  M. Bode, E.W. Kreutz and M. Krösche, Direct writing of conducting traces by chemical modification of solid coatings with laser radiation  Y. Zhang and M. Stuke, VUV synchrotron radiation processing of thin palladium acetate spin-on films for	environment G. Wahl and H. Esrom, Simulation of		two methods  J. Elders, D. Bebelaar and J.D.W. van	46 (1990) 210
Y. Morishige, S. Kitamura and S. Kishida, High performance contact formation in LSI circuit restructuring using visible pulse laser induced ablation and CVD  A. Bauer, J. Ganz, K. Hesse and E. Köhler, Laser-assisted deposition for electronic packaging applications  A.F. Bernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems  R. Putzar, HC. Petzold and H. Staiger, Optimization of the laser-induced deposition technique for its application in X-ray mask repair  A.J.P. van Maaren, R.L. Krans and W.C. Sinke, HF formation in laser-induced CVD of tungsten  H.G. Müller, K. Buschick, S. Schuler and A. Paredes, Laser direct writing of coper on various thin-film substrate materials  M. Bode, E.W. Kreutz and M. Krösche, Direct writing of conducting traces by chemical modification of solid coatings with laser radiation  Y. Zhang and M. Stuke, VUV synchrotron radiation processing of thin palladium acetate spin-on films for  H. G. Müller, K. Buschick, S. Verutz and M. Stuke, VUV synchrotron radiation processing of thin palladium acetate spin-on films for  H. G. Müller, K. Buschick, S. Verutz and M. Krösche, Direct writing of conducting traces by chemical modification of foling for  H. Stafast, On the role of the substrate tensor the substrate tensor that H. Stafast, On the role of the substrate tensor the of the substrate tensor the substrate tensor that H. Stafast, On the role of the substrate position in the CO <sub>2</sub> laser CVD of amorphous hydrogenated silicon  H. Stafast, On the role of the substrate position in the CO <sub>2</sub> laser CVD of amorphous hydrogenated silicon  H. Stafast, On the role of the substrate position in the CO <sub>2</sub> laser CVD of amorphous hydrogenated silicon  H. Stafast, On the role of the substrate position in the CO <sub>2</sub> laser CVD of amorphous hydrogenated silicon  H. Stafast, On the role of the substrate position in the CO <sub>2</sub> laser CVD of amorphous hydrogenated silicon  H. Stafast, On the role of the substrate pos	L. Konstantinov, R. Nowak and P. Hess,	46 (1990) 96	tion of titaniumdiboride	46 (1990) 215
High performance contact formation in LSI circuit restructuring using visible pulse laser induced ablation and CVD  A. Bauer, J. Ganz, K. Hesse and E. Köhler, Laser-assisted deposition for electronic packaging applications  A.F. Bernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems  R. Putzar, HC. Petzold and H. Staiger, Optimization of the laser-induced deposition technique for its application in X-ray mask repair  A.J.P. van Maaren, R.L. Krans and W.C. Sinke, HF formation in laser-induced CVD of ungsten  H.G. Müller, K. Buschick, S. Schuler and A. Paredes, Laser direct writing of cooper on various thin-film substrate materials  M. Bode, E.W. Kreutz and M. Krösche, Direct writing of conducting traces by chemical modification of solid coatings with laser radiation  Y. Zhang and M. Stuke, VUV synchrotrotron radiation processing of thin palladium acetate spin-on films for		46 (1990) 102		
in LSI circuit restructuring using visible pulse laser induced ablation and CVD  A. Bauer, J. Ganz, K. Hesse and E. Köhler, Laser-assisted deposition for electronic packaging applications  A.F. Bernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems  R. Putzar, HC. Petzold and H. Staiger, Optimization of the laser-induced deposition in chenique for its application in X-ray mask repair  A.J.P. van Maaren, R.L. Krans and W.C. Sinke, HF formation in laser-induced CVD of tungsten  H.G. Müller, K. Buschick, S. Schuler and A. Paredes, Laser direct writing of copper on various thin-film substrate materials  M. Bode, E.W. Kreutz and M. Krösche, Direct writing of conducting traces by chemical modification of solid coatings with laser radiation  Y. Zhang and M. Stuke, VUV synchrotron radiation processing of thin palladium acetate spin-on films for				46 (1000) 220
ble pulse laser induced ablation and CVD  46 (1990) 108  46 (1990) 108  TiO <sub>2</sub> powders by a CW CO <sub>2</sub> laser  46 (1990) 225  46 (1990) 113  A.F. Bernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems  R. Putzar, HC. Petzold and H. Staiger, Optimization of the laser-induced deposition in X-ray mask repair  A.J.P. van Maaren, R.L. Krans and W.C. Sinke, HF formation in laser-induced CVD of tungsten  A. Paredes, Laser direct writing of copper on various thin-film substrate materials  M. Bode, E.W. Kreutz and M. Krösche, Direct writing of copper on various thin-film substrate materials  M. Bode, E.W. Kreutz and M. Krösche, Direct writing of conducting traces by chemical modification of solid coatings with laser radiation  Y. Zhang and M. Stuke, VUV synchrotron radiation processing of thin palladium acetate spin-on films for  46 (1990) 108  TiO <sub>2</sub> powders by a CW CO <sub>2</sub> laser  46 (1990) 113  H. Stafast, On the role of the substrate position in the CO <sub>2</sub> laser CVD of amorphous vilcon  K. Hesch, P. Hess, H. Oetzmann and C. Schmidt, Laser CVD of a-Si:H from SiH <sub>4</sub> and Si <sub>2</sub> H <sub>4</sub> : relations between chemistry, growth rate and film properties  46 (1990) 121  W. Marine, J.M. Scotto D'Aniello and J. Marfaing, Picosecond YAG laser photoablation of amorphous silicon  C.N. Afonso, R. Serna, F. Catalina and D. Bermejo, Good-quality Ge films grown by excimer laser deposition  F.G. Bachmann, Industrial laser applications  46 (1990) 143  H. Hiraoka and S. Lazare, Surface modifications of Kapton and cured polyimide films by ArF excimer laser: applications to imagewise wetting and metallization  46 (1990) 254  46 (1990) 259  C.N. Afonso, R. Serna, F. Catalina and D. Bermejo, Good-quality Ge films grown by excimer laser deposition  46 (1990) 249  H. Hiraoka and S. Lazare, Surface modifications of Kapton and cured polyimide films by ArF excimer laser: applications to imagewise wetting and metallization  46 (1990) 254  H. Hiraoka and S. Lazar				46 (1990) 220
CVD A. Bauer, J. Ganz, K. Hesse and E. Köhler, Laser-assisted deposition for electronic packaging applications A.F. Bernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems R. Putzar, HC. Petzold and H. Staiger, Optimization of the laser-induced deposition technique for its application in X-ray mask repair A.J.P. van Maaren, R.L. Krans and W.C. Sinke, H. F formation in laser-induced CVD of tungsten H.G. Müller, K. Buschick, S. Schuler and A. Paredes, Laser direct writing of copper on various thin-film substrate materials M. Bode, E.W. Kreutz and M. Krösche, Direct writing of conducting traces by chemical modification of solid coatings with laser radiation Y. Zhang and M. Stuke, VUV synchrotron radiation processing of thin palladium acetate spin-on films for  46 (1990) 113 H. Stafast, On the role of the substrate position in the CO <sub>2</sub> laser CWD of amorphous hydrogenated silicon H. Stafast, On the role of the substrate position in the CO <sub>2</sub> laser CWD of amorphous hydrogenated silicon H. Stafast, On the role of the substrate position in the CO <sub>2</sub> laser CWD of amorphous hydrogenated silicon K. Hesch, P. Hess, H. Oetzmann and C. Schmidt, Laser CVD of a-Si:H from SiH <sub>4</sub> and Si <sub>2</sub> H <sub>6</sub> : relations between chemistry, growth rate and film properties W. Marine, J.M. Scotto D'Aniello and J. Marfaing, Picosecond YAG laser photoablation of amorphous silicon C.N. Afonso, R. Serna, F. Catalina and D. Bermejo, Good-quality Ge films grown by excimer laser deposition F.G. Bachmann, Industrial laser applications of Kapton and cured poly-imide films by AFF excimer laser: applications to imagewise wetting and metallization F.G. Bachmann, Industrial laser applications to imagewise wetting and metallization F.G. Bachmann, F.L. E. Campbell, Excimer laser ablation of polyimide F.G. Bachmann and E.E. Campbell, Excimer laser ablation of polyimide F.G. Bachmann, Industrial laser applications to imagewise wetting and metallization F.G. Bachmann,				
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electronic packaging applications  A.F. Bernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems  R. Putzar, HC. Petzold and H. Staiger, Optimization of the laser-induced deposition technique for its application in X-ray mask repair  A.J.P. van Maaren, R.L. Krans and W.C. Sinke, HF formation in laser-induced CVD of tungsten  H.G. Müller, K. Buschick, S. Schuler and A. Paredes, Laser direct writing of copper on various thin-film substrate materials  M. Bode, E.W. Kreutz and M. Krösche, Direct writing of conducting traces by chemical modification of solid coatings with laser radiation  Y. Zhang and M. Stuke, VUV synchrotron radiation processing of thin palladium acetate spin-on films for  46 (1990) 113  46 (1990) 121  46 (1990) 121  46 (1990) 121  46 (1990) 121  46 (1990) 121  46 (1990) 121  46 (1990) 121  46 (1990) 121  46 (1990) 121  46 (1990) 121  46 (1990) 123  46 (1990) 233  W. Marine, J.M. Scotto D'Aniello and J. Marfaing, Picosecond YAG laser photoablation of amorphous silicon  C.N. Afonso, R. Serna, F. Catalina and D. Bermejo, Good-quality Ge films grown by excimer laser deposition  F.G. Bachmann, Industrial laser applications of Kapton and cured polyimide films by ArF excimer laser: applications to imagewise wetting and metallization  46 (1990) 254  46 (1990) 148  G. Ulmer, B. Hasselberger, HG. Busmann and E.B. Campbell, Excimer laser ablation of polyimide  46 (1990) 272	A. Bauer, J. Ganz, K. Hesse and E.			
A.F. Bernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems  R. Putzar, HC. Petzold and H. Staiger, Optimization of the laser-induced deposition technique for its application in X-ray mask repair  A.J.P. van Maaren, R.L. Krans and W.C. Sinke, HF formation in laser-induced CVD of tungsten  H.G. Müller, K. Buschick, S. Schuler and A. Paredes, Laser direct writing of corper on various thin-film substrate materials  M. Bode, E.W. Kreutz and M. Krösche, Direct writing of conducting traces by chemical modification of solid coatings with laser radiation  Y. Zhang and M. Stuke, VUV synchrotor radiation processing of thin palladium acetate spin-on films for  A (1990) 231  K. Hesch, P. Hess, H. Oetzmann and C. Schmidt, Laser CVD of a-Si:H from SiH <sub>4</sub> and Si <sub>2</sub> H <sub>6</sub> : relations between chemistry, growth rate and film properties  W. Marine, J.M. Scotto D'Aniello and J. Marfaing, Picosecond YAG laser photoablation of amorphous silicon  C.N. Afonso, R. Serna, F. Catalina and D. Bermejo, Good-quality Ge films grown by excimer laser deposition  F.G. Bachmann, Industrial laser applications of Kapton and cured polyimide films by ArF excimer laser: applications to imagewise wetting and metallization  46 (1990) 249  H. G. Willer, K. Buschick, S. Schuler and A. Paredes, Laser direct writing of conducting traces by chemical modification of solid coatings with laser radiation  46 (1990) 143  G. Ulmer, B. Hasselberger, HG. Busmann and E.E.B. Campbell, Excimer laser ablation of polyimide  46 (1990) 272				
Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems  R. Putzar, HC. Petzold and H. Staiger, Optimization of the laser-induced de- position technique for its application in X-ray mask repair  A.J.P. van Maaren, R.L. Krans and W.C. Sinke, HF formation in laser-induced CVD of tungsten  H.G. Müller, K. Buschick, S. Schuler and A. Paredes, Laser direct writing of copper on various thin-film substrate materials  M. Bode, E.W. Kreutz and M. Krösche, Direct writing of conducting traces by chemical modification of solid coatings with laser radiation  Y. Zhang and M. Stuke, VUV synchro- tron radiation processing of thin pal- ladium acetate spin-on films for  K. Hesch, P. Hess, H. Oetzmann and C. Schmidt, Laser CVD of a-Si:H from SiH <sub>4</sub> and Si <sub>2</sub> H <sub>6</sub> : relations between chemistry, growth rate and film prop- etries  46 (1990) 121  M. Marfaing, Picosecond YAG laser pho- toablation of amorphous silicon  C.N. Afonso, R. Serna, F. Catalina and D. Bermejo, Good-quality Ge films grown by excimer laser deposition  F.G. Bachmann, Industrial laser applica- tions  46 (1990) 249  H. Hiraoka and S. Lazare, Surface mod- ifications of Kapton and cured poly- imide films by ArF excimer laser: ap- plications to imagewise wetting and metallization  46 (1990) 264  46 (1990) 148  M. Bolle, K. Luther, J. Troe, J. Ihlemann		46 (1990) 113		46 (1000) 220
Raley and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems  R. Putzar, HC. Petzold and H. Staiger, Optimization of the laser-induced deposition technique for its application in X-ray mask repair  A.J.P. van Maaren, R.L. Krans and W.C. Sinke, HF formation in laser-induced CVD of tungsten  A. Paredes, Laser direct writing of copper on various thin-film substrate materials  M. Bode, E.W. Kreutz and M. Krösche, Direct writing of conducting traces by chemical modification of solid coatings with laser radiation  Y. Zhang and M. Stuke, VUV synchrotron radiation processing of thin palladium acetate spin-on films for  A6 (1990) 121  A6 (1990) 123  A6 (1990) 124  A6 (1990) 128  A6 (1990) 128  A6 (1990) 129  A6 (1990)				46 (1990) 230
packaging for very-high-speed digital systems  R. Putzar, HC. Petzold and H. Staiger, Optimization of the laser-induced deposition technique for its application in X-ray mask repair  A.J.P. van Maaren, R.L. Krans and W.C. Sinke, HF formation in laser-induced CVD of tungsten  H.G. Müller, K. Buschick, S. Schuler and A. Paredes, Laser direct writing of copper on various thin-film substrate materials  M. Bode, E.W. Kreutz and M. Krösche, Direct writing of conducting traces by chemical modification of solid coatings with laser radiation  Y. Zhang and M. Stuke, VUV synchrotron radiation processing of thin palladium acetate spin-on films for  46 (1990) 121  SiH <sub>4</sub> and Si <sub>2</sub> H <sub>6</sub> : relations between chemistry, growth rate and film properties (hemistry,				
R. Putzar, HC. Petzold and H. Staiger, Optimization of the laser-induced deposition technique for its application in X-ray mask repair  A.J.P. van Maaren, R.L. Krans and W.C. Sinke, HF formation in laser-induced CVD of tungsten  H.G. Müller, K. Buschick, S. Schuler and A. Paredes, Laser direct writing of copper on various thin-film substrate materials  M. Bode, E.W. Kreutz and M. Krösche, Direct writing of chemical modification of solid coatings with laser radiation  Y. Zhang and M. Stuke, VUV synchrotron radiation processing of thin palladium acetate spin-on films for  46 (1990) 121  chemistry, growth rate and film properties  W. Marine, J.M. Scotto D'Aniello and J. Marfaing, Picosecond YAG laser photoablation of amorphous silicon  46 (1990) 239  C.N. Afonso, R. Serna, F. Catalina and D. Bermejo, Good-quality Ge films grown by excimer laser deposition  46 (1990) 138  F.G. Bachmann, Industrial laser applications  46 (1990) 249  H. Hiraoka and S. Lazare, Surface modifications of Kapton and cured polyimide films by ArF excimer laser: applications to imagewise wetting and metallization  46 (1990) 254  G. Ulmer, B. Hasselberger, HG. Busmann and E.E.B. Campbell, Excimer laser ablation of polyimide  46 (1990) 272				
Optimization of the laser-induced deposition technique for its application in X-ray mask repair  A.J.P. van Maaren, R.L. Krans and W.C. Sinke, HF formation in laser-induced CVD of tungsten  H.G. Müller, K. Buschick, S. Schuler and A. Paredes, Laser direct writing of copper on various thin-film substrate materials  M. Bode, E.W. Kreutz and M. Krösche, Direct writing of conducting traces by chemical modification of solid coatings with laser radiation  Y. Zhang and M. Stuke, VUV synchrotror radiation processing of thin palladium acetate spin-on films for  W. Marine, J.M. Scotto D'Aniello and J. Marfaing, Picosecond YAG laser photoablation of amorphous silicon  (A6 (1990) 131  D. Bermejo, Good-quality Ge films grown by excimer laser deposition  F.G. Bachmann, Industrial laser applications  46 (1990) 249  H. Hiraoka and S. Lazare, Surface modifications of Kapton and cured polyimide films by ArF excimer laser: applications to imagewise wetting and metallization  46 (1990) 148  G. Ulmer, B. Hasselberger, HG. Busmann and E.E.B. Campbell, Excimer laser ablation of polyimide  M. Bolle, K. Luther, J. Troe, J. Ihlemann		46 (1990) 121		
position technique for its application in X-ray mask repair  A.J.P. van Maaren, R.L. Krans and W.C. Sinke, HF formation in laser-induced CVD of tungsten  H.G. Müller, K. Buschick, S. Schuler and A. Paredes, Laser direct writing of copper on various thin-film substrate materials  M. Bode, E.W. Kreutz and M. Krösche, Direct writing of conducting traces by chemical modification of solid coatings with laser radiation  Y. Zhang and M. Stuke, VUV synchrotron radiation processing of thin palladium acetate spin-on films for  Marfaing, Picosecond YAG laser photoablation of amorphous silicon  Marfaing, Picosecond YAG laser photoablation of amorphous silicon  46 (1990) 131  C.N. Afonso, R. Serna, F. Catalina and D. Bermejo, Good-quality Ge films grown by excimer laser deposition  F.G. Bachmann, Industrial laser applications  46 (1990) 249  H. Hiraoka and S. Lazare, Surface modifications of Kapton and cured polyimide films by ArF excimer laser: applications to imagewise wetting and metallization  46 (1990) 254  G. Ulmer, B. Hasselberger, HG. Busmann and E.E.B. Campbell, Excimer laser ablation of polyimide  46 (1990) 272  M. Bolle, K. Luther, J. Troe, J. Ihlemann				46 (1990) 233
in X-ray mask repair  A.J.P. van Maaren, R.L. Krans and W.C. Sinke, HF formation in laser-induced CVD of tungsten  H.G. Müller, K. Buschick, S. Schuler and A. Paredes, Laser direct writing of copper on various thin-film substrate materials  M. Bode, E.W. Kreutz and M. Krösche, Direct writing of conducting traces by chemical modification of solid coatings with laser radiation  Y. Zhang and M. Stuke, VUV synchrotron radiation processing of thin palladium acetate spin-on films for  46 (1990) 131  toablation of amorphous silicon  46 (1990) 239  C.N. Afonso, R. Serna, F. Catalina and D. Bermejo, Good-quality Ge films grown by excimer laser deposition  46 (1990) 249  F.G. Bachmann, Industrial laser applications of Kapton and cured polyimide films by ArF excimer laser: applications to imagewise wetting and metallization  46 (1990) 254  G. Ulmer, B. Hasselberger, HG. Busmann and E.E.B. Campbell, Excimer laser ablation of polyimide  46 (1990) 272				
A.J.P. van Maaren, R.L. Krans and W.C. Sinke, HF formation in laser-induced CVD of tungsten  H.G. Müller, K. Buschick, S. Schuler and A. Paredes, Laser direct writing of copper on various thin-film substrate materials  M. Bode, E.W. Kreutz and M. Krösche, Direct writing of conducting traces by chemical modification of solid coatings with laser radiation  Y. Zhang and M. Stuke, VUV synchrotror radiation processing of thin palladium acetate spin-on films for  C.N. Afonso, R. Serna, F. Catalina and D. Bermejo, Good-quality Ge films grown by excimer laser deposition 46 (1990) 249  H. Hiraoka and S. Lazare, Surface modifications of Kapton and cured polyimide films by ArF excimer laser: applications to imagewise wetting and metallization 46 (1990) 264  G. Ulmer, B. Hasselberger, HG. Busmann and E.E.B. Campbell, Excimer laser ablation of polyimide 46 (1990) 272  M. Bolle, K. Luther, J. Troe, J. Ihlemann		46 (1000) 131		46 (1990) 239
Sinke, HF formation in laser-induced CVD of tungsten  H.G. Müller, K. Buschick, S. Schuler and A. Paredes, Laser direct writing of copper on various thin-film substrate materials  M. Bode, E.W. Kreutz and M. Krösche, Direct writing of conducting traces by chemical modification of solid coatings with laser radiation  Y. Zhang and M. Stuke, VUV synchrotron radiation processing of thin palladium acetate spin-on films for  D. Bermejo, Good-quality Ge films grown by excimer laser deposition  46 (1990) 249  H. Hiraoka and S. Lazare, Surface modifications of Kapton and cured polyimide films by ArF excimer laser: applications to imagewise wetting and metallization  46 (1990) 254  G. Ulmer, B. Hasselberger, HG. Busmann and E.E.B. Campbell, Excimer laser ablation of polyimide  46 (1990) 272  M. Bolle, K. Luther, J. Troe, J. Ihlemann		40 (1990) 131		40 (1770) 237
CVD of tungsten  H.G. Müller, K. Buschick, S. Schuler and A. Paredes, Laser direct writing of copper on various thin-film substrate materials  M. Bode, E.W. Kreutz and M. Krösche, Direct writing of conducting traces by chemical modification of solid coatings with laser radiation  Y. Zhang and M. Stuke, VUV synchrotron radiation processing of thin palladium acetate spin-on films for  46 (1990) 138  grown by excimer laser deposition  F.G. Bachmann, Industrial laser applications  46 (1990) 254  H. Hiraoka and S. Lazare, Surface modifications of Kapton and cured polyimide films by ArF excimer laser: applications to imagewise wetting and metallization  46 (1990) 264  G. Ulmer, B. Hasselberger, HG. Busmann and E.E.B. Campbell, Excimer laser ablation of polyimide  46 (1990) 272  M. Bolle, K. Luther, J. Troe, J. Ihlemann				
A. Paredes, Laser direct writing of copper on various thin-film substrate materials  M. Bode, E.W. Kreutz and M. Krösche, Direct writing of conducting traces by chemical modification of solid coatings with laser radiation  Y. Zhang and M. Stuke, VUV synchrotron radiation processing of thin palladium acetate spin-on films for  H. Hiraoka and S. Lazare, Surface modifications of Kapton and cured polyimide films by ArF excimer laser: applications to imagewise wetting and metallization  46 (1990) 254  H. Hiraoka and S. Lazare, Surface modifications of Kapton and cured polyimide films by ArF excimer laser: applications to imagewise wetting and metallization  46 (1990) 264  G. Ulmer, B. Hasselberger, HG. Busmann and E.E.B. Campbell, Excimer laser ablation of polyimide  46 (1990) 272		46 (1990) 138		46 (1990) 249
copper on various thin-film substrate materials  M. Bode, E.W. Kreutz and M. Krösche, Direct writing of conducting traces by chemical modification of solid coatings with laser radiation  Y. Zhang and M. Stuke, VUV synchrotron radiation processing of thin palladium acetate spin-on films for  H. Hiraoka and S. Lazare, Surface modifications of Kapton and cured polyimide films by ArF excimer laser: applications to imagewise wetting and metallization  46 (1990) 148  G. Ulmer, B. Hasselberger, HG. Busmann and E.E.B. Campbell, Excimer laser ablation of polyimide  46 (1990) 272				
materials  M. Bode, E.W. Kreutz and M. Krösche, Direct writing of conducting traces by chemical modification of solid coatings with laser radiation  Y. Zhang and M. Stuke, VUV synchrotron radiation processing of thin palladium acetate spin-on films for  46 (1990) 143  ifications of Kapton and cured polyimide films by ArF excimer laser: applications to imagewise wetting and metallization  46 (1990) 264  G. Ulmer, B. Hasselberger, HG. Busmann and E.E.B. Campbell, Excimer laser ablation of polyimide  46 (1990) 272  M. Bolle, K. Luther, J. Troe, J. Ihlemann				46 (1990) 254
M. Bode, E.W. Kreutz and M. Krösche, Direct writing of conducting traces by chemical modification of solid coatings with laser radiation  Y. Zhang and M. Stuke, VUV synchrotron radiation processing of thin palladium acetate spin-on films for  M. Bode, E.W. Kreutz and M. Krösche, imide films by ArF excimer laser: applications to imagewise wetting and metallization  46 (1990) 264  G. Ulmer, B. Hasselberger, HG. Busmann and E.E.B. Campbell, Excimer laser ablation of polyimide  46 (1990) 272		46 (1000) 143		
Direct writing of conducting traces by chemical modification of solid coatings with laser radiation  Y. Zhang and M. Stuke, VUV synchrotron radiation processing of thin palladium acetate spin-on films for  Direct writing of conducting traces by plications to imagewise wetting and metallization  46 (1990) 264  G. Ulmer, B. Hasselberger, HG. Busmann and E.E.B. Campbell, Excimer laser ablation of polyimide  46 (1990) 272  M. Bolle, K. Luther, J. Troe, J. Ihlemann		40 (1990) 143		
chemical modification of solid coatings with laser radiation  46 (1990) 264  G. Ulmer, B. Hasselberger, HG. Busmann and E.E.B. Campbell, Excimer laser ablation of polyimide  46 (1990) 272  M. Bolle, K. Luther, J. Troe, J. Ihlemann			The state of the s	
Y. Zhang and M. Stuke, VUV synchro- tron radiation processing of thin pal- ladium acetate spin-on films for mann and E.E.B. Campbell, Excimer laser ablation of polyimide 46 (1990) 272	chemical modification of solid coat-		metallization	46 (1990) 264
tron radiation processing of thin pal- ladium acetate spin-on films for I laser ablation of polyimide 46 (1990) 272		46 (1990) 148		
ladium acetate spin-on films for M. Bolle, K. Luther, J. Troe, J. Ihlemann				46 (1000) 272
				40 (1990) 2/2
	The state of the s	46 (1990) 153		

	sisted laser ablation of doped poly- methyl-methacrylate	46 (1990) 279	nanosecond laser irradiation: a time- resolved study	46 (1990) 383
	Baller, J.C.S. Kools and J. Dieleman, Surface temperature measurements using pyrometry during excimer laser pulsed etching of silicon in a Cl <sub>2</sub> en-		B. Hu, A. Seidl, R. Buchner, D. Boll- mann, W. van der Wel and K. Ha- berger, Investigation of laser recrys- tallization of thin Si films using	
	vironment	46 (1990) 292	numerical simulation	46 (1990) 388
	Iermann, C. Boulmer-Leborgne and B. Dubreuil, Spectroscopic study of the plasma created by interaction between		O. Bostanjoglo and P. Thomsen-Schmidt, Time-resolved TEM of laser-induced structural changes in GeTe films	46 (1990) 392
i	a TEA CO <sub>2</sub> laser beam and a Ti target in a cell containing helium gas Giardini-Guidoni, A. Morone, M.	46 (1990) 315	V. Dupuis, M.F. Ravet, C. Tête and M. Piecuch, Thermal evolution of W/Si and W/C multilayers under pulsed	(2220) 222
;	Snels, E. Desimoni, A.M. Salvi, R. Fantoni, W.C.M. Berden and M. Giorgi, Luminescence and ESCA		laser heating and classical annealing R. Serna, C.N. Afonso, F. Catalina, N. Teixeira, M.F. da Silva and J.C.	46 (1990) 398
w.	analysis of laser-ablated materials  Kesting, T. Bahners and E. Scholmeyer, Controlled structuring of	46 (1990) 321	Soares, Diffusion and microstructures induced by excimer laser irradiation in Ge-Sb thin film bilayers	46 (1990) 405
I	polymer surfaces by UV-laser irradia- tion Breuer, S. Metev, G. Sepold, OD.	46 (1990) 326	I. Zouari, M. Calvo, F. Lapicque and M. Cabrera, Morphological improvement of zinc electrodeposits by laser assis-	40 (1990) 403
	Hennemann, H. Kollek and G. Krüger,		tance	46 (1990) 411
	Laser-induced photochemical ad-		K. Kolev, M. Wautelet and L.D. Laude,	40 (1770) 411
	nerence enhancement	46 (1990) 336	CW laser-induced transformation of	
_	Hiraoka and S. Lazare, Applications	(2770) 220	thin Sb, Se and Sb <sub>2</sub> Se <sub>3</sub> films in air	46 (1990) 418
	of doping and dedoping of Teflon AF		C. Buerhop, B. Blumenthal, R. Weiss-	10 (1770) 110
	ilms in microfabrication using KrF		mann, N. Lutz and S. Biermann, Glass	
	and ArF excimer lasers	46 (1990) 342	surface treatment with excimer and	
	Stock, D. Bollmann, R. Buchner, G.		CO <sub>2</sub> lasers	46 (1990) 430
	Neumayer and K. Haberger, Ultra-flat		H. Roulet, G. Dufour, A. Cheenne, F.	
F	o-n junctions formed by solid source		Rochet and C. Cartier, Physicoche-	
1	aser doping	46 (1990) 348	mistry of laser-deposited BiSrCaCuO	
E.J.	Petit and R. Caudano, Chemical re-		thin films studied by XPS and XAS	47 (1991) 173
a	ctions at solid-solid interfaces in-		E.B.D. Bourdon and R.H. Prince, Growth	
d	luced by pulsed laser annealing	46 (1990) 357	mechanisms of diamond-like films	
E. I	D'Anna, G. Leggieri, A. Luches, M.		formed by laser ablation of graphite	48/49 (1991) 50
N	Martino, A.V. Drigo, G. Majni, P.		V.A. Ukraintsev, A.A. Chernov, A.N.	
N	Mengucci and I.N. Mihailescu, Nitri-		Mezhuyev and B.S. Podolsky, Effec-	
	lation of titanium by multipulse ex-		tive temperature of products in laser	
	imer laser irradiation	46 (1990) 365	evaporation and desorption	48/49 (1991) 198
	Iartiti, A. Slaoui, J.C. Muller and P.		E.C. Benck, Z. Rong, S.H. Chen and H.A.	
	iffert, Annealing kinetics during		Schuessler, Cavity-enhanced detection	
	apid thermal processing of excimer		of surface ablation	48/49 (1991) 257
	aser-induced defects in virgin silicon	46 (1990) 371		
	adin, I.V. Filiouguine, M. Wautelet		Lead	
	nd L.D. Laude, Influence of the sub-			
	trate on the temperature induced by	46 (1000) 275	C. I. I. W. H.: II. D.	
_	ulsed laser irradiation of thin films	46 (1990) 375	G. Le Lay, K. Hricovini and J.E. Bonnet,	
	Elliq, E. Fogarassy, J.P. Stoquert, C.		Synchrotron radiation investigation and surface spectroscopy studies of	
	Fuchs, S. de Unamuno, B. Prévot and I. Pattyn, Pulsed excimer and		prototypical systems: lead-semicon-	
	Id:YAG laser crystallization of a-		ductor interfaces	41/42 (1989) 25
	i:H. The specific role of hydrogen	46 (1990) 378	S. Priggemeyer, A. Brockmeyer, H.	11/ 12 (1707) 23
	olis, C.N. Afonso and F. Catalina,	10 (1770) 370	Dötsch, H. Koschmieder, D.J. O'Con-	
	The influence of the substrate on the		nor and W. Heiland, The segregation	
	ransformations induced in Si by		of Pb on yttrium-iron-garnet (YIG)	

surfaces studied by ion scattering spectrometry (ISS)	44 (1990) 255	B.H. Bairamov, V.A. Voitenko, I.P. Ipatova, V.V. Toporov, G. Irmer, J.	
S. Bharathi, V. Yegnaraman and G. Prabhakara Rao, Alloy formation in the monolayers of underpotentially		Monecke and E. Jahne, Characteriza- tion of III-V compounds by quasi- elastic electronic scattering of light	50 (1991) 300
deposited lead and thallium  W. Li, JS. Lin, M. Karimi, C. Moses and G. Vidali, Structural characterization	47 (1991) 293	M. Mendik, M. Ospelt, H. von Känel and P. Wachter, Determination of elastic properties of Si/Ge superlattices and	, , , , , , , , , , , , , , , , , , , ,
of ultra-thin metal overlayers on Cu(001) by atom beam scattering	48/49 (1991) 160	$Si_{1-x}Ge_x$ films from surface acoustic modes by Brillouin scattering	50 (1991) 303
T. Hibma, H.H. Weitering, D.R. Heslinga and T.M. Klapwijk, Interface struc- ture and Schottky barriers of epitaxial		J.F. Donegan, J.P. Doran, R.P. Stanley, J. Hegarty, R.D. Feldman and R.F. Austin, Resonant Rayleigh scattering	
Pb on Si(111)  Light scattering	48/49 (1991) 209	from excitons in $Cd_xZn_{1-x}Te:ZnTe$ quantum wells: measurement of homogeneous linewidths	50 (1991) 321
N. Esser, M. Hünermann, U. Resch, D.		W. Kütt, G.C. Cho, M. Strahnen and H. Kurz, Electro-optic sampling of surface space-charge fields on III-V	
Spaltmann, J. Geurts, D.R.T. Zahn, W. Richter and R.H. Williams, Bismuth on GaAs(110): characterisation		compounds S.C. Moss, J.F. Knudsen, R.C. Bowman,	50 (1991) 325
of growth mode and Schottky barrier formation at low and room tempera-		Jr., P.M. Adams and D.D. Smith, Pi- cosecond transient photoreflectance measurements of ion-implanted GaAs	50 (1991) 337
Y. Borensztein, T. Lopez-Rios and G. Vuye, Roughness induced at Si(111)	41/42 (1989) 169	B. Sartorius, M. Brandstättner and H. Venghaus, Two-wavelength transmis-	
surfaces by high temperature heating F. Priolo, A. La Ferla, C. Spinella, E.	41/42 (1989) 439	sion: a rapid and precise method for measuring the light absorption in semiconductors	50 (1991) 369
Rimini, S.U. Campisano and G. Ferla, Crystal-amorphous-silicon interface kinetics under ion beam irradiation	41/42 (1989) 619	M. Wagner, N. Winkler and H.D. Geiler, Single-beam thermowave analysis of semiconductors	50 (1991) 373
C.N. Afonso, J. Solis and F. Catalina, Time-resolved optical measurements of laser melting and rapid solidifica-		Lithium	
tion on GeAl films  F. Priolo, C. Spinella, A. La Ferla, E. Rimini and G. Ferla, Ion-assisted re-	43 (1989) 171	C. Julien and M. Balkanski, Thin-film growth and structure for solid-state	
crystallization of amorphous silicon  F. Hanus and M. Wautelet, Time-re- solved temperature measurements dur-	43 (1989) 178	batteries  Luminescence	48/49 (1991) 1
ing laser-induced synthesis of Cu-Te compounds	43 (1989) 271	J. Christen, M. Grundmann and D. Bim-	
E. Fogarassy, C. Fuchs, S. de Unamuno and P. Siffert, Excimer laser induced melting of heavily doped silicon: a		berg, Direct imaging and theoretical modelling of the atomistic morpho- logical and chemical structure of semi-	
contribution to the optimization of the laser doping process	43 (1989) 316	conductor heterointerfaces C. López, J. Sánchez-Dehesa, F. Mese-	41/42 (1989) 329
A. Esser, W. Kütt, M. Strahnen, G. Maidorn and H. Kurz, Femtosecond transient reflectivity measurements as		guer, F. Borondo and K. Ploog, Elec- tronic structure of modulation n- doped multiple quantum well	41/42 (1989) 464
<ul><li>a probe for process-induced defects in silicon</li><li>R. Fornari, N. Tchandjou, P. Gall and</li></ul>	46 (1990) 446	T. Sasaki, T. Matsuoka and A. Katsui, MOVPE-grown GaN on polar planes of 6H-SiC	41/42 (1989) 504
J.M. Lussert, A study of structural properties of bulk double-doped InP		S. Hongo, Y. Kataoka, T. Urano and T. Kanaji, Evaluation by resonant light	
by laser scattering tomography and photoetching	50 (1991) 207	scattering of ZnTe epitaxial layer de- posited on GaAs	41/42 (1989) 522

K. Kanamoto, K. Fujiwara, Y. Tokuda, N. Tsukada, M. Ishii and T. Nakaya- ma, Photoluminescence line shape due		S.C. Jain, A. Atkinson and W.S. Khokle, Relationship between mechanical, electronic and vibrational properties	
to arrayed steps at the interfaces of GaAs/AlGaAs single quantum wells grown on vicinal surfaces by molecu-		of Ge <sub>x</sub> Si <sub>1-x</sub> strained layers  B. Deveaud, Subpicosecond luminescence spectroscopy of heterostructures (Ex-	48/49 (1991) 387
lar beam epitaxy S. Hayashi, T. Sakamoto, S. Fujita and S. Fujita, Strained-layer superlattice buffers for high-quality heteroepilayers of ZnSe on GaAs	41/42 (1989) 526 41/42 (1989) 534	tended Abstract)  J. Schreiber, W. Hergert and S. Hildebrandt, Combined application of SEM-CL and SEM-EBIC for the investigation of compound semiconduc-	50 (1991) 63
H. Okumura, K. Miki, K. Sakamoto, T. Sakamoto, K. Endo and S. Yoshida, Raman scattering and photoluminescence characterization of Ge/Si strained-layer superlattices grown by	41/42 (1909) 334	tors  A. Gustafsson, S. Nilsson and L. Samuelson, Intensity variations in the nearband-edge recombination of GaP epitaxial layers, grown on (111) and (001)	50 (1991) 181
phase-locked epitaxy C. Girault, D. Damiani, C. Champeaux, P. Marchet, C. Germain, J.P. Mercurio, J. Aubreton and A. Catherinot,	41/42 (1989) 548	oriented substrates, as observed by cathodoluminescence imaging  B.L. Chen, M. Eckstein and HU.  Habermeier, Cathodoluminescence in-	50 (1991) 186
Characterization of the KrF laser-in- duced plasma plume created above an YBaCuO superconducting target and preparation of superconducting thin films	46 (1990) 78	vestigations of RIE-induced defects in InP  J.C. Fariñas and M.F. Barba, Inductively coupled plasma-atomic emission spectrometry (ICP-AES): an analyti-	50 (1991) 191
P.E. Dyer, A. Issa and P.H. Key, An investigation of laser ablation and deposition of Y-Ba-Cu-O in an oxygen environment	46 (1990) 89	cal technique for the chemical char- acterization of perovskite ceramic semiconductors  A. Antolini and C. Lamberti, Computing	50 (1991) 202
R. Teghil, A. Giardini-Guidoni, S. Piccirillo, A. Mele and F. Polla-Mattiot, In situ formation of ionic carbide clusters by laser ablation	46 (1990) 220	errors in Fourier transform photo- luminescence  M. Baumgartner and K. Löhnert, Char- acterization of si-GaAs wafer quality	50 (1991) 212
J. Hermann, C. Boulmer-Leborgne and B.  Dubreuil, Spectroscopic study of the plasma created by interaction between	40 (1990) 220	by room-temperature photolumines- cence  Z.M. Wang, J. Windscheif, D.J. As and	50 (1991) 222
<ul> <li>a TEA CO<sub>2</sub> laser beam and a Ti target in a cell containing helium gas</li> <li>A. Giardini-Guidoni, A. Morone, M.</li> </ul>	46 (1990) 315	W. Jantz, Ambient and low tempera- ture photoluminescence topography of GaAs substrates, epitaxial and im-	(1001)
Snels, E. Desimoni, A.M. Salvi, R. Fantoni, W.C.M. Berden and M. Giorgi, Luminescence and ESCA analysis of laser-ablated materials Y.C. Sasaki and K. Hirokawa, New tech-	46 (1990) 321	planted layers  N. Ohnishi, Y. Makita, A. Yamada, H. Asakura and T. Matsumori, Effect of substrate orientation on the defect-in- duced bound exciton emissions in	50 (1991) 228
nique for evaluation of surfaces and interfaces at atmospheric pressure by using refracted X-ray fluorescence (RXF)  D. Haneman and N. McAlpine, Light	47 (1991) 371	<ul> <li>GaAs grown by molecular beam epitaxy</li> <li>H. L'Haridon, P.N. Favennec, R. Coquille, M. Salvi, M. Gauneau, Y. Le Guillou, R. Callec and P. Gall, Spatial</li> </ul>	50 (1991) 233
emission from Si cleaved and gas- covered surfaces  Y. Nakanishi, Y. Fukuda, Y. Hatanaka and G. Shimaoka, The dependence of	48/49 (1991) 111	investigation of an iron-doped indium phosphide ingot B.J. Heijmink Liesert, M. Godlewski, T. Gregorkiewicz and C.A.J. Ammerlaan,	50 (1991) 237
the polycrystalline structure and elec- troluminescent properties of ZnS:Mn deposited on Y <sub>2</sub> O <sub>3</sub> films on thickness	48/49 (1991) 297	Neutron transmutation doping of GaP: optical studies J. Tatarkiewicz, A. Kozanecki, Z. Kaliń-	50 (1991) 245

ski and K. Paprocki, Photolumines-		high-T <sub>c</sub> SQUID for measuring sus-	
cence study of proton-implanted		ceptibility of high- $T_c$ superconductive	
$InP_{1-x}As_x$ :Yb	50 (1991) 249	thin films	48/49 (1991) 430
T. Monteiro and E. Pereira, Complex for-		S.J. Pickart, M.L. Crow, A.C. Nunes, T.R.	
mation in Mn-doped GaP samples	50 (1991) 253	McGuire and A. Gupta, Neutron de-	
A. Zakrzewski and M. Godlewski, Three-		polarization study of a high- $T_c$ epi-	
center Auger effect and the quantum		taxial thin film	48/49 (1991) 436
yield of the luminescence of ZnS-based		H.G. Grimmeiss and M. Kleverman,	
phosphors	50 (1991) 257	Electrical and optical defect spec-	
G.M. Crean, P.A.F. Herbert, I. Little,		troscopy of compound semiconduc-	
W.M. Kelly, J.Y. Marzin, A. Izrael		tors	50 (1991) 52
and B. Jusserand, Investigation of re-		R.A. Stradling, Far-infrared spectroscopy	
active ion etch-induced damage in InP		of impurities in semiconductors	50 (1991) 65
surfaces using a noncontact photo-		B.J. Heijmink Liesert, M. Godlewski, T.	()
thermal radiometric probe	50 (1991) 281	Gregorkiewicz and C.A.J. Ammerlaan,	
V. Amarger, C. Dubon-Chevallier, A.C.	30 (1))1) 201	Neutron transmutation doping of	
Papadopoulo, B. Descouts and Y. Gao,		GaP: optical studies	50 (1991) 245
Correlated use of characterization		B. Meyer, P. Omling and P. Emanuelsson,	30 (1991) 243
techniques to optimize the Mg implan-		Landau oscillations in single quantum	
	50 (1001) 462		
tation annealing for self-aligned HBT's	50 (1991) 462	wells observed by microwave detec-	50 (1001) 420
M.R. Brozel, L. Breivik, D.J. Stirland,		tion	50 (1991) 420
G.M. Williams and A.G. Cullis, Dislo-			
cation density, infrared absorption and		Magnetic structures	
cathodoluminescence mapping of mi-		0	
crostructure associated with disloca-		E.E. Marinara Material transformations	
tion cells in semi-insulating LEC GaAs	50 (1991) 475	E.E. Marinero, Material transformations	
W. Jantz, R. Stibal, J. Windscheif and J.		in semiconductor and magnetic thin	42 (1000) 117
Wagner, Variation of material param-		films	43 (1989) 117
eters along the growth direction of		H. Strecker and G. Persch, Scanning tun-	
liquid encapsulated Czochralski grown		neling microscopy and technical appli-	
GaAs ingots	50 (1991) 480	cations	46 (1990) 441
		S. Hashimoto, XPS and AES studies on	
Massasium		the interface between metal and poly-	
Magnesium		mer layers. The effect of Ar-plasma	
		treatment of the polymer surface pre-	
X.D. Peng and M.A. Barteau, Characteri-		ceding the metal deposition	47 (1991) 323
zation of the crystallographic structure			
of MgO thin films by ISS on the basis		Manganese	
of trajectory-dependent neutralization	44 (1990) 87	Manganese	
V. Amarger, C. Dubon-Chevallier, A.C.	, , ,		
Papadopoulo, B. Descouts and Y. Gao,		A. Seidel and G. Linker, Amorphization	
Correlated use of characterization		mechanisms in Mn <sup>+</sup> -implanted thin Al	
techniques to optimize the Mg implan-		films and single crystals	43 (1989) 97
tation annealing for self-aligned HBT's	50 (1991) 462	S.C. Tjong and H.C. Swart, Auger char-	
tation amouning for son angliou 112 1	00 (1))1) 102	acterization of the surface oxidation	
		of austenitic Fe-26Mn-7Al-0.9C al-	
Magnesium oxide		loy	47 (1991) 311
		Y.C. Sasaki and K. Hirokawa, New tech-	,
X.D. Peng and M.A. Barteau, Characteri-		nique for evaluation of surfaces and	
zation of the crystallographic structure		interfaces at atmospheric pressure by	
of MgO thin films by ISS on the basis		using refracted X-ray fluorescence	
	44 (1990) 87	(RXF)	47 (1991) 371
of trajectory-dependent neutralization	44 (1330) 8/	G.N. Pain, T. Warminski, S. Sulcs, M.S.	47 (1771) 3/1
		Kwietniak, D. Gao, S.R. Glanvill, C.J.	
Magnetic measurements		Rossouw, A.W. Stevenson, S.P. Russo,	
9		R.G. Elliman, L.S. Wielunski, R.S.	
IW Oin I W Than VE Thora 7 M			
J.W. Qiu, L.W. Zhou, X.F. Zhang, Z.M.		Rowe, G.B. Deacon, R.S. Dickson and	
Tang, Y.J. Qian and Z.Y. Hua, A		B.O. West, Characterization of low-	

temperature MOCVD $Cd_{1-x}Mn_xTe$ thin films  Y. Nakanishi, Y. Fukuda, Y. Hatanaka and G. Shimaoka, The dependence of	48/49 (1991) 76	K. Hesch, P. Hess, H. Oetzmann and C. Schmidt, Laser CVD of a-Si:H from SiH <sub>4</sub> and Si <sub>2</sub> H <sub>6</sub> : relations between chemistry, growth rate and film prop-	
the polycrystalline structure and elec- troluminescent properties of ZnS:Mn deposited on Y <sub>2</sub> O <sub>3</sub> films on thickness	48/49 (1991) 297	erties G. Ulmer, B. Hasselberger, HG. Busmann and E.E.B. Campbell, Excimer	46 (1990) 233
T. Nakamura, Y. Takeuchi, H. Mura- matsu, H. Fujiyasu and Y. Nakanishi, ESR studies on luminescent ZnS:Mn		laser ablation of polyimide  N. Eleftheriadis, HP. Ludescher, M. Süssbauer and D. von der Linde, Pico-	46 (1990) 272
films and CdS-ZnS:Mn superlattices deposited on a GaAs(100) substrate by hot-wall epitaxy	48/49 (1991) 478	second time-resolved laser desorption Fu-Ming Pan, Yuh-Lin Lin and Shean- Ren Horng, Decomposition of perflu-	46 (1990) 284
H.G. Grimmeiss and M. Kleverman, Electrical and optical defect spec- troscopy of compound semiconduc-		oropolyethers during XPS measure- ments J.J. Vajo and J.G. McCarty, Thermody-	47 (1991) 9
tors  T. Monteiro and E. Pereira, Complex formation in Mn-doped GaP samples	50 (1991) 52 50 (1991) 253	namics of carbon coadsorbed with sulfur on Ni(100) R.A.D. Mackenzie, J.A. Liddle and	47 (1991) 23
S.J.C.H.M. van Gisbergen, M. Godlewski, T. Gregorkiewicz and C.A.J. Ammerlaan, Interstitial Mn as a new		C.R.M. Grovenor, Ultrahigh resolu- tion characterisation of compound semiconductors using pulsed laser	
donor in GaP and GaAs: an EPR study	50 (1991) 273	atom probe techniques  Melting	50 (1991) 196
14		neumg	
Mass spectroscopy		C.N. Afonso, J. Solis and F. Catalina, Time-resolved optical measurements	
E.E.B. Campbell, G. Ulmer, B. Hassel- berger and I.V. Hertel, Investigation of positive and negative ionic products	43 (1989) 346	of laser melting and rapid solidifica- tion on GeAl films  E. Fogarassy, C. Fuchs, S. de Unamuno and P. Siffert, Excimer laser induced	43 (1989) 171
from laser ablation of polymers  M. Buck and P. Hess, Ablation of benzene from van der Waals films with		melting of heavily doped silicon: a contribution to the optimization of the laser doping process	43 (1989) 316
A. Mele, D. Consalvo, D. Stranges, A. Giardini-Guidoni and R. Teghil, Cluster formation by local expression.	43 (1989) 358	P.G. Carey and T.W. Sigmon, In-situ doping of silicon using the gas immer- sion laser doping (GILD) process	43 (1989) 325
ter ion formation by laser evaporation of solid complex oxides  T.S. Baller and J. Dieleman, Nanosecond	43 (1989) 398	Mercury	
excimer laser-enhanced chemical etch- ing  J. Boulmer, B. Bourguignon, J.P. Budin and D. Debarre, Time of flight study	43 (1989) 409	W. Li, JS. Lin, M. Karimi, C. Moses and G. Vidali, Structural characterization of ultra-thin metal overlayers on	
of low pressure laser etching of silicon by chlorine	43 (1989) 424	Cu(001) by atom beam scattering A.M. Keir, S.J. Barnett, J. Giess, T.D. Walsh and M.G. Astles, A combina-	48/49 (1991) 160
L.V. Interrante, B. Han, J.B. Hudson and C. Whitmarsh, Design and synthesis of CVD precursors to thin film ceramic		tion of high-resolution X-ray dif- fractometry and diffraction imaging	
materials A.J.P. van Maaren, R.L. Krans and W.C. Sinke, HF formation in laser-induced	46 (1990) 5	techniques applied to the study of MOVPE-grown $Cd_xHg_{1-x}Te/CdTe$ on GaAs	50 (1991) 103
CVD of tungsten  R. Teghil, A. Giardini-Guidoni, S. Pic-	46 (1990) 138	Metals	
cirillo, A. Mele and F. Polla-Mattiot, In situ formation of ionic carbide clus- ters by laser ablation	46 (1990) 220	I. Yamada, Growth processes of epitaxial metal films on semiconductor and in-	

sulator substrates by ionized cluster		ST. Li, S. Hasegawa, N. Yamashita and	
G. Auvert, Kinetics and mechanisms of	43 (1989) 23	H. Nakashima, Initial stages of aluminum epitaxy on the Si(111) $\sqrt{3} \times \sqrt{3}$ -Al	
CW laser induced deposition of metals		surface studied by electron-energy-loss	
for microelectronics	43 (1989) 47	spectroscopy	41/42 (1989) 118
H. Dupendant, J.P. Gavigan, D. Givord,		K. Hirose, H. Tsuda and T. Mizutani,	
A. Lienard, J.P. Rebouillat and Y. Souche, Velocity distribution of mi-		Control of the Al/GaAs Schottky	
cron-size particles in thin film laser		barrier height using a rare-earth metal interlayer	41/42 (1989) 174
ablation deposition (LAD) of metals		Y. Gekka, M. Saitoh, K. Ohga, Y. Akaida	, (,
and oxide superconductors	43 (1989) 369	and M. Akimoto, Electrical character-	
R. Pielmeier, D. Bollmann and K. Ha-		istics of metal contacts on the surfaces	
berger, Laser evaporation of metal sandwich layers for improved IC		of a-Si:H films annealed at low tem- perature	41/42 (1989) 184
metallization	46 (1990) 163	R.H. Williams, N. Forsyth, I.M. Dhar-	41/42 (1707) 104
B.L. Halpern, J.J. Schmitt, J.W. Golz, Y.	(2000)	madasa and Z. Sobiesierski, Metal	
Di and D.L. Johnson, Gas jet deposi-		contacts to II-VI semiconductors:	
tion of thin films	48/49 (1991) 19	CdS and CdTe	41/42 (1989) 189
E.C. Benck, Z. Rong, S.H. Chen and H.A. Schuessler, Cavity-enhanced detection		M. Murakami, H.J. Kim, YC. Shih, W.H. Price and C.C. Parks, Effects of inter-	
of surface ablation	48/49 (1991) 257	facial microstructure on ohmic con-	
	, , , , , , , , , , , , , , , , , , , ,	tacts to GaAs	41/42 (1989) 195
Metal – semiconductor interfaces		R. Sporken, P.A. Thiry, P. Xhonneux, R.	
nzerar semiconameror interjaces		Caudano and J.P. Delrue, Spectro-	
W.E. Spicer, R. Cao, K. Miyano, T.		scopic study of metal/semimetal and metal/semiconductor interfaces	41/42 (1989) 201
Kendelewicz, I. Lindau, E. Weber, Z.		H. Sugahara and J. Nagano, Thermal sta-	11/ 12 (1707) 201
Liliental-Weber and N. Newman,		bility of WSiN-GaAs and Au-WSiN	
From synchrotron radiation to $I-V$		interfaces	41/42 (1989) 207
measurements of GaAs Schottky bar-	41 (42 (1000) 1	M. Renda and K. Morita, Epitaxial	
rier formation  D. Paget, HJ. Drouhin and J. Peretti,	41/42 (1989) 1	growth of a mono-crystalline metasta- ble AuIn layer at the Au/InP(001)	
Infrared field assisted photoemission		interface	41/42 (1989) 216
of metal-semiconductor structures	41/42 (1989) 38	P.J. van den Hoek and E.J. Baerends,	
A. Ichimiya, S. Kohmoto, T. Fujii and Y.		Chemical bonding at metal-semicon-	41 (42 (1000) 22(
Horio, RHEED intensity analysis of $Si(111)\sqrt{3} \times \sqrt{3}$ -Ag structure	41/42 (1989) 82	ductor interfaces  I. Yamada, Interfacial structure of ICB	41/42 (1989) 236
F. Salvan, F. Thibaudau and Ph. Dumas,	41/42 (1989) 82	epitaxially deposited Al(110) bicrystal	
STM studies of metal-semiconductor		films on Si(100) substrates	41/42 (1989) 253
interface formation	41/42 (1989) 88	K. Takayanagi, Y. Tanishiro, T. Ishitsuka	
M. Iwami, M. Kusaka, M. Hirai, M.		and K. Akiyama, In-situ UHV elec-	
Kubota, H. Tochihara and Y. Murata, Mechanism of alloy formation due to		tron microscope study of metal-sili- con surfaces	41/42 (1989) 337
noble metal deposition on silicon		B.A. Orlowski, J.P. Lacharme, C.A. Sébe-	11) 12 (1707) 007
surfaces at room temperature: chem-		nne and S. Bensalah, Interface forma-	
ical bonding model	41/42 (1989) 97	tion on n- and p-CdTe(110) surfaces	44 44 44 44 44 44 44 44 44 44 44 44 44
T. Urano, M. Kaburagi, S. Hongo and T.		with Cu and Au	41/42 (1989) 491
Kanaji, LEED $I-V$ curve analysis for the structure of iron films on Si(111)		K. Nishimori, H. Tokutaka, H. Sumi and N. Ishihara, Interface reaction of Si	
surfaces	41/42 (1989) 103	thin film on Au substrate	47 (1991) 365
K. Sumitomo, K. Tanaka, Y. Izawa, I.	,	D. Heskett, D. Tang, A.B. McLean, R.	•
Katayama, F. Shoji, K. Oura and T.		Ludeke, M. Prietsch, T. Maeda Wong,	
Hanawa, Structural study of Ag over-		E.W. Plummer and N.J. DiNardo,	
layers deposited on a Si(111) substrate by impact-collision ion-scattering-		Metal-induced states on the GaAs- (110) surface probed by angle-resolved	
spectroscopy with time-of-flight detec-		photoemission spectroscopy	48/49 (1991) 260
tion	41/42 (1989) 112	D. Mao, A. Kahn, M. Marsi and G.	

Margaritondo, Synchrotron radiation		D.R.T. Zahn, W. Richter, T. Eickhoff, J.	
induced surface photovoltage at		Geurts, T.D. Golding, J.H. Dinan, K.J.	
metal/GaAs interfaces	48/49 (1991) 324	Mackey and R.H. Williams, The in-	
L. Roberts and G.J. Hughes, An investi-		fluence of Cd overpressure in the	
gation of metal/GaAs(100) interfaces		molecular beam epitaxy of InSb/CdTe	
by deep level transient spectroscopy	50 (1991) 424	heterostructures: a combined Raman	
		and infrared spectroscopy study	41/42 (1989) 497
MIS (metal-insulator-semicondu	ector) structure	T. Nomura, K. Wakatuki, M. Miyao and	
see also MOS (metal – oxide – semic		M. Hagino, Characterization of the	
· ·	conductor) struc-	GaAs buffer layer grown on GaP by	
ture		MBE for the two-step growth method	41/42 (1989) 512
		S. Hongo, Y. Kataoka, T. Urano and T.	
A.S. Barrière, G. Couturier, H. Guegan,		Kanaji, Evaluation by resonant light	
T. Séguelong, A. Thabti, P. Alnot and		scattering of ZnTe epitaxial layer de-	
J. Chazelas, Interface GaAs - gallium		posited on GaAs	41/42 (1989) 522
fluoride thin film grown by fluorin-		T. Takeuchi, C. Maezawa, T. Nomura, K.	
ation. Electrical behaviour of the ob-		Ishikawa, M. Miyao and M. Hagino,	
tained MIS fluorinated GaAs struc-		Raman study of strain distribution in	
tures	41/42 (1989) 383	interface region of GaAs/GaP hetero-	
Y. Yasuda, S. Zaima and M. Sakashita,		epitaxial layers grown by MBE	41/42 (1989) 530
Studies on charge trapping and inter-		K. Maehashi, S. Hasegawa and H.	
face state generation in MOS capaci-		Nakashima, Atomic rearrangement	
tors at low temperatures	41/42 (1989) 420	during the initial stages of GaAs	
S. Zaima, T. Maruyama and Y. Yasuda,		growth on $Si(111)(\sqrt{3} \times \sqrt{3})$ -Ga	
Piezoresistance in n-channel inversion		surface	41/42 (1989) 567
layers of Si MOSFET's	41/42 (1989) 433	K. Iizuka, T. Yoshida, M. Hasobe, I.	
S. Fujieda, K. Akimoto, I. Hirosawa, Y.		Matsuda and T. Suzuki, Raman study	
Mochizuki, J. Mizuki, Y. Matsumoto		of the stress in MBE-grown Al <sub>x</sub>	
and J. Matsui, Electrical properties		$Ga_{1-x}As$ on Si	41/42 (1989) 587
and structures of the MOCVD-		Y. Yamada Maruo, M. Oshima, T. Waho,	
AlN/GaAs interface	41/42 (1989) 516	T. Kawamura, S. Maeyama and T.	
H. Miyatake, Y. Yamaguchi, Y. Mashiko,		Miyahara, Photoemission studies of	
T. Nishimura and H. Koyama, Micro-		bonding properties at the MBE-grown	
structure of high temperature an-		CaF <sub>2</sub> /GaAs interface	41/42 (1989) 647
nealed SIMOX wafer	41/42 (1989) 643	T. Ito, T. Yasumatsu and A. Hiraki, Ho-	
		moepitaxial growth of silicon on	
Molecular beam epitaxy		anodized porous silicon	44 (1990) 97
Molecular beam epitaxy		A.E.M.J. Fischer, W.F.J. Slijkerman, J.F.	
		van der Veen and I. Ohdomari, Ther-	
E. Vlieg and J.F. van der Veen, X-ray		mal stability of supersaturated oxy-	
scattering studies of semiconductor in-		gen-doped silicon epitaxial films	44 (1990) 115
terfaces: atomic structure and mor-		D.C. Bradley, New metallo-organic pre-	
phology	41/42 (1989) 62	cursors for surface processing	46 (1990) 1
A. Koma, K. Saiki and Y. Sato, Heteroep-		E.J. Puik, M.J. van der Wiel, H. Zeijle-	
itaxy of a two-dimensional material		maker and J. Verhoeven, Ion bom-	
on a three-dimensional material	41/42 (1989) 451	bardment of X-ray multilayer coat-	
M. Yano, M. Ashida, Y. Iwai and M.		ings: comparison of ion etching and	
Inoue, Characteristic properties of		ion assisted deposition	47 (1991) 251
III-V <sub>A</sub> /III-V <sub>B</sub> heterointerfaces grown		N. Ohshima, Y. Koide, S. Zaima and Y.	
by molecular beam epitaxy	41/42 (1989) 457	Yasuda, Formation of a superstruc-	
S. Tatarenko, J. Cibert, Y. Gobil, G.		ture in the initial stage of Ge epitaxial	10 110 11001
Feuillet, K. Saminadayar, A.C. Chami		growth on Si(100) substrates	48/49 (1991) 69
and E. Ligeon, RHEED, XPS,		W. Li, JS. Lin, M. Karimi, C. Moses and	
HRTEM and channeling studies of		G. Vidali, Structural characterization	
molecular beam epitaxy growth of	41 /40 /4000	of ultra-thin metal overlayers on	40 /40 /4001 4 55
CdTe on (001) GaAs	41/42 (1989) 470	Cu(001) by atom beam scattering	48/49 (1991) 160

M. Arienzo, S.S. Iyer, B.S. Meyerson, G.L. Patton and J.M.C. Stork, Si-Ge al-		by ion scattering and X-ray diffrac-	50 (1991) 450
loys: growth, properties and applica- tions	48/49 (1991) 377	Molybdenum	
<ul> <li>Y. Sasajima, Y. Suzuki, M. Takeuchi and S. Ozawa, New approach for a computer simulation of the vacuum deposition process</li> <li>C.T. Foxon, Control of MBE, MOMBE and CBE growth using RHEED</li> <li>C. Grattepain and A.M. Huber, Secondary ion mass spectrometry of</li> </ul>	48/49 (1991) 498 50 (1991) 28	S.C. Tjong and J.B. Malherbe, Auger studies of the effect of Mo, V and Pd additions on the oxidation characteristics of Fe-24Cr alloy  K.E. Smith, G.S. Elliott and S.D. Kevan, The role of non-adiabaticity and two-	44 (1990) 179
dopants and impurities in compound semiconductors: depth profiling of homo- and heterostructure	50 (1991) 42	dimensional Fermi surfaces in the re- construction of Mo(001) and W(001) F. Shoji, A. Ogawa and K. Oura, Sputter-deposition by a new Penning-	48/49 (1991) 135
R. Zaus, M. Schuster, H. Göbel and JP. Reithmaier, Characterization of (In, Ga)As/GaAs strained-layer multiple quantum wells with high-resolution		discharge source with an axially in- tegrated hot-cathode W.M.R. Divigalpitiya, R.F. Frindt and S.R. Morrison, Spread films of single	48/49 (1991) 373
X-ray diffraction and computer simu- lations	50 (1991) 92	molecular transition-metal sulphides	48/49 (1991) 572
P. Auvray, A. Poudoulec, M. Baudet, B. Guenais, A. Regreny, C. d'Anterroches and J. Massies, Interface		Molybdenum oxide	
roughness of GaAs/AlAs super- lattices MBE-grown on vicinal surfaces N. Ohnishi, Y. Makita, A. Yamada, H. Asakura and T. Matsumori, Effect of	50 (1991) 109	A. Vázquez, J.M. Domínguez and S. Fuentes, Thermally induced modifications on the crystal surface of molybdate-type catalysts	44 (1990) 331
substrate orientation on the defect-in- duced bound exciton emissions in GaAs grown by molecular beam epi-		MOS (metal – oxide – semiconductor	
B. Jusserand and F. Mollot, Confined optical vibrations: a new probe for	50 (1991) 233	S. Kar, A. Raychaudhuri, A.K. Sinha and S. Ashok, Ion beam modification of the dielectric properties of thin silicon	
alloy disorder C. Ghezzi, R. Mosca, A. Bosacchi, S. Franchi and E. Gombia, The influence	50 (1991) 317	dioxide films G. Abstreiter, Micro-Raman spectroscopy for characterization of semiconductor	48/49 (1991) 264
of the DX center on the capacitance of Schottky barriers in n-type AlGaAs C. Raisin, A. Rocher, G. Landa, R. Carles and L. Lassabatere, GaSb/GaAs het- eroepitaxy characterized as a stress-	50 (1991) 400	devices J. Tardy, I. Thomas, P. Viktorovitch, M. Gendry, J.L. Perrossier, C. Santinelli, M.P. Besland, P. Louis and G. Post, Long-term stability of InP MIS de-	50 (1991) 73
free system	50 (1991) 434	vices	50 (1991) 383
D. Ashenford, J.H.C. Hogg, B. Lunn and C.G. Scott, The relationship between electrical and structural characteristics		Neutron scattering	
of CdTe and CdMnTe layers grown on InSb  D.A. Woolf, D.I. Westwood, M.A. Anderson and R.H. Williams, The molecular beam epitaxial growth of GaAs(111)/Si(111): a variable growth temperature	50 (1991) 440	S.J. Pickart, M.L. Crow, A.C. Nunes, T.R. McGuire and A. Gupta, Neutron depolarization study of a high- $T_{\rm c}$ epitaxial thin film	48/49 (1991) 436
study  B. Holländer, S. Mantl, B. Stritzker, F.	50 (1991) 445	Nickel	
Schäffler, HJ. Herzog and E. Kasper, Strain and defect densities in Si/ Si <sub>1-x</sub> Ge <sub>x</sub> heterostructures investigated		E. Gaffet, J.M. Pelletier and S. Bonnet- Jobez, Laser surface alloying of Ni film on Al-based alloy	43 (1989) 248

V.V. Tokarev, A.V. Kibardin, T.M. Pyat- kova and D.I. Zarovsky, Nickel, cobalt and iron silicide formation stimulated		and structural characterization of Co and Ni silicide contacts to silicon D.E. Ramaker, Evidence for vertical C <sub>2</sub>	48/49 (1991) 307
by argon implantation V.V. Tokarev, A.I. Demchenko, A.I. Ivanov and V.E. Borisenko, Influence of boron implantation on phase trans- formations in nickel silicides	44 (1990) 235 44 (1990) 241	on Ni as a precursor for graphite nucleation  N. Hizem, G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double and single acceptor state of isolated	48/49 (1991) 351
E.M. Perry, D.L. Cocke and M.K. Miller, The oxidation of Ni <sub>3</sub> Zr investigated by atom-probe field-ion microscopy	44 (1000) 221	Ni <sub>Ga</sub> in GaAs	50 (1991) 490
and X-ray photoelectron spectroscopy E. Nowicka, Z. Wolfram and R. Duś, Deuterium adsorption on thin nickel	44 (1990) 321	Niobium  A Chavariar N Chavariar M El	
films G. Ranga Rao and C.N.R. Rao, Adsorption of nitrogen on clean and modified	45 (1990) 13	A. Chevarier, N. Chevarier, M. El Bouanani, E. Gerlic, M. Stern, B. Roux and F. Thimon, Profiling of carbon,	
single-crystal Ni surfaces S. Deckers, F.H.P.M. Habraken, W.F. van der Weg, A.W. Denier van der Gon,	45 (1990) 65	oxygen and argon contamination in sputter-deposited films using nuclear backscattering and nuclear reaction	
J.F. van der Veen and J.W. Geus, Oxidation-induced segregation at the		spectroscopy	48/49 (1991) 215
Pt <sub>0.5</sub> Ni <sub>0.5</sub> (111) surface studied by medium-energy ion scattering	45 (1990) 121	Nitric oxide	
R.M. Wallace, C.C. Cheng, P.A. Taylor, W.J. Choyke and J.T. Yates, Jr., Ni impurity effects on hydrogen surface	45 (1990) 201	A.R. Balkenende, H. den Daas, M. Huisman, O.L.J. Gijzeman and J.W. Geus, The interaction of NO, O <sub>2</sub> and CO	
chemistry and etching of Si(111)  S. Deckers, F.H.P.M. Habraken, W.F. van der Weg and J.W. Geus, Oxidation of		with Cu(100) and Cu(110) H.H. Madden and R. Imbihl, Interaction of NO and H <sub>2</sub> with Pt(100)	47 (1991) 341 48/49 (1991) 130
clean and Pt-covered Ni(111)  J.C. Ingram, K.W. Nebesny and J.E.  Pemberton, Optical properties of	45 (1990) 207	Nitrides	
selected first-row transition metals de- termined by reflection electron energy loss spectroscopy	45 (1990) 247	H. Sugahara and J. Nagano, Thermal sta- bility of WSiN-GaAs and Au-WSiN	41 (42 (1000) 207
J.J. Vajo and J.G. McCarty, Thermody- namics of carbon coadsorbed with sulfur on Ni(100)	47 (1991) 23	interfaces  N. Fujimura and T. Ito, TiSi <sub>2</sub> formation at the Ti-rich TiN <sub>x</sub> /Si interface	41/42 (1989) 207 41/42 (1989) 272
E.J. Puik, M.J. van der Wiel, H. Zeijle- maker and J. Verhoeven, Ion bom- bardment of X-ray multilayer coat-	47 (1991) 23	K. Suguro, Y. Nakasaki, T. Yoshii and T. Itoh, Barrier metal between tungsten and silicon for high temperature	41/42 (1969) 272
ings: comparison of ion etching and ion assisted deposition  T. Zhang and S.Y. Wei, Hydrogen chem-	47 (1991) 251	processing  K. Kamimura, Y. Takase, Y. Onuma and A. Kunioka, Surface nitridation of InP	41/42 (1989) 277
isorption on contaminated composite catalysts	48/49 (1991) 139	with a N <sub>2</sub> plasma T. Sasaki, T. Matsuoka and A. Katsui,	41/42 (1989) 443
G. Shimaoka, MEED studies of thin metal film covered semiconductor surfaces D.G. Ren, Study of interface structure of	48/49 (1991) 190	MOVPE-grown GaN on polar planes of 6H-SiC S. Fujieda, K. Akimoto, I. Hirosawa, Y.	41/42 (1989) 504
the oxide grown on nickel alloys by AP-FIM  B.V. King, D.J. O'Connor, Y. Shen, R.J.  MacDonald, M. Katayama and M.	48/49 (1991) 227	Mochizuki, J. Mizuki, Y. Matsumoto and J. Matsui, Electrical properties and structures of the MOCVD- AlN/GaAs interface	41 /42 (1080) 514
MacDonald, M. Katayama and M. Aono, LEIS for structure determination of surfaces and thin films  A.K. Kulkarni and A.J. Canale, Electrical	48/49 (1991) 246	V. Craciun, G. Leggieri, A. Luches, M. Martino, I.N. Mihailescu and I. Ursu, Synthesis of metallic and semiconduc-	41/42 (1989) 516

tor nitrides by multipulse laser irradia- tion of solid samples in ambient gases	43 (1989) 304	based epitaxy (Sentaxy). Investigation of initial nucleation stages	41/42 (1989) 638
J.L. Chartier, A. Serrari, R. Le Bihan, M. Ligeon, F. Gaspard and F. Muller,	43 (1707) 304	S. Metev and K. Meteva, Nucleation and growth of laser-plasma deposited thin	
Thermal nitridation of anodic silicon dioxide	45 (1990) 351	films A.D. Gates and J.L. Robins, Nucleation	43 (1989) 402
E. D'Anna, G. Leggieri, A. Luches, M. Martino, A.V. Drigo, G. Majni, P. Mengucci and I.N. Mihailescu, Nitri-	()	of gold on Ca <sup>2+</sup> -doped NaCl D.E. Ramaker, Evidence for vertical C <sub>2</sub> on Ni as a precursor for graphite	48/49 (1991) 154
dation of titanium by multipulse excimer laser irradiation  J.S. Kim, P.K. Banerjee, S.S. Mitra, H. Shastry, J.J. Loferski and R. Beaulieu,	46 (1990) 365	nucleation  JK. Zuo and J.F. Wendelken, Substrate temperature effects on $(\sqrt{3} \times \sqrt{3})$ R30° domain growth of Ag on Si(111)	48/49 (1991) 351
Optical, electrical and mechanical properties of RF-sputtered TiN-W-Au films	48/49 (1991) 548	surface	48/49 (1991) 366
P. Bhardwaj, O.J. Gregory, K. Bragga and M.H. Richman, Sputtered TiN thin	40/49 (1991) 340	Optical properties	
films for improved corrosion resis- tance	48/49 (1991) 555	J.C. Ingram, K.W. Nebesny and J.E. Pemberton, Optical properties of metal surfaces from electron energy loss	
Nitrogen  G. Ranga Rao and C.N.R. Rao, Adsorp-		spectroscopy in the reflection mode  J.C. Ingram, K.W. Nebesny and J.E.  Pemberton, Optical constants of the	44 (1990) 279
tion of nitrogen on clean and modified single-crystal Ni surfaces B.C. Beard, Cellulose nitrate as a binding	45 (1990) 65	noble metals determined by reflection electron energy loss spectroscopy  J.C. Ingram, K.W. Nebesny and J.E.	44 (1990) 293
energy reference in N(1s) XPS studies of nitrogen-containing organic mole- cules	45 (1990) 221	Pemberton, Optical properties of selected first-row transition metals de- termined by reflection electron energy loss spectroscopy	45 (1990) 247
Nitrous oxide		M. Zeman, I. Ferreira, M.J. Geerts and	43 (1990) 247
		J.W. Metselaar, The influence of de- position parameters on the growth of	
M. Takeuchi, Y. Watanabe and S. Ozawa, Gas-sensitive properties of ultrafine In <sub>2</sub> O <sub>3</sub> particle layers prepared by gas evaporation technique	48/49 (1991) 526	a-SiGe: H alloys in a plasma CVD system  C.N. Afonso, R. Serna, F. Catalina and	46 (1990) 245
Noble gases	, (,	D. Bermejo, Good-quality Ge films grown by excimer laser deposition	46 (1990) 249
J. Hermann, C. Boulmer-Leborgne and B.		<ul> <li>J. Davenas, G. Boiteux, J.M. Bureau and</li> <li>D. Broussoux, Ion-beam-assisted formation of interconnections into high</li> </ul>	
Dubreuil, Spectroscopic study of the plasma created by interaction between a TEA CO <sub>2</sub> laser beam and a Ti target		temperature polymers  J. Solis, C.N. Afonso and F. Catalina,	46 (1990) 330
in a cell containing helium gas  S. Hongo, T. Urano and T. Kanaji, Mechanisms of He*(2 <sup>1</sup> S) de-excitation on	46 (1990) 315	The influence of the substrate on the transformations induced in Si by nanosecond laser irradiation: a time-	47 (1000) 202
oxygen-adsorbed Si(100) surfaces S.C. Moss, J.F. Knudsen, R.C. Bowman,	48/49 (1991) 143	resolved study T. Easwarakhanthan, Z. Ouennoughi, M. Renard and J.R. Cussenot, Characteri-	46 (1990) 383
Jr., P.M. Adams and D.D. Smith, Pi- cosecond transient photoreflectance measurements of ion-implanted GaAs	50 (1991) 337	zation of double-layer transparent films on absorbing substrates using multiple-angle ellipsometry E.B.D. Bourdon and R.H. Prince, Growth	47 (1991) 299
Nucleation		mechanisms of diamond-like films formed by laser ablation of graphite	48/49 (1991) 50
H. Kumomi, T. Yonehara, Y. Nishigaki and N. Sato, Selective nucleation		Y. Nakanishi, Y. Suzuki, T. Nakamura, Y. Hatanaka, Y. Fukuda, A. Fujisawa	

tion of silicon-nitride films by plasma-enhanced chemical apan deposition H.A. Schuessler, S.H. Chen, Z.C. Tang and Z. Rong, Cavity-enhanced photo-thermal spectroscopy and detection P.K. Banerjee, J.S. Kim and S.S. Mitra, Electrical and optical properties of aluminum-doped amorphous silicon carbide films E. Gofuku, Y. Toyoda, Y. Uehara, M. Kohara and M. Nunoshita, Highly conductive TiO, thin films prepared by EB-modification M. Takeuchi, M. Masui and Y. Momose, Copper-phthalocyanine thin film photoelectrochemical cells J.S. Kim, P.K. Banerjee, S.S. Mitra, H. Shastry, J.J. Loferski and R. Beaulieu, Optical, electrical and methanical properties of RF-sputtered TiN-W-Au films H.G. Grimmeits and M. Kleverman, Electrical and optical defect spectroscopy of compound semiconductors A. Deneuville, D.B. Tanner, R.M. Park and P.H. Holloway, Semiconductor electrical properties for mit frequency dependence of the dielectric constant: application to n-type ZaSe heteroepitaxial thin films J.F. Dongan, J.P. Doran, R.P. Stanley, J. Hegarry, R.D. Feldman and R.F. Austin, Resonant Rayleigh scattering from excitons in Cd, Zn-, Tie-Zarfe quantum wells: measurement of homogeneous inewidths W. Watta, G.C. Cho, M. Strahnen and H. Kurz, Electro-optic sampling of surface space-charge fields on III-V compounds P.L. Swart, B.M. Lacquet and R. Thavar, Physical characterization of OMVPE-grown Al, Cla, _, As multi-layer films by means of non-destrucitive optical reflectometry-aided surface layer investigation F. Scale, D. Hofmann and G. Müller, Infrared absorption of n- and p-type F-cdoped InP and mapping of surfaces layer investigation F. Scale, D. Hofmann and G. Müller, Infrared absorption of n- and p-type F-cdoped InP and mapping of surfaces and modified coloped InP and mapping of surfaces and modi	and G. Shimaoka, Coloration of Sn-Sb-O thin films I.K. Han, Y.J. Lee, J.W. Jo, J.I. Lee and	48/49 (1991) 55	S. Tüzemen and M.R. Brozel, An investi- gation of photo-quenching properties of LEC GaAs by using optical and	
and Z. Rong, Cavity-enhanced photo- thermal spectroscopy and detection  P.K. Banerjee, J.S. Kim and S.S. Mira, Electrical and optical properties of a- luminum-doped amorphous silicon carbide films  E. Gofuku, Y. Toyoda, Y. Uchara, M. Kohara and M. Nunoshita, Highly conductive TiO <sub>2</sub> thin films prepared by EB-modification  M. Takeuchi, M. Masui and Y. Momose, Copper-phthalocyanine thin film pho- toelectrochemical cells  J.S. Kim, P.K. Banerjee, S.S. Mitra, H. Shastry, J. Loferski and R. Beaulieu, Optical, electrical and mechanical properties of RF-sputtered TiN-W- Au films  H.G. Grimmeiss and M. Kleverman, Electrical and optical defect spec- troscopy of compound semiconductors and single acceptor state of isolated No. G. Guillot and W. Ulrici, Complete identification of the Ti-re- lated levels in GaP  Organic substances  Organic substa	enhanced chemical vapor deposition	48/49 (1991) 104	Gavand, J. Gregoire, G. Guillot and	50 (1991) 395
Electrical and optical properties of a- luminum-doped amorphous silicon carbide films  E. Gofuku, Y. Toyoda, Y. Uehara, M. Kohara and M. Nunoshita, Highly conductive TiO <sub>2</sub> thin films prepared by E.B-modification  M. Takeuchi, M. Masui and Y. Momose, Copper-phthalocyanine thin film pho- toelectrochemical cells  J.S. Kim, P.K. Banerjee, S.S. Mitra, H. Shastry, J.J. Loferski and R. Beaulieu, Optical, electrical and mechanical properties of RF-sputterd TiN-W- Au films  H.G. Grimmeiss and M. Kleverman, Electrical and optical defect spec- troscopy of compound semiconduc- tors  A. Deneuville, D.B. Tanner, R.M. Park and P.H. Holloway, Semiconductor electrical properties from the frequen- cy dependence of the dielectric con- stant: application to n-type ZnSc het- ercepitaxii thin films  J.F. Donegan, J.P. Doran, R.P. Stanley, J. Hegarry, R.D. Feldman and R.F. Austin, Resonant Rayleigh scattering from excitons in Cd, Zn <sub>1-x</sub> :E-ZnTe quantum wells: measurement of ho- mogeneous linewidths  W. Kütt, G.C. Cho, M. Strahnen and H. Kurz, Electro-optic sampling of sur- face space-charge fields on III-V compounds  P.L. Swart, B.M. Lacquet and R. Thavar, Physical characterization of OMVPE- grown AJ, Ga <sub>1-x</sub> , As multi-layer films by means of non-destructive optical reflectometry  K. Watti, G.C. Cho, M. Strahnen and H. Kurz, Electro-optic sampling of sur- face space-charge fields on III-V compounds  P.L. Swart, B.M. Lacquet and R. Thavar, Physical characterization of OMVPE- grown AJ, Ga <sub>1-x</sub> , As multi-layer films by means of non-destructive optical reflectometry  K. Dezierski, Z. Guminenny and J. Mis- iewicz, Reflectometry-aided surface layer investigation  F. Mosel, A. Seidl, D. Hofmann and G. Müller, Infrared absorption of n- and p-type Fe-doped Inl <sup>2</sup> and mapping of  M. Sasaki, Y. Kawakyu, H. Ishikawa and M. Mashita, UV absorption spectra of adlayers of MOCVD source gases  Y. Kanemitsu and S. Imamura, Charge transport and trapping at the interface in two-layer oganic photoconductors  A. Klumpa and H. Sigmund, Photoin- duced trans	and Z. Rong, Cavity-enhanced photo- thermal spectroscopy and detection	48/49 (1991) 254	and single acceptor state of isolated Ni <sub>Ga</sub> in GaAs	50 (1991) 490
E. Gofuku, Y. Toyoda, Y. Uchara, M. Kohara and M. Nunoshita, Highly conductive TiO <sub>2</sub> thin films prepared by EB-modification M. Takeuchi, M. Masui and Y. Momose, Copper-phthalocyanine thin film photoelectrochemical cells J.S. Kim, P.K. Banerjee, S.S. Mitra, H. Shastry, J.J. Loferski and R. Beaulieu, Optical, electrical and mechanical properties of RF-sputtered Tin-W-Au films H.G. Grimmeiss and M. Kleverman, Electrical and optical defect spectroscopy of compound semiconductors A. Deneuville, D.B. Tanner, R.M. Park and P.H. Holloway, Semiconductor electrical properties from the frequency dependence of the dielectric constant: application to n-type ZnSe heteroepitaxial thin films J.F. Donegan, J.P. Doran, R.P. Stanley, J. Hegarty, R.D. Feldman and R.F. Austin, Resonant Rayleigh scattering from excitons in Cd. Zn_, Te:ZnTequantum wells: measurement of homogeneous linewidths W. Kütt, C.C. Cho, M. Strahmen and H. Kurz, Electro-optic sampling of surface space-charge fields on III-V compounds P.L. Swart, B.M. Lacquet and R. Thavar, Physical characterization of OMYPEgrown Al, Ga <sub>1-x</sub> , As multi-layer films by means of non-destructive optical reflectometry K. Deizerki, Z. Gumienny and J. Misiewicz, Reflectometry-aided surface layer investigation F. Mosel, A. Seidl, D. Hofmann and G. Müller, Infrared absorption of n- and p-type F-edoped In Pan dmapping of	Electrical and optical properties of a- luminum-doped amorphous silicon		Benyattou, G. Guillot and W. Ulrici, Complete identification of the Ti-re-	
conductive TiO, thin films prepared by EB-modification M. Takeuchi, M. Masui and Y. Momose, Copper-phthalocyanine thin film photoelectrochemical cells J.S. Kim, P.K. Banerjee, S.S. Mitra, H. Shastry, J.J. Loferski and R. Beaulieu, Optical, electrical and mechanical properties of RF-sputtered Tin-W-An films H.G. Grimmeiss and M. Kleverman, Electrical and optical defect spectroscopy of compound semiconductors A. Deneuville, D.B. Tanner, R.M. Park and P.H. Holloway, Semiconductor electrical properties from the frequency dependence of the dielectric constant: application to n-type ZnSe heterocopitasial thin films  J.F. Donegan, J.P. Doran, R.P. Stanley, J. Hegarty, R.D. Feldman and R.F. Austin, Resonant Rayleigh scattering from excitons in Cd_ZnTezznTequantum wells: measurement of homogeneous linewidths  W. Kütt, G.C. Cho, M. Strahnen and H. Kurz, Electro-optic sampling of surface space-charge fields on III-V compounds  S. O (1991) 325  P.L. Swart, B.M. Lacquet and R. Thavar, Physical characterization of OMVPEgrown Al, Gal, As multi-layer films by means of non-destructive optical reflectometry.  K. Lezierski, Z. Gumienny and J. Misiewicz, Reflectometry-aided surface layer investigation  F. Mosel, A. Seidl, D. Hofmann and G. Müller, Infrared absorption of n- and p-type Fe-doped InP and mapping of	E. Gofuku, Y. Toyoda, Y. Uehara, M.	48/49 (1991) 288	lated levels in GaP	50 (1991) 496
Copper-phthalocyanine thin film photoelectrochemical cells  J.S. Kim, P.K. Banerjee, S.S. Mitra, H. Shastry, J.J. Loferski and R. Beaulieu, Optical, electrical and mechanical properties of RF-sputtered TiN-W-Au films  H.G. Grimmeiss and M. Kleverman, Electrical and optical defect spectroscopy of compound semiconductor clectrical properties from the frequency dependence of the dielectric constant: application to n-type ZnSe heteroepitaxial thin films  J.F. Donegan, J.P. Doran, R.P. Stanley, J. Hegarty, R.D. Feldman and R.F. Austin, Resonant Rayleigh scattering from excitons in Cd <sub>x</sub> Zn <sub>1-x</sub> Te:ZnTe quantum wells: measurement of homogeneous linewidths  W. Kütt, G.C. Cho, M. Strahnen and H. Kurz, Electro-optic sampling of surface space-charge fields on III-V compounds  P.L. Swart, B.M. Lacquet and R. Thavar, Physical characterization of OMVPE-grown Al <sub>x</sub> Ca <sub>1-x</sub> As multi-layer films by means of non-destructive optical reflectometry  K. Jezierski, Z. Gumienny and J. Misiewicz, Reflectometry-aided surface layer investigation  F. Mosel, A. Seidl, D. Hofmann and G. Müller, Infrared absorption of n- and p-type Fe-doped InP and mapping of	conductive TiO2 thin films prepared	48/49 (1991) 343	Organic substances	
J.S. Kim, P.K. Banerjee, S.S. Mitra, H. Shastry, J.J. Loferski and R. Beaulieu, Optical, electrical and mechanical properties of RF-sputtered TiN-W-Au films  48/49 (1991) 548  48/49 (1991) 549  48/49 (1991) 548  48/49 (1991) 54	Copper-phthalocyanine thin film pho-	40 (40 (1001) 517	M. Mashita, UV absorption spectra of	41 (42 (1000) 242
Optical, electrical and mechanical properties of RF-sputtered TiN-W-Au films  H.G. Grimmeiss and M. Kleverman, Electrical and optical defect spectroscopy of compound semiconductors  50 (1991) 52  A. Deneuville, D.B. Tanner, R.M. Park and P.H. Holloway, Semiconductor electrical properties from the frequency of the dielectric constant: application to n-type ZnSe heteropitaxial thin films  J.F. Donegan, J.P. Doran, R.P. Stanley, J. Hegarty, R.D. Feldman and R.F. Austin, Resonant Rayleigh scattering from excitons in Cd_zZn_1_rE-zZnTe quantum wells: measurement of homogeneous linewidths  W. Kütt, G.C. Cho, M. Strahnen and H. Kurz, Electro-optic sampling of surface space-charge fields on III-V compounds  P.L. Swart, B.M. Lacquet and R. Thavar, Physical characterization of OMVPE-grown Al_zGa_1_x As multi-layer films by means of non-destructive optical reflectometry  K. Jezierski, Z. Gumienny and J. Misiewicz, Reflectometry-aided surface layer investigation  F. Mosel, A. Seidl, D. Hofmann and G. Müller, Infrared absorption of nand p-type Fe-doped InP and mapping of	J.S. Kim, P.K. Banerjee, S.S. Mitra, H.	48/49 (1991) 517	Y. Kanemitsu and S. Imamura, Charge	41/42 (1989) 342
H.G. Grimmeiss and M. Kleverman, Electrical and optical defect spectroscopy of compound semiconductors  A. Deneuville, D.B. Tanner, R.M. Park and P.H. Holloway, Semiconductor electrical properties from the frequency dependence of the dielectric constant: application to n-type ZnSe heteroepitaxial thin films  J.F. Donegan, J.P. Doran, R.P. Stanley, J. Hegarty, R.D. Feldman and R.F. Austin, Resonant Rayleigh scattering from excitons in Cd, Zn <sub>1-x</sub> Te:ZnTe quantum wells: measurement of homogeneous linewidths  W. Kütt, G.C. Cho, M. Strahnen and H. Kurz, Electro-optic sampling of surface space-charge fields on III-V compounds  P.L. Swart, B.M. Lacquet and R. Thavar, Physical characterization of OMVPE-grown Al, Ga <sub>1-x</sub> As multi-layer films by means of non-destructive optical reflectometry  K. Jezierski, Z. Gumienny and J. Misiewicz, Reflectometry-aided surface layer investigation  F. Mosel, A. Seidl, D. Hofmann and G. Müller, Infrared absorption of n- and p-type Fe-doped InP and mapping of	Optical, electrical and mechanical properties of RF-sputtered TiN-W-	40 (40 (1001) 540	in two-layer organic photoconductors P. Hoffmann, B. Lecohier, S. Goldoni	41/42 (1989) 544
troscopy of compound semiconductors  A. Deneuville, D.B. Tanner, R.M. Park and P.H. Holloway, Semiconductor electrical properties from the frequency dependence of the dielectric constant: application to n-type ZnSe heteroepitaxial thin films  J.F. Donegan, J.P. Doran, R.P. Stanley, J. Hegarty, R.D. Feldman and R.F. Austin, Resonant Rayleigh scattering from excitons in Cd <sub>x</sub> Zn <sub>1-x</sub> Te:ZnTe quantum wells: measurement of homogeneous linewidths  W. Kütt, G.C. Cho, M. Strahnen and H. Kurz, Electro-optic sampling of surface space-charge fields on III-V compounds  P.L. Swart, B.M. Lacquet and R. Thavar, Physical characterization of OMVPE-grown Al <sub>x</sub> Ga <sub>1-x</sub> As multi-layer films by means of non-destructive optical reflectometry  K. Jezierski, Z. Gumienny and J. Misiewicz, Reflectometry-aided surface layer investigation  F. Mosel, A. Seidl, D. Hofmann and G. Müller, Infrared absorption of n- and p-type Fe-doped InP and mapping of  50 (1991) 52  A. Klumpp and H. Sigmund, Photoin-duced transformation of polysiloxane layer is to SiO <sub>2</sub> T. Wadayama, W. Shiraishi, A. Hatta and W. Suètaka, A double-modulation method of observing infrared emission spectra of thin films on metal surfaces  S. Sapicha, E. Sacher and M.R. Wertheimer, X-ray photoelectron study of the plasma fluorination of lignocellulose  So (1991) 321  J.A. Kelber, J.W. Rogers, Jr., B.A. Banse and B.E. Koel, Interaction of dimethylamine with clean and partially oxidized copper surfaces a combined EELS—UPS study  S. Yoshida, H. Ishida and J.S. Jen, X-ray photoelectron spectroscopic and X-ray diffractometric characterization of alkylimidazole films on copper oxide and alkylimidazolato copper(II) complexes  W. Wülter, Infrared emission spectra of thin films on metal surfaces (44 (1990) 43  J.F. Doregan, J.P. Doran, R.P. Stanley, J.  Westaka, A double-modulation method of observing infrared emission spectra of thin films on metal surfaces (50 (1991) 321  S. Sapicha, E. Sacher and M.R. Wertheimer, X-ray photoelectron study of the plasma fluorination of lignocellulose (an	H.G. Grimmeiss and M. Kleverman,	48/49 (1991) 548	ing of copper and iridium lines from	
and P.H. Holloway, Semiconductor electrical properties from the frequency dependence of the dielectric constant: application to n-type ZnSe heteroepitaxial thin films  J.F. Donegan, J.P. Doran, R.P. Stanley, J. Hegarty, R.D. Feldman and R.F. Austin, Resonant Rayleigh scattering from excitons in Cd <sub>x</sub> Zn <sub>1-x</sub> Te:ZnTe quantum wells: measurement of homogeneous linewidths  W. Kütt, G.C. Cho, M. Strahnen and H. Kurz, Electro-optic sampling of surface space-charge fields on III-V compounds  P.L. Swart, B.M. Lacquet and R. Thavar, Physical characterization of OMVPE-grown Al <sub>x</sub> Ga <sub>1-x</sub> As multi-layer films by means of non-destructive optical reflectometry.  K. Jezierski, Z. Gumienny and J. Misiewicz, Reflectometry-aided surface layer investigation  F. Mosel, A. Seidl, D. Hofmann and G. Müller, Infrared absorption of rand p-type Fe-doped InP and mapping of	troscopy of compound semiconduc- tors	50 (1991) 52	A. Klumpp and H. Sigmund, Photoin-	43 (1989) 54
stant: application to n-type ZnSe heteroepitaxial thin films  J.F. Donegan, J.P. Doran, R.P. Stanley, J. Hegarty, R.D. Feldman and R.F. Austin, Resonant Rayleigh scattering from excitons in Cd <sub>x</sub> Zn <sub>1-x</sub> Te:ZnTe quantum wells: measurement of homogeneous linewidths  W. Kütt, G.C. Cho, M. Strahnen and H. Kurz, Electro-optic sampling of surface space-charge fields on III-V compounds  P.L. Swart, B.M. Lacquet and R. Thavar, Physical characterization of OMVPE-grown Al <sub>x</sub> Ga <sub>1-x</sub> As multi-layer films by means of non-destructive optical reflectometry  K. Jezierski, Z. Gumienny and J. Misiewicz, Reflectometry-aided surface layer investigation  F. Mosel, A. Seidl, D. Hofmann and G. Müller, Infrared absorption of n- and p-type Fe-doped InP and mapping of	and P.H. Holloway, Semiconductor		layers to SiO <sub>2</sub>	43 (1989) 301
J.F. Donegan, J.P. Doran, R.P. Stanley, J.  Hegarty, R.D. Feldman and R.F. Austin, Resonant Rayleigh scattering from excitons in Cd <sub>x</sub> Zn <sub>1-x</sub> Te:ZnTe quantum wells: measurement of homogeneous linewidths  W. Kütt, G.C. Cho, M. Strahnen and H. Kurz, Electro-optic sampling of surface space-charge fields on III-V compounds  P.L. Swart, B.M. Lacquet and R. Thavar, Physical characterization of OMVPE-grown Al <sub>x</sub> Ga <sub>1-x</sub> As multi-layer films by means of non-destructive optical reflectometry  K. Jezierski, Z. Gumienny and J. Misiewicz, Reflectometry-aided surface layer investigation  F. Mosel, A. Seidl, D. Hofmann and G.  Müller, Infrared absorption of n- and p-type Fe-doped InP and mapping of  S. Sapieha, M. Verreault, J.E. Klemberg-Sapieha, E. Sacher and M.R. Wertheimer, X-ray photoelectron study of the plasma fluorination of lignocellu-lose  144 (1990) 165  S. Papieha, E. Sacher and M.R. Wertheimer, X-ray photoelectron study of the plasma fluorination of lignocellu-lose  144 (1990) 165  S. Papieha, E. Sacher and M.R. Wertheimer, X-ray photoelectron study of the plasma fluorination of lignocellu-lose  144 (1990) 165  S. Papieha, E. Sacher and M.R. Wertheimer, X-ray photoelectron study of the plasma fluorination of lignocellu-lose  144 (1990) 165  S. Pabhakaran and C.N.R. Rao, Adsorption of carbonyl compounds on clean and modified Cu(110) surfaces: a combined EELS-UPS study 350 (1991) 330  S. Yoshida, H. Ishida and J.S. Jen, X-ray photoelectron spectroscopic and X-ray diffractometric characterization of alkylimidazole films on copper oxide and alkylimidazolato copper(II) complexes  M. Wolpers, H. Viefhaus and M. Stratmann, SEM and SAM imaging of	stant: application to n-type ZnSe het-	50 (1001) 205	method of observing infrared emission	44 (1000) 42
quantum wells: measurement of homogeneous linewidths  W. Kütt, G.C. Cho, M. Strahnen and H. Kurz, Electro-optic sampling of surface space-charge fields on III-V compounds  P.L. Swart, B.M. Lacquet and R. Thavar, Physical characterization of OMVPE-grown Al <sub>x</sub> Ga <sub>1-x</sub> As multi-layer films by means of non-destructive optical reflectometry  K. Jezierski, Z. Gumienny and J. Misiewicz, Reflectometry-aided surface layer investigation  F. Mosel, A. Seidl, D. Hofmann and G. Müller, Infrared absorption of n- and p-type Fe-doped InP and mapping of  So (1991) 321  J.A. Kelber, J.W. Rogers, Jr., B.A. Banse and B.E. Koel, Interaction of dimethylamine with clean and partially oxidized copper surfaces  So (1991) 325  K. Prabhakaran and C.N.R. Rao, Adsorption of carbonyl compounds on clean and modified Cu(110) surfaces: a combined EELS-UPS study  S. Yoshida, H. Ishida and J.S. Jen, X-ray diffractometric characterization of alkylimidazole films on copper oxide and alkylimidazolato copper(II) complexes  M. Wolpers, H. Viefhaus and M. Stratmann, SEM and SAM imaging of	J.F. Donegan, J.P. Doran, R.P. Stanley, J. Hegarty, R.D. Feldman and R.F. Austin, Resonant Rayleigh scattering	50 (1991) 285	S. Sapieha, M. Verreault, J.E. Klemberg- Sapieha, E. Sacher and M.R. Wert- heimer, X-ray photoelectron study of	44 (1990) 43
W. Kütt, G.C. Cho, M. Strahnen and H.  Kurz, Electro-optic sampling of surface space-charge fields on III-V compounds  P.L. Swart, B.M. Lacquet and R. Thavar, Physical characterization of OMVPE-grown Al <sub>x</sub> Ga <sub>1-x</sub> As multi-layer films by means of non-destructive optical reflectometry  K. Jezierski, Z. Gumienny and J. Misiewicz, Reflectometry-aided surface layer investigation  F. Mosel, A. Seidl, D. Hofmann and G. Müller, Infrared absorption of n- and p-type Fe-doped InP and mapping of  M. Kütt, G.C. Cho, M. Strahnen and H.  ylamine with clean and partially oxidized copper surfaces  44 (1990) 193  K. Prabhakaran and C.N.R. Rao, Adsorption of carbonyl compounds on clean and modified Cu(110) surfaces: a combined EELS-UPS study  S. Yoshida, H. Ishida and J.S. Jen, X-ray photoelectron spectroscopic and X-ray diffractometric characterization of alkylimidazole films on copper oxide and alkylimidazolato copper(II) complexes  M. Wolpers, H. Viefhaus and M. Stratmann, SEM and SAM imaging of	quantum wells: measurement of ho-	50 (1001) 221	lose	44 (1990) 165
compounds  50 (1991) 325  K. Prabhakaran and C.N.R. Rao, Adsorption of carbonyl compounds on clean and modified Cu(110) surfaces: a combined EELS-UPS study  44 (1990) 205  S. Yoshida, H. Ishida and J.S. Jen, X-ray photoelectron spectroscopic and X-ray diffractometric characterization of alkylimidazole films on copper oxide and alkylimidazolato copper(II) complexes  Müller, Infrared absorption of n- and p-type Fe-doped InP and mapping of  K. Prabhakaran and C.N.R. Rao, Adsorption of carbonyl compounds on clean and modified Cu(110) surfaces: a combined EELS-UPS study  S. Yoshida, H. Ishida and J.S. Jen, X-ray photoelectron spectroscopic and X-ray diffractometric characterization of alkylimidazole films on copper oxide and alkylimidazolato copper(II) complexes  44 (1990) 301  M. Wolpers, H. Viefhaus and M. Stratmann, SEM and SAM imaging of	W. Kütt, G.C. Cho, M. Strahnen and H. Kurz, Electro-optic sampling of sur-	30 (1991) 321	and B.E. Koel, Interaction of dimeth- ylamine with clean and partially	44 (1000) 102
grown Al <sub>x</sub> Ga <sub>1-x</sub> As multi-layer films by means of non-destructive optical reflectometry  K. Jezierski, Z. Gumienny and J. Misiewicz, Reflectometry-aided surface layer investigation  F. Mosel, A. Seidl, D. Hofmann and G. Müller, Infrared absorption of n- and p-type Fe-doped InP and mapping of  a combined EELS-UPS study S. Yoshida, H. Ishida and J.S. Jen, X-ray photoelectron spectroscopic and X-ray diffractometric characterization of al- kylimidazole films on copper oxide and alkylimidazolato copper(II) com- plexes  44 (1990) 205  S. Yoshida, H. Ishida and J.S. Jen, X-ray diffractometric characterization of al- kylimidazole films on copper oxide and alkylimidazolato copper(II) com- plexes  44 (1990) 301	compounds	50 (1991) 325	K. Prabhakaran and C.N.R. Rao, Ad-	44 (1990) 193
reflectometry 50 (1991) 330 photoelectron spectroscopic and X-ray diffractometric characterization of alkylimidazole films on copper oxide and alkylimidazolato copper(II) complexes 44 (1990) 301 Müller, Infrared absorption of n- and p-type Fe-doped InP and mapping of M. Wolpers, H. Viefhaus and M. Stratmann, SEM and SAM imaging of	grown Al <sub>x</sub> Ga <sub>1-x</sub> As multi-layer films		a combined EELS-UPS study	44 (1990) 205
F. Mosel, A. Seidl, D. Hofmann and G.  Müller, Infrared absorption of n- and p-type Fe-doped InP and mapping of  plexes  M. Wolpers, H. Viefhaus and M. Stratmann, SEM and SAM imaging of	reflectometry K. Jezierski, Z. Gumienny and J. Mis-	50 (1991) 330	photoelectron spectroscopic and X-ray diffractometric characterization of al-	
p-type Fe-doped InP and mapping of mann, SEM and SAM imaging of	F. Mosel, A. Seidl, D. Hofmann and G.	50 (1991) 341	and alkylimidazolato copper(II) com- plexes	44 (1990) 301
the Fe distribution 50 (1991) 364 silane LB films on metallic substrates 45 (1990) 167	The state of the s	50 (1991) 364		45 (1990) 167

B.C. Beard, Cellulose nitrate as a binding energy reference in N(1s) XPS studies of nitrogen-containing organic mole- cules	45 (1990) 221	duced palladium deposition process from thin solid palladium acetate films Y. Horiike, T. Ichihara and H. Sakaue, Filling of Si oxide into a deep trench	46 (1990) 158
Xin Xu and J.I. Steinfeld, UV-laser photodeposition of iron films from Fe(CO) <sub>5</sub> : role of gas-phase and surface dissociation processes	45 (1990) 281	using digital CVD method  A. Boelle, J.A. Roger, B. Canut, J.  Mugnier and M. Pitaval, Sol-gel low- temperature preparation of silica	46 (1990) 168
D.C. Bradley, New metallo-organic pre-		films: RBS, TEM and MOS C-V	46 (1000) 200
cursors for surface processing L.V. Interrante, B. Han, J.B. Hudson and C. Whitmarsh, Design and synthesis of CVD precursors to thin film ceramic	46 (1990) 1	M. Bolle, K. Luther, J. Troe, J. Ihlemann and H. Gerhardt, Photochemically assisted laser ablation of doped poly-	46 (1990) 200
materials	46 (1990) 5	methyl-methacrylate	46 (1990) 279
D. Braichotte, C. Garrido and H. van den Bergh, The photolytic laser chemical vapor deposition rate of platinum, its		M. Wolpers, H. Viefhaus and M. Strat- mann, Surface analytical investiga- tions of metal surfaces modified by	
dependence on wavelength, precursor vapor pressure, light intensity, and		Langmuir-Blodgett films of silanes B. Biliński, W. Wójcik and A.L. Dawido-	47 (1991) 49
laser beam diameter  R. Larciprete, Photoprocesses in organo-	46 (1990) 9	wicz, Investigation of the surface free energy components of thermally	
metallics  J. Simpson and J.O. Williams, Preferential (111) orientation of ZnSe on	46 (1990) 19	inverse gas chromatography  A.J. Pertsin and Yu.M. Pashunin, An XPS	47 (1991) 99
(100) GaAs deposited by laser-in- duced MOCVD	46 (1990) 27	study of the in-situ formation of the polyimide/copper interface	47 (1991) 115
M.E. Pemble, J.T. Allen, D.S. Buhaenko,		M. Bou, J.M. Martin, Th. Le Mogne and	,
S.M. Francis, P.A. Goulding, J. Lee and M.J. Parrott, The adsorption of triethylgallium on GaAs(100) at 300		L. Vovelle, Chemistry of the interface between aluminium and polyethylene- terephthalate by XPS	47 (1991) 149
K: adsorption kinetics from optical	46 (1000) 22	B. Heens, Ch. Grégoire, J.J. Pireaux, P.A.	
second harmonic generation transients G. Radhakrishnan, W. Stenzel, H. Con- rad and A.M. Bradshaw, Photoreac-	46 (1990) 32	Cornelio and J.A. Gardella, Jr., On the stability and homogeneity of Langmuir-Blodgett films as models of	
tions of adsorbed CH <sub>3</sub> Br on Pt(111)	46 (1990) 36	polymers and biological materials for	47 (1001) 1(2
F. Schmaderer, R. Huber, H. Oetzmann and G. Wahl, High-T <sub>c</sub> YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-δ</sub>		surface studies: an XPS study A.H.M. Sondag, M.C. Raas and F.J.	47 (1991) 163
prepared by chemical vapour deposi-	46 (1000) 52	Touwslager, A comparison between	
tion  A. Bauer, J. Ganz, K. Hesse and E. Köhler, Laser-assisted deposition for	46 (1990) 53	inelastic electron tunnelling and in- frared reflection-absorption spec- troscopy for vibrational surface analy-	
electronic packaging applications	46 (1990) 113	sis	47 (1991) 205
R. Putzar, HC. Petzold and H. Staiger, Optimization of the laser-induced de- position technique for its application		D. Vassilakis, CM. Pradier, Y. Berthier and J. Oudar, Hydrogen, hydrogen sulfide and hydrocarbon coadsorption	
in X-ray mask repair	46 (1990) 131	on Pt(111) and Pt(110): selective for-	
H.G. Müller, K. Buschick, S. Schuler and A. Paredes, Laser direct writing of		mation of alkylthiols B.L. Halpern, J.J. Schmitt, J.W. Golz, Y.	47 (1991) 273
copper on various thin-film substrate materials	46 (1990) 143	Di and D.L. Johnson, Gas jet deposi- tion of thin films	48/49 (1991) 19
Y. Zhang and M. Stuke, VUV synchro-	,	A. Hatta, Y. Suzuki, T. Wadayama and	
tron radiation processing of thin pal- ladium acetate spin-on films for		W. Suëtaka, Kretschmann ATR-IR spectroscopy of investigating metal/	
metallic surface patterning H. Esrom and U. Kogelschatz, Investiga-	46 (1990) 153	liquid(or solid) interfaces  M. Takeuchi, M. Masui and Y. Momose,	48/49 (1991) 222
tion of the mechanism of the UV-in-			

Copper-phthalocyanine thin film pho-		G.N. Pain, T. Warminski, S. Sulcs, M.S.	
toelectrochemical cells	48/49 (1991) 517	Kwietniak, D. Gao, S.R. Glanvill, C.J.	
R.B. Gore, R.K. Pandey and S.R. Kumar,		Rossouw, A.W. Stevenson, S.P. Russo, R.G. Elliman, L.S. Wielunski, R.S.	
Preparation and characterisation of nearly stoichiometric CdTe films from		Rowe, G.B. Deacon, R.S. Dickson and	
a non-aqueous electrodeposition bath	48/49 (1991) 530	B.O. West, Characterization of low-	
A. Diarra, S. Hotchandani, H. Kassi and	10) 11 (2772) 222	temperature MOCVD Cd <sub>1-x</sub> Mn <sub>x</sub> Te	
R.M. Leblanc, Capacitance character-		thin films	48/49 (1991) 76
istics of mixed monolayers of chloro-		N. Hamaguchi, R. Gardiner and P.S.	
phyll a and carotenoid canthaxanthin	48/49 (1991) 567	Kirlin, MOCVD of TlBaCaCuO su-	
W.M.R. Divigalpitiya, R.F. Frindt and		perconducting thin films: structure-	
S.R. Morrison, Spread films of single	40 (40 (1001) 573	property-processing relationships	48/49 (1991) 441
molecular transition-metal sulphides	48/49 (1991) 572	C.T. Foxon, Control of MBE, MOMBE	50 (1001) 20
		and CBE growth using RHEED  C. Grattepain and A.M. Huber, Sec-	50 (1991) 28
Organometallic vapour deposition		ondary ion mass spectrometry of	
Organomeranic vapour acposition		dopants and impurities in compound	
		semiconductors: depth profiling of	
M. Sasaki, Y. Kawakyu, H. Ishikawa and		homo- and heterostructure	50 (1991) 42
M. Mashita, UV absorption spectra of		N. Herres, G. Bender and G. Neumann,	,
adlayers of MOCVD source gases	41/42 (1989) 342	Assessment of mismatched epitaxial	
T. Sasaki, T. Matsuoka and A. Katsui,		layers by X-ray rocking curve mea-	
MOVPE-grown GaN on polar planes of 6H-SiC	41/42 (1989) 504	surements and simulations	50 (1991) 97
S. Hayashi, T. Sakamoto, S. Fujita and S.	41/42 (1909) 304	A.M. Keir, S.J. Barnett, J. Giess, T.D.	
Fujita, Strained-layer superlattice		Walsh and M.G. Astles, A combina-	
buffers for high-quality heteroepi-		tion of high-resolution X-ray dif-	
layers of ZnSe on GaAs	41/42 (1989) 534	fractometry and diffraction imaging techniques applied to the study of	
H. Horikawa, M. Akiyama, S. Onozawa,		MOVPE-grown $Cd_xHg_{1-x}Te/CdTe$	
Y. Kawai and M. Sakuta, Interfacial		on GaAs	50 (1991) 103
layers of InP/Si heteroepitaxy	41/42 (1989) 598	J.G. Bauer, R. Treichler, T. Hillmer, J.	()
K.J. Mackey, D.C. Rodway, P.C. Smith		Müller and G. Ebbinghaus, Optimiza-	
and A.W. Vere, Photo-assisted	42 (1000) 1	tion of Zn dopant profiles in a pin-di-	
MOVPE growth of calcium fluoride B. Lecohier and H. van den Bergh, Selec-	43 (1989) 1	ode/FET by combination of depth	
tive copper film growth on platinum		profiling techniques: a SIMS, ECV	
clusters	43 (1989) 61	and AES study	50 (1991) 138
M. Jubber, J.I.B. Wilson, J.L. Davidson,	(2,0,0)	A. Gustafsson, S. Nilsson and L. Samuel-	
P.A. Fernie and P. John, Laser writing		son, Intensity variations in the near- band-edge recombination of GaP epi-	
of high purity gold tracks	43 (1989) 74	taxial layers, grown on (111) and (001)	
J.E. Epler, R.D. Bringans, F.A. Ponce,		oriented substrates, as observed by	
G.B. Anderson, D.W. Treat and T.L.		cathodoluminescence imaging	50 (1991) 186
Paoli, Laser patterned desorption		Z.M. Wang, J. Windscheif, D.J. As and	, ,
within an upflow metalorganic chem-	42 (1000) 422	W. Jantz, Ambient and low tempera-	
ical vapor deposition reactor  J. Morais, A.M. Machado, M.A. Sacilotti	43 (1989) 432	ture photoluminescence topography of	
and R. Landers, AES sputter depth		GaAs substrates, epitaxial and im-	
profiles applied to interface analysis		planted layers	50 (1991) 228
of GaInAs/InP grown by atmospheric		P.L. Swart, B.M. Lacquet and R. Thavar,	
pressure MOCVD	44 (1990) 161	Physical characterization of OMVPE- grown $Al_xGa_{1-x}As$ multi-layer films	
Y.C. Sasaki and K. Hirokawa, New tech-		by means of non-destructive optical	
nique for evaluation of surfaces and		reflectometry	50 (1991) 330
interfaces at atmospheric pressure by			( , , , , , , , , , , , , , , , , , , ,
using refracted X-ray fluorescence	47 (1001) 271	Oxidation	
(RXF)	47 (1991) 371	- Manual VII	
H.L.M. Chang, H. You, J. Guo and D.J. Lam, Epitaxial TiO <sub>2</sub> and VO <sub>2</sub> films		10 100 5 10 1 115	
Luin, Epitaniai 1102 and 102 inins		A Unitmand PH Hings I Reul and I H	
prepared by MOCVD	48/49 (1991) 12	A. Ourmazd, P.H. Fuoss, J. Bevk and J.F. Morar, The Si(001)/SiO <sub>2</sub> interface	41/42 (1989) 365

S. Nadahara, J. Shiozawa, K. Imai, K. Suguro and K. Yamabe, Protuberance growth at polysilicon surfaces during oxidation	41/42 (1989) 425	<ul> <li>H.J. Grabke, D. Wiemer and H. Viefhaus, Segregation of sulfur during growth of oxide scales</li> <li>W.J. Quadakkers, J. Jedlinski, K. Schmidt,</li> </ul>	47 (1991) 243
Y. Yasuda, S. Zaima, T. Kaida and Y. Koide, Formation of Si-SiO <sub>2</sub> interfaces at low temperatures using microwave-excited plasma	41/42 (1989) 429	M. Krašovec, G. Borchardt and H. Nickel, The effect of implanted yttrium on the growth and adherence of alumina scales on Fe-20Cr-5Al	47 (1991) 261
E.J. Petit, J. Riga, R. Caudano and J. Verbist, Ultraviolet laser-induced oxidation of antimony: chemical com-		S.C. Tjong and H.C. Swart, Auger characterization of the surface oxidation of austenitic Fe-26Mn-7Al-0.9C al-	
position and growth kinetics of the oxide layer W.C.M. Claassen, R.W.A.H. Schmitz and	43 (1989) 285	S. Hashimoto, XPS and AES studies on the interface between metal and poly-	47 (1991) 311
J. Dieleman, Influence of surface fluo- rination on the oxidation of amor- phous silicon by atomic oxygen at 300		mer layers. The effect of Ar-plasma treatment of the polymer surface pre- ceding the metal deposition	47 (1991) 323
K J. Kubátová, V. Cháb, I. Lukeš, P. Jiříček and F. Fendrych, ArF excimer laser	43 (1989) 292	I. Dalins, M. Karimi and D. Ila, Violent oxidation of lithium-containing alumi- num alloys in liquid oxygen	48/49 (1991) 509
induced changes in the Si(100)/SiO <sub>2</sub> interface studied in situ by ESCA and		Oxides	48/49 (1991) 309
LEED  J.P. Baltrus and A. Proctor, Composition	43 (1989) 297	K. Matsuo and K. Nakano, Characteriza-	
of overlayers on oxidized pyrite surfaces	44 (1990) 147	tion of semiconductor oxides by IR diffuse reflectance spectroscopy	41/42 (1989) 53
S.C. Tjong and J.B. Malherbe, Auger studies of the effect of Mo, V and Pd additions on the oxidation characteris-		T. Arakawa, H. Baba and G. Adachi, Deep level transient spectroscopic studies of the perovskite oxides as gas	
tics of Fe-24Cr alloy M.J. van Staden and J.P. Roux, The controlled oxidation of the high chro-	44 (1990) 179	sensor material T.A. Nguyen Tan, N. Guerfi, J.Y. Veuil- len and J. Derrien, Oxidation of TaSi <sub>2</sub>	41/42 (1989) 212
mium steel alloys Fe40Cr and Fe40Cr3Ru	44 (1990) 263	thin films on polycrystalline Si H. Ishii, H. Hasegawa, A. Ishii and H.	41/42 (1989) 266
E.M. Perry, D.L. Cocke and M.K. Miller, The oxidation of Ni <sub>3</sub> Zr investigated by atom-probe field-ion microscopy		Ohno, X-ray photo-electron spec- troscopy analysis of InP insulator- semiconductor structures prepared by	
and X-ray photoelectron spectroscopy S. Deckers, F.H.P.M. Habraken, W.F. van der Weg, A.W. Denier van der Gon,	44 (1990) 321	anodic oxidation  A. Mele, D. Consalvo, D. Stranges, A. Giardini-Guidoni and R. Teghil, Clus-	41/42 (1989) 390
J.F. van der Veen and J.W. Geus, Oxidation-induced segregation at the Pt <sub>0.5</sub> Ni <sub>0.5</sub> (111) surface studied by		ter ion formation by laser evaporation of solid complex oxides J.A. Kelber, J.W. Rogers, Jr., B.A. Banse	43 (1989) 398
medium-energy ion scattering S. Deckers, F.H.P.M. Habraken, W.F. van	45 (1990) 121	and B.E. Koel, Interaction of dimeth- ylamine with clean and partially	
der Weg and J.W. Geus, Oxidation of clean and Pt-covered Ni(111)	45 (1990) 207	oxidized copper surfaces S. Yoshida, H. Ishida and J.S. Jen, X-ray	44 (1990) 193
P. Patel and I.W. Boyd, Low temperature VUV enhanced growth of thin silicon dioxide films	46 (1990) 352	photoelectron spectroscopic and X-ray diffractometric characterization of al- kylimidazole films on copper oxide	
K. Kolev, M. Wautelet and L.D. Laude, CW laser-induced transformation of	10 (1550) 202	and alkylimidazolato copper(II) com- plexes	44 (1990) 301
thin Sb, Se and Sb <sub>2</sub> Se <sub>3</sub> films in air G.E. Rhead, On the work function variations produced by the oxidation of	46 (1990) 418	A.R. Gonzalez-Elipe, J.P. Espinos, A. Fernandez and G. Munuera, XPS study of the surface carbonation/hy-	(2770) 501
adsorbed alkali metal layers	47 (1991) 35	droxylation state of metal oxides	45 (1990) 103

J.A. Treverton and A. Rosenfeld, De- termination of etching characteristics of a Vacuum Generators AG21 argon-		J.H. Craig, Jr. and J. Lozano, Effect of oxygen on chemisorption of CO on Rh(100)	45 (1990) 151
ion gun by interference colour and ellipsometric assessment of craters		W.S. Lee, R.A. Outlaw, G.B. Hoflund and M.R. Davidson, Auger electron	43 (1990) 131
etched in tantalum oxide films  R. Pielmeier, D. Bollmann and K. Haberger, Laser evaporation of metal	45 (1990) 263	intensity variations in oxygen-charged silver A.R. Balkenende, H. den Daas, M. Huis-	47 (1991) 91
sandwich layers for improved IC metallization	46 (1990) 163	man, O.L.J. Gijzeman and J.W. Geus, The interaction of NO, O <sub>2</sub> and CO	
R. Kötz, Ultraviolet photoelectron spectroscopy (UPS) of anodic oxide films	47 (1001) 100	with Cu(100) and Cu(110) S.S. Fu and G.A. Somorjai, Zinc oxide	47 (1991) 341
on Au, Pt, Ru and Ru <sub>0.5</sub> Ir <sub>0.5</sub> alloy S.U.M. Khan, J.P. Baltrus, R.W. Lai and A.G. Richardson, X-ray photoelectron	47 (1991) 109	and oxygen overlayers on Cu(110): a model for Cu-Zn-O catalysts  S. Hongo, T. Urano and T. Kanaji, Mech-	48/49 (1991) 93
spectroscopic study of the interaction of xanthate with coal pyrite and mineral pyrite surfaces	47 (1991) 355	anisms of He*(2 <sup>1</sup> S) de-excitation on oxygen-adsorbed Si(100) surfaces  A. Chevarier, N. Chevarier, M. El Bou-	48/49 (1991) 143
D.G. Ren, Study of interface structure of the oxide grown on nickel alloys by	49 /40 /1001) 227	anani, E. Gerlic, M. Stern, B. Roux and F. Thimon, Profiling of carbon,	
AP-FIM  T. Hosaka, Effects of impurities in a two-layer evaporated Au film on its tensile	48/49 (1991) 227	oxygen and argon contamination in sputter-deposited films using nuclear backscattering and nuclear reaction	
fracture  J.C. Fariñas and M.F. Barba, Inductively coupled plasma-atomic emission spectrometry (ICP-AES): an analyti-	48/49 (1991) 502	spectroscopy B.V. King, D.J. O'Connor, Y. Shen, R.J. MacDonald, M. Katayama and M. Aono, LEIS for structure determina-	48/49 (1991) 215
cal technique for the chemical char- acterization of perovskite ceramic semiconductors	50 (1991) 202	tion of surfaces and thin films Y. Gao, I. Ardelean, D. Renard, B. Rose and Y. Jin, High-depth-resolution SIMS analysis for InGaAs/InP inter-	48/49 (1991) 246
Oxygen		faces  A. Deneuville, C.H. Park, P. Ayyub, T. Anderson, P. Lowen, K. Jones and	50 (1991) 131
M. Bowker and D. Halstead, Adsorption studies on catalysts. II. Application to rapid adsorbers – oxygen on Europ-		P.H. Holloway, O implantation in ZnSe: lattice distortion by Raman measurement	50 (1991) 308
latinum 1 R. Ducros and J. Fusy, Oxygen adsorp-	44 (1990) 1	Palladium	
tion on $Pt(110)(1 \times 2)$ . Surface characterization by photoemission of adsorbed xenon (PAX)	44 (1990) 59	B. Oral, Y.C. Lee and R.W. Vook, Ther- mal desorption spectroscopy investi-	
A.E.M.J. Fischer, W.F.J. Slijkerman, J.F. van der Veen and I. Ohdomari, Thermal stability of supersaturated oxy-	(,	gation of CO adsorption on Cu/Pd(111) surfaces S.C. Tjong and J.B. Malherbe, Auger	44 (1990) 65
gen-doped silicon epitaxial films C.O. de González and E.A. García, De-	44 (1990) 115	studies of the effect of Mo, V and Pd additions on the oxidation characteris-	
termination of the diffusion coeffi- cients of oxygen in zirconium by means of XPS	44 (1990) 211	tics of Fe-24Cr alloy P. Ptáček and Z. Bastl, XPS characterization of supported bimetallic pal-	44 (1990) 179
H. Zaïdi, D. Paulmier and J. Lepage, The influence of the environment on the friction and wear of graphitic carbons.		ladium-silver clusters Y. Zhang and M. Stuke, VUV synchrotron radiation processing of thin pal-	45 (1990) 319
II. Gas coverage of wear debris D.R. Baer, R.L. Gordon and C.W. Hubbard, Work function and UPS study	44 (1990) 221	ladium acetate spin-on films for metallic surface patterning  H. Esrom and U. Kogelschatz, Investiga-	46 (1990) 153
of Au and O on Re	45 (1990) 71	tion of the mechanism of the UV-in-	

duced palladium deposition process from thin solid palladium acetate films R.W. Vook and B. Oral, Carbon mono- xide oxidation on epitaxial Cu(111)/ Pd(111) bilayers at atmospheric pres-	46 (1990) 158	G. Strasser, S. Dubois, M. Besson, E. Gornik, G. Weimann, E. Bauser and H. Riechert, Analysis of impurity distribution in n-GaAs layers by photoconductivity and cyclotron resonance	
sures	48/49 (1991) 125	measurements S. Usala, G.J. Adriaenssens, Ö. Öktü and M. Nesladek, Post-transit-time analy-	50 (1991) 261
Phosphine		sis of time-of-flight photocurrents D.I. Desnica, B. Šantić and U.V. Desnica,	50 (1991) 265
XL. Zhou, C. Yoon and J.M. White, Interactions of PF <sub>3</sub> and PD <sub>3</sub> with clean, P-covered and H(D)-covered (100)-		Time-evolution of low-temperature photoconductivity and Hall mobility in semi-insulating GaAs	50 (1991) 269
oriented W foil	44 (1990) 103	M. Hage-Ali, B. Yaacoub, S. Mergui, M. Samimi, B. Biglari and P. Siffert, Microscopic defect level characterization	
Phosphorus		of semi-insulating compound semicon- ductors by TSC and PICTS. Applica-	
P. Lejček, M. Koutník, J. Brádler, V. Paidar and A. Potměšilová, Anisotropy of grain boundary segregation		A. Baraldi, C. Ghezzi, A. Parisini, A. Bosacchi and S. Franchi, Analysis of electron mobility versus temperature	50 (1991) 377
in as-grown Fe-6at%Si alloy bi- crystals XL. Zhou, C. Yoon and J.M. White, Interactions of PF <sub>3</sub> and PD <sub>3</sub> with clean,	44 (1990) 75	after photoexcitation in Si-doped $Al_xGa_{1-x}As$	50 (1991) 405
P-covered and H(D)-covered (100)-oriented W foil	44 (1990) 103	Photodesorption	
G. Stock, D. Bollmann, R. Buchner, G. Neumayer and K. Haberger, Ultra-flat p-n junctions formed by solid source laser doping	46 (1990) 348	J.E. Epler, R.D. Bringans, F.A. Ponce, G.B. Anderson, D.W. Treat and T.L. Paoli, Laser patterned desorption	
HG. Hettwer, W. Lerch, B. Lentfort, N.A. Stolwijk and H. Mehrer, Com- bined application of spreading-resis-	(3.3.7)	within an upflow metalorganic chemical vapor deposition reactor  N. Eleftheriadis, HP. Ludescher, M. Süssbauer and D. von der Linde, Pico-	43 (1989) 432
tance and electron-microprobe depth profiling on GaAs:Zn and Si:P	50 (1991) 470	second time-resolved laser desorption A.I. Agafonov and T.M. Makhviladze, Mechanisms of photon-stimulated de-	46 (1990) 284
Photoconductivity		sorption and chemisorption of atomic particles on the surfaces of semicon-	47 (1000) 200
Y. Kanemitsu and S. Imamura, Charge transport and trapping at the interface in two-layer organic photoconductors	41/42 (1989) 544	ductors and metals  Fu-Ming Pan, Yuh-Lin Lin and Shean- Ren Horng, Decomposition of perflu- oropolyethers during XPS measure-	46 (1990) 288
K. Oishi, K. Fukuchi, T. Suzuki and J. Sunada, Mechanism of photoconduc-		ments E.C. Benck, Z. Rong, S.H. Chen and H.A.	47 (1991) 9
tion on surface-oxidized Ge films M. Takeuchi, Y. Watanabe and S. Ozawa, Gas-sensitive properties of ultrafine	48/49 (1991) 276	Schuessler, Cavity-enhanced detection of surface ablation	48/49 (1991) 257
In <sub>2</sub> O <sub>3</sub> particle layers prepared by gas evaporation technique R.A. Stradling, Far-infrared spectroscopy	48/49 (1991) 526	Photoelectron spectroscopy	
of impurities in semiconductors  S.D. Baranovskii, Theoretical basis for the quantitative characterization of impur- ities in n-type III-V compound semi-	50 (1991) 65	W.E. Spicer, R. Cao, K. Miyano, T. Kendelewicz, I. Lindau, E. Weber, Z. Liliental-Weber and N. Newman, From synchrotron radiation to <i>I-V</i>	
conductors by photoelectromagnetic spectroscopy	50 (1991) 218	measurements of GaAs Schottky bar- rier formation	41/42 (1989) 1

G. Le Lay, K. Hricovini and J.E. Bonnet, Synchrotron radiation investigation and surface spectroscopy studies of prototypical systems: lead-semicon-		<ul> <li>N. Fujimura, S. Tachibana and T. Ito, Characterization of Si-rich WSi<sub>x</sub> on Si</li> <li>J.F. Morar, U.O. Karlsson, R.I.G. Uhrberg, J. Kanski, P.O. Nilsson and H.</li> </ul>	41/42 (1989) 286
ductor interfaces  D. Paget, HJ. Drouhin and J. Peretti, Infrared field assisted photoemission of metal-semiconductor structures	41/42 (1989) 25 41/42 (1989) 38	Qu, Angle-resolved photoemission study of the As/Ge(100) interface F.J. Himpsel, T.F. Heinz, A.B. McLean and E. Palange, Bonding at silicon/in-	41/42 (1989) 312
S. Nakanishi, H. Tokutaka, K. Nishimori, S. Kishida and N. Ishihara, The difference between 6H-SiC (0001) and (0001) faces observed by AES, LEED and ESCA	41/42 (1989) 38	sulator interfaces  C.A. Sébenne, J.P. Lacharme, I. Andriamanantenasoa and M. Khial, Local roughness and surface states on Si(001): analysis of vacuum anneal-	41/42 (1989) 346
S. Kono, Y. Enta, T. Abukawa, T. Kinoshita and T. Sakamoto, Photo-electron spectroscopy and photoelec-		<ul><li>ings and oxygen adsorption-desorption processes</li><li>A. Ourmazd, P.H. Fuoss, J. Bevk and J.F.</li></ul>	41/42 (1989) 352
tron diffraction studies of Si(001) 2 × 1-K and -Cs surfaces M. Iwami, M. Kusaka, M. Hirai, M.	41/42 (1989) 75	Morar, The Si(001)/SiO <sub>2</sub> interface  A.S. Barrière, G. Couturier, H. Guegan,  T. Séguelong, A. Thabti, P. Alnot and	41/42 (1989) 365
Kubota, H. Tochihara and Y. Murata, Mechanism of alloy formation due to noble metal deposition on silicon surfaces at room temperature: chem-		J. Chazelas, Interface GaAs – gallium fluoride thin film grown by fluorin- ation. Electrical behaviour of the ob- tained MIS fluorinated GaAs struc-	
ical bonding model  X.M. Ding, G.S. Dong, X.K. Lu, H.Y.  Xiao, P. Chen and X. Wang, Application of HREELS to Al/GaAs and	41/42 (1989) 97	tures H. Ishii, H. Hasegawa, A. Ishii and H. Ohno, X-ray photo-electron spec- troscopy analysis of InP insulator—	41/42 (1989) 383
Al/GaP interfaces  D.W. Niles, M. Tang, J. McKinley, R.  Zanoni and G. Margaritondo, From	41/42 (1989) 123	semiconductor structures prepared by anodic oxidation P. Soukiassian, H.I. Starnberg and T.	41/42 (1989) 390
heterojunction interfaces to metal- semiconductor interfaces D.R.T. Zahn, W. Richter, A.B. McLean, R.H. Williams, C. Stephens, I.T. Mc-	41/42 (1989) 139	Kendelewicz, Insulator-semiconduc- tor interface formation by electronic promotion using alkali metal and re- moval of the catalyst	41/42 (1989) 395
Govern, R. Cimino, W. Braun and N. Esser, Temperature effects on the formation of the Sb/InP(110) interface	41/42 (1989) 179	T. Hattori, H. Yamagishi, N. Koike, K. Imai and K. Yamabe, Structural studies of ultrathin silicon oxides and their	
R.H. Williams, N. Forsyth, I.M. Dhar- madasa and Z. Sobiesierski, Metal contacts to II-VI semiconductors: CdS and CdTe	41/42 (1989) 189	interfaces by XPS  S. Tatarenko, J. Cibert, Y. Gobil, G. Feuillet, K. Saminadayar, A.C. Chami and E. Ligeon, RHEED, XPS,	41/42 (1989) 416
H. Sugahara and J. Nagano, Thermal sta- bility of WSiN-GaAs and Au-WSiN interfaces	41/42 (1989) 207	HRTEM and channeling studies of molecular beam epitaxy growth of CdTe on (001) GaAs	41/42 (1989) 470
N. Cherief, R. Cinti, M. De Crescenzi, J. Derrien, T.A. Nguyen Tan and J.Y. Veuillen, Heteroepitaxy of metallic		R. Haight and J.A. Silberman, Surface intervalley scattering on GaAs(110) studied with picosecond laser photo-	, (,
and semiconducting silicides on sili- con L. Haderbache, P. Wetzel, C. Pirri, J.C.	41/42 (1989) 241	emission  B.A. Orlowski, J.P. Lacharme, C.A. Se benne and S. Bensalah, Interface for-	41/42 (1989) 487
Peruchetti, D. Bolmont and G. Gewinner, Identification of three distinct $CoSi_2(111)(1 \times 1)$ surface struc-		mation on n- and p-CdTe(110) surfaces with Cu and Au T. Sasaki, T. Matsuoka and A. Katsui,	41/42 (1989) 491
tures T.A. Nguyen Tan, N. Guerfi, J.Y. Veuillen and J. Derrien, Oxidation of TaSi 2	41/42 (1989) 257	MOVPE-grown GaN on polar planes of 6H-SiC C. Tatsuyama, T. Tanbo and N. Nakaya-	41/42 (1989) 504
thin films on polycrystalline Si	41/42 (1989) 266		

ma, Heteroepitaxy between layered semiconductors GaSe and InSe	41/42 (1989) 539	S. Sapieha, M. Verreault, J.E. Klemberg- Sapieha, E. Sacher and M.R. Wert-	
P.S. Ho, Chemistry and adhesion of		heimer, X-ray photoelectron study of	
metal-polymer interfaces  K. Maehashi, S. Hasegawa and H.	41/42 (1989) 559	the plasma fluorination of lignocellu- lose	44 (1990) 165
Nakashima, Atomic rearrangement		A.J. Pertsin and Yu.M. Pashunin, Dif-	44 (1770) 103
during the initial stages of GaAs		ferential charging in XPS studies of	
growth on Si(111)( $\sqrt{3} \times \sqrt{3}$ )-Ga		polymer/metal interfaces	44 (1990) 171
surface	41/42 (1989) 567	K. Prabhakaran and C.N.R. Rao, Ad-	, , , , , , , , , , , , , , , , , , , ,
T. Aoyama, T. Sugi and T. Ito, De-	, , , ,	sorption of carbonyl compounds on	
termination of band line-up in $\beta$ -		clean and modified Cu(110) surfaces:	
SiC/Si heterojunction for Si-HBT's	41/42 (1989) 584	a combined EELS-UPS study	44 (1990) 205
Y. Yamada Maruo, M. Oshima, T. Waho,		C.O. de González and E.A. García, De-	
T. Kawamura, S. Maeyama and T.		termination of the diffusion coeffi-	
Miyahara, Photoemission studies of		cients of oxygen in zirconium by	
bonding properties at the MBE-grown		means of XPS	44 (1990) 211
CaF <sub>2</sub> /GaAs interface	41/42 (1989) 647	M.J. van Staden and J.P. Roux, The con-	
R. Nowak, P. Hess, H. Oetzmann and C.		trolled oxidation of the high chro-	
Schmidt, XPS characterization of		mium steel alloys Fe40Cr and	44 (1000) 2(2
chromium films deposited from	42 (1000) 11	Fe40Cr3Ru	44 (1990) 263
Cr(CO) <sub>6</sub> at 248 nm E.J. Petit, J. Riga, R. Caudano and J.	43 (1989) 11	S. Yoshida, H. Ishida and J.S. Jen, X-ray photoelectron spectroscopic and X-ray	
Verbist, Ultraviolet laser-induced		diffractometric characterization of al-	
oxidation of antimony: chemical com-		kylimidazole films on copper oxide	
position and growth kinetics of the		and alkylimidazolato copper(II) com-	
oxide layer	43 (1989) 285	plexes	44 (1990) 301
J. Kubátová, V. Cháb, I. Lukeš, P. Jiříček	(2,0), 200	M. Gendry, J. Durand, M. Erman, J.B.	(2770) 222
and F. Fendrych, ArF excimer laser		Theeten, L. Nevot and B. Pardo,	
induced changes in the Si(100)/SiO <sub>2</sub>		Chemical and structural analysis by	
interface studied in situ by ESCA and		ellipsometry and X-ray reflectometry	
LEED	43 (1989) 297	of thin sulfide layers grown on InP	44 (1990) 309
S. Akhter, K.C. Cannon and J.M. White,		E.M. Perry, D.L. Cocke and M.K. Miller,	
Distribution of compositional defects		The oxidation of Ni <sub>3</sub> Zr investigated	
in solvent cast polyvinyl alcohol films:		by atom-probe field-ion microscopy	
angular dependent XPS and reactivity		and X-ray photoelectron spectroscopy	44 (1990) 321
study	44 (1990) 49	S.L.T. Andersson and J.C. Otamiri,	
R. Ducros and J. Fusy, Oxygen adsorp-		Surface and bulk composition of	
tion on Pt(110)(1 $\times$ 2). Surface char-		$YBa_2Cu_3O_{6+x}$ compounds studied by	45 (1000) 1
acterization by photoemission of ad-	44 (1000) 50	XPS	45 (1990) 1
sorbed xenon (PAX)	44 (1990) 59	W.A.M. Aarnink, A. Weishaupt and A.	
T. Ito, T. Yasumatsu and A. Hiraki, Ho- moepitaxial growth of silicon on		van Silfhout, Angle-resolved X-ray photoelectron spectroscopy (ARXPS)	
anodized porous silicon	44 (1990) 97	and a modified Levenberg-Marquardt	
J. Lausmaa, B. Kasemo and H. Mattsson,	44 (1990) 97	fit procedure: a new combination for	
Surface spectroscopic characterization		modeling thin layers	45 (1990) 37
of titanium implant materials	44 (1990) 133	G. Ranga Rao and C.N.R. Rao, Adsorp-	(2225)
J.P. Baltrus and A. Proctor, Composition	()	tion of nitrogen on clean and modified	
of overlayers on oxidized pyrite		single-crystal Ni surfaces	45 (1990) 65
surfaces	44 (1990) 147	D.R. Baer, R.L. Gordon and C.W. Hub-	
S. Suzuki and M. Oku, Surface orienta-		bard, Work function and UPS study	
tion dependence of the surface com-		of Au and O on Re	45 (1990) 71
position in an Fe-20%Cr alloy and an		A.R. Gonzalez-Elipe, J.P. Espinos, A.	
Fe-3%Si alloy treated by mechanical		Fernandez and G. Munuera, XPS	
polishing and chemical etching	44 (1990) 151	study of the surface carbonation/hy-	
A.L. Tofterup, Estimates of errors and		droxylation state of metal oxides	45 (1990) 103
validity of Shirley-type backgrounds	44 (1990) 157	Ch. Cardinaud and G. Turban, Mechanis-	

tic studies of the initial stages of etch-	45 (1000) 100	surface of silicon: a comparative SIMS	47 (1991) 1
ing of Si and SiO <sub>2</sub> in a CHF <sub>3</sub> plasma R.V. Siriwardane and J.A. Poston, Inter-	45 (1990) 109	and XPS study Fu-Ming Pan, Yuh-Lin Lin and Shean-	47 (1991) 1
		Ren Horng, Decomposition of perflu-	
action of H <sub>2</sub> S with zinc titanate in the	45 (1990) 131	oropolyethers during XPS measure-	
presence of H <sub>2</sub> and CO	43 (1990) 131	ments	47 (1991) 9
S.C. Tjong, A surface study of the passi-		J.C. Lascovich, R. Giorgi and S. Scagl-	47 (1991)
vation of Fe-Cr-Co magnet alloys in	45 (1990) 141	ione, Evaluation of the sp <sup>2</sup> /sp <sup>3</sup> ratio	
sulphuric acid solution	45 (1990) 141	in amorphous carbon structure by XPS	
J. Lausmaa, B. Kasemo, H. Mattsson and		and XAES	47 (1991) 17
H. Odelius, Multi-technique surface			47 (1991) 17
characterization of oxide films on		S.J. Hoekje and G.B. Hoflund, Surface	
electropolished and anodically oxi-	45 (1000) 100	characterization study of InP(100)	
dized titanium	45 (1990) 189	substrates using ISS, AES and ESCA:	
B.C. Beard, Cellulose nitrate as a binding		comparison of substrates from two	47 (1001) 42
energy reference in N(1s) XPS studies		different commercial sources	47 (1991) 43
of nitrogen-containing organic mole-	45 (1000) 221	M. Wolpers, H. Viefhaus and M. Strat-	
cules	45 (1990) 221	mann, Surface analytical investiga-	
Xin Xu and J.I. Steinfeld, UV-laser pho-		tions of metal surfaces modified by	47 (1001) 40
todeposition of iron films from		Langmuir-Blodgett films of silanes	47 (1991) 49
Fe(CO) <sub>5</sub> : role of gas-phase and surface	47 (4000) 204	M.M. Hills and G.S. Arnold, Chemical	
dissociation processes	45 (1990) 281	treatment of fused silica with xenon	45 (1001) 55
S.C. Tjong, Self-passivation of Fe-Cr-		difluoride	47 (1991) 77
PGM alloys in reducing acids studied		R. Kötz, Ultraviolet photoelectron spec-	
by electrochemical and electron spec-		troscopy (UPS) of anodic oxide films	45 (4004) 400
troscopic techniques	45 (1990) 301	on Au, Pt, Ru and Ru <sub>0.5</sub> Ir <sub>0.5</sub> alloy	47 (1991) 109
P. Ptáček and Z. Bastl, XPS characteriza-		A.J. Pertsin and Yu.M. Pashunin, An XPS	
tion of supported bimetallic pal-		study of the in-situ formation of the	
ladium-silver clusters	45 (1990) 319	polyimide/copper interface	47 (1991) 115
D.E. King, J.E. Fernandez and W.E.		M. Bou, J.M. Martin, Th. Le Mogne and	
Swartz, An XPS study of the doping		L. Vovelle, Chemistry of the interface	
of trans, trans-p-distyrylbenzene with		between aluminium and polyethylene-	.= (1001) 110
AsF <sub>5</sub> : a model conducting polymer		terephthalate by XPS	47 (1991) 149
system	45 (1990) 325	B. Heens, Ch. Grégoire, J.J. Pireaux, P.A.	
G. Moretti, S. De Rossi and G. Ferraris,		Cornelio and J.A. Gardella, Jr., On	
Characterization of well dispersed		the stability and homogeneity of	
copper species on the surface of ZnO		Langmuir-Blodgett films as models of	
by X-ray photoelectron spectroscopy	45 (1990) 341	polymers and biological materials for	
J.L. Chartier, A. Serrari, R. Le Bihan, M.		surface studies: an XPS study	47 (1991) 163
Ligeon, F. Gaspard and F. Muller,		H. Roulet, G. Dufour, A. Cheenne, F.	
Thermal nitridation of anodic silicon		Rochet and C. Cartier, Physicoche-	
dioxide	45 (1990) 351	mistry of laser-deposited BiSrCaCuO	
A. Bauer, J. Ganz, K. Hesse and E.		thin films studied by XPS and XAS	47 (1991) 173
Köhler, Laser-assisted deposition for		B.R. Strohmeier, Evaluation of polymeric	
electronic packaging applications	46 (1990) 113	standard reference materials for moni-	
H.G. Müller, K. Buschick, S. Schuler and		toring the performance of X-ray pho-	
A. Paredes, Laser direct writing of		toelectron spectrometers	47 (1991) 225
copper on various thin-film substrate		E. Occhiello, M. Morra, F. Garbassi, D.	
materials	46 (1990) 143	Johnson and P. Humphrey, SSIMS	
A. Giardini-Guidoni, A. Morone, M.		studies of hydrophobic recovery:	
Snels, E. Desimoni, A.M. Salvi, R.		oxygen plasma treated PS	47 (1991) 235
Fantoni, W.C.M. Berden and M.		M. Muhler, Z. Paál and R. Schlögl, XPS	
Giorgi, Luminescence and ESCA		of platinum in Pt/SiO <sub>2</sub> (Europt-1):	
analysis of laser-ablated materials	46 (1990) 321	possibilities and limitations of the	4=
D. Ballutaud, P. de Mierry, M. Aucoutu-		method	47 (1991) 281
rier and E. Darque-Ceretti, Influence		S. Hashimoto, XPS and AES studies on	
of thermal treatments on the distribu-		the interface between metal and poly-	
tion of contaminating copper near the		mer layers. The effect of Ar-plasma	

<ul> <li>Y. Shigesato, S. Takaki and T. Haranou, Crystallinity and electrical properties of tin-doped indium oxide films de- posited by DC magnetron sputtering</li> <li>P.K. Banerjee, J.S. Kim and S.S. Mitra,</li> </ul>	48/49 (1991) 269	Piezoelectric effect  S. Zaima, T. Maruyama and Y. Yasuda, Piezoresistance in n-channel inversion layers of Si MOSFET's	41/42 (1989) 433
Ludeke, M. Prietsch, T. Maeda Wong, E.W. Plummer and N.J. DiNardo, Metal-induced states on the GaAs- (110) surface probed by angle-resolved photoemission spectroscopy	48/49 (1991) 260	P.E. Dyer, R.D. Greenough, A. Issa and P.H. Key, TEA CO <sub>2</sub> laser ablation studies of Y-Ba-Cu-O	43 (1989) 387
ture and Schottky barriers of epitaxial Pb on Si(111) D. Heskett, D. Tang, A.B. McLean, R.	48/49 (1991) 209	Photon emission	
T. Hibma, H.H. Weitering, D.R. Heslinga and T.M. Klapwijk, Interface struc-	, (	spectroscopy of compound semicon- ductor surfaces and interfaces	50 (1991) 34
Marthon and J.F.M. Westendorp, Surface composition analysis of HF vapour cleaned silicon by X-ray pho- toelectron spectroscopy	48/49 (1991) 178	Preparation and characterisation of nearly stoichiometric CdTe films from a non-aqueous electrodeposition bath I.T. McGovern, Soft X-ray photoelectron	48/49 (1991) 530
N. Igata, The effect of electronic excitation produced by an electron shower on the adhesion of copper films deposited on stainless steel  A. Ermolieff, F. Martin, A. Amouroux, S.	48/49 (1991) 173	Kishida and N. Ishihara, Surface study of single-crystal 80 K Bi-Sr-Ca-Cu-O superconductor with Si and Nb by RHEED and XPS depth profile R.B. Gore, R.K. Pandey and S.R. Kumar,	48/49 (1991) 450
<ul> <li>Y. Fukuda and M. Nagoshi, Chemisorption of hydrogen on Cr(111) studied by XPS, UPS, and HREELS</li> <li>H. Yumoto, K. Watanabe, K. Akashi and</li> </ul>	48/49 (1991) 147	characterization of Bi-based high-T <sub>c</sub> superconducting thin films and bulk single crystals  K. Nishimori, H. Tokutaka, T. Tamon, S.	48/49 (1991) 425
The role of non-adiabaticity and two- dimensional Fermi surfaces in the re- construction of Mo(001) and W(001)	48/49 (1991) 135	CdS/CuInSe <sub>2</sub> heterojunction interface H. Tokutaka and S. Kishida, Surface	48/49 (1991) 419
Heichler and K. Wandelt, Properties of noble metal and binary alloy monolayer films on Ru(001)  K.E. Smith, G.S. Elliott and S.D. Kevan,	48/49 (1991) 59	<ul> <li>A.J. Nelson, S. Gebhard, L.L. Kazmerski,</li> <li>A. Rockett, E. Colavita, M. Engelhardt and H. Höchst, Soft X-ray photoemission investigation of the</li> </ul>	
Y. Nakanishi, Y. Suzuki, T. Nakamura, Y. Hatanaka, Y. Fukuda, A. Fujisawa and G. Shimaoka, Coloration of Sn-Sb-O thin films K. Kalki, B. Pennemann, U. Schröder, W.	48/49 (1991) 55	Ruolian, Hu Liqun, Zhong Peixin, Yu Shidong, Li Qi, Feng Duan and Chen Guangxi, The structure of $Ge_xSi_{1-x}/Si$ strained layer superlattices and heterostructures	48/49 (1991) 356
A. Mowbray and R.G. Jones, Homo- and hetero-iodide thin film growth on InSb(001): low-temperature iodide formation and epitaxial growth of CdI <sub>2</sub>	48/49 (1991) 27	photoelectron spectroscopy M.L. Shek, T.K. Sham, J. Hrbek and G Q. Xu, A soft X-ray study of a Li-S surface compound Zhang Rong, Zheng Youdou, Jiang	48/49 (1991) 312 48/49 (1991) 332
perthwaite, P.R. Davies, E.M. Moser and M.W. Roberts, Activation of carbon dioxide at bismuth, gold and copper surfaces	47 (1991) 375	process gases  A. Mansour, G. Indlekofer and P. Oelhafen, Investigation of the electronic structure of thin diamond films by	48/49 (1991) 301
spectroscopic study of the interaction of xanthate with coal pyrite and mineral pyrite surfaces V.M. Browne, A.F. Carley, R.G. Cop-	47 (1991) 355	Oelhafen, In situ electron spectros- copy on polymeric films prepared by RF plasma polymerization: styrene and hydrogen/styrene gas mixtures as	
treatment of the polymer surface pre- ceding the metal deposition S.U.M. Khan, J.P. Baltrus, R.W. Lai and A.G. Richardson, X-ray photoelectron	47 (1991) 323	Electrical and optical properties of a- luminum-doped amorphous silicon carbide films  S. Schelz, J. Eitle, R. Steiner and P.	48/49 (1991) 288

41/42 (1989) 184

41/42 (1989) 443

41/42 (1989) 572

44 (1990) 165

46 (1990) 245

46 (1990) 352

47 (1991) 235

Plasma pi	rocessing
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- Y. Gekka, M. Saitoh, K. Ohga, Y. Akaida and M. Akimoto, Electrical characteristics of metal contacts on the surfaces of a-Si:H films annealed at low temperature
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and hydrogen/styrene gas mixtures as process gasesS. Kishida, H. Tokutaka, H. Higashi, K. Nishimori and N. Ishihara, Prepara-

Nishimori and N. Ishihara, Preparation conditions of flat 80 K phase Bi-Sr-Ca-Cu-O thin films by RF magnetron sputtering

T. Yamashina and T. Hino, Plasmasurface interactions of graphite as nuclear fusion material

41/42 (1989) 429 D.M. Mattox, Surface effects in reactive ion plating

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H.P. Zappe and G. Kaufel, Reactive-ionetch damage in GaAs processing evaluated by a microwave absorption technique

A.W.R. Leitch, Th. Prescha and M. Stutzmann, Hydrogen passivation and reactivation of shallow Zn acceptors in GaAs

### 46 (1990) 435 Platinum

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47 (1991) 323 M. Bowker and D. Halstead, Adsorption studies on catalysts. II. Application to rapid adsorbers – oxygen on Europlatinum 1

48/49 (1991) 104

R. Ducros and J. Fusy, Oxygen adsorption on Pt(110)(1 × 2). Surface characterization by photoemission of adsorbed xenon (PAX)

M.J. van Staden and J.P. Roux, Surface segregation in the alloys Fe40Cr3Ru, Fe40Cr3Pt and Fe40Cr with a 1000 Å Pt overlayer 48/49 (1991) 361

48/49 (1991) 446

48/49 (1991) 483

48/49 (1991) 540

50 (1991) 165

50 (1991) 191

50 (1991) 281

50 (1991) 290

50 (1991) 390

43 (1989) 61

43 (1989) 68

44 (1990) 1

44 (1990) 59

44 (1990) 271

W. Unger, G. Lietz, H. Lieske and J.		R. Braun, R. Nowak, P. Hess, H. Oetz-	
Völter, SIMS and FAB-MS surface		mann and C. Schmidt, Photoablation	
studies of Pt-Sn/Al <sub>2</sub> O <sub>3</sub> and Pt <sub>3</sub> Pb model catalysts	45 (1990) 29	of polyimide with IR and UV laser radiation	43 (1989) 352
S. Deckers, F.H.P.M. Habraken, W.F. van	43 (1990) 29	S. Kuniyoshi, K. Kudo and K. Tanaka,	43 (1909) 332
der Weg, A.W. Denier van der Gon,		Surface modification of low density	
J.F. van der Veen and J.W. Geus,		polyethylene by N <sup>+</sup> , Ar <sup>+</sup> ion implan-	
Oxidation-induced segregation at the		tation for space charge devices	43 (1989) 447
Pt <sub>0.5</sub> Ni <sub>0.5</sub> (111) surface studied by		K.J. Hook, T.J. Hook, J.H. Wandass and	(2,0,)
medium-energy ion scattering	45 (1990) 121	J.A. Gardella, Jr., Secondary ion for-	
S. Deckers, F.H.P.M. Habraken, W.F. van	(2220) 222	mation from functional polymer sys-	
der Weg and J.W. Geus, Oxidation of		tems in static secondary ion mass	
clean and Pt-covered Ni(111)	45 (1990) 207	spectrometry	44 (1990) 29
D. Braichotte, C. Garrido and H. van den	( , , , , , , , , , , , , , , , , , , ,	S. Akhter, K.C. Cannon and J.M. White,	
Bergh, The photolytic laser chemical		Distribution of compositional defects	
vapor deposition rate of platinum, its		in solvent cast polyvinyl alcohol films:	
dependence on wavelength, precursor		angular dependent XPS and reactivity	
vapor pressure, light intensity, and		study	44 (1990) 49
laser beam diameter	46 (1990) 9	A.J. Pertsin and Yu.M. Pashunin, Dif-	
G. Radhakrishnan, W. Stenzel, H. Con-		ferential charging in XPS studies of	
rad and A.M. Bradshaw, Photoreac-		polymer/metal interfaces	44 (1990) 171
tions of adsorbed CH <sub>3</sub> Br on Pt(111)	46 (1990) 36	M. Wolpers, H. Viefhaus and M. Strat-	
R. Kötz, Ultraviolet photoelectron spec-		mann, SEM and SAM imaging of	
troscopy (UPS) of anodic oxide films		silane LB films on metallic substrates	45 (1990) 167
on Au, Pt, Ru and Ru <sub>0.5</sub> Ir <sub>0.5</sub> alloy	47 (1991) 109	D.E. King, J.E. Fernandez and W.E.	
D. Vassilakis, CM. Pradier, Y. Berthier		Swartz, An XPS study of the doping	
and J. Oudar, Hydrogen, hydrogen		of trans, trans-p-distyrylbenzene with	
sulfide and hydrocarbon coadsorption		AsF <sub>5</sub> : a model conducting polymer	
on Pt(111) and Pt(110): selective for-		system	45 (1990) 325
mation of alkylthiols	47 (1991) 273	A. Bauer, J. Ganz, K. Hesse and E.	
M. Muhler, Z. Paál and R. Schlögl, XPS		Köhler, Laser-assisted deposition for	
of platinum in Pt/SiO <sub>2</sub> (Europt-1):		electronic packaging applications	46 (1990) 113
possibilities and limitations of the		H. Hiraoka and S. Lazare, Surface mod-	
method	47 (1991) 281	ifications of Kapton and cured poly-	
H.H. Madden and R. Imbihl, Interaction		imide films by ArF excimer laser: ap-	
of NO and H <sub>2</sub> with Pt(100)	48/49 (1991) 130	plications to imagewise wetting and	
D.G. Frank, T. Golden, O.M.R. Chyan		metallization	46 (1990) 264
and A.T. Hubbard, Direct imaging		G. Ulmer, B. Hasselberger, HG. Bus-	
of thin film atomic structure by an-		mann and E.E.B. Campbell, Excimer	46 (1000) 070
gular distribution Auger microscopy	10 /10 /1001 1 / /	laser ablation of polyimide	46 (1990) 272
(ADAM)	48/49 (1991) 166	W. Kesting, T. Bahners and E. Scholl-	
D 4		meyer, Controlled structuring of poly-	46 (1000) 226
Polymers		mer surfaces by UV-laser irradiation	46 (1990) 326
DC II Cl		J. Davenas, G. Boiteux, J.M. Bureau and	
P.S. Ho, Chemistry and adhesion of	41 /42 (1000) 550	D. Broussoux, Ion-beam-assisted for-	
metal-polymer interfaces	41/42 (1989) 559	mation of interconnections into high	46 (1990) 330
J. Davenas, Influence of the temperature		temperature polymers	46 (1990) 330
on the ion beam induced conductivity	42 (1000) 210	J. Breuer, S. Metev, G. Sepold, OD.	
of polyimide	43 (1989) 218	Hennemann, H. Kollek and G. Krüger,	
G. Compagnini, R. Reitano, L. Calcagno,		Laser-induced photochemical ad- herence enhancement	46 (1990) 336
G. Marletta and G. Foti, Hydro- genated amorphous carbon synthesis		H. Hiraoka and S. Lazare, Applications	40 (1990) 330
by ion beam irradiation	43 (1989) 228	of doping and dedoping of Teflon AF	
E.E.B. Campbell, G. Ulmer, B. Hassel-	73 (1707) 220	films in microfabrication using KrF	
berger and I.V. Hertel, Investigation		and ArF excimer lasers	46 (1990) 342
of positive and negative ionic products		Fu-Ming Pan, Yuh-Lin Lin and Shean-	(2773) 512
from laser ablation of polymers	43 (1989) 346	Ren Horng, Decomposition of perflu-	
The same of polymone	(2.02) 0.0	O,	

oropolyethers during XPS measure- ments	47 (1991) 9	<ul><li>A. Claverie, C. Vieu and J. Beauvillain,</li><li>3D simulations of ion implantation</li></ul>	
B. Heens, Ch. Grégoire, J.J. Pireaux, P.A. Cornelio and J.A. Gardella, Jr., On the stability and homogeneity of		processes  D.C. Kothari and A. Miotello, Effects on the implanted profiles of point defect	43 (1989) 106
Langmuir-Blodgett films as models of polymers and biological materials for surface studies: an XPS study	47 (1991) 163	flux during nitrogen implantation in copper  B.L. Chen, M. Eckstein and HU.	43 (1989) 237
B.R. Strohmeier, Evaluation of polymeric standard reference materials for moni- toring the performance of X-ray pho-		Habermeier, Cathodoluminescence investigations of RIE-induced defects in InP	50 (1991) 191
toelectron spectrometers  E. Occhiello, M. Morra, F. Garbassi, D. Johnson and P. Humphrey, SSIMS	47 (1991) 225	J. Tatarkiewicz, A. Kozanecki, Z. Kaliń- ski and K. Paprocki, Photolumines- cence study of proton-implanted	
studies of hydrophobic recovery: oxy- gen plasma treated PS S. Hashimoto, XPS and AES studies on	47 (1991) 235	InP <sub>1-x</sub> As <sub>x</sub> :Yb G.M. Crean, P.A.F. Herbert, I. Little, W.M. Kelly, J.Y. Marzin, A. Izrael	50 (1991) 249
the interface between metal and poly- mer layers. The effect of Ar-plasma		and B. Jusserand, Investigation of re- active ion etch-induced damage in InP	
treatment of the polymer surface preceding the metal deposition  S. Schelz, J. Eitle, R. Steiner and P.	47 (1991) 323	surfaces using a noncontact photo- thermal radiometric probe H.P. Zappe and G. Kaufel, Reactive-ion-	50 (1991) 281
Oelhafen, In situ electron spectros- copy on polymeric films prepared by RF plasma polymerization: styrene		etch damage in GaAs processing evaluated by a microwave absorption technique	50 (1991) 290
and hydrogen/styrene gas mixtures as process gases	48/49 (1991) 301	H.W. Dinges, B. Kempf, H. Burkhard and R. Göbel, Determination of ion beam etching damage on InP by spec-	50 (1001) 250
Quantum effects		troscopic ellipsometry	50 (1991) 359
Y.L. Jiang and H.L. Hwang, Electron		Raman scattering	
transport in hydrogenated amorphous	49 /40 /1001\ 202		
silicon quantum wells  B. Deveaud, Subpicosecond luminescence	48/49 (1991) 392	N. Esser, M. Hünermann, U. Resch, D.	
spectroscopy of heterostructures (Ex-		Spaltmann, J. Geurts, D.R.T. Zahn, W. Richter and R.H. Williams, Bis-	
tended Abstract)  J.F. Donegan, J.P. Doran, R.P. Stanley, J.  Hegarty, R.D. Feldman and R.F.	50 (1991) 63	Spaltmann, J. Geurts, D.R.T. Zahn,	
tended Abstract)  J.F. Donegan, J.P. Doran, R.P. Stanley, J.		Spaltmann, J. Geurts, D.R.T. Zahn, W. Richter and R.H. Williams, Bismuth on GaAs(110): characterisation of growth mode and Schottky barrier formation at low and room temperature  M. Yano, M. Ashida, Y. Iwai and M.	41/42 (1989) 169
tended Abstract)  J.F. Donegan, J.P. Doran, R.P. Stanley, J.  Hegarty, R.D. Feldman and R.F.  Austin, Resonant Rayleigh scattering from excitons in Cd <sub>x</sub> Zn <sub>1-x</sub> Te:ZnTe	50 (1991) 63 50 (1991) 321	<ul> <li>Spaltmann, J. Geurts, D.R.T. Zahn, W. Richter and R.H. Williams, Bismuth on GaAs(110): characterisation of growth mode and Schottky barrier formation at low and room temperature</li> <li>M. Yano, M. Ashida, Y. Iwai and M. Inoue, Characteristic properties of III-V<sub>A</sub>/III-V<sub>B</sub> heterointerfaces grown by molecular beam epitaxy</li> </ul>	41/42 (1989) 169 41/42 (1989) 457
tended Abstract)  J.F. Donegan, J.P. Doran, R.P. Stanley, J.  Hegarty, R.D. Feldman and R.F.  Austin, Resonant Rayleigh scattering from excitons in $Cd_xZn_{1-x}Te$ :ZnTe quantum wells: measurement of homogeneous linewidths  B. Meyer, P. Omling and P. Emanuelsson,		<ul> <li>Spaltmann, J. Geurts, D.R.T. Zahn, W. Richter and R.H. Williams, Bismuth on GaAs(110): characterisation of growth mode and Schottky barrier formation at low and room temperature</li> <li>M. Yano, M. Ashida, Y. Iwai and M. Inoue, Characteristic properties of III-V<sub>A</sub>/III-V<sub>B</sub> heterointerfaces grown by molecular beam epitaxy</li> <li>C. López, J. Sánchez-Dehesa, F. Meseguer, F. Borondo and K. Ploog, Electronic structure of modulation n-</li> </ul>	41/42 (1989) 457
tended Abstract)  J.F. Donegan, J.P. Doran, R.P. Stanley, J.  Hegarty, R.D. Feldman and R.F.  Austin, Resonant Rayleigh scattering from excitons in Cd <sub>x</sub> Zn <sub>1-x</sub> Te:ZnTe quantum wells: measurement of homogeneous linewidths  B. Meyer, P. Omling and P. Emanuelsson, Landau oscillations in single quantum wells observed by microwave detec-	50 (1991) 321	<ul> <li>Spaltmann, J. Geurts, D.R.T. Zahn, W. Richter and R.H. Williams, Bismuth on GaAs(110): characterisation of growth mode and Schottky barrier formation at low and room temperature</li> <li>M. Yano, M. Ashida, Y. Iwai and M. Inoue, Characteristic properties of III-V<sub>A</sub>/III-V<sub>B</sub> heterointerfaces grown by molecular beam epitaxy</li> <li>C. López, J. Sánchez-Dehesa, F. Meseguer, F. Borondo and K. Ploog, Electronic structure of modulation ndoped multiple quantum well</li> <li>D.R.T. Zahn, W. Richter, T. Eickhoff, J. Geurts, T.D. Golding, J.H. Dinan, K.J.</li> </ul>	
tended Abstract)  J.F. Donegan, J.P. Doran, R.P. Stanley, J. Hegarty, R.D. Feldman and R.F. Austin, Resonant Rayleigh scattering from excitons in Cd <sub>x</sub> Zn <sub>1-x</sub> Te:ZnTe quantum wells: measurement of ho- mogeneous linewidths  B. Meyer, P. Omling and P. Emanuelsson, Landau oscillations in single quantum wells observed by microwave detec- tion  Radiation damage  N. Hecking and E.H. te Kaat, Modelling of lattice damage accumulation during	50 (1991) 321 50 (1991) 420	<ul> <li>Spaltmann, J. Geurts, D.R.T. Zahn, W. Richter and R.H. Williams, Bismuth on GaAs(110): characterisation of growth mode and Schottky barrier formation at low and room temperature</li> <li>M. Yano, M. Ashida, Y. Iwai and M. Inoue, Characteristic properties of III-V<sub>A</sub>/III-V<sub>B</sub> heterointerfaces grown by molecular beam epitaxy</li> <li>C. López, J. Sánchez-Dehesa, F. Meseguer, F. Borondo and K. Ploog, Electronic structure of modulation ndoped multiple quantum well</li> <li>D.R.T. Zahn, W. Richter, T. Eickhoff, J. Geurts, T.D. Golding, J.H. Dinan, K.J. Mackey and R.H. Williams, The influence of Cd overpressure in the molecular beam epitaxy of InSb/CdTe</li> </ul>	41/42 (1989) 457
tended Abstract)  J.F. Donegan, J.P. Doran, R.P. Stanley, J. Hegarty, R.D. Feldman and R.F. Austin, Resonant Rayleigh scattering from excitons in Cd <sub>x</sub> Zn <sub>1-x</sub> Te:ZnTe quantum wells: measurement of ho- mogeneous linewidths  B. Meyer, P. Omling and P. Emanuelsson, Landau oscillations in single quantum wells observed by microwave detec- tion  Radiation damage  N. Hecking and E.H. te Kaat, Modelling	50 (1991) 321	<ul> <li>Spaltmann, J. Geurts, D.R.T. Zahn, W. Richter and R.H. Williams, Bismuth on GaAs(110): characterisation of growth mode and Schottky barrier formation at low and room temperature</li> <li>M. Yano, M. Ashida, Y. Iwai and M. Inoue, Characteristic properties of III-V<sub>A</sub>/III-V<sub>B</sub> heterointerfaces grown by molecular beam epitaxy</li> <li>C. López, J. Sánchez-Dehesa, F. Meseguer, F. Borondo and K. Ploog, Electronic structure of modulation ndoped multiple quantum well</li> <li>D.R.T. Zahn, W. Richter, T. Eickhoff, J. Geurts, T.D. Golding, J.H. Dinan, K.J. Mackey and R.H. Williams, The influence of Cd overpressure in the</li> </ul>	41/42 (1989) 457

scattering of ZnTe epitaxial layer de-		B.H. Bairamov, V.A. Voitenko, I.P.	
posited on GaAs	41/42 (1989) 522	Ipatova, V.V. Toporov, G. Irmer, J.	
T. Takeuchi, C. Maezawa, T. Nomura, K.		Monecke and E. Jahne, Characteriza-	
Ishikawa, M. Miyao and M. Hagino,		tion of III-V compounds by quasi-	
Raman study of strain distribution in		elastic electronic scattering of light	50 (1991) 300
interface region of GaAs/GaP hetero-	*	A. Deneuville, C.H. Park, P. Ayyub, T.	
epitaxial layers grown by MBE	41/42 (1989) 530	Anderson, P. Lowen, K. Jones and	
H. Okumura, K. Miki, K. Sakamoto, T.		P.H. Holloway, O implantation in	
Sakamoto, K. Endo and S. Yoshida, Raman scattering and photolumines-		ZnSe: lattice distortion by Raman measurement	50 (1001) 209
cence characterization of Ge/Si		G.M. O'Connor, C.J. McDonagh, F.G.	50 (1991) 308
strained-layer superlattices grown by		Anderson, T.J. Glynn, G.P. Morgan,	
phase-locked epitaxy	41/42 (1989) 548	G.J. Hughes, L. Roberts and M.O.	
K. Iizuka, T. Yoshida, M. Hasobe, I.	, - ( ,	Henry, Raman characterization of	
Matsuda and T. Suzuki, Raman study		passivated GaAs surfaces	50 (1991) 312
of the stress in MBE-grown Alx		B. Jusserand and F. Mollot, Confined	
$Ga_{1-x}As$ on $Si$	41/42 (1989) 587	optical vibrations: a new probe for	
C.N. Afonso, R. Serna, F. Catalina and		alloy disorder	50 (1991) 317
D. Bermejo, Good-quality Ge films	46 (1000) 240	S.C. Moss, J.F. Knudsen, R.C. Bowman,	
grown by excimer laser deposition M. Elliq, E. Fogarassy, J.P. Stoquert, C.	46 (1990) 249	Jr., P.M. Adams and D.D. Smith, Pi- cosecond transient photoreflectance	
Fuchs, S. de Unamuno, B. Prévot and		measurements of ion-implanted GaAs	50 (1991) 337
H. Pattyn, Pulsed excimer and		C. Raisin, A. Rocher, G. Landa, R. Carles	30 (1771) 337
Nd:YAG laser crystallization of a-		and L. Lassabatere, GaSb/GaAs het-	
Si:H. The specific role of hydrogen	46 (1990) 378	eroepitaxy characterized as a stress-	
C. Julien and M. Balkanski, Thin-film		free system	50 (1991) 434
growth and structure for solid-state			
batteries	48/49 (1991) 1	Raman spectroscopy	
Y. Matsuda, K. Fujita and S. Hinotani,			
Raman studies on GaAs epitaxial films	48/49 (1991) 231	P.V. Huong, O. Segond, P. Gentilini and	
on Si A. Mansour, G. Indlekofer and P. Oelha-	46/49 (1991) 231	R. Cavagnat, Silicon aggregates pro-	
fen, Investigation of the electronic		duced by laser beam in a silicon	42 (1000) 256
structure of thin diamond films by		carbide surface	43 (1989) 256
photoelectron spectroscopy	48/49 (1991) 312	D. A:	
S.C. Jain, A. Atkinson and W.S. Khokle,		Reflection spectroscopy	
Relationship between mechanical,		M Ellia E Eggaragey ID Staguert C	
electronic and vibrational properties		M. Elliq, E. Fogarassy, J.P. Stoquert, C. Fuchs, S. de Unamuno, B. Prévot and	
of $Ge_xSi_{1-x}$ strained layers	48/49 (1991) 387	H. Pattyn, Pulsed excimer and	
G. Abstreiter, Micro-Raman spectroscopy for characterization of semiconductor		Nd:YAG laser crystallization of a-	
devices	50 (1991) 73	Si:H. The specific role of hydrogen	46 (1990) 378
J. Wagner, Raman spectroscopy for im-	30 (1771) 73	K. Jezierski, Z. Gumienny and J. Mis-	
purity characterization in III-V semi-		iewicz, Reflectometry-aided surface	
conductors	50 (1991) 79	layer investigation	50 (1991) 341
G.M. Crean, P.A.F. Herbert, I. Little,		A. Dimoulas, A. Derekis, G. Kyriakidis	
W.M. Kelly, J.Y. Marzin, A. Izrael		and A. Christou, Alloy disorder ef-	
and B. Jusserand, Investigation of re-		fects in III-V ternaries studied by modulation spectroscopy	50 (1991) 353
active ion etch-induced damage in InP		modulation spectroscopy	30 (1991) 333
surfaces using a noncontact photo-	50 (1001) 201	Rhenium	
thermal radiometric probe  B. Boudart, B. Prévot and C. Schwab,	50 (1991) 281	Michiani	
Free-carrier concentration in n-doped		D.R. Baer, R.L. Gordon and C.W. Hub-	
InP crystals determined by Raman		bard, Work function and UPS study	
scattering measurements	50 (1991) 295	of Au and O on Re	45 (1990) 71

Rhodium		of silicide/silicon Schottky barrier	
		heights	41/42 (1989) 159
J.H. Craig, Jr. and J. Lozano, Effect of oxygen on chemisorption of CO on		H. Fujitani and S. Asano, Electronic structure of Si/disilicide interfaces	41/42 (1989) 164
Rh(100)	45 (1990) 151	N. Esser, M. Hünermann, U. Resch, D. Spaltmann, J. Geurts, D.R.T. Zahn,	
W.G. Durrer, J.H. Craig, Jr. and J.		W. Richter and R.H. Williams, Bis-	
Lozano, Surface carbon and its effects	45 (1990) 275	muth on GaAs(110): characterisation	
on hydrogen adsorption on Rh(100)	43 (1990) 273	of growth mode and Schottky barrier	
Ruthenium		formation at low and room tempera-	41 /42 (1090) 160
Rumemum		K. Hirose, H. Tsuda and T. Mizutani,	41/42 (1989) 169
S.C. Tjong, Electrochemical and surface		Control of the Al/GaAs Schottky	
analysis of the Fe-Cr-Ru system in		barrier height using a rare-earth metal	
non-oxidizing acid solutions	44 (1990) 7	interlayer	41/42 (1989) 174
M.J. van Staden and J.P. Roux, The su-		Y. Gekka, M. Saitoh, K. Ohga, Y. Akaida	, , , ,
perposition of carbon and ruthenium		and M. Akimoto, Electrical character-	
Auger spectra	44 (1990) 259	istics of metal contacts on the surfaces	
R. Kötz, Ultraviolet photoelectron spec-		of a-Si:H films annealed at low tem-	
troscopy (UPS) of anodic oxide films		perature	41/42 (1989) 184
on Au, Pt, Ru and Ru <sub>0.5</sub> Ir <sub>0.5</sub> alloy	47 (1991) 109	R.H. Williams, N. Forsyth, I.M. Dhar-	
P.J. Godowski, Analysis of surface segre-		madasa and Z. Sobiesierski, Metal	
gation in Co-Ru alloy using Auger	47 (1001) 222	contacts to II-VI semiconductors:	41 /42 /1000\ 100
electron spectroscopy	47 (1991) 333	CdS and CdTe	41/42 (1989) 189
K. Kalki, B. Pennemann, U. Schröder, W. Heichler and K. Wandelt, Properties		H. Sugahara and J. Nagano, Thermal sta- bility of WSiN-GaAs and Au-WSiN	
of noble metal and binary alloy mono-		interfaces	41/42 (1989) 207
layer films on Ru(001)	48/49 (1991) 59	G. Myburg, J.B. Malherbe and E. Fried-	41/42 (1909) 207
myer mine on rea(eer)	10/ 12 (2222) 22	land, Electrical characteristics of ion	
Sahattley hamian		bombarded Ni/n-Si Schottky contacts	43 (1989) 242
Schottky barrier		T. Hibma, H.H. Weitering, D.R. Heslinga	
W.E. Crisco P. Coo V. Misson T.		and T.M. Klapwijk, Interface struc-	
W.E. Spicer, R. Cao, K. Miyano, T. Kendelewicz, I. Lindau, E. Weber, Z.		ture and Schottky barriers of epitaxial	
Liliental-Weber and N. Newman,		Pb on Si(111)	48/49 (1991) 209
From synchrotron radiation to $I-V$		A. Diarra, S. Hotchandani, H. Kassi and	
measurements of GaAs Schottky bar-		R.M. Leblanc, Capacitance character-	
rier formation	41/42 (1989) 1	istics of mixed monolayers of chloro- phyll a and carotenoid canthaxanthin	40 (40 (1001) 567
M.H. Hecht, L.D. Bell and W.J. Kaiser,		C. Ghezzi, R. Mosca, A. Bosacchi, S.	48/49 (1991) 567
Ballistic-electron-emission microscopy		Franchi and E. Gombia, The influence	
of subsurface defects at the Au-		of the DX center on the capacitance	
GaAs(100) interface	41/42 (1989) 17	of Schottky barriers in n-type AlGaAs	50 (1991) 400
W. Mönch, Mechanisms of barrier forma-		L. Roberts and G.J. Hughes, An investi-	(2,1,2)
tion in Schottky contacts: metal-in-	41 (42 (1000) 100	gation of metal/GaAs(100) interfaces	
duced surface and interface states	41/42 (1989) 128	by deep level transient spectroscopy	50 (1991) 424
D.W. Niles, M. Tang, J. McKinley, R.		L.J. Bredell, F.D. Auret, G. Myburg and	
Zanoni and G. Margaritondo, From heterojunction interfaces to metal-		W.O. Barnard, Electrical characteriza-	
semiconductor interfaces	41/42 (1989) 139	tion of argon-ion sputtered n-GaAs	50 (1991) 466
F. Fiores, A. Muñoz and J.C. Durán,	41/ 42 (1909) 199		
Semiconductor interface formation:		Secondary ion mass spectuages	
the role of the induced density of in-		Secondary ion mass spectroscopy	
terface states	41/42 (1989) 144		
R. Ludeke, A. Taleb-Ibrahimi and G.		M. Murakami, H.J. Kim, YC. Shih, W.H.	
Jezequel, Delocalization of defects: a		Price and C.C. Parks, Effects of inter-	
new model for the Schottky barrier	41/42 (1989) 151	facial microstructure on ohmic con-	
J.H. Werner, H. von Känel, G. Markewitz		tacts to GaAs	41/42 (1989) 195
and R.T. Tung, Pressure dependences		H. Sugahara and J. Nagano, Thermal sta-	

hility of WSIN Co.Ac and An WSIN		comiconductors, double and Cilina of	
bility of WSiN-GaAs and Au-WSiN interfaces	41/42 (1989) 207	semiconductors: depth profiling of homo- and heterostructure	50 (1991) 42
S. Ogawa, T. Yoshida, T. Kouzaki, S.	41/42 (1909) 207	Y. Gao, I. Ardelean, D. Renard, B. Rose	30 (1991) 42
Okuda and K. Tsukamoto, Thermal		and Y. Jin, High-depth-resolution	
instability of the TiSi2/Si structure:		SIMS analysis for InGaAs/InP inter-	
impurity effects	41/42 (1989) 290	faces	50 (1991) 131
Y. Kamiura, F. Hashimoto and M. Iwami,		J.G. Bauer, R. Treichler, T. Hillmer, J.	
Iron accumulation at the Si-SiO2 in-		Müller and G. Ebbinghaus, Optimiza-	
terface and possible reduction of SiO <sub>2</sub>	41/42 (1989) 447	tion of Zn dopant profiles in a pin-di-	
K.J. Hook, T.J. Hook, J.H. Wandass and		ode/FET by combination of depth	
J.A. Gardella, Jr., Secondary ion for-		profiling techniques: a SIMS, ECV	
mation from functional polymer sys-		and AES study	50 (1991) 138
tems in static secondary ion mass		H. L'Haridon, P.N. Favennec, R. Co-	
spectrometry	44 (1990) 29	quille, M. Salvi, M. Gauneau, Y. Le	
W. Unger, G. Lietz, H. Lieske and J.		Guillou, R. Callec and P. Gall, Spatial	
Völter, SIMS and FAB-MS surface		investigation of an iron-doped indium	
studies of Pt-Sn/Al <sub>2</sub> O <sub>3</sub> and Pt <sub>3</sub> Pb		phosphide ingot	50 (1991) 237
model catalysts	45 (1990) 29	P.L. Swart, B.M. Lacquet and R. Thavar,	
J. Lausmaa, B. Kasemo, H. Mattsson and		Physical characterization of OMVPE-	
H. Odelius, Multi-technique surface		grown $Al_xGa_{1-x}As$ multi-layer films	
characterization of oxide films on		by means of non-destructive optical	50 (1001) 220
electropolished and anodically oxi-	45 (1000) 100	reflectometry	50 (1991) 330
dized titanium  G. Stock D. Bollmann B. Buchner G.	45 (1990) 189	D. Lee, S.J. Barnett, A.D. Pitt, M.R.	
G. Stock, D. Bollmann, R. Buchner, G. Neumayer and K. Haberger, Ultra-flat		Houlton and G.W. Smith, Characterization of allow composition in	
p-n junctions formed by solid source		zation of alloy composition in $Ga_{1-x}Al_xAs/GaAs$ structures: com-	
laser doping	46 (1990) 348	parison of photovoltage, X-ray, SIMS	
D. Ballutaud, P. de Mierry, M. Aucoutu-	40 (1990) 340	and RHEED techniques	50 (1991) 428
rier and E. Darque-Ceretti, Influence		V. Amarger, C. Dubon-Chevallier, A.C.	30 (1991) 420
of thermal treatments on the distribu-		Papadopoulo, B. Descouts and Y. Gao,	
tion of contaminating copper near the		Correlated use of characterization	
surface of silicon: a comparative SIMS		techniques to optimize the Mg implan-	
and XPS study	47 (1991) 1	tation annealing for self-aligned HBT's	50 (1991) 462
E. Occhiello, M. Morra, F. Garbassi, D.		P. Roura, J.R. Morante, G. Bremond, T.	, ,
Johnson and P. Humphrey, SSIMS		Benyattou, G. Guillot and W. Ulrici,	
studies of hydrophobic recovery:		Complete identification of the Ti-re-	
oxygen plasma treated PS	47 (1991) 235	lated levels in GaP	50 (1991) 496
G.N. Pain, T. Warminski, S. Sulcs, M.S.			
Kwietniak, D. Gao, S.R. Glanvill, C.J.			
Rossouw, A.W. Stevenson, S.P. Russo,		Second harmonic generation	
R.G. Elliman, L.S. Wielunski, R.S.			
Rowe, G.B. Deacon, R.S. Dickson and			
B.O. West, Characterization of low-		F.J. Himpsel, T.F. Heinz, A.B. McLean	
temperature MOCVD $Cd_{1-x}Mn_xTe$	40 440 440045 = 5	and E. Palange, Bonding at silicon/in-	44 440 44 0000 044
thin films	48/49 (1991) 76	sulator interfaces	41/42 (1989) 346
M. Arienzo, S.S. Iyer, B.S. Meyerson, G.L.		M.E. Pemble, J.T. Allen, D.S. Buhaenko,	
Patton and J.M.C. Stork, Si-Ge al-		S.M. Francis, P.A. Goulding, J. Lee	
loys: growth, properties and applica-	49 /40 /1001) 277	and M.J. Parrott, The adsorption of	
tions	48/49 (1991) 377	triethylgallium on GaAs(100) at 300	
A. Hishinuma, T. Goda, M. Kitaoka, S. Hayashi and H. Kawahara, Formation		K: adsorption kinetics from optical second harmonic generation transients	46 (1990) 32
of silicon dioxide films in acidic solu-		J. Heidberg, B. Brase, KW. Stahmer and	40 (1990) 32
tions	48/49 (1991) 405	M. Suhren, Second harmonic genera-	
C. Grattepain and A.M. Huber, Sec-	10/ 17 (1771) 403	tion of CO <sub>2</sub> -laser radiation and FTIR	
ondary ion mass spectrometry of		spectroscopy for resonant desorption	
dopants and impurities in compound		in the adsorbate CO-NaCl(100)	46 (1990) 44
			(====)

### Selenium

Selenium		fluence of Cd overpressure in the	
A. Jadin, I.V. Filiouguine, M. Wautelet and L.D. Laude, Influence of the sub- strate on the temperature induced by		molecular beam epitaxy of InSb/CdTe heterostructures: a combined Raman and infrared spectroscopy study S.K. De Figueiredo and A.C. Ferraz, In-	41/42 (1989) 497
pulsed laser irradiation of thin films K. Kolev, M. Wautelet and L.D. Laude, CW laser-induced transformation of	46 (1990) 375	terface geometry of (GaAs) <sub>n</sub> (InAs) <sub>n</sub> and (GaP) <sub>n</sub> (InP) <sub>n</sub> ultra-thin super- lattices	41/42 (1989) 509
thin Sb, Se and Sb <sub>2</sub> Se <sub>3</sub> films in air C. Julien and M. Balkanski, Thin-film growth and structure for solid-state	46 (1990) 418	T. Nomura, K. Wakatuki, M. Miyao and M. Hagino, Characterization of the GaAs buffer layer grown on GaP by	41 (42 (1000) 512
batteries S. Nagashima, E. Fukuchi and I. Ogura, Growth modes of overlayers of Se de-	48/49 (1991) 1	MBE for the two-step growth method S. Hongo, Y. Kataoka, T. Urano and T. Kanaji, Evaluation by resonant light	41/42 (1989) 512
posited on Cu(111) surfaces C.H. Champness and W.R. Clark, Anomalous inductive effect in Se-	48/49 (1991) 44	scattering of ZnTe epitaxial layer deposited on GaAs  K. Kanamoto, K. Fujiwara, Y. Tokuda,	41/42 (1989) 522
metal contacts  Semiconductors	48/49 (1991) 337	N. Tsukada, M. Ishii and T. Nakaya- ma, Photoluminescence line shape due to arrayed steps at the interfaces of	
B.L. Halpern, J.J. Schmitt, J.W. Golz, Y. Di and D.L. Johnson, Gas jet deposi-		GaAs/AlGaAs single quantum wells grown on vicinal surfaces by molecu- lar beam epitaxy	41/42 (1989) 526
tion of thin films	48/49 (1991) 19	T. Aoyama, T. Sugi and T. Ito, Determination of band line-up in $\beta$ -SiC/Si heterojunction for Si-HBT's	41/42 (1989) 584
Semiconductor – semiconductor inter	faces	H. Horikawa, M. Akiyama, S. Onozawa, Y. Kawai and M. Sakuta, Interfacial	
J. Christen, M. Grundmann and D. Bim- berg, Direct imaging and theoretical modelling of the atomistic morpho-		layers of InP/Si heteroepitaxy J. Morais, A.M. Machado, M.A. Sacilotti and R. Landers, AES sputter depth	41/42 (1989) 598
logical and chemical structure of semi- conductor heterointerfaces H. Hasegawa, H. Ohno, H. Ishii, T. Haga,	41/42 (1989) 329	profiles applied to interface analysis of GaInAs/InP grown by atmospheric pressure MOCVD	44 (1990) 161
Y. Abe and H. Takahashi, Origin and properties of interface states at insulator-semiconductor and semiconduc-		Y. Matsuda, K. Fujita and S. Hinotani, Raman studies on GaAs epitaxial films on Si	48/49 (1991) 231
tor-semiconductor interfaces of com- pound semiconductors  M. Yano, M. Ashida, Y. Iwai and M. Inoue, Characteristic properties of	41/42 (1989) 372	A.J. Nelson, S. Gebhard, L.L. Kazmerski, A. Rockett, E. Colavita, M. En- gelhardt and H. Höchst, Soft X-ray photoemission investigation of the	
by molecular beam epitaxy	41/42 (1989) 457	CdS/CuInSe <sub>2</sub> heterojunction interface	48/49 (1991) 419
Feuillet, K. Saminadayar, A.C. Chami		Y. Hatanaka, Heterostructures with hy- drogenated amorphous silicon for use in imaging devices	48 / 49 (1991) 457
HRTEM and channeling studies of molecular beam epitaxy growth of	41 (42 (1090) 470	H. Mimura and Y. Hatanaka, The current transport mechanism of p-type a-	10, 15 (1551) 151
S. Goto, H. Kakibayashi, M. Kawata and	41/42 (1989) 4/0	their application to an imaging device	48/49 (1991) 472
at low doping concentration in selec- tively Si-doped Al <sub>0.3</sub> Ga <sub>0.7</sub> As/GaAs heterointerfaces	41/42 (1989) 480	tion of heteroepitaxial structures P. Auvray, A. Poudoulec, M. Baudet, B. Guenais, A. Regreny, C. d'Anter-	50 (1991) 9
D.R.T. Zahn, W. Richter, T. Eickhoff, J. Geurts, T.D. Golding, J.H. Dinan, K.J. Mackey and R.H. Williams, The in-		roches and J. Massies, Interface roughness of GaAs/AlAs super-	50 (1991) 109
<ul> <li>M. Yano, M. Ashida, Y. Iwai and M. Inoue, Characteristic properties of III-V<sub>A</sub>/III-V<sub>B</sub> heterointerfaces grown by molecular beam epitaxy</li> <li>S. Tatarenko, J. Cibert, Y. Gobil, G. Feuillet, K. Saminadayar, A.C. Chami and E. Ligeon, RHEED, XPS, HRTEM and channeling studies of molecular beam epitaxy growth of CdTe on (001) GaAs</li> <li>S. Goto, H. Kakibayashi, M. Kawata and T. Usagawa, Evaluation of disordering at low doping concentration in selectively Si-doped Al<sub>0.3</sub>Ga<sub>0.7</sub>As/GaAs heterointerfaces</li> <li>D.R.T. Zahn, W. Richter, T. Eickhoff, J. Geurts, T.D. Golding, J.H. Dinan, K.J.</li> </ul>	41/42 (1989) 457 41/42 (1989) 470	gelhardt and H. Höchst, Soft X-ray photoemission investigation of the CdS/CuInSe <sub>2</sub> heterojunction interface  Y. Hatanaka, Heterostructures with hydrogenated amorphous silicon for use in imaging devices  H. Mimura and Y. Hatanaka, The current transport mechanism of p-type a-Si:H/n-type c-Si heterojunctions and their application to an imaging device  P.F. Fewster, Multicrystal X-ray diffraction of heteroepitaxial structures  P. Auvray, A. Poudoulec, M. Baudet, B. Guenais, A. Regreny, C. d'Anterroches and J. Massies, Interface	48/49 (1991) 457 48/49 (1991) 472

Y. Gao, I. Ardelean, D. Renard, B. Rose		Veuillen, Heteroepitaxy of metallic	
and Y. Jin, High-depth-resolution		and semiconducting silicides on sili-	
SIMS analysis for InGaAs/InP inter-	EO (1001) 121	con	41/42 (1989) 241
faces J.S. Rimmer, M. Missous and A.R. Peaker,	50 (1991) 131	L. Haderbache, P. Wetzel, C. Pirri, J.C. Peruchetti, D. Bolmont and G.	
A new, fast method for the computer		Gewinner, Identification of three dis-	
simulation of CV profiles in multi-		tinct $CoSi_2(111)(1 \times 1)$ surface struc-	
layer structures	50 (1991) 149	tures	41/42 (1989) 257
B. Jusserand and F. Mollot, Confined	()	M. Itoh, M. Kinoshita, T. Ajioka, M. Itoh	12/ 12 (2202) 201
optical vibrations: a new probe for		and T. Inada, Crystalline quality of	
alloy disorder	50 (1991) 317	heteroepitaxial silicon on epitaxial	
D.A. Woolf, D.I. Westwood, M.A. Ander-		NiSi <sub>2</sub> /Si(100)	41/42 (1989) 262
son and R.H. Williams, The molecular		T.A. Nguyen Tan, N. Guerfi, J.Y. Veuil-	
beam epitaxial growth of GaAs(111)/		len and J. Derrien, Oxidation of TaSi <sub>2</sub>	
Si(111): a variable growth temperature		thin films on polycrystalline Si	41/42 (1989) 266
study	50 (1991) 445	N. Fujimura and T. Ito, TiSi <sub>2</sub> formation	
		at the Ti-rich TiN <sub>x</sub> /Si interface	41/42 (1989) 272
Silane		K. Suguro, Y. Nakasaki, T. Yoshii and T.	
Situite		Itoh, Barrier metal between tungsten and silicon for high temperature	
		processing	41/42 (1989) 277
E. Boch, C. Fuchs, E. Fogarassy and P.		Y. Igarashi, T. Yamaji, S. Nishikawa and	41/ 42 (1707) 277
Siffert, Influence of dilution in nitro-		S. Ohno, Influence of annealing am-	
gen on the photodissociation processes	40.44000 4.7	bients on ZrSi <sub>2</sub> formation	41/42 (1989) 282
of silane and disilane at 193 nm	43 (1989) 17	N. Fujimura, S. Tachibana and T. Ito,	
R. Fantoni, E. Borsella, S. Piccirillo, C.A.		Characterization of Si-rich WSi, on Si	41/42 (1989) 286
Nannetti, R. Ceccato and S. Enzo, Laser assisted synthesis of ultrafine		S. Ogawa, T. Yoshida, T. Kouzaki, S.	
silicon powder	43 (1989) 308	Okuda and K. Tsukamoto, Thermal	
R.M. Wallace, C.C. Cheng, P.A. Taylor,	45 (1707) 500	instability of the TiSi <sub>2</sub> /Si structure:	
W.J. Choyke and J.T. Yates, Jr., Ni		impurity effects	41/42 (1989) 290
impurity effects on hydrogen surface		Y. Kawadzu, M. Iioka, A. Fujii, H.	
chemistry and etching of Si(111)	45 (1990) 201	Oyanagi and T. Arai, Interfacial reac-	
M. Wolpers, H. Viefhaus and M. Strat-		tion of nickel/hydrogenated amor-	
mann, Surface analytical investiga-		phous silicon system at low tempera- ture studied by fluorescence EXAFS	41/42 (1989) 296
tions of metal surfaces modified by		T. Ito, A. Yamama, A. Hiraki and M.	41/42 (1707) 270
Langmuir-Blodgett films of silanes	47 (1991) 49	Satou, Silicidation of porous silicon	
		and its application for the fabrication	
Silicides		of a buried metal layer	41/42 (1989) 301
Siliciaes		M. Wagner, A. Witzmann, H.D. Geiler	
		and KH. Heinig, Formation of p-n	
J.H. Werner, H. von Känel, G. Markewitz		junctions and silicides in silicon using	
and R.T. Tung, Pressure dependences		a high performance laser beam homo-	
of silicide/silicon Schottky barrier	44 440 (1000) 150	genization system	43 (1989) 260
heights	41/42 (1989) 159	F. Richter, E. Bugiel, R. Grötzschel, H.	
H. Fujitani and S. Asano, Electronic	41 /42 (1000) 164	Reichardt, A. Schöpke, E. Wieser and	
structure of Si/disilicide interfaces  R.T. Tung and F. Schrey, Epitaxial	41/42 (1989) 164	F. Wolf, Formation of titanium dis- ilicide using different annealing meth-	
CoSi <sub>2</sub> /Si(111) interfaces	41/42 (1989) 223	ods	44 (1990) 127
J. Falta, M. Horn and M. Henzler, SPA-	41/42 (1707) 223	V.V. Tokarev, A.V. Kibardin, T.M.	11 (1770) 127
LEED studies of defects in thin epi-		Pyatkova and D.I. Zarovsky, Nickel,	
taxial NiSi <sub>2</sub> layers on Si(111)	41/42 (1989) 230	cobalt and iron silicide formation	
P.J. van den Hoek and E.J. Baerends,		stimulated by argon implantation	44 (1990) 235
Chemical bonding at metal-semicon-		V.V. Tokarev, A.I. Demchenko, A.I.	
ductor interfaces	41/42 (1989) 236	Ivanov and V.E. Borisenko, Influence	
N. Cherief, R. Cinti, M. De Crescenzi, J.		of boron implantation on phase trans-	
Derrien, T.A. Nguyen Tan and J.Y.		formations in nickel silicides	44 (1990) 241

K. Nishimori, H. Tokutaka, H. Sumi and N. Ishihara, Interface reaction of Si		tions of the silicon wafer direct-bond- ing technique to electron devices	41/42 (1989) 627
thin film on Au substrate  A.K. Kulkarni and A.J. Canale, Electrical and structural characterization of Co	47 (1991) 365	M. Okuyama, N. Fujiki, Y. Nakatani, K. Inoue and Y. Hamakawa, Growth be- havior of highly oriented Si films on	
and Ni silicide contacts to silicon	48/49 (1991) 307	fused quartz by photo-CVD  D. Milne, J.I.B. Wilson, T.T. Rantala and J. Lenkkeri, Morphological and struct-	41/42 (1989) 633
Silicon		ural changes in laser CVD of silicon: comparison of theoretical temperature	
K. Nishimori, H. Tokutaka, Z. Okinaga, S. Kishida and N. Ishihara, Observa- tion of Si and SiC surface structures		<ul> <li>calculations with experimental results</li> <li>N. Hecking and E.H. te Kaat, Modelling of lattice damage accumulation during</li> </ul>	43 (1989) 81
using the magnetic LEED method  E. Vlieg and J.F. van der Veen, X-ray scattering studies of semiconductor in-	41/42 (1989) 49	high energy ion implantation P. Mary, P. Bogdanski, G. Nouet and M. Toulemonde, Defects created by 3.5	43 (1989) 87
terfaces: atomic structure and mor- phology R.S. Williams, R.S. Daley, J.H. Huang	41/42 (1989) 62	GeV xenon ions in silicon  R. M'Ghaieth, R. Gauthier and P. Pinard,  Structure and defects induced by elec-	43 (1989) 102
and R.M. Charatan, Initial stages of metal/semiconductor interface formation: Au and Ag on Si(111)	41/42 (1989) 70	tron beam irradiation in silicon sub- strates and EPR ribbons W.C. Sinke, A. Polman, S. Roorda and	43 (1989) 111
S. Kono, Y. Enta, T. Abukawa, T. Kinoshita and T. Sakamoto, Photo-	41/42 (1909) 70	P.A. Stolk, Explosive crystallization of amorphous silicon: triggering and	
electron spectroscopy and photoelectron diffraction studies of Si(001) $2 \times 1$ -K and -Cs surfaces	41/42 (1989) 75	propagation E.L. Mathé, J.G. Maillou, A. Naudon, E. Fogarassy, M. Elliq and S. de Un-	43 (1989) 128
S. Kohmoto, S. Mizuno and A. Ichimiya, RHEED intensity analysis of Li/ Si(111) structures	41/42 (1989) 107	amuno, Excimer laser recrystallization of amorphous Si films characterized by grazing X-ray diffraction and opti-	
M. Itoh, M. Kinoshita, T. Ajioka, M. Itoh and T. Inada, Crystalline quality of	, (,	cal reflectivity  J.G. Maillou, E.L. Mathé, J.C. Desoyer, S. de Unamuno and E. Fogarassy,	43 (1989) 142
heteroepitaxial silicon on epitaxial NiSi <sub>2</sub> /Si(100)  A. Förster, J.M. Layet and H. Lüth, Evaluation of dopant profiles and dif-	41/42 (1989) 262	Comparison between microscopical aspects of a-Si films crystallized by pulsed UV excimer laser and calcu-	
fusion constants by means of electron energy loss spectroscopy C.A. Sébenne, J.P. Lacharme, I. Andria-	41/42 (1989) 306	lated temperature profiles  M. Berti, G. Mazzi, A.V. Drigo, A.  Migliori, E. Jannitti and S. Nicoletti,	43 (1989) 150
manantenasoa and M. Khial, Local roughness and surface states on Si(001): analysis of vacuum anneal-		Laser induced epitaxial regrowth of $Si_{1-x}Ge_x/Si$ layers produced by Ge ion implantation	43 (1989) 158
ings and oxygen adsorption-desorp- tion processes  Y. Borensztein, T. Lopez-Rios and G.	41/42 (1989) 352	F. Priolo, C. Spinella, A. La Ferla, E. Rimini and G. Ferla, Ion-assisted recrystallization of amorphous silicon	43 (1989) 178
Vuye, Roughness induced at Si(111) surfaces by high temperature heating	41/42 (1989) 439	C. Spinella, S. Lombardo and S.U. Campisano, Amorphous to polycrystal transition in ion irradiated chemical	
Y. Hatanaka, K. Mitsuoka and T. Yama- guchi, Properties of a-Si:H based in- terface transient layers measured by		vapor deposited amorphous silicon S.P. Withrow, O.W. Holland and S.J.	43 (1989) 187
in-situ ellipsometry  F. Priolo, A. La Ferla, C. Spinella, E. Rimini, S.U. Campisano and G. Ferla,	41/42 (1989) 591	Pennycook, Ion beam annealing of Ga-implanted Si M. Voelskow, W. Skorupa, K. Woll-	43 (1989) 191
Crystal-amorphous-silicon interface kinetics under ion beam irradiation K. Furukawa and A. Nakagawa, Applica-	41/42 (1989) 619	schlaeger, J. Matthaei, P. Knothe, K H. Heinig and H. Bartsch, Epitaxial lateral overgrowth of amorphous CVD	

silicon films induced by ion irradia-	44 (4000) 404	moepitaxial growth of silicon on	44 (1000) 07
tion	43 (1989) 196	anodized porous silicon	44 (1990) 97
G. Massouras, J.A. Roger, G. Fuchs, A.		A.E.M.J. Fischer, W.F.J. Slijkerman, J.F.	
Perez and L. Romana, Fluence depen- dence of ion beam induced atomic		van der Veen and I. Ohdomari, Ther-	
mixing in the immiscible tin-silicon		mal stability of supersaturated oxy- gen-doped silicon epitaxial films	44 (1990) 115
system	43 (1989) 213	J.M. Gómez-Rodríguez, A.M. Baró and	44 (1990) 113
W.I. Milne, F.J. Clough, S.C. Deane, S.D.	43 (1909) 213	V.P. Parkhutik, Morphology of porous	
Baker and P.A. Robertson, Photoen-		silicon studied by STM/SEM	44 (1990) 185
hanced CVD of hydrogenated amor-		Ch. Cardinaud and G. Turban, Mechanis-	(1))0)103
phous silicon using an internal hydro-		tic studies of the initial stages of etch-	
gen discharge lamp	43 (1989) 277	ing of Si and SiO <sub>2</sub> in a CHF <sub>3</sub> plasma	45 (1990) 109
W.C.M. Claassen, R.W.A.H. Schmitz and	(2,0,) 2, ,	R.M. Wallace, C.C. Cheng, P.A. Taylor,	()
J. Dieleman, Influence of surface fluo-		W.J. Choyke and J.T. Yates, Jr., Ni	
rination on the oxidation of amor-		impurity effects on hydrogen surface	
phous silicon by atomic oxygen at 300		chemistry and etching of Si(111)	45 (1990) 201
K	43 (1989) 292	A.F. Bernhardt, A.T. Barfknecht, R.J.	
J. Kubátová, V. Cháb, I. Lukeš, P. Jiříček		Contolini, V. Malba, S.T. Mayer, N.F.	
and F. Fendrych, ArF excimer laser		Raley and D.B. Tuckerman, Multichip	
induced changes in the Si(100)/SiO <sub>2</sub>		packaging for very-high-speed digital	
interface studied in situ by ESCA and		systems	46 (1990) 121
LEED	43 (1989) 297	E. Golusda, R. Lange, G. Mollekopf and	
R. Fantoni, E. Borsella, S. Piccirillo, C.A.		H. Stafast, On the role of the substrate	
Nannetti, R. Ceccato and S. Enzo,		position in the CO <sub>2</sub> laser CVD of	
Laser assisted synthesis of ultrafine		amorphous hydrogenated silicon	46 (1990) 230
silicon powder	43 (1989) 308	K. Hesch, P. Hess, H. Oetzmann and C.	
E. Fogarassy, C. Fuchs, S. de Unamuno		Schmidt, Laser CVD of a-Si:H from	
and P. Siffert, Excimer laser induced		SiH <sub>4</sub> and Si <sub>2</sub> H <sub>6</sub> : relations between	
melting of heavily doped silicon: a		chemistry, growth rate and film prop-	
contribution to the optimization of the		erties	46 (1990) 233
laser doping process	43 (1989) 316	W. Marine, J.M. Scotto D'Aniello and J.	
R. Nipoti, M. Bianconi, R. Fabbri, M.		Marfaing, Picosecond YAG laser pho-	
Servidori, S. Nicoletti and R. Canteri,		toablation of amorphous silicon	46 (1990) 239
Electrical and structural characteriza-		M. Zeman, I. Ferreira, M.J. Geerts and	
tion of silicon layers directly doped		J.W. Metselaar, The influence of de-	
with boron by excimer laser irradia-		position parameters on the growth of	
tion	43 (1989) 321	a-SiGe:H alloys in a plasma CVD sys-	
P.G. Carey and T.W. Sigmon, In-situ		tem	46 (1990) 245
doping of silicon using the gas immer-		T.S. Baller, J.C.S. Kools and J. Dieleman,	
sion laser doping (GILD) process	43 (1989) 325	Surface temperature measurements	
T.S. Baller and J. Dieleman, Nanosecond		using pyrometry during excimer laser	
excimer laser-enhanced chemical etch-		pulsed etching of silicon in a Cl <sub>2</sub> en-	
ing	43 (1989) 409	vironment	46 (1990) 292
J. Boulmer, B. Bourguignon, J.P. Budin		D. Korzec, T. Kessler and J. Engemann,	
and D. Debarre, Time of flight study		Reactive ion beam etching of Si/SiO <sub>2</sub>	44 (4000) 400
of low pressure laser etching of silicon		systems using SF <sub>6</sub> /O <sub>2</sub> chemistry	46 (1990) 299
by chlorine	43 (1989) 424	B. Hartiti, A. Slaoui, J.C. Muller and P.	
G.C. Tyrrell, I.W. Boyd and R.B. Jack-		Siffert, Annealing kinetics during	
man, Ion beam assisted etching of		rapid thermal processing of excimer	46 (1000) 271
silicon with bromine. The role of the	40.4000	laser-induced defects in virgin silicon	46 (1990) 371
adsorbed state	43 (1989) 439	M. Elliq, E. Fogarassy, J.P. Stoquert, C.	
P. Lejček, M. Koutník, J. Brádler, V.		Fuchs, S. de Unamuno, B. Prévot and	
Paidar and A. Potměšilová, Ani-		H. Pattyn, Pulsed excimer and	
sotropy of grain boundary segregation		Nd:YAG laser crystallization of a-	46 (1990) 378
in as-grown Fe-6at%Si alloy bi-	44 (1000) 75	Si:H. The specific role of hydrogen	40 (1990) 3/8
crystals T. Ito, T. Yasumatsu and A. Hiraki, Ho-	44 (1990) 75	J. Solis, C.N. Afonso and F. Catalina, The influence of the substrate on the	
1. 100, 1. 1 asumatsu and A. Illiaki, 110-		The influence of the substrate on the	

nanosecond lase resolved study	induced in Si by er irradiation: a time- R. Buchner, D. Boll-	46 (1990) 383	T. Hashizume, Y. Hasegawa and T. Sakurai, Alkali-metal adsorption on silicon surfaces studied by field ion-scanning tunneling microscopy (FI-	
mann, W. van	der Wel and K. Ha-		STM)	48/49 (1991) 119
berger, Investiga	ation of laser recrys-		S. Hongo, T. Urano and T. Kanaji, Mech-	
tallization of	thin Si films using		anisms of He*(21S) de-excitation on	
numerical simula	ation	46 (1990) 388	oxygen-adsorbed Si(100) surfaces	48/49 (1991) 143
V. Dupuis, M.F. R	avet, C. Tête and M.		V.A. Ukraintsev, B.S. Podolsky and A.A.	
Piecuch, Therma	al evolution of W/Si		Chernov, Water adsorption kinetics on	
and W/C mult	tilayers under pulsed		Si(111)-7 $\times$ 7: defect generation mech-	
	d classical annealing	46 (1990) 398	anism	48/49 (1991) 151
	Marine, B. Vidal, M.		A. Ermolieff, F. Martin, A. Amouroux, S.	
	. Hage Ali and J.P.		Marthon and J.F.M. Westendorp,	
	bility and structural		Surface composition analysis of HF	
-	of amorphous ultra-		vapour cleaned silicon by X-ray pho-	
	ilayer structures dur-		toelectron spectroscopy	48/49 (1991) 178
ing heavy ion irr	7.	46 (1990) 422	M. Kimura, A. Tanaka and T. Sukegawa,	, , , ,
-	Booth and C. Pomot,	(	Dissolution process of silicon in an	
•	a treatment of silicon		indium solution	48/49 (1991) 185
	by in-situ spectro-		G. Shimaoka, MEED studies of thin metal	10) 11 (2772) 200
scopic ellipsomet		46 (1990) 435	film covered semiconductor surfaces	48/49 (1991) 190
	t, M. Strahnen, G.	10 (1770) 122	V.A. Ukraintsev, A.A. Chernov, A.N.	10) 15 (1551) 150
	. Kurz, Femtosecond		Mezhuyev and B.S. Podolsky, Effec-	
	vity measurements as		tive temperature of products in laser	
	ess-induced defects in		evaporation and desorption	48/49 (1991) 198
silicon	css-maucea acreets in	46 (1990) 446	T. Hibma, H.H. Weitering, D.R. Heslinga	40/ 47 (1771) 170
	lhier and C. Ganibal,	40 (1770) 440	and T.M. Klapwijk, Interface struc-	
	solid state regrowth		ture and Schottky barriers of epitaxial	
	ment in a rapid ther-		Pb on Si(111)	48/49 (1991) 209
mal processor	ment in a rapid ther-	46 (1990) 451	Y. Matsuda, K. Fujita and S. Hinotani,	40/ 47 (1771) 207
7	Mierry, M. Aucou-	40 (1770) 431	Raman studies on GaAs epitaxial films	
	Darque-Ceretti, In-		on Si	48/49 (1991) 231
	al treatments on the		P.C. Karulkar, R.J. Hillard, J.M. Heddle-	40/47 (1771) 231
	contaminating copper		son and P. Rai-Choudhury, A pres-	
	of silicon: a compara-		sure contact current-voltage tech-	
tive SIMS and X		47 (1991) 1	nique for rapid characterization of thin	
	der Wiel, H. Zeijle-	47 (1991)	dielectric films	48/49 (1991) 237
	erhoeven, Ion bom-		B.V. King, D.J. O'Connor, Y. Shen, R.J.	40/49 (1991) 237
	ray multilayer coat-		MacDonald, M. Katayama and M.	
	of ion etching and		Aono, LEIS for structure determina-	
ion assisted depo		47 (1991) 251	tion of surfaces and thin films	48/49 (1991) 246
_	Hirokawa, New tech-	47 (1991) 231	S. Berger, Y. Komem and B.Z. Weiss, On	40/49 (1991) 240
	tion of surfaces and		the microstructure, composition and	
			electrical properties of Al/TiW/poly-	
	ospheric pressure by			48/49 (1991) 281
_	X-ray fluorescence	47 (1991) 371	Si system	40/49 (1991) 201
(RXF)	fattha: A malamlan	47 (1991) 371	P.K. Banerjee, J.S. Kim and S.S. Mitra,	
	Matthai, A molecular		Electrical and optical properties of a-	
	of the critical thick-	49 /40 (1001) 20	luminum-doped amorphous silicon	49 /40 (1001) 200
ness of Ge layers		48/49 (1991) 39	carbide films	48/49 (1991) 288
N. Ohshima, Y. Koi			Zhang Rong, Zheng Youdou, Jiang	
	on of a superstruc-		Ruolian, Hu Liqun, Zhong Peixin, Yu	
	stage of Ge epitaxial	49 (40 (1001) (0	Shidong, Li Qi, Feng Duan and Chen	
growth on Si(100)		48/49 (1991) 69	Guangxi, The structure of $Ge_xSi_{1-x}$	
D. Haneman and I	-		Si strained layer superlattices and het-	40 /40 (1001) 257
	Si cleaved and gas-	49 /40 (1001) 111	erostructures	48/49 (1991) 356
covered surfaces		48/49 (1991) 111	I. Katayama, T. Hanawa, F. Shoji and K.	

Oura, ISS-AES study of the initial growth stage of Cu thin films on		$Si_{1-x}Ge_x$ films from surface acoustic modes by Brillouin scattering	50 (1991) 303
$Si(111)-7\times7$	48/49 (1991) 361	A. Baraldi, C. Ghezzi, A. Parisini, A.	
JK. Zuo and J.F. Wendelken, Substrate		Bosacchi and S. Franchi, Analysis of	
temperature effects on $(\sqrt{3} \times \sqrt{3})$ R30°		electron mobility versus temperature	
domain growth of Ag on Si(111)		after photoexcitation in Si-doped	
surface	48/49 (1991) 366	$Al_xGa_{1-x}As$	50 (1991) 405
M. Arienzo, S.S. Iyer, B.S. Meyerson, G.L.		R. Nipoti, D. Pocci, A. Cetronio and C.	
Patton and J.M.C. Stork, Si-Ge al-		Lanzieri, Carrier and mobility profile	
loys: growth, properties and applica-		measurements in n-type ion-implanted	
tions	48/49 (1991) 377	GaAs by the differential sheet resistiv-	
S.C. Jain, A. Atkinson and W.S. Khokle,		ity and Hall effect technique	50 (1991) 410
Relationship between mechanical,		D.A. Woolf, D.I. Westwood, M.A. Ander-	
electronic and vibrational properties		son and R.H. Williams, The molecular	
of $Ge_xSi_{1-x}$ strained layers	48/49 (1991) 387	beam epitaxial growth of GaAs(111)/	
Y.L. Jiang and H.L. Hwang, Electron		Si(111): a variable growth temperature	
transport in hydrogenated amorphous		study	50 (1991) 445
silicon quantum wells	48/49 (1991) 392	B. Holländer, S. Mantl, B. Stritzker, F.	
T. Yasumatsu, T. Ito, H. Nishizawa and		Schäffler, HJ. Herzog and E. Kasper,	
A. Hiraki, Ultrathin Si films grown		Strain and defect densities in Si/	
epitaxially on porous silicon	48/49 (1991) 414	$Si_{1-x}Ge_x$ heterostructures investigated	
Y. Hatanaka, Heterostructures with hy-		by ion scattering and X-ray diffrac-	
drogenated amorphous silicon for use	40 /40 /1001> 457	tion	50 (1991) 450
in imaging devices	48/49 (1991) 457	R. Schwarz, T. Fischer, P. Hanesch, T.	
H. Mimura and Y. Hatanaka, The current		Muschik, J. Kolodzey, H. Cerva, H.L.	
transport mechanism of p-type a-		Meyerheim and B.M.U. Scherzer,	
Si:H/n-type c-Si heterojunctions and	40 /40 /1001) 472	Limitations of interface sharpness in	50 (1001) 456
their application to an imaging device	48/49 (1991) 472	a-Si:H/a-SiC:H multilayers	50 (1991) 456
H. Mimura, K. Sai, Y. Ohta, K. Yamamo-		HG. Hettwer, W. Lerch, B. Lentfort,	
to and K. Kitamura, A two-dimen-		N.A. Stolwijk and H. Mehrer, Com-	
sional image sensor with a-Si:H pin	49 /40 /1001) 521	bined application of spreading-resis-	
diodes	48/49 (1991) 521	tance and electron-microprobe depth	50 (1001) 470
P.F. Fewster, Multicrystal X-ray diffrac- tion of heteroepitaxial structures	50 (1001) 0	profiling on GaAs:Zn and Si:P  A. Castaldini, A. Cavallini, E. Gombia, R.	50 (1991) 470
C. Grattepain and A.M. Huber, Sec-	50 (1991) 9	Mosca and L. Tarricone, Evaluation	
ondary ion mass spectrometry of		of the diffusion length of minority car-	
dopants and impurities in compound		riers in bulk GaAs	50 (1991) 485
semiconductors: depth profiling of		ners in bulk Gans	30 (1771) 483
homo- and heterostructure	50 (1991) 42	Silicon carbide	
H.G. Grimmeiss and M. Kleverman,	30 (1771) 42	Sincon carolae	
Electrical and optical defect spec-		S. Nakanishi, H. Tokutaka, K. Nishimori,	
troscopy of compound semiconduc-		S. Kishida and N. Ishihara, The dif-	
tors	50 (1991) 52	ference between 6H-SiC (0001) and	
J. Wagner, Raman spectroscopy for im-	00 (1771) 02	(0001) faces observed by AES, LEED	
purity characterization in III-V semi-		and ESCA	41/42 (1989) 44
conductors	50 (1991) 79	K. Nishimori, H. Tokutaka, Z. Okinaga,	12/ 12 (2202) 11
C. Frigeri, J.L. Weyher and M. De Potter,	(2002)	S. Kishida and N. Ishihara, Observa-	
TEM study of the origin of the surface		tion of Si and SiC surface structures	
microroughness in DSL photoetched		using the magnetic LEED method	41/42 (1989) 49
Si-implanted GaAs wafers	50 (1991) 115	T. Aoyama, T. Sugi and T. Ito, De-	, , , , ,
S. Usala, G.J. Adriaenssens, Ö. Öktü and		termination of band line-up in $\beta$ -	
M. Nesladek, Post-transit-time analy-		SiC/Si heterojunction for Si-HBT's	41/42 (1989) 584
sis of time-of-flight photocurrents	50 (1991) 265	P.V. Huong, O. Segond, P. Gentilini and	
M. Mendik, M. Ospelt, H. von Känel and		R. Cavagnat, Silicon aggregates pro-	
P. Wachter, Determination of elastic		duced by laser beam in a silicon	
properties of Si/Ge superlattices and		carbide surface	43 (1989) 256

I. Kusunoki, M. Hiroi, T. Sato, Y. Igari		ies of ultrathin silicon oxides and their	41 (42 (1000) 41 (
and S. Tomoda, SiC film formation on Si(001) by reaction with C <sub>2</sub> H <sub>2</sub> beams L.V. Interrante, B. Han, J.B. Hudson and C. Whitmarsh, Design and synthesis	45 (1990) 171	interfaces by XPS  S. Nadahara, J. Shiozawa, K. Imai, K. Suguro and K. Yamabe, Protuberance growth at polysilicon surfaces during	41/42 (1989) 416
of CVD precursors to thin film ceramic materials  V.Kh. Kudoyarova, G.M. Gusinsky, L.A.	46 (1990) 5	oxidation  Y. Yasuda, S. Zaima, T. Kaida and Y. Koide, Formation of Si-SiO <sub>2</sub> inter-	41/42 (1989) 425
Rassadin and I.V. Kudryavtsev, Hydrogen depth profile measurement in $a-Si_{1-x}C_x$ :H films by elastic recoil de-		faces at low temperatures using micro- wave-excited plasma  Y. Kamiura, F. Hashimoto and M. Iwami,	41/42 (1989) 429
tection R. Schwarz, T. Fischer, P. Hanesch, T.	50 (1991) 173	Iron accumulation at the Si-SiO <sub>2</sub> interface and possible reduction of SiO <sub>2</sub> G. Bomchil, A. Halimaoui and R. Herino,	41/42 (1989) 447
Muschik, J. Kolodzey, H. Cerva, H.L. Meyerheim and B.M.U. Scherzer, Limitations of interface sharpness in	50 (1001) 456	Porous silicon: the material and its applications in silicon-on-insulator	41 /42 (1080) 604
a-Si:H/a-SiC:H multilayers  Silicon nitride	50 (1991) 456	Y. Kato, T. Ito and A. Hiraki, Low temperature oxidation of crystalline por-	41/42 (1989) 604
		ous silicon  A. Klumpp and H. Sigmund, Photoin-	41/42 (1989) 614
R. Fantoni, E. Borsella, S. Piccirillo, C.A. Nannetti, R. Ceccato and S. Enzo, Laser assisted synthesis of ultrafine		duced transformation of polysiloxane layers to SiO <sub>2</sub> W.A.M. Aarnink, A. Weishaupt and A.	43 (1989) 301
silicon powder  B.L. Halpern, J.J. Schmitt, J.W. Golz, Y. Di and D.L. Johnson, Gas jet deposi-	43 (1989) 308	van Silfhout, Angle-resolved X-ray photoelectron spectroscopy (ARXPS) and a modified Levenberg-Marquardt	
tion of thin films I.K. Han, Y.J. Lee, J.W. Jo, J.I. Lee and K.N. Kang, Growth and characteriza-	48/49 (1991) 19	fit procedure: a new combination for modeling thin layers Ch. Cardinaud and G. Turban, Mechanis-	45 (1990) 37
tion of silicon-nitride films by plasma- enhanced chemical vapor deposition T. Wadayama, T. Hihara, A. Hatta and	48/49 (1991) 104	tic studies of the initial stages of etching of Si and SiO <sub>2</sub> in a CHF <sub>3</sub> plasma J.L. Chartier, A. Serrari, R. Le Bihan, M.	45 (1990) 109
W. Suëtaka, In situ IR observation of photo-chemically deposited silicon nitride thin films	48/49 (1991) 409	Ligeon, F. Gaspard and F. Muller, Thermal nitridation of anodic silicon dioxide	45 (1990) 351
J.J. Fijol, A.M. Then, G.W. Tasker and R.J. Soave, Secondary electron yield of SiO <sub>2</sub> and Si <sub>3</sub> N <sub>4</sub> thin films for con-	(2) (2)	A.F. Bernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip	(2550) 222
tinuous dynode electron multipliers	48/49 (1991) 464	packaging for very-high-speed digital systems	46 (1990) 121
Silicon oxide		Y. Horiike, T. Ichihara and H. Sakaue, Filling of Si oxide into a deep trench	46 (1000) 160
H. Akatsu and I. Ohdomari, HRTEM observation of the Si/SiO <sub>2</sub> interface	41/42 (1989) 357	using digital CVD method  M. Petitjean, N. Proust, JF. Chapeau- blanc and J. Perrin, SiO <sub>2</sub> deposition	46 (1990) 168
K. Inoue, M. Okuyama and Y. Hamaka- wa, Optical and interfacial properties		by direct photolysis at 185 nm of N <sub>2</sub> O and SiH <sub>4</sub>	46 (1990) 189
of SiO <sub>2</sub> films deposited on Si by photo-CVD  K. Yokota, K. Ohtsuki, M. Ochi, S.	41/42 (1989) 407	E. Fogarassy, A. Slaoui, C. Fuchs and J.P. Stoquert, Deposition of SiO <sub>2</sub> by reactive excimer laser ablation from a SiO	
Ishihara and I. Kimura, Accumulation of implanted arsenic at the interface		A. Boelle, J.A. Roger, B. Canut, J.	46 (1990) 195
during annealing on thermally oxi- dized Si and SiO <sub>2</sub> covered Si T. Hattori, H. Yamagishi, N. Koike, K.	41/42 (1989) 411	Mugnier and M. Pitaval, Sol-gel low- temperature preparation of silica films: RBS, TEM and MOS C-V	
Imai and K. Yamabe, Structural stud-		characterization	46 (1990) 200

Silver		Solid phase epitaxy	
G. Abstreiter, Micro-Raman spectroscopy for characterization of semiconductor devices	50 (1991) 73	A. Diarra, S. Hotchandani, H. Kassi and R.M. Leblanc, Capacitance character- istics of mixed monolayers of chloro- phyll a and carotenoid canthaxanthin	48/49 (1991) 567
spectroscopy of compound semicon- ductor surfaces and interfaces	50 (1991) 34	Solar cells	
of SiO <sub>2</sub> and Si <sub>3</sub> N <sub>4</sub> thin films for continuous dynode electron multipliers  I.T. McGovern, Soft X-ray photoelectron	48/49 (1991) 464	surface	48/49 (1991) 366
epitaxially on porous silicon  J.J. Fijol, A.M. Then, G.W. Tasker and  R.J. Soave, Secondary electron yield	48/49 (1991) 414	JK. Zuo and J.F. Wendelken, Substrate temperature effects on $(\sqrt{3} \times \sqrt{3})$ R30° domain growth of Ag on Si(111)	
tions T. Yasumatsu, T. Ito, H. Nishizawa and A. Hiraki, Ultrathin Si films grown	48/49 (1991) 405	Margaritondo, Synchrotron radiation induced surface photovoltage at metal/GaAs interfaces	48/49 (1991) 324
the dielectric properties of thin silicon dioxide films  A. Hishinuma, T. Goda, M. Kitaoka, S. Hayashi and H. Kawahara, Formation of silicon dioxide films in acidic solu-	48/49 (1991) 264	W. Suëtaka, Kretschmann ATR-IR spectroscopy of investigating metal/liquid(or solid) interfaces  D. Mao, A. Kahn, M. Marsi and G.	48/49 (1991) 222
S. Kar, A. Raychaudhuri, A.K. Sinha and S. Ashok, Ion beam modification of the dielectric properties of thin silicon		<ul> <li>G. Shimaoka, MEED studies of thin metal film covered semiconductor surfaces</li> <li>A. Hatta, Y. Suzuki, T. Wadayama and</li> </ul>	48/49 (1991) 190
son and P. Rai-Choudhury, A pres- sure contact current-voltage tech- nique for rapid characterization of thin dielectric films	48/49 (1991) 237	and A.T. Hubbard, Direct imaging of thin film atomic structure by an- gular distribution Auger microscopy (ADAM)	48/49 (1991) 166
Mezhuyev and B.S. Podolsky, Effective temperature of products in laser evaporation and desorption P.C. Karulkar, R.J. Hillard, J.M. Heddle-	48/49 (1991) 198	Prabhakara Rao, Alloy formation in the monolayers of underpotentially deposited lead and thallium D.G. Frank, T. Golden, O.M.R. Chyan	47 (1991) 293
<ul> <li>M. Muhler, Z. Paál and R. Schlögl, XPS of platinum in Pt/SiO<sub>2</sub> (Europt-1): possibilities and limitations of the method</li> <li>V.A. Ukraintsev, A.A. Chernov, A.N.</li> </ul>	47 (1991) 281	<ul> <li>W.S. Lee, R.A. Outlaw, G.B. Hoflund and M.R. Davidson, Auger electron intensity variations in oxygen-charged silver</li> <li>S. Bharathi, V. Yegnaraman and G.</li> </ul>	47 (1991) 91
M.M. Hills and G.S. Arnold, Chemical treatment of fused silica with xenon diffuoride	47 (1991) 77	P. Ptáček and Z. Bastl, XPS characteriza- tion of supported bimetallic pal- ladium-silver clusters	45 (1990) 319
P. Patel and I.W. Boyd, Low temperature VUV enhanced growth of thin silicon dioxide films	46 (1990) 352	file studies of interdiffusion in thin polycrystalline Au-Ag multilayer films	45 (1990) 57
of silica films: a comparison between two methods  D. Korzec, T. Kessler and J. Engemann, Reactive ion beam etching of Si/SiO <sub>2</sub> systems using SF <sub>6</sub> /O <sub>2</sub> chemistry	46 (1990) 210 46 (1990) 299	J.C. Ingram, K.W. Nebesny and J.E. Pemberton, Optical constants of the noble metals determined by reflection electron energy loss spectroscopy A. Bukaluk and W. Bała, AES depth pro-	44 (1990) 293
of SiO <sub>2</sub> films using an ArF laser  B. León, A. Klumpp, M. Pérez-Amor and H. Sigmund, Excimer laser deposition	46 (1990) 206	and R.M. Charatan, Initial stages of metal/semiconductor interface formation: Au and Ag on Si(111)	41/42 (1989) 70
<ul> <li>T. Szörényi, P. González, D. Fernández,</li> <li>J. Pou, B. León and M. Pérez-Amor,</li> <li>Gas mixture dependence of the LCVD</li> </ul>		terfaces: atomic structure and mor- phology R.S. Williams, R.S. Daley, J.H. Huang	41/42 (1989) 62

E. Vlieg and J.F. van der Veen, X-ray scattering studies of semiconductor inM. Berti, G. Mazzi, A.V. Drigo, A. Migliori, E. Jannitti and S. Nicoletti,

Laser induced epitaxial regrowth of Si <sub>1-x</sub> Ge <sub>x</sub> /Si layers produced by Ge ion implantation  JM. Dilhac, N. Nolhier and C. Ganibal,	43 (1989) 158	Optical, electrical and mechanical properties of RF-sputtered TiN-W-Au films P. Bhardwaj, O.J. Gregory, K. Bragga and	48/49 (1991) 548
In situ silicon solid state regrowth kinetics measurement in a rapid ther- mal processor	46 (1990) 451	M.H. Richman, Sputtered TiN thin films for improved corrosion resistance	48/49 (1991) 555
Sputter deposition		Sputtering	
E. Marclay, D.J. Webb, P. Buchmann and P. Vettiger, Broadband low-reflectivity coating for semiconductor power lasers		J. van Zwol, S.T. de Zwart, C.C.A. Busquet and J. Dieleman, Resputter- ing of low-energy implanted inert gases: an angle-resolved time-of-flight	
by ion-beam and PECVD deposition J.H. James, B.J. Kellett, A. Gauzzi, B. Dwir and D. Pavuna, In-situ super- conducting YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7</sub> thin films	43 (1989) 43	study J. Morais, A.M. Machado, M.A. Sacilotti and R. Landers, AES sputter depth profiles applied to interface analysis	43 (1989) 363
grown by ion beam co-deposition A.R. Krauss, O. Auciello, A.I. Kingon, M.S. Ameen, Y.L. Liu, T. Barr, T.M. Graettinger, S.H. Rou, C.S. Soble and	43 (1989) 393	of GaInAs/InP grown by atmospheric pressure MOCVD H.M. Hütten, KD. Raddatz, M.K. Sharma and J. Engemann, On the two-	44 (1990) 161
D.M. Gruen, Computer-controlled ion beam deposition systems for high $T_c$ superconductor and other multi-component oxide thin films and layered		and three-dimensional simulation of ion-milled structures  T. Yamashina and T. Hino, Plasma—surface interactions of graphite as	46 (1990) 306
structures J. Gao, W.A.M. Aarnink, G.J. Gerritsma and H. Rogalla, High quality YBa <sub>2</sub> Cu <sub>3</sub> O <sub>x</sub> ultra-thin films and Y/Pr/Y	46 (1990) 67	nuclear fusion material L.J. Bredell, F.D. Auret, G. Myburg and W.O. Barnard, Electrical characteriza- tion of argon-ion sputtered n-GaAs	48/49 (1991) 483 50 (1991) 466
multilayers made by a modified RF- magnetron sputtering technique A. Chevarier, N. Chevarier, M. El Bou- anani, E. Gerlic, M. Stern, B. Roux	46 (1990) 74	Steel	
and F. Thimon, Profiling of carbon, oxygen and argon contamination in sputter-deposited films using nuclear backscattering and nuclear reaction		C. Neelmeijer, P. Knothe, M. Posselt, E. Richter and KH. Heinig, Wear re- sistant coatings produced by C <sup>+</sup> im- plantation	43 (1989) 232
y. Shigesato, S. Takaki and T. Haranou, Crystallinity and electrical properties	48/49 (1991) 215	M.J. van Staden and J.P. Roux, The controlled oxidation of the high chromium steel alloys Fe40Cr and	44 (1990) 263
of tin-doped indium oxide films de- posited by DC magnetron sputtering F. Shoji, A. Ogawa and K. Oura, Sputter-deposition by a new Penning-	48/49 (1991) 269	Fe40Cr3Ru  M.J. van Staden and J.P. Roux, Surface segregation in the alloys Fe40Cr3Ru, Fe40Cr3Pt and Fe40Cr with a 1000 Å	44 (1990) 203
discharge source with an axially integrated hot-cathode  S. Kishida, H. Tokutaka, H. Higashi, K. Nishimori and N. Ishihara, Prepara-	48/49 (1991) 373	Pt overlayer  A. Elbiache and P. Marcus, Adsorption and surface segregation of sulphur on Fe-17Cr-12.6Ni(100) and Fe-17Cr-	44 (1990) 271
tion conditions of flat 80 K phase Bi-Sr-Ca-Cu-O thin films by RF magnetron sputtering M. Takeuchi, M. Masui and Y. Momose,	48/49 (1991) 446	<ul> <li>14.5Ni-2.3Mo(100) alloys</li> <li>H. Yumoto, K. Watanabe, K. Akashi and</li> <li>N. Igata, The effect of electronic excitation produced by an electron shower</li> </ul>	45 (1990) 49
Copper-phthalocyanine thin film photoelectrochemical cells  J.S. Kim, P.K. Banerjee, S.S. Mitra, H. Shastry, J.J. Loferski and R. Beaulieu,	48/49 (1991) 517	on the adhesion of copper films de- posited on stainless steel  P. Bhardwaj, O.J. Gregory, K. Bragga and M.H. Richman, Sputtered TiN thin	48/49 (1991) 173

films for improved corrosion resistance	48/49 (1991) 555	Superconductivity	
Sulphides		<ul> <li>H. Dupendant, J.P. Gavigan, D. Givord,</li> <li>A. Lienard, J.P. Rebouillat and Y.</li> <li>Souche, Velocity distribution of micron-size particles in thin film laser</li> </ul>	
J.P. Baltrus and A. Proctor, Composition of overlayers on oxidized pyrite surfaces	44 (1990) 147	ablation deposition (LAD) of metals and oxide superconductors	43 (1989) 369
M. Gendry, J. Durand, M. Erman, J.B. Theeten, L. Nevot and B. Pardo, Chemical and structural analysis by		W. Marine, M. Peray, Y. Mathey and D. Pailharey, Deposition of Y-Ba-Cu oxide superconducting thin films by	
ellipsometry and X-ray reflectometry of thin sulfide layers grown on InP Y. Nakanishi, Y. Fukuda, Y. Hatanaka	44 (1990) 309	Nd:YAG laser evaporation  M. Brown, M. Shiloh, R.B. Jackman and I.W. Boyd, Geometric optimisation for	43 (1989) 377
and G. Shimaoka, The dependence of the polycrystalline structure and elec- troluminescent properties of ZnS:Mn		the deposition of high temperature su- perconductors P.E. Dyer, R.D. Greenough, A. Issa and	43 (1989) 382
deposited on Y <sub>2</sub> O <sub>3</sub> films on thickness M.L. Shek, T.K. Sham, J. Hrbek and G Q. Xu, A soft X-ray study of a Li-S	48/49 (1991) 297	P.H. Key, TEA CO <sub>2</sub> laser ablation studies of Y-Ba-Cu-O J.H. James, B.J. Kellett, A. Gauzzi, B.	43 (1989) 387
surface compound C. Feldman, G. Deutscher and E. Grünbaum, Single-crystal transforma-	48/49 (1991) 332	Dwir and D. Pavuna, In-situ super- conducting YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7</sub> thin films grown by ion beam co-deposition	43 (1989) 393
tion of sphalerite CdS to cubic phase Cu <sub>x</sub> S W.M.R. Divigalpitiya, R.F. Frindt and	48/49 (1991) 535	S.L.T. Andersson and J.C. Otamiri, Sur- face and bulk composition of YBa <sub>2</sub> Cu <sub>3</sub> O <sub>6+x</sub> compounds studied by	
<ul><li>S.R. Morrison, Spread films of single molecular transition-metal sulphides</li><li>C. Levade, J.J. Couderc, G.</li></ul>	48/49 (1991) 572	XPS F. Schmaderer, R. Huber, H. Oetzmann and G. Wahl, High-T <sub>c</sub> YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-δ</sub>	45 (1990) 1
Vanderschaeve, D. Caillard and A. Couret, TEM in-situ observation of recombination-enhanced mobility of dislocations in II-VI compounds	50 (1991) 119	prepared by chemical vapour deposition  P. Vase, Shen Yueqiang and T. Freltoft, Deposition, characterization, and laser	46 (1990) 53
A. Zakrzewski and M. Godlewski, Three- center Auger effect and the quantum yield of the luminescence of ZnS-based		ablation patterning of YBCO thin films  A.R. Krauss, O. Auciello, A.I. Kingon,	46 (1990) 61
phosphors C. De las Heras, I.J. Ferrer and C. Sánchez, Comparison of pyrite thin	50 (1991) 257	M.S. Ameen, Y.L. Liu, T. Barr, T.M. Graettinger, S.H. Rou, C.S. Soble and D.M. Gruen, Computer-controlled ion	
films obtained from Fe and natural pyrite powder	50 (1991) 505	beam deposition systems for high $T_c$ superconductor and other multi-component oxide thin films and layered	
Sulphur		structures  J. Gao, W.A.M. Aarnink, G.J. Gerritsma and H. Rogalla, High quality YBa <sub>2</sub>	46 (1990) 67
A. Elbiache and P. Marcus, Adsorption and surface segregation of sulphur on Fe-17Cr-12.6Ni(100) and Fe-17Cr-		Cu <sub>3</sub> O <sub>x</sub> ultra-thin films and Y/Pr/Y multilayers made by a modified RF-magnetron sputtering technique C. Girault, D. Damiani, C. Champeaux,	46 (1990) 74
14.5Ni-2.3Mo(100) alloys  J.J. Vajo and J.G. McCarty, Thermodynamics of carbon coadsorbed with	45 (1990) 49	P. Marchet, C. Germain, J.P. Mer- curio, J. Aubreton and A. Catherinot, Characterization of the KrF laser-in-	
sulfur on Ni(100) H.J. Grabke, D. Wiemer and H. Viefhaus, Segregation of sulfur during growth of	47 (1991) 23	duced plasma plume created above an YBaCuO superconducting target and preparation of superconducting thin	
oxide scales	47 (1991) 243	films	46 (1990) 78

A. Sajjadi, K. Kuen-Lau, F. Saba, F.		at low doping concentration in selec-	
Beech and I.W. Boyd, Laser-ablation deposition of uniform thin films of	46 (1990) 84	tively Si-doped Al <sub>0.3</sub> Ga <sub>0.7</sub> As/GaAs heterointerfaces S.K. De Figueiredo and A.C. Ferraz, In-	41/42 (1989) 480
Bi <sub>2</sub> Sr <sub>2</sub> CaCu <sub>2</sub> O <sub>x</sub> P.E. Dyer, A. Issa and P.H. Key, An investigation of laser ablation and deposition of Y-Ba-Cu-O in an oxygen	40 (1990) 64	terface geometry of $(GaAs)_n(InAs)_n$ and $(GaP)_n(InP)_n$ ultra-thin super- lattices	41/42 (1989) 509
environment H. Roulet, G. Dufour, A. Cheenne, F. Rochet and C. Cartier, Physicoche-	46 (1990) 89	S. Hayashi, T. Sakamoto, S. Fujita and S. Fujita, Strained-layer superlattice buffers for high-quality heteroepi-	
mistry of laser-deposited BiSrCaCuO thin films studied by XPS and XAS W.A.M. Aarnink, D.H.A. Blank, D.J.	47 (1991) 173	layers of ZnSe on GaAs  H. Okumura, K. Miki, K. Sakamoto, T. Sakamoto, K. Endo and S. Yoshida,	41/42 (1989) 534
Adelerhof, J. Flokstra, H. Rogalla, A. van Silfhout and R. de Reus, Interdiffusion studies on high- $T_c$ supercon-		Raman scattering and photolumines- cence characterization of Ge/Si strained-layer superlattices grown by	
ducting YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-8</sub> thin films on Si(111) with a NiSi <sub>2</sub> /ZrO <sub>2</sub> buffer layer F. Shoji, A. Ogawa and K. Oura,	47 (1991) 195	phase-locked epitaxy G. Vecris and J.J. Quinn, Novel diagrammatic method for analyzing the surface	41/42 (1989) 548
Sputter-deposition by a new Penning- discharge source with an axially in- tegrated hot-cathode	48/49 (1991) 373	electronic modes of finite multilayer structures Zhang Rong, Zheng Youdou, Jiang	48/49 (1991) 319
H. Tokutaka and S. Kishida, Surface characterization of Bi-based high- $T_c$ superconducting thin films and bulk		Ruolian, Hu Liqun, Zhong Peixin, Yu Shidong, Li Qi, Feng Duan and Chen Guangxi, The structure of Ge <sub>x</sub> Si <sub>1-x</sub> /	
single crystals  J.W. Qiu, L.W. Zhou, X.F. Zhang, Z.M.	48/49 (1991) 425	Si strained layer superlattices and het- erostructures	48/49 (1991) 356
Tang, Y.J. Qian and Z.Y. Hua, A high- $T_c$ SQUID for measuring susceptibility of high- $T_c$ superconductive thin films	48/49 (1991) 430	T. Nakamura, Y. Takeuchi, H. Mura- matsu, H. Fujiyasu and Y. Nakanishi, ESR studies on luminescent ZnS:Mn films and CdS-ZnS:Mn superlattices	
S.J. Pickart, M.L. Crow, A.C. Nunes, T.R. McGuire and A. Gupta, Neutron depolarization study of a high- $T_c$ epi-	10, 12 (1222) 100	deposited on a GaAs(100) substrate by hot-wall epitaxy P.F. Fewster, Multicrystal X-ray diffrac-	48/49 (1991) 478
taxial thin film  N. Hamaguchi, R. Gardiner and P.S. Kirlin, MOCVD of TlBaCaCuO su-	48/49 (1991) 436	tion of heteroepitaxial structures  C. Grattepain and A.M. Huber, Secondary ion mass spectrometry of	50 (1991) 9
perconducting thin films: structure- property-processing relationships	48/49 (1991) 441	dopants and impurities in compound semiconductors: depth profiling of homo- and heterostructure	50 (1991) 42
S. Kishida, H. Tokutaka, H. Higashi, K. Nishimori and N. Ishihara, Preparation conditions of flat 80 K phase		J.H.C. Hogg, D. Shaw and D.M. Staudte, Modelling interdiffusion in epitaxial	30 (1991) 42
Bi-Sr-Ca-Cu-O thin films by RF magnetron sputtering K. Nishimori, H. Tokutaka, T. Tamon, S. Kishida and N. Ishihara, Surface study	48/49 (1991) 446	multilayer structures using X-ray simulation techniques  R. Zaus, M. Schuster, H. Göbel and JP. Reithmaier, Characterization of (In,	50 (1991) 87
of single-crystal 80 K Bi-Sr-Ca-Cu- O superconductor with Si and Nb by RHEED and XPS depth profile	48/49 (1991) 450	Ga)As/GaAs strained-layer multiple quantum wells with high-resolution X-ray diffraction and computer simu-	70 (1001) 00
H. Kezuka and T. Masaki, Characterization of the surface of high-T <sub>c</sub> Y-Ba-Cu-O	48/49 (1991) 454	P. Auvray, A. Poudoulec, M. Baudet, B. Guenais, A. Regreny, C. d'Anter-	50 (1991) 92
Superlattices		roches and J. Massies, Interface roughness of GaAs/AlAs super- lattices MBE-grown on vicinal surfaces	50 (1991) 109
S. Goto, H. Kakibayashi, M. Kawata and T. Usagawa, Evaluation of disordering		M. Mendik, M. Ospelt, H. von Känel and P. Wachter, Determination of elastic	(2002)

properties of Si/Ge superlattices and Si <sub>1-x</sub> Ge <sub>x</sub> films from surface acoustic modes by Brillouin scattering  B. Jusserand and F. Mollot, Confined optical vibrations: a new probe for alloy disorder	50 (1991) 303 50 (1991) 317	<ul> <li>K.E. Smith, G.S. Elliott and S.D. Kevan, The role of non-adiabaticity and two- dimensional Fermi surfaces in the re- construction of Mo(001) and W(001)</li> <li>T. Hariu, S. Yamauchi, H. Tanaka and S. Ono, Interface characterization of ZnSe/GaAs heterojunctions</li> </ul>	48/49 (1991) 135 48/49 (1991) 204
Surface and interface states		T. Hibma, H.H. Weitering, D.R. Heslinga and T.M. Klapwijk, Interface struc-	14, 16 (2114, 211
W. Mönch, Mechanisms of barrier forma- tion in Schottky contacts: metal-in- duced surface and interface states	41/42 (1989) 128	ture and Schottky barriers of epitaxial Pb on Si(111) D. Heskett, D. Tang, A.B. McLean, R.	48/49 (1991) 209
F. Flores, A. Muñoz and J.C. Durán, Semiconductor interface formation: the role of the induced density of in-	, (2,2,, 22,	Ludeke, M. Prietsch, T. Maeda Wong, E.W. Plummer and N.J. DiNardo, Metal-induced states on the GaAs-	
terface states  R. Ludeke, A. Taleb-Ibrahimi and G.	41/42 (1989) 144	<ul><li>(110) surface probed by angle-resolved photoemission spectroscopy</li><li>G. Vecris and J.J. Quinn, Novel diagram-</li></ul>	48/49 (1991) 260
Jezequel, Delocalization of defects: a new model for the Schottky barrier H. Fujitani and S. Asano, Electronic	41/42 (1989) 151	matic method for analyzing the surface electronic modes of finite multilayer structures	48/49 (1991) 319
structure of Si/disilicide interfaces L. Haderbache, P. Wetzel, C. Pirri, J.C. Peruchetti, D. Bolmont and G.	41/42 (1989) 164	L. Roberts and G.J. Hughes, An investigation of metal/GaAs(100) interfaces	
Gewinner, Identification of three distinct $CoSi_2(111)(1 \times 1)$ surface struc-	41/42 (1989) 257	by deep level transient spectroscopy  Surface composition	50 (1991) 424
J.F. Morar, U.O. Karlsson, R.I.G. Uhr-	41/42 (1989) 237	Surface composition	
berg, J. Kanski, P.O. Nilsson and H. Qu, Angle-resolved photoemission study of the As/Ge(100) interface	41 /42 (1080) 212	S.C. Tjong, Electrochemical and surface analysis of the Fe-Cr-Ru system in non-oxidizing acid solutions	44 (1990) 7
F.J. Himpsel, T.F. Heinz, A.B. McLean and E. Palange, Bonding at silicon/in-	41/42 (1989) 312	J. Lausmaa, B. Kasemo and H. Mattsson, Surface spectroscopic characterization	44 (1990)
sulator interfaces C.A. Sébenne, J.P. Lacharme, I. Andria- manantenasoa and M. Khial, Local	41/42 (1989) 346	of titanium implant materials  J.P. Baltrus and A. Proctor, Composition of overlayers on oxidized pyrite sur-	44 (1990) 133
roughness and surface states on		faces	44 (1990) 147
Si(001): analysis of vacuum anneal- ings and oxygen adsorption—desorp- tion processes H. Hasegawa, H. Ohno, H. Ishii, T. Haga,	41/42 (1989) 352	S. Suzuki and M. Oku, Surface orientation dependence of the surface composition in an Fe-20%Cr alloy and an Fe-3%Si alloy treated by mechanical	
Y. Abe and H. Takahashi, Origin and properties of interface states at insulator-semiconductor and semiconduc-		polishing and chemical etching S.L.T. Andersson and J.C. Otamiri, Surface and bulk composition of	44 (1990) 151
tor-semiconductor interfaces of com- pound semiconductors T. Saitoh, H. Hasegawa, S. Konishi and	41/42 (1989) 372	YBa <sub>2</sub> Cu <sub>3</sub> O <sub>6+x</sub> compounds studied by XPS W.A.M. Aarnink, A. Weishaupt and A.	45 (1990) 1
H. Ohno, A computer simulation of the recombination process at com- pound semiconductor surfaces and		van Silfhout, Angle-resolved X-ray photoelectron spectroscopy (ARXPS) and a modified Levenberg-Marquardt	
hetero-interfaces Y. Yasuda, S. Zaima and M. Sakashita, Studies on charge trapping and inter-	41/42 (1989) 402	fit procedure: a new combination for modeling thin layers A.R. Gonzalez-Elipe, J.P. Espinos, A.	45 (1990) 37
face state generation in MOS capaci- tors at low temperatures  D. Haneman and N. McAlpine, Light	41/42 (1989) 420	Fernandez and G. Munuera, XPS study of the surface carbonation/hydroxylation state of metal oxides	45 (1990) 103
emission from Si cleaved and gas- covered surfaces	48/49 (1991) 111	S. Deckers, F.H.P.M. Habraken, W.F. van der Weg, A.W. Denier van der Gon,	

J.F. van der Veen and J.W. Geus, Oxidation-induced segregation at the		a probe for process-induced defects in silicon	46 (1990) 446
Pt <sub>0.5</sub> Ni <sub>0.5</sub> (111) surface studied by medium-energy ion scattering S.C. Tjong, A surface study of the passi-	45 (1990) 121	P. Ashu and C.C. Matthai, A molecular dynamics study of the critical thick- ness of Ge layers on Si substrates	48/49 (1991) 39
vation of Fe-Cr-Co magnet alloys in sulphuric acid solution	45 (1990) 141		, (2)
D. Ballutaud, P. de Mierry, M. Aucouturier and E. Darque-Ceretti, Influence		Surface diffusion	
of thermal treatments on the distribu- tion of contaminating copper near the surface of silicon: a comparative SIMS	47 (1991) 1	Y. Sasajima, Y. Suzuki, M. Takeuchi and S. Ozawa, New approach for a com- puter simulation of the vacuum de-	
and XPS study S.J. Hoekje and G.B. Hoflund, Surface characterization study of InP(100) substrates using ISS, AES and ESCA:	47 (1991)	position process  Surface energy	48/49 (1991) 498
comparison of substrates from two different commercial sources	47 (1991) 43		
M.M. Hills and G.S. Arnold, Chemical treatment of fused silica with xenon		P. Ashu and C.C. Matthai, A molecular dynamics study of the critical thick- ness of Ge layers on Si substrates	48/49 (1991) 39
difluoride B. Heens, Ch. Grégoire, J.J. Pireaux, P.A.	47 (1991) 77		, (2.2.2, 2.2
Cornelio and J.A. Gardella, Jr., On the stability and homogeneity of Lan-		Surface morphology	
gmuir-Blodgett films as models of polymers and biological materials for surface studies: an XPS study	47 (1991) 163	T. Ito, A. Yamama, A. Hiraki and M. Satou, Silicidation of porous silicon and its application for the fabrication	
T.M. Razykov, Chemical molecular beam deposition of II–VI binary and ternary	40.440.4100100	of a buried metal layer  S. Nadahara, J. Shiozawa, K. Imai, K.	41/42 (1989) 301
A. Ermolieff, F. Martin, A. Amouroux, S. Marthon and J.F.M. Westendorp,	48/49 (1991) 89	Suguro and K. Yamabe, Protuberance growth at polysilicon surfaces during	
Surface composition analysis of HF vapour cleaned silicon by X-ray pho-	49 /40 /1001\ 179	oxidation  T. Sasaki, T. Matsuoka and A. Katsui,  MOVPE-grown GaN on polar planes	41/42 (1989) 425
D.G. Ren, Study of interface structure of the oxide grown on nickel alloys by	48/49 (1991) 178	of 6H-SiC  K. Fukushima and I. Yamada, Surface smoothness and crystalline structure	41/42 (1989) 504
AP-FIM  I. Katayama, T. Hanawa, F. Shoji and K.  Oura, ISS-AES study of the initial growth stage of Cu thin films on Si(111)-7 × 7	48/49 (1991) 227 48/49 (1991) 361	of ICB deposited TiO <sub>2</sub> films  D. Milne, J.I.B. Wilson, T.T. Rantala and J. Lenkkeri, Morphological and structural changes in laser CVD of silicon:	43 (1989) 32
K. Nishimori, H. Tokutaka, T. Tamon, S. Kishida and N. Ishihara, Surface study of single-crystal 80 K Bi-Sr-Ca-Cu-	46/47 (1771) 301	comparison of theoretical temperature calculations with experimental results B. Woratschek, P.G. Carey, M. Stolz and	43 (1989) 81
O superconductor with Si and Nb by RHEED and XPS depth profile H. Kezuka and T. Masaki, Characteriza-	48/49 (1991) 450	F.G. Bachmann, Excimer laser plan- arization of AlSi, AlSiTi and AlSiCu alloys	43 (1989) 264
tion of the surface of high- $T_c$ Y-Ba-Cu-O	48/49 (1991) 454	<ul> <li>J.M. Gómez-Rodríguez, A.M. Baró and</li> <li>V.P. Parkhutik, Morphology of porous silicon studied by STM/SEM</li> <li>A. Sajjadi, K. Kuen-Lau, F. Saba, F.</li> </ul>	44 (1990) 185
Surface defects		Beech and I.W. Boyd, Laser-ablation deposition of uniform thin films of	46 (1000) 04
A. Esser, W. Kütt, M. Strahnen, G. Maidorn and H. Kurz, Femtosecond		Bi <sub>2</sub> Sr <sub>2</sub> CaCu <sub>2</sub> O <sub>x</sub> W. Kesting, T. Bahners and E. Schollmeyer, Controlled structuring of poly-	46 (1990) 84
transient reflectivity measurements as		mer surfaces by UV-laser irradiation	46 (1990) 326

<ul> <li>M. Elliq, E. Fogarassy, J.P. Stoquert, C. Fuchs, S. de Unamuno, B. Prévot and H. Pattyn, Pulsed excimer and Nd:YAG laser crystallization of a-</li> </ul>		D. Lee, S.J. Barnett, A.D. Pitt, M.R. Houlton and G.W. Smith, Characterization of alloy composition in $Ga_{1-x}Al_xAs/GaAs$ structures: com-	
Si:H. The specific role of hydrogen I. Zouari, M. Calvo, F. Lapicque and M. Cabrera, Morphological improvement of zinc electrodeposits by laser assis-	46 (1990) 378	parison of photovoltage, X-ray, SIMS and RHEED techniques  A. Castaldini, A. Cavallini, E. Gombia, R. Mosca and L. Tarricone, Evaluation	50 (1991) 428
H. Strecker and G. Persch, Scanning tun- neling microscopy and technical appli-	46 (1990) 411	of the diffusion length of minority car- riers in bulk GaAs	50 (1991) 485
cations  E.J. Puik, M.J. van der Wiel, H. Zeijle- maker and J. Verhoeven, Ion etching	46 (1990) 441	Surface plasmons	
of thin W layers: enhanced reflectivity of W-C multilayer coatings R. Bartlett, H. Jaeger, B.A. Sexton, R.P.	47 (1991) 63	A. Förster, J.M. Layet and H. Lüth, Evaluation of dopant profiles and dif- fusion constants by means of electron energy loss spectroscopy	41/42 (1989) 306
Netterfield and P.J. Martin, A scan- ning tunnelling and transmission elec- tron microscopy comparison of the surface structure of evaporated and		T.S. Jones, M.Q. Ding, N.V. Richardson and C.F. McConville, The effects of surface damage on surface plasmon	41/42 (1989) 300
ion-assisted gold films  P. Ashu and C.C. Matthai, A molecular dynamics study of the critical thick-	47 (1991) 187	excitations in doped InSb(100)	45 (1990) 85
ness of Ge layers on Si substrates M. Kimura, A. Tanaka and T. Sukegawa,	48/49 (1991) 39	Surface roughness	
Dissolution process of silicon in an indium solution  I. Katayama, T. Hanawa, F. Shoji and K.	48/49 (1991) 185	E. Vlieg and J.F. van der Veen, X-ray scattering studies of semiconductor in- terfaces: atomic structure and mor-	
Oura, ISS-AES study of the initial growth stage of Cu thin films on $Si(111)-7 \times 7$	48/49 (1991) 361	phology  J. Falta, M. Horn and M. Henzler, SPA- LEED studies of defects in thin epi- taxial NiSi <sub>2</sub> layers on Si(111)	41/42 (1989) 62 41/42 (1989) 230
Surface phonons and adsorbate vibra	ations	C.A. Sébenne, J.P. Lacharme, I. Andria- manantenasoa and M. Khial, Local roughness and surface states on Si(001): analysis of vacuum anneal-	
G. Radhakrishnan, W. Stenzel, H. Conrad and A.M. Bradshaw, Photoreac-	46 (1990) 36	ings and oxygen adsorption-desorp- tion processes	41/42 (1989) 352
tions of adsorbed CH <sub>3</sub> Br on Pt(111)  A.I. Agafonov and T.M. Makhviladze, Mechanisms of photon-stimulated de- sorption and chemisorption of atomic	46 (1990) 36	<ul> <li>Y. Borensztein, T. Lopez-Rios and G.</li> <li>Vuye, Roughness induced at Si(111) surfaces by high temperature heating</li> <li>T. Yamashina and T. Hino, Plasma-</li> </ul>	41/42 (1989) 439
particles on the surfaces of semiconductors and metals	46 (1990) 288	surface interactions of graphite as nuclear fusion material	48/49 (1991) 483
M. Mendik, M. Ospelt, H. von Känel and P. Wachter, Determination of elastic properties of Si/Ge superlattices and $Si_{1-x}Ge_x$ films from surface acoustic		<ul> <li>P.F. Fewster, Multicrystal X-ray diffraction of heteroepitaxial structures</li> <li>P. Auvray, A. Poudoulec, M. Baudet, B. Guenais, A. Regreny, C. d'Anter-</li> </ul>	50 (1991) 9
modes by Brillouin scattering	50 (1991) 303	roches and J. Massies, Interface roughness of GaAs/AlAs super- lattices MBE-grown on vicinal surfaces	50 (1991) 109
Surface photovoltage		C. Frigeri, J.L. Weyher and M. De Potter, TEM study of the origin of the surface	30 (1991) 109
D. Mao, A. Kahn, M. Marsi and G. Margaritondo, Synchrotron radiation induced surface photovoltage at metal/GaAs interfaces	48/49 (1991) 324	microroughness in DSL photoetched Si-implanted GaAs wafers R.A.D. Mackenzie, J.A. Liddle and C.R.M. Grovenor, Ultrahigh resolu-	50 (1991) 115

tion characterisation of compound semiconductors using pulsed laser atom probe techniques	50 (1991) 196	P.J. Godowski, Analysis of surface segre- gation in Co-Ru alloy using Auger electron spectroscopy	47 (1991) 333
Surface segregation		Surface stress	
S. Akhter, K.C. Cannon and J.M. White, Distribution of compositional defects in solvent cast polyvinyl alcohol films: angular dependent XPS and reactivity		Y. Matsuda, K. Fujita and S. Hinotani, Raman studies on GaAs epitaxial films on Si	48/49 (1991) 231
study P. Lejček, M. Koutník, J. Brádler, V.	44 (1990) 49	Surface structure	
Paidar and A. Potměšilová, Anisotropy of grain boundary segregation in as-grown Fe-6at%Si alloy bi-		<ul><li>K. Nishimori, H. Tokutaka, Z. Okinaga,</li><li>S. Kishida and N. Ishihara, Observa-</li></ul>	
crystals  S. Suzuki and M. Oku, Surface orientation dependence of the surface composition in an Fe-20%Cr alloy and an	44 (1990) 75	tion of Si and SiC surface structures using the magnetic LEED method E. Vlieg and J.F. van der Veen, X-ray scattering studies of semiconductor in-	41/42 (1989) 49
Fe-3%Si alloy treated by mechanical polishing and chemical etching  S. Priggemeyer, A. Brockmeyer, H.	44 (1990) 151	terfaces: atomic structure and mor- phology R.S. Williams, R.S. Daley, J.H. Huang	41/42 (1989) 62
Dötsch, H. Koschmieder, D.J. O'Con- nor and W. Heiland, The segregation of Pb on yttrium-iron-garnet (YIG) surfaces studied by ion scattering		and R.M. Charatan, Initial stages of metal/semiconductor interface formation: Au and Ag on Si(111)  S. Kono, Y. Enta, T. Abukawa, T.	41/42 (1989) 70
spectrometry (ISS)  M.J. van Staden and J.P. Roux, Surface segregation in the alloys Fe40Cr3Ru, Fe40Cr3Pt and Fe40Cr with a 1000 Å	44 (1990) 255	Kinoshita and T. Sakamoto, Photo- electron spectroscopy and photoelec- tron diffraction studies of Si(001) 2 × 1-K and -Cs surfaces	41/42 (1989) 75
Pt overlayer  A. Elbiache and P. Marcus, Adsorption and surface segregation of sulphur on	44 (1990) 271	A. Ichimiya, S. Kohmoto, T. Fujii and Y. Horio, RHEED intensity analysis of $Si(111)\sqrt{3} \times \sqrt{3}$ -Ag structure	41/42 (1989) 82
Fe-17Cr-12.6Ni(100) and Fe-17Cr-14.5Ni-2.3Mo(100) alloys	45 (1990) 49	F. Salvan, F. Thibaudau and Ph. Dumas, STM studies of metal-semiconductor interface formation	41/42 (1989) 88
S. Deckers, F.H.P.M. Habraken, W.F. van der Weg, A.W. Denier van der Gon, J.F. van der Veen and J.W. Geus,		T. Urano, M. Kaburagi, S. Hongo and T. Kanaji, LEED $I-V$ curve analysis for	41/42 (1909) 00
Oxidation-induced segregation at the Pt <sub>0.5</sub> Ni <sub>0.5</sub> (111) surface studied by medium-energy ion scattering	45 (1990) 121	the structure of iron films on Si(111) surfaces S. Kohmoto, S. Mizuno and A. Ichimiya,	41/42 (1989) 103
D. Ballutaud, P. de Mierry, M. Aucouturier and E. Darque-Ceretti, Influence of thermal treatments on the distribution of contaminating copper near the		RHEED intensity analysis of Li/Si(111) structures  J.F. Morar, U.O. Karlsson, R.I.G. Uhrberg, J. Kanski, P.O. Nilsson and H. Qu, Angle-resolved photoemission	41/42 (1989) 107
surface of silicon: a comparative SIMS and XPS study  J.J. Vajo and J.G. McCarty, Thermody- namics of carbon coadsorbed with	47 (1991) 1	study of the As/Ge(100) interface  K. Akimoto, J. Mizuki, I. Hirosawa and J.  Matsui, Interfacial superstructures	41/42 (1989) 312
sulfur on Ni(100) H.J. Grabke, D. Wiemer and H. Viefhaus, Segregation of sulfur during growth of	47 (1991) 23	studied by grazing incidence X-ray diffraction K. Takayanagi, Y. Tanishiro, T. Ishitsuka	41/42 (1989) 317
oxide scales S.C. Tjong and H.C. Swart, Auger characterization of the surface oxidation	47 (1991) 243	and K. Akiyama, In-situ UHV elec- tron microscope study of metal-sili- con surfaces	41/42 (1989) 337
of austenitic Fe-26Mn-7Al-0.9C alloy	47 (1991) 311	X.D. Peng and M.A. Barteau, Characterization of the crystallographic structure	71/72 (1707) 331

of MgO thin films by ISS on the basis of trajectory-dependent neutralization  A. Vázquez, J.M. Domínguez and S. Fuentes, Thermally induced modifications on the crystal surface of molybdate-type catalysts  T.S. Jones, M.Q. Ding, N.V. Richardson and C.F. McConville, The effects of	44 (1990) 87 44 (1990) 331	G.N. Pain, T. Warminski, S. Sulcs, M.S. Kwietniak, D. Gao, S.R. Glanvill, C.J. Rossouw, A.W. Stevenson, S.P. Russo, R.G. Elliman, L.S. Wielunski, R.S. Rowe, G.B. Deacon, R.S. Dickson and B.O. West, Characterization of low-temperature MOCVD Cd <sub>1-x</sub> Mn <sub>x</sub> Te thin films	48/49 (1991) 76
surface damage on surface plasmon excitations in doped InSb(100)  A. Mowbray and R.G. Jones, Homo- and	45 (1990) 85	Thallium	46/42 (1771) 70
hetero-iodide thin film growth on InSb(001): low-temperature iodide formation and epitaxial growth of		S. Bharathi, V. Yegnaraman and G. Prabhakara Rao, Alloy formation in the monolayers of underpotentially	
<ul> <li>CdI<sub>2</sub></li> <li>N. Ohshima, Y. Koide, S. Zaima and Y.</li> <li>Yasuda, Formation of a superstruc-</li> </ul>	48/49 (1991) 27	deposited lead and thallium C.H. Champness and W.R. Clark, Anom-	47 (1991) 293
ture in the initial stage of Ge epitaxial growth on Si(100) substrates  D. Haneman and N. McAlpine, Light	48/49 (1991) 69	alous inductive effect in Se-metal contacts	48/49 (1991) 337
emission from Si cleaved and gas-		Thermal desorption	
covered surfaces  K.E. Smith, G.S. Elliott and S.D. Kevan, The role of non-adiabaticity and two- dimensional Fermi surfaces in the re-	48/49 (1991) 111	G.C. Tyrrell, I.W. Boyd and R.B. Jackman, Ion beam assisted etching of silicon with bromine. The role of the	
construction of Mo(001) and W(001) G. Shimaoka, MEED studies of thin metal film covered semiconductor surfaces	48/49 (1991) 135 48/49 (1991) 190	adsorbed state  M. Bowker and D. Halstead, Adsorption studies on catalysts. II. Application to	43 (1989) 439
B.V. King, D.J. O'Connor, Y. Shen, R.J. MacDonald, M. Katayama and M. Aono, LEIS for structure determina-		rapid adsorbers – oxygen on Euro- platinum 1  B. Oral, Y.C. Lee and R.W. Vook, Ther- mal desorption spectroscopy investi-	44 (1990) 1
tion of surfaces and thin films	48/49 (1991) 246	gation of CO adsorption on Cu/ Pd(111) surfaces	44 (1990) 65
Surface thermodynamics		XL. Zhou, C. Yoon and J.M. White, Interactions of PF <sub>3</sub> and PD <sub>3</sub> with clean,	44 (1990) 63
<ul> <li>J.J. Vajo and J.G. McCarty, Thermodynamics of carbon coadsorbed with sulfur on Ni(100)</li> <li>B. Biliński, W. Wójcik and A.L. Dawi-</li> </ul>	47 (1991) 23	P-covered and H(D)-covered (100)- oriented W foil J.A. Kelber, J.W. Rogers, Jr., B.A. Banse and B.E. Koel, Interaction of dimeth-	44 (1990) 103
dowicz, Investigation of the surface free energy components of thermally treated controlled porosity glasses by inverse gas chromatography	47 (1991) 99	ylamine with clean and partially oxi- dized copper surfaces  J.H. Craig, Jr. and J. Lozano, Effect of oxygen on chemisorption of CO on	44 (1990) 193
	,	Rh(100) R.M. Wallace, C.C. Cheng, P.A. Taylor,	45 (1990) 151
Tantalum		W.J. Choyke and J.T. Yates, Jr., Ni	
F. Shoji, A. Ogawa and K. Oura, Sputter-deposition by a new Penning- discharge source with an axially in- tegrated hot-cathode	48/49 (1991) 373	impurity effects on hydrogen surface chemistry and etching of Si(111) W.G. Durrer, J.H. Craig, Jr. and J. Lozano, Surface carbon and its effects	45 (1990) 201
Tellurium	, (1771) 313	on hydrogen adsorption on Rh(100) G. Radhakrishnan, W. Stenzel, H. Conrad and A.M. Bradshaw, Photoreac-	45 (1990) 275
O. Bostanjoglo and P. Thomsen-Schmidt, Time-resolved TEM of laser-induced		tions of adsorbed CH <sub>3</sub> Br on Pt(111) M.M. Hills and G.S. Arnold, Chemical treatment of fused silica with xenon	46 (1990) 36
structural changes in GeTe films	46 (1990) 392	difluoride	47 (1991) 77

D. Vassilakis C. M. Bradier V. Berthier		R. Putzar, HC. Petzold and H. Staiger,	
D. Vassilakis, CM. Pradier, Y. Berthier and J. Oudar, Hydrogen, hydrogen sulfide and hydrocarbon coadsorption		Optimization of the laser-induced de- position technique for its application	
on Pt(111) and Pt(110): selective for- mation of alkylthiols	47 (1991) 273	in X-ray mask repair Y. Shigesato, S. Takaki and T. Haranou,	46 (1990) 131
K. Kalki, B. Pennemann, U. Schröder, W. Heichler and K. Wandelt, Properties of noble metal and binary alloy mono-		Crystallinity and electrical properties of tin-doped indium oxide films de- posited by DC magnetron sputtering	48/49 (1991) 269
layer films on Ru(001) S.S. Fu and G.A. Somorjai, Zinc oxide and oxygen overlayers on Cu(110): a	48/49 (1991) 59	B. Mari, A. Segura and A. Chevy, Electri- cal properties of neutron-transmuta- tion-doped InSe	50 (1991) 415
model for Cu-Zn-O catalysts	48/49 (1991) 93	, ,	00 (2772) 120
H.H. Madden and R. Imbihl, Interaction of NO and H <sub>2</sub> with Pt(100)	48/49 (1991) 130	Tin oxide	
V.A. Ukraintsev, B.S. Podolsky and A.A. Chernov, Water adsorption kinetics on Si(111)-7 × 7: defect generation mech-		Y. Nakanishi, Y. Suzuki, T. Nakamura, Y. Hatanaka, Y. Fukuda, A. Fujisawa	
anism T. Yamashina and T. Hino, Plasma- surface interactions of graphite as	48/49 (1991) 151	and G. Shimaoka, Coloration of Sn-Sb-O thin films	48/49 (1991) 55
nuclear fusion material	48/49 (1991) 483	Titanium	
Thin films		F. Richter, E. Bugiel, R. Grötzschel, H.	
S. Metev and K. Meteva, Nucleation and growth of laser-plasma deposited thin		Reichardt, A. Schöpke, E. Wieser and F. Wolf, Formation of titanium disilicide using different annealing	
films J. Rickards, A. Oliver, J. Miranda and	43 (1989) 402	methods	44 (1990) 127
E.P. Zironi, Uses of PIXE at low proton energies	45 (1990) 155	J. Lausmaa, B. Kasemo and H. Mattsson, Surface spectroscopic characterization	
I. Kusunoki, M. Hiroi, T. Sato, Y. Igari	43 (1990) 133	of titanium implant materials J.C. Ingram, K.W. Nebesny and J.E.	44 (1990) 133
and S. Tomoda, SiC film formation on Si(001) by reaction with $C_2H_2$ beams	45 (1990) 171	Pemberton, Optical properties of selected first-row transition metals de-	
J. Lausmaa, B. Kasemo, H. Mattsson and H. Odelius, Multi-technique surface		termined by reflection electron energy loss spectroscopy	45 (1990) 247
characterization of oxide films on electropolished and anodically oxi-		J. Hermann, C. Boulmer-Leborgne and B. Dubreuil, Spectroscopic study of the	
dized titanium  J. Eymery, C. Senillou, J.C. Joud and A.	45 (1990) 189	plasma created by interaction between	
Chamberod, An Auger depth profile analysis of a sputtered Fe-Ti multi-		a TEA CO <sub>2</sub> laser beam and a Ti target in a cell containing helium gas	46 (1990) 315
layer structure	47 (1991) 127	E. D'Anna, G. Leggieri, A. Luches, M. Martino, A.V. Drigo, G. Majni, P.	
H. Roulet, G. Dufour, A. Cheenne, F. Rochet and C. Cartier, Physicoche-		Mengucci and I.N. Mihailescu, Nitri- dation of titanium by multipulse ex-	
mistry of laser-deposited BiSrCaCuO thin films studied by XPS and XAS	47 (1991) 173	cimer laser irradiation  J. Eymery, C. Senillou, J.C. Joud and A.	46 (1990) 365
Tin		Chamberod, An Auger depth profile analysis of a sputtered Fe-Ti multi-	47 (1001) 107
G. Massouras, J.A. Roger, G. Fuchs, A.		layer structure S. Berger, Y. Komem and B.Z. Weiss, On	47 (1991) 127
Perez and L. Romana, Fluence depen- dence of ion beam induced atomic mixing in the immiscible tin-silicon		the microstructure, composition and electrical properties of Al/TiW/poly-Si system	48/49 (1991) 281
system F. Abel, C. Cohen, J.A. Davies, J. Moulin	43 (1989) 213	P. Roura, J.R. Morante, G. Bremond, T. Benyattou, G. Guillot and W. Ulrici,	()
and D. Schmaus, Thin-film growth of Sn on Cu(100)	44 (1990) 17	Complete identification of the Ti-re- lated levels in GaP	50 (1991) 496

Titanium dioxide		S.Yu. Shapoval, O.E. Balvinskii, I.V. Malikov, A.A. Chumakov and L.A.	
K. Fukushima and I. Yamada, Surface smoothness and crystalline structure		Niselson, Chemical vapour deposition of tungsten layers at low substrate	
of ICB deposited TiO <sub>2</sub> films	43 (1989) 32	temperatures A.J.P. van Maaren, R.L. Krans and W.C. Sinke, HF formation in laser-induced	45 (1990) 257
Titanium oxide		CVD of tungsten V. Dupuis, M.F. Ravet C. Tête and M.	46 (1990) 138
J. Lausmaa, B. Kasemo and H. Mattsson, Surface spectroscopic characterization of titanium implant materials	44 (1990) 133	Piecuch, Thermal evolution of W/Si and W/C multilayers under pulsed laser heating and classical annealing	46 (1990) 398
R.V. Siriwardane and J.A. Poston, Inter- action of H <sub>2</sub> S with zinc titanate in the		J. Marfaing, W. Marine, B. Vidal, M. Toulemonde, M. Hage Ali and J.P.	(,
presence of H <sub>2</sub> and CO  J. Lausmaa, B. Kasemo, H. Mattsson and H. Odelius, Multi-technique surface	45 (1990) 131	Stoquert, Instability and structural transformation of amorphous ultra- thin W-Si multilayer structures dur-	
characterization of oxide films on electropolished and anodically oxi-	4. 4	ing heavy ion irradiation E.J. Puik, M.J. van der Wiel, H. Zeijle-	46 (1990) 422
dized titanium  F. Curcio, M. Musci, N. Notaro and G. De Michele, Synthesis of ultrafine	45 (1990) 189	maker and J. Verhoeven, Ion etching of thin W layers: enhanced reflectivity of W-C multilayer coatings	47 (1991) 63
TiO <sub>2</sub> powders by a CW CO <sub>2</sub> laser J.Ph. Nogier, J. Thoret, N. Jammul and J. Fraissard, Phase distribution in Ti-	46 (1990) 225	E.J. Puik, M.J. van der Wiel, H. Zeijle- maker and J. Verhoeven, Ion bom- bardment of X-ray multilayer coat-	
V-O catalysts H.L.M. Chang, H. You, J. Guo and D.J.	47 (1991) 287	ings: comparison of ion etching and ion assisted deposition	47 (1991) 251
Lam, Epitaxial TiO <sub>2</sub> and VO <sub>2</sub> films prepared by MOCVD  E. Gofuku, Y. Toyoda, Y. Uehara, M.	48/49 (1991) 12	K.E. Smith, G.S. Elliott and S.D. Kevan, The role of non-adiabaticity and two- dimensional Fermi surfaces in the re-	
Kohara and M. Nunoshita, Highly conductive TiO <sub>2</sub> thin films prepared		construction of Mo(001) and W(001) S. Berger, Y. Komem and B.Z. Weiss, On	48/49 (1991) 135
by EB-modification	48/49 (1991) 343	the microstructure, composition and electrical properties of Al/TiW/poly-Si system	48/49 (1991) 281
Tribology  S. Scaglione, D. Flori and G. Emiliani,		F. Shoji, A. Ogawa and K. Oura, Sputter-deposition by a new Penning- discharge source with an axially in-	
Modification of mechanical properties of e-gun evaporated MgF <sub>2</sub> and CaF <sub>2</sub>		tegrated hot-cathode J.S. Kim, P.K. Banerjee, S.S. Mitra, H.	48/49 (1991) 373
thin films under ion beam bombard- ment C. Neelmeijer, P. Knothe, M. Posselt, E.	43 (1989) 224	Shastry, J.J. Loferski and R. Beaulieu, Optical, electrical and mechanical properties of RF-sputtered TiN-W-	
Richter and KH. Heinig, Wear re- sistant coatings produced by C <sup>+</sup> im- plantation	43 (1989) 232	Au films W.M.R. Divigalpitiya, R.F. Frindt and	48/49 (1991) 548
H. Zaïdi, D. Paulmier and J. Lepage, The influence of the environment on the	43 (1707) 232	S.R. Morrison, Spread films of single molecular transition-metal sulphides	48/49 (1991) 572
friction and wear of graphitic carbons.  II. Gas coverage of wear debris	44 (1990) 221	Tunneling	
Tungsten		M.H. Hecht, L.D. Bell and W.J. Kaiser, Ballistic-electron-emission microscopy of subsurface defects at the Au-	
XL. Zhou, C. Yoon and J.M. White, Interactions of PF <sub>3</sub> and PD <sub>3</sub> with clean, P-covered and H(D)-covered (100)-		GaAs(100) interface  F. Salvan, F. Thibaudau and Ph. Dumas,  STM studies of metal-semiconductor	41/42 (1989) 17
oriented W foil	44 (1990) 103	interface formation	41/42 (1989) 88

J.M. Gómez-Rodríguez, A.M. Baró and		H.L.M. Chang, H. You, J. Guo and D.J.	
V.P. Parkhutik, Morphology of porous silicon studied by STM/SEM	44 (1990) 185	Lam, Epitaxial TiO <sub>2</sub> and VO <sub>2</sub> films prepared by MOCVD	48/49 (1991) 12
H. Strecker and G. Persch, Scanning tun-	44 (1990) 103	prepared by MOCVD	40/49 (1991) 12
neling microscopy and technical appli-		Water	
cations	46 (1990) 441	w ater	
B. Heens, Ch. Grégoire, J.J. Pireaux, P.A.		H. Zaïdi, D. Paulmier and J. Lepage, The	
Cornelio and J.A. Gardella, Jr., On		influence of the environment on the	
the stability and homogeneity of Lan-		friction and wear of graphitic carbons.	
gmuir-Blodgett films as models of polymers and biological materials for		II. Gas coverage of wear debris	44 (1990) 221
surface studies: an XPS study	47 (1991) 163	E. Occhiello, M. Morra, F. Garbassi, D.	
R. Bartlett, H. Jaeger, B.A. Sexton, R.P.	(/	Johnson and P. Humphrey, SSIMS	
Netterfield and P.J. Martin, A scan-		studies of hydrophobic recovery:	45 (1001) 205
ning tunnelling and transmission elec-		oxygen plasma treated PS	47 (1991) 235
tron microscopy comparison of the		V.A. Ukraintsev, B.S. Podolsky and A.A. Chernov, Water adsorption kinetics on	
surface structure of evaporated and	47 (1001) 107	Si(111)-7 $\times$ 7: defect generation mech-	
ion-assisted gold films A.H.M. Sondag, M.C. Raas and F.J.	47 (1991) 187	anism	48/49 (1991) 151
Touwslager, A comparison between			, , , , , , , , , , , , , , , , , , , ,
inelastic electron tunnelling and in-		Wetting	
frared reflection-absorption spec-		,, ,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	
troscopy for vibrational surface analy-		H. Hiraoka and S. Lazare, Surface mod-	
sis	47 (1991) 205	ifications of Kapton and cured poly-	
T. Hashizume, Y. Hasegawa and T.		imide films by ArF excimer laser: ap-	
Sakurai, Alkali-metal adsorption on		plications to imagewise wetting and	
silicon surfaces studied by field ion- scanning tunneling microscopy (FI-		metallization	46 (1990) 264
STM)	48/49 (1991) 119	E. Occhiello, M. Morra, F. Garbassi, D.	
,	, (2.2.2) 222	Johnson and P. Humphrey, SSIMS studies of hydrophobic recovery:	
Ultraviolet spectroscopy		oxygen plasma treated PS	47 (1991) 235
M. Sasaki, Y. Kawakyu, H. Ishikawa and		Work function	
M. Mashita, UV absorption spectra of		Work function	
adlayers of MOCVD source gases	41/42 (1989) 342	D.R. Baer, R.L. Gordon and C.W. Hub-	
K. Inoue, M. Okuyama and Y. Hamaka-		bard, Work function and UPS study	
wa, Optical and interfacial properties of SiO <sub>2</sub> films deposited on Si by		of Au and O on Re	45 (1990) 71
photo-CVD	41/42 (1989) 407	G.E. Rhead, On the work function varia-	(222)
photo CVB	41/ 42 (1909) 407	tions produced by the oxidation of	
Vanadium		adsorbed alkali metal layers	47 (1991) 35
		A. Mowbray and R.G. Jones, Homo- and	
S.C. Tjong and J.B. Malherbe, Auger		hetero-iodide thin film growth on	
studies of the effect of Mo, V and Pd		InSb(001): low-temperature iodide formation and epitaxial growth of	
additions on the oxidation characteris-		CdI,	48/49 (1991) 27
tics of Fe-24Cr alloy	44 (1990) 179	K. Kalki, B. Pennemann, U. Schröder, W.	10/ 17 (1771) 27
J.C. Ingram, K.W. Nebesny and J.E. Pemberton, Optical properties of		Heichler and K. Wandelt, Properties	
selected first-row transition metals de-		of noble metal and binary alloy mono-	
termined by reflection electron energy		layer films on Ru(001)	48/49 (1991) 59
loss spectroscopy	45 (1990) 247	H.H. Madden and R. Imbihl, Interaction of NO and H <sub>2</sub> with Pt(100)	48/49 (1991) 130
Vanadium oxida		2	()
Vanadium oxide		X-ray absorption	
J.Ph. Nogier, J. Thoret, N. Jammul and J.			
Fraissard, Phase distribution in Ti-		Y. Kawadzu, M. Iioka, A. Fujii, H.	
V-O catalysts	47 (1991) 287	Oyanagi and T. Arai, Interfacial reac-	

tion of nickel/hydrogenated amorphous silicon system at low temperature studied by fluorescence EXAFS	41/42 (1989) 296	van Silfhout and R. de Reus, Interdif- fusion studies on high- $T_c$ supercon- ducting YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-<math>\delta</math></sub> thin films on	47 (1001) 105
H. Roulet, G. Dufour, A. Cheenne, F. Rochet and C. Cartier, Physicochemistry of laser-deposited BiSrCaCuO		Si(111) with a NiSi <sub>2</sub> /ZrO <sub>2</sub> buffer layer J.Ph. Nogier, J. Thoret, N. Jammul and J. Fraissard, Phase distribution in Ti-	47 (1991) 195
thin films studied by XPS and XAS D.E. Ramaker, Evidence for vertical C <sub>2</sub> on Ni as a precursor for graphite nucleation	47 (1991) 173 48/49 (1991) 351	V-O catalysts Y.C. Sasaki and K. Hirokawa, New technique for evaluation of surfaces and interfaces at atmospheric pressure by	47 (1991) 287
		using refracted X-ray fluorescence	45 (1001) 051
X-ray diffraction		(RXF) C. Julien and M. Balkanski, Thin-film growth and structure for solid-state	47 (1991) 371
E. Vlieg and J.F. van der Veen, X-ray scattering studies of semiconductor interfaces: atomic structure and mor-		batteries H.L.M. Chang, H. You, J. Guo and D.J.	48/49 (1991) 1
phology M. Renda and K. Morita, Epitaxial	41/42 (1989) 62	Lam, Epitaxial TiO <sub>2</sub> and VO <sub>2</sub> films prepared by MOCVD  Y. Nakanishi, Y. Suzuki, T. Nakamura,	48/49 (1991) 12
growth of a mono-crystalline metasta- ble AuIn layer at the Au/InP(001)		Y. Hatanaka, Y. Fukuda, A. Fujisawa and G. Shimaoka, Coloration of Sn-	
interface	41/42 (1989) 216	Sb-O thin films	48/49 (1991) 55
K. Akimoto, J. Mizuki, I. Hirosawa and J. Matsui, Interfacial superstructures studied by grazing incidence X-ray	41 /42 /1090\ 217	G.N. Pain, T. Warminski, S. Sulcs, M.S. Kwietniak, D. Gao, S.R. Glanvill, C.J. Rossouw, A.W. Stevenson, S.P. Russo,	
diffraction S. Fujieda, K. Akimoto, I. Hirosawa, Y.	41/42 (1989) 317	R.G. Elliman, L.S. Wielunski, R.S. Rowe, G.B. Deacon, R.S. Dickson and	
Mochizuki, J. Mizuki, Y. Matsumoto and J. Matsui, Electrical properties		B.O. West, Characterization of low- temperature MOCVD $Cd_{1-x}Mn_xTe$	
and structures of the MOCVD-		thin films	48/49 (1991) 76
AlN/GaAs interface	41/42 (1989) 516	Y. Shigesato, S. Takaki and T. Haranou,	
T. Wada, M. Takeda, T. Yamada and M.		Crystallinity and electrical properties	
Ichimura, Formation of a $Ge_xSi_{1-x}$		of tin-doped indium oxide films de-	40 440 (1001) 040
alloy layer by high-energy electron-	41/42 (1989) 580	posited by DC magnetron sputtering	48/49 (1991) 269
beam irradiation  K. Fukushima and I. Yamada, Surface	41/42 (1909) 300	S. Berger, Y. Komem and B.Z. Weiss, On the microstructure, composition and	
smoothness and crystalline structure		electrical properties of Al/TiW/poly-	
of ICB deposited TiO <sub>2</sub> films	43 (1989) 32	Si system	48/49 (1991) 281
A. Seidel and G. Linker, Amorphization		C.H. Champness and W.R. Clark, Anom-	
mechanisms in Mn+-implanted thin Al		alous inductive effect in Se-metal	
films and single crystals	43 (1989) 97	contacts	48/49 (1991) 337
S. Yoshida, H. Ishida and J.S. Jen, X-ray		E. Gofuku, Y. Toyoda, Y. Uehara, M.	
photoelectron spectroscopic and X-ray diffractometric characterization of al-		Kohara and M. Nunoshita, Highly conductive TiO <sub>2</sub> thin films prepared	
kylimidazole films on copper oxide		by EB-modification	48/49 (1991) 343
and alkylimidazolato copper(II) com-		Zhang Rong, Zheng Youdou, Jiang	, , , , ,
plexes	44 (1990) 301	Ruolian, Hu Liqun, Zhong Peixin, Yu	
J. Simpson and J.O. Williams, Prefer-		Shidong, Li Qi, Feng Duan and Chen	
ential (111) orientation of ZnSe on		Guangxi, The structure of $Ge_xSi_{1-x}$	
(100) GaAs deposited by laser-in-	46 (1000) 27	Si strained layer superlattices and het-	40 (40 (1001) 25(
duced MOCVD	46 (1990) 27	erostructures	48/49 (1991) 356
<ul> <li>F. Schmaderer, R. Huber, H. Oetzmann and G. Wahl, High-T<sub>c</sub> YBa<sub>2</sub>Cu<sub>3</sub>O<sub>7-δ</sub></li> </ul>		S.C. Jain, A. Atkinson and W.S. Khokle, Relationship between mechanical,	
prepared by chemical vapour deposi-		electronic and vibrational properties	
tion	46 (1990) 53	of $Ge_xSi_{1-x}$ strained layers	48/49 (1991) 387
W.A.M. Aarnink, D.H.A. Blank, D.J. Adelerhof, J. Flokstra, H. Rogalla, A.		N. Hamaguchi, R. Gardiner and P.S. Kirlin, MOCVD of TlBaCaCuO su-	

perconducting thin films: structure-		zation of alloy composition in	
property-processing relationships	48/49 (1991) 441	$Ga_{1-x}Al_xAs/GaAs$ structures: com-	
S. Kishida, H. Tokutaka, H. Higashi, K.		parison of photovoltage, X-ray, SIMS	
Nishimori and N. Ishihara, Prepara-		and RHEED techniques	50 (1991) 428
tion conditions of flat 80 K phase		D. Ashenford, J.H.C. Hogg, B. Lunn and	
Bi-Sr-Ca-Cu-O thin films by RF		C.G. Scott, The relationship between	
magnetron sputtering	48/49 (1991) 446	electrical and structural characteristics	
R.B. Gore, R.K. Pandey and S.R. Kumar,		of CdTe and CdMnTe layers grown	
Preparation and characterisation of		on InSb	50 (1991) 440
nearly stoichiometric CdTe films from		D.A. Woolf, D.I. Westwood, M.A. Ander-	
a non-aqueous electrodeposition bath	48/49 (1991) 530	son and R.H. Williams, The molecular	
W.M.R. Divigalpitiya, R.F. Frindt and		beam epitaxial growth of $GaAs(\overline{111})$	
S.R. Morrison, Spread films of single		Si(111): a variable growth temperature	
molecular transition-metal sulphides	48/49 (1991) 572	study	50 (1991) 445
J. Matsui, Study of strain variation in	40/ 47 (1771) 312	B. Holländer, S. Mantl, B. Stritzker, F.	30 (1))1) 443
LEC-grown GaAs bulk crystals by		Schäffler, HJ. Herzog and E. Kasper,	
synchrotron radiation X-ray topogra-	50 (1001) 1	Strain and defect densities in Si/	
phy	50 (1991) 1	$Si_{1-x}Ge_x$ heterostructures investigated	
P.F. Fewster, Multicrystal X-ray diffrac-		by ion scattering and X-ray diffrac-	
tion of heteroepitaxial structures	50 (1991) 9	tion	50 (1991) 450
J.H.C. Hogg, D. Shaw and D.M. Staudte,		R. Schwarz, T. Fischer, P. Hanesch, T.	
Modelling interdiffusion in epitaxial		Muschik, J. Kolodzey, H. Cerva, H.L.	
multilayer structures using X-ray		Meyerheim and B.M.U. Scherzer,	
simulation techniques	50 (1991) 87	Limitations of interface sharpness in	
R. Zaus, M. Schuster, H. Göbel and JP.		a-Si:H/a-SiC:H multilayers	50 (1991) 456
Reithmaier, Characterization of (In,		C. De las Heras, I.J. Ferrer and C.	
Ga)As/GaAs strained-layer multiple		Sánchez, Comparison of pyrite thin	
quantum wells with high-resolution		films obtained from Fe and natural	
X-ray diffraction and computer simu-		pyrite powder	50 (1991) 505
lations	50 (1991) 92	13	()
N. Herres, G. Bender and G. Neumann,	()	V	
Assessment of mismatched epitaxial		X-ray emission	
layers by X-ray rocking curve mea-			
surements and simulations	50 (1991) 97	M. Iwami, M. Kusaka, M. Hirai and H.	
A.M. Keir, S.J. Barnett, J. Giess, T.D.	30 (1991) 97	Nakamura, A new non-destructive	
		analysis of semiconductor heterojunc-	
Walsh and M.G. Astles, A combina-		tions with very thin surface layers: an	
tion of high-resolution X-ray dif-		application of soft X-ray spectroscopy	
fractometry and diffraction imaging		to Si-compound (film)/Si (substrate)	41/42 (1989) 57
techniques applied to the study of		J. Rickards, A. Oliver, J. Miranda and	/
MOVPE-grown $Cd_xHg_{1-x}Te/CdTe$		E.P. Zironi, Uses of PIXE at low pro-	
on GaAs	50 (1991) 103	ton energies	45 (1990) 155
P. Auvray, A. Poudoulec, M. Baudet, B.		I. Dalins, M. Karimi and D. Ila, Violent	43 (1770) 133
Guenais, A. Regreny, C. d'Anter-		oxidation of lithium-containing alumi-	
roches and J. Massies, Interface			49 /40 (1001) 500
roughness of GaAs/AlAs super-		num alloys in liquid oxygen	48/49 (1991) 509
lattices MBE-grown on vicinal surfaces	50 (1991) 109		
P.L. Swart, B.M. Lacquet and R. Thavar,		X-ray scattering	
Physical characterization of OMVPE-			
grown Al <sub>x</sub> Ga <sub>1-x</sub> As multi-layer films		H. Sugahara and J. Nagano, Thermal sta-	
by means of non-destructive optical		bility of WSiN-GaAs and Au-WSiN	
reflectometry	50 (1991) 330	interfaces	41/42 (1989) 207
S.C. Moss, J.F. Knudsen, R.C. Bowman,	(1771) 550	G. Bomchil, A. Halimaoui and R. Herino,	.1/ 12 (1707) 207
Jr., P.M. Adams and D.D. Smith, Pi-		Porous silicon: the material and its	
cosecond transient photoreflectance	50 (1991) 337	applications in silicon-on-insulator technologies	41 /42 (1000) (04
measurements of ion-implanted GaAs	10119911111	technologies	41/42 (1989) 604
I loo C I Down off A I Did I I	30 (1))1) 331		, (,
D. Lee, S.J. Barnett, A.D. Pitt, M.R. Houlton and G.W. Smith, Characteri-	30 (1771) 337	M. Gendry, J. Durand, M. Erman, J.B. Theeten, L. Nevot and B. Pardo,	, (,

Chemical and structural analysis by ellipsometry and X-ray reflectometry of thin sulfide layers grown on InP V. Dupuis, M.F. Ravet, C. Tête and M.	44 (1990) 309	profiling techniques: a SIMS, ECV and AES study  A.W.R. Leitch, Th. Prescha and M. Stutzmann, Hydrogen passivation and re-	50 (1991) 138
Piecuch, Thermal evolution of W/Si and W/C multilayers under pulsed		activation of shallow Zn acceptors in GaAs	50 (1991) 390
laser heating and classical annealing E.J. Puik, M.J. van der Wiel, H. Zeijle- maker and J. Verhoeven, Ion etching of thin W layers: enhanced reflectivity	46 (1990) 398	HG. Hettwer, W. Lerch, B. Lentfort, N.A. Stolwijk and H. Mehrer, Com- bined application of spreading-resis- tance and electron-microprobe depth	
of W-C multilayer coatings  E.J. Puik, M.J. van der Wiel, H. Zeijlemaker and J. Verhoeven, Ion bom-	47 (1991) 63	profiling on GaAs:Zn and Si:P	50 (1991) 470
bardment of X-ray multilayer coat- ings: comparison of ion etching and		Zinc oxide	
ion assisted deposition	47 (1991) 251		
•		A.R. de Wit, M.D. Janssen and J.J. Kelly, Electrochemical characterization of	
Yttrium		polycrystalline ZnO layers R.V. Siriwardane and J.A. Poston, Inter-	45 (1990) 21
S. Priggemeyer, A. Brockmeyer, H. Dötsch, H. Koschmieder, D.J. O'Con-		action of H <sub>2</sub> S with zinc titanate in the presence of H <sub>2</sub> and CO	45 (1990) 131
nor and W. Heiland, The segregation of Pb on yttrium-iron-garnet (YIG) surfaces studied by ion scattering		G. Moretti, S. De Rossi and G. Ferraris, Characterization of well dispersed copper species on the surface of ZnO	
spectrometry (ISS)	44 (1990) 255	by X-ray photoelectron spectroscopy	45 (1990) 341
W.J. Quadakkers, J. Jedlinski, K. Schmidt, M. Krašovec, G. Borchardt and H.		S.S. Fu and G.A. Somorjai, Zinc oxide and oxygen overlayers on Cu(110): a	
Nickel, The effect of implanted yt- trium on the growth and adherence of		model for Cu-Zn-O catalysts  T. Zhang and S.Y. Wei, Hydrogen chem-	48/49 (1991) 93
alumina scales on Fe-20Cr-5Al	47 (1991) 261	isorption on contaminated composite catalysts	48/49 (1991) 139
Zinc			
I Zanari M Calus E Laninasa and M		Zirconium	
I. Zouari, M. Calvo, F. Lapicque and M. Cabrera, Morphological improvement			
of zinc electrodeposits by laser assis-		Y. Igarashi, T. Yamaji, S. Nishikawa and	
tance T.M. Razykov, Chemical molecular beam	46 (1990) 411	S. Ohno, Influence of annealing ambients on ZrSi <sub>2</sub> formation	41/42 (1989) 282
deposition of II-VI binary and ternary		C.O. de González and E.A. García, De-	41/42 (1707) 202
compound films in a gas flow Y. Nakanishi, Y. Fukuda, Y. Hatanaka	48/49 (1991) 89	termination of the diffusion coeffi- cients of oxygen in zirconium by	
and G. Shimaoka, The dependence of		means of XPS	44 (1990) 211
the polycrystalline structure and elec- troluminescent properties of ZnS:Mn		E.M. Perry, D.L. Cocke and M.K. Miller, The oxidation of Ni <sub>3</sub> Zr investigated	
deposited on Y2O3 films on thickness	48/49 (1991) 297	by atom-probe field-ion microscopy	44 (1000) 223
J.G. Bauer, R. Treichler, T. Hillmer, J. Müller and G. Ebbinghaus, Optimiza-		and X-ray photoelectron spectroscopy LU.A. Andersen and J. Bøttiger, Crys-	44 (1990) 321
tion of Zn dopant profiles in a pin-di- ode/FET by combination of depth		tallization of Fe-Zr metallic glasses during ion irradiation	46 (1990) 427

# List of terms used in the subject index

Adhesion

Adsorption isotherms

Alkali halides

Alkali metals

Alloys

Aluminium

Aluminium oxide

Amorphous materials

Annealing

Antimony

Argon

Arsenic

Atomic and molecular beam studies

Auger electron spectroscopy

Band structure

Benzene

**Bismuth** 

**Borides** 

Boron

Cadmium

Cadmium selenide

Cadmium sulphide

Cadmium telluride

Calcium

Carbides

Carbon

Carbon dioxide

Carbon monoxide

Catalysis

Cathodes

Ceramics

Chalcogenides

Chemical vapour deposition

Chemisorption theory

Chromium

Clusters

Coatings

Cobalt

Compound formation

Conductivity

Contacts

Copper

Corrosion

Crystallization

Cyclotron resonance studies

Deuterium

Diamond

Diffusion

Doping effects

Electrical measurements

Electrical properties

Electron bombardment

Electron diffraction

Electron emission

Electron energy loss spectroscopy

Electron microscopy

Electron scattering

Electron spin resonance

Electron stimulated desorption

Ellipsometry

**Epitaxy** 

Etching

Ethylene

Evaporation

Field ion microscopy

**Fluorides** 

Gallium antimonide

Gallium arsenide

Gallium phosphide

Germanium

Glass

Gold

Grain boundaries

Graphite

Halides
Hall effect
Halogens
Halogenides
Heterostructures
Hydrogen

Hydrogen sulphide

Indium
Indium antimonide
Indium arsenide
Indium oxide
Indium phosphide

Infrared spectroscopy
Insulator-semiconductor interfaces

Interfaces

Ion bombardment
Ion implantation
Ion scattering
Iridium
Iron

Lanthanides Laser processing

Lead

Light scattering

Lithium

Luminescence

Magnesium

Magnesium oxide

Magnetic measurements Magnetic structures

Manganese

Mass spectroscopy

Melting Mercury Metals

Metal-semiconductor interfaces

MIS (metal-insulator-semiconductor) structure

Molybdenum

Molybdenum oxide

MOS (metal-oxide-semiconductor) structure

Neutron scattering

Nickel Niobium Nitric oxide Nitrides Nitrogen Nitrous oxide Noble gases Nucleation

Optical properties Organic substances

Organometallic vapour deposition

Oxidation Oxides Oxygen

Palladium Phosphine Phosphorus Photoconductivity Photodesorption

Photoelectron spectroscopy

Photon emission Piezoelectric effect Plasma processing

Platinum Polymers

Quantum effects

Radiation damage Raman scattering Raman spectroscopy Reflection spectroscopy

Rhenium Rhodium Ruthenium

Schottky barrier

Secondary ion mass spectroscopy Second harmonic generation

Selenium

Semiconductors

Semiconductor-semiconductor interfaces

Silane Silicides Silicon

Silicon carbide Silicon nitride Silicon oxide

Silver

Solar cells

Solid phase epitaxy

Sputter deposition

Sputtering

Steel

Sulphides

Sulphur

Superconductivity

Superlattices

Surface and interface states

Surface composition

Surface defects

Surface diffusion

Surface energy

Surface morphology

Surface phonons and adsorbate vibrations

Surface photovoltage

Surface plasmons

Surface roughness

Surface segregation

Surface stress

Surface structure

Surface thermodynamics

Tantalum

Tellurium

Thallium

Thermal desorption

Thin films

Tin

Tin oxide

Titanium

Titanium dioxide

Titanium oxide

Tribology

Tungsten

Tunneling

Ultraviolet spectroscopy

Vanadium

Vanadium oxide

Water

Wetting

Work function

X-ray absorption

X-ray diffraction

X-ray emission

X-ray scattering

Yttrium

Zinc

Zinc oxide

Zirconium

# Introduction to Zeolite Science and Practice

edited by H. van Bekkum, TU Delft, Delft, The Netherlands, E.M. Flanigen, UOP, Tarrytown, NY, USA and J.C. Jansen, TU Delft, Delft, The Netherlands

(Studies in Surface Science and Catalysis, 58)

Zeolites and related molecular sieves have quickly become important pathways to new opportunities in the fields of oil processing and petrochemical synthesis. The signs of intense activity in both industry and academia are evident: burgeoning papers and patent applications; increasing numbers of industrial zeolite-based processes and their rapid expansion into organic chemicals manufacturing; recent progress in zeolite accessibility range, matrix behaviour, lattice components and satellite structures; and the recognition that zeolites, which are stable and can be regenerated, may be incorporated into new, environmentally friendly processes.

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- [3] F.J. Himpsel, Surf. Sci. Rep. 12 (1990) 1.
- [4] A. Roth, Vacuum Technology, 3rd ed. (North-Holland, Amsterdam, 1990).
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# applied surface science

# **MASTER INDEX**

Volumes 41-50

Author index	1
Subject index	36
List of terms used in the subject index	134